Processing Data Where It Makes Sense in Modern Computing Systems: Enabling In-Memory Computation

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24 June 2018
Design Automation Summer School @ DAC 2018

Systems@ETH zürich
SAFARI

Brief Self Introduction

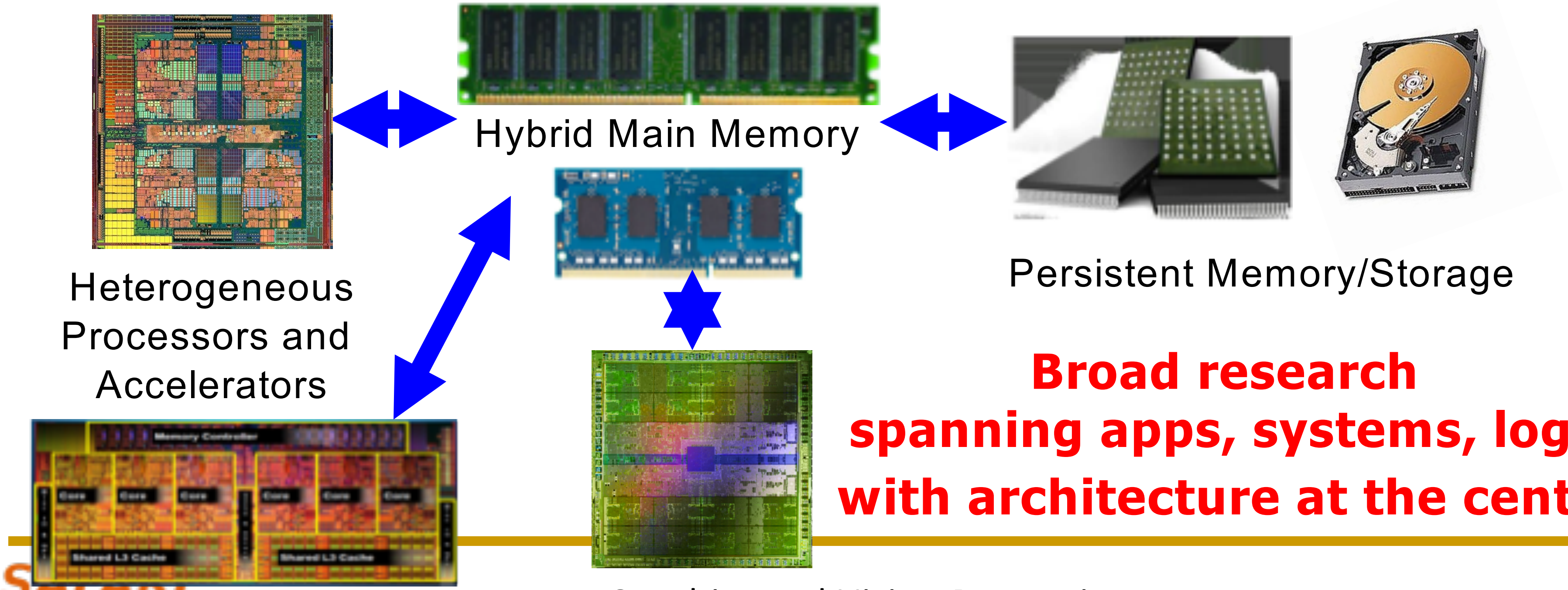
- Onur Mutlu
  - Full Professor @ ETH Zurich CS, since September 2015
  - Strecker Professor @ Carnegie Mellon University ECE/CS, 2009-2016, 2016-…
  - PhD from UT-Austin, worked at Google, VMware, Microsoft Research, Intel, AMD
  - https://people.inf.ethz.ch/omutlu/
  - omutlu@gmail.com (Best way to reach me)
  - https://people.inf.ethz.ch/omutlu/projects.htm

- Research and Teaching in:
  - Computer architecture, computer systems, hardware security, bioinformatics
  - Memory and storage systems
  - Hardware security, safety, predictability
  - Fault tolerance
  - Hardware/software cooperation
  - Architectures for bioinformatics, health, medicine
  - …

Current Research Focus Areas

Research Focus: **Computer architecture, HW/SW, bioinformatics, security**

- *Memory and storage (DRAM, flash, emerging), interconnects*
- *Heterogeneous & parallel systems, GPUs, systems for data analytics*
- *System/architecture interaction, new execution models, new interfaces*
- *Hardware security, energy efficiency, fault tolerance, performance*
- *Genome sequence analysis & assembly algorithms and architectures*
- *Biologically inspired systems & system design for bio/medicine*



Hybrid Main Memory

Persistent Memory/Storage

Heterogeneous Processors and Accelerators

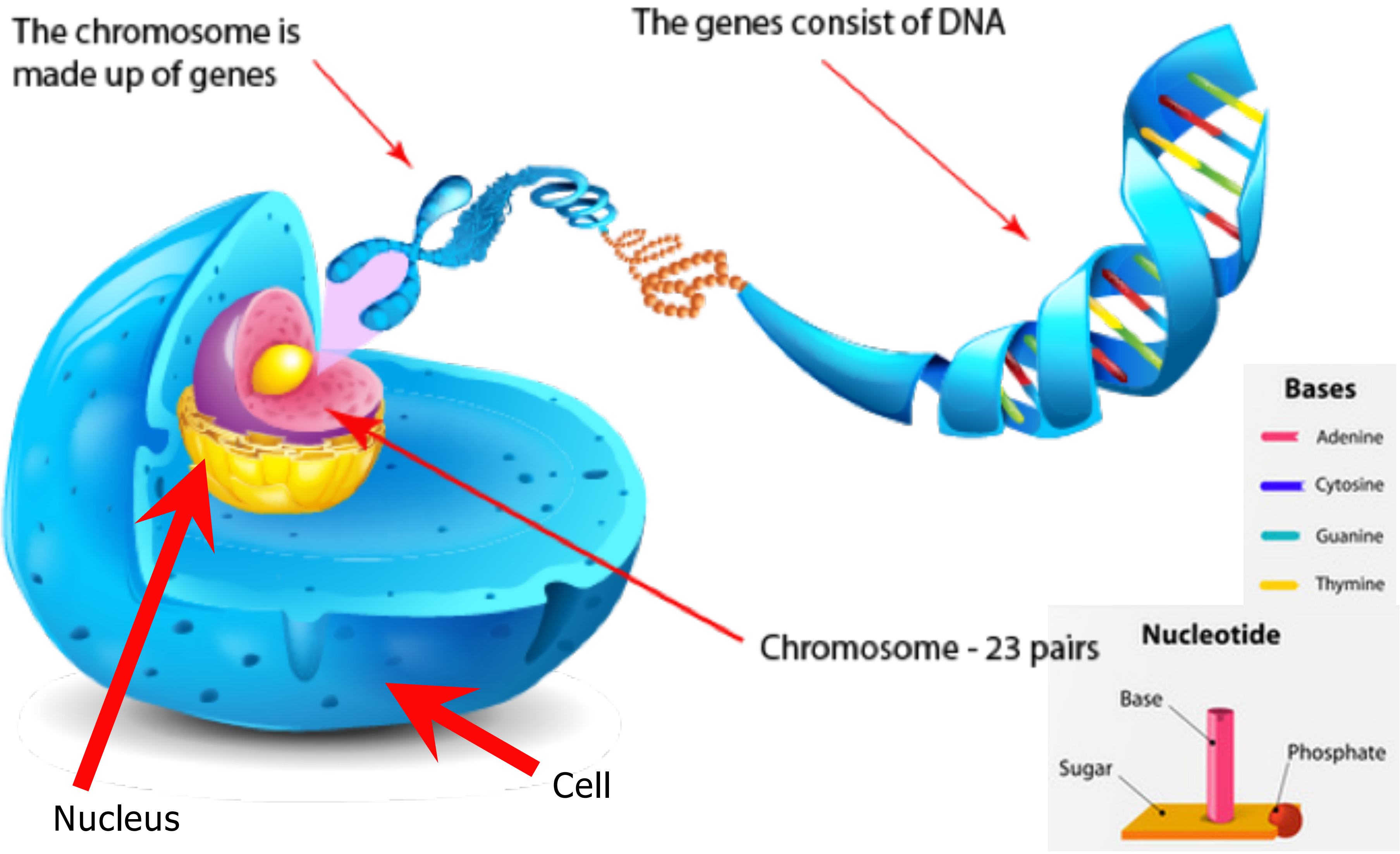
Graphics and Vision Processing

Broad research spanning apps, systems, logic with architecture at the center

Four Key Directions

- Fundamentally Secure/Reliable/Safe Architectures
- Fundamentally Energy-Efficient Architectures
  - Memory-centric (Data-centric) Architectures
- Fundamentally Low-Latency Architectures
- Architectures for Genomics, Medicine, Health

What Is a Genome Made Of?



The chromosome is made up of genes

The genes consist of DNA

Chromosome - 23 pairs

Nucleus

Cell

SAFARI The discovery of DNA’s double-helical structure (Watson+, 1953)

DNA Sequencing

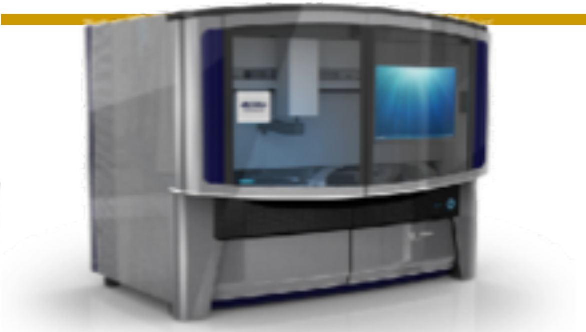
- Goal:
  - Find the complete sequence of A, C, G, T’s in DNA.

- Challenge:
  - There is no machine that takes long DNA as an input, and gives the complete sequence as output
  - All sequencing machines chop DNA into pieces and identify relatively small pieces (but not how they fit together)

Untangling Yarn Balls & DNA Sequencing

Genome Sequencers

Roche/454



AB SOLiD

Illumina MiSeq

Complete Genomics

Oxford Nanopore MinION

Illumina NovaSeq 6000

Illumina HiSeq2000

Pacific Biosciences RS

Oxford Nanopore GridION

Ion Torrent PGM

Ion Torrent Proton

… and more! All produce data with different properties.

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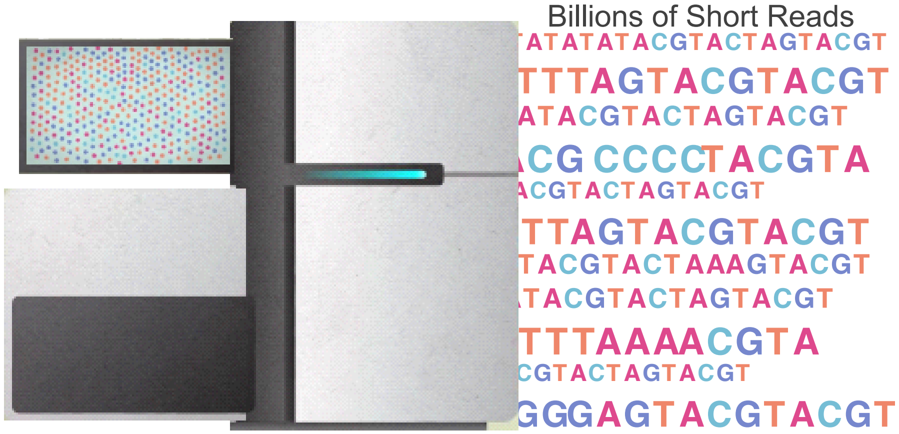
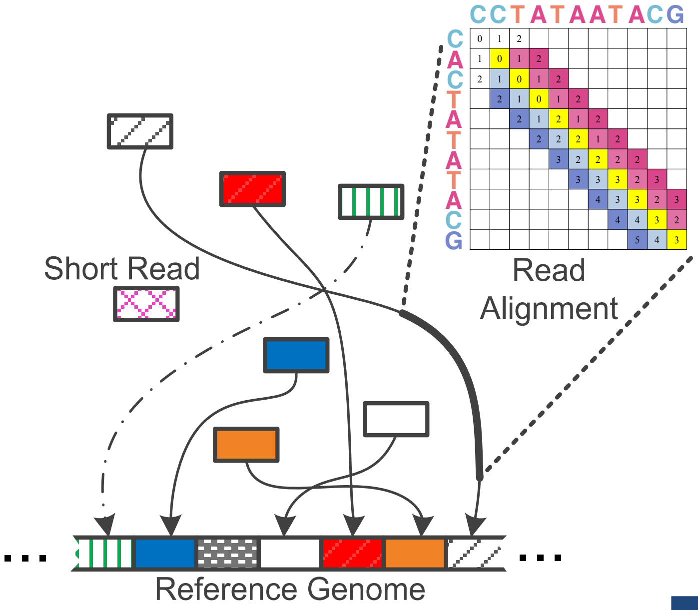


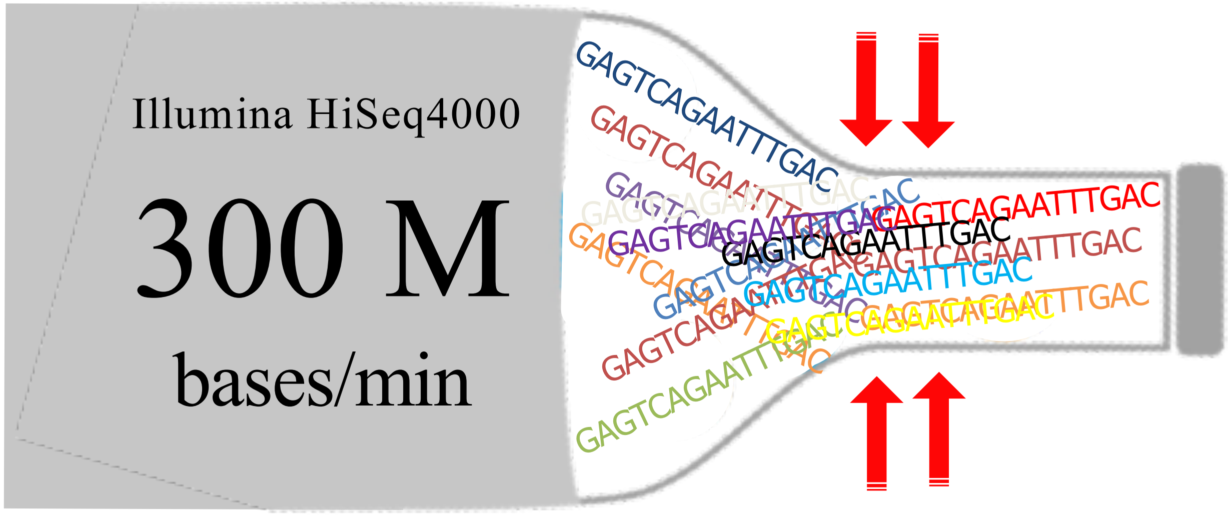
1 Sequencing



	C	C	T	A	T	A	A	T	A	C	G
C	0	1	2								
A	1	0	1	2							
C	2	1	0	1	2						
T		2	1	0	1	2					
A			2	1	2	1	2				
T				2	2	2	1	2			
A					3	2	2	2	2		
T						3	3	3	2	3	
A							4	3	3	2	3
C								4	4	3	2
G									5	4	3

Read Mapping 2

Bottlenecked in Mapping!!



Illumina HiSeq4000

300 M

bases/min

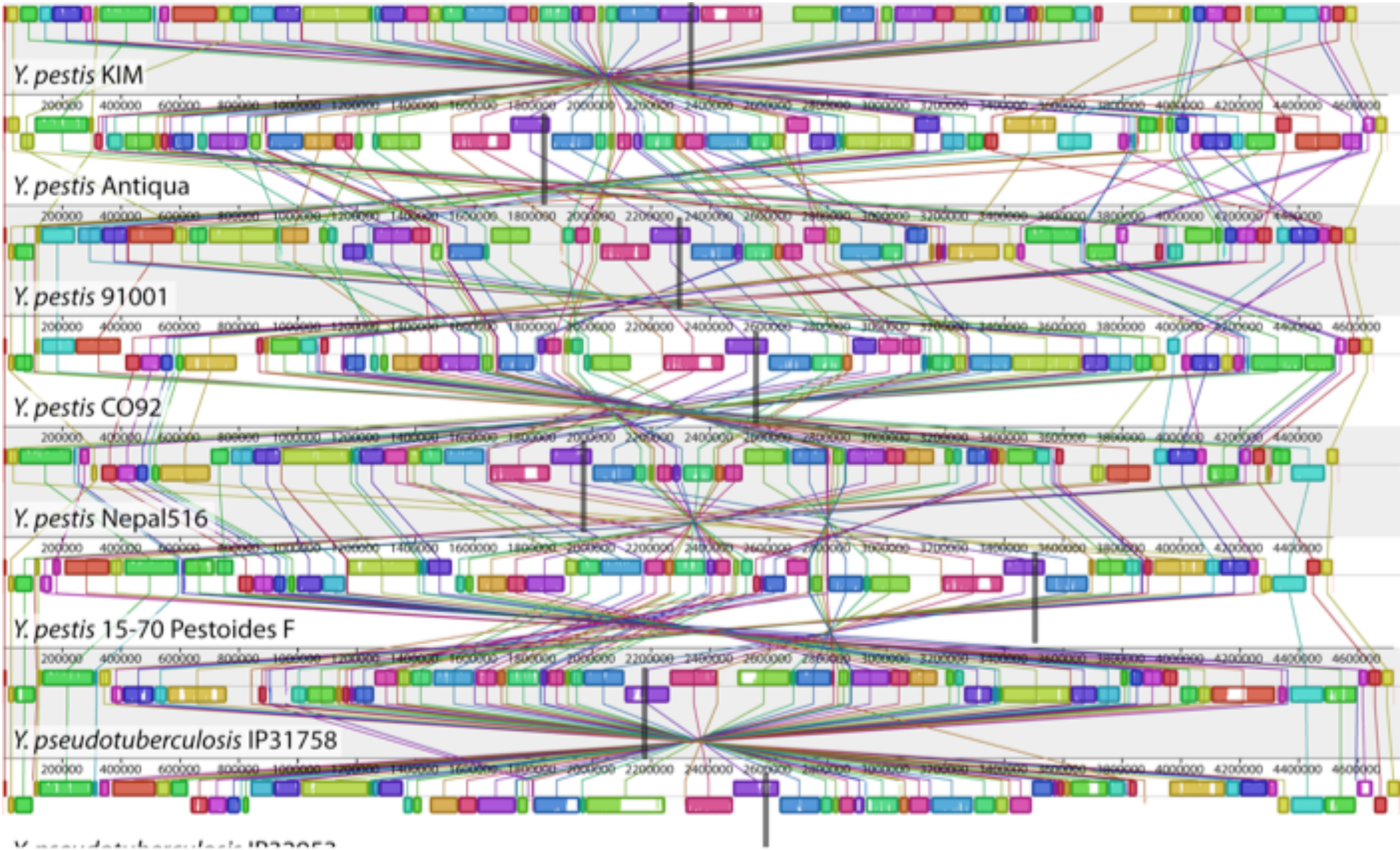
on average

2 M

bases/min

(0.6%)

Genome Sequence Alignment: Example



Source: By Aaron E. Darling, István Miklós, Mark A. Ragan - Figure 1 from Darling AE, Miklós I, Ragan MA (2008). "Dynamics of Genome Rearrangement in Bacterial Populations". PLOS Genetics. DOI:10.1371/journal.pgen.1000128., CC BY 2.5, https://commons.wikimedia.org/w/index.php?curid=30550950

Advantages of Hash Table Based Mappers

- + Guaranteed to find *all* mappings → sensitive
- + Can tolerate up to *e* errors

nature genetics

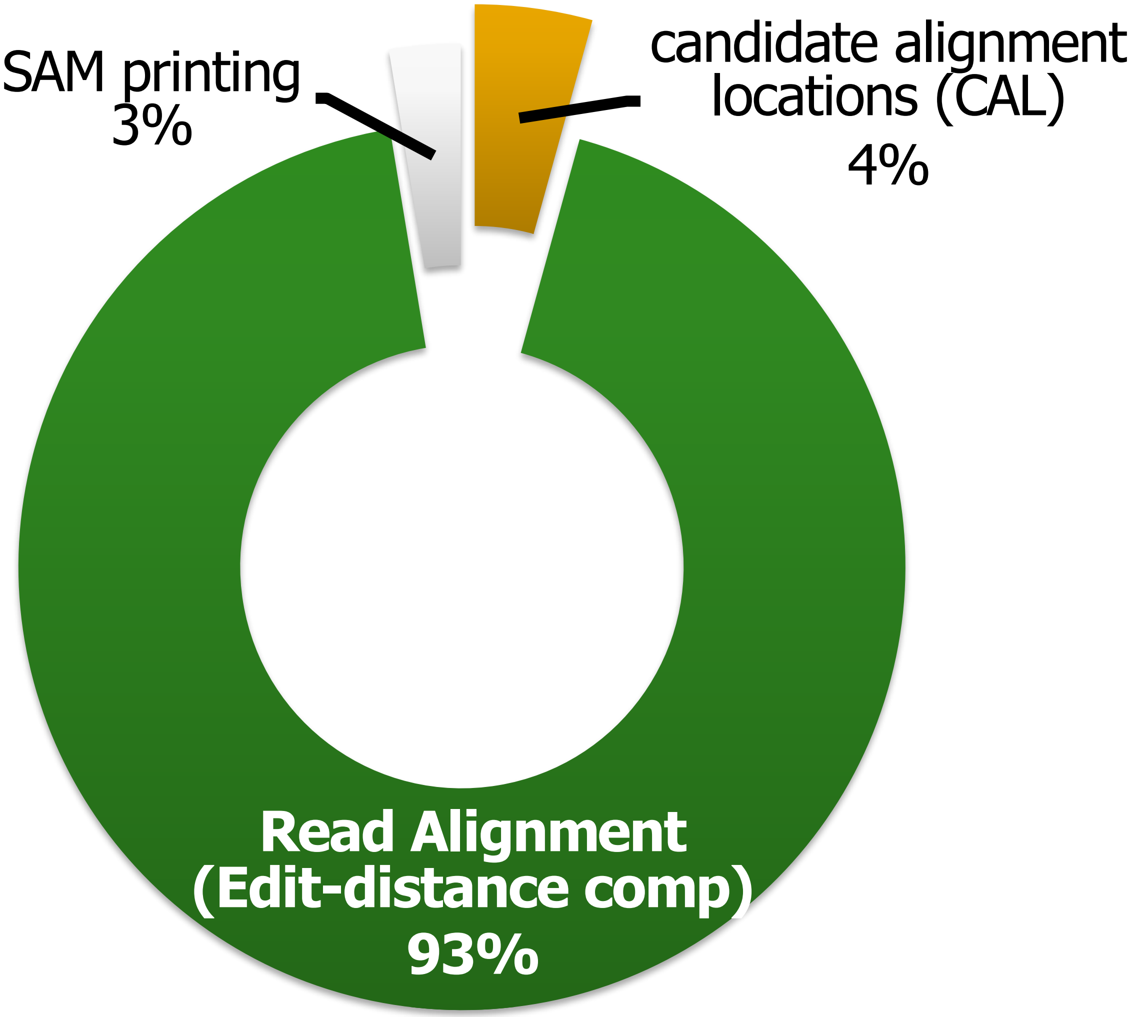
http://mrfast.sourceforge.net/

Personalized copy number and segmental duplication maps using next-generation sequencing

Can Alkan[1,2], Jeffrey M Kidd[1], Tomas Marques-Bonet[1,3], Gozde Aksay[1], Francesca Antonacci[1], Fereydoun Hormozdiari[4], Jacob O Kitzman[1], Carl Baker[1], Maika Malig[1], Onur Mutlu[5], S Cenk Sahinalp[4], Richard A Gibbs[6] & Evan E Eichler[1,2]

Alkan+, **"Personalized copy number and segmental duplication maps using next-generation sequencing"**, Nature Genetics 2009.

Read Mapping Execution Time Breakdown



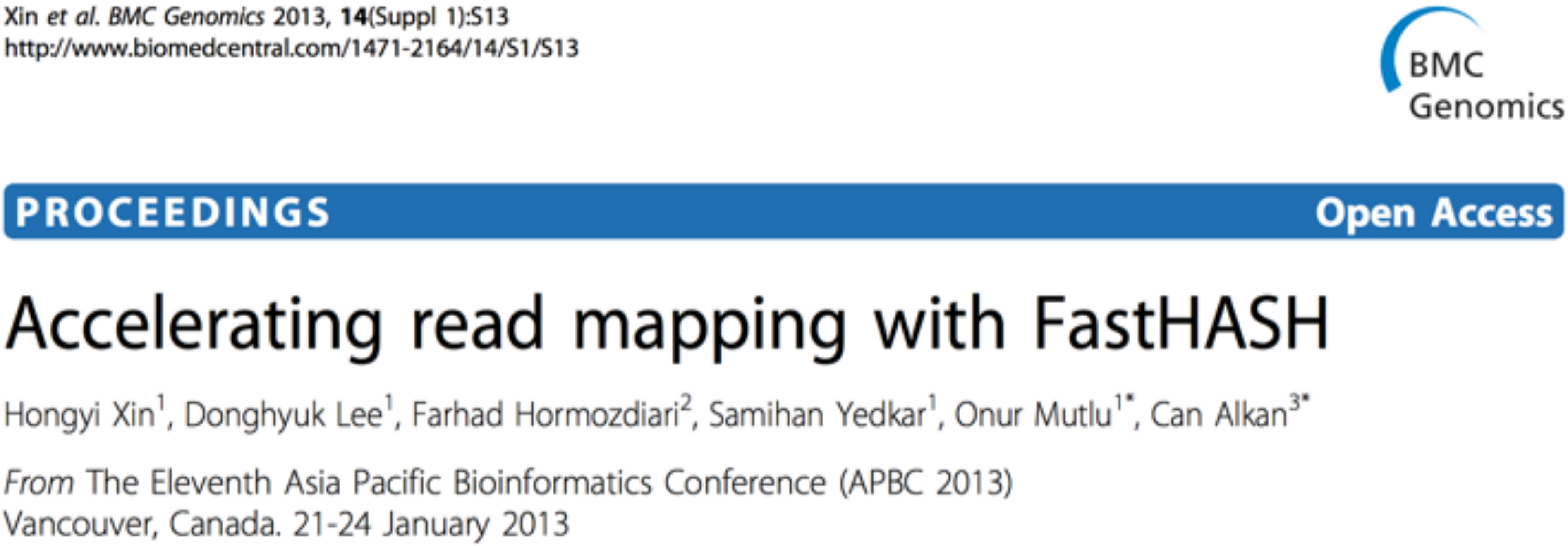
Idea

Filter fast before you align

Minimize costly
"approximate string comparisons"

Our First Filter: Pure Software Approach

- Download source code and try for yourself
  - Download link to FastHASH



Xin *et al. BMC Genomics* 2013, **14**(Suppl 1):S13
http://www.biomedcentral.com/1471-2164/14/S1/S13

BMC Genomics

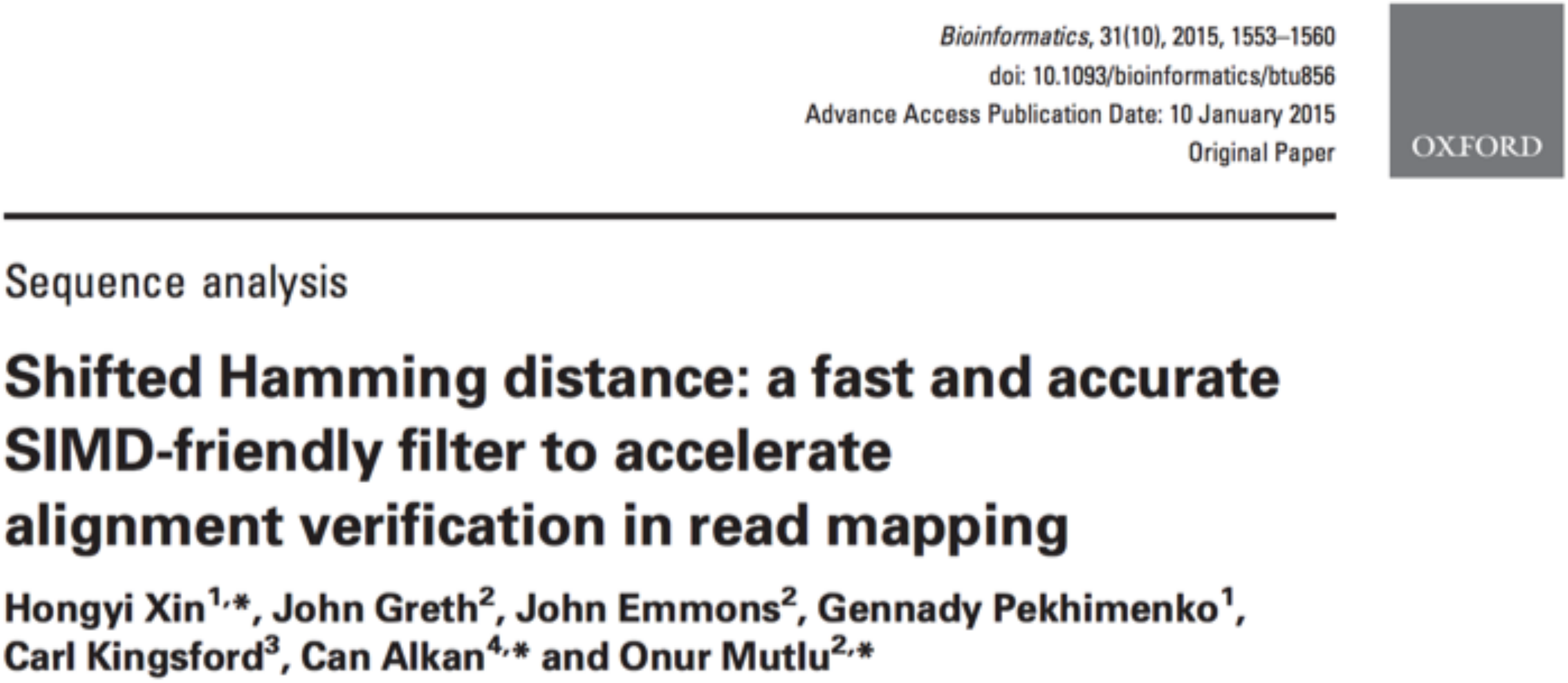
PROCEEDINGS **Open Access**

Accelerating read mapping with FastHASH

Hongyi Xin[1], Donghyuk Lee[1], Farhad Hormozdiari[2], Samihan Yedkar[1], Onur Mutlu[1*], Can Alkan[3*]

From The Eleventh Asia Pacific Bioinformatics Conference (APBC 2013)
Vancouver, Canada. 21-24 January 2013

Shifted Hamming Distance: SIMD Acceleration



Bioinformatics, 31(10), 2015, 1553–1560
doi: 10.1093/bioinformatics/btu856
Advance Access Publication Date: 10 January 2015
Original Paper

Sequence analysis

Shifted Hamming distance: a fast and accurate SIMD-friendly filter to accelerate alignment verification in read mapping

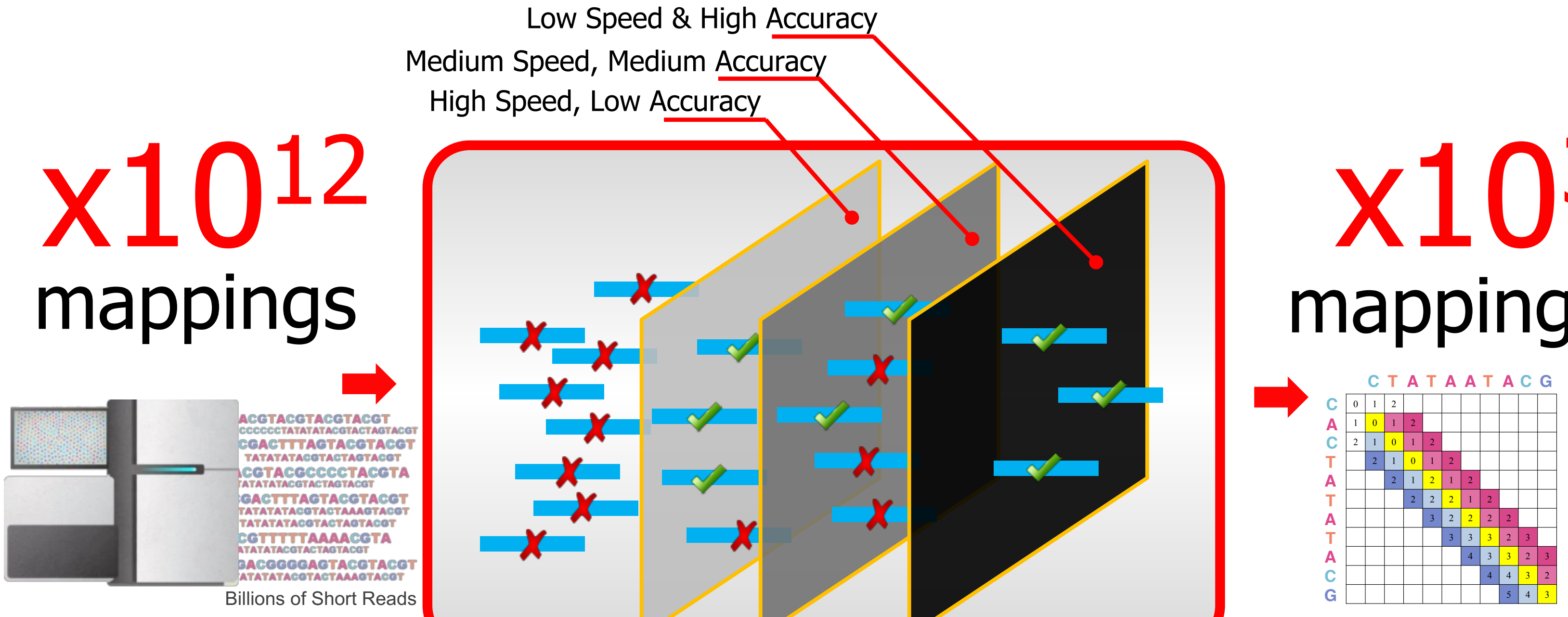
Hongyi Xin[1,*], John Greth[2], John Emmons[2], Gennady Pekhimenko[1], Carl Kingsford[3], Can Alkan[4,*] and Onur Mutlu[2,*]

Xin+, **"Shifted Hamming Distance: A Fast and Accurate SIMD-friendly Filter to Accelerate Alignment Verification in Read Mapping", Bioinformatics 2015.**

An Example Solution: GateKeeper

Alignment Filter +

= 1st FPGA-based Alignment Filter.



Billions of Short Reads

x10^{12} mappings

Low Speed & High Accuracy

Medium Speed, Medium Accuracy

High Speed, Low Accuracy

x10^{3} mappings

		C	T	A	T	A	A	T	A	C	G
C	0	1	2								
A	1	0	1	2							
C	2	1	0	1	2						
T		2	1	0	1	2					
A			2	1	2	1	2				
T				2	2	2	1	2			
A					3	2	2	2	2		
T						3	3	3	2	3	
A							4	3	3	2	3
C								4	4	3	2
G									5	4	3

1 **High throughput DNA sequencing (HTS) technologies**

2 **Read Pre-Alignment Filtering**
Fast & Low False Positive Rate

3 **Read Alignment**
Slow & Zero False Positives

FPGA-Based Alignment Filtering

- Mohammed Alser, Hasan Hassan, Hongyi Xin, Oguz Ergin, Onur Mutlu, and Can Alkan
  "GateKeeper: A New Hardware Architecture for Accelerating Pre-Alignment in DNA Short Read Mapping"
  Bioinformatics, [published online, May 31], 2017.
  [Source Code]
  [Online link at Bioinformatics Journal]

GateKeeper: a new hardware architecture for accelerating pre-alignment in DNA short read mapping

Mohammed Alser ✉, Hasan Hassan, Hongyi Xin, Oğuz Ergin, Onur Mutlu ✉, Can Alkan ✉

Bioinformatics, Volume 33, Issue 21, 1 November 2017, Pages 3355–3363,
https://doi.org/10.1093/bioinformatics/btx342

Published: 31 May 2017 **Article history ▾**

DNA Read Mapping & Filtering

- Problem: **Heavily bottlenecked by Data Movement**
- GateKeeper FPGA performance limited by DRAM bandwidth [Alser+, Bioinformatics 2017]
- Ditto for SHD on SIMD [Xin+, Bioinformatics 2015]
- Solution: Processing-in-memory can alleviate the bottleneck
- However, we need to design mapping & filtering algorithms to fit processing-in-memory

In-Memory DNA Sequence Analysis

- Jeremie S. Kim, Damla Senol Cali, Hongyi Xin, Donghyuk Lee, Saugata Ghose, Mohammed Alser, Hasan Hassan, Oguz Ergin, Can Alkan, and Onur Mutlu,
  "GRIM-Filter: Fast Seed Location Filtering in DNA Read Mapping Using Processing-in-Memory Technologies"
  BMC Genomics, 2018.
  Proceedings of the 16th Asia Pacific Bioinformatics Conference (***APBC***),
  Yokohama, Japan, January 2018.
  arxiv.org Version (pdf)

GRIM-Filter: Fast seed location filtering in DNA read mapping using processing-in-memory technologies

Jeremie S. Kim[1,6*], Damla Senol Cali[1], Hongyi Xin[2], Donghyuk Lee[3], Saugata Ghose[1], Mohammed Alser[4], Hasan Hassan[6], Oguz Ergin[5], Can Alkan[4*] and Onur Mutlu[6,1*]

From The Sixteenth Asia Pacific Bioinformatics Conference 2018
Yokohama, Japan. 15-17 January 2018

Key Principles and Results

- Two key principles:
  - Exploit the structure of the genome to minimize computation
  - Morph and exploit the structure of the underlying hardware to maximize performance and efficiency

- **Algorithm-architecture co-design** for DNA read mapping
  - **Speeds up** read mapping by **~200X (sometimes more)**
  - **Improves accuracy** of read mapping in the presence of errors

Xin et al., "Accelerating Read Mapping with FastHASH," BMC Genomics 2013.

Xin et al., "Shifted Hamming Distance: A Fast and Accurate SIMD-friendly Filter to Accelerate Alignment Verification in Read Mapping," Bioinformatics 2015.

Alser et al., "GateKeeper: A New Hardware Architecture for Accelerating Pre-Alignment in DNA Short Read Mapping," Bioinformatics 2017.

Kim et al., "Genome Read In-Memory (GRIM) Filter," BMC Genomics 2018.

New Genome Sequencing Technologies

Nanopore sequencing technology and tools for genome assembly: computational analysis of the current state, bottlenecks and future directions

Damla Senol Cali ✉, Jeremie S Kim, Saugata Ghose, Can Alkan, Onur Mutlu

Briefings in Bioinformatics, bby017, https://doi.org/10.1093/bib/bby017

Published: 02 April 2018 **Article history** ▾

Oxford Nanopore MinION

Senol Cali+, "**Nanopore Sequencing Technology and Tools for Genome Assembly: Computational Analysis of the Current State, Bottlenecks and Future Directions**," Briefings in Bioinformatics, 2018.

[Preliminary arxiv.org version]

Nanopore Genome Assembly Pipeline

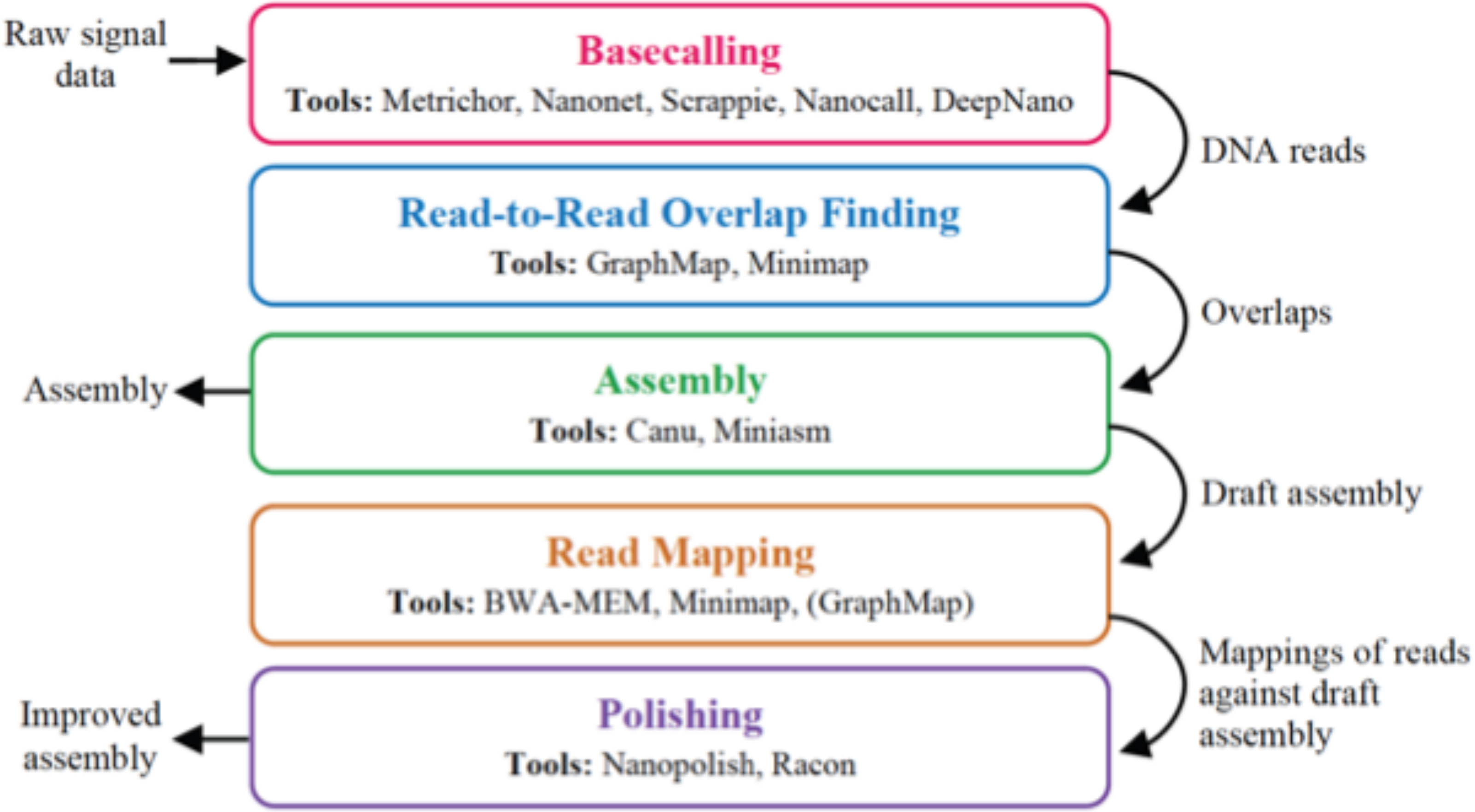
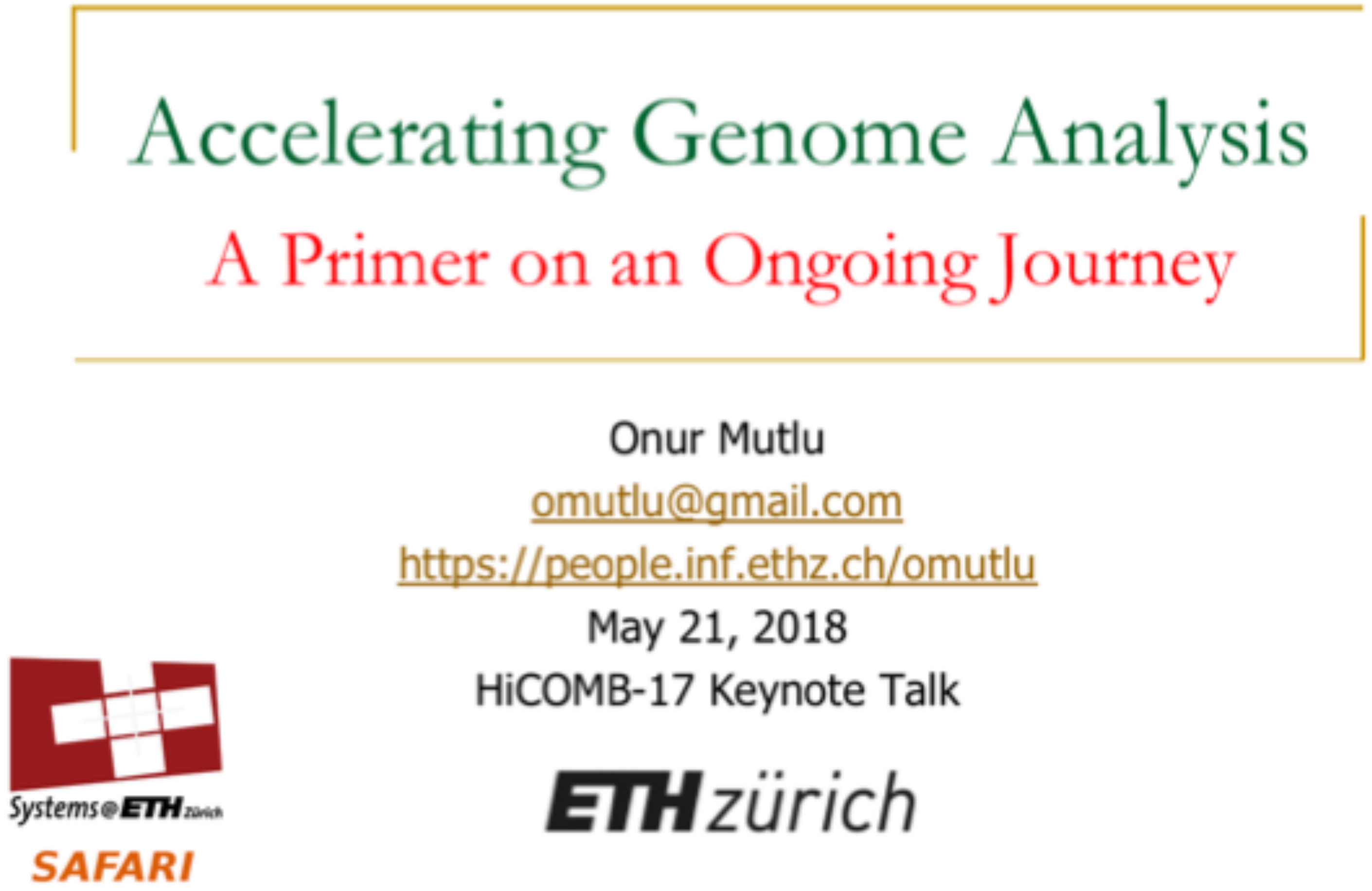


Figure 1. The analyzed genome assembly pipeline using nanopore sequence data, with its five steps and the associated tools for each step.

Senol Cali+, "**Nanopore Sequencing Technology and Tools for Genome Assembly**" to appear in Briefings in Bioinformatics, 2018.

More on Genome Analysis: Another Talk



Accelerating Genome Analysis

A Primer on an Ongoing Journey

Onur Mutlu
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https://people.inf.ethz.ch/omutlu
May 21, 2018
HiCOMB-17 Keynote Talk

ETH zürich

Four Key Directions

- Fundamentally Secure/Reliable/Safe Architectures

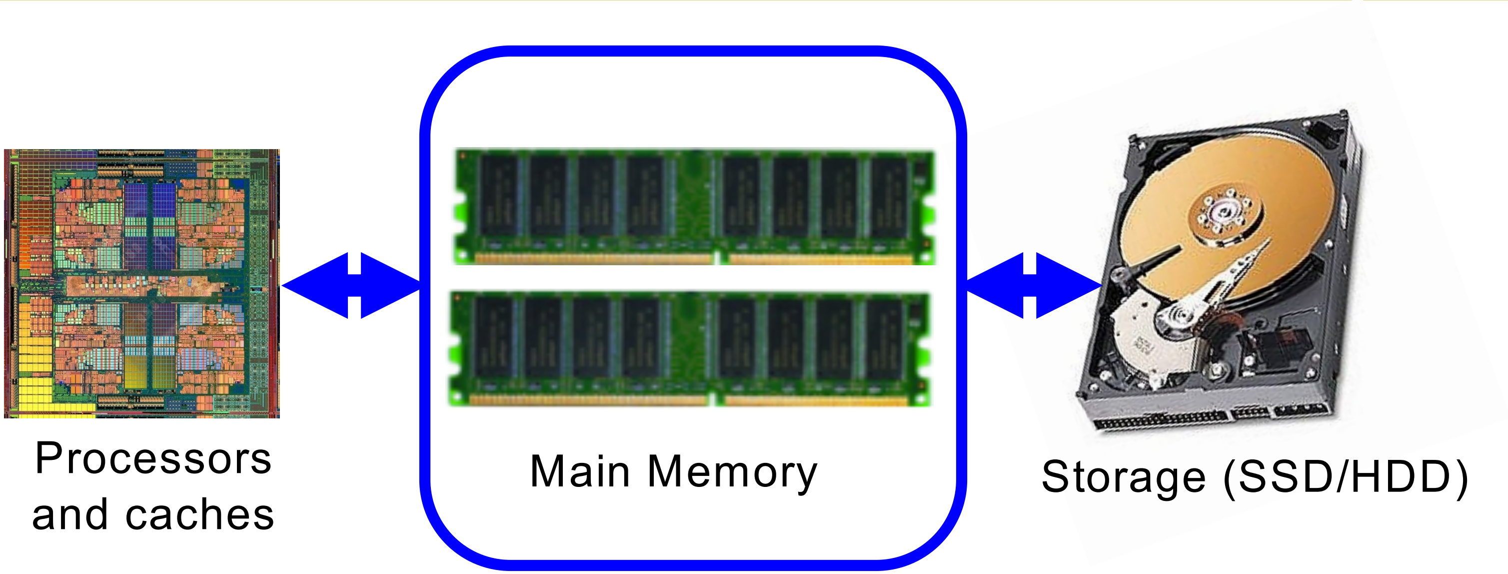
- Fundamentally Energy-Efficient Architectures
  - Memory-centric (Data-centric) Architectures

- Fundamentally Low-Latency Architectures

- Architectures for Genomics, Medicine, Health

Memory & Storage

The Main Memory System



Processors
and caches

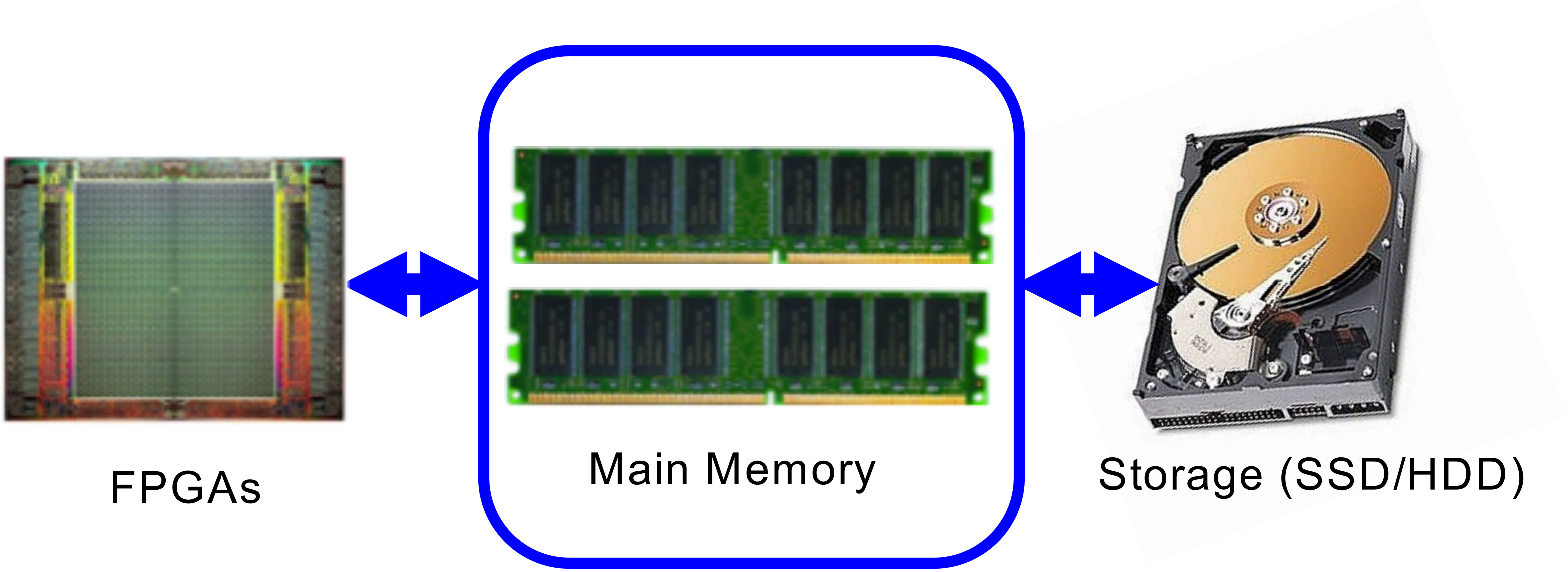
Main Memory

Storage (SSD/HDD)

- Main memory is a critical component of all computing systems: server, mobile, embedded, desktop, sensor

- Main memory system must scale (in *size*, *technology*, *efficiency*, *cost*, and *management algorithms*) to maintain performance growth and technology scaling benefits

The Main Memory System



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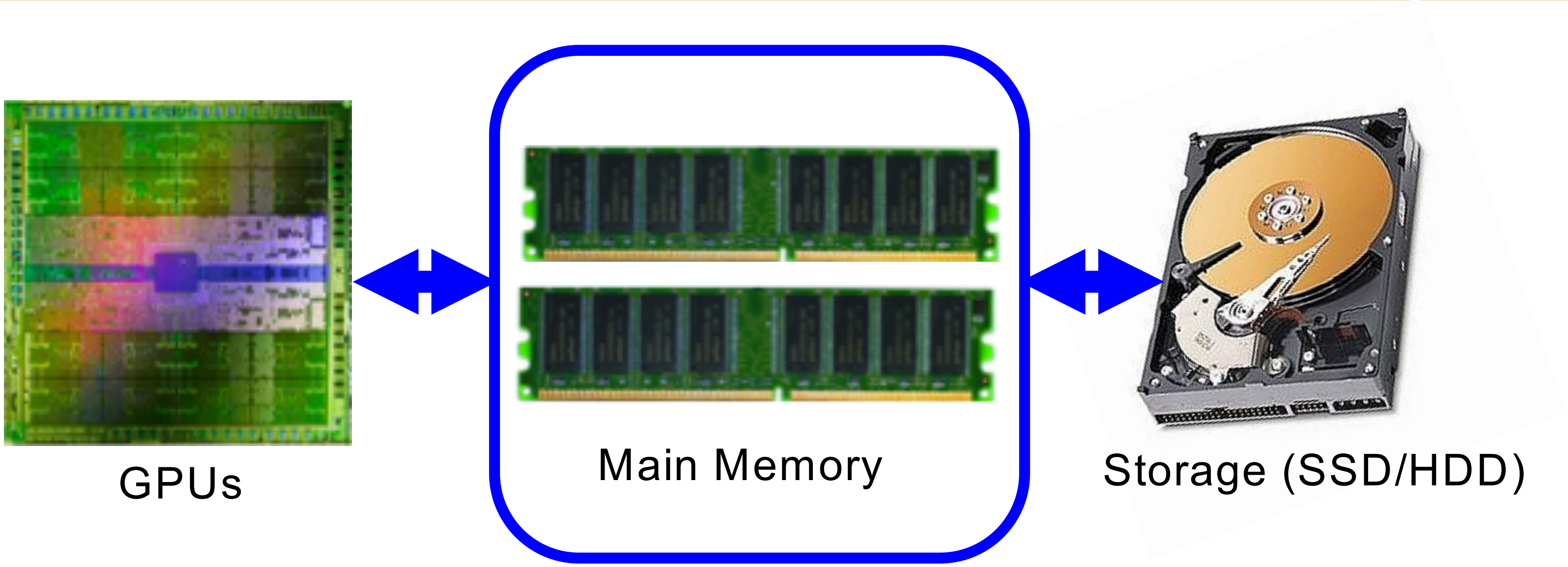
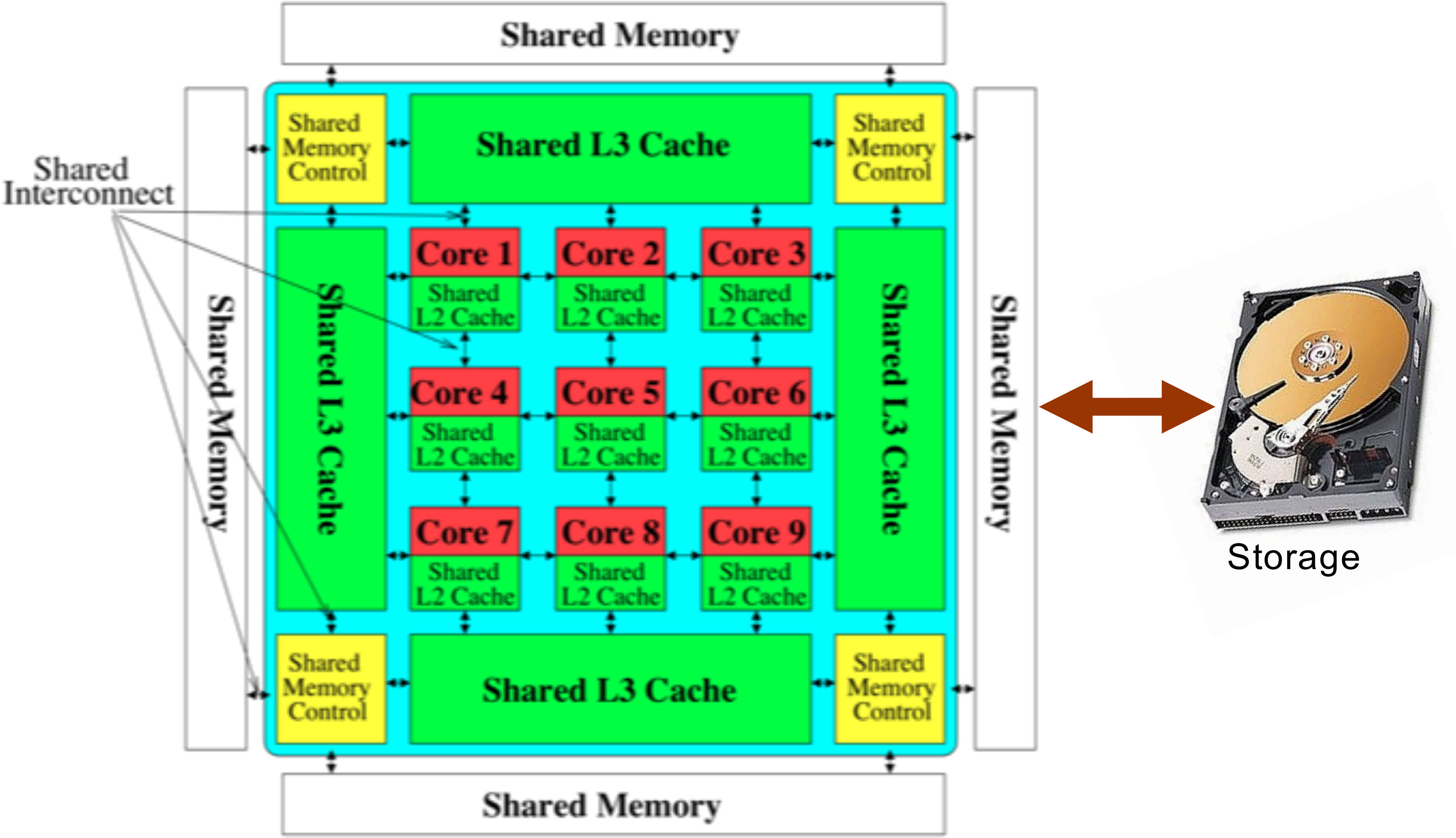
The Main Memory System



- Main memory is a critical component of all computing systems: server, mobile, embedded, desktop, sensor

- Main memory system must scale (in *size*, *technology*, *efficiency*, *cost*, and *management algorithms*) to maintain performance growth and technology scaling benefits

Memory System: A ***Shared Resource*** View



Most of the system is dedicated to storing and moving data

State of the Main Memory System

- Recent technology, architecture, and application trends
  - lead to new requirements
  - exacerbate old requirements

- DRAM and memory controllers, as we know them today, are (will be) unlikely to satisfy all requirements

- Some emerging non-volatile memory technologies (e.g., PCM) enable new opportunities: memory+storage merging

- We need to rethink the main memory system
  - to fix DRAM issues and enable emerging technologies
  - to satisfy all requirements

Major Trends Affecting Main Memory (I)

- Need for main memory capacity, bandwidth, QoS increasing

- Main memory energy/power is a key system design concern

- DRAM technology scaling is ending

Major Trends Affecting Main Memory (II)

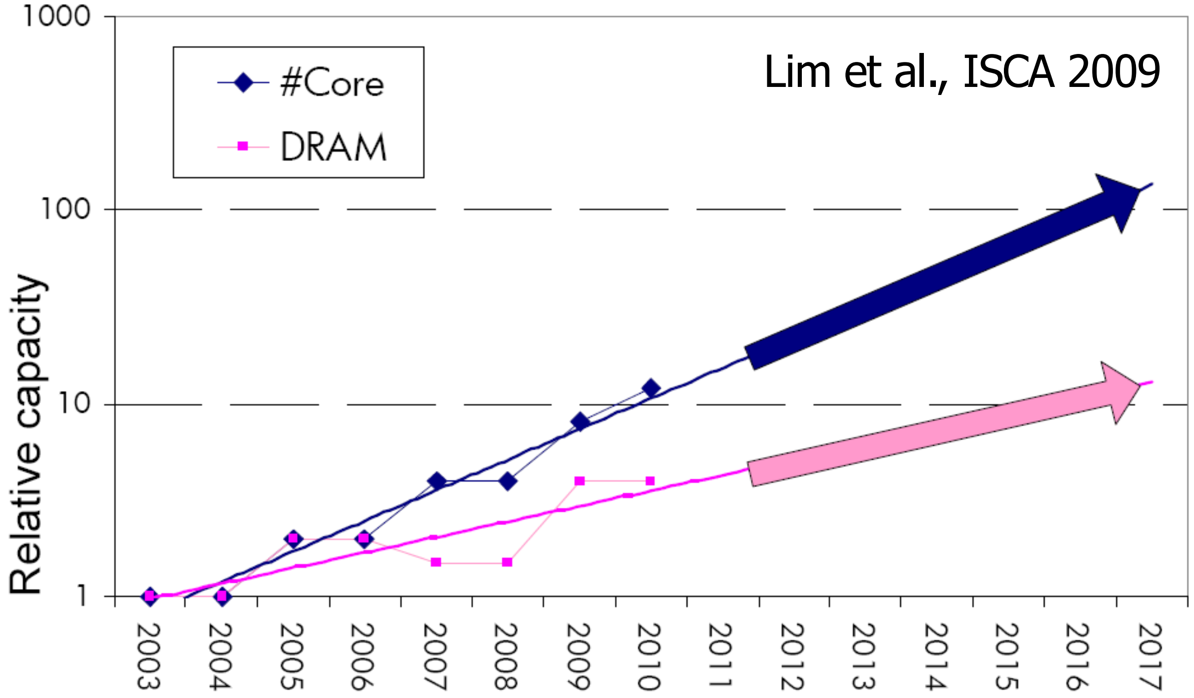
- Need for main memory capacity, bandwidth, QoS increasing
  - Multi-core: increasing number of cores/agents
  - Data-intensive applications: increasing demand/hunger for data
  - Consolidation: cloud computing, GPUs, mobile, heterogeneity

- Main memory energy/power is a key system design concern

- DRAM technology scaling is ending

Example: The Memory Capacity Gap

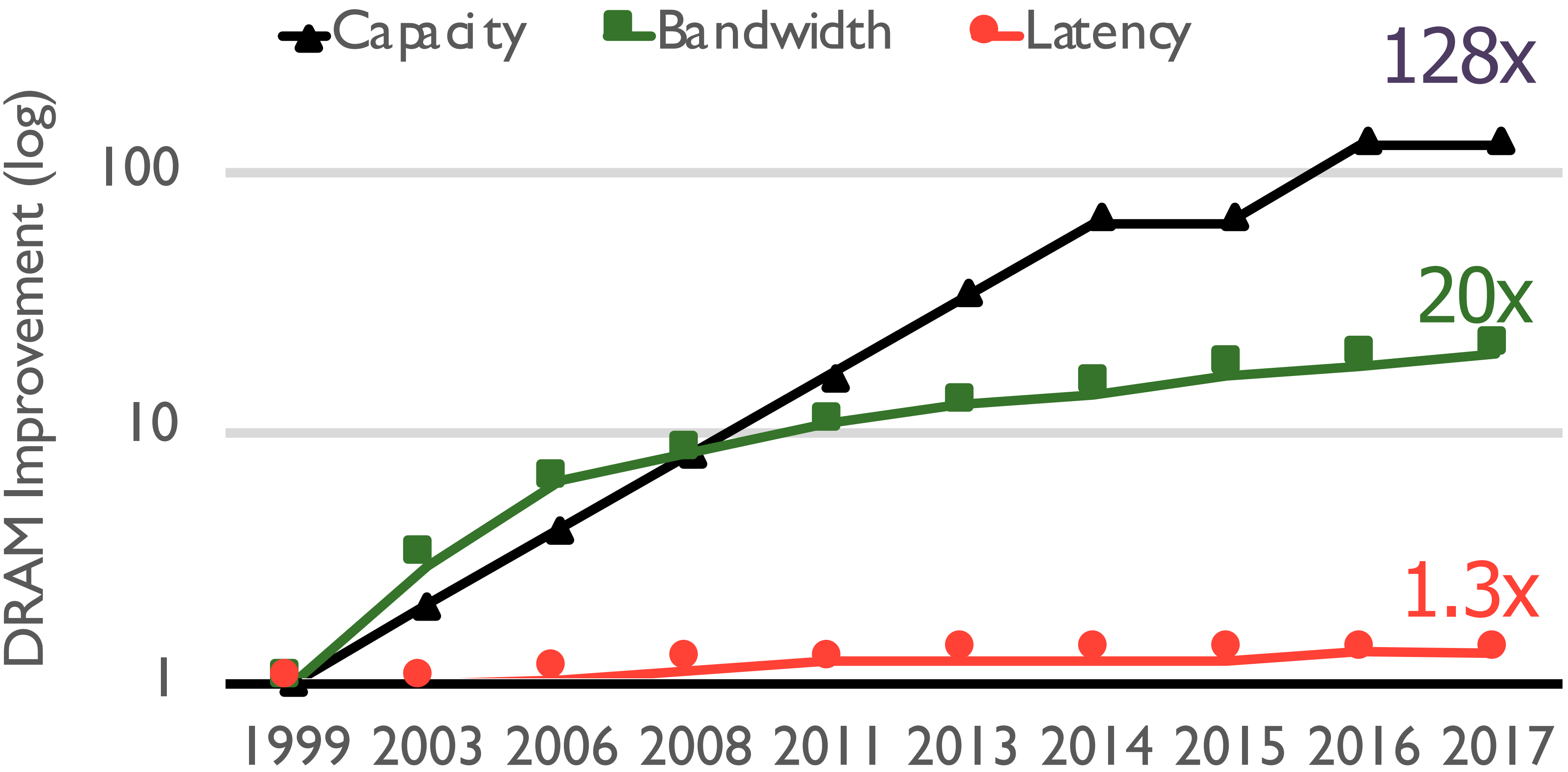
Core count doubling ~ every 2 years
DRAM DIMM capacity doubling ~ every 3 years



Lim et al., ISCA 2009

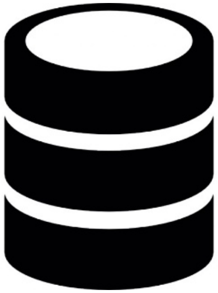
- *Memory capacity per core* expected to drop by 30% every two years
- Trends worse for *memory bandwidth per core*!

Example: Capacity, Bandwidth & Latency



Memory latency remains almost constant

DRAM Latency Is Critical for Performance



In-memory Databases

[Mao+, EuroSys'12;
Clapp+ (**Intel**), IISWC'15]

Graph/Tree Processing

[Xu+, IISWC'12; Umuroglu+, FPL'15]

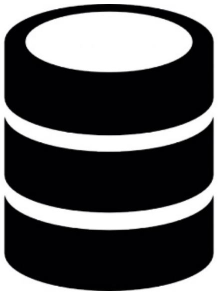
In-Memory Data Analytics

[Clapp+ (**Intel**), IISWC'15;
Awan+, BDCloud'15]

Datacenter Workloads

[Kanev+ (**Google**), ISCA'15]

DRAM Latency Is Critical for Performance



In-memory Databases

Graph/Tree Processing

Long memory latency → performance bottleneck

In-Memory Data Analytics

[Clapp+ (**Intel**), IISWC'15;
Awan+, BDCloud'15]

Datacenter Workloads

[Kanev+ (**Google**), ISCA'15]

Major Trends Affecting Main Memory (III)

- Need for main memory capacity, bandwidth, QoS increasing

- Main memory energy/power is a key system design concern
  - ~40-50% energy spent in off-chip memory hierarchy [Lefurgy, IEEE Computer'03] >40% power in DRAM [Ware, HPCA'10][Paul,ISCA'15]
  - DRAM consumes power even when not used (periodic refresh)

- DRAM technology scaling is ending

Major Trends Affecting Main Memory (IV)

- Need for main memory capacity, bandwidth, QoS increasing

- Main memory energy/power is a key system design concern

- DRAM technology scaling is ending
  - ITRS projects DRAM will not scale easily below X nm
  - Scaling has provided many benefits:
    - higher capacity (density), lower cost, lower energy

Major Trends Affecting Main Memory (V)

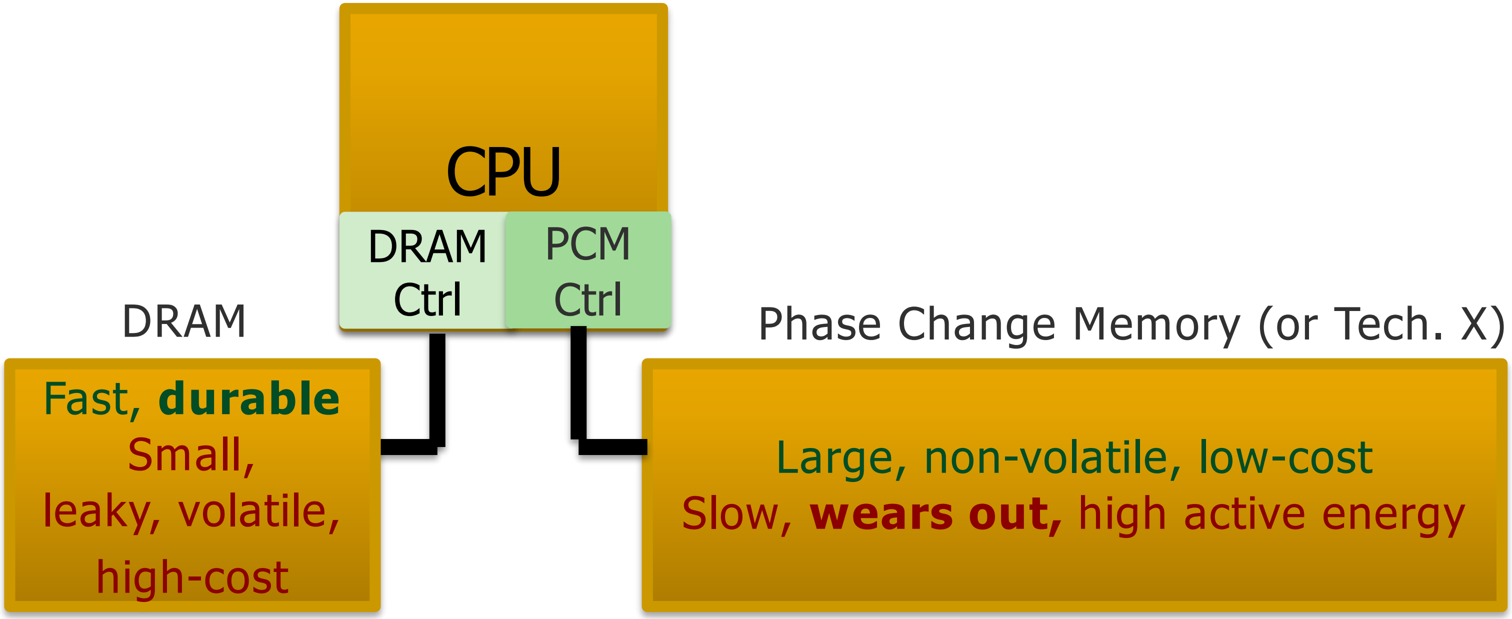
- DRAM scaling has already become increasingly difficult
  - Increasing cell leakage current, reduced cell reliability, increasing manufacturing difficulties [Kim+ ISCA 2014], [Liu+ ISCA 2013], [Mutlu IMW 2013], [Mutlu DATE 2017]
  - **Difficult to significantly improve capacity, energy**
- **Emerging memory technologies** are promising

Major Trends Affecting Main Memory (V)

- DRAM scaling has already become increasingly difficult
  - Increasing cell leakage current, reduced cell reliability, increasing manufacturing difficulties [Kim+ ISCA 2014], [Liu+ ISCA 2013], [Mutlu IMW 2013], [Mutlu DATE 2017]
  - **Difficult to significantly improve capacity, energy**
- **Emerging memory technologies** are promising

3D-Stacked DRAM	higher bandwidth	smaller capacity
Reduced-Latency DRAM (e.g., RL/TL-DRAM, FLY-RAM)	lower latency	higher cost
Low-Power DRAM (e.g., LPDDR3, LPDDR4, Voltron)	lower power	higher latency higher cost
Non-Volatile Memory (NVM) (e.g., PCM, STTRAM, ReRAM, 3D Xpoint)	larger capacity	higher latency higher dynamic power lower endurance

Major Trend: Hybrid Main Memory


CPU

DRAM Ctrl

PCM Ctrl

DRAM

Fast, **durable**
Small,
leaky, volatile,
high-cost

Phase Change Memory (or Tech. X)

Large, non-volatile, low-cost
Slow, **wears out,** high active energy

Hardware/software manage data allocation and movement
to achieve the best of multiple technologies

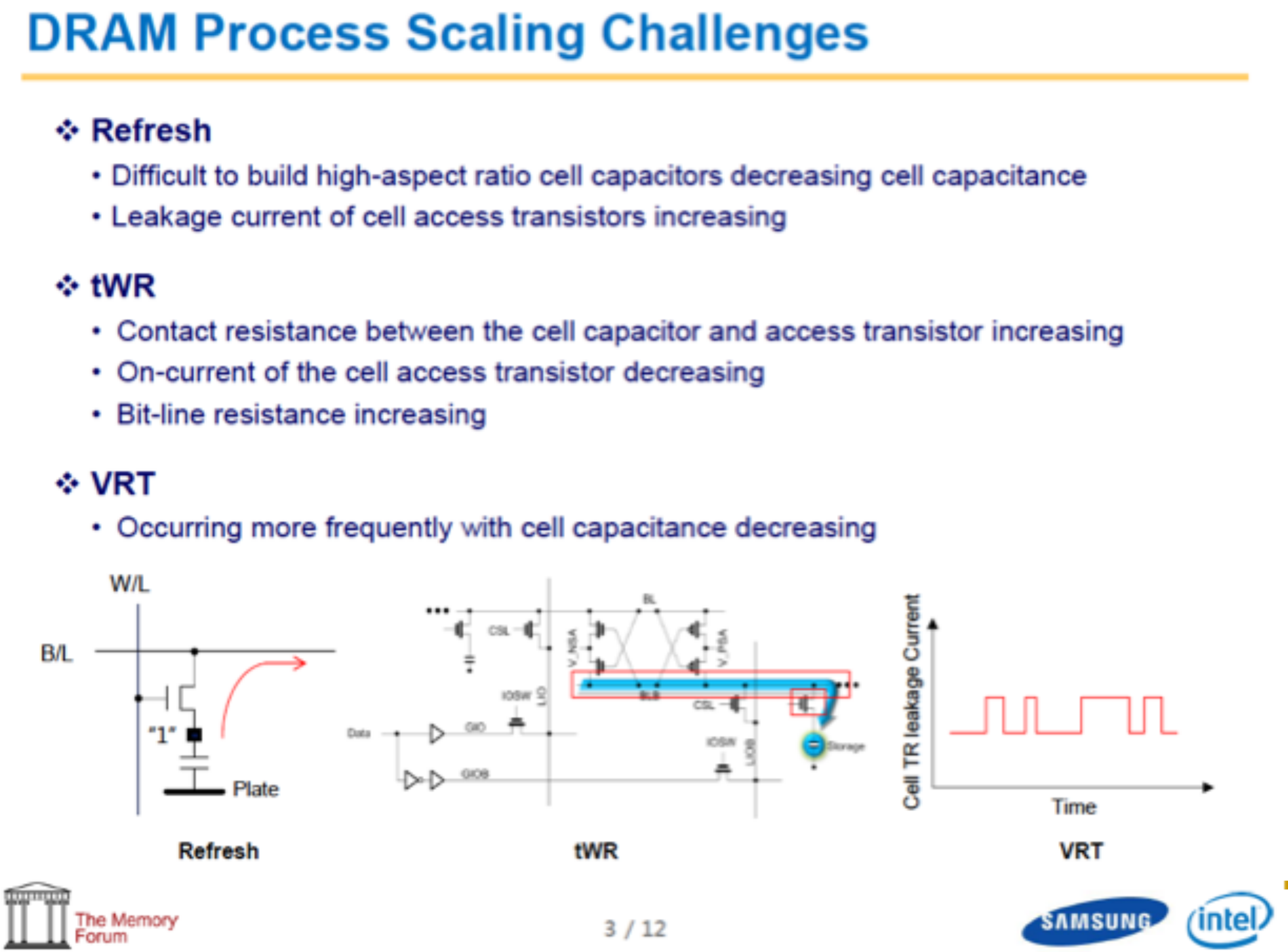
Meza+, "Enabling Efficient and Scalable Hybrid Memories," IEEE Comp. Arch. Letters, 2012.
Yoon+, "Row Buffer Locality Aware Caching Policies for Hybrid Memories," ICCD 2012 Best Paper Award.

Foreshadowing

Main Memory Needs

Intelligent Controllers

Industry Is Writing Papers About It, Too



DRAM Process Scaling Challenges

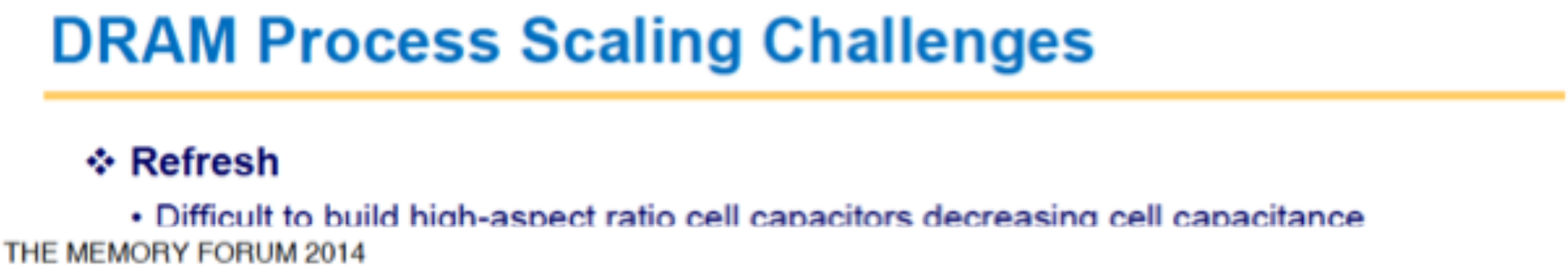
- **Refresh**
  - Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance
  - Leakage current of cell access transistors increasing
- **tWR**
  - Contact resistance between the cell capacitor and access transistor increasing
  - On-current of the cell access transistor decreasing
  - Bit-line resistance increasing
- **VRT**
  - Occurring more frequently with cell capacitance decreasing

Refresh **tWR** **VRT**

The Memory Forum

3 / 12

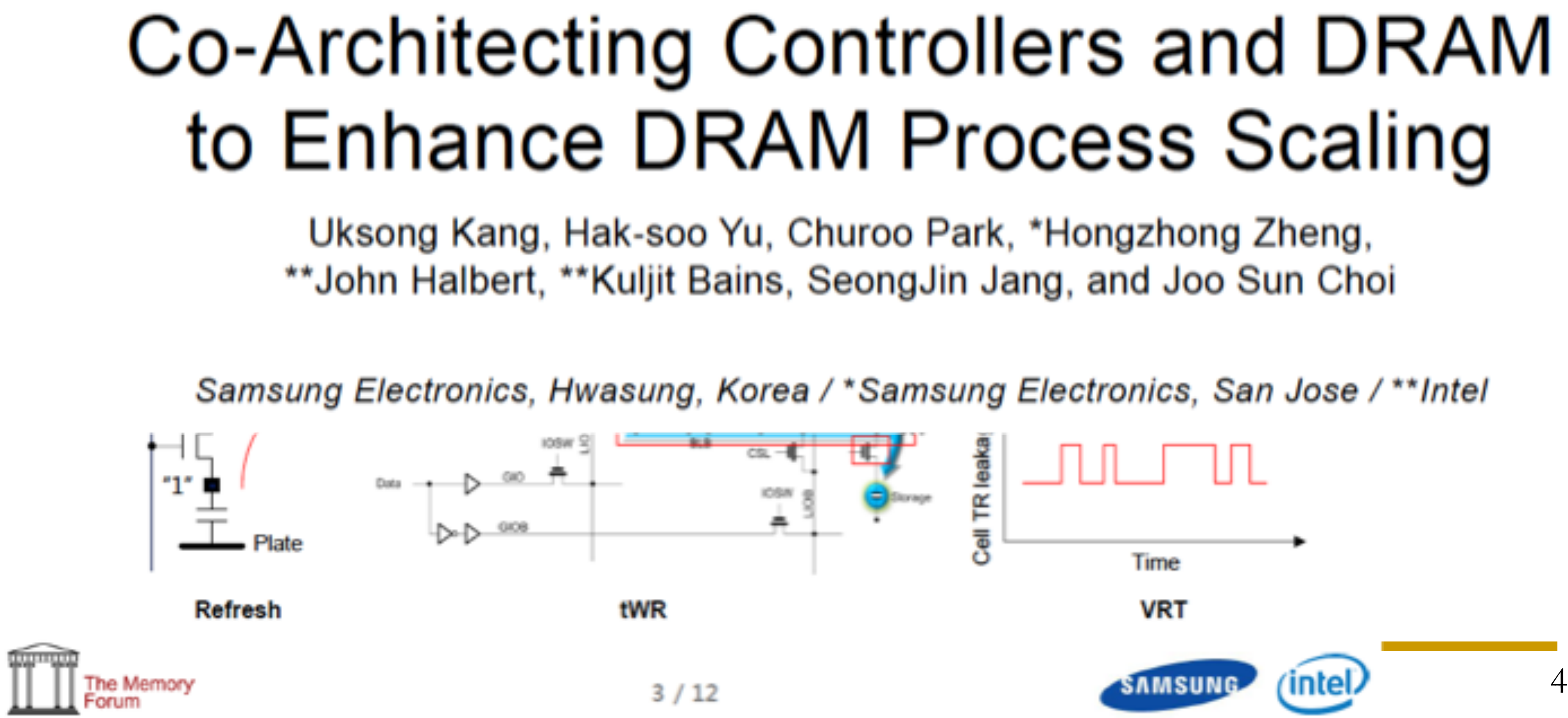
Call for Intelligent Memory Controllers



DRAM Process Scaling Challenges

- **Refresh**
  - Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance

THE MEMORY FORUM 2014



Co-Architecting Controllers and DRAM to Enhance DRAM Process Scaling

Uksong Kang, Hak-soo Yu, Churoo Park, *Hongzhong Zheng,
**John Halbert, **Kuljit Bains, SeongJin Jang, and Joo Sun Choi

*Samsung Electronics, Hwasung, Korea / *Samsung Electronics, San Jose / **Intel*

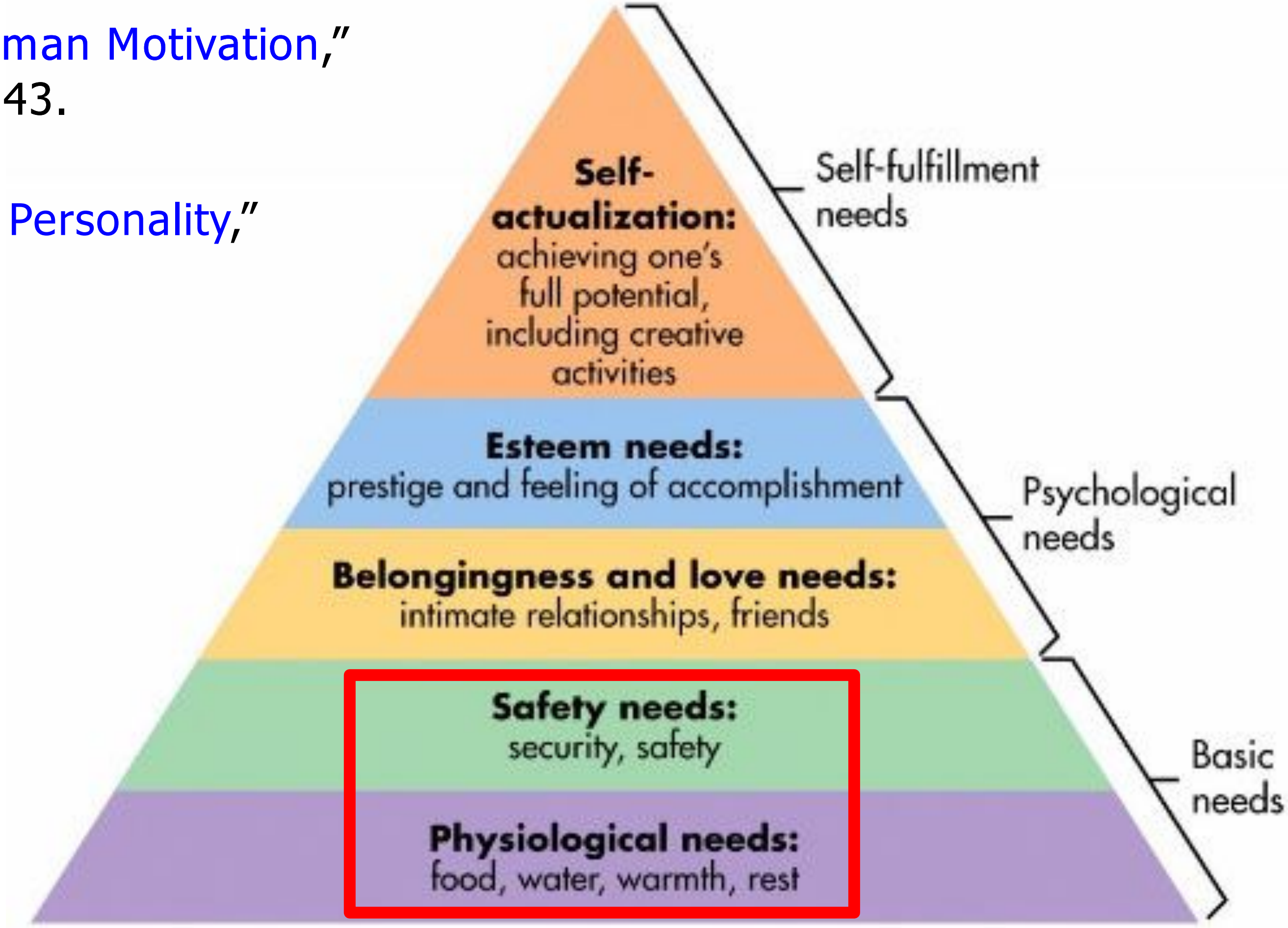
Agenda

- Major Trends Affecting Main Memory
- The Need for Intelligent Memory Controllers
    - Bottom Up: Push from Circuits and Devices
    - Top Down: Pull from Systems and Applications
- Processing in Memory: Two Directions
    - Minimally Changing Memory Chips
    - Exploiting 3D-Stacked Memory
- How to Enable Adoption of Processing in Memory
- Conclusion

Maslow's (Human) Hierarchy of Needs

Maslow, "A Theory of Human Motivation," Psychological Review, 1943.

Maslow, "Motivation and Personality," Book, 1954-1970.



- We need to start with reliability and security…

Source: https://www.simplypsychology.org/maslow.html

How Reliable/Secure/Safe is This Bridge?

Source: http://www.technologystudent.com/struct1/tacom1.png

Collapse of the "Galloping Gertie"

Source: AP

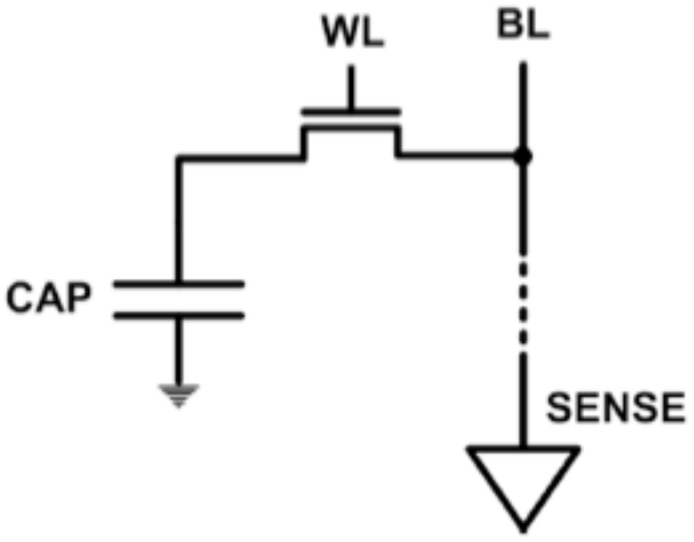
How Secure Are These People?

Security is about preventing unforeseen consequences

Source: https://s-media-cache-ak0.pinimg.com/originals/48/09/54/4809543a9c7700246a0cf8acdae27abf.jpg

The DRAM Scaling Problem

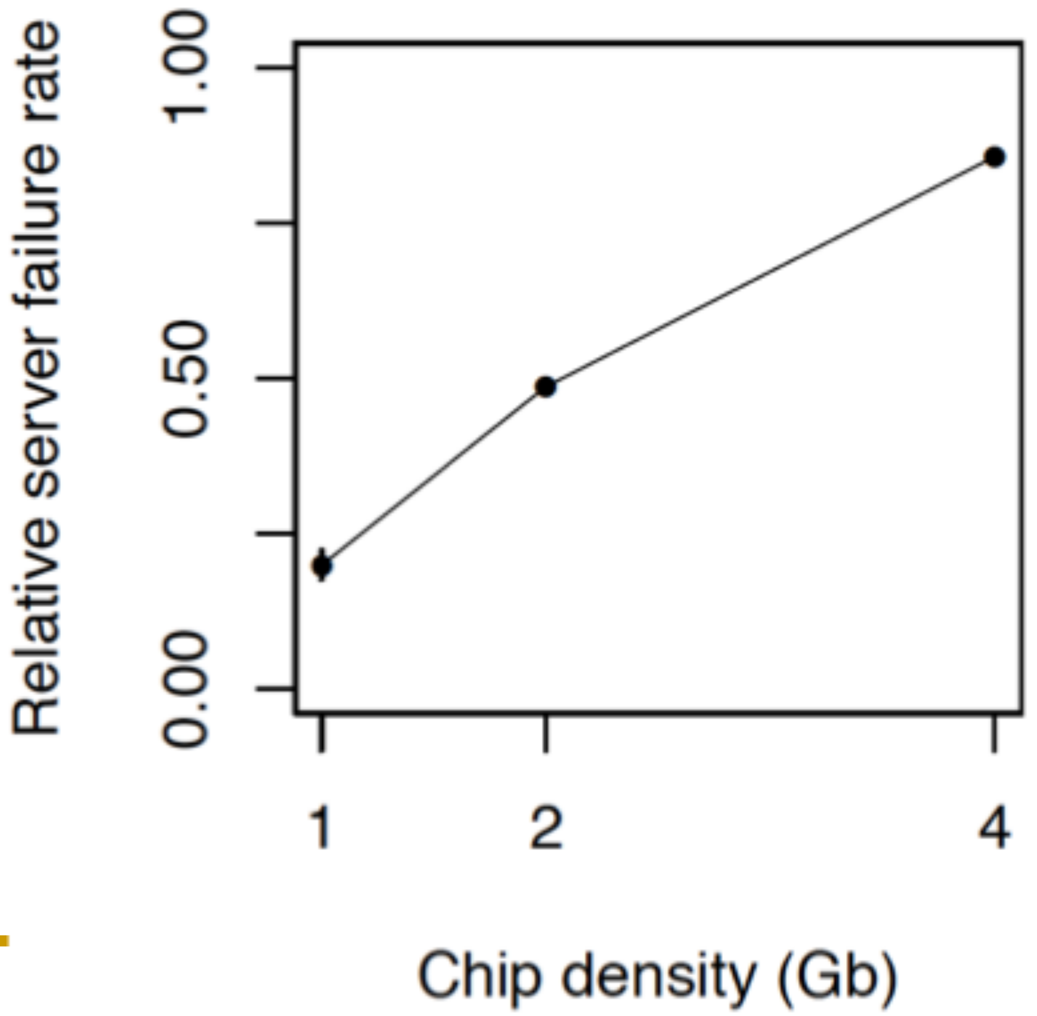
- DRAM stores charge in a capacitor (charge-based memory)
  - Capacitor must be large enough for reliable sensing
  - Access transistor should be large enough for low leakage and high retention time
  - Scaling beyond 40-35nm (2013) is challenging [ITRS, 2009]



- DRAM capacity, cost, and energy/power hard to scale

As Memory Scales, It Becomes Unreliable

- Data from all of Facebook's servers worldwide
- Meza+, "Revisiting Memory Errors in Large-Scale Production Data Centers," DSN'15.

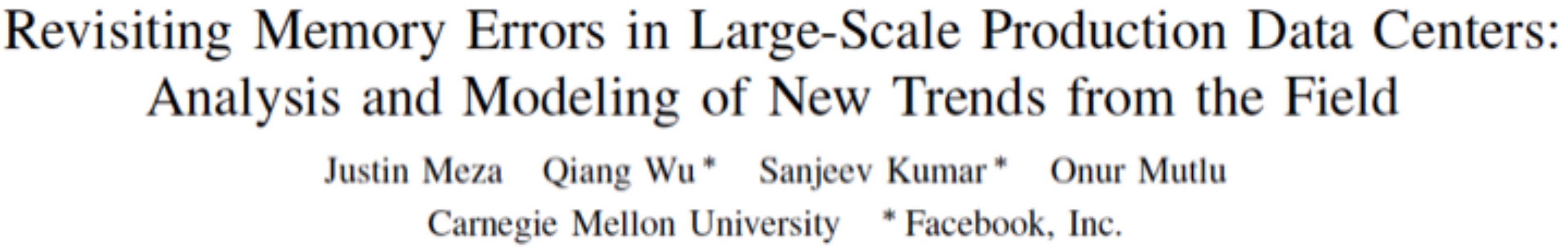


Intuition: quadratic increase in capacity

Large-Scale Failure Analysis of DRAM Chips

- Analysis and modeling of memory errors found in all of Facebook's server fleet

- Justin Meza, Qiang Wu, Sanjeev Kumar, and Onur Mutlu, **"Revisiting Memory Errors in Large-Scale Production Data Centers: Analysis and Modeling of New Trends from the Field"** *Proceedings of the 45th Annual IEEE/IFIP International Conference on Dependable Systems and Networks (**DSN**)*, Rio de Janeiro, Brazil, June 2015.
  [Slides (pptx) (pdf)] [DRAM Error Model]



Revisiting Memory Errors in Large-Scale Production Data Centers: Analysis and Modeling of New Trends from the Field

Justin Meza   Qiang Wu *   Sanjeev Kumar *   Onur Mutlu
Carnegie Mellon University   * Facebook, Inc.

Infrastructures to Understand Such Issues

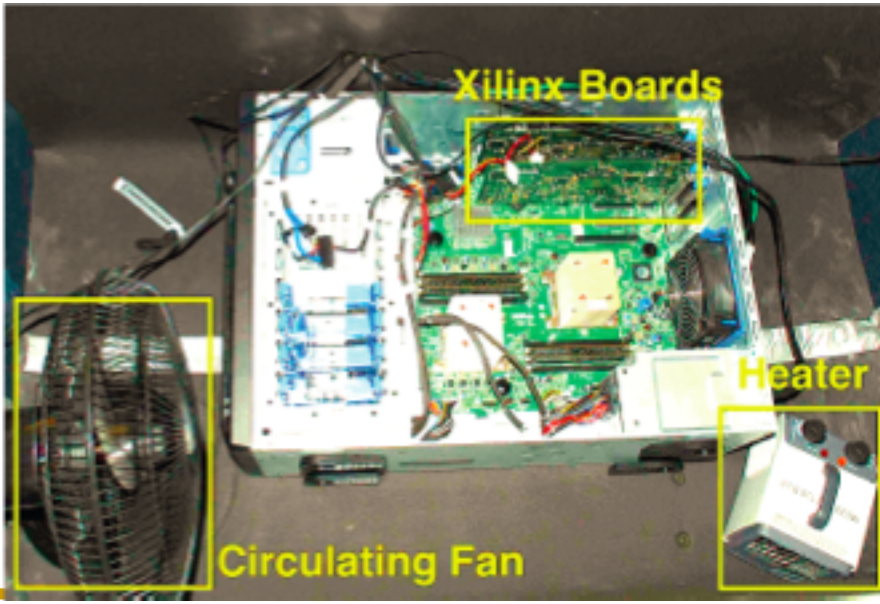
An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms (Liu et al., ISCA 2013)

The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study (Khan et al., SIGMETRICS 2014)

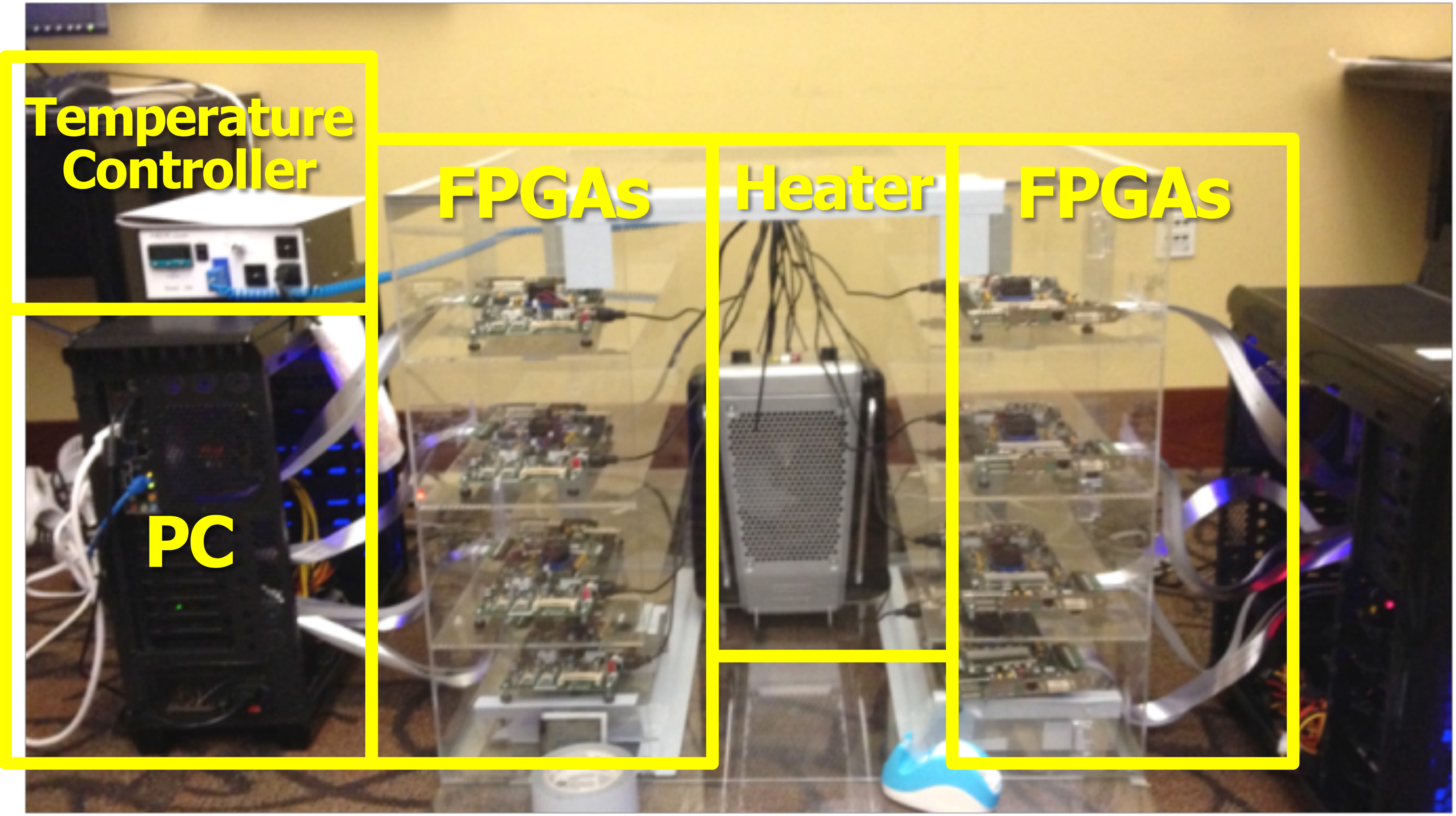
Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors (Kim et al., ISCA 2014)

Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case (Lee et al., HPCA 2015)

AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems (Qureshi et al., DSN 2015)



Infrastructures to Understand Such Issues



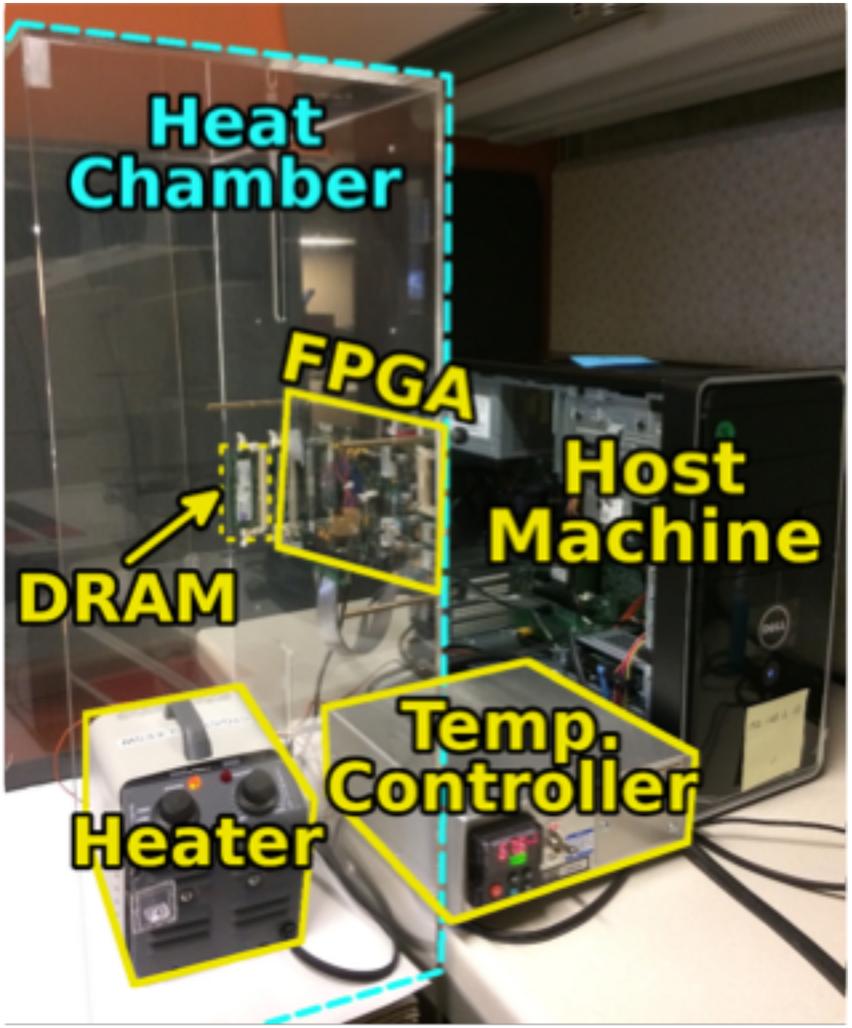
Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.

SoftMC: Open Source DRAM Infrastructure

- Hasan Hassan et al., "SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies," HPCA 2017.

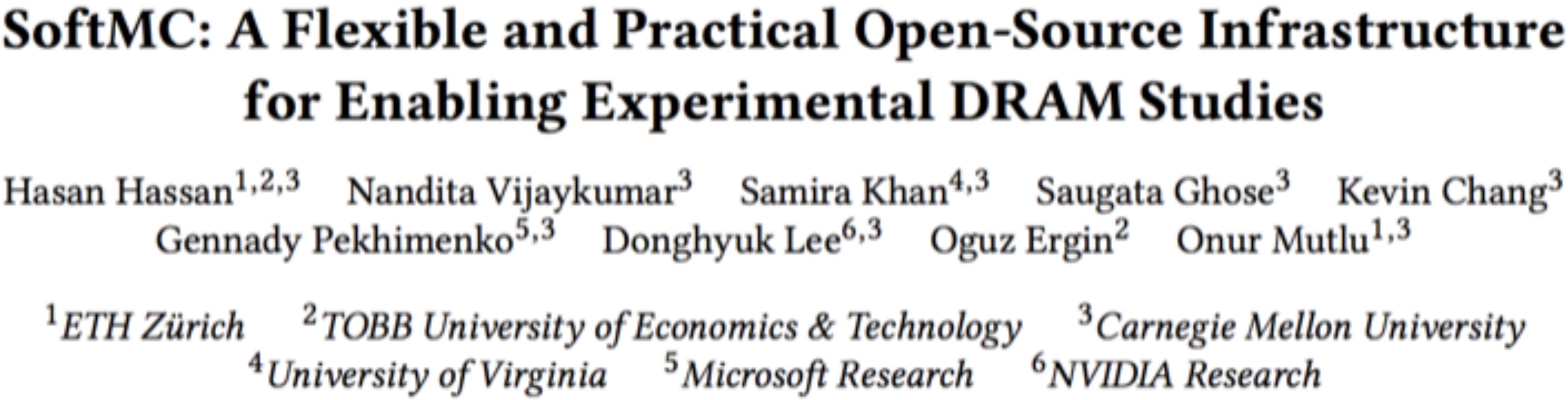
- **Flexible**
- **Easy to Use (C++ API)**
- **Open-source**

github.com/CMU-SAFARI/SoftMC



SoftMC

- https://github.com/CMU-SAFARI/SoftMC



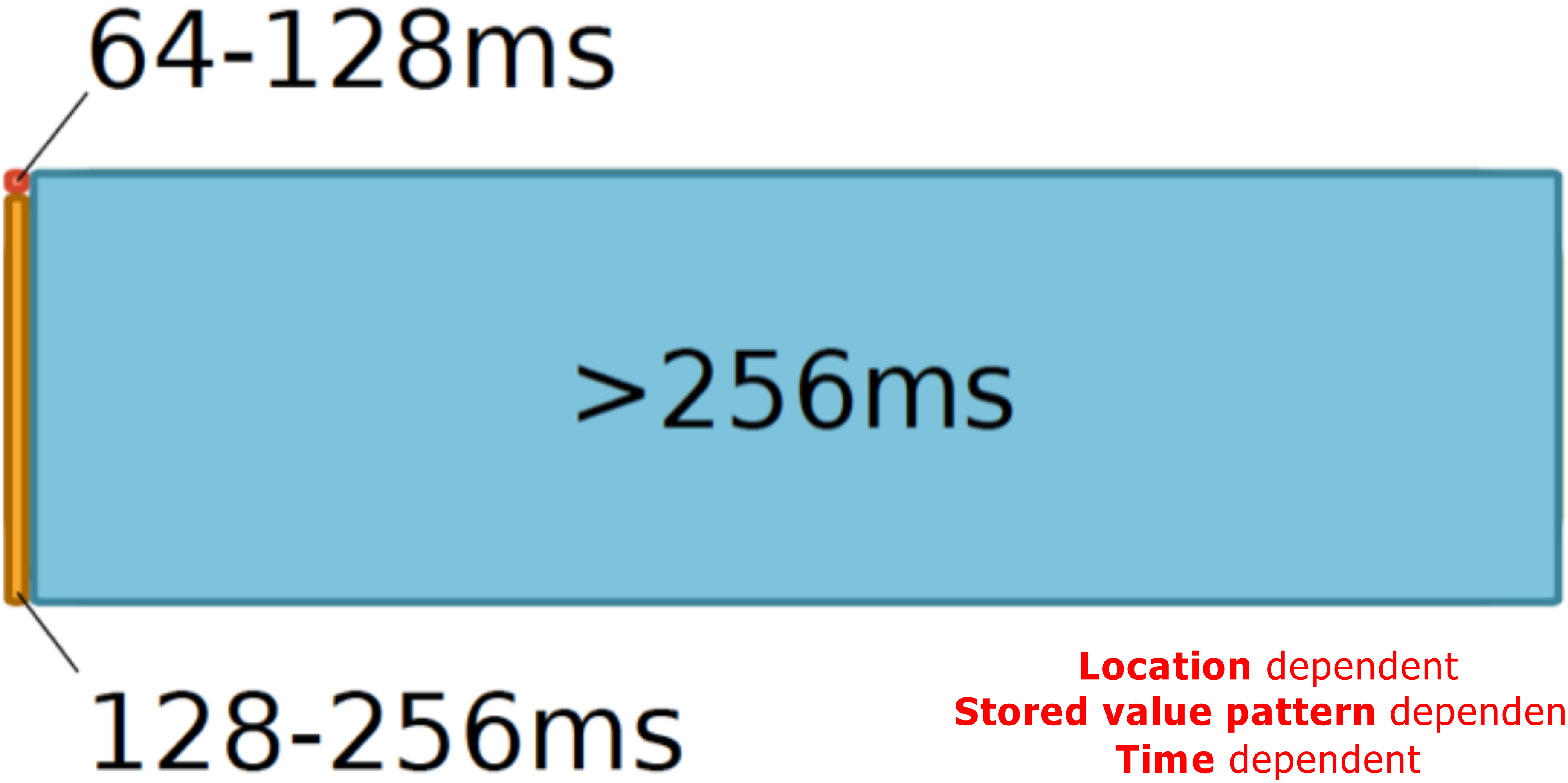
SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies

Hasan Hassan[1,2,3] Nandita Vijaykumar[3] Samira Khan[4,3] Saugata Ghose[3] Kevin Chang[3]
Gennady Pekhimenko[5,3] Donghyuk Lee[6,3] Oguz Ergin[2] Onur Mutlu[1,3]

[1]ETH Zürich [2]TOBB University of Economics & Technology [3]Carnegie Mellon University
[4]University of Virginia [5]Microsoft Research [6]NVIDIA Research

Data Retention in Memory [Liu et al., ISCA 2013]

- Retention Time Profile of DRAM looks like this:



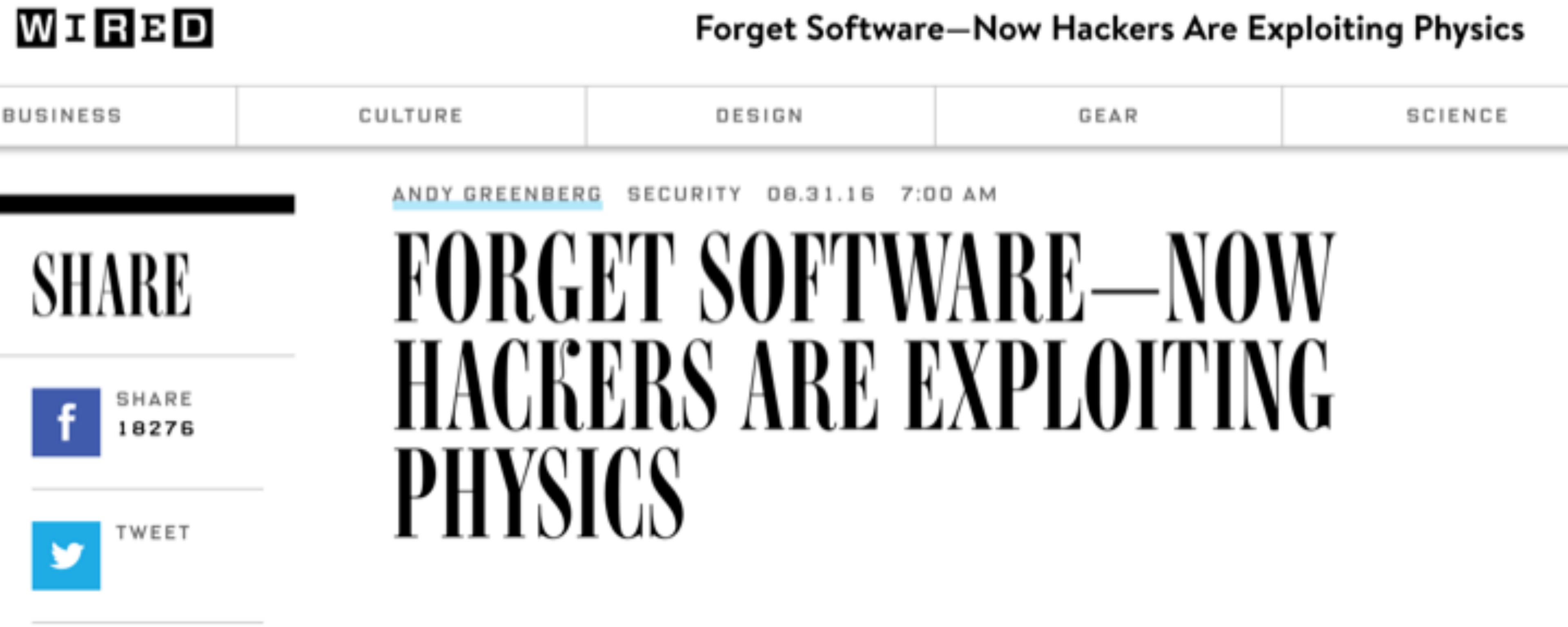
Location dependent
Stored value pattern dependent
Time dependent

A Curious Discovery **[Kim et al., ISCA 2014]**

One can
predictably induce errors
in most DRAM memory chips

DRAM RowHammer

A simple hardware failure mechanism
can create a widespread
system security vulnerability

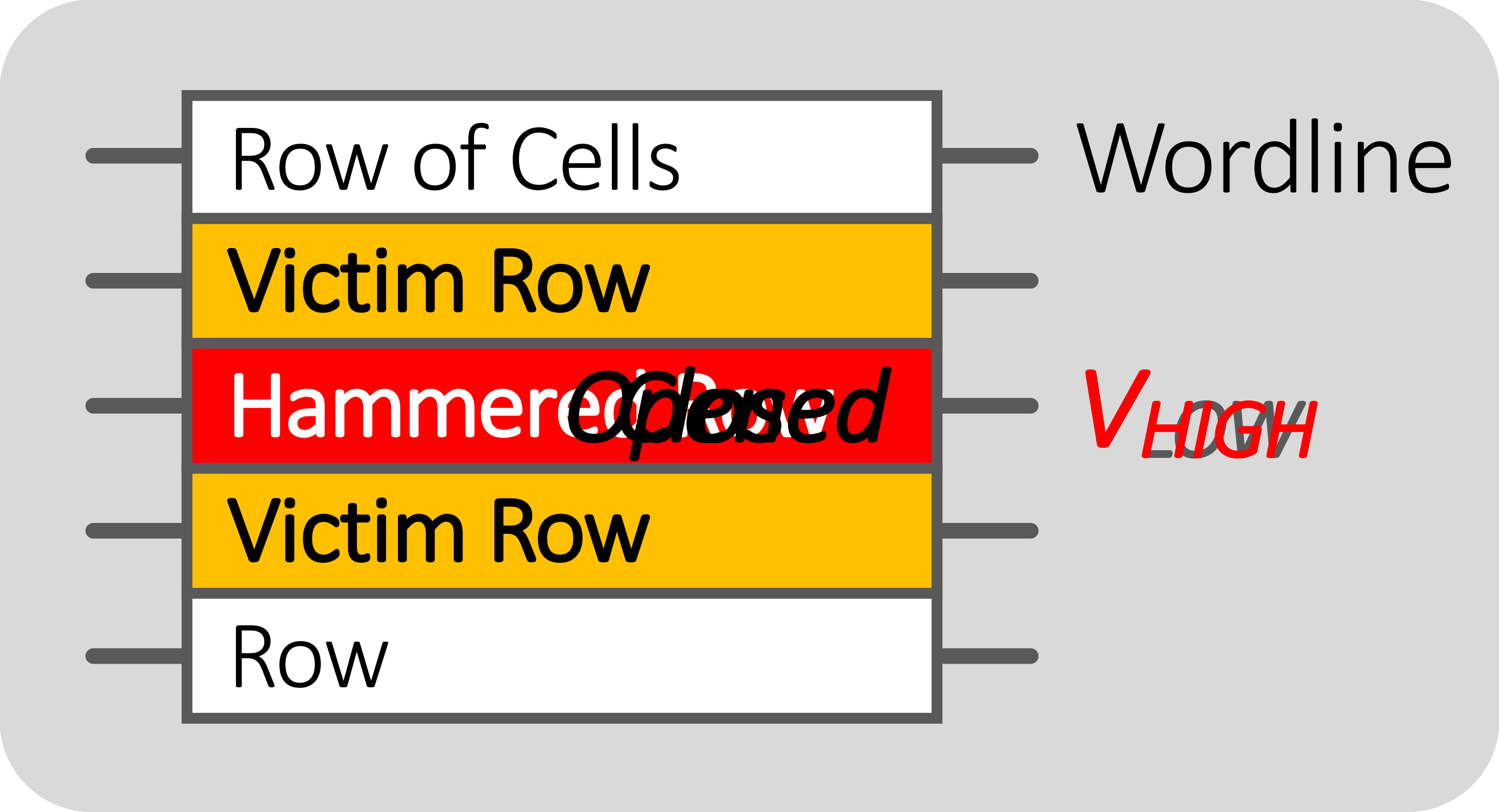


Forget Software—Now Hackers Are Exploiting Physics

ANDY GREENBERG SECURITY 08.31.16 7:00 AM

FORGET SOFTWARE—NOW HACKERS ARE EXPLOITING PHYSICS

Modern DRAM is Prone to Disturbance Errors



Row of Cells

Wordline

Victim Row

Hammered Row

Opened

Closed

V_{HIGH}

V_{LOW}

Victim Row

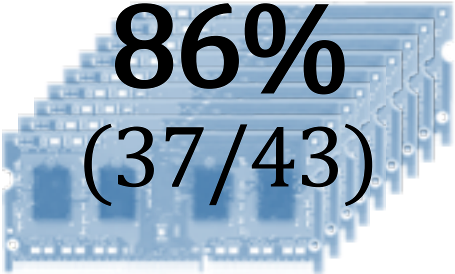
Row

Repeatedly reading a row enough times (before memory gets refreshed) induces **disturbance errors** in **adjacent rows** in **most real DRAM chips you can buy today**

Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors, (Kim et al., ISCA 2014)

Most DRAM Modules Are Vulnerable

A company



86%

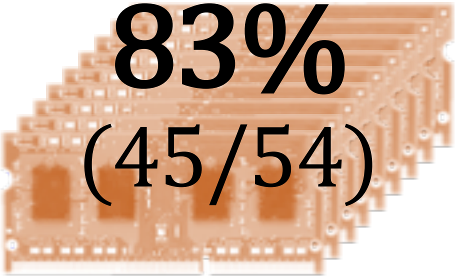
(37/43)

Up to

1.0×10⁷

errors

B company



83%

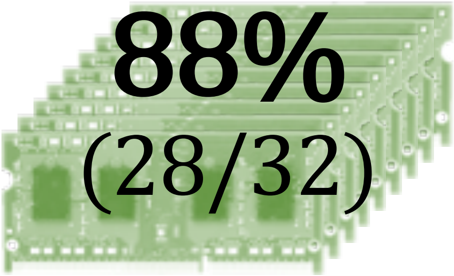
(45/54)

Up to

2.7×10⁶

errors

C company



88%

(28/32)

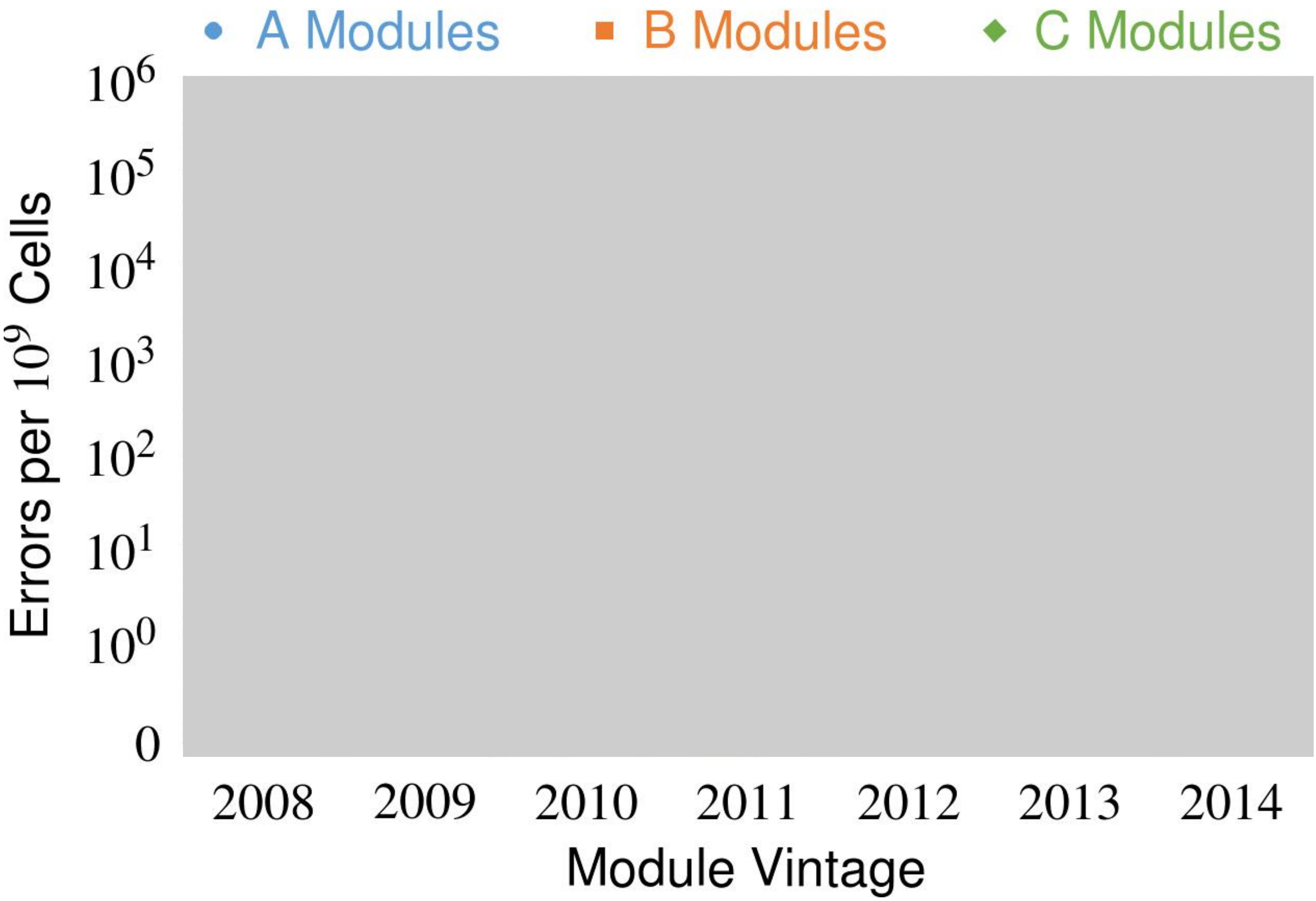
Up to

3.3×10⁵

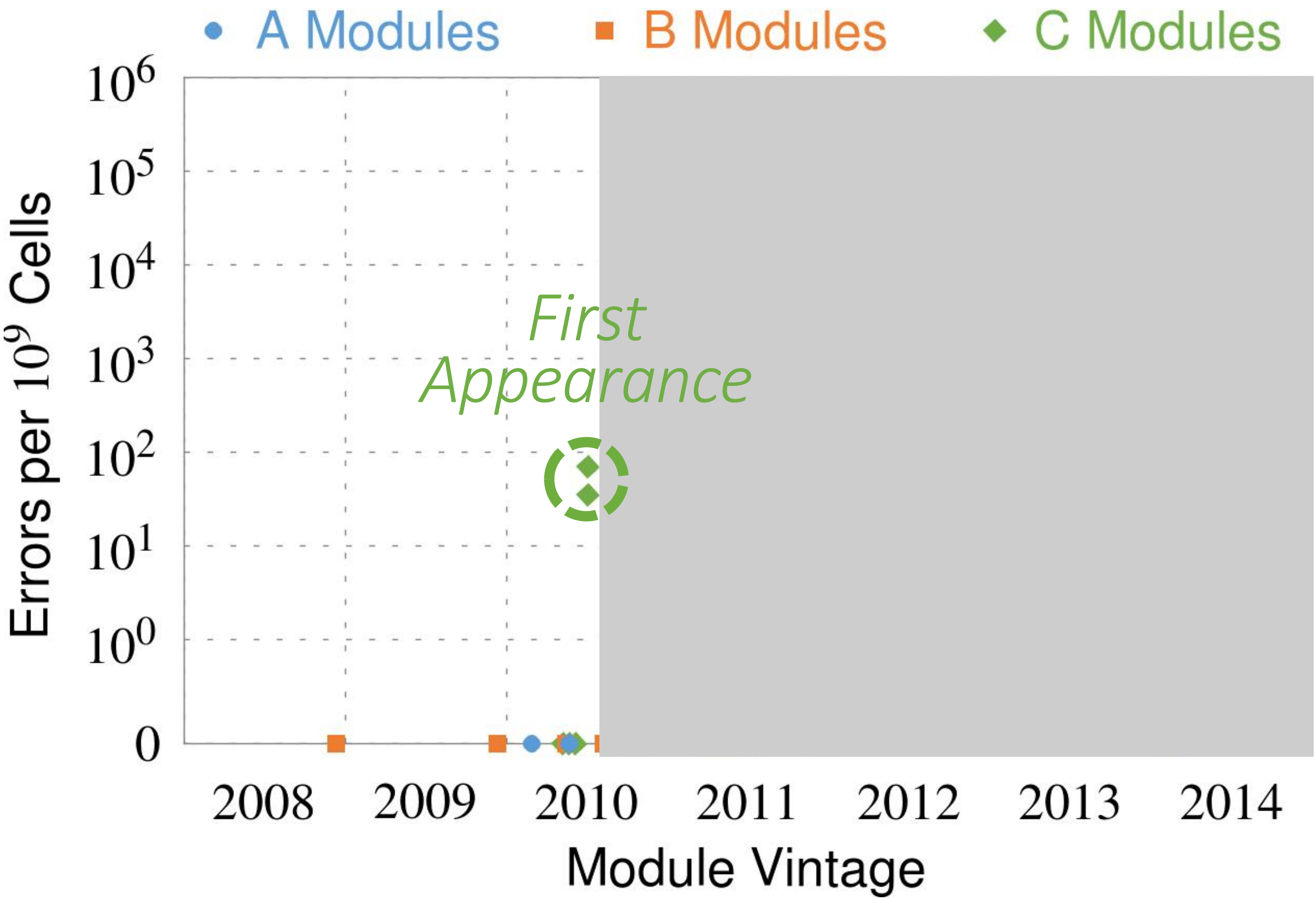
errors

[Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors](), (Kim et al., ISCA 2014)

Recent DRAM Is More Vulnerable

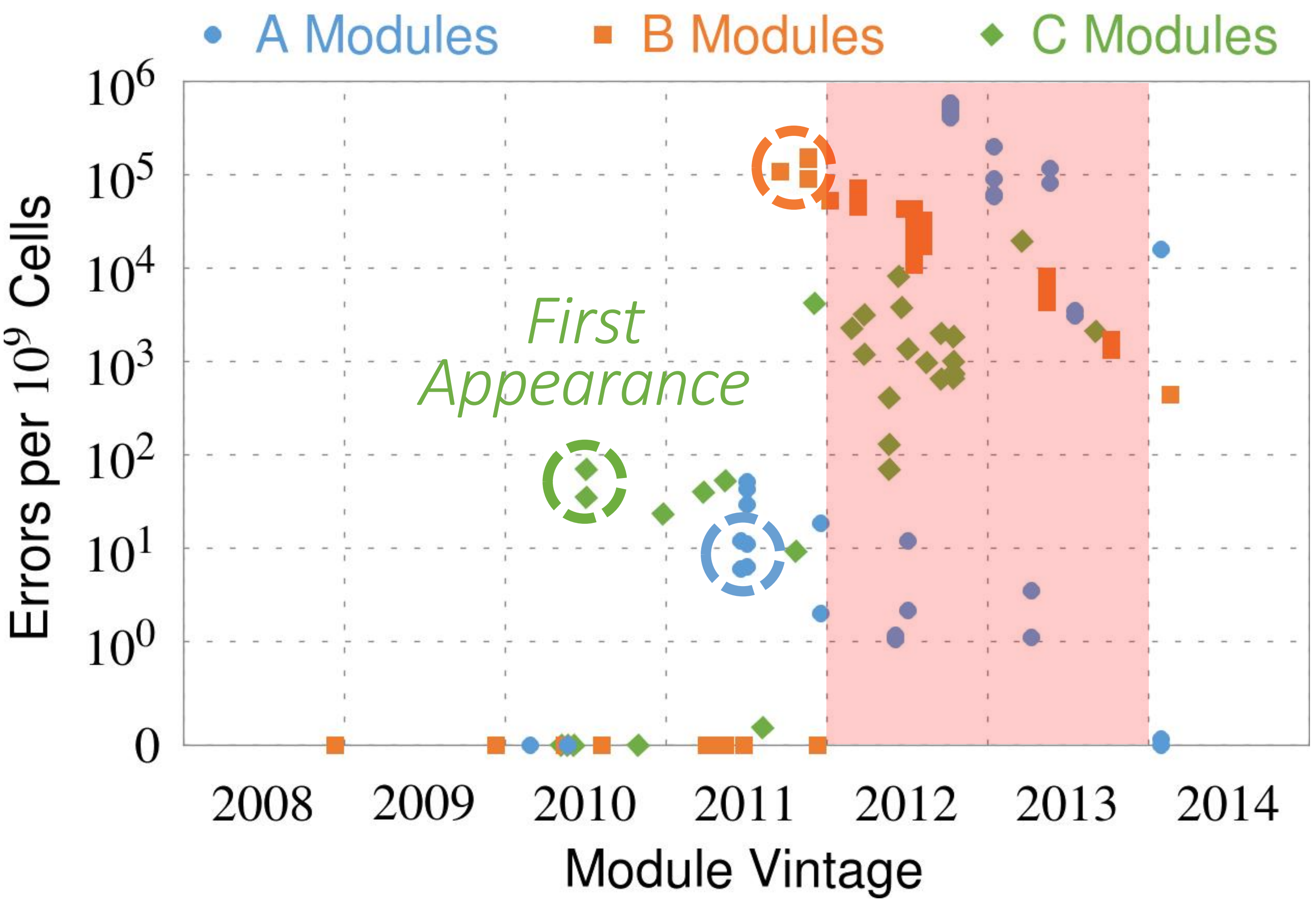


Recent DRAM Is More Vulnerable



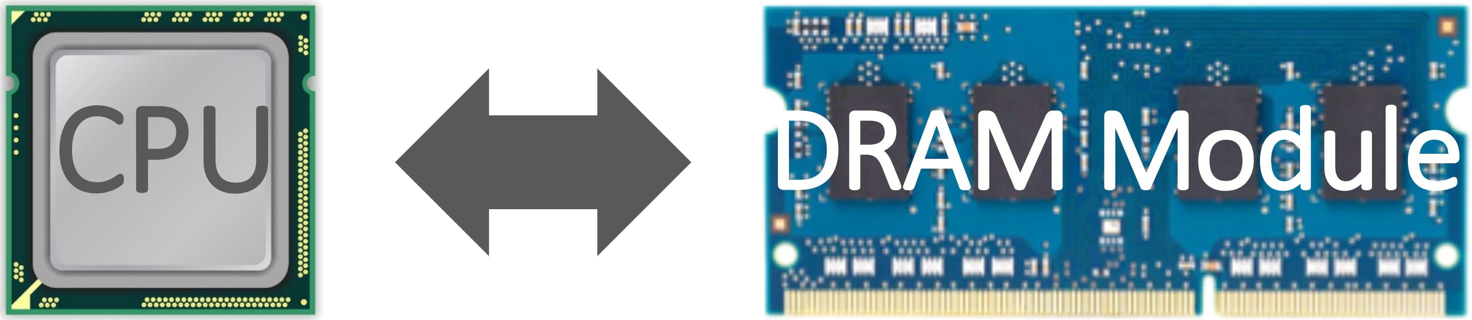
First Appearance

Recent DRAM Is More Vulnerable

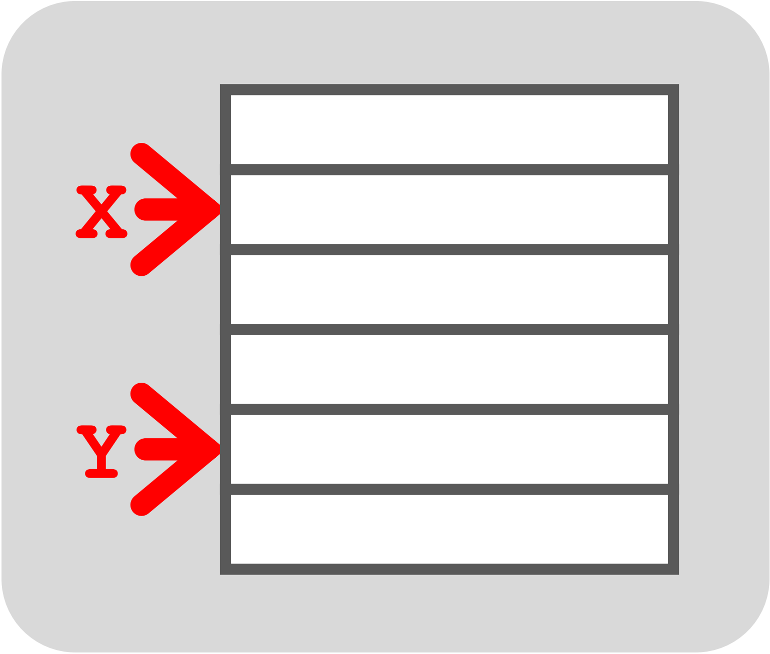


All modules from 2012–2013 are vulnerable

A Simple Program Can Induce Many Errors

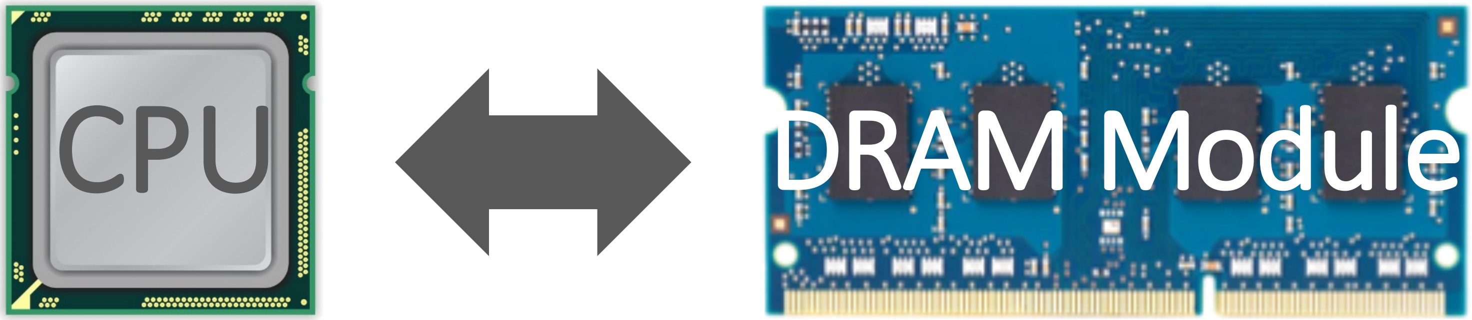


```
loop:
   mov  (X), %eax
   mov  (Y), %ebx
   clflush (X)
   clflush (Y)
   mfence
   jmp loop
```



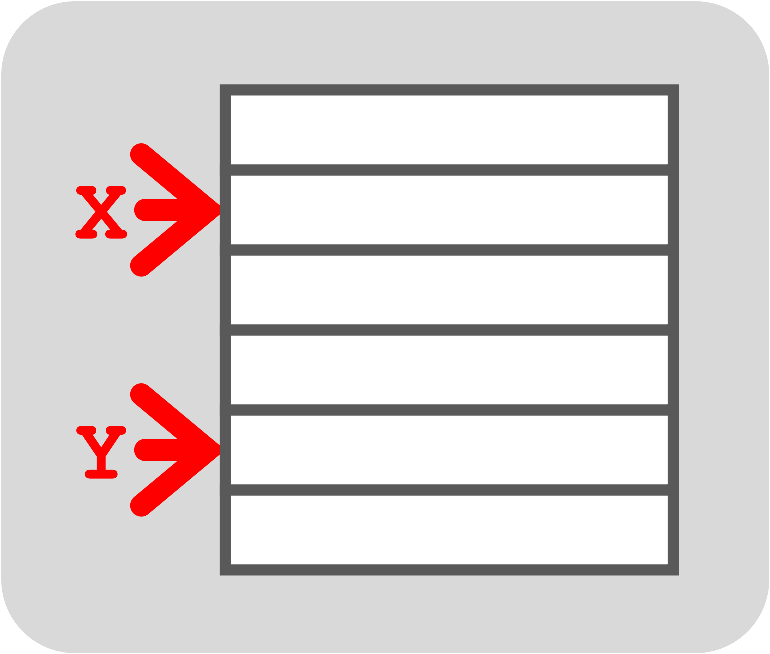
Download from: https://github.com/CMU-SAFARI/rowhammer

A Simple Program Can Induce Many Errors



1. Avoid ***cache hits***
   - Flush **X** from cache

2. Avoid ***row hits*** to **X**
   - Read **Y** in another row



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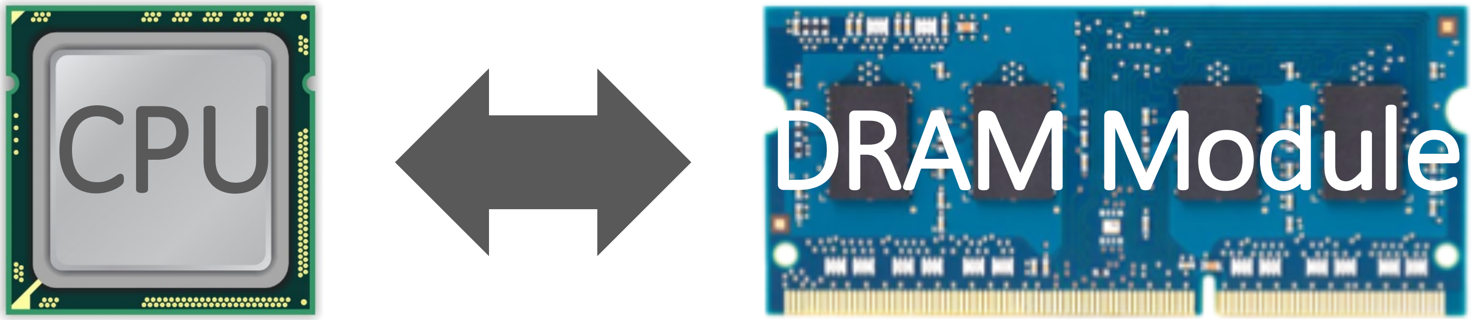

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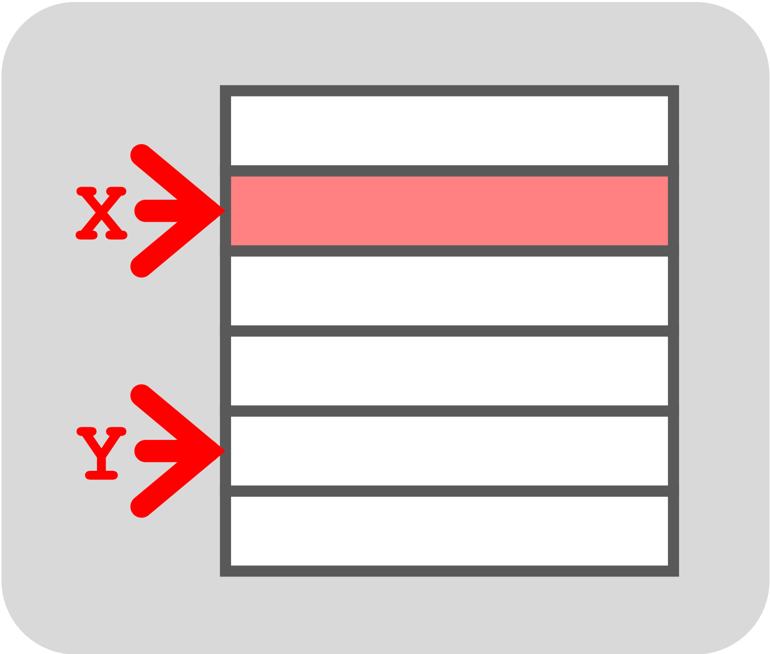
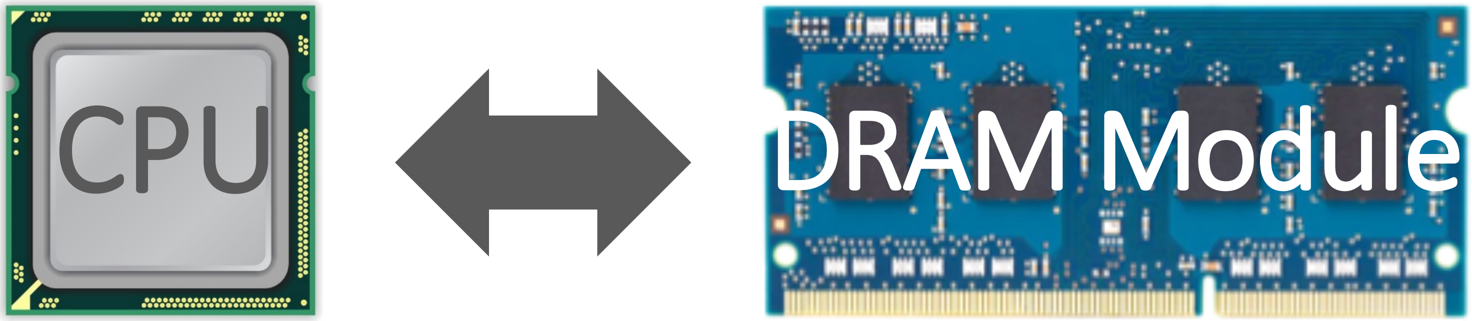


Download from: https://github.com/CMU-SAFARI/rowhammer

A Simple Program Can Induce Many Errors



```
loop:
  mov (X), %eax
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  clflush (X)
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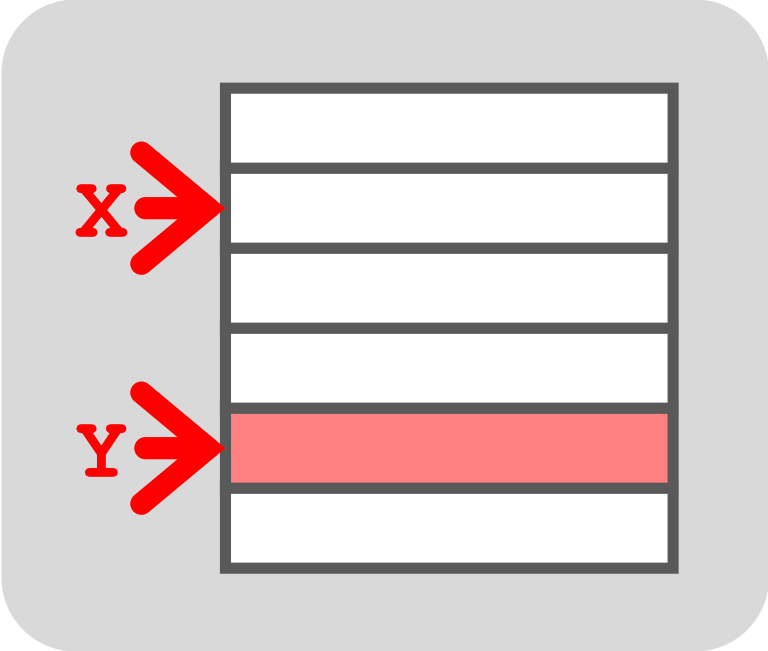
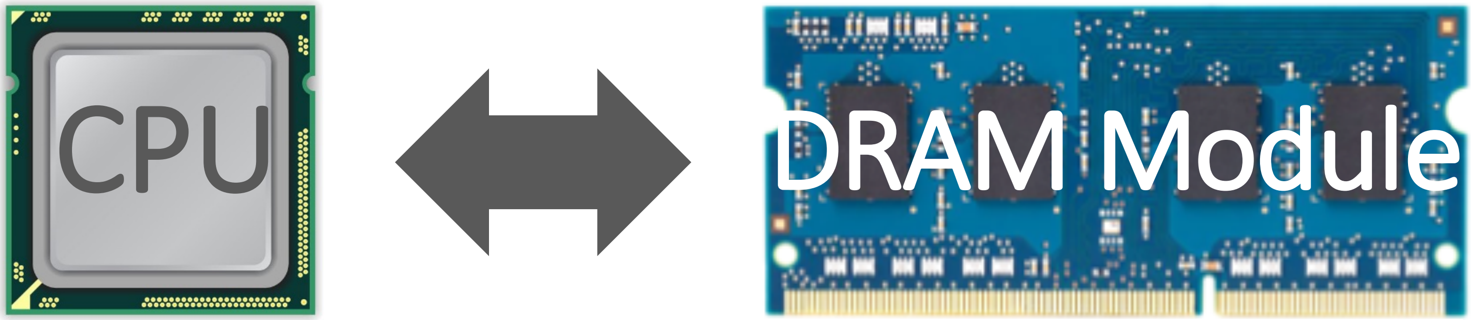
  mfence
  jmp loop
```



Download from: https://github.com/CMU-SAFARI/rowhammer

A Simple Program Can Induce Many Errors



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loop:
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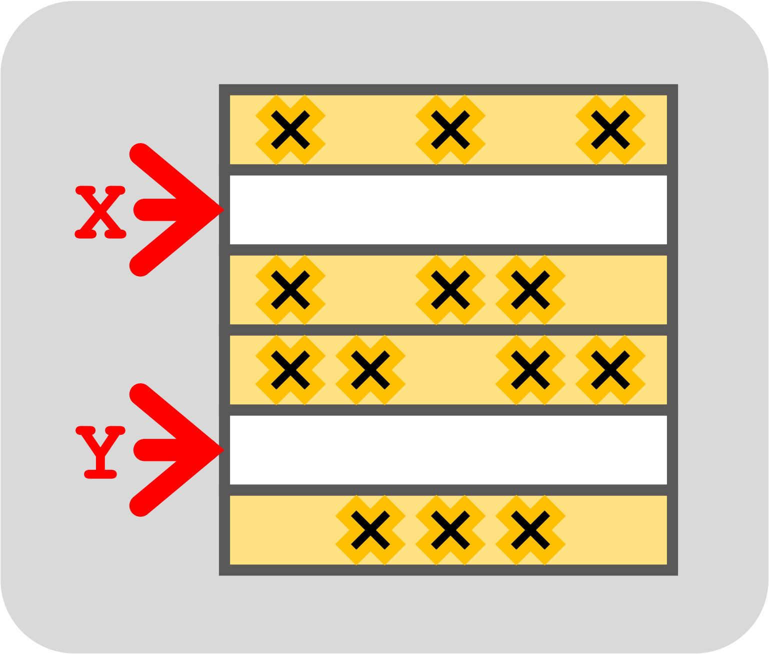
```



Download from: https://github.com/CMU-SAFARI/rowhammer

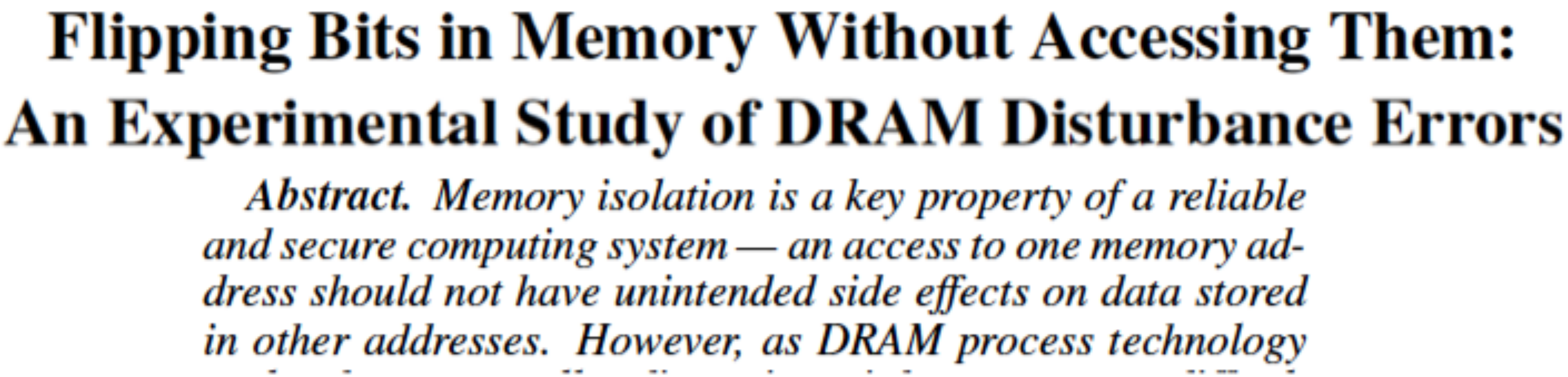
Observed Errors in Real Systems

CPU Architecture	Errors	Access-Rate
Intel Haswell (2013)	22.9K	12.3M/sec
Intel Ivy Bridge (2012)	20.7K	11.7M/sec
Intel Sandy Bridge (2011)	16.1K	11.6M/sec
AMD Piledriver (2012)	59	6.1M/sec

A real reliability & security issue

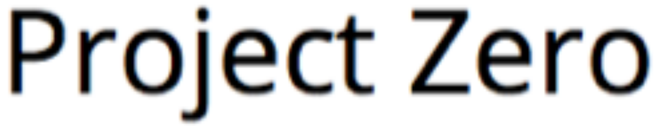
Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.

One Can Take Over an Otherwise-Secure System



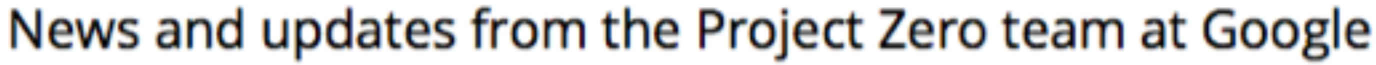
Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors

Abstract. *Memory isolation is a key property of a reliable and secure computing system — an access to one memory address should not have unintended side effects on data stored in other addresses. However, as DRAM process technology*



Project Zero

Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors (Kim et al., ISCA 2014)



News and updates from the Project Zero team at Google

Exploiting the DRAM rowhammer bug to gain kernel privileges (Seaborn, 2015)

Monday, March 9, 2015

Exploiting the DRAM rowhammer bug to gain kernel privileges

RowHammer Security Attack Example

- "Rowhammer" is a problem with some recent DRAM devices in which repeatedly accessing a row of memory can cause bit flips in adjacent rows (Kim et al., ISCA 2014).
  - Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors (Kim et al., ISCA 2014)

- We tested a selection of laptops and found that a subset of them exhibited the problem.
- We built two working privilege escalation exploits that use this effect.
  - Exploiting the DRAM rowhammer bug to gain kernel privileges (Seaborn+, 2015)

- One exploit uses rowhammer-induced bit flips to gain kernel privileges on x86-64 Linux when run as an unprivileged userland process.
- When run on a machine vulnerable to the rowhammer problem, the process was able to induce bit flips in page table entries (PTEs).
- It was able to use this to gain write access to its own page table, and hence gain read-write access to all of physical memory.

Exploiting the DRAM rowhammer bug to gain kernel privileges (Seaborn & Dullien, 2015)

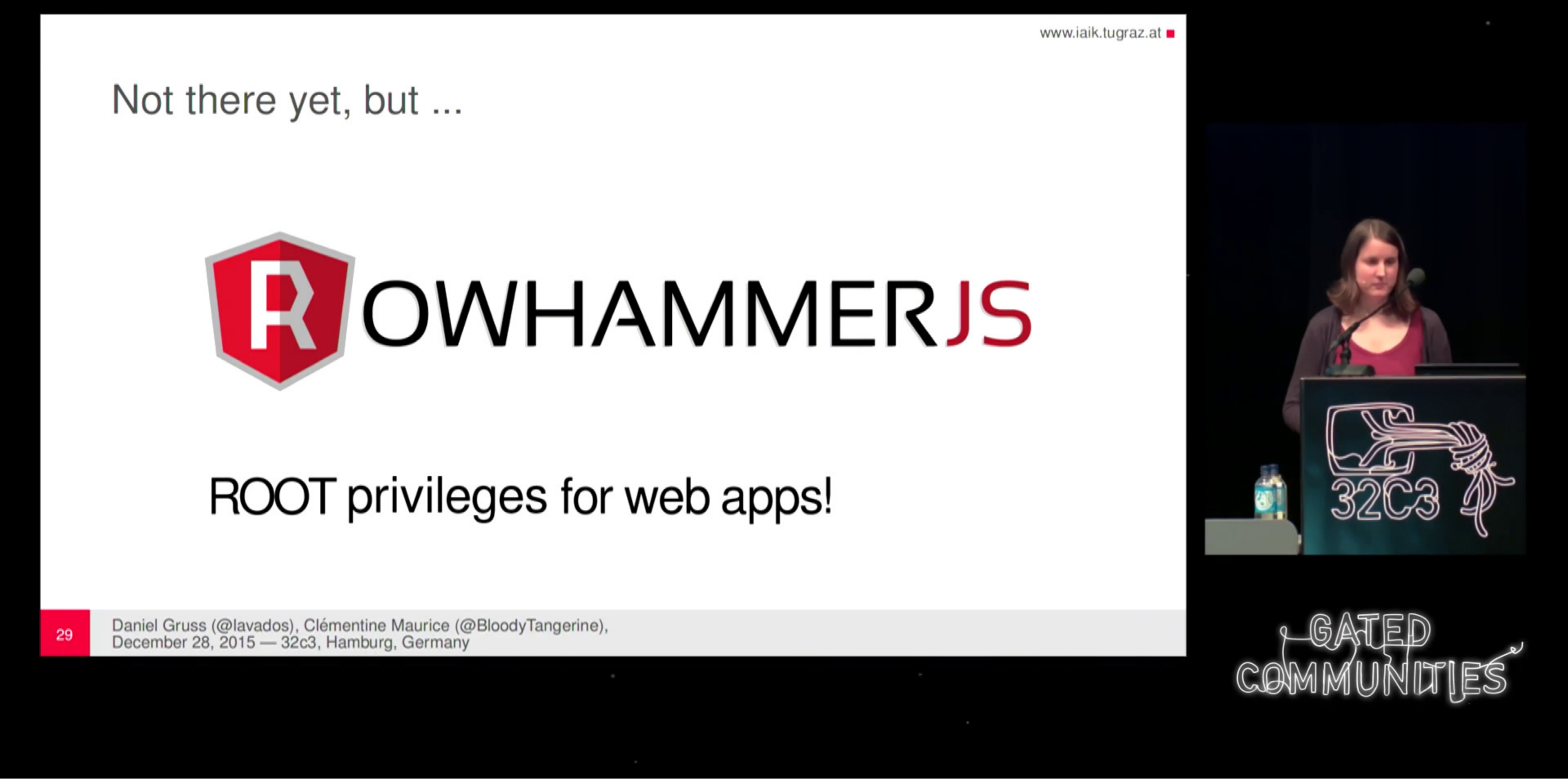
Security Implications

Security Implications

It’s like breaking into an apartment by repeatedly slamming a neighbor’s door until the vibrations open the door you were after

More Security Implications (I)

“We can gain unrestricted access to systems of website visitors.”



www.iaik.tugraz.at

Not there yet, but ...

ROWHAMMERJS

ROOT privileges for web apps!

29 Daniel Gruss (@lavados), Clémentine Maurice (@BloodyTangerine), December 28, 2015 — 32c3, Hamburg, Germany

Rowhammer.js: A Remote Software-Induced Fault Attack in JavaScript (DIMVA’16)

Source: https://lab.dsst.io/32c3-slides/7197.html

More Security Implications (II)

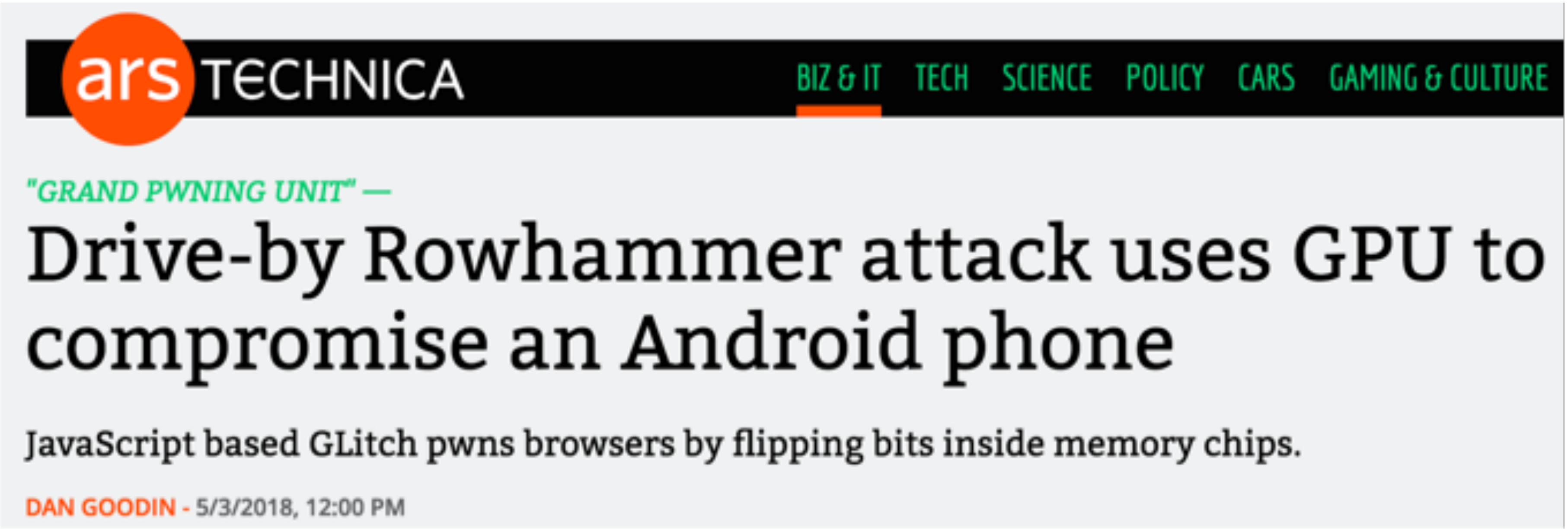
"Can gain control of a smart phone deterministically"

Source: https://fossbytes.com/drammer-rowhammer-attack-android-root-devices/

Drammer: Deterministic Rowhammer Attacks on Mobile Platforms, CCS'16

More Security Implications (III)

- Using an integrated GPU in a mobile system to remotely escalate privilege via the WebGL interface

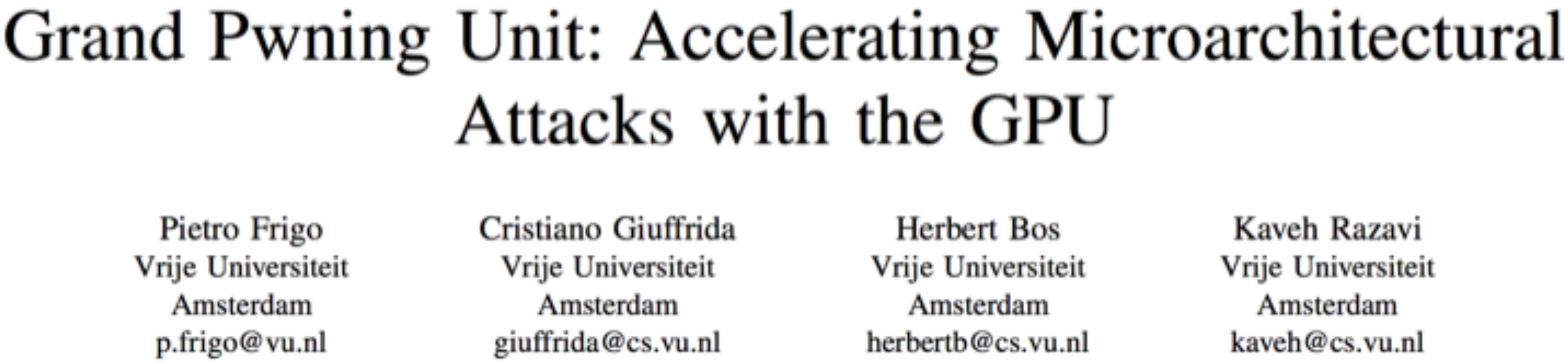


"GRAND PWNING UNIT" —

Drive-by Rowhammer attack uses GPU to compromise an Android phone

JavaScript based GLitch pwns browsers by flipping bits inside memory chips.

DAN GOODIN - 5/3/2018, 12:00 PM



Grand Pwning Unit: Accelerating Microarchitectural Attacks with the GPU

Pietro Frigo
Vrije Universiteit
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Cristiano Giuffrida
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Herbert Bos
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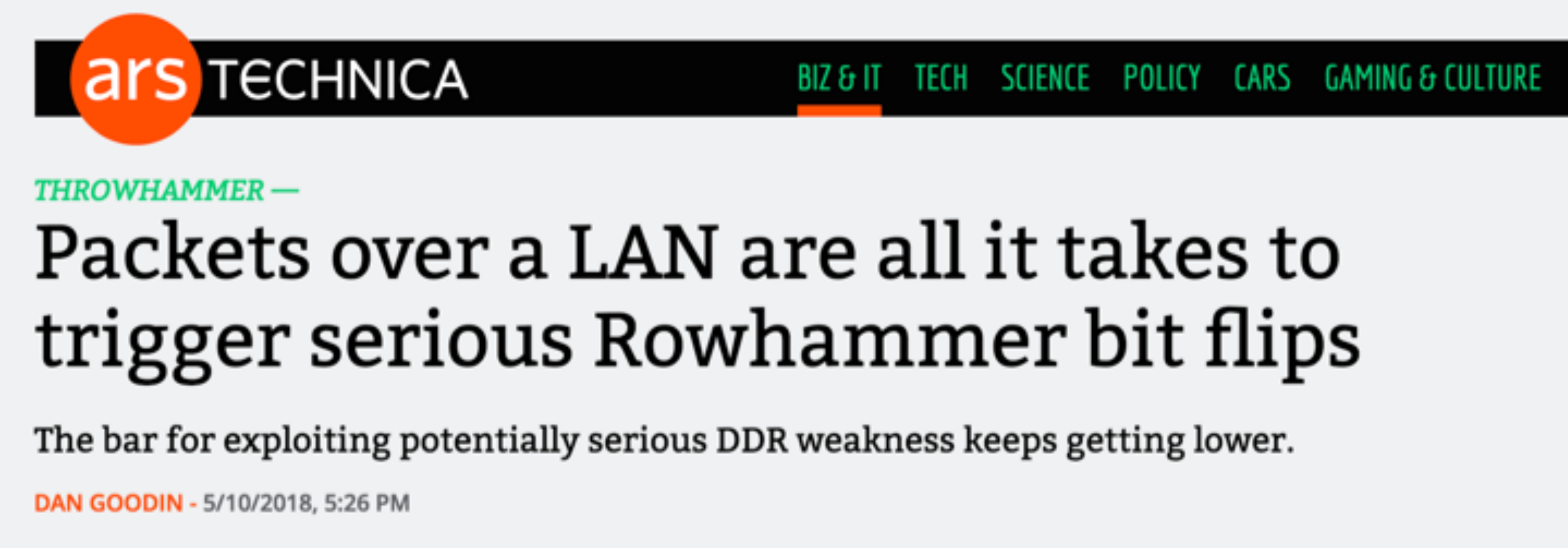
herbertb@cs.vu.nl

Kaveh Razavi
Vrije Universiteit
Amsterdam
kaveh@cs.vu.nl

More Security Implications (IV)

- Rowhammer over RDMA (I)

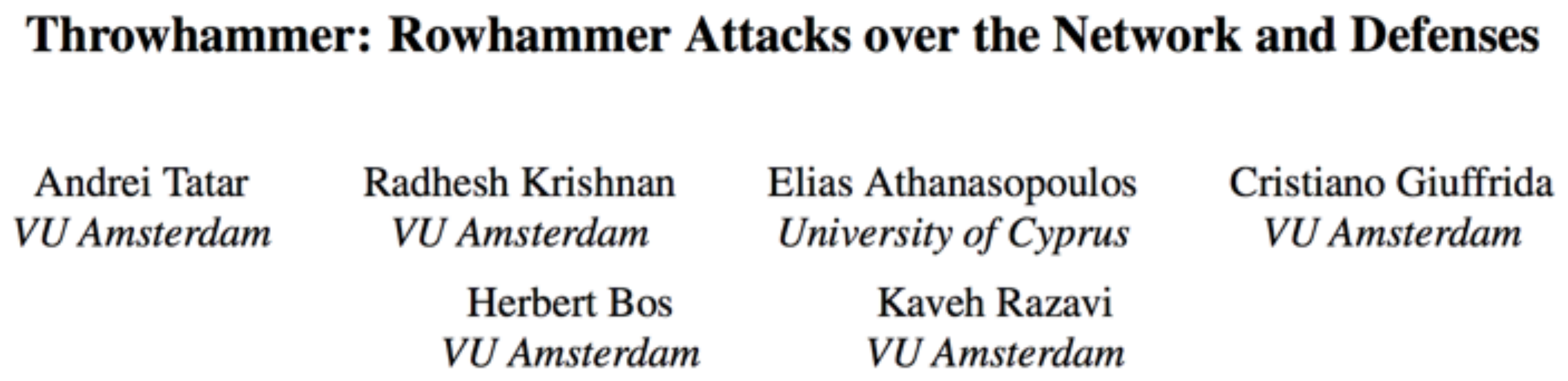


THROWHAMMER —

Packets over a LAN are all it takes to trigger serious Rowhammer bit flips

The bar for exploiting potentially serious DDR weakness keeps getting lower.

DAN GOODIN - 5/10/2018, 5:26 PM



Throwhammer: Rowhammer Attacks over the Network and Defenses

Andrei Tatar
VU Amsterdam

Radhesh Krishnan
VU Amsterdam

Elias Athanasopoulos
University of Cyprus

Cristiano Giuffrida
VU Amsterdam

Herbert Bos
VU Amsterdam

Kaveh Razavi
VU Amsterdam

More Security Implications (V)

- Rowhammer over RDMA (II)


The Hacker News™
Security in a serious way

Nethammer—Exploiting DRAM Rowhammer Bug Through Network Requests


Nethammer:
Inducing Rowhammer Faults through Network Requests

Moritz Lipp
Graz University of Technology

Misiker Tadesse Aga
University of Michigan

Michael Schwarz
Graz University of Technology

Daniel Gruss
Graz University of Technology

Clémentine Maurice
Univ Rennes, CNRS, IRISA

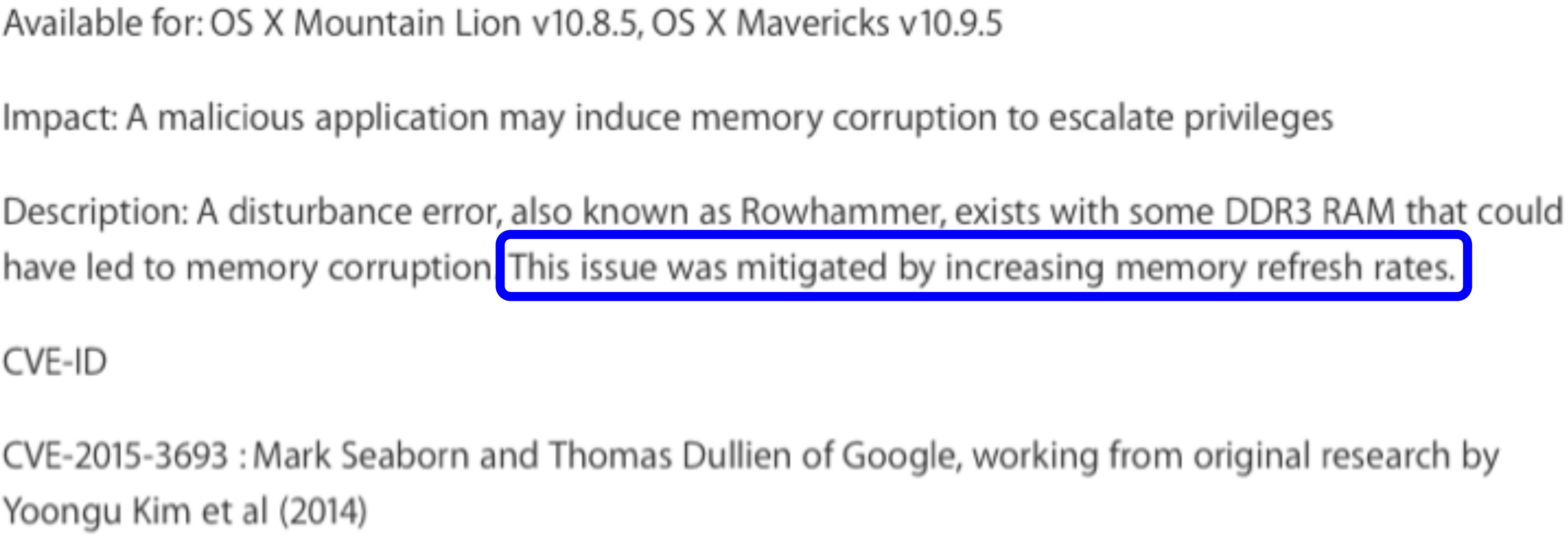
Lukas Raab
Graz University of Technology

Lukas Lamster
Graz University of Technology

More Security Implications?

Apple's Patch for RowHammer

- https://support.apple.com/en-gb/HT204934



Available for: OS X Mountain Lion v10.8.5, OS X Mavericks v10.9.5

Impact: A malicious application may induce memory corruption to escalate privileges

Description: A disturbance error, also known as Rowhammer, exists with some DDR3 RAM that could have led to memory corruption. This issue was mitigated by increasing memory refresh rates.

CVE-ID

CVE-2015-3693 : Mark Seaborn and Thomas Dullien of Google, working from original research by Yoongu Kim et al (2014)

HP, Lenovo, and other vendors released similar patches

Our Solution to RowHammer

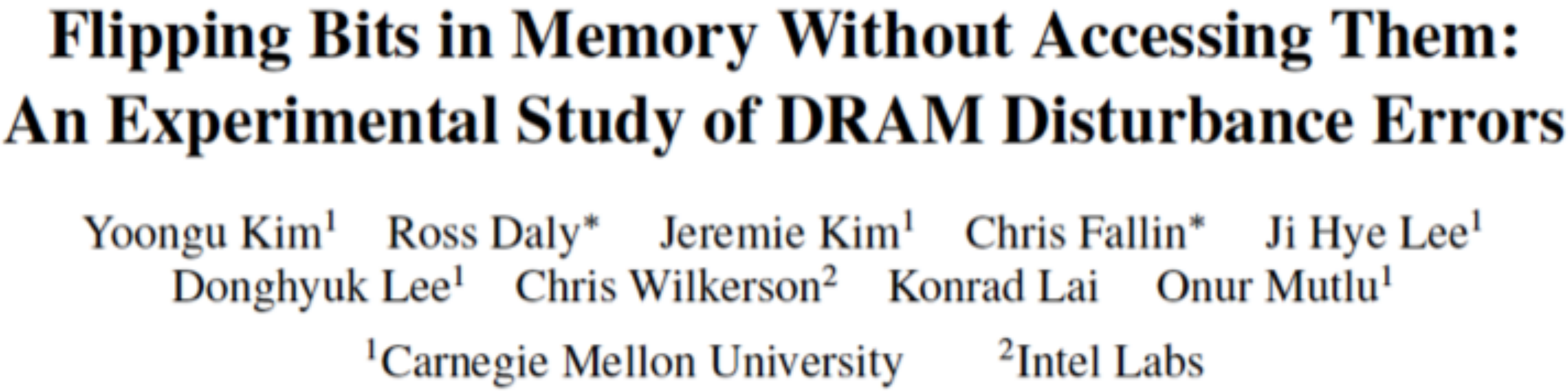
- **PARA**: *Probabilistic Adjacent Row Activation*

- Key Idea
  - After closing a row, we activate (i.e., refresh) one of its neighbors with a low probability: $p = 0.005$

- Reliability Guarantee
  - When $p=0.005$, errors in one year: 9.4×10^{-14}
  - By adjusting the value of p, we can vary the strength of protection against errors

More on RowHammer Analysis

- Yoongu Kim, Ross Daly, Jeremie Kim, Chris Fallin, Ji Hye Lee, Donghyuk Lee, Chris Wilkerson, Konrad Lai, and Onur Mutlu,
  "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors"
  Proceedings of the 41st International Symposium on Computer Architecture (***ISCA***), Minneapolis, MN, June 2014.
  [Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)] [Source Code and Data]



Flipping Bits in Memory Without Accessing Them:
An Experimental Study of DRAM Disturbance Errors

Yoongu Kim[1] Ross Daly* Jeremie Kim[1] Chris Fallin* Ji Hye Lee[1]
Donghyuk Lee[1] Chris Wilkerson[2] Konrad Lai Onur Mutlu[1]
[1]Carnegie Mellon University [2]Intel Labs

Future of Memory Reliability

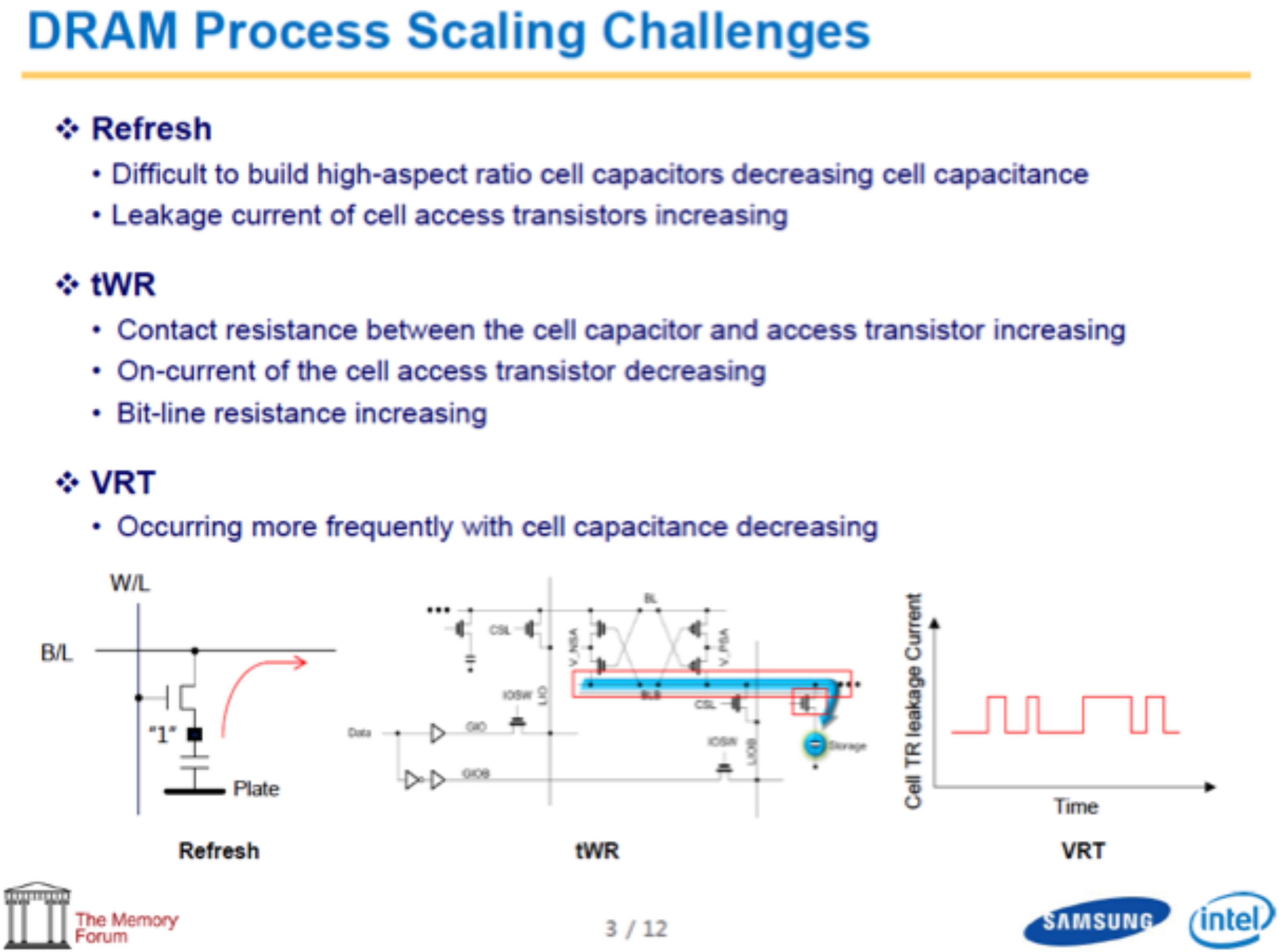
- Onur Mutlu,
  "The RowHammer Problem and Other Issues We May Face as Memory Becomes Denser"
  Invited Paper in Proceedings of the Design, Automation, and Test in Europe Conference (***DATE***), Lausanne, Switzerland, March 2017.
  [Slides (pptx) (pdf)]

The RowHammer Problem
and Other Issues We May Face as Memory Becomes Denser

Onur Mutlu
ETH Zürich
onur.mutlu@inf.ethz.ch
https://people.inf.ethz.ch/omutlu

https://people.inf.ethz.ch/omutlu/pub/rowhammer-and-other-memory-issues_date17.pdf

Industry Is Writing Papers About It, Too



DRAM Process Scaling Challenges

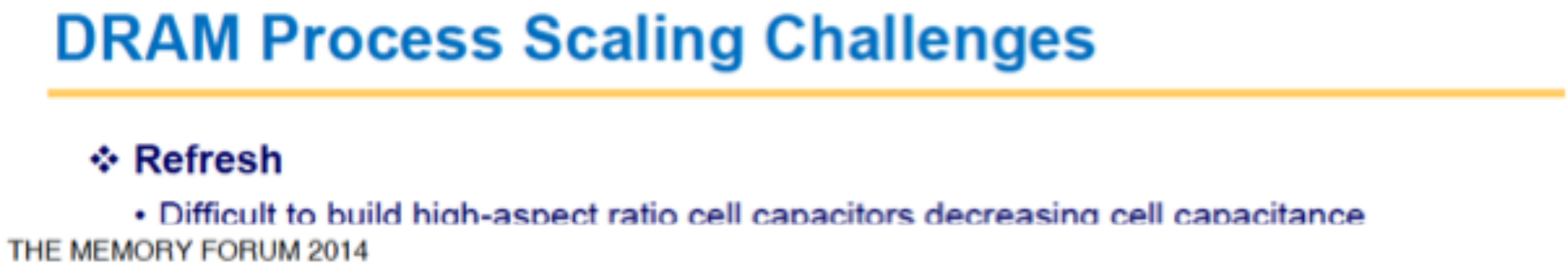
- **Refresh**
  - Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance
  - Leakage current of cell access transistors increasing
- **tWR**
  - Contact resistance between the cell capacitor and access transistor increasing
  - On-current of the cell access transistor decreasing
  - Bit-line resistance increasing
- **VRT**
  - Occurring more frequently with cell capacitance decreasing

Refresh **tWR** **VRT**

The Memory Forum

3 / 12

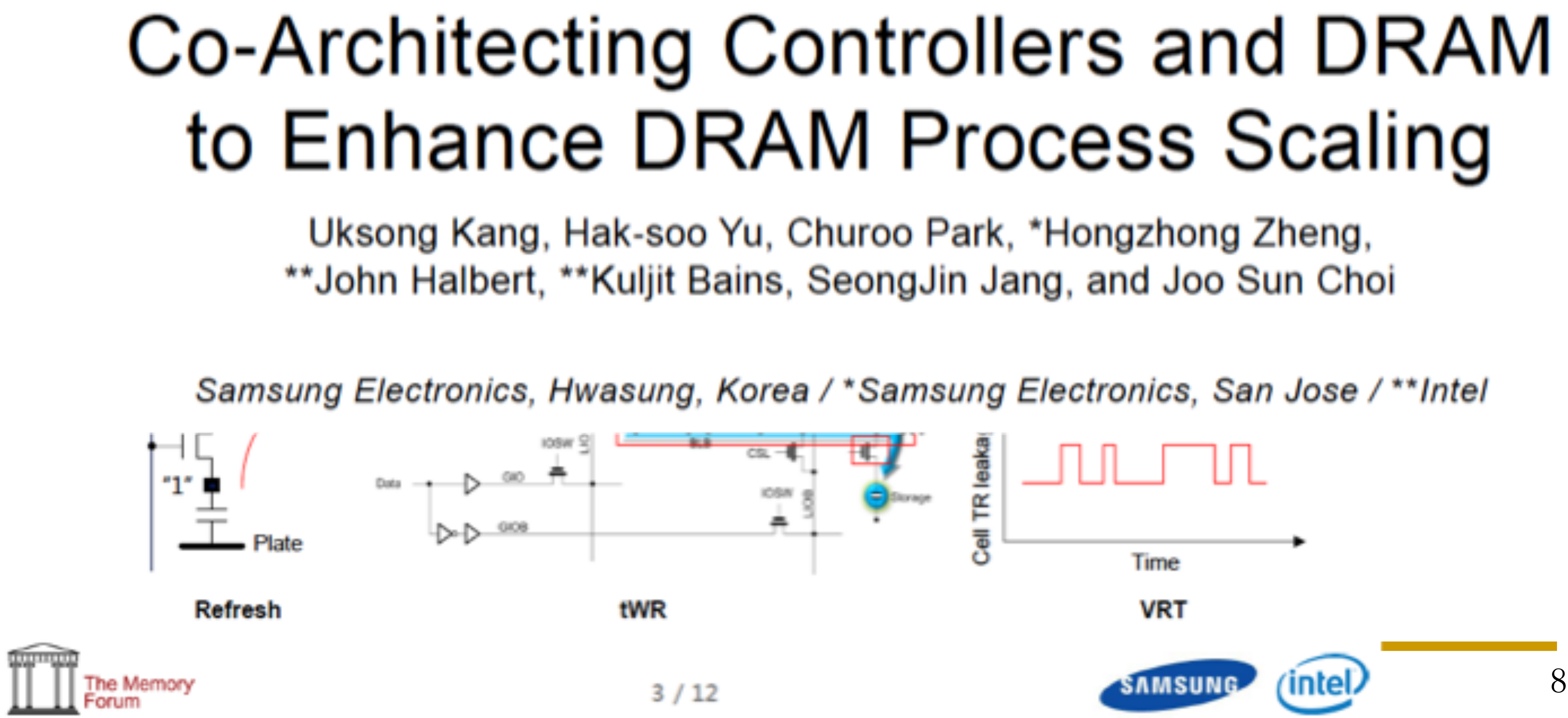
Call for Intelligent Memory Controllers



DRAM Process Scaling Challenges

- **Refresh**
  - Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance

THE MEMORY FORUM 2014



Co-Architecting Controllers and DRAM to Enhance DRAM Process Scaling

Uksong Kang, Hak-soo Yu, Churoo Park, *Hongzhong Zheng,
**John Halbert, **Kuljit Bains, SeongJin Jang, and Joo Sun Choi

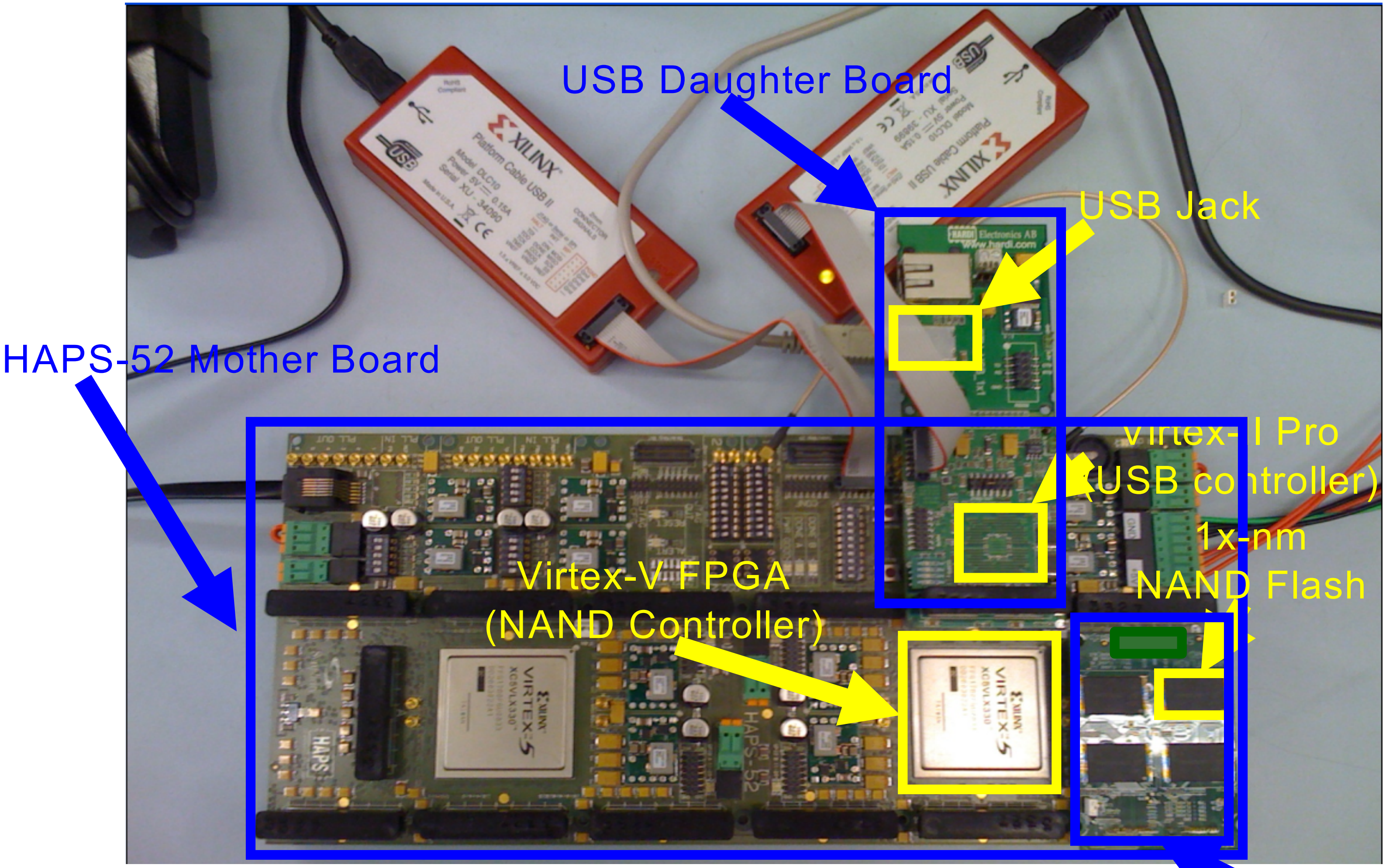
*Samsung Electronics, Hwasung, Korea / *Samsung Electronics, San Jose / **Intel*

Refresh **tWR** **VRT**

The Memory Forum

3 / 12

Aside: Intelligent Controller for NAND Flash

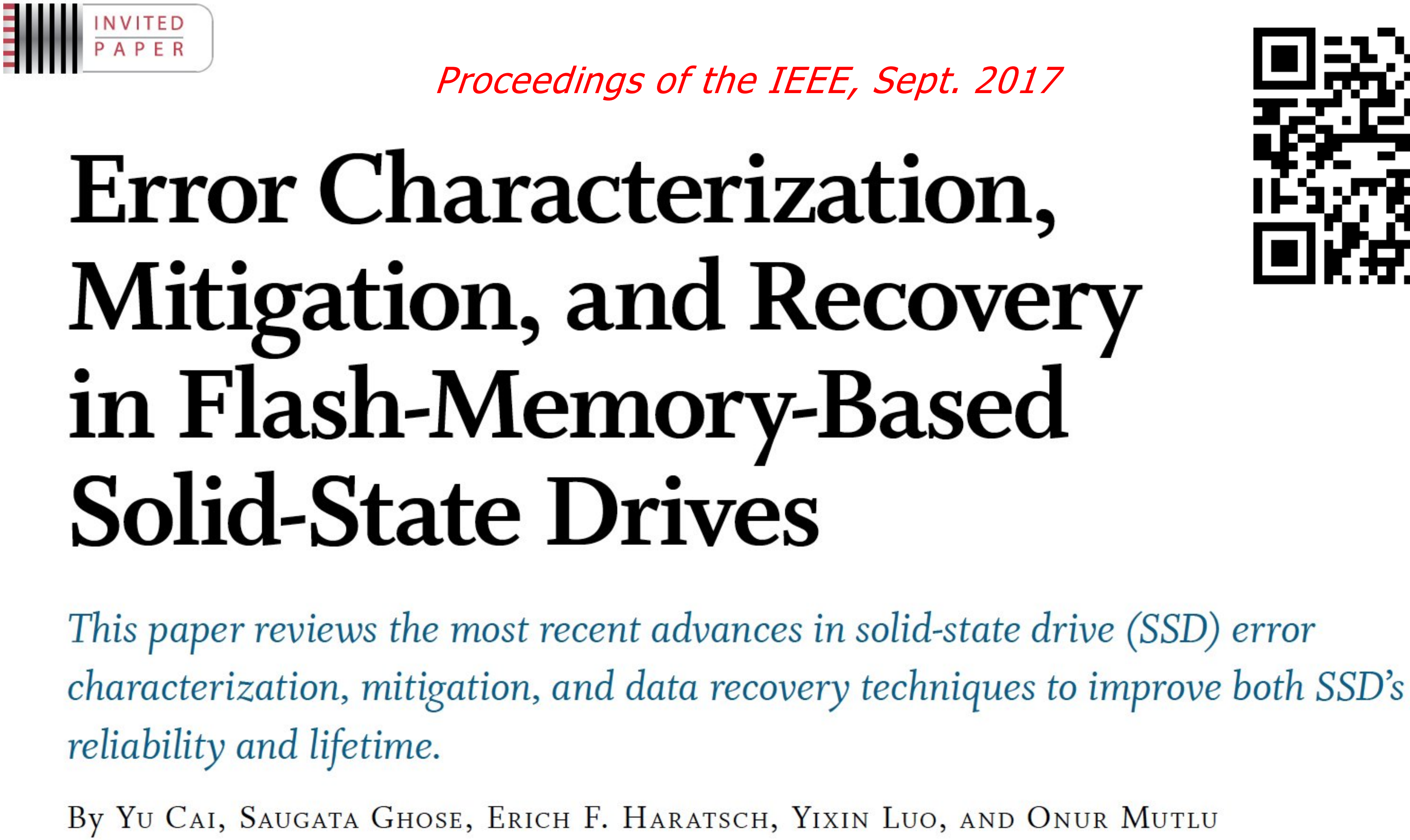


[DATE 2012, ICCD 2012, DATE 2013, ITJ 2013, ICCD 2013, SIGMETRICS 2014, HPCA 2015, DSN 2015, MSST 2015, JSAC 2016, HPCA 2017, DFRWS 2017, PIEEE 2017, HPCA 2018, SIGMETRICS 2018]

Cai+, "Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives," Proc. IEEE 2017.

Aside: Intelligent Controller for NAND Flash

Proceedings of the IEEE, Sept. 2017



INVITED PAPER

Error Characterization, Mitigation, and Recovery in Flash-Memory-Based Solid-State Drives

This paper reviews the most recent advances in solid-state drive (SSD) error characterization, mitigation, and data recovery techniques to improve both SSD's reliability and lifetime.

By Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu

https://arxiv.org/pdf/1706.08642

Takeaway

Main Memory Needs

Intelligent Controllers

Agenda

- Major Trends Affecting Main Memory
- The Need for Intelligent Memory Controllers
  - Bottom Up: Push from Circuits and Devices
  - Top Down: Pull from Systems and Applications
- Processing in Memory: Two Directions
  - Minimally Changing Memory Chips
  - Exploiting 3D-Stacked Memory
- How to Enable Adoption of Processing in Memory
- Conclusion

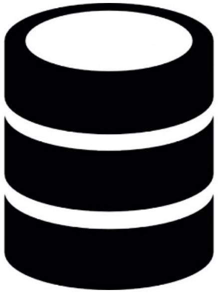
Three Key Systems Trends

1. Data access is a major bottleneck
    - Applications are increasingly data hungry

2. Energy consumption is a key limiter

3. Data movement energy dominates compute
    - Especially true for off-chip to on-chip movement

The Need for More Memory Performance



In-memory Databases

[Mao+, EuroSys'12;
Clapp+ (**Intel**), IISWC'15]

Graph/Tree Processing

[Xu+, IISWC'12; Umuroglu+, FPL'15]

In-Memory Data Analytics

[Clapp+ (**Intel**), IISWC'15;
Awan+, BDCloud'15]

Datacenter Workloads

[Kanev+ (**Google**), ISCA'15]

Challenge and Opportunity for Future

High Performance,

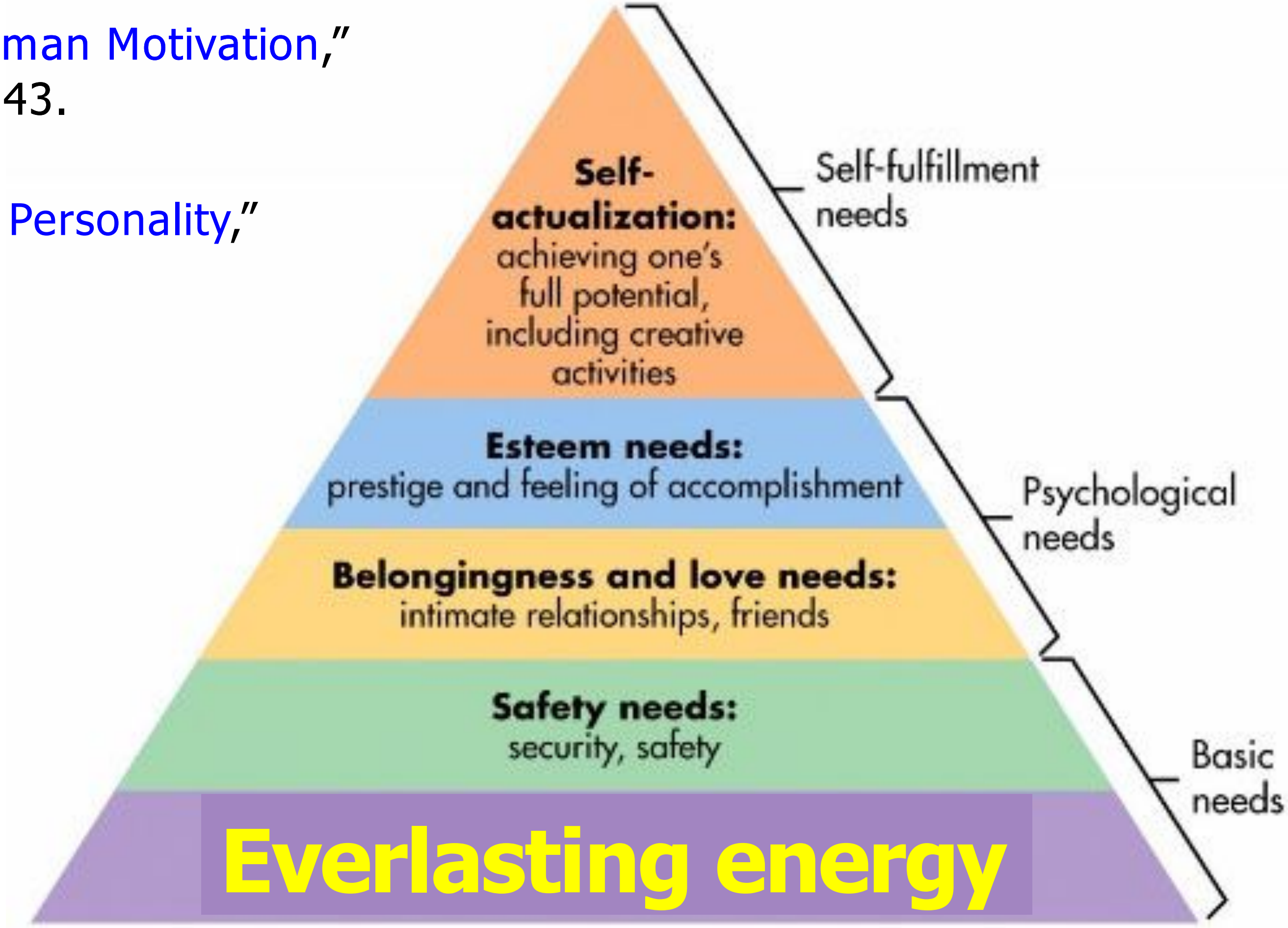
Energy Efficient,

Sustainable

Maslow's (Human) Hierarchy of Needs, Revisited

Maslow, "A Theory of Human Motivation," Psychological Review, 1943.

Maslow, "Motivation and Personality," Book, 1954-1970.



Source: https://www.simplypsychology.org/maslow.html

The Problem

Data access is the major performance and energy bottleneck

Our current

design principles

cause great energy waste

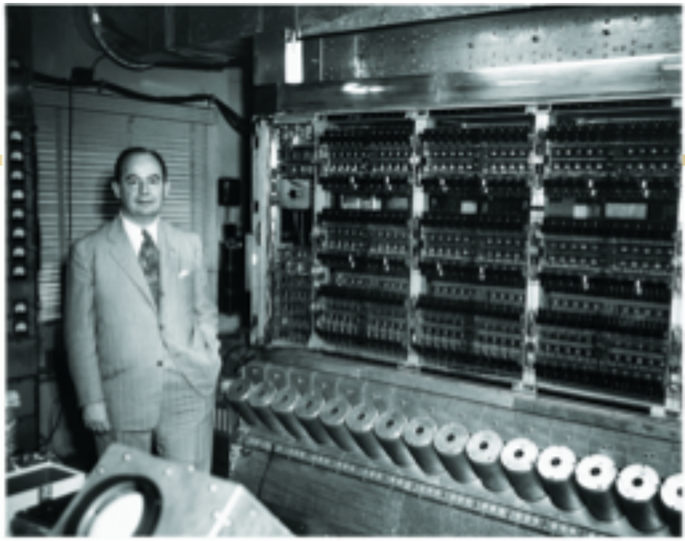
(and great performance loss)

The Problem

Processing of data
is performed
far away from the data

A Computing System

- Three key components
- Computation
- Communication
- Storage/memory



Burks, Goldstein, von Neumann, "Preliminary discussion of the logical design of an electronic computing instrument," 1946.

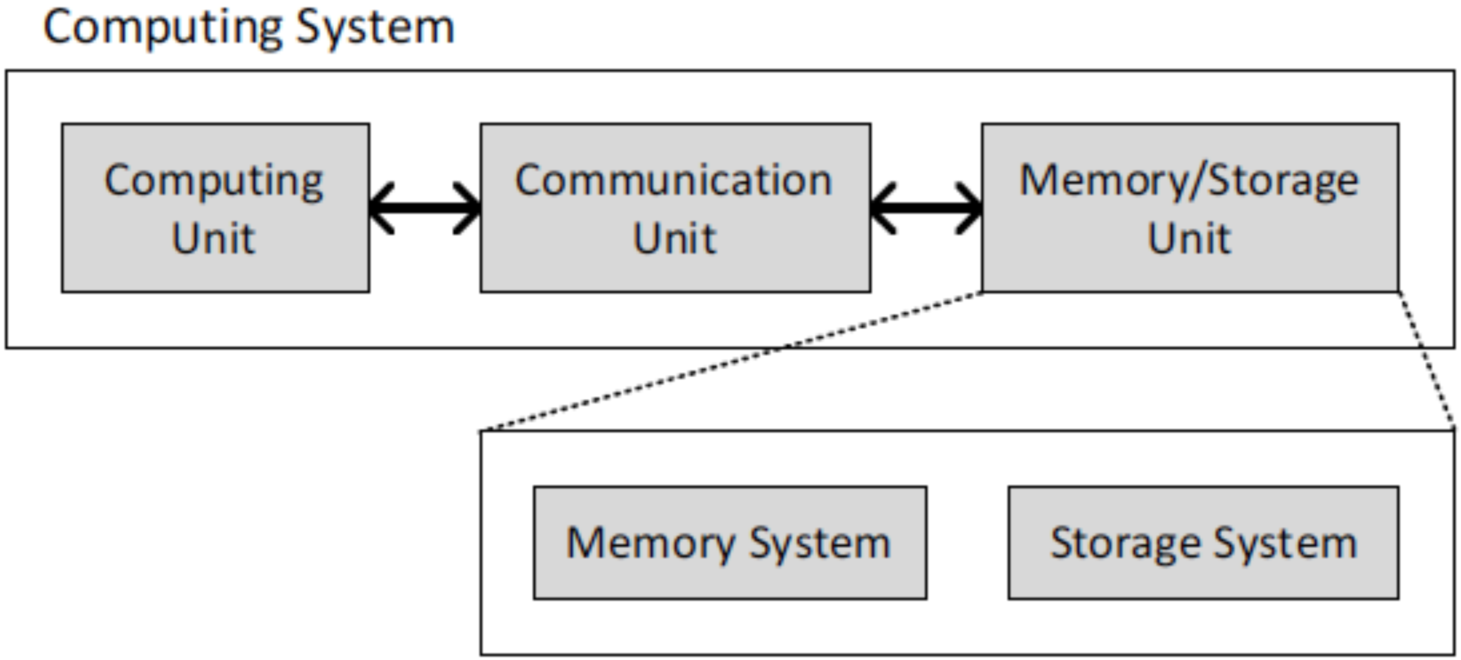


Image source: https://lbsitbytes2010.wordpress.com/2013/03/29/john-von-neumann-roll-no-15/

A Computing System

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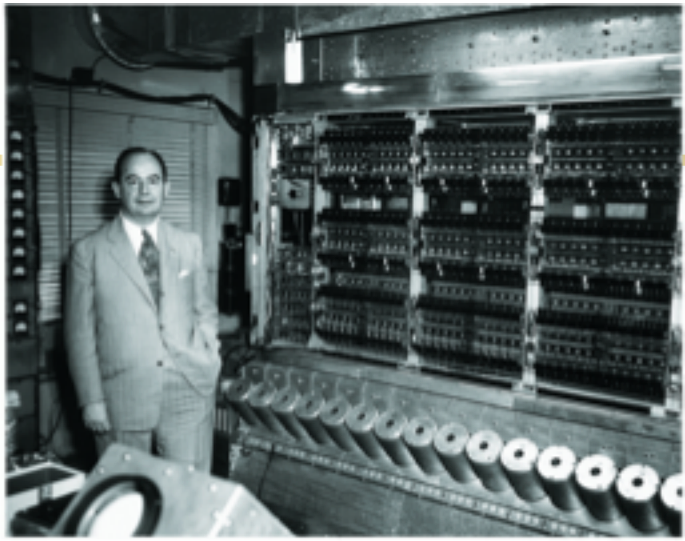


Burks, Goldstein, von Neumann, “Preliminary discussion of the logical design of an electronic computing instrument,” 1946.

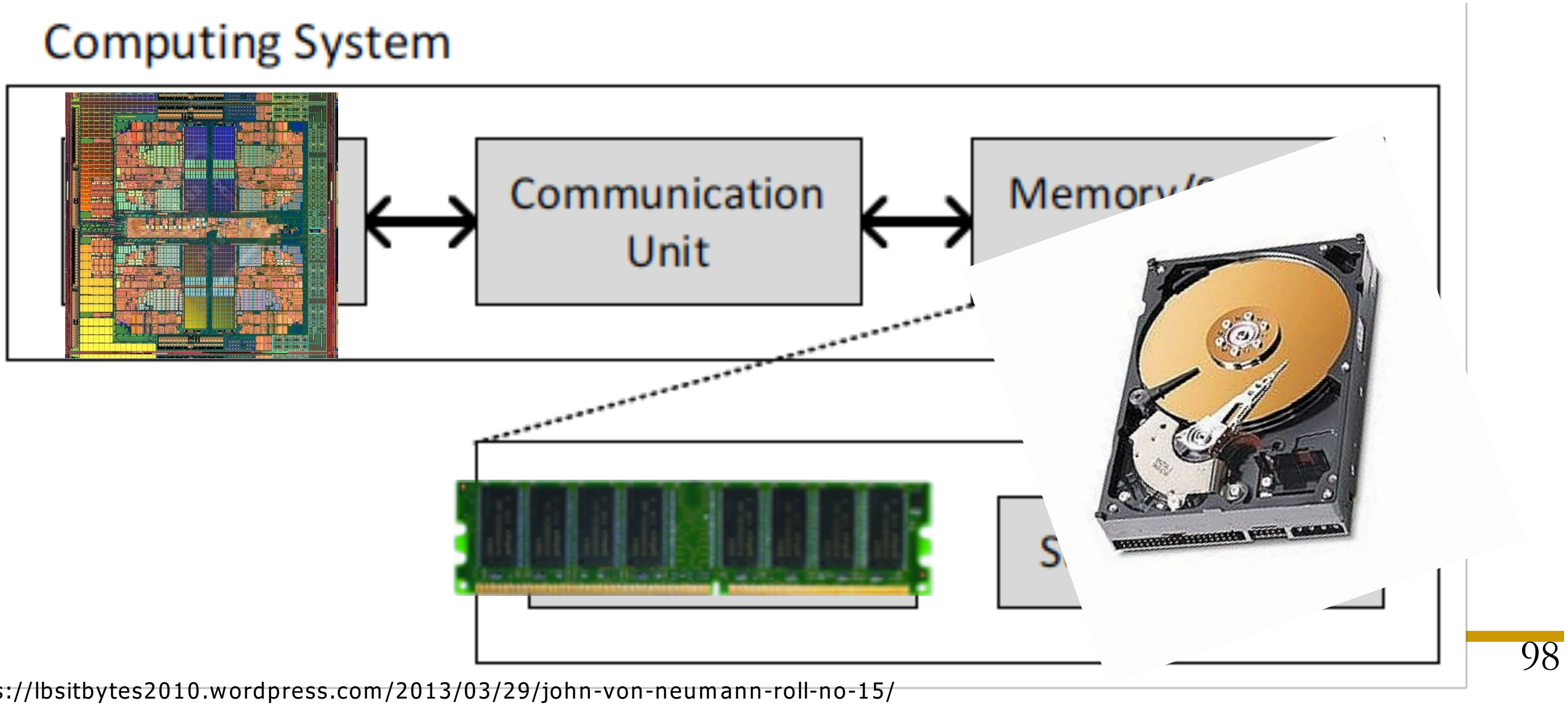
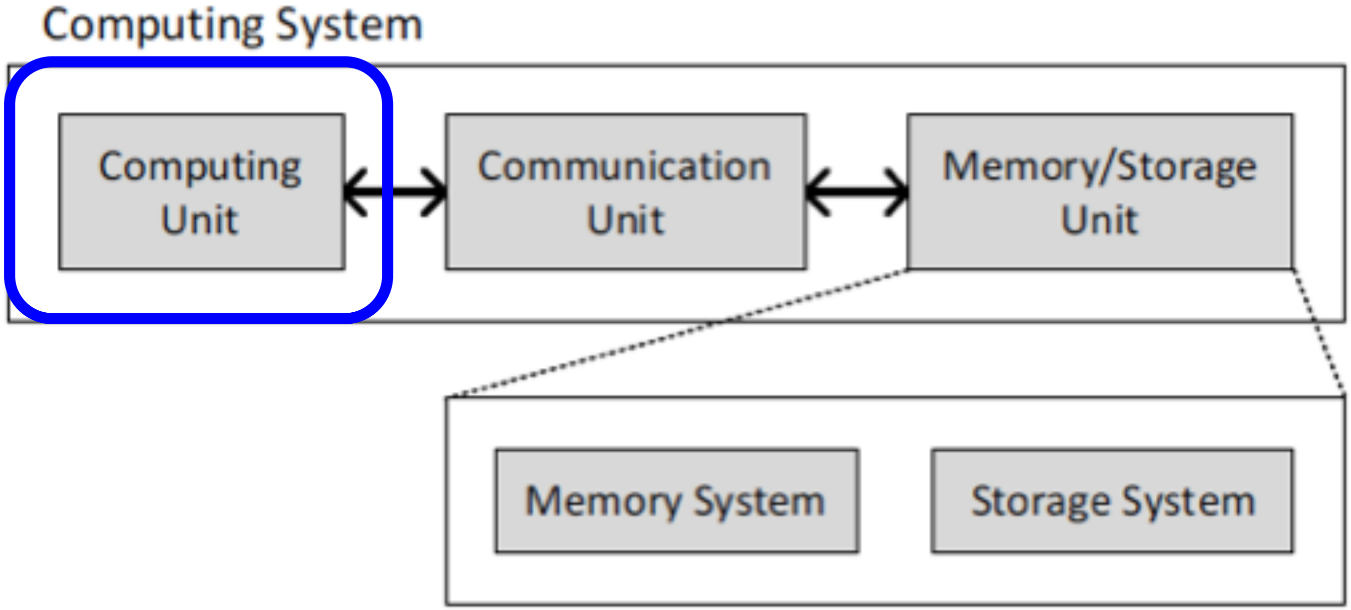


Image source: https://lbsitbytes2010.wordpress.com/2013/03/29/john-von-neumann-roll-no-15/

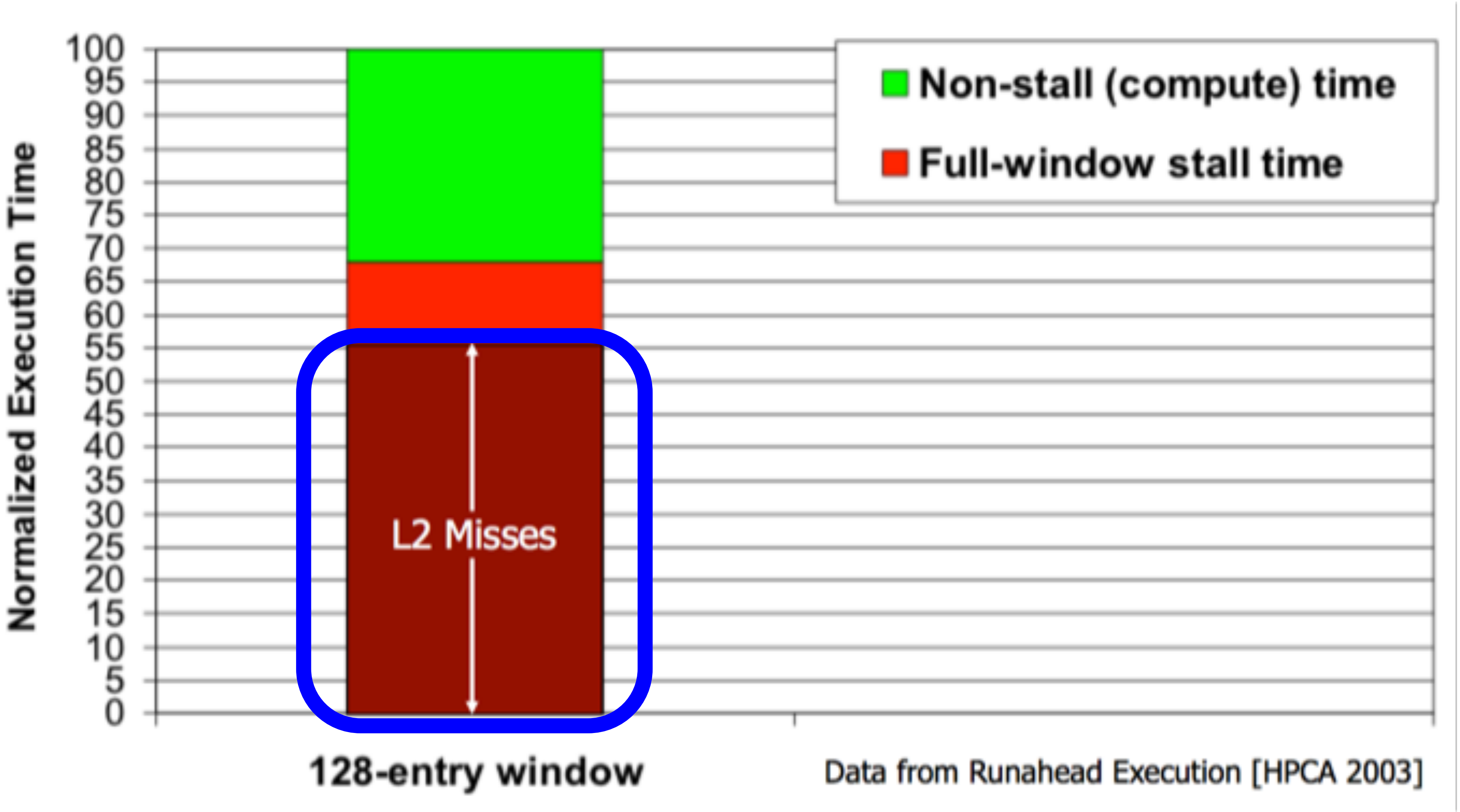
Today's Computing Systems

- Are overwhelmingly processor centric
- All data processed in the processor → at great system cost
- Processor is heavily optimized and is considered the master
- Data storage units are dumb and are largely unoptimized (except for some that are on the processor die)



Yet …

- “**It’s the Memory, Stupid!**” (Richard Sites, MPR, 1996)

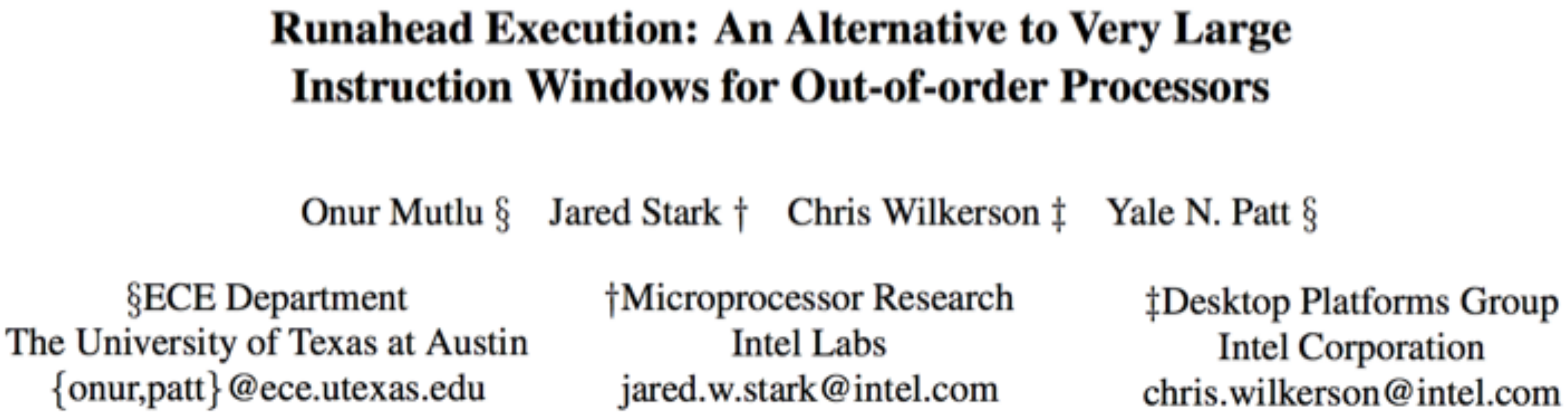


Data from Runahead Execution [HPCA 2003]

Mutlu+, “Runahead Execution: An Alternative to Very Large Instruction Windows for Out-of-Order Processors,” HPCA 2003.

The Performance Perspective

- Onur Mutlu, Jared Stark, Chris Wilkerson, and Yale N. Patt, **"Runahead Execution: An Alternative to Very Large Instruction Windows for Out-of-order Processors"** *Proceedings of the 9th International Symposium on High-Performance Computer Architecture* (***HPCA***), pages 129-140, Anaheim, CA, February 2003. Slides (pdf)



Runahead Execution: An Alternative to Very Large Instruction Windows for Out-of-order Processors

Onur Mutlu § Jared Stark † Chris Wilkerson ‡ Yale N. Patt §

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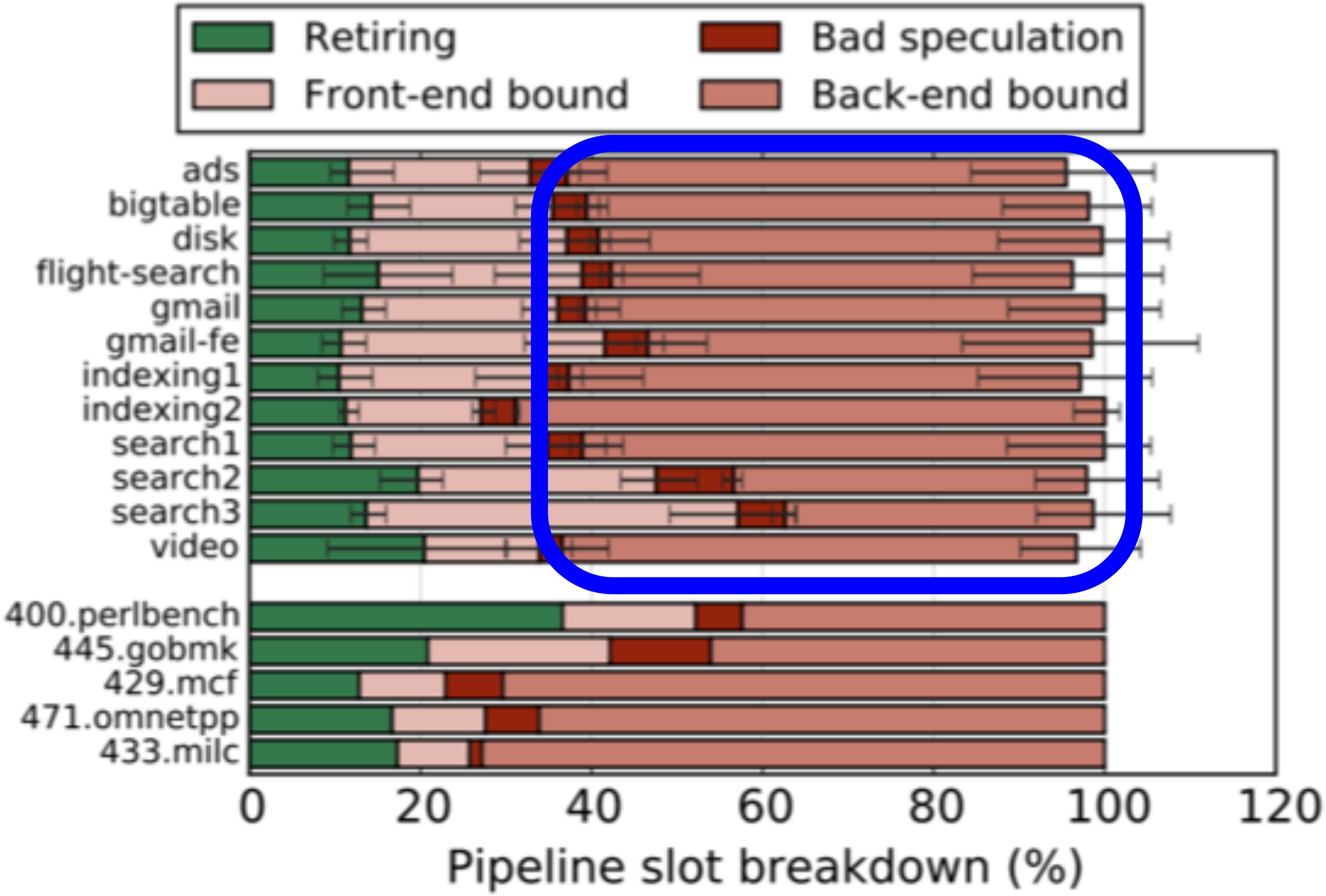
†Microprocessor Research
Intel Labs
jared.w.stark@intel.com

‡Desktop Platforms Group
Intel Corporation
chris.wilkerson@intel.com

The Performance Perspective (Today)

- All of Google's Data Center Workloads (2015):



Kanev+, "Profiling a Warehouse-Scale Computer," ISCA 2015.

The Performance Perspective (Today)

- All of Google's Data Center Workloads (2015):

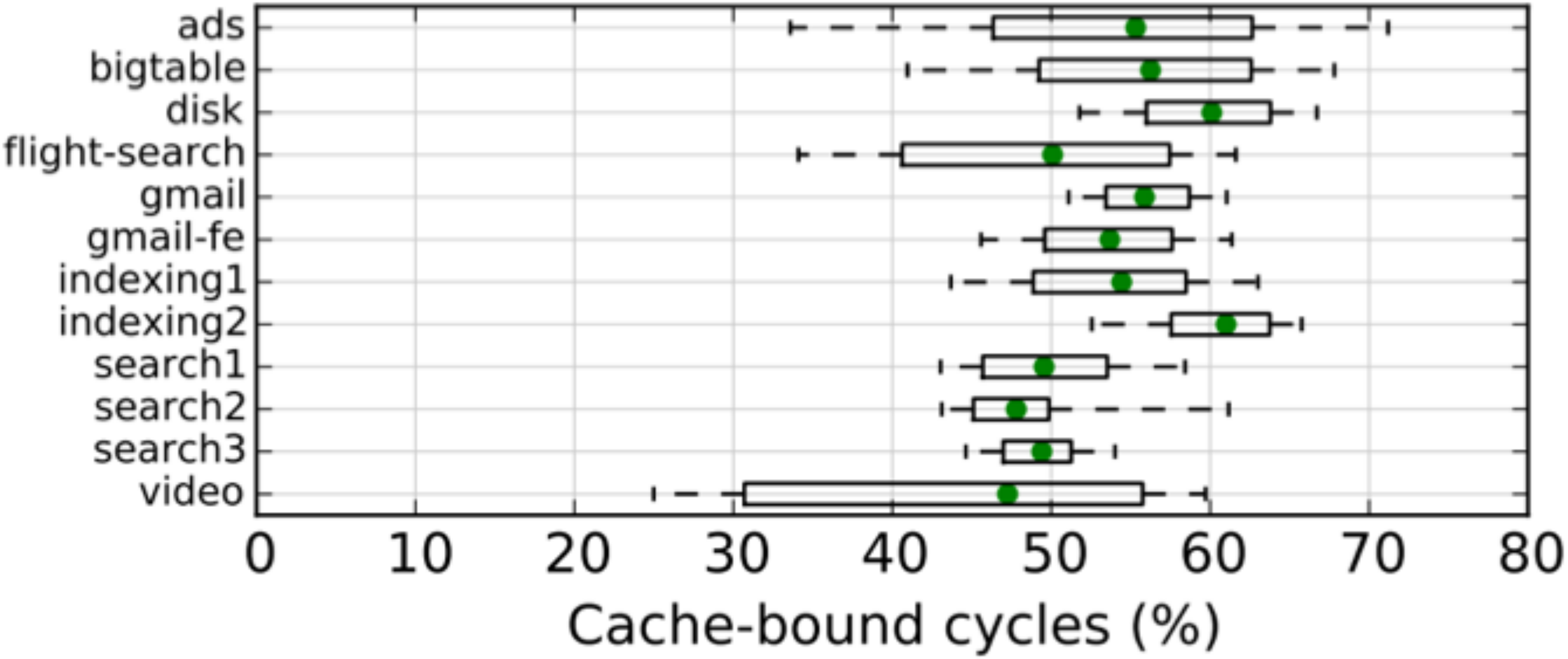


Figure 11: Half of cycles are spent stalled on caches.

Kanev+, "Profiling a Warehouse-Scale Computer," ISCA 2015.

Perils of Processor-Centric Design

- Grossly-imbalanced systems
  - Processing done only in **one place**
  - Everything else just stores and moves data: **data moves a lot**

  → Energy inefficient

  → Low performance

  → Complex

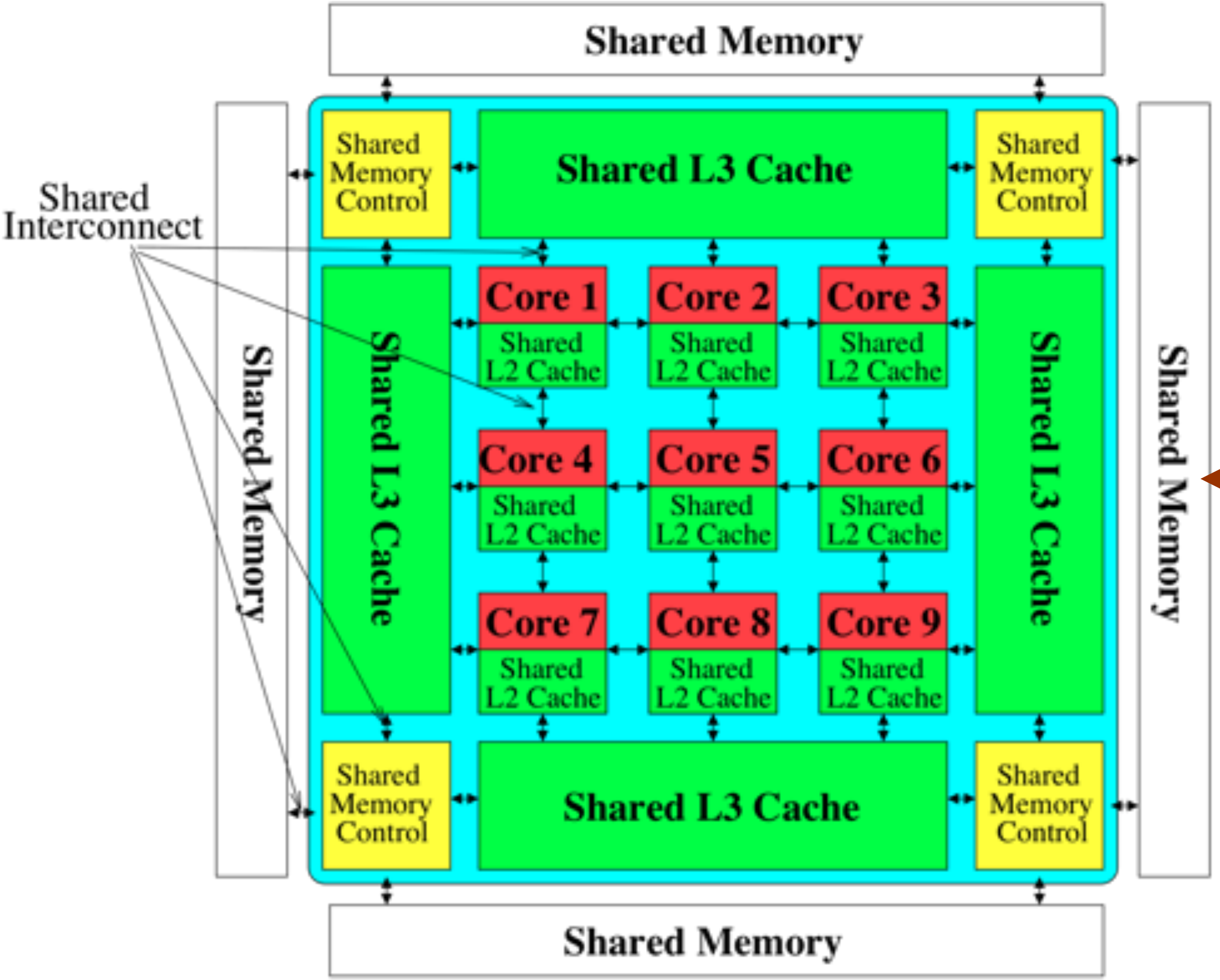
- Overly complex and bloated processor (and accelerators)
  - To tolerate data access from memory
  - Complex hierarchies and mechanisms

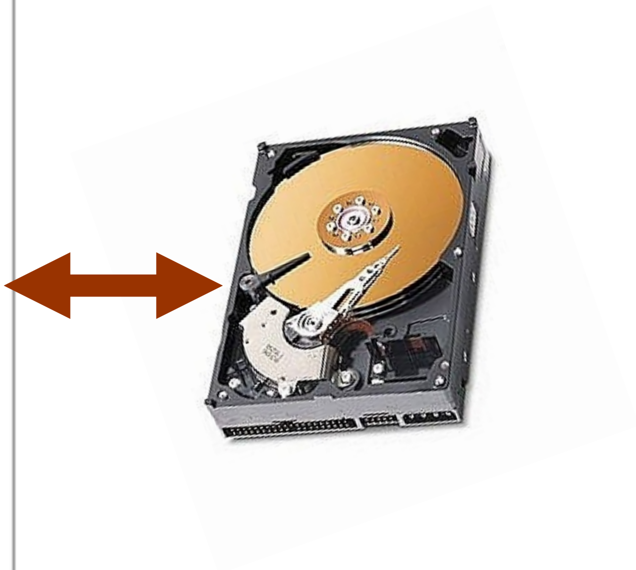
  → Energy inefficient

  → Low performance

  → Complex

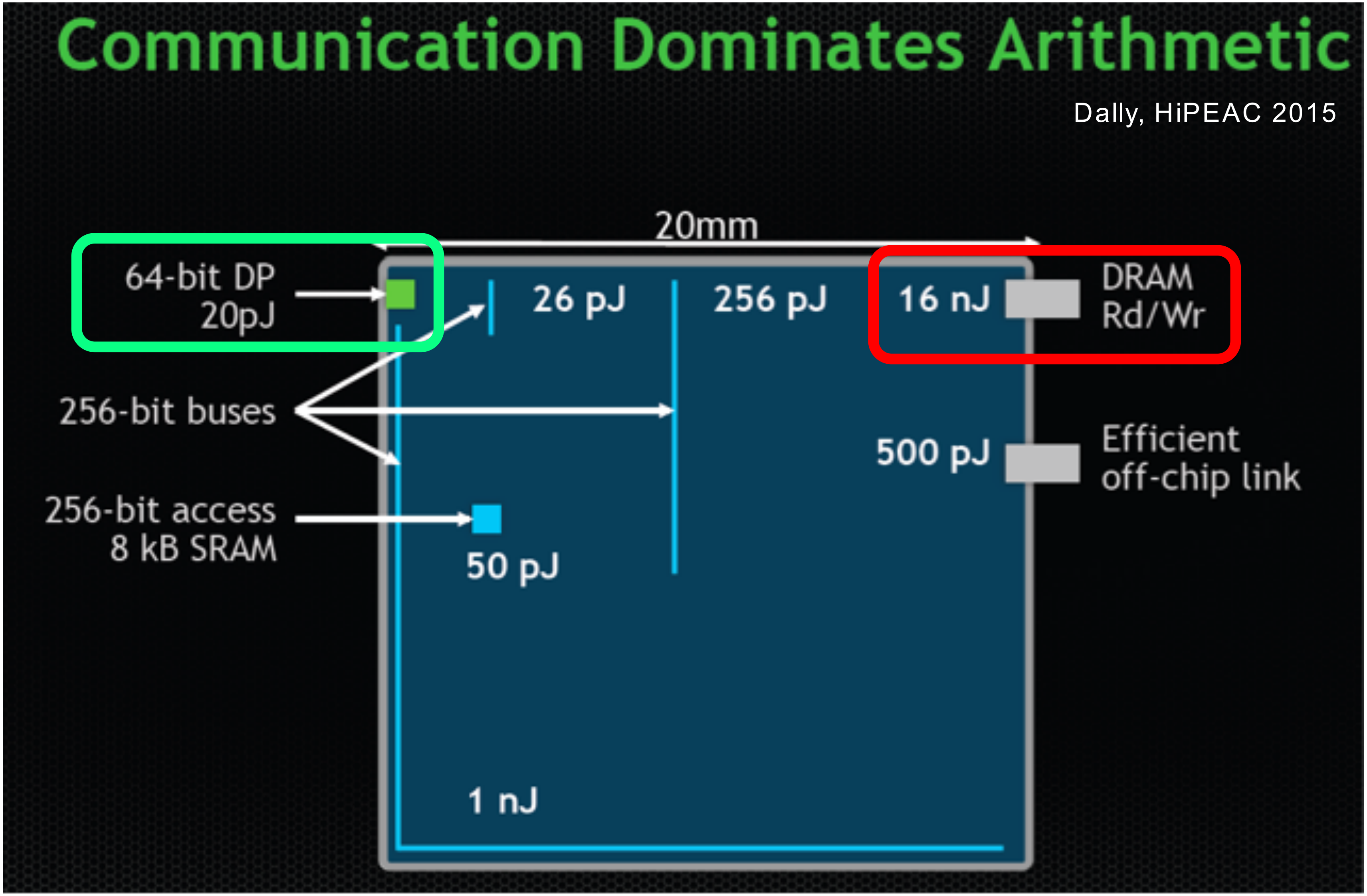
Perils of Processor-Centric Design



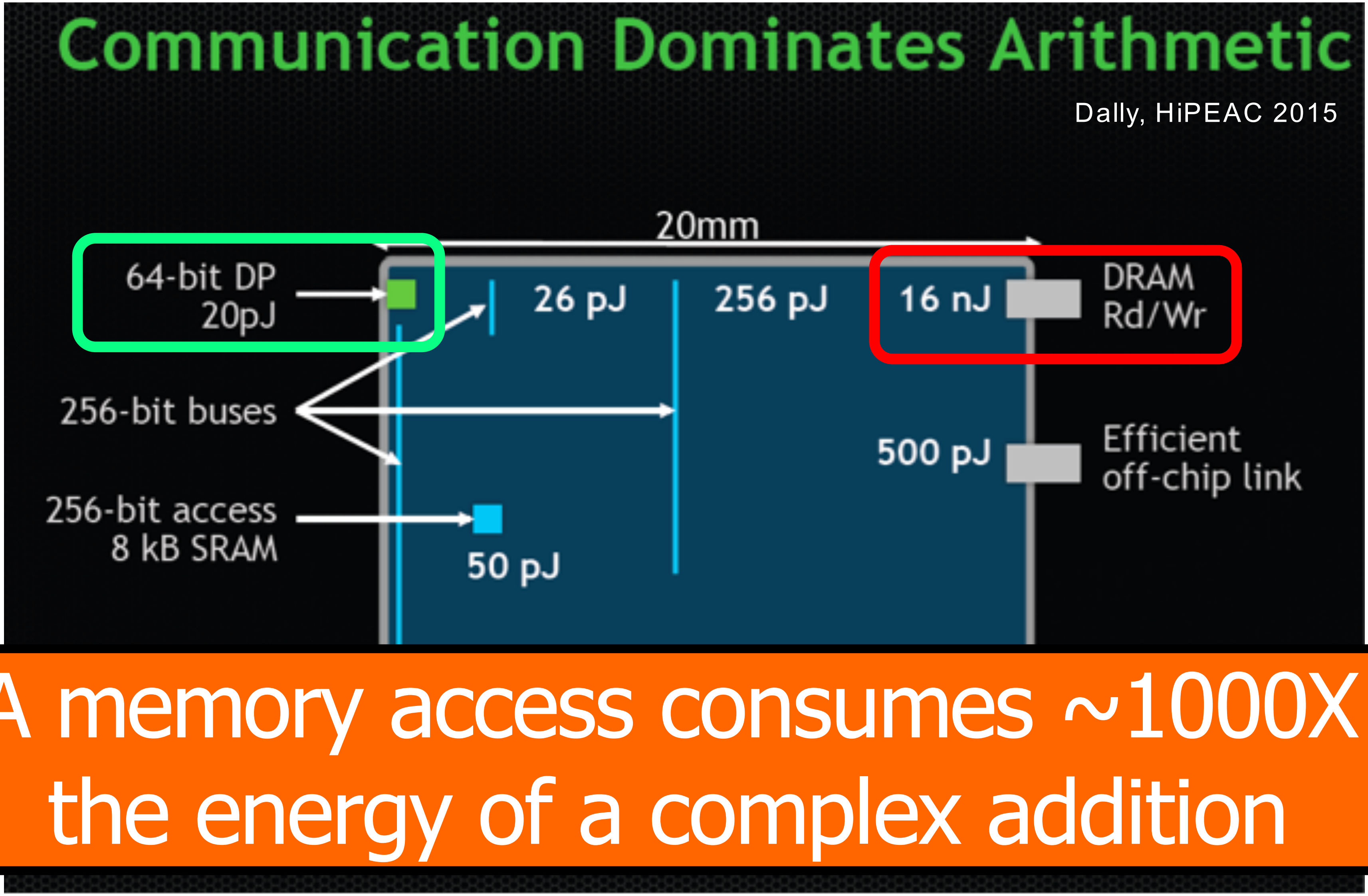


Most of the system is dedicated to storing and moving data

The Energy Perspective



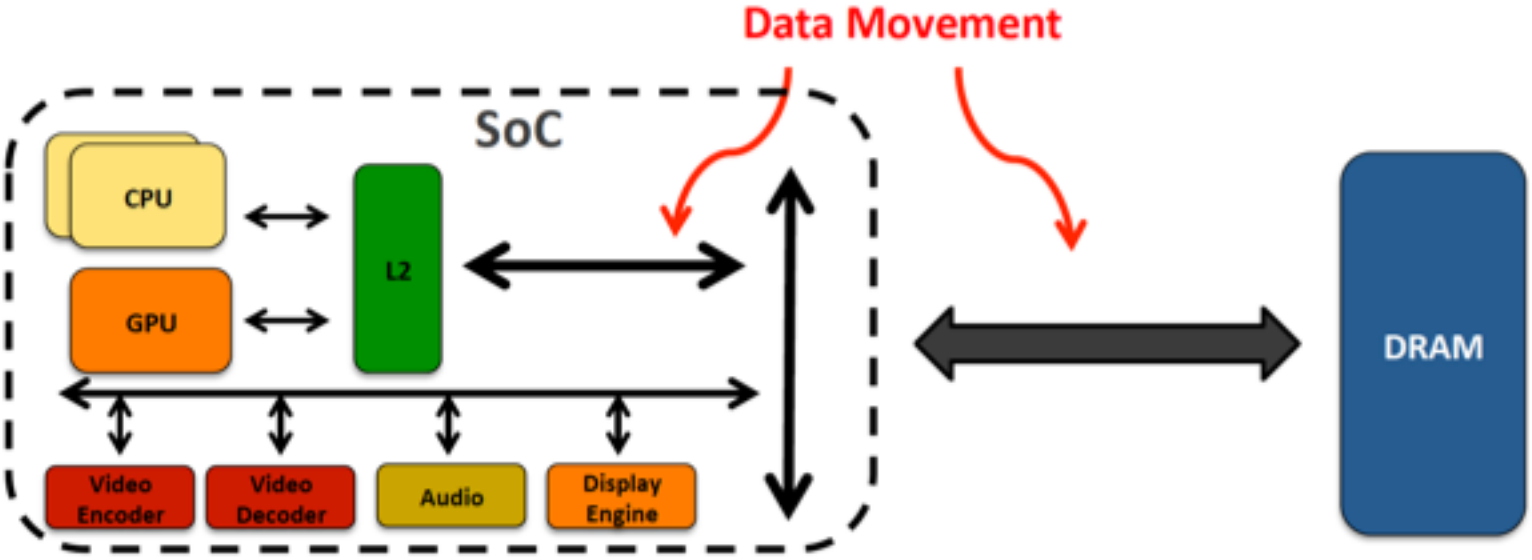
Data Movement vs. Computation Energy



A memory access consumes ~1000X the energy of a complex addition

Data Movement vs. Computation Energy

- Data movement is a major system energy bottleneck
  - Comprises 41% of mobile system energy during web browsing [2]
  - Costs ~115 times as much energy as an ADD operation [1, 2]



[1]: Reducing data Movement Energy via Online Data Clustering and Encoding (MICRO’16)

[2]: Quantifying the energy cost of data movement for emerging smart phone workloads on mobile platforms (IISWC’14)

Energy Waste in Mobile Devices

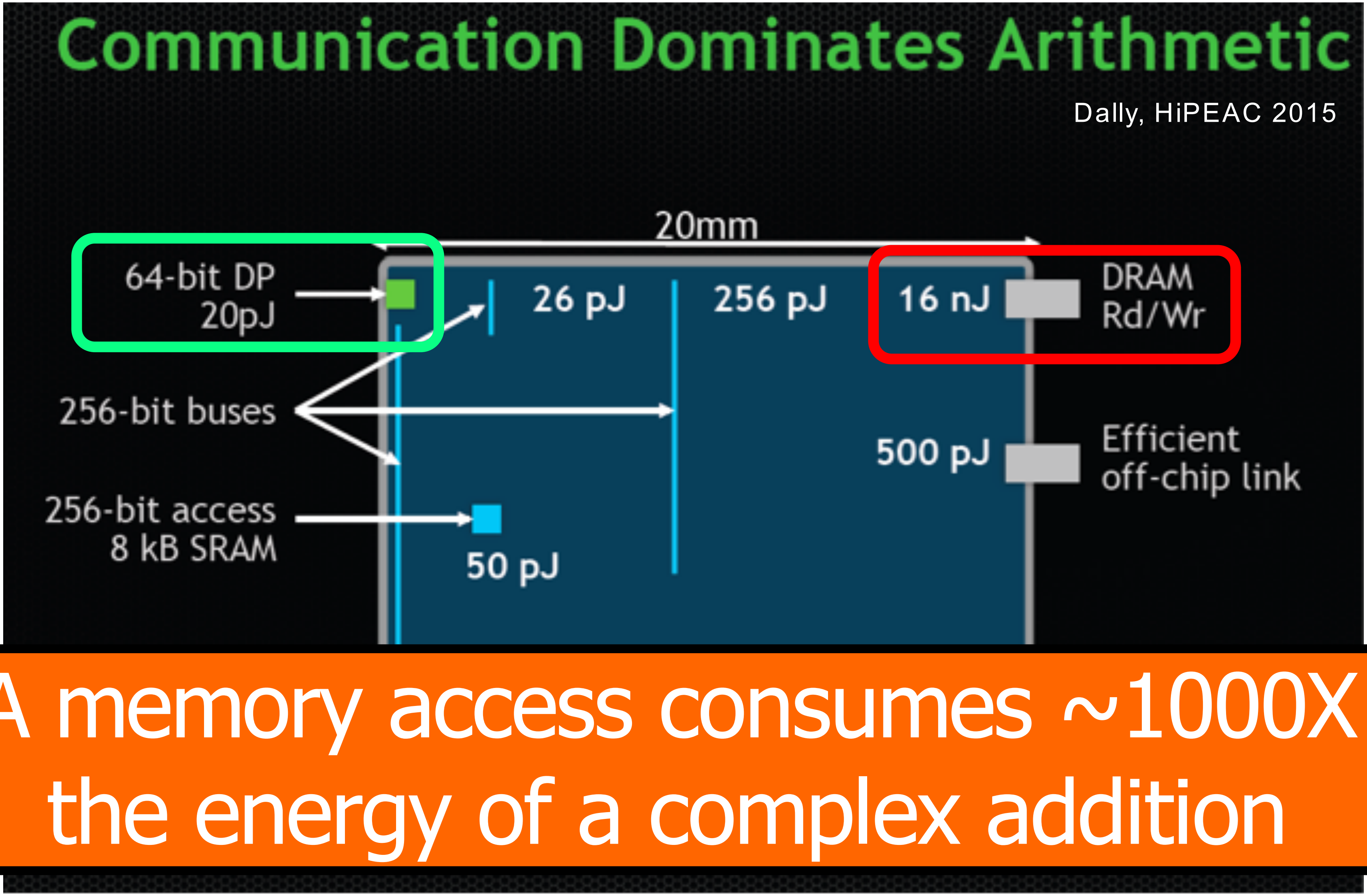
- Amirali Boroumand, Saugata Ghose, Youngsok Kim, Rachata Ausavarungnirun, Eric Shiu, Rahul Thakur, Daehyun Kim, Aki Kuusela, Allan Knies, Parthasarathy Ranganathan, and Onur Mutlu, **"Google Workloads for Consumer Devices: Mitigating Data Movement Bottlenecks"** *Proceedings of the 23rd International Conference on Architectural Support for Programming Languages and Operating Systems* (***ASPLOS***), Williamsburg, VA, USA, March 2018.

62.7% of the total system energy is spent on data movement

Google Workloads for Consumer Devices: Mitigating Data Movement Bottlenecks

Amirali Boroumand[1] Saugata Ghose[1] Youngsok Kim[2]
Rachata Ausavarungnirun[1] Eric Shiu[3] Rahul Thakur[3] Daehyun Kim[4,3]
Aki Kuusela[3] Allan Knies[3] Parthasarathy Ranganathan[3] Onur Mutlu[5,1]

We Do Not Want to Move Data!



Communication Dominates Arithmetic

Dally, HiPEAC 2015

A memory access consumes ~1000X the energy of a complex addition

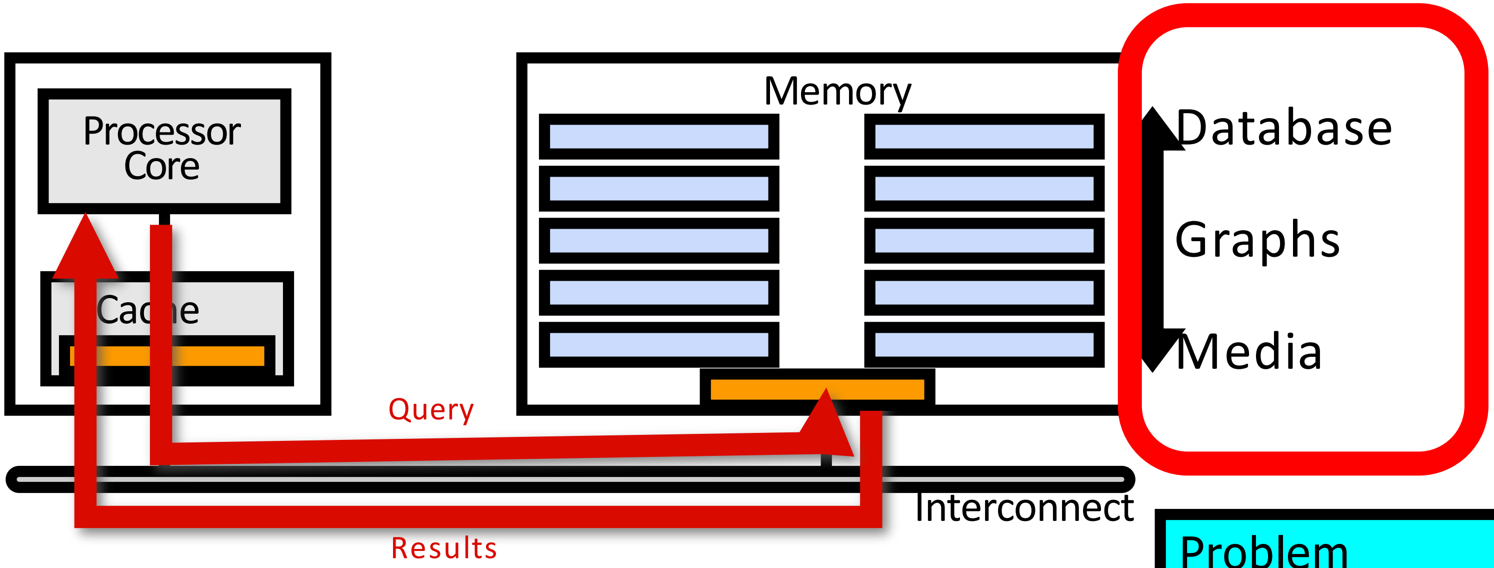
We Need A Paradigm Shift To …

- Enable computation with minimal data movement

- Compute where it makes sense (where data resides)

- Make computing architectures more data-centric

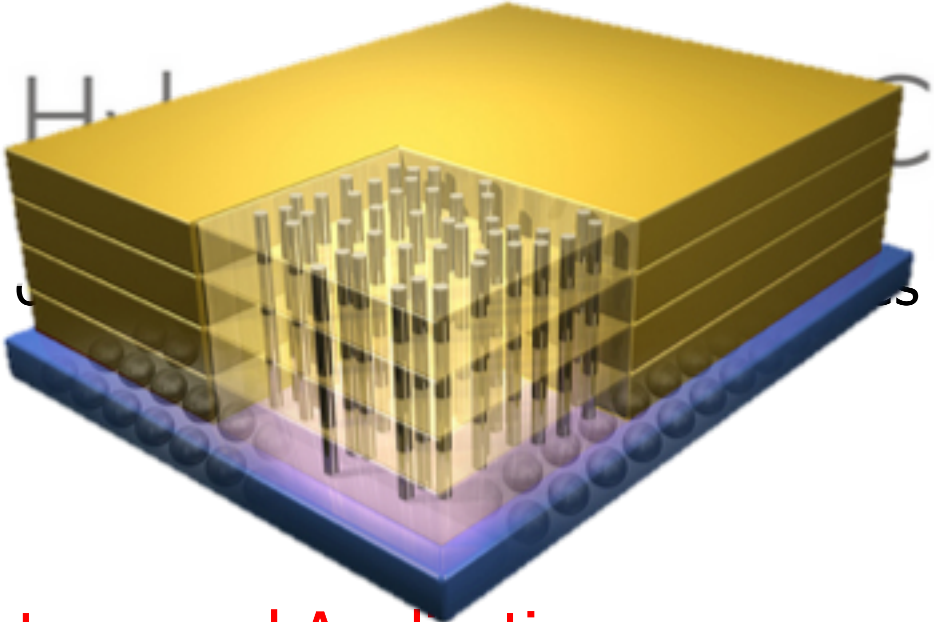
Goal: Processing Inside Memory



- Many questions … How do we design the:
  - compute-capable memory & controllers?
  - processor chip and in-memory units?
  - software and hardware interfaces?
  - system software and languages?
  - algorithms?

Problem
Algorithm
Program/Language
System Software
SW/HW Interface
Micro-architecture
Logic
Devices
Electrons

Why In-Memory Computation Today?



Micron

Dally, HiPEAC 2

AUTOMATA PROCESSING

→ Industry

- Pull from Systems and Applications
  - Data access is a major system and application bottleneck
  - Systems are energy limited
  - Data movement much more energy-hungry than computation

Agenda

- Major Trends Affecting Main Memory
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  - Bottom Up: Push from Circuits and Devices
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- Processing in Memory: Two Directions
  - Minimally Changing Memory Chips
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Processing in Memory: Two Approaches

1. Minimally changing memory chips
2. Exploiting 3D-stacked memory

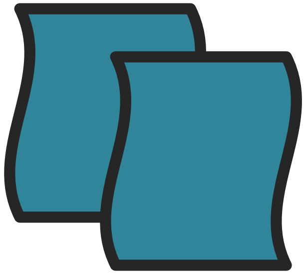
Approach 1: Minimally Changing DRAM

- DRAM has great capability to perform bulk data movement and computation internally with small changes
  - Can exploit internal connectivity to move data
  - Can exploit analog computation capability
  - …

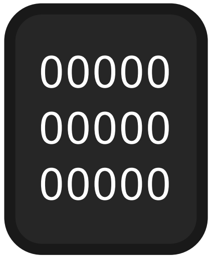
- Examples: RowClone, In-DRAM AND/OR, Gather/Scatter DRAM
  - RowClone: Fast and Efficient In-DRAM Copy and Initialization of Bulk Data (Seshadri et al., MICRO 2013)
  - Fast Bulk Bitwise AND and OR in DRAM (Seshadri et al., IEEE CAL 2015)
  - Gather-Scatter DRAM: In-DRAM Address Translation to Improve the Spatial Locality of Non-unit Strided Accesses (Seshadri et al., MICRO 2015)
  - "Ambit: In-Memory Accelerator for Bulk Bitwise Operations Using Commodity DRAM Technology" (Seshadri et al., MICRO 2017)

Starting Simple: Data Copy and Initialization

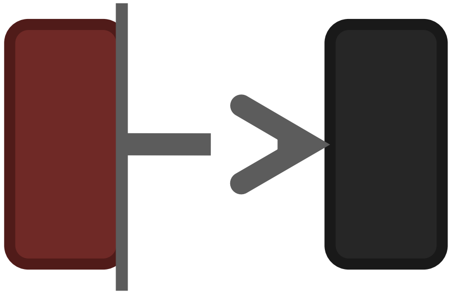
memmove & *memcpy*: 5% cycles in Google's datacenter [Kanev+ ISCA'15]



Forking

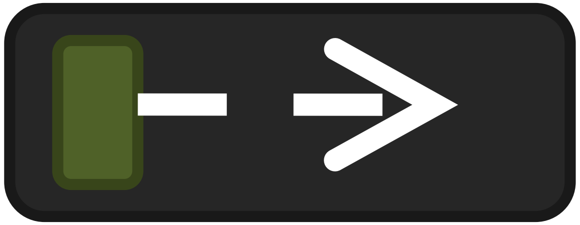


Zero initialization
(e.g., security)



Checkpointing

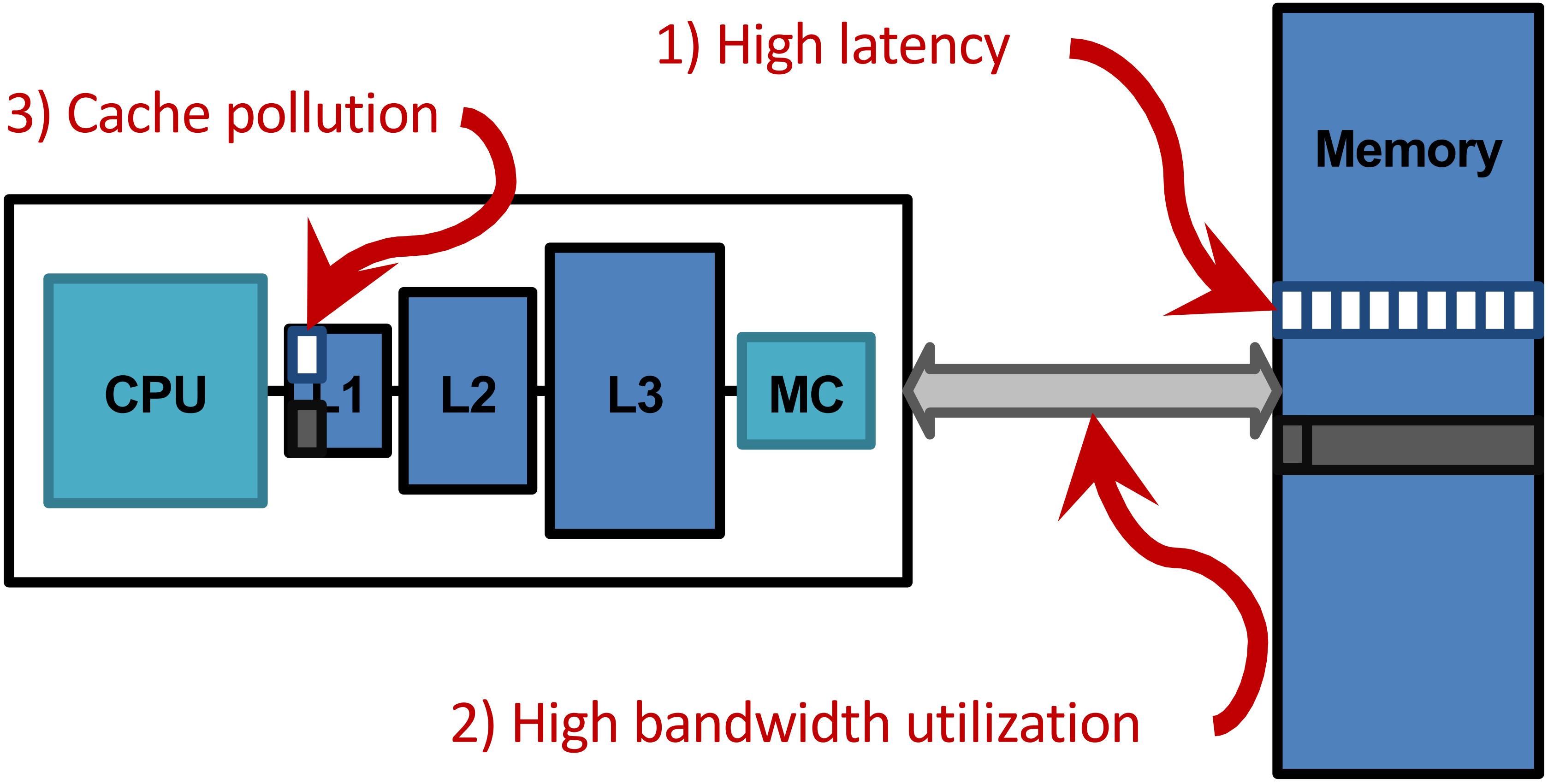
VM Cloning
Deduplication



Page Migration

…
Many more

Today's Systems: Bulk Data Copy



1) High latency

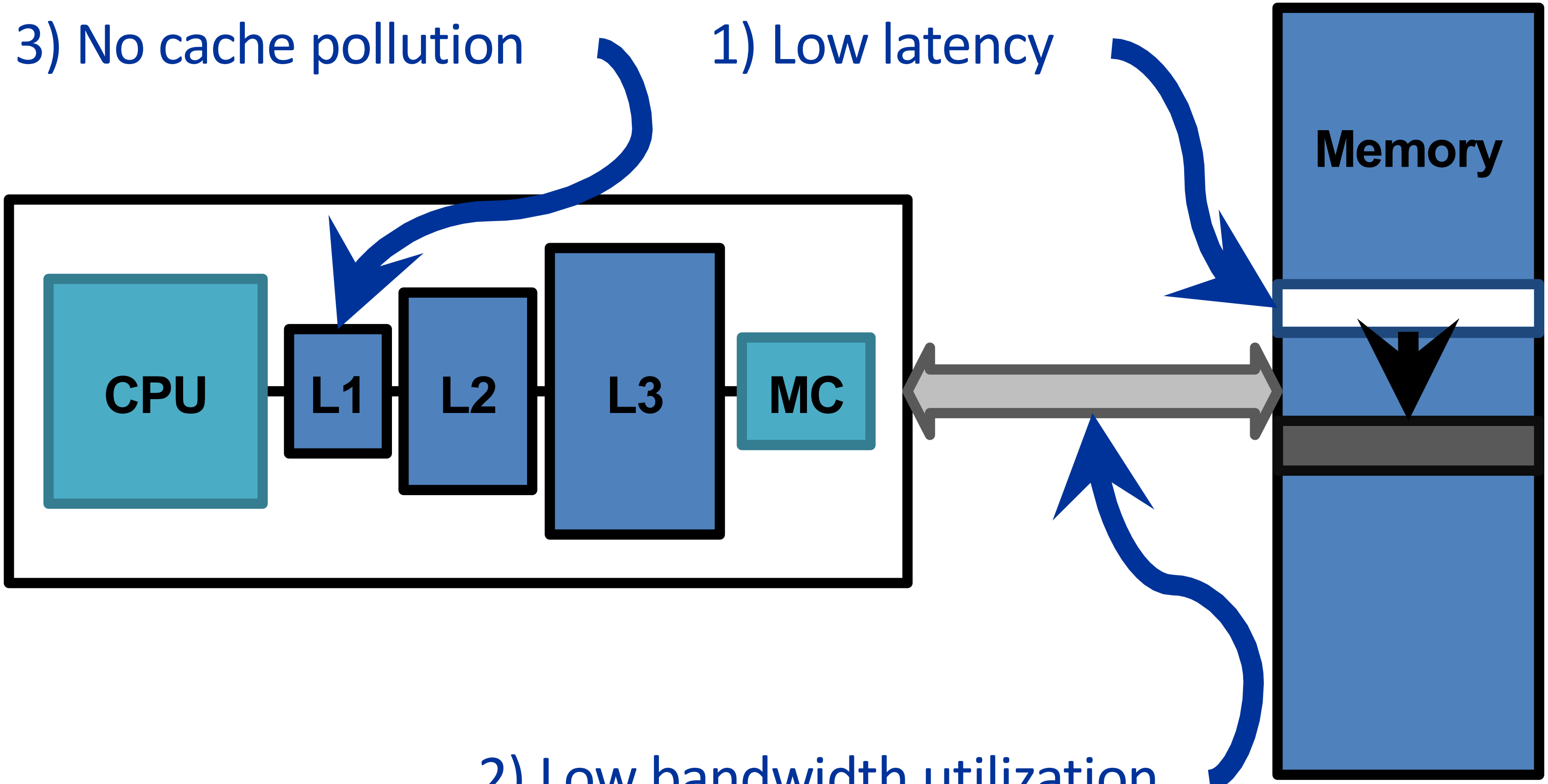
3) Cache pollution

2) High bandwidth utilization

4) Unwanted data movement

1046ns, 3.6uJ (for 4KB page copy via DMA)

Future Systems: In-Memory Copy



3) No cache pollution

1) Low latency

2) Low bandwidth utilization

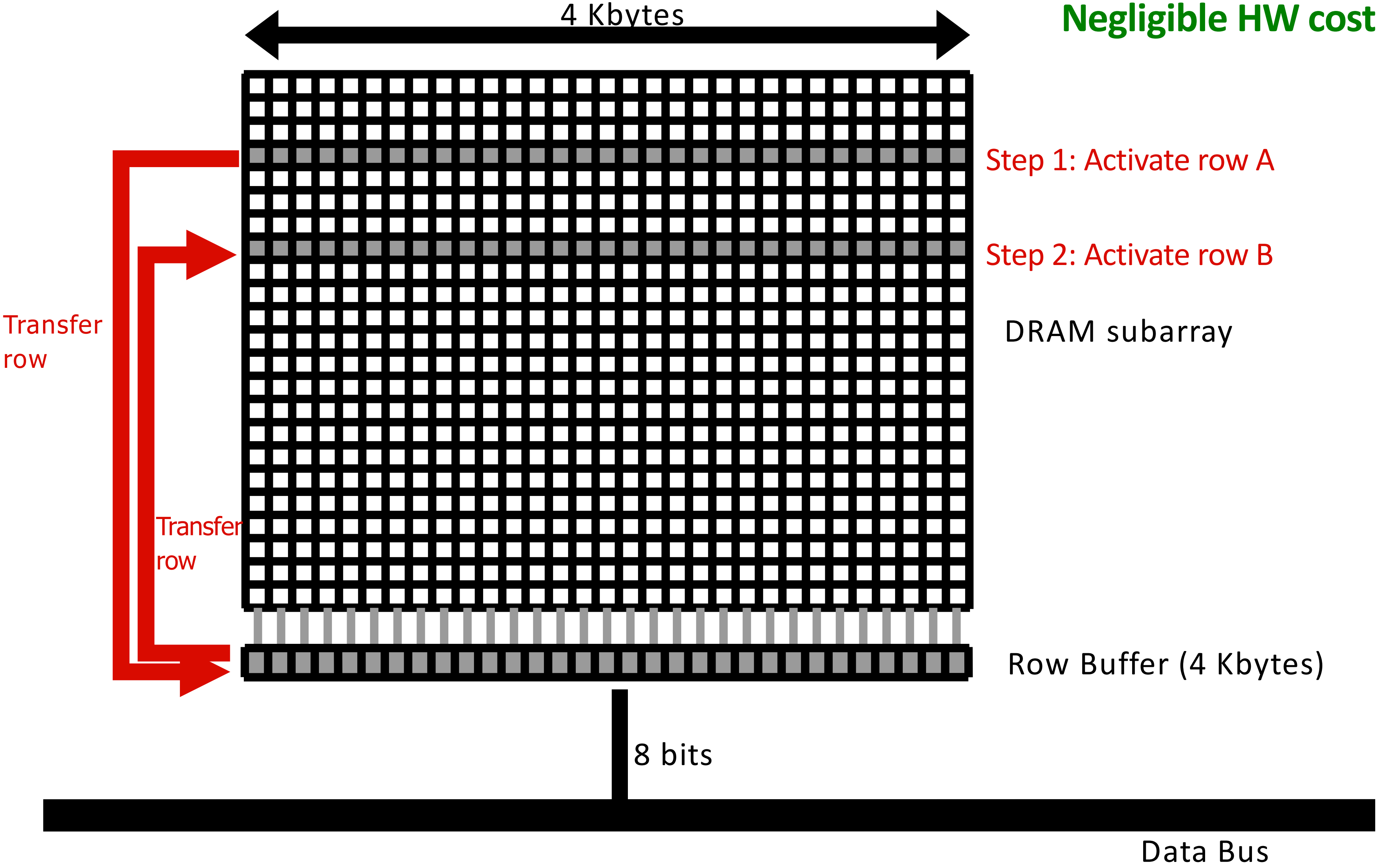
4) No unwanted data movement

1046ns, 3.6uJ → 90ns, 0.04uJ

RowClone: In-DRAM Row Copy

Idea: Two consecutive ACTivates

Negligible HW cost



4 Kbytes

Step 1: Activate row A

Step 2: Activate row B

Transfer row

Transfer row

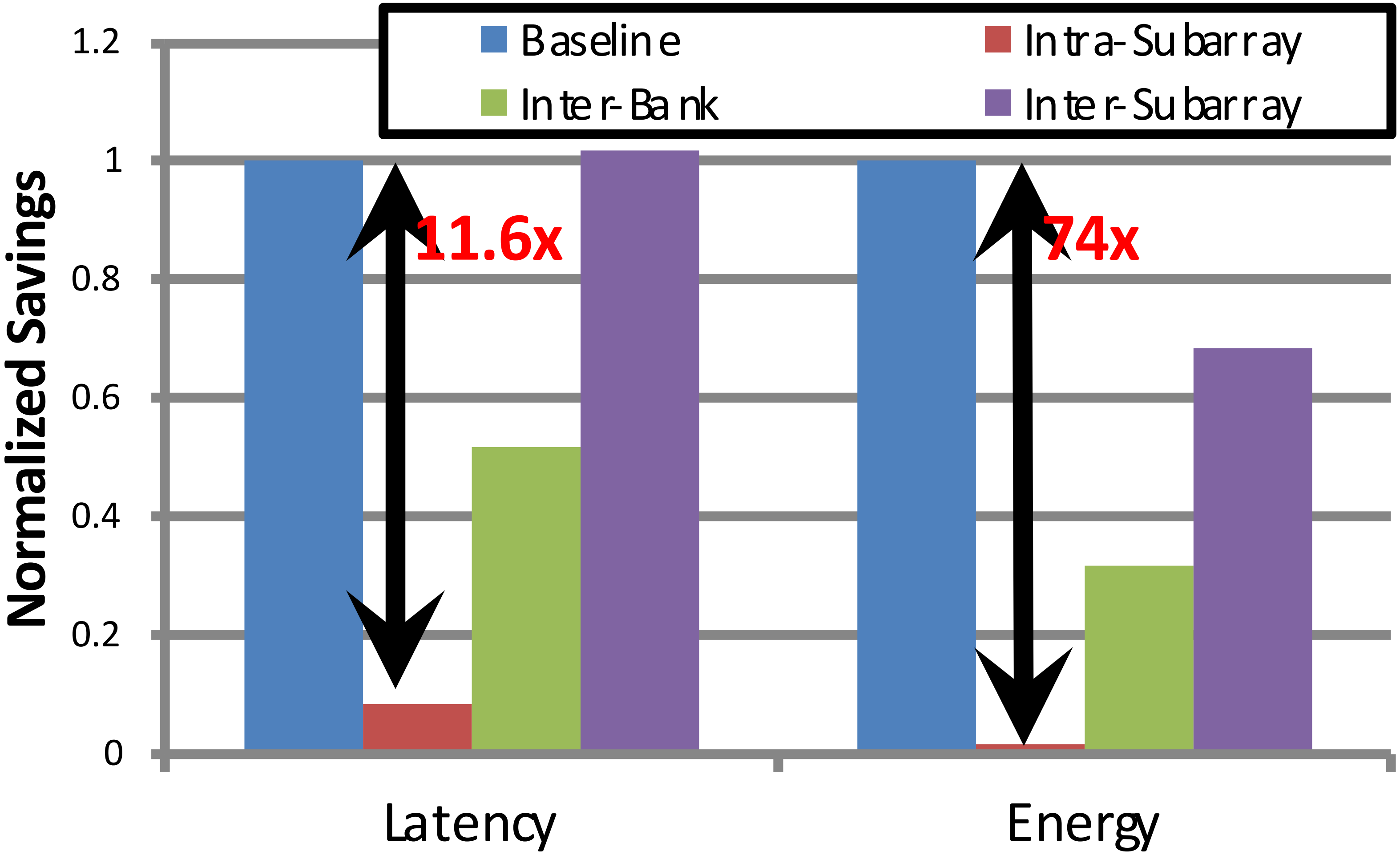
DRAM subarray

Row Buffer (4 Kbytes)

8 bits

Data Bus

RowClone: Latency and Energy Savings



Seshadri et al., "RowClone: Fast and Efficient In-DRAM Copy and Initialization of Bulk Data," MICRO 2013.

More on RowClone

- Vivek Seshadri, Yoongu Kim, Chris Fallin, Donghyuk Lee, Rachata Ausavarungnirun, Gennady Pekhimenko, Yixin Luo, Onur Mutlu, Michael A. Kozuch, Phillip B. Gibbons, and Todd C. Mowry,

  "RowClone: Fast and Energy-Efficient In-DRAM Bulk Data Copy and Initialization"
  *Proceedings of the 46th International Symposium on Microarchitecture (**MICRO**)*, Davis, CA, December 2013. [Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)] [Poster (pptx) (pdf)]

RowClone: Fast and Energy-Efficient In-DRAM Bulk Data Copy and Initialization

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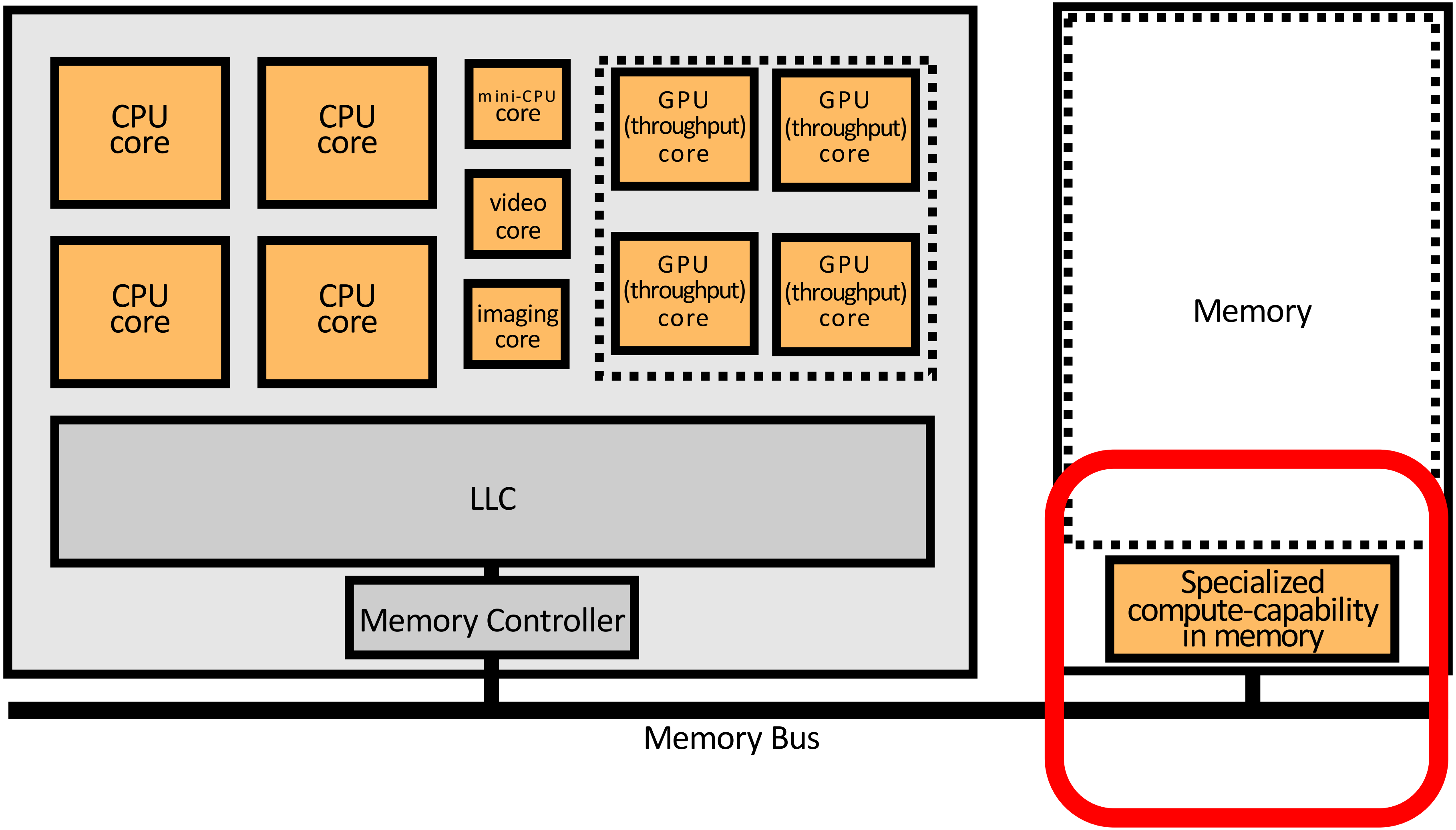
Yixin Luo yixinluo@andrew.cmu.edu
Onur Mutlu onur@cmu.edu
Phillip B. Gibbons† phillip.b.gibbons@intel.com
Michael A. Kozuch† michael.a.kozuch@intel.com
Todd C. Mowry tcm@cs.cmu.edu
Carnegie Mellon University †Intel Pittsburgh

Memory as an Accelerator



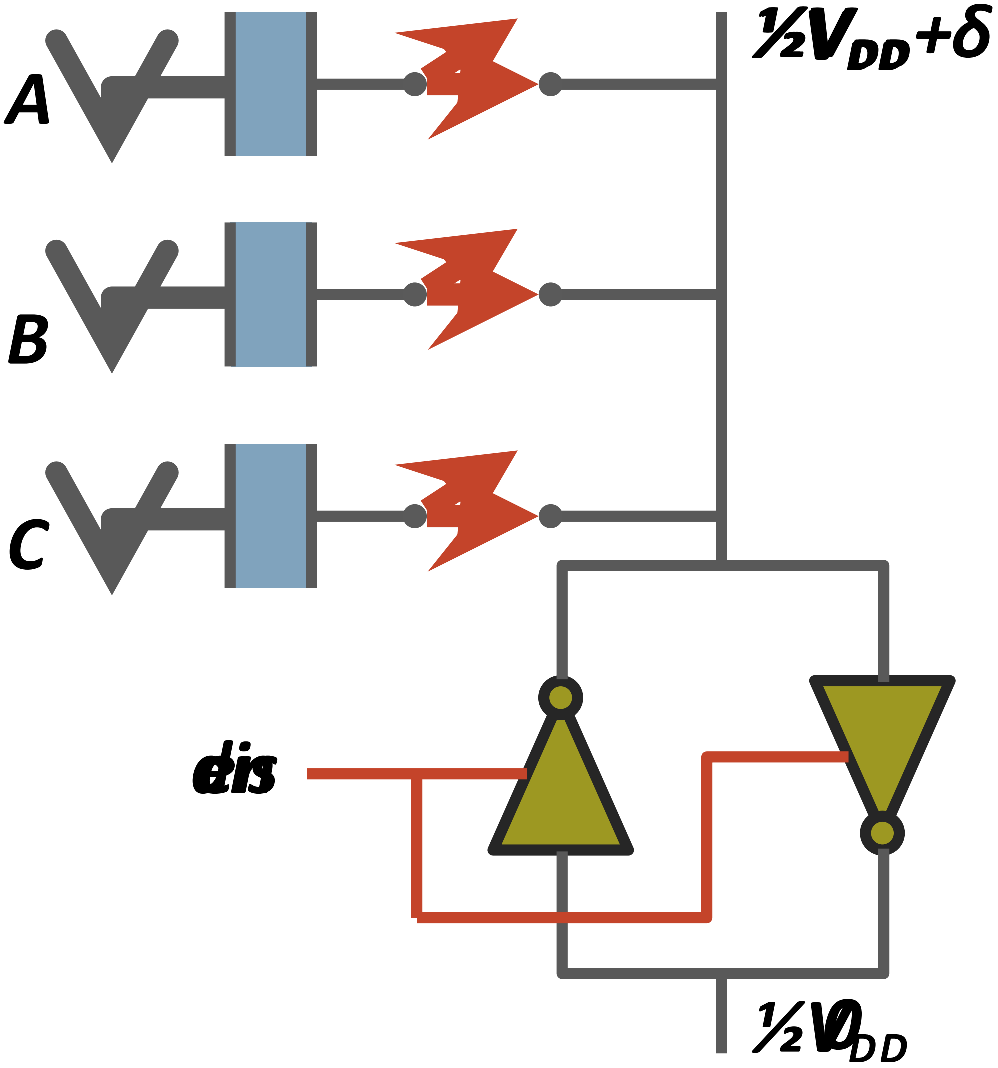
Memory similar to a "conventional" accelerator

In-Memory Bulk Bitwise Operations

- We can support in-DRAM COPY, ZERO, AND, OR, NOT, MAJ
- At low cost
- Using analog computation capability of DRAM
  - Idea: activating multiple rows performs computation
- 30-60X performance and energy improvement
  - Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations Using Commodity DRAM Technology," MICRO 2017.

- New memory technologies enable even more opportunities
  - Memristors, resistive RAM, phase change mem, STT-MRAM, …
  - Can operate on data with minimal movement

In-DRAM AND/OR: Triple Row Activation



Final State
$AB + BC + AC$

$C(A + B) +$
$\sim C(AB)$

Seshadri+, "Fast Bulk Bitwise AND and OR in DRAM", IEEE CAL 2015.

In-DRAM NOT: Dual Contact Cell

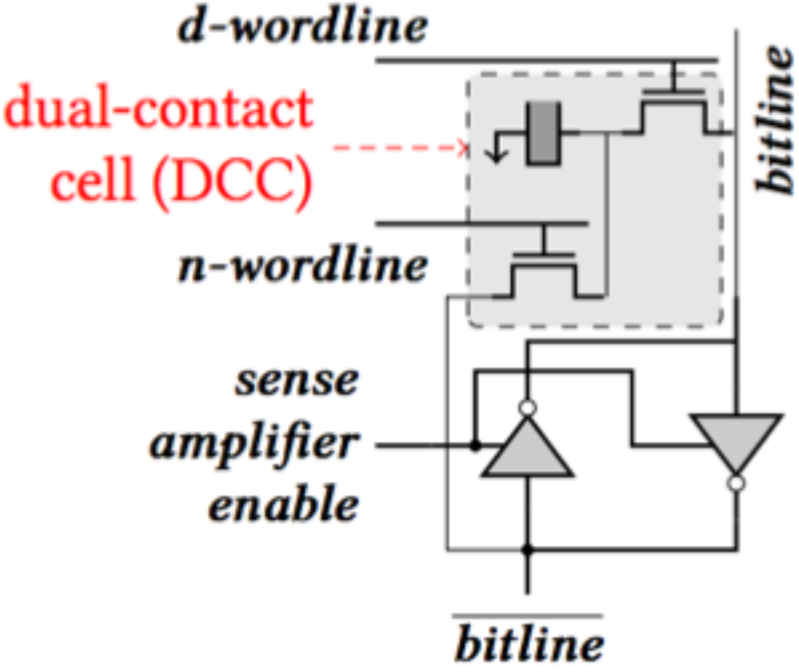


Figure 5: A dual-contact cell connected to both ends of a sense amplifier

Idea:

Feed the negated value in the sense amplifier into a special row

Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," MICRO 2017.

Performance: In-DRAM Bitwise Operations

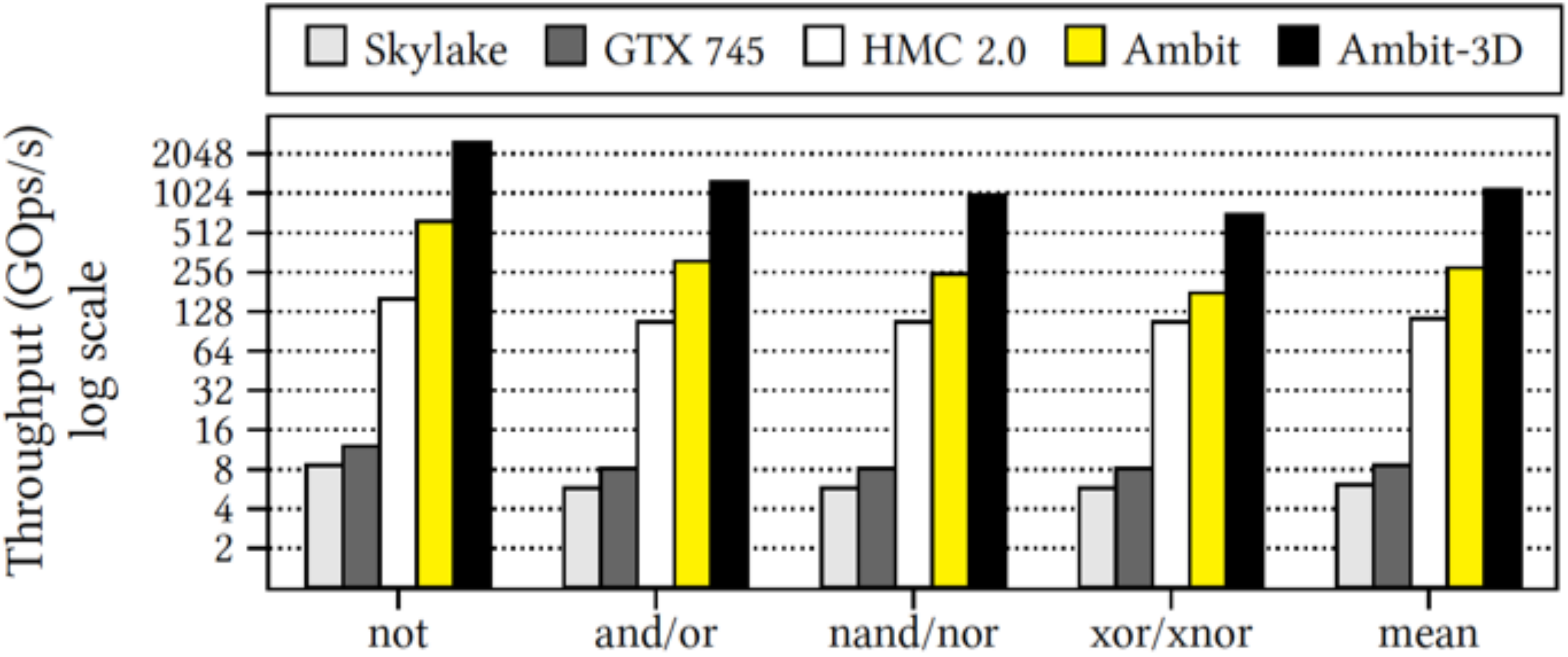
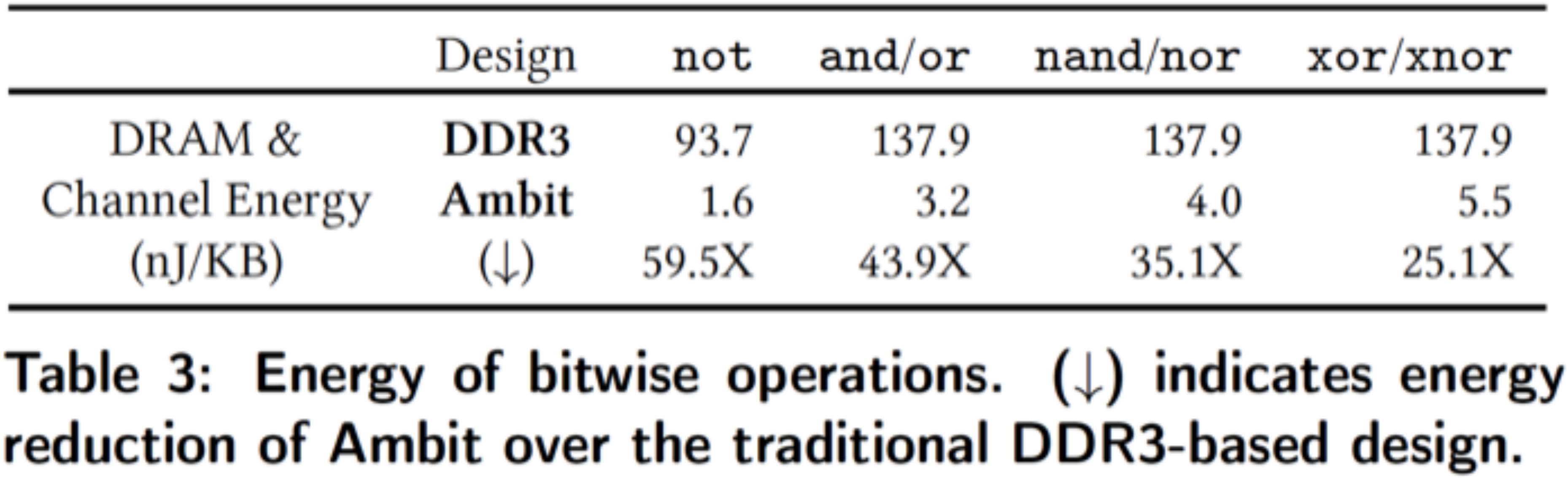


Figure 9: Throughput of bitwise operations on various systems.

Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," MICRO 2017.

Energy of In-DRAM Bitwise Operations

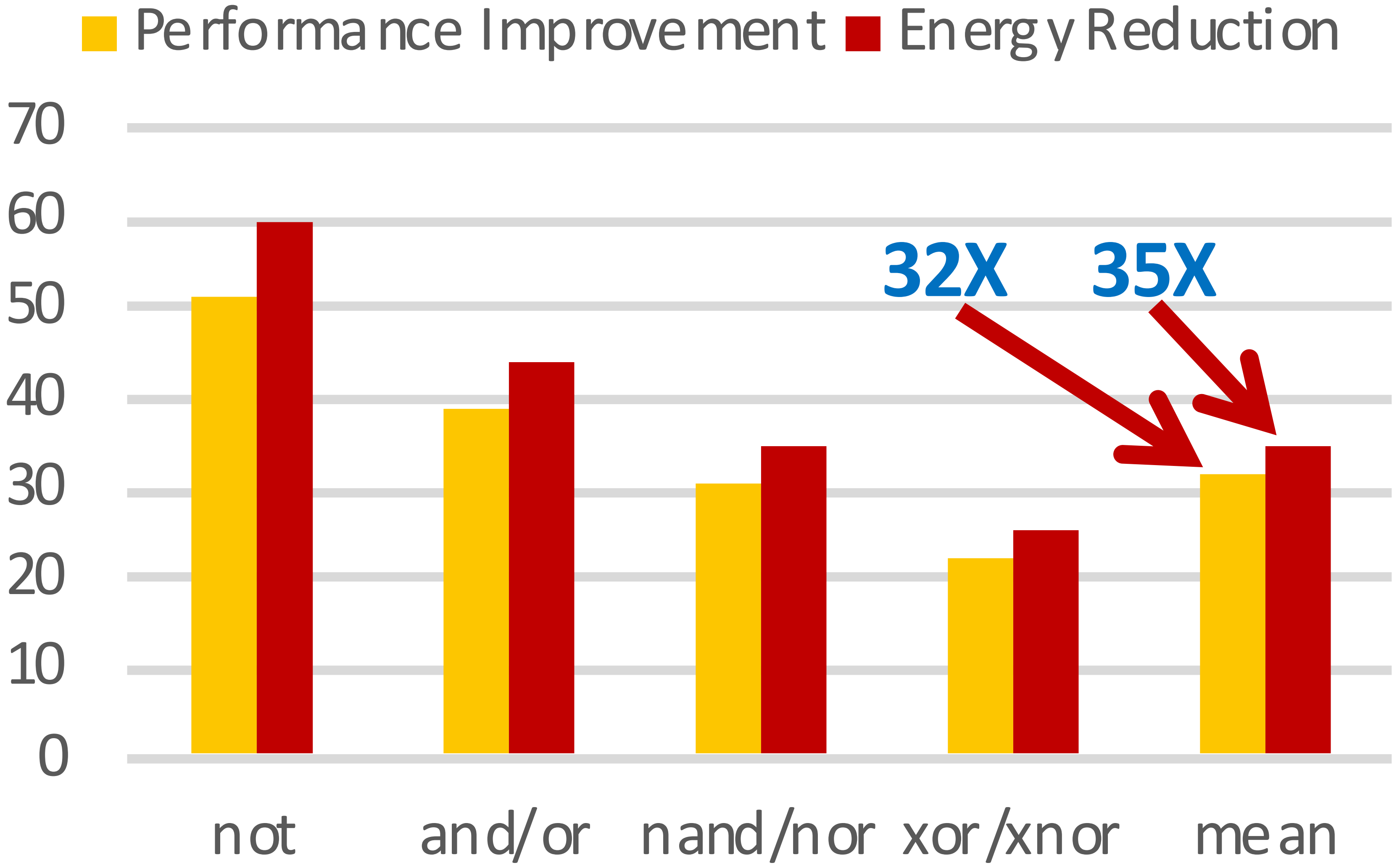


	Design	not	and/or	nand/nor	xor/xnor
DRAM & Channel Energy (nJ/KB)	**DDR3**	93.7	137.9	137.9	137.9
	Ambit	1.6	3.2	4.0	5.5
	(↓)	59.5X	43.9X	35.1X	25.1X

Table 3: Energy of bitwise operations. (↓) indicates energy reduction of Ambit over the traditional DDR3-based design.

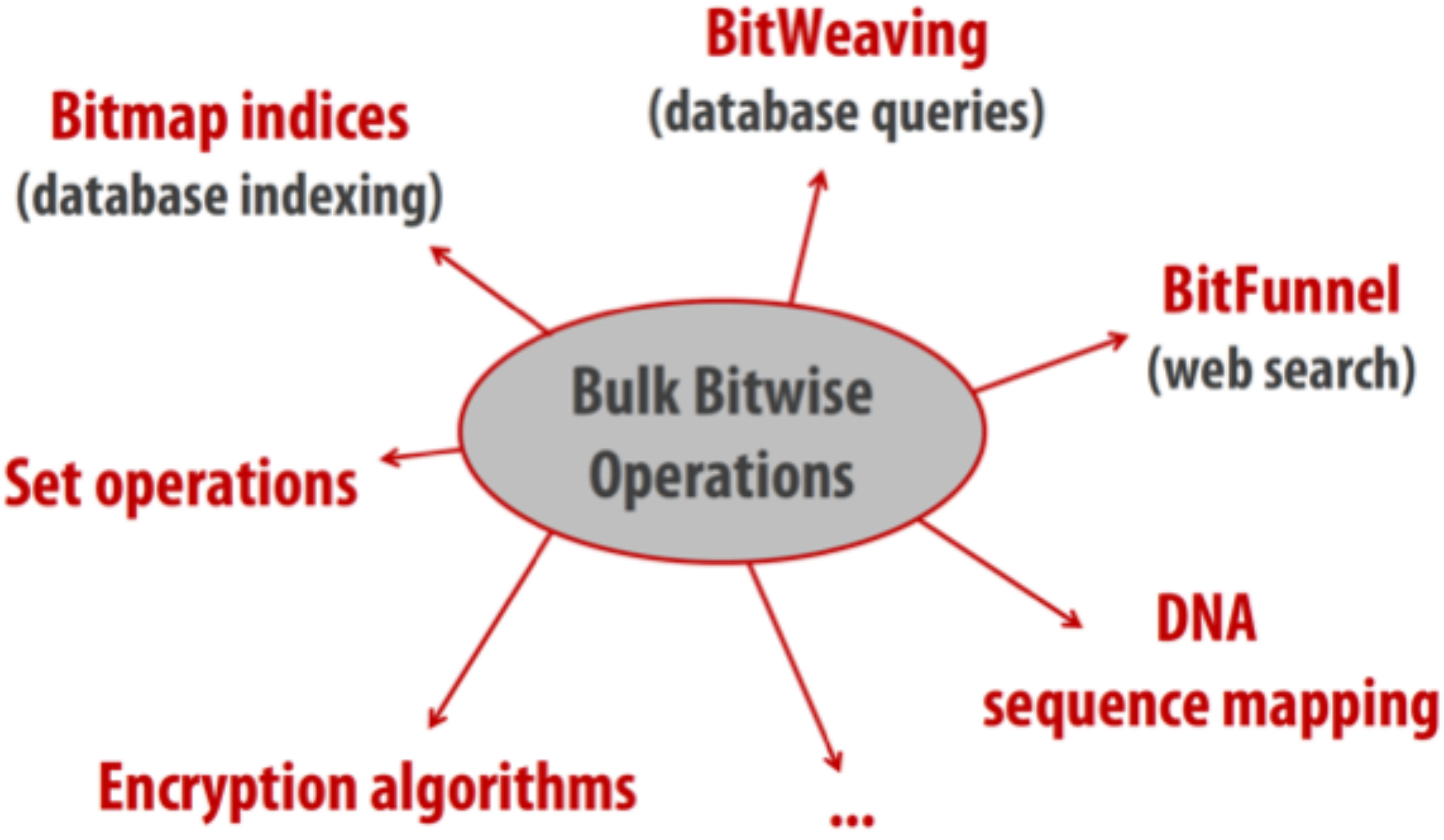
Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," MICRO 2017.

Ambit vs. DDR3: Performance and Energy



Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," MICRO 2017.

Bulk Bitwise Operations in Workloads



Bitmap indices
(database indexing)

BitWeaving
(database queries)

BitFunnel
(web search)

Bulk Bitwise Operations

Set operations

DNA sequence mapping

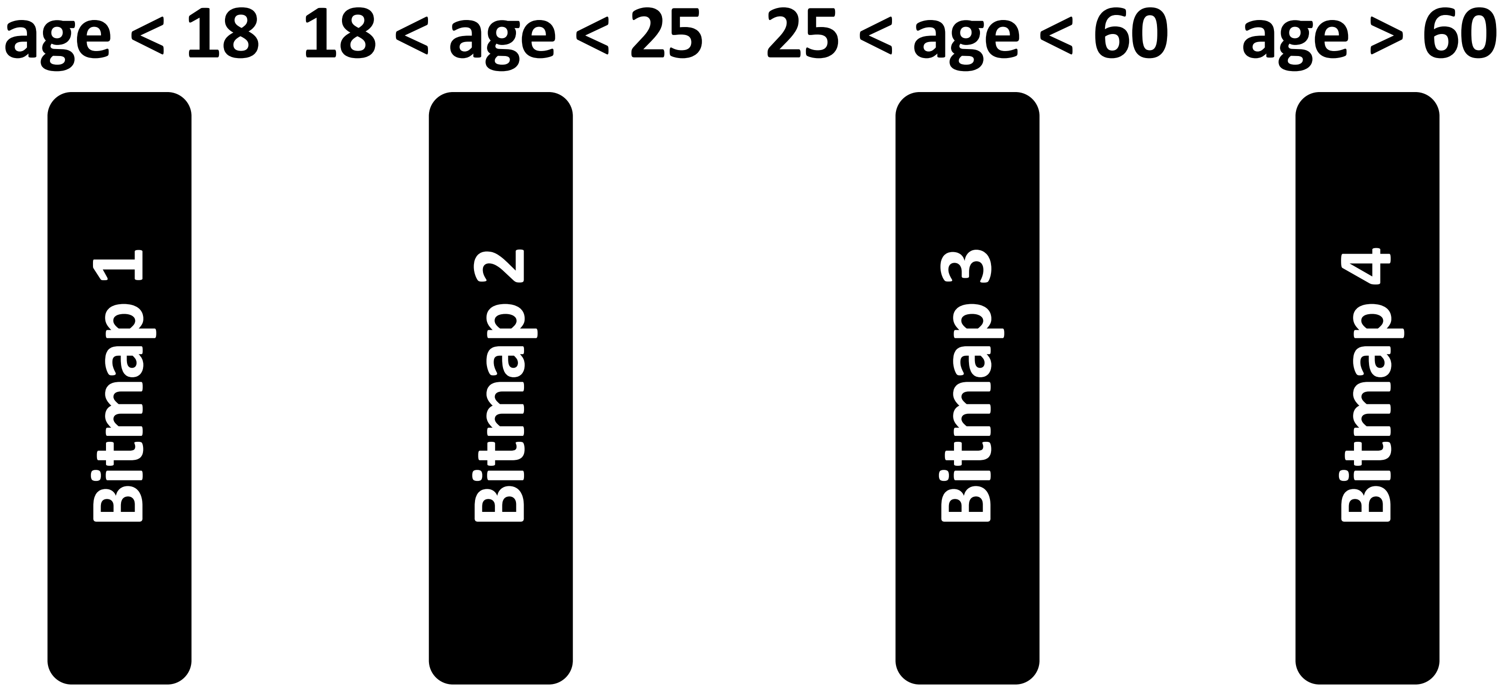
Encryption algorithms

...

[1] Li and Patel, BitWeaving, SIGMOD 2013
[2] Goodwin+, BitFunnel, SIGIR 2017

Example Data Structure: Bitmap Index

- Alternative to B-tree and its variants
- Efficient for performing *range queries* and *joins*
- **Many bitwise operations to perform a query**



age < 18

18 < age < 25

25 < age < 60

age > 60

Bitmap 1

Bitmap 2

Bitmap 3

Bitmap 4

Performance: Bitmap Index on Ambit

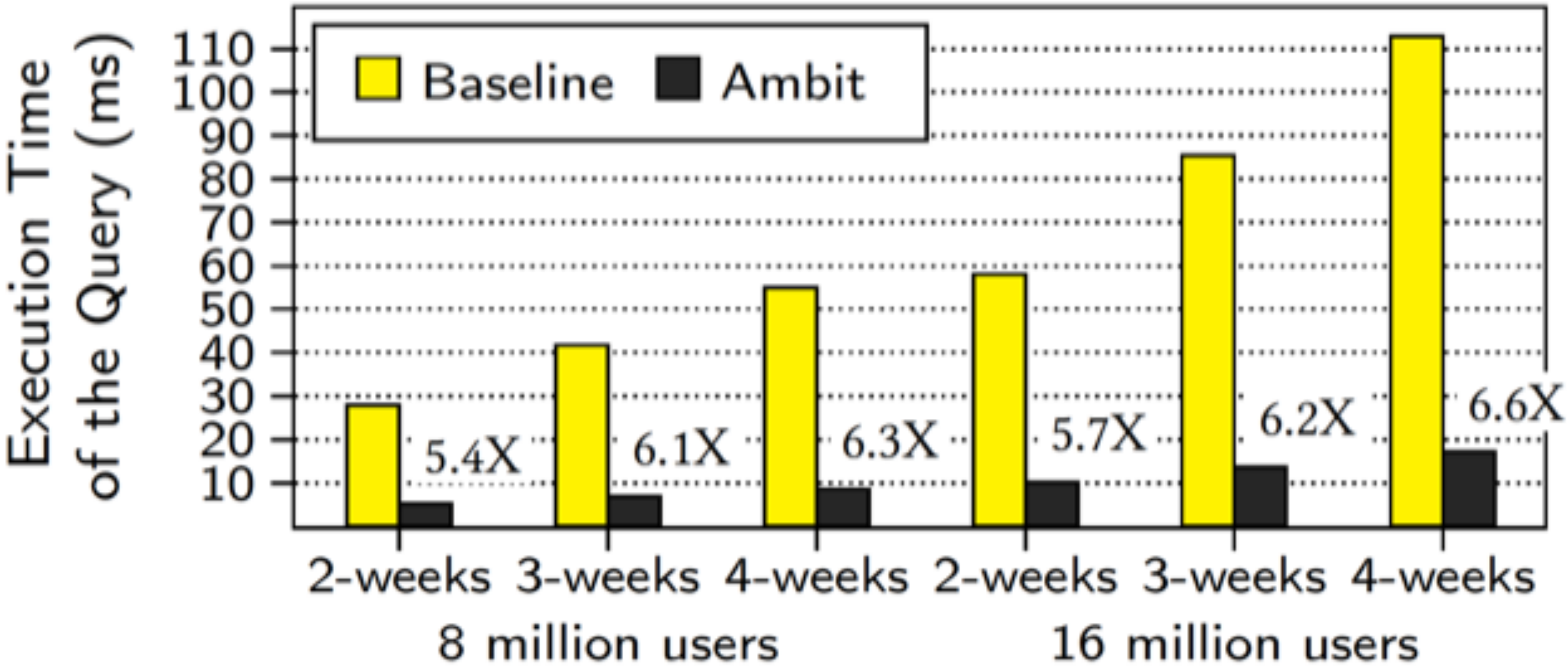
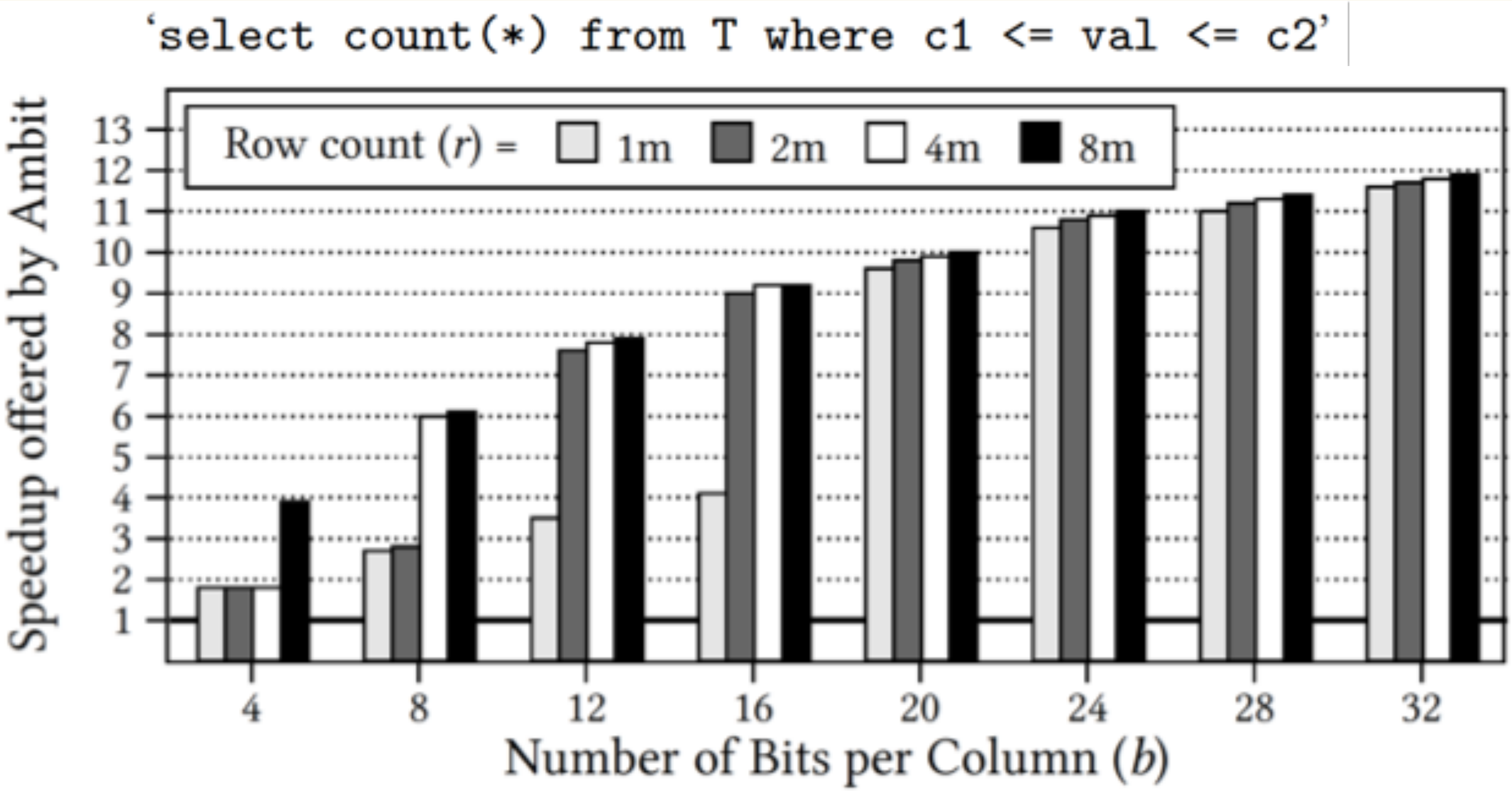


Figure 10: Bitmap index performance. The value above each bar indicates the reduction in execution time due to Ambit.

Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," MICRO 2017.

Performance: BitWeaving on Ambit



'select count(*) from T where c1 <= val <= c2'

Figure 11: Speedup offered by Ambit over baseline CPU with SIMD for BitWeaving

Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," MICRO 2017.

More on In-DRAM Bulk AND/OR

- Vivek Seshadri, Kevin Hsieh, Amirali Boroumand, Donghyuk Lee, Michael A. Kozuch, Onur Mutlu, Phillip B. Gibbons, and Todd C. Mowry,
  "Fast Bulk Bitwise AND and OR in DRAM"
  IEEE Computer Architecture Letters (***CAL***), April 2015.

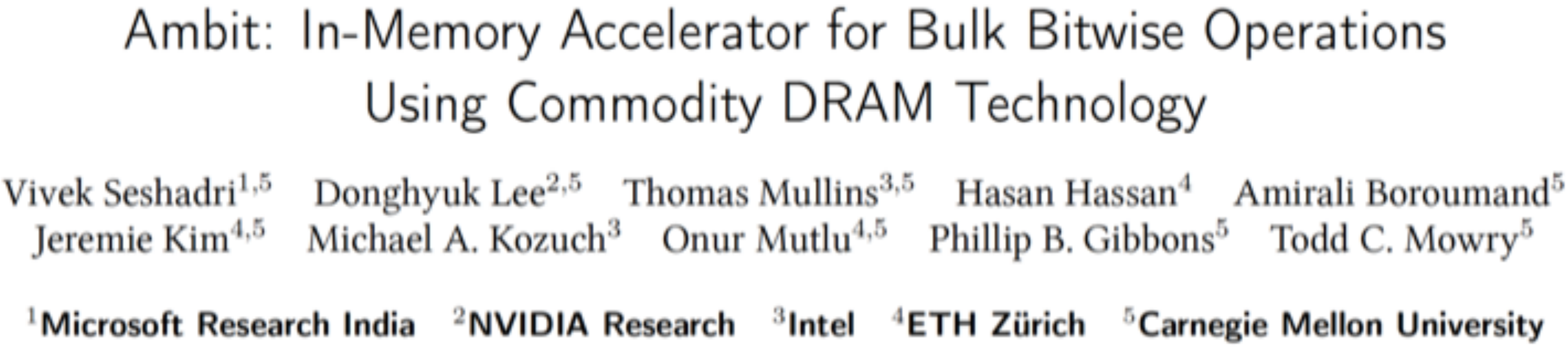
Fast Bulk Bitwise AND and OR in DRAM

Vivek Seshadri*, Kevin Hsieh*, Amirali Boroumand*, Donghyuk Lee*,
Michael A. Kozuch†, Onur Mutlu*, Phillip B. Gibbons†, Todd C. Mowry*

*Carnegie Mellon University †Intel Pittsburgh

More on Ambit

- Vivek Seshadri et al., "**Ambit: In-Memory Accelerator for Bulk Bitwise Operations Using Commodity DRAM Technology**," MICRO 2017.



Ambit: In-Memory Accelerator for Bulk Bitwise Operations Using Commodity DRAM Technology

Vivek Seshadri[1,5] Donghyuk Lee[2,5] Thomas Mullins[3,5] Hasan Hassan[4] Amirali Boroumand[5]
Jeremie Kim[4,5] Michael A. Kozuch[3] Onur Mutlu[4,5] Phillip B. Gibbons[5] Todd C. Mowry[5]

[1]Microsoft Research India [2]NVIDIA Research [3]Intel [4]ETH Zürich [5]Carnegie Mellon University

Challenge and Opportunity for Future

Computing Architectures

with

Minimal Data Movement

Challenge: Intelligent Memory Device

Does memory have to be dumb?

Agenda

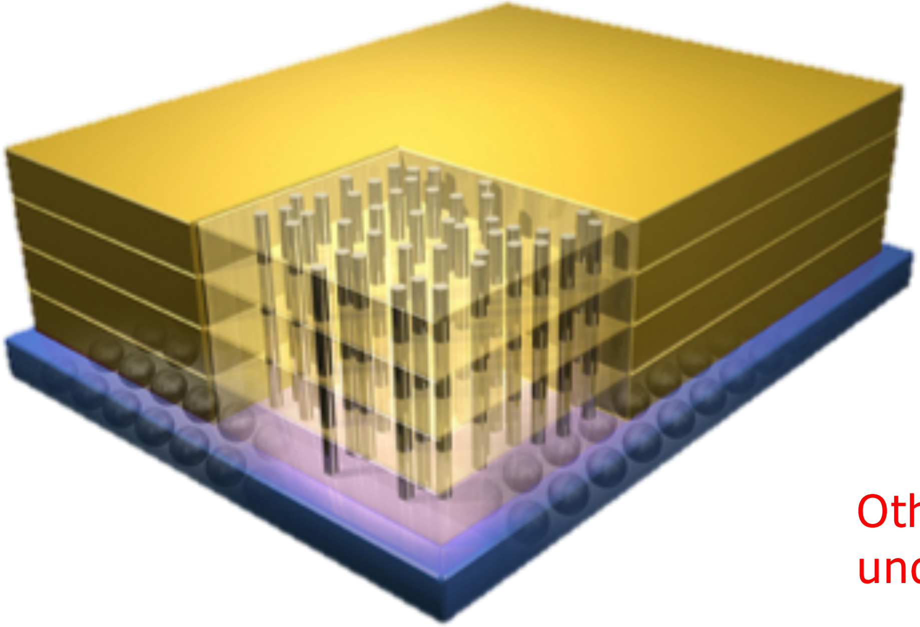
- Major Trends Affecting Main Memory
- The Need for Intelligent Memory Controllers
  - Bottom Up: Push from Circuits and Devices
  - Top Down: Pull from Systems and Applications
- Processing in Memory: Two Directions
  - Minimally Changing Memory Chips
  - Exploiting 3D-Stacked Memory
- How to Enable Adoption of Processing in Memory
- Conclusion

Processing in Memory: Two Approaches

1. Minimally changing memory chips
2. Exploiting 3D-stacked memory

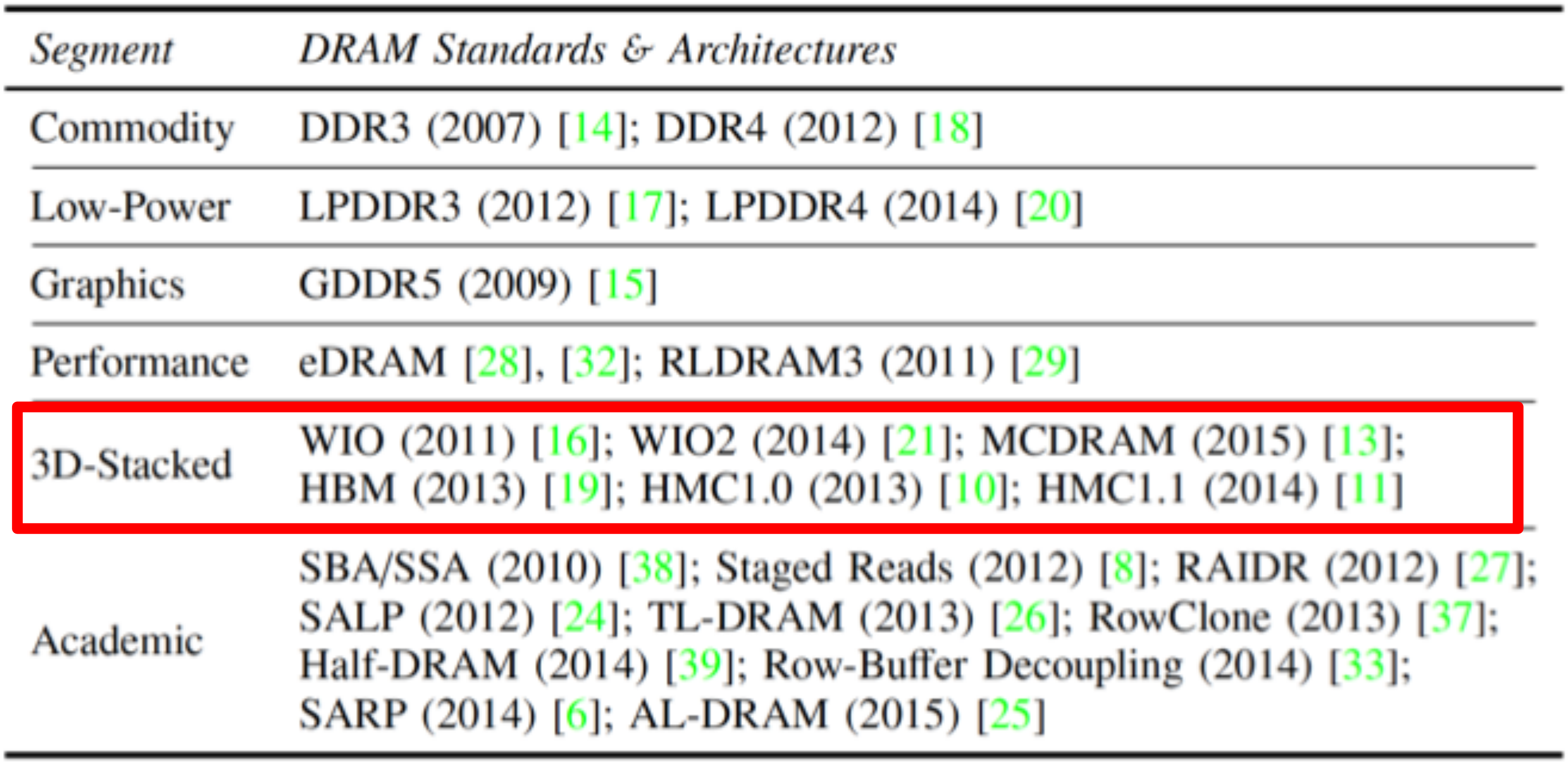
Opportunity: 3D-Stacked Logic+Memory

Hybrid Memory Cube
CONSORTIUM



Other “True 3D” technologies under development

DRAM Landscape (circa 2015)



Segment	*DRAM Standards & Architectures*
Commodity	DDR3 (2007) [14]; DDR4 (2012) [18]
Low-Power	LPDDR3 (2012) [17]; LPDDR4 (2014) [20]
Graphics	GDDR5 (2009) [15]
Performance	eDRAM [28], [32]; RLDRAM3 (2011) [29]
3D-Stacked	WIO (2011) [16]; WIO2 (2014) [21]; MCDRAM (2015) [13]; HBM (2013) [19]; HMC1.0 (2013) [10]; HMC1.1 (2014) [11]
Academic	SBA/SSA (2010) [38]; Staged Reads (2012) [8]; RAIDR (2012) [27]; SALP (2012) [24]; TL-DRAM (2013) [26]; RowClone (2013) [37]; Half-DRAM (2014) [39]; Row-Buffer Decoupling (2014) [33]; SARP (2014) [6]; AL-DRAM (2015) [25]

Table 1. Landscape of DRAM-based memory

Kim+, "Ramulator: A Flexible and Extensible DRAM Simulator", IEEE CAL 2015.

Two Key Questions in 3D-Stacked PIM

- How can we accelerate important applications if we use 3D-stacked memory as a coarse-grained accelerator?
  - what is the architecture and programming model?
  - what are the mechanisms for acceleration?

- What is the minimal processing-in-memory support we can provide?
  - without changing the system significantly
  - while achieving significant benefits

Graph Processing

- Large graphs are everywhere (circa 2015)

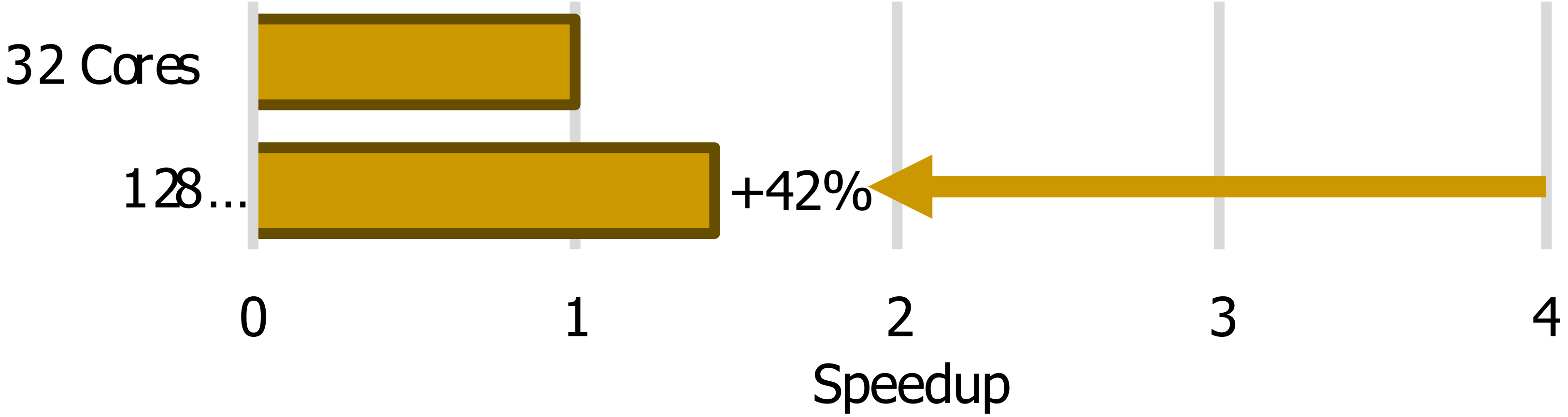
36 Million
Wikipedia Pages

1.4 Billion
Facebook Users

300 Million
Twitter Users

30 Billion
Instagram Photos

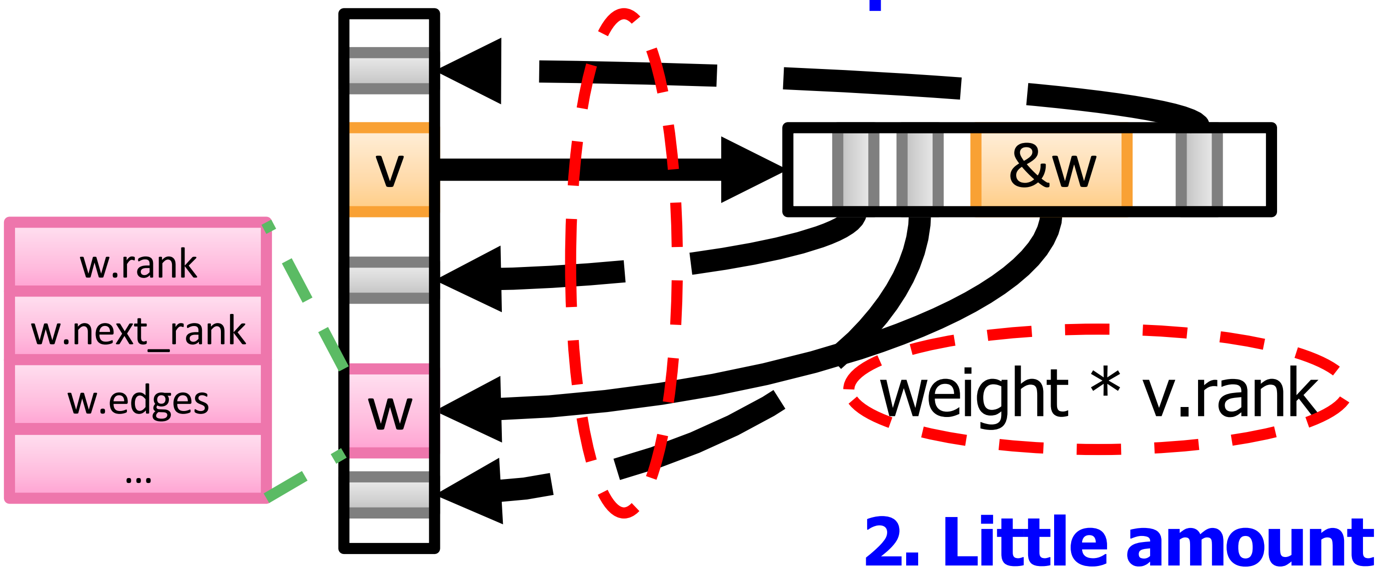
- Scalable large-scale graph processing is challenging



Key Bottlenecks in Graph Processing

```
for (v: graph.vertices) {
  for (w: v.successors) {
    w.next_rank += weight * v.rank;
  }
}
```

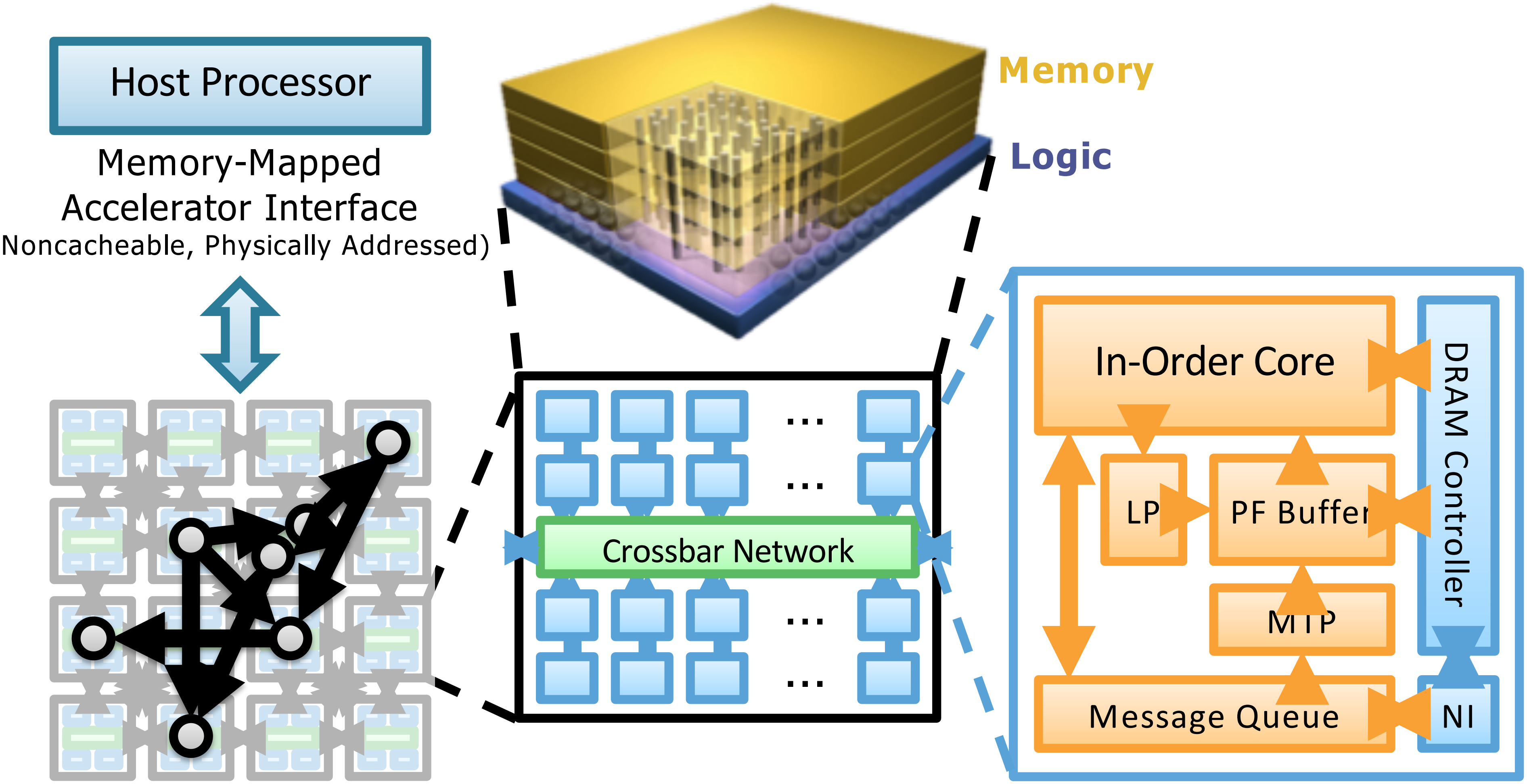
1. Frequent random memory accesses



2. Little amount of computation

Tesseract System for Graph Processing

Interconnected set of 3D-stacked memory+logic chips with simple cores

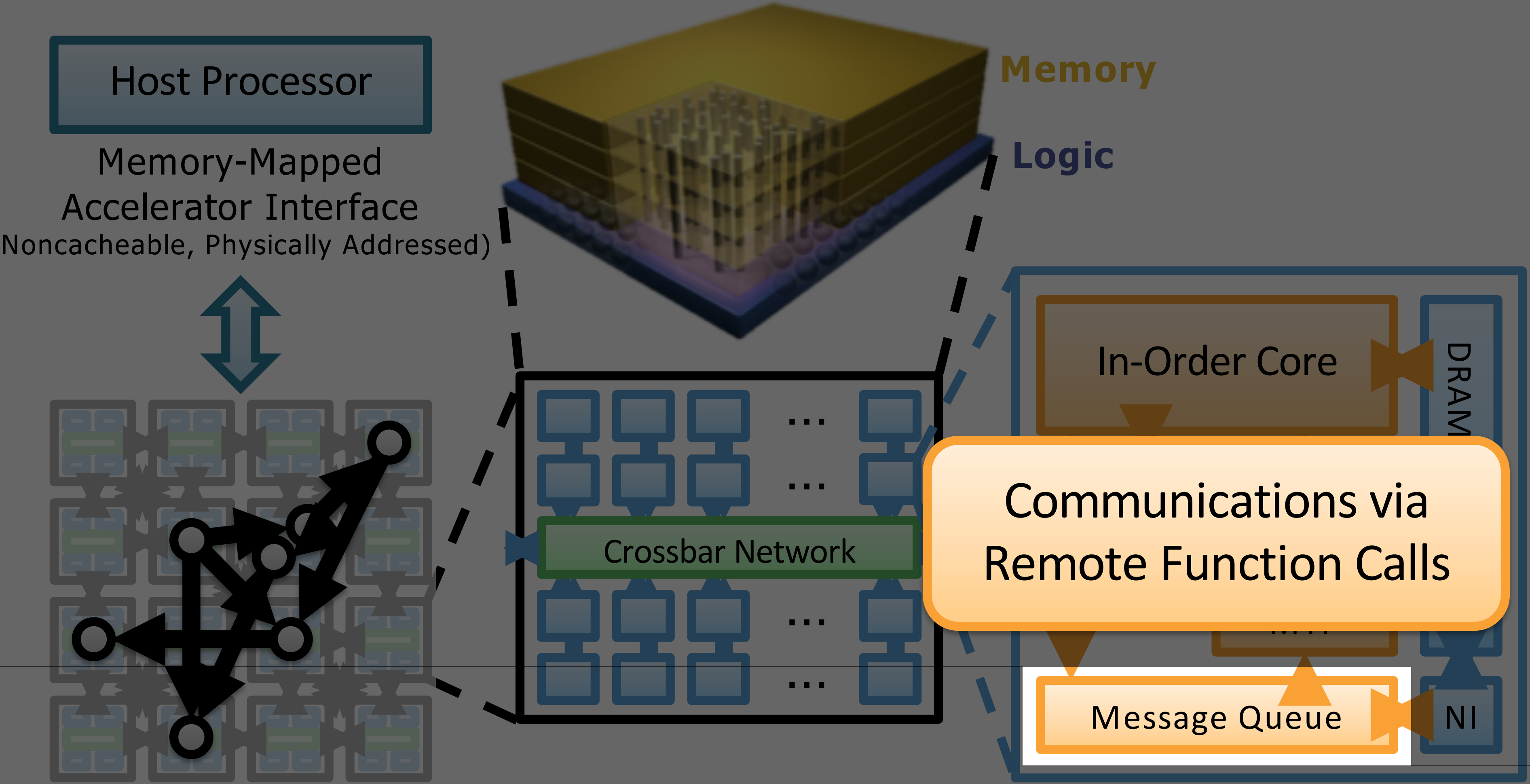


Host Processor

Memory-Mapped
Accelerator Interface
Noncacheable, Physically Addressed)

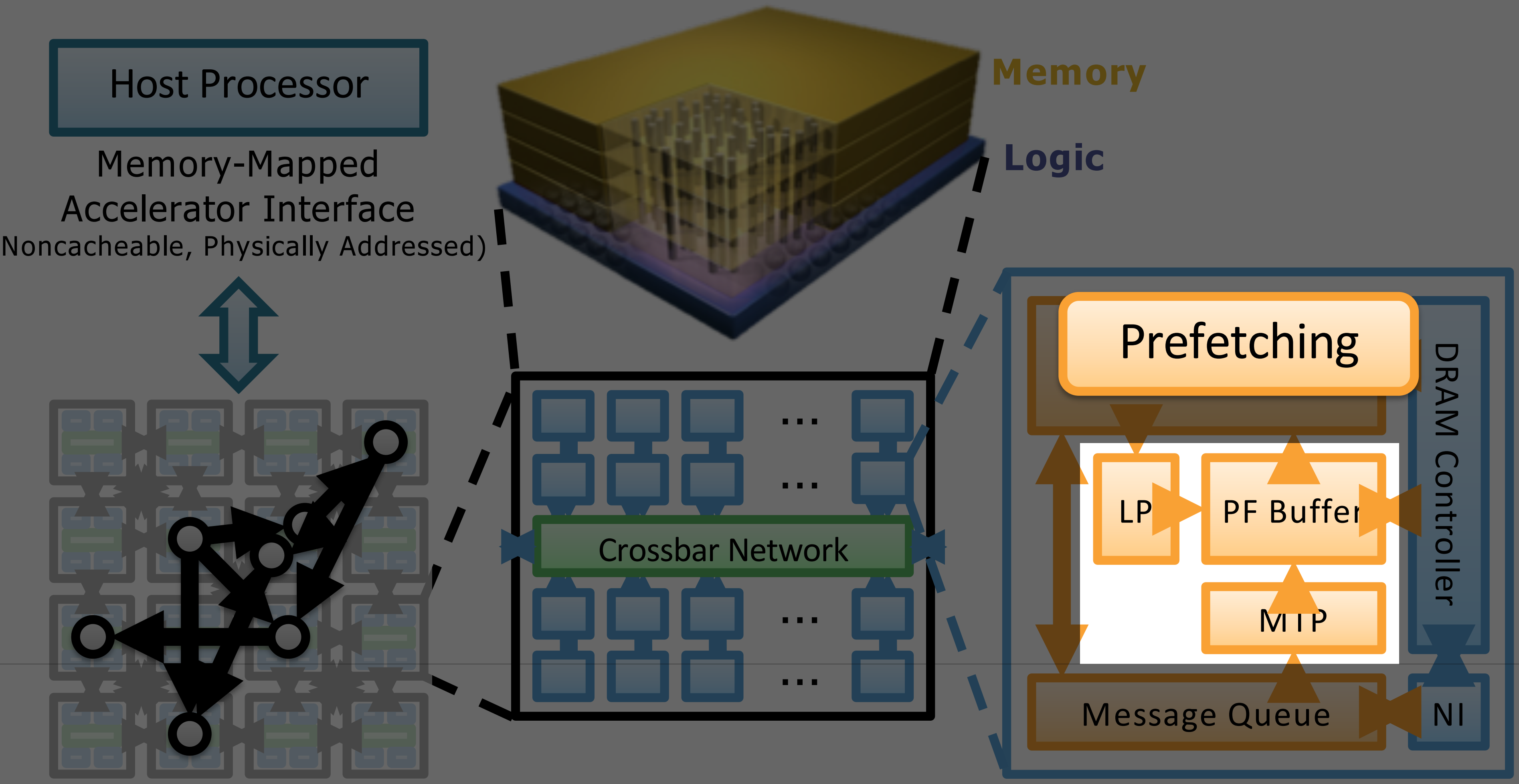
SAFARI Ahn+, "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing" ISCA 2015.

Tesseract System for Graph Processing



Communications via Remote Function Calls

Tesseract System for Graph Processing

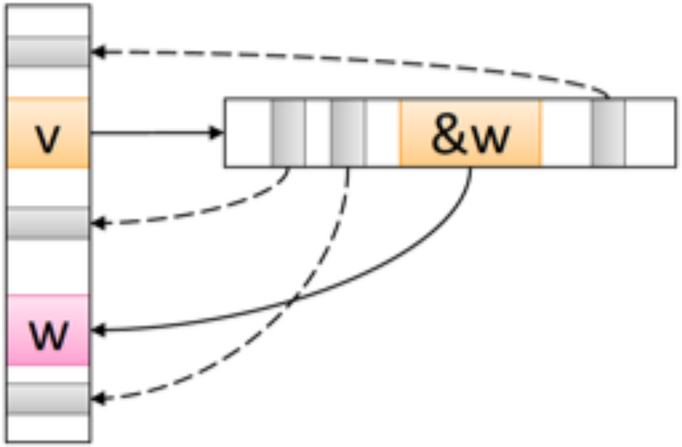


Host Processor

Memory-Mapped
Accelerator Interface
Noncacheable, Physically Addressed)

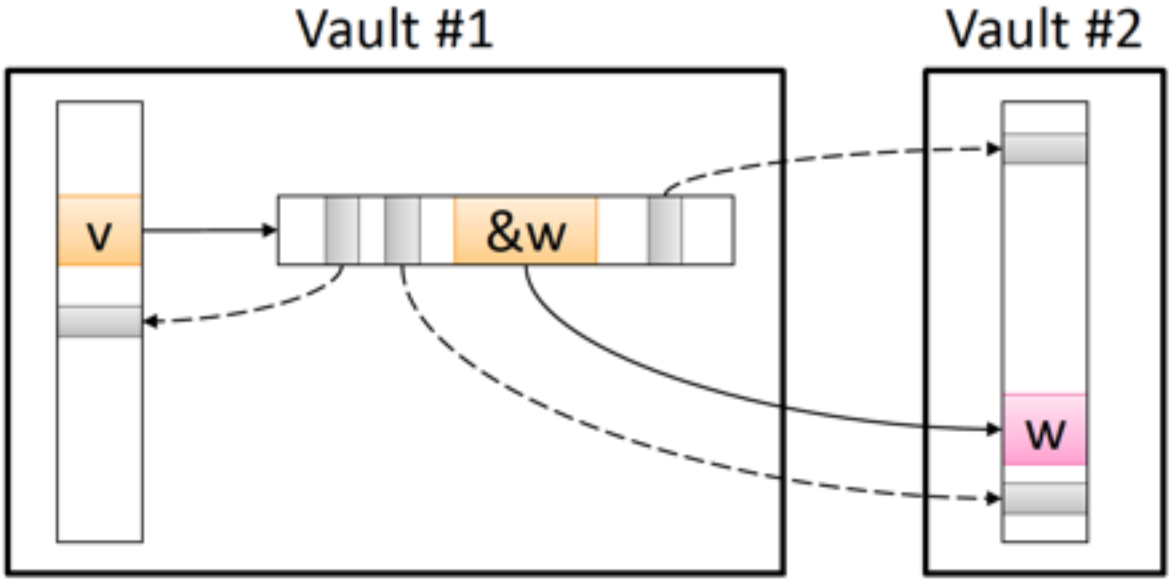
Communications In Tesseract (I)

```
for (v: graph.vertices) {
    for (w: v.successors) {
        w.next_rank += weight * v.rank;
    }
}
```



Communications In Tesseract (II)

```
for (v: graph.vertices) {
    for (w: v.successors) {
        w.next_rank += weight * v.rank;
    }
}
```

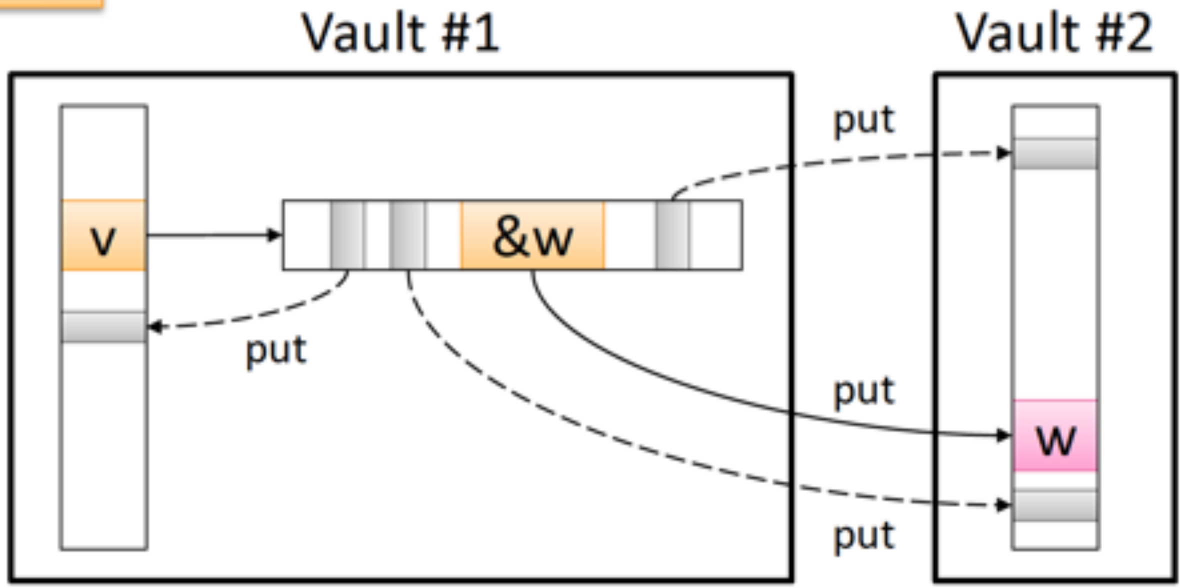


Communications In Tesseract (III)

```
for (v: graph.vertices) {
  for (w: v.successors) {
    put(w.id, function() { w.next_rank += weight * v.rank; });
  }
}
barrier();
```

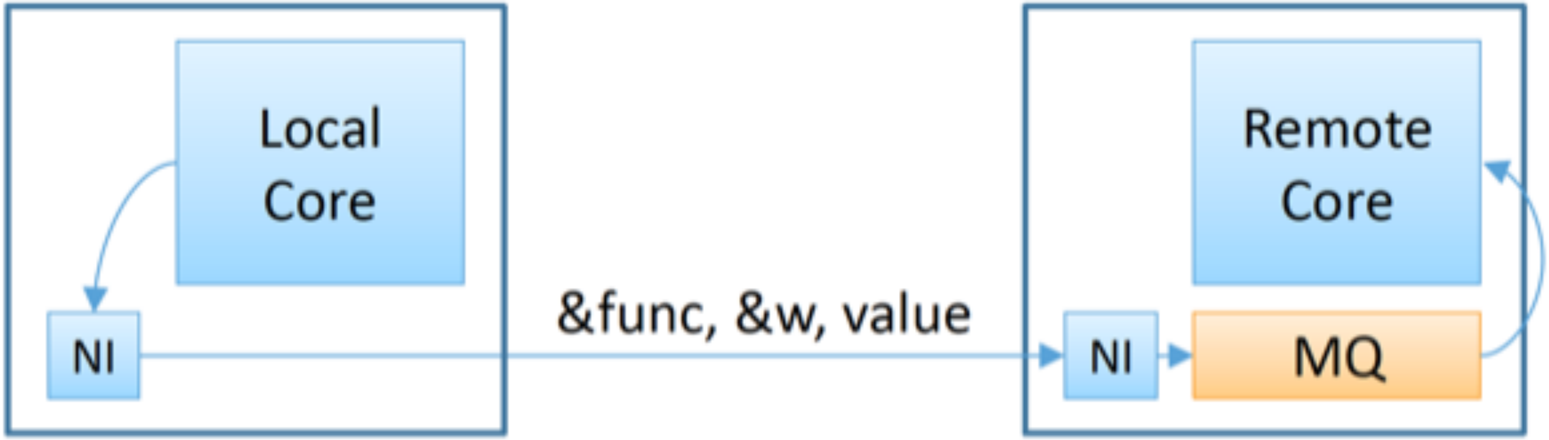
Non-blocking Remote Function Call

Can be **delayed** until the nearest barrier



Remote Function Call (Non-Blocking)

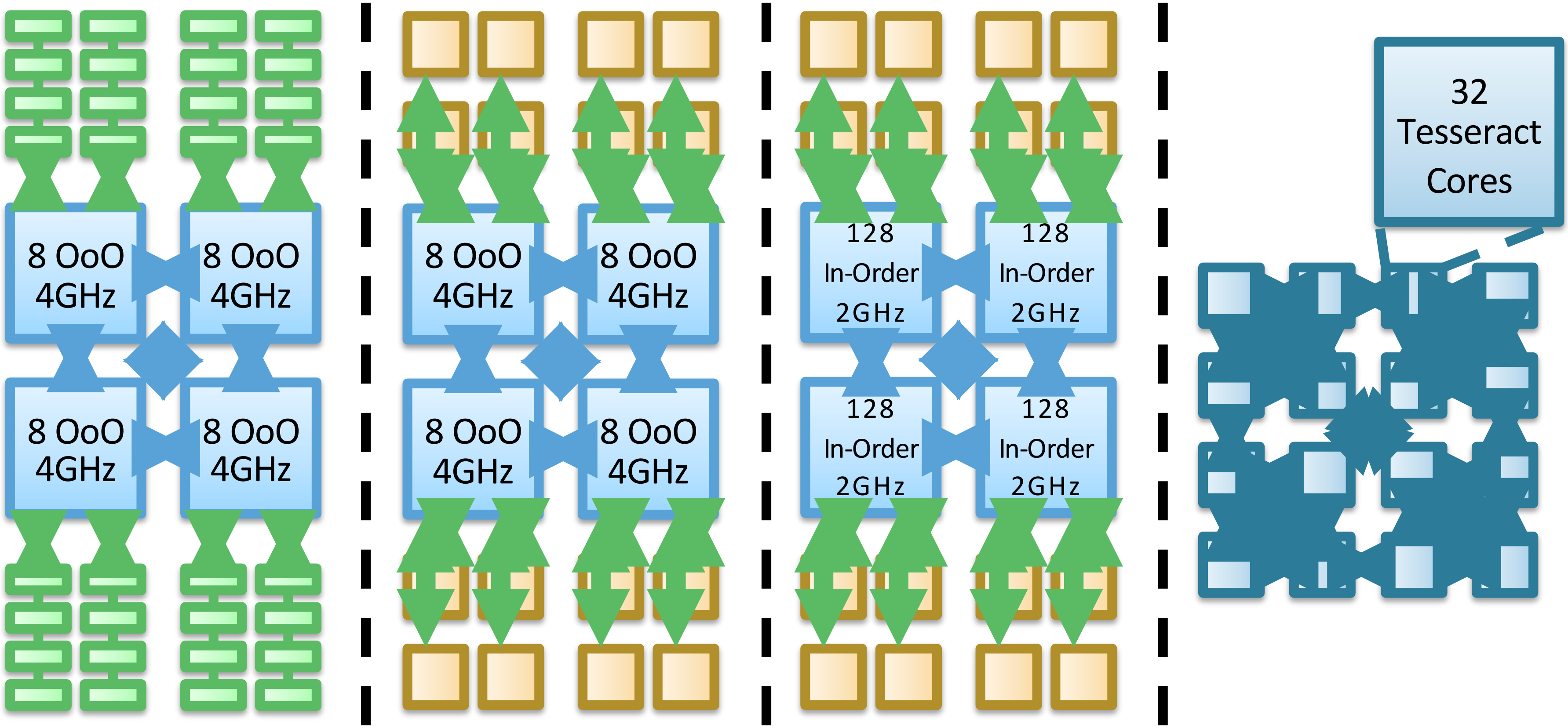
1. Send function address & args to the remote core
2. Store the incoming message to the message queue
3. Flush the message queue when it is full or a synchronization barrier is reached



put(w.id, function() { w.next_rank += value; })

Evaluated Systems

DDR3-OoO | HMC-OoO | HMC-MC | **Tesseract**

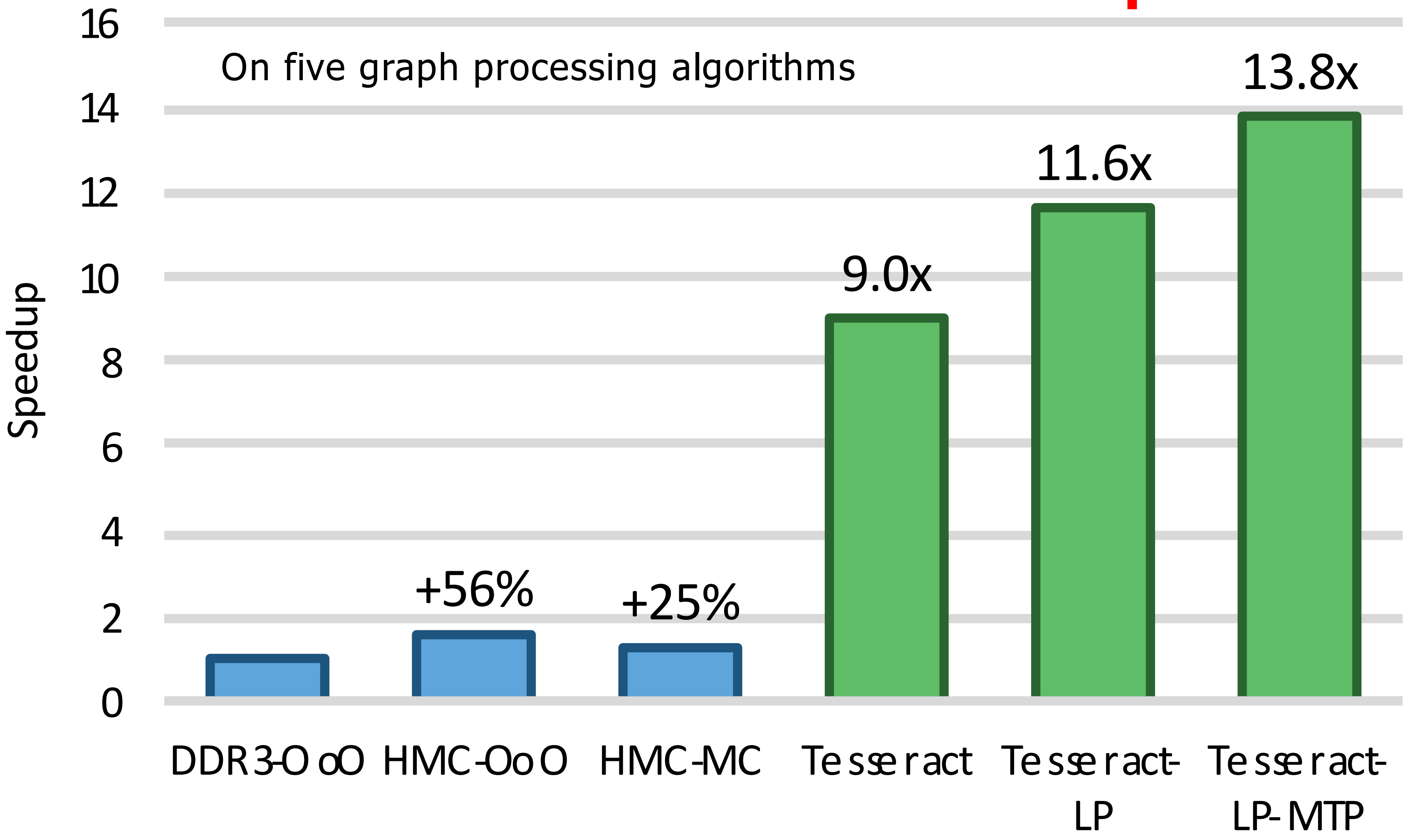


102.4GB/s | 640GB/s | 640GB/s | **8TB/s**

Ahn+, "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing" ISCA 2015.

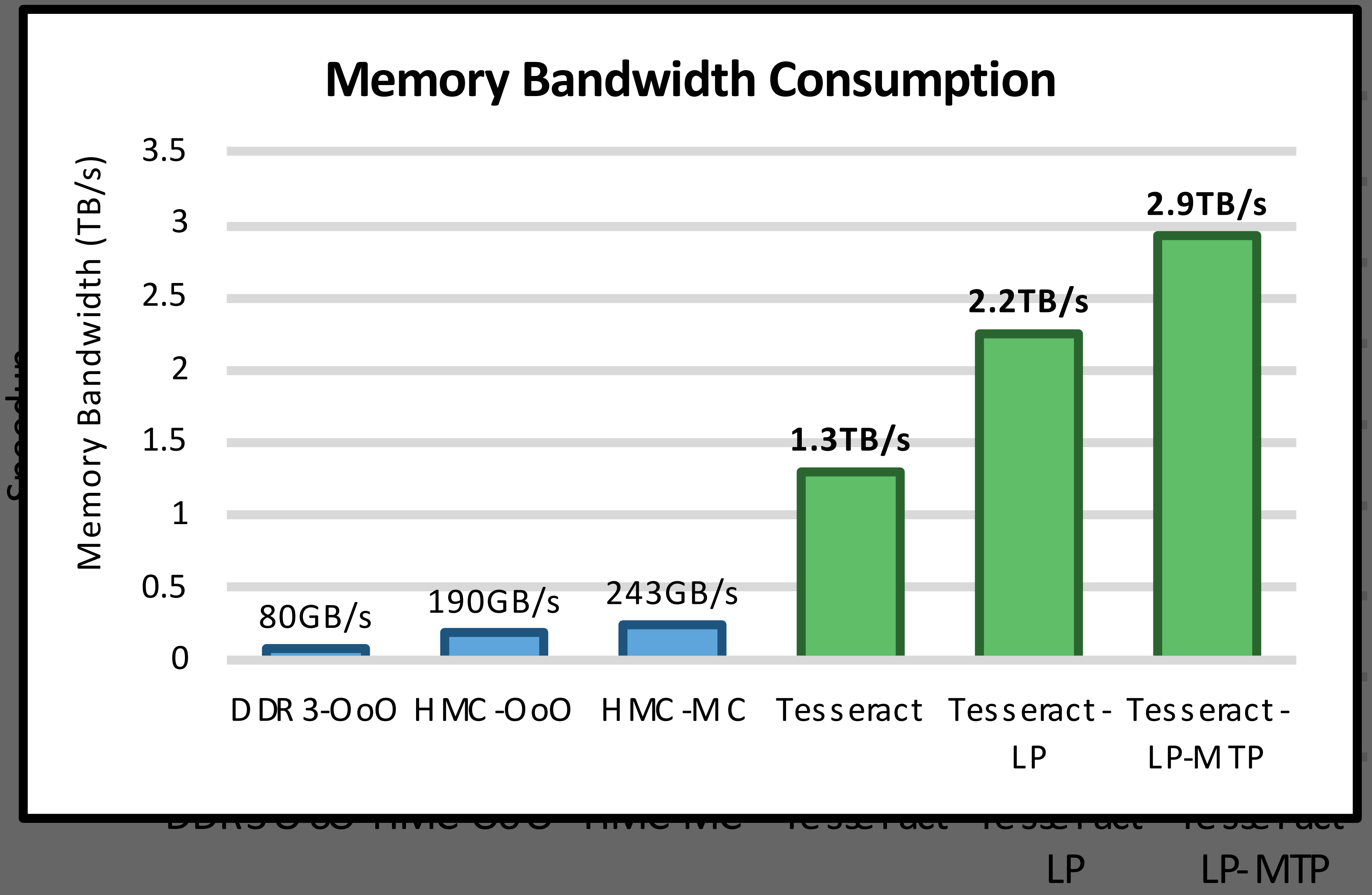
Tesseract Graph Processing Performance

>13X Performance Improvement

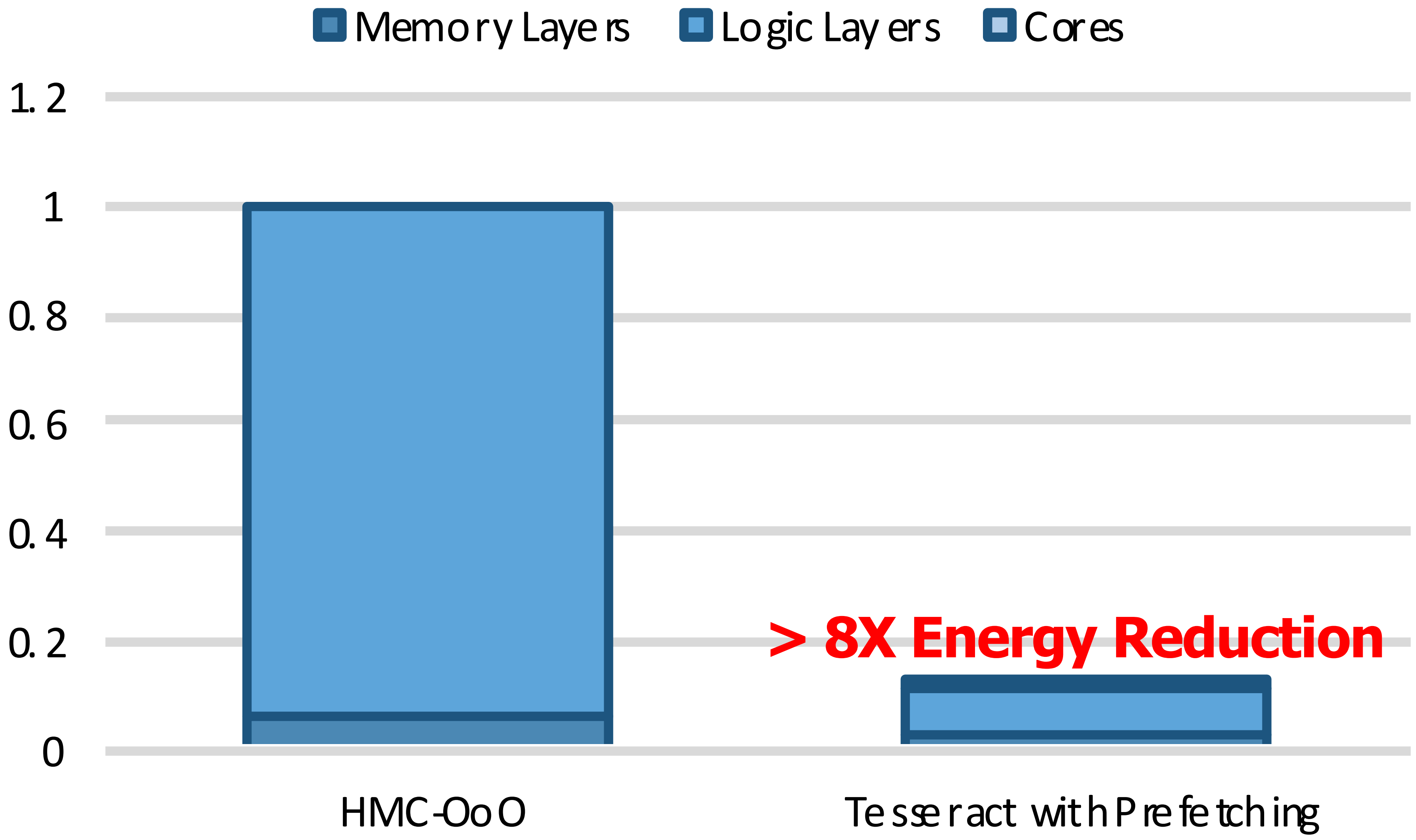


SAFARI Ahn+, "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing" ISCA 2015.

Tesseract Graph Processing Performance



Tesseract Graph Processing System Energy

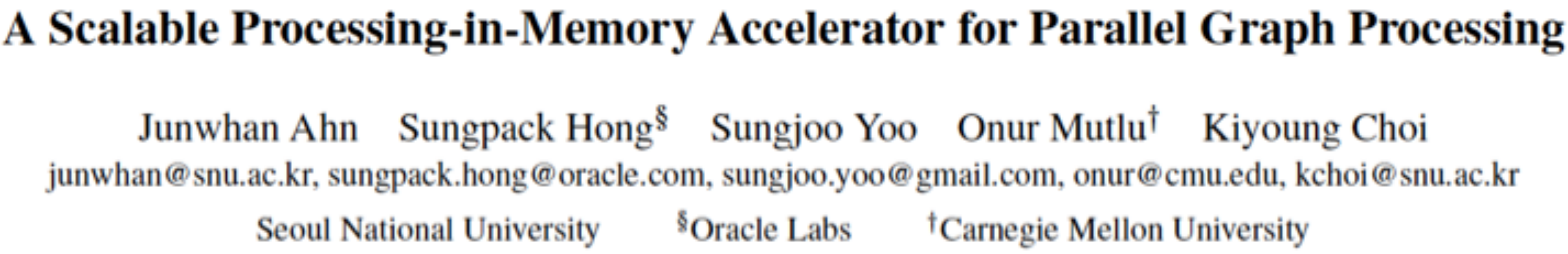


> 8X Energy Reduction

SAFARI Ahn+, "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing" ISCA 2015.

More on Tesseract

- Junwhan Ahn, Sungpack Hong, Sungjoo Yoo, Onur Mutlu, and Kiyoung Choi,
  "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing"
  Proceedings of the 42nd International Symposium on Computer Architecture (***ISCA***), Portland, OR, June 2015.
  [Slides (pdf)] [Lightning Session Slides (pdf)]



A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing

Junwhan Ahn Sungpack Hong[§] Sungjoo Yoo Onur Mutlu[†] Kiyoung Choi
junwhan@snu.ac.kr, sungpack.hong@oracle.com, sungjoo.yoo@gmail.com, onur@cmu.edu, kchoi@snu.ac.kr
Seoul National University [§]Oracle Labs [†]Carnegie Mellon University

PIM on Mobile Devices

- Amirali Boroumand, Saugata Ghose, Youngsok Kim, Rachata Ausavarungnirun, Eric Shiu, Rahul Thakur, Daehyun Kim, Aki Kuusela, Allan Knies, Parthasarathy Ranganathan, and Onur Mutlu, **"Google Workloads for Consumer Devices: Mitigating Data Movement Bottlenecks"** *Proceedings of the 23rd International Conference on Architectural Support for Programming Languages and Operating Systems* (***ASPLOS***), Williamsburg, VA, USA, March 2018.

Google Workloads for Consumer Devices: Mitigating Data Movement Bottlenecks

Amirali Boroumand[1] Saugata Ghose[1] Youngsok Kim[2]
Rachata Ausavarungnirun[1] Eric Shiu[3] Rahul Thakur[3] Daehyun Kim[4,3]
Aki Kuusela[3] Allan Knies[3] Parthasarathy Ranganathan[3] Onur Mutlu[5,1]

Google Workloads for Consumer Devices: Mitigating Data Movement Bottlenecks

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Allan Knies, Parthasarathy Ranganathan, Onur Mutlu

Consumer Devices

Consumer devices are everywhere!

Energy consumption is a first-class concern in consumer devices

Popular Google Consumer Workloads

Chrome

Google's web browser

TensorFlow Mobile

Google's machine learning framework

Video Playback

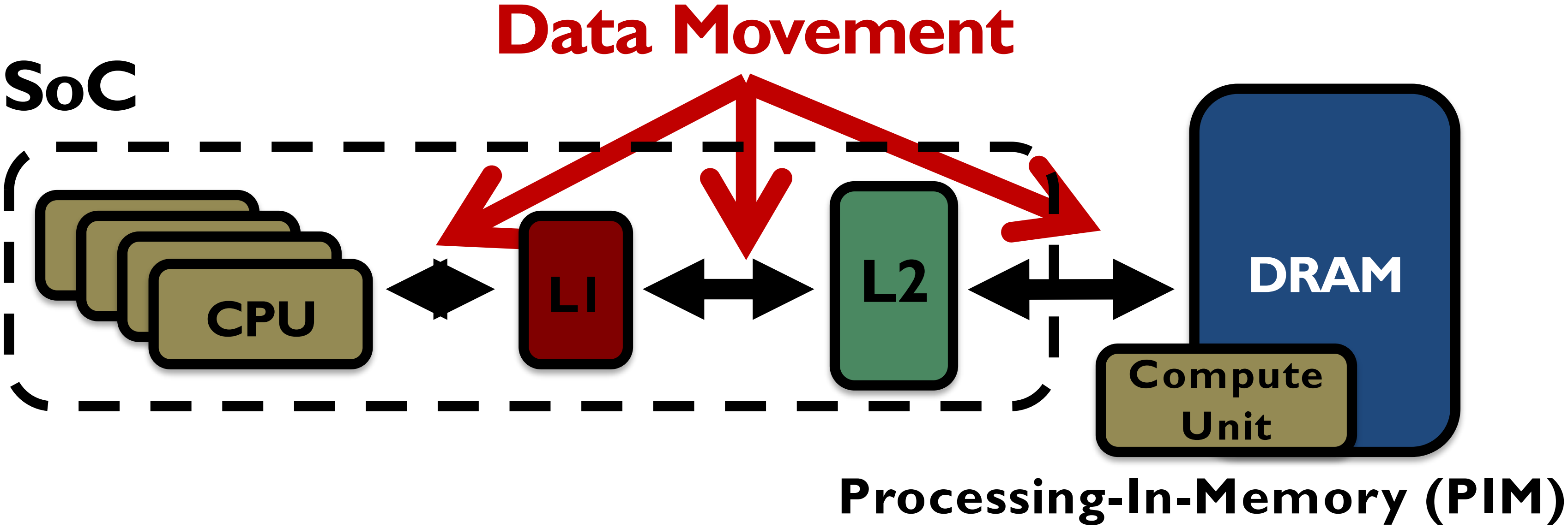
Google's video codec

Video Capture

Google's video codec

Energy Cost of Data Movement

1st key observation: 62.7% of the total system energy is spent on data movement



Potential solution: move computation **close to data**

Challenge: limited area and energy budget

Using PIM to Reduce Data Movement

2nd key observation: a significant fraction of the data movement often comes from simple functions

We can design lightweight logic to implement these *simple functions* in memory

Small embedded low-power core

PIM Core

Small fixed-function accelerators

PIM Accelerator

Offloading to PIM logic reduces energy and improves performance, on average, by 55.4% and 54.2%

Google Workloads for Consumer Devices: Mitigating Data Movement Bottlenecks

Amirali Boroumand

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Allan Knies, Parthasarathy Ranganathan, Onur Mutlu

ASPLOS 2018

SAFARI Carnegie Mellon Google

SAMSUNG SEOUL NATIONAL UNIVERSITY ETH Zürich

More on PIM for Mobile Devices

- Amirali Boroumand, Saugata Ghose, Youngsok Kim, Rachata Ausavarungnirun, Eric Shiu, Rahul Thakur, Daehyun Kim, Aki Kuusela, Allan Knies, Parthasarathy Ranganathan, and Onur Mutlu, **"Google Workloads for Consumer Devices: Mitigating Data Movement Bottlenecks"** *Proceedings of the 23rd International Conference on Architectural Support for Programming Languages and Operating Systems* (***ASPLOS***), Williamsburg, VA, USA, March 2018.

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Google Workloads for Consumer Devices: Mitigating Data Movement Bottlenecks

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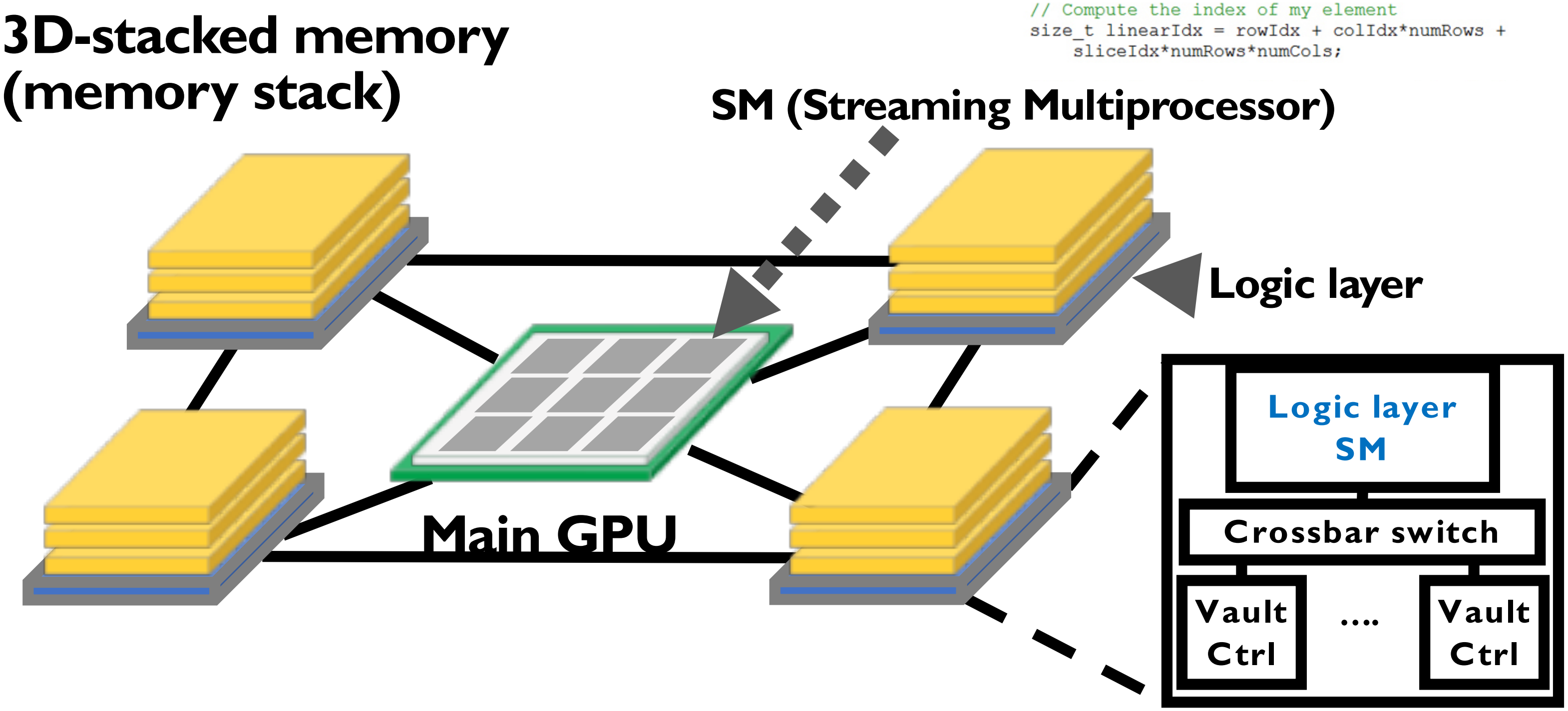
Aki Kuusela[3] Allan Knies[3] Parthasarathy Ranganathan[3] Onur Mutlu[5,1]

Truly Distributed GPU Processing with PIM?

```
__global__
void applyScaleFactorsKernel( uint8_T * const out,
    uint8_T const * const in, const double *factor,
    size_t const numRows, size_t const numCols )
{
    // Work out which pixel we are working on.
    const int rowIdx = blockIdx.x * blockDim.x + threadIdx.x;
    const int colIdx = blockIdx.y;
    const int sliceIdx = threadIdx.z;

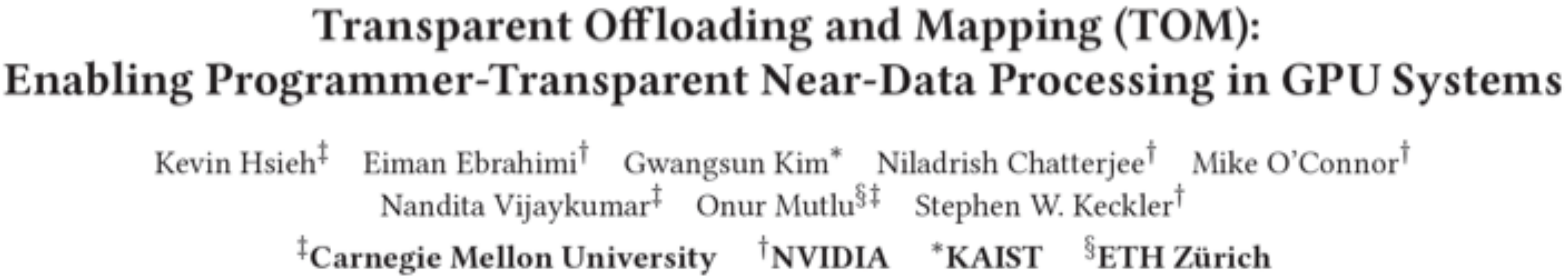
    // Check this thread isn't off the image
    if( rowIdx >= numRows ) return;

    // Compute the index of my element
    size_t linearIdx = rowIdx + colIdx*numRows +
        sliceIdx*numRows*numCols;
```



Accelerating GPU Execution with PIM (I)

- Kevin Hsieh, Eiman Ebrahimi, Gwangsun Kim, Niladrish Chatterjee, Mike O'Connor, Nandita Vijaykumar, Onur Mutlu, and Stephen W. Keckler, **"Transparent Offloading and Mapping (TOM): Enabling Programmer-Transparent Near-Data Processing in GPU Systems"**
  Proceedings of the 43rd International Symposium on Computer Architecture (***ISCA***), Seoul, South Korea, June 2016.
  [Slides (pptx) (pdf)]
  [Lightning Session Slides (pptx) (pdf)]

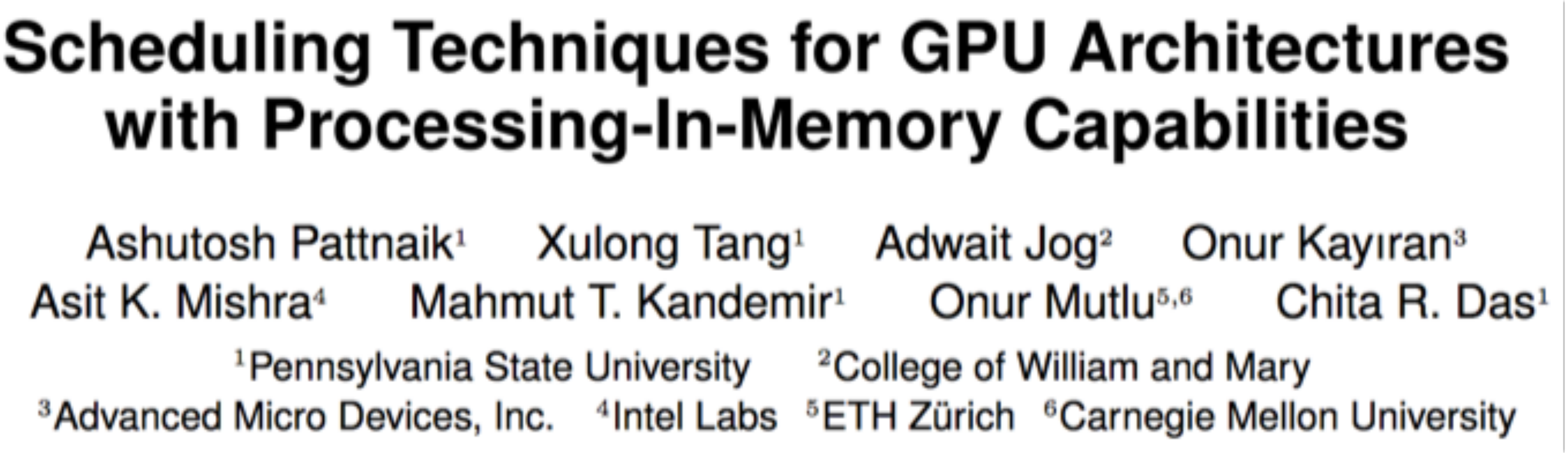


Transparent Offloading and Mapping (TOM):
Enabling Programmer-Transparent Near-Data Processing in GPU Systems

Kevin Hsieh‡ Eiman Ebrahimi† Gwangsun Kim* Niladrish Chatterjee† Mike O'Connor†
Nandita Vijaykumar‡ Onur Mutlu§‡ Stephen W. Keckler†
‡Carnegie Mellon University †NVIDIA *KAIST §ETH Zürich

Accelerating GPU Execution with PIM (II)

- Ashutosh Pattnaik, Xulong Tang, Adwait Jog, Onur Kayiran, Asit K. Mishra, Mahmut T. Kandemir, Onur Mutlu, and Chita R. Das, **"Scheduling Techniques for GPU Architectures with Processing-In-Memory Capabilities"** *Proceedings of the 25th International Conference on Parallel Architectures and Compilation Techniques (**PACT**)*, Haifa, Israel, September 2016.



Scheduling Techniques for GPU Architectures with Processing-In-Memory Capabilities

Ashutosh Pattnaik[1] Xulong Tang[1] Adwait Jog[2] Onur Kayıran[3]
Asit K. Mishra[4] Mahmut T. Kandemir[1] Onur Mutlu[5,6] Chita R. Das[1]
[1]Pennsylvania State University [2]College of William and Mary
[3]Advanced Micro Devices, Inc. [4]Intel Labs [5]ETH Zürich [6]Carnegie Mellon University

Accelerating Linked Data Structures

- Kevin Hsieh, Samira Khan, Nandita Vijaykumar, Kevin K. Chang, Amirali Boroumand, Saugata Ghose, and Onur Mutlu, **"Accelerating Pointer Chasing in 3D-Stacked Memory: Challenges, Mechanisms, Evaluation"** *Proceedings of the 34th IEEE International Conference on Computer Design (**ICCD**)*, Phoenix, AZ, USA, October 2016.

Accelerating Pointer Chasing in 3D-Stacked Memory: Challenges, Mechanisms, Evaluation

Kevin Hsieh[†] Samira Khan[‡] Nandita Vijaykumar[†]
Kevin K. Chang[†] Amirali Boroumand[†] Saugata Ghose[†] Onur Mutlu[§†]
[†]*Carnegie Mellon University* [‡]*University of Virginia* [§]*ETH Zürich*

Accelerating Dependent Cache Misses

- Milad Hashemi, Khubaib, Eiman Ebrahimi, Onur Mutlu, and Yale N. Patt, **"Accelerating Dependent Cache Misses with an Enhanced Memory Controller"**
  Proceedings of the 43rd International Symposium on Computer Architecture (***ISCA***), Seoul, South Korea, June 2016.
  [Slides (pptx) (pdf)]
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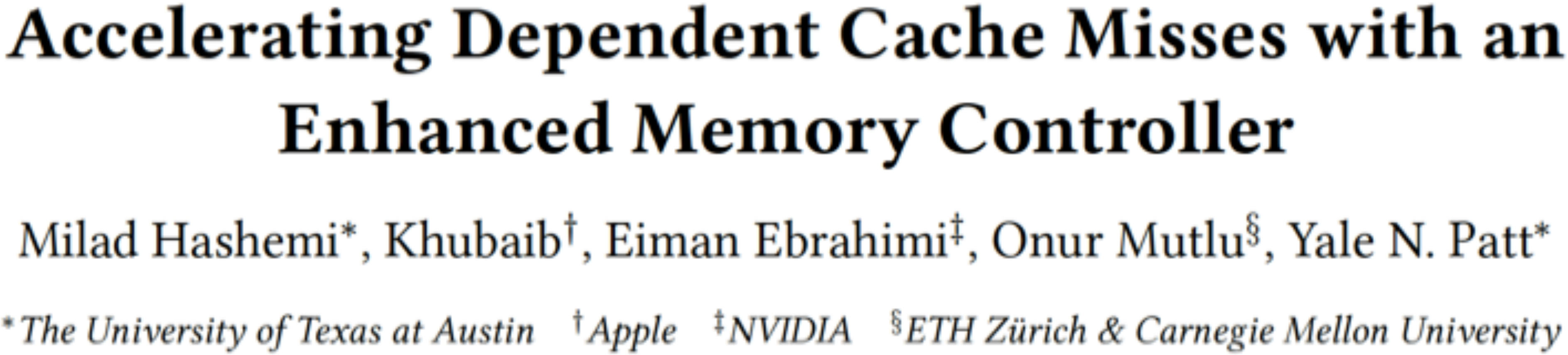


Accelerating Dependent Cache Misses with an Enhanced Memory Controller

Milad Hashemi*, Khubaib†, Eiman Ebrahimi‡, Onur Mutlu§, Yale N. Patt*

**The University of Texas at Austin ††Apple ‡NVIDIA §ETH Zürich & Carnegie Mellon University*

Two Key Questions in 3D-Stacked PIM

- How can we accelerate important applications if we use 3D-stacked memory as a coarse-grained accelerator?
  - what is the architecture and programming model?
  - what are the mechanisms for acceleration?

- What is the minimal processing-in-memory support we can provide?
  - without changing the system significantly
  - while achieving significant benefits

PEI: PIM-Enabled Instructions (Ideas)

- Goal: Develop mechanisms to get the most out of near-data processing with minimal cost, minimal changes to the system, no changes to the programming model
- Key Idea 1: Expose each PIM operation as a cache-coherent, virtually-addressed host processor instruction (called PEI) that operates on only a single cache block
  - e.g., __pim_add(&w.next_rank, value) → pim.add r1, (r2)
  - No changes sequential execution/programming model
  - No changes to virtual memory
  - Minimal changes to cache coherence
  - No need for data mapping: Each PEI restricted to a single memory module
- Key Idea 2: Dynamically decide where to execute a PEI (i.e., the host processor or PIM accelerator) based on simple locality characteristics and simple hardware predictors
  - Execute each operation at the location that provides the best performance

PEI: PIM-Enabled Instructions (Example)

```
for (v: graph.vertices) {
  value = weight * v.rank;
  for (w: v.successors) {
    __pim_add(&w.next_rank, value);
  }
}
pfence();
```

`pim.add r1, (r2)`

`pfence`

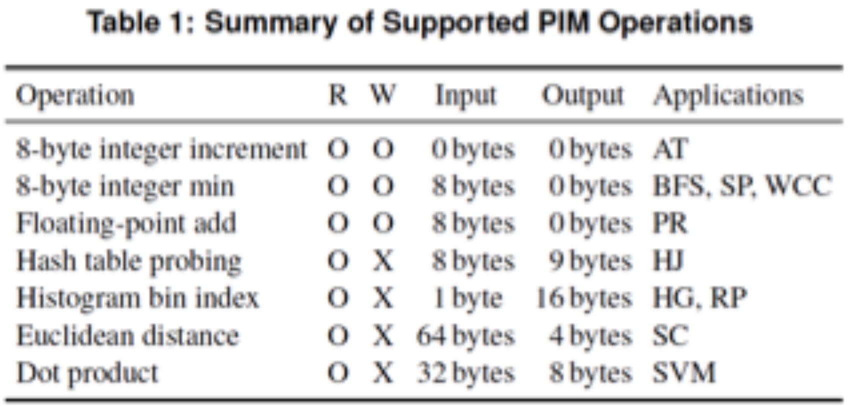
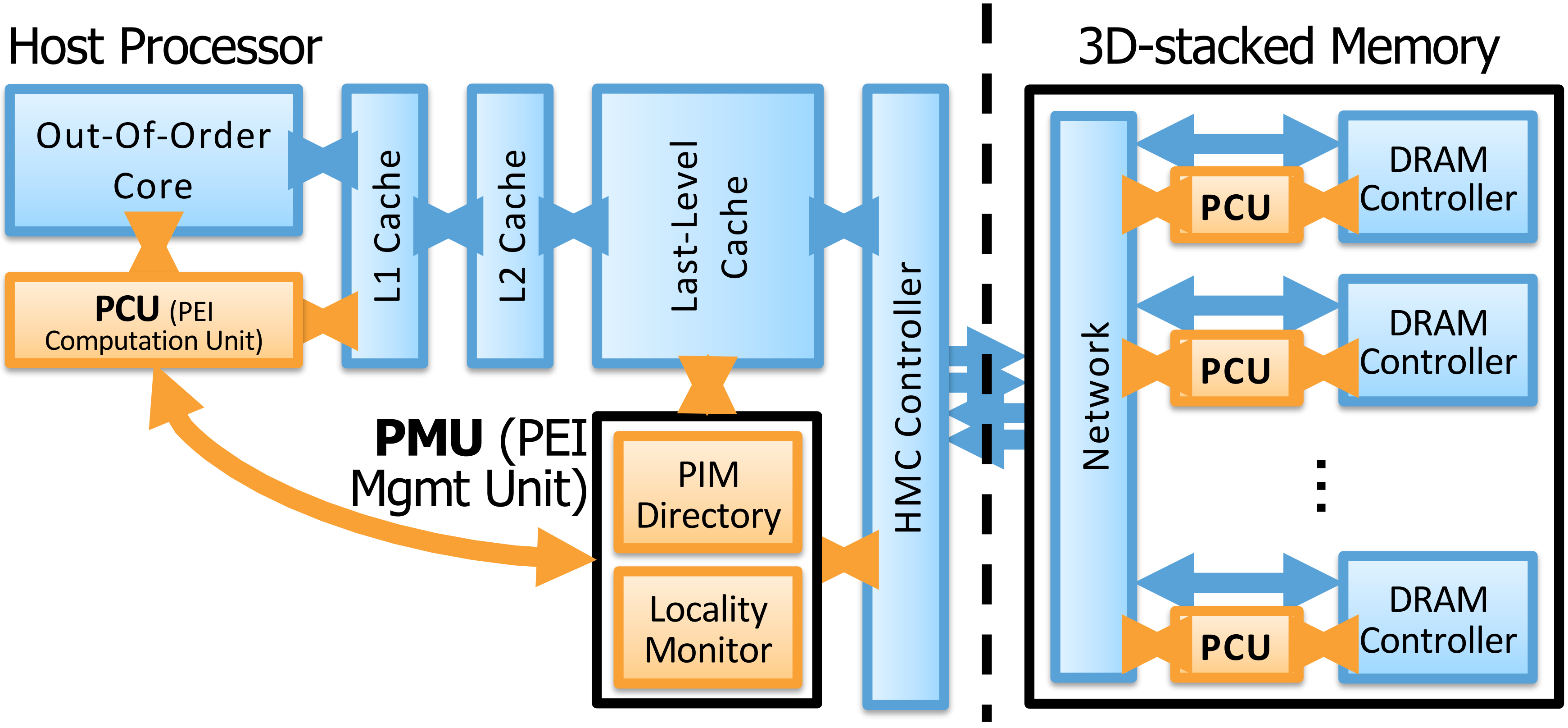


Table 1: Summary of Supported PIM Operations

Operation	R	W	Input	Output	Applications
8-byte integer increment	O	O	0 bytes	0 bytes	AT
8-byte integer min	O	O	8 bytes	0 bytes	BFS, SP, WCC
Floating-point add	O	O	8 bytes	0 bytes	PR
Hash table probing	O	X	8 bytes	9 bytes	HJ
Histogram bin index	O	X	1 byte	16 bytes	HG, RP
Euclidean distance	O	X	64 bytes	4 bytes	SC
Dot product	O	X	32 bytes	8 bytes	SVM

- Executed either in memory or in the processor: dynamic decision
  - Low-cost locality monitoring for a single instruction
- Cache-coherent, virtually-addressed, single cache block only
- Atomic between different PEIs
- *Not* atomic with normal instructions (use *pfence* for ordering)

Example (Abstract) PEI uArchitecture



Example PEI uArchitecture

PEI: Initial Evaluation Results

- Initial evaluations with 10 emerging data-intensive workloads
  - Large-scale graph processing
  - In-memory data analytics
  - Machine learning and data mining
  - Three input sets (small, medium, large) for each workload to analyze the impact of data locality

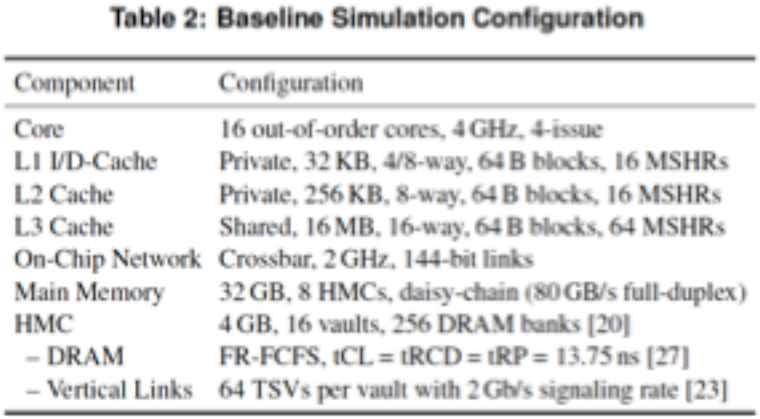


Table 2: Baseline Simulation Configuration

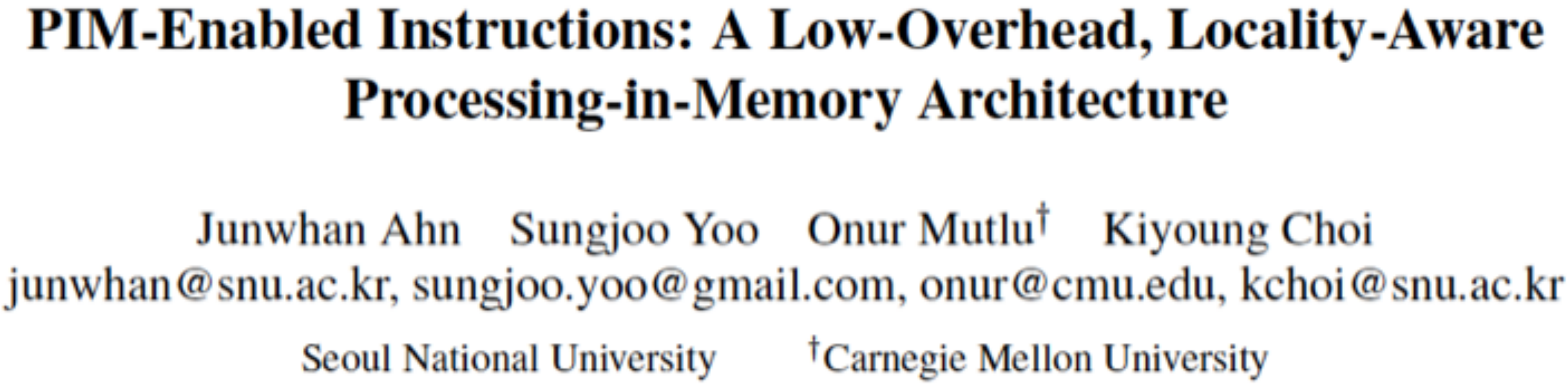
Component	Configuration
Core	16 out-of-order cores, 4 GHz, 4-issue
L1 I/D-Cache	Private, 32 KB, 4/8-way, 64 B blocks, 16 MSHRs
L2 Cache	Private, 256 KB, 8-way, 64 B blocks, 16 MSHRs
L3 Cache	Shared, 16 MB, 16-way, 64 B blocks, 64 MSHRs
On-Chip Network	Crossbar, 2 GHz, 144-bit links
Main Memory	32 GB, 8 HMCs, daisy-chain (80 GB/s full-duplex)
HMC	4 GB, 16 vaults, 256 DRAM banks [20]
– DRAM	FR-FCFS, tCL = tRCD = tRP = 13.75 ns [27]
– Vertical Links	64 TSVs per vault with 2 Gb/s signaling rate [23]

- Pin-based cycle-level x86-64 simulation

- **Performance Improvement and Energy Reduction:**
  - 47% average speedup with large input data sets
  - 32% speedup with small input data sets
  - 25% avg. energy reduction in a single node with large input data sets

Simpler PIM: PIM-Enabled Instructions

- Junwhan Ahn, Sungjoo Yoo, Onur Mutlu, and Kiyoung Choi, **"PIM-Enabled Instructions: A Low-Overhead, Locality-Aware Processing-in-Memory Architecture"** *Proceedings of the 42nd International Symposium on Computer Architecture* (***ISCA***), Portland, OR, June 2015. [Slides (pdf)] [Lightning Session Slides (pdf)]

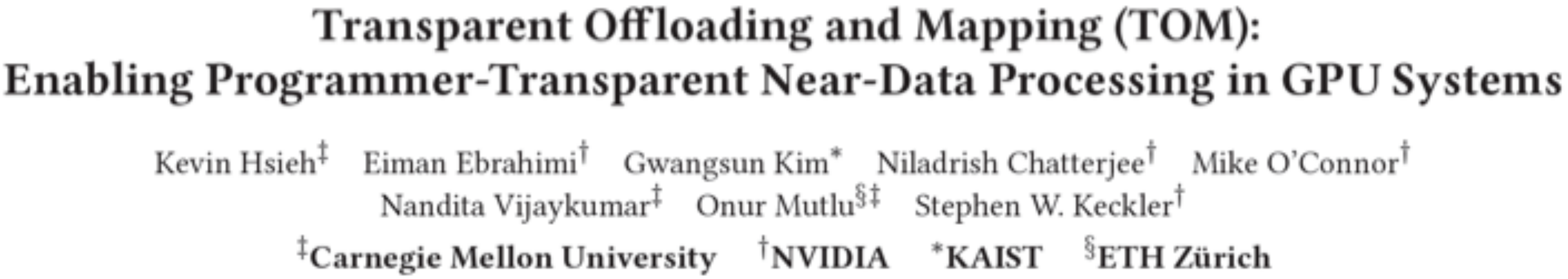


PIM-Enabled Instructions: A Low-Overhead, Locality-Aware Processing-in-Memory Architecture

Junwhan Ahn Sungjoo Yoo Onur Mutlu[†] Kiyoung Choi
junwhan@snu.ac.kr, sungjoo.yoo@gmail.com, onur@cmu.edu, kchoi@snu.ac.kr
Seoul National University [†]Carnegie Mellon University

Automatic Code and Data Mapping

- Kevin Hsieh, Eiman Ebrahimi, Gwangsun Kim, Niladrish Chatterjee, Mike O'Connor, Nandita Vijaykumar, Onur Mutlu, and Stephen W. Keckler, **"Transparent Offloading and Mapping (TOM): Enabling Programmer-Transparent Near-Data Processing in GPU Systems"**
  Proceedings of the 43rd International Symposium on Computer Architecture (***ISCA***), Seoul, South Korea, June 2016.
  [Slides (pptx) (pdf)]
  [Lightning Session Slides (pptx) (pdf)]



Transparent Offloading and Mapping (TOM):
Enabling Programmer-Transparent Near-Data Processing in GPU Systems

Kevin Hsieh[‡] Eiman Ebrahimi[†] Gwangsun Kim[*] Niladrish Chatterjee[†] Mike O'Connor[†]
Nandita Vijaykumar[‡] Onur Mutlu[§‡] Stephen W. Keckler[†]
[‡]Carnegie Mellon University [†]NVIDIA [*]KAIST [§]ETH Zürich

Efficient Automatic Data Coherence Support

- Amirali Boroumand, Saugata Ghose, Minesh Patel, Hasan Hassan, Brandon Lucia, Kevin Hsieh, Krishna T. Malladi, Hongzhong Zheng, and Onur Mutlu,
"LazyPIM: An Efficient Cache Coherence Mechanism for Processing-in-Memory"
IEEE Computer Architecture Letters (***CAL***), June 2016.

LazyPIM: An Efficient Cache Coherence Mechanism for Processing-in-Memory

Amirali Boroumand[†], Saugata Ghose[†], Minesh Patel[†], Hasan Hassan[†§], Brandon Lucia[†],
Kevin Hsieh[†], Krishna T. Malladi[*], Hongzhong Zheng[*], and Onur Mutlu[‡†]

[†]*Carnegie Mellon University* [*]*Samsung Semiconductor, Inc.* [§]*TOBB ETÜ* [‡]*ETH Zürich*

Challenge and Opportunity for Future

Fundamentally

Energy-Efficient

(Data-Centric)

Computing Architectures

Challenge and Opportunity for Future

Fundamentally

Low-Latency

(Data-Centric)

Computing Architectures

Challenge and Opportunity for Future

Computing Architectures
with
Minimal Data Movement

Agenda

- Major Trends Affecting Main Memory
- The Need for Intelligent Memory Controllers
  - Bottom Up: Push from Circuits and Devices
  - Top Down: Pull from Systems and Applications
- Processing in Memory: Two Directions
  - Minimally Changing Memory Chips
  - Exploiting 3D-Stacked Memory
- How to Enable Adoption of Processing in Memory
- Conclusion

Eliminating the Adoption Barriers

How to Enable Adoption of Processing in Memory

Barriers to Adoption of PIM

1. Functionality of and applications for PIM

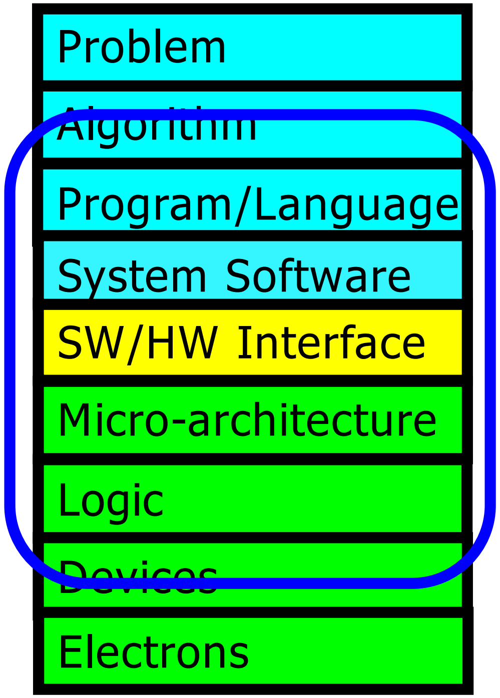
2. Ease of programming (interfaces and compiler/HW support)

3. System support: coherence & virtual memory

4. Runtime systems for adaptive scheduling, data mapping, access/sharing control

5. Infrastructures to assess benefits and feasibility

We Need to Revisit the Entire Stack



Problem

Algorithm

Program/Language

System Software

SW/HW Interface

Micro-architecture

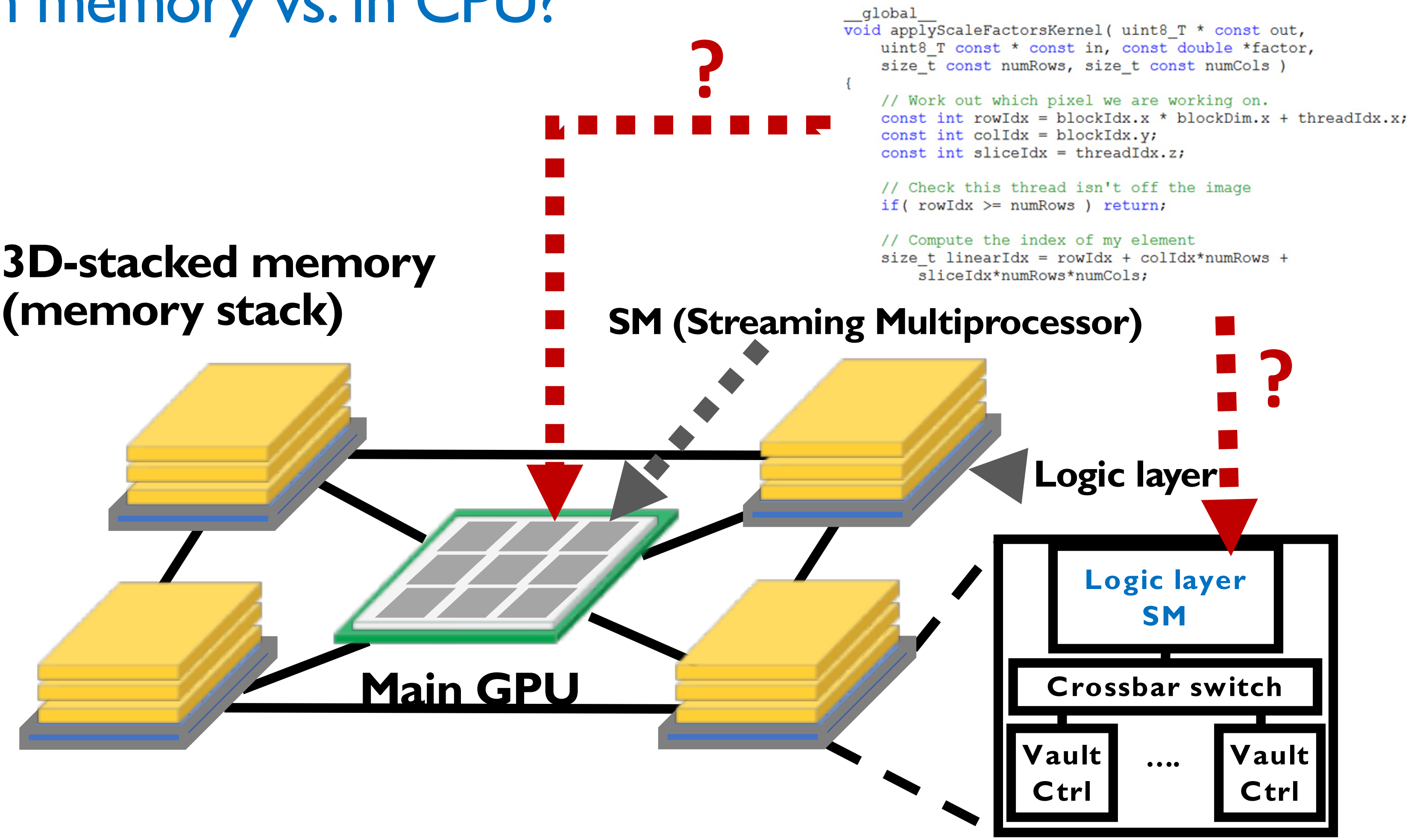
Logic

Devices

Electrons

Key Challenge 1: Code Mapping

- **Challenge 1:** Which operations should be executed in memory vs. in CPU?



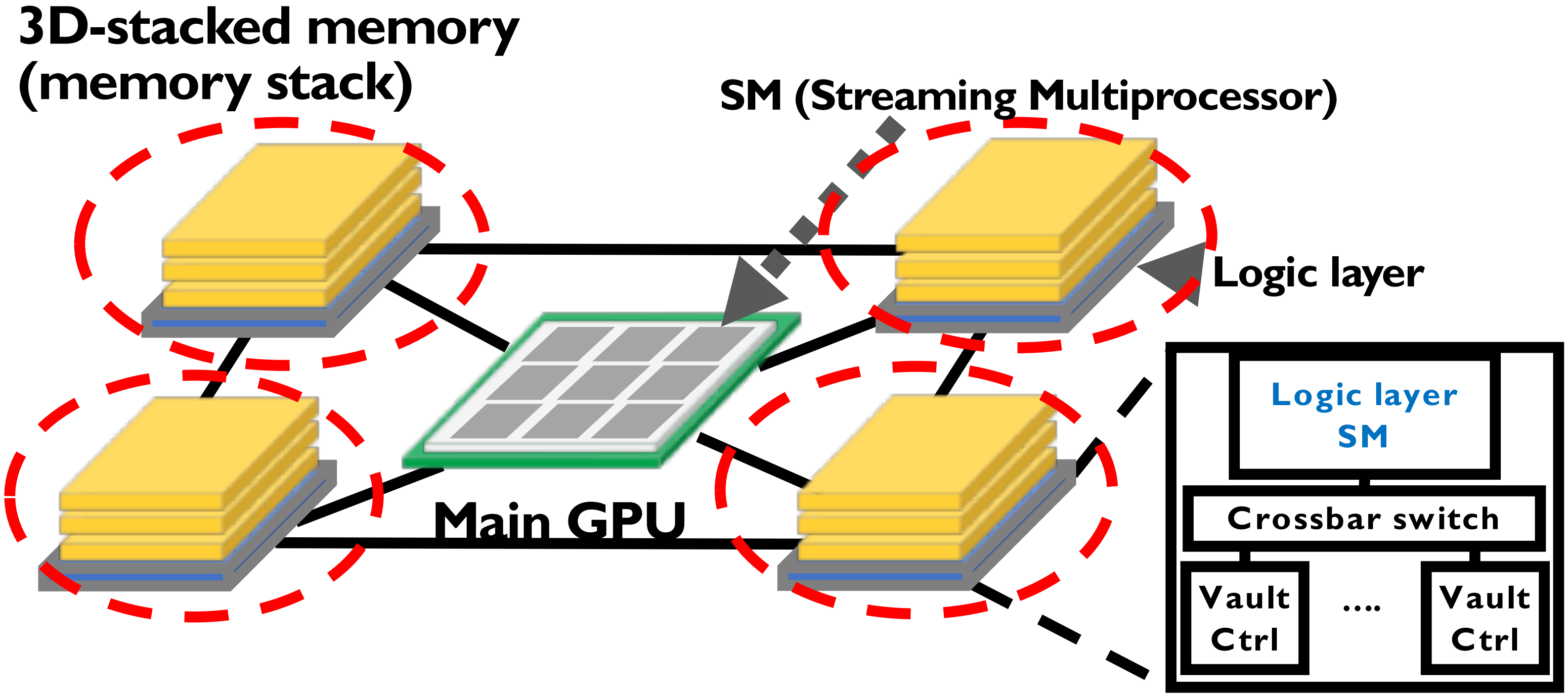
```
__global__
void applyScaleFactorsKernel( uint8_T * const out,
    uint8_T const * const in, const double *factor,
    size_t const numRows, size_t const numCols )
{
    // Work out which pixel we are working on.
    const int rowIdx = blockIdx.x * blockDim.x + threadIdx.x;
    const int colIdx = blockIdx.y;
    const int sliceIdx = threadIdx.z;

    // Check this thread isn't off the image
    if( rowIdx >= numRows ) return;

    // Compute the index of my element
    size_t linearIdx = rowIdx + colIdx*numRows +
        sliceIdx*numRows*numCols;
```

Key Challenge 2: Data Mapping

- **Challenge 2:** How should data be mapped to different 3D memory stacks?



How to Do the Code and Data Mapping?

- Kevin Hsieh, Eiman Ebrahimi, Gwangsun Kim, Niladrish Chatterjee, Mike O'Connor, Nandita Vijaykumar, Onur Mutlu, and Stephen W. Keckler, **"Transparent Offloading and Mapping (TOM): Enabling Programmer-Transparent Near-Data Processing in GPU Systems"**
*Proceedings of the 43rd International Symposium on Computer Architecture (**ISCA**)*, Seoul, South Korea, June 2016.
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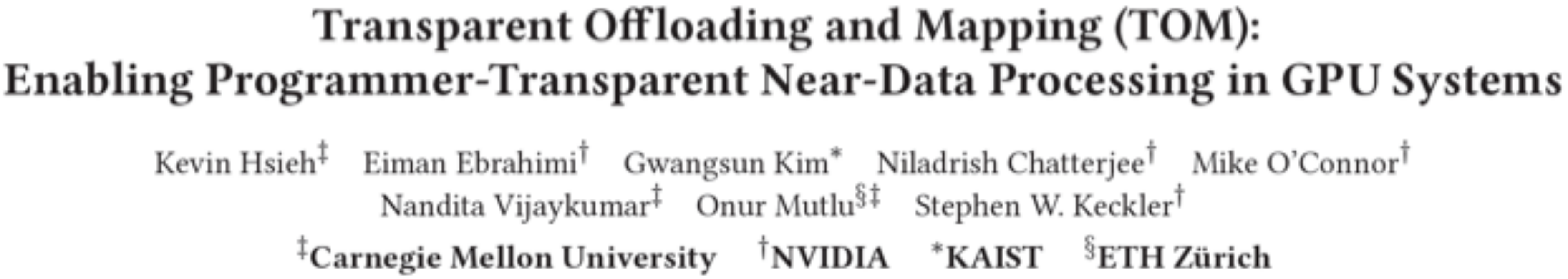
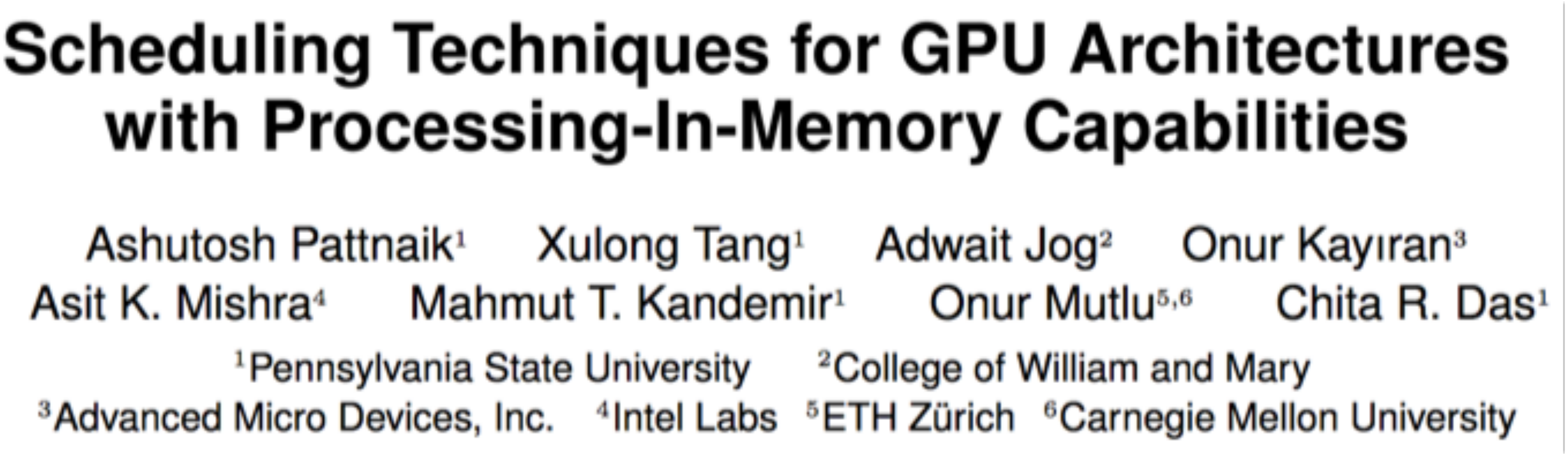


Transparent Offloading and Mapping (TOM):
Enabling Programmer-Transparent Near-Data Processing in GPU Systems

Kevin Hsieh[‡] Eiman Ebrahimi[†] Gwangsun Kim[*] Niladrish Chatterjee[†] Mike O'Connor[†]
Nandita Vijaykumar[‡] Onur Mutlu[§‡] Stephen W. Keckler[†]
[‡]Carnegie Mellon University [†]NVIDIA [*]KAIST [§]ETH Zürich

How to Schedule Code?

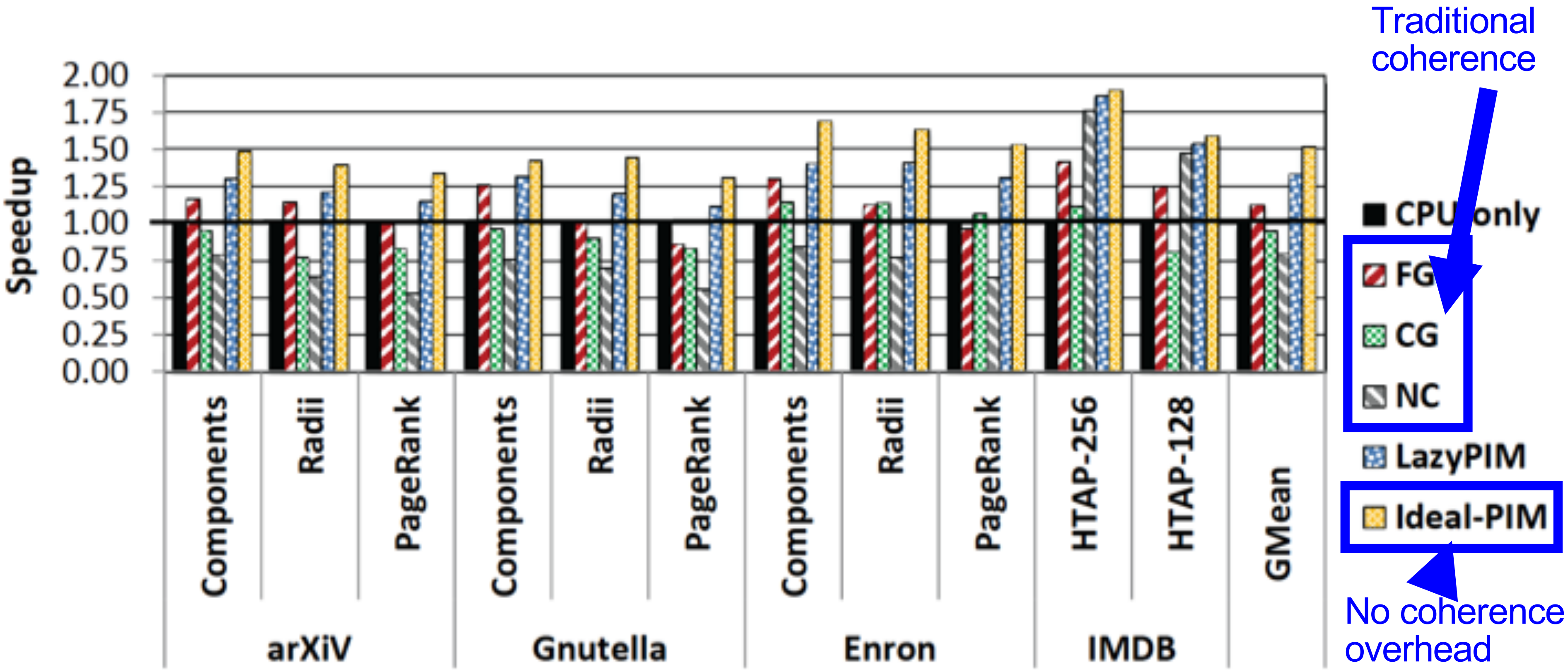
- Ashutosh Pattnaik, Xulong Tang, Adwait Jog, Onur Kayiran, Asit K. Mishra, Mahmut T. Kandemir, Onur Mutlu, and Chita R. Das, **"Scheduling Techniques for GPU Architectures with Processing-In-Memory Capabilities"** *Proceedings of the 25th International Conference on Parallel Architectures and Compilation Techniques (**PACT**)*, Haifa, Israel, September 2016.



Scheduling Techniques for GPU Architectures with Processing-In-Memory Capabilities

Ashutosh Pattnaik[1] Xulong Tang[1] Adwait Jog[2] Onur Kayıran[3]
Asit K. Mishra[4] Mahmut T. Kandemir[1] Onur Mutlu[5,6] Chita R. Das[1]
[1]Pennsylvania State University [2]College of William and Mary
[3]Advanced Micro Devices, Inc. [4]Intel Labs [5]ETH Zürich [6]Carnegie Mellon University

Challenge: Coherence for Hybrid CPU-PIM Apps



Traditional coherence

No coherence overhead

How to Maintain Coherence?

- Amirali Boroumand, Saugata Ghose, Minesh Patel, Hasan Hassan, Brandon Lucia, Kevin Hsieh, Krishna T. Malladi, Hongzhong Zheng, and Onur Mutlu, **"LazyPIM: An Efficient Cache Coherence Mechanism for Processing-in-Memory"** *IEEE Computer Architecture Letters* (***CAL***), June 2016.

LazyPIM: An Efficient Cache Coherence Mechanism for Processing-in-Memory

Amirali Boroumand[†], Saugata Ghose[†], Minesh Patel[†], Hasan Hassan[†§], Brandon Lucia[†],
Kevin Hsieh[†], Krishna T. Malladi[*], Hongzhong Zheng[*], and Onur Mutlu[‡†]

[†]*Carnegie Mellon University* [*]*Samsung Semiconductor, Inc.* [§]*TOBB ETÜ* [‡]*ETH Zürich*

How to Support Virtual Memory?

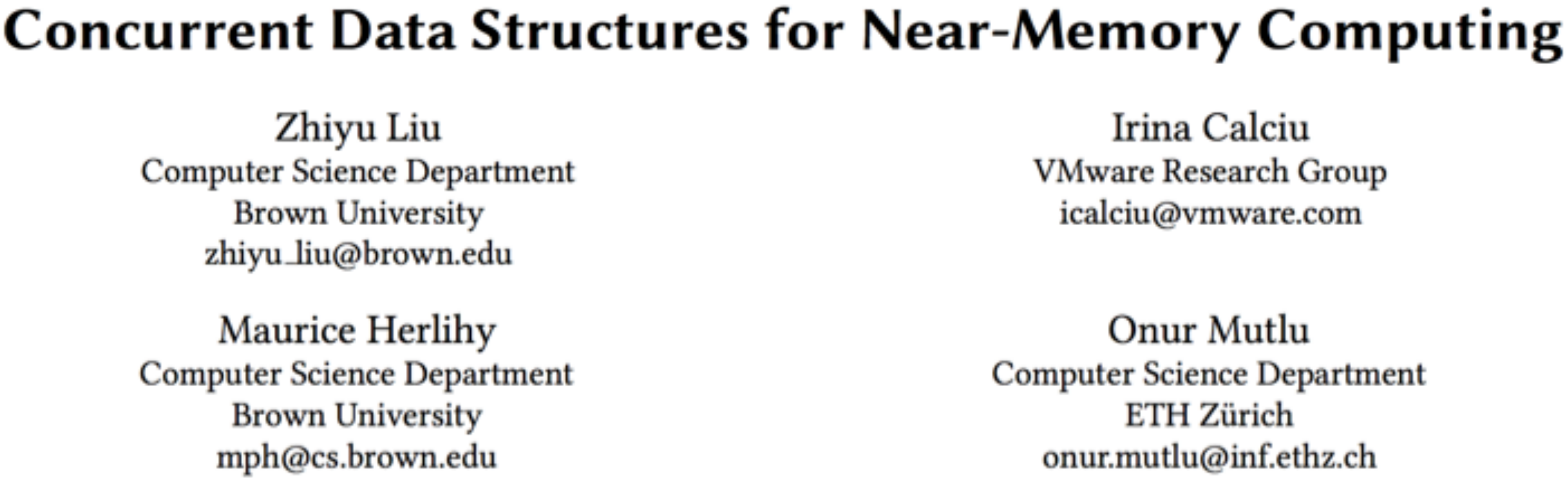
- Kevin Hsieh, Samira Khan, Nandita Vijaykumar, Kevin K. Chang, Amirali Boroumand, Saugata Ghose, and Onur Mutlu,
  "Accelerating Pointer Chasing in 3D-Stacked Memory: Challenges, Mechanisms, Evaluation"
  Proceedings of the 34th IEEE International Conference on Computer Design (***ICCD***), Phoenix, AZ, USA, October 2016.

Accelerating Pointer Chasing in 3D-Stacked Memory: Challenges, Mechanisms, Evaluation

Kevin Hsieh[†] Samira Khan[‡] Nandita Vijaykumar[†]
Kevin K. Chang[†] Amirali Boroumand[†] Saugata Ghose[†] Onur Mutlu[§†]
[†]*Carnegie Mellon University* [‡]*University of Virginia* [§]*ETH Zürich*

How to Design Data Structures for PIM?

- Zhiyu Liu, Irina Calciu, Maurice Herlihy, and Onur Mutlu, **"Concurrent Data Structures for Near-Memory Computing"** *Proceedings of the 29th ACM Symposium on Parallelism in Algorithms and Architectures (**SPAA**)*, Washington, DC, USA, July 2017. [Slides (pptx) (pdf)]



Concurrent Data Structures for Near-Memory Computing

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Maurice Herlihy
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Brown University
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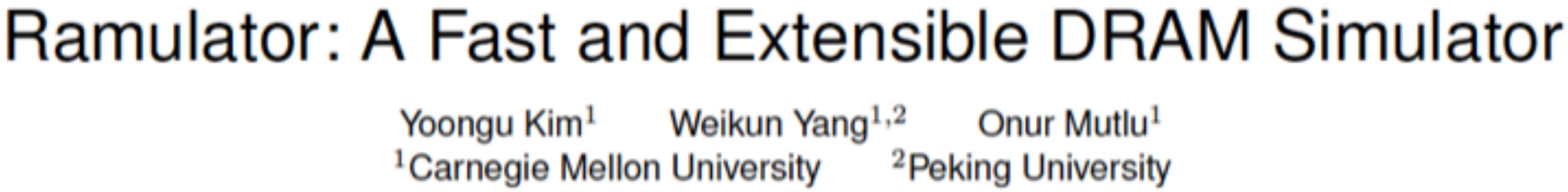
Onur Mutlu
Computer Science Department
ETH Zürich
onur.mutlu@inf.ethz.ch

Simulation Infrastructures for PIM

- Ramulator extended for PIM
  - Flexible and extensible DRAM simulator
  - Can model many different memory standards and proposals
  - Kim+, "**Ramulator: A Flexible and Extensible DRAM Simulator**", IEEE CAL 2015.
  - https://github.com/CMU-SAFARI/ramulator



Ramulator: A Fast and Extensible DRAM Simulator

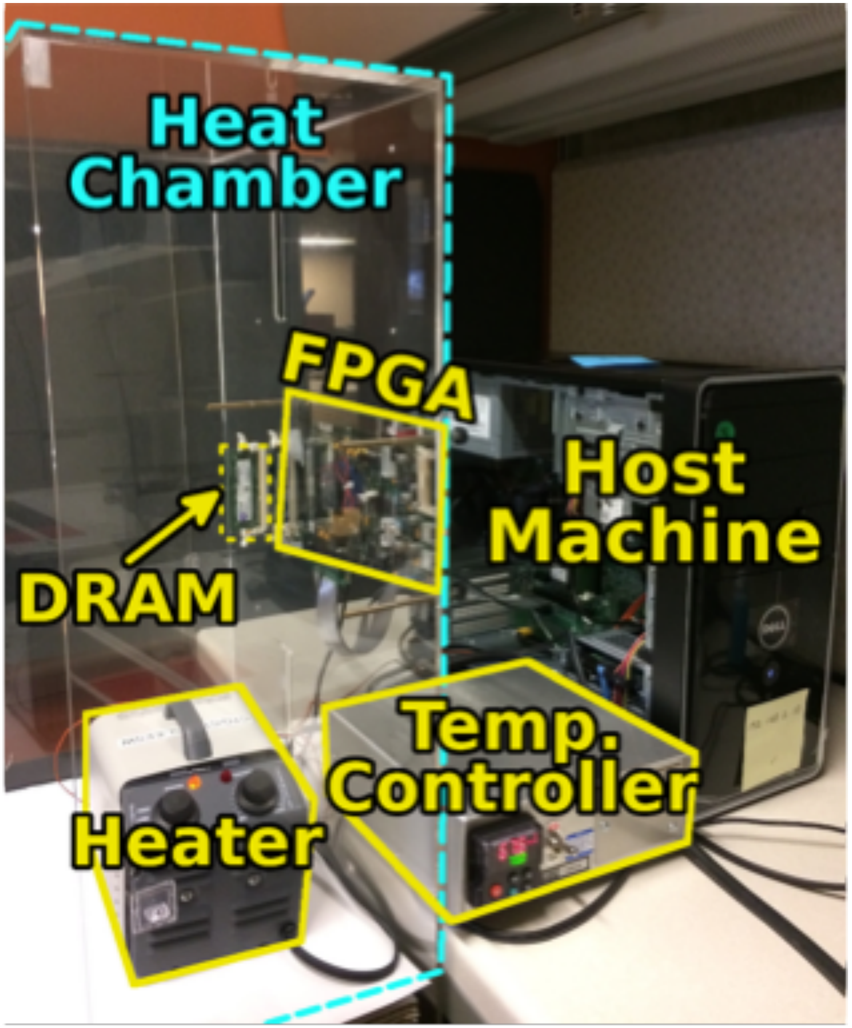
Yoongu Kim[1] Weikun Yang[1,2] Onur Mutlu[1]
[1]Carnegie Mellon University [2]Peking University

An FPGA-based Test-bed for PIM?

- Hasan Hassan et al., **SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies** HPCA 2017.

- **Flexible**
- **Easy to Use (C++ API)**
- **Open-source**

github.com/CMU-SAFARI/SoftMC



New Applications and Use Cases for PIM

- Jeremie S. Kim, Damla Senol Cali, Hongyi Xin, Donghyuk Lee, Saugata Ghose, Mohammed Alser, Hasan Hassan, Oguz Ergin, Can Alkan, and Onur Mutlu,
  "GRIM-Filter: Fast Seed Location Filtering in DNA Read Mapping Using Processing-in-Memory Technologies"
  BMC Genomics, 2018.
  Proceedings of the 16th Asia Pacific Bioinformatics Conference (***APBC***),
  Yokohama, Japan, January 2018.
  arxiv.org Version (pdf)

GRIM-Filter: Fast seed location filtering in DNA read mapping using processing-in-memory technologies

Jeremie S. Kim[1,6*], Damla Senol Cali[1], Hongyi Xin[2], Donghyuk Lee[3], Saugata Ghose[1],
Mohammed Alser[4], Hasan Hassan[6], Oguz Ergin[5], Can Alkan[4*] and Onur Mutlu[6,1*]

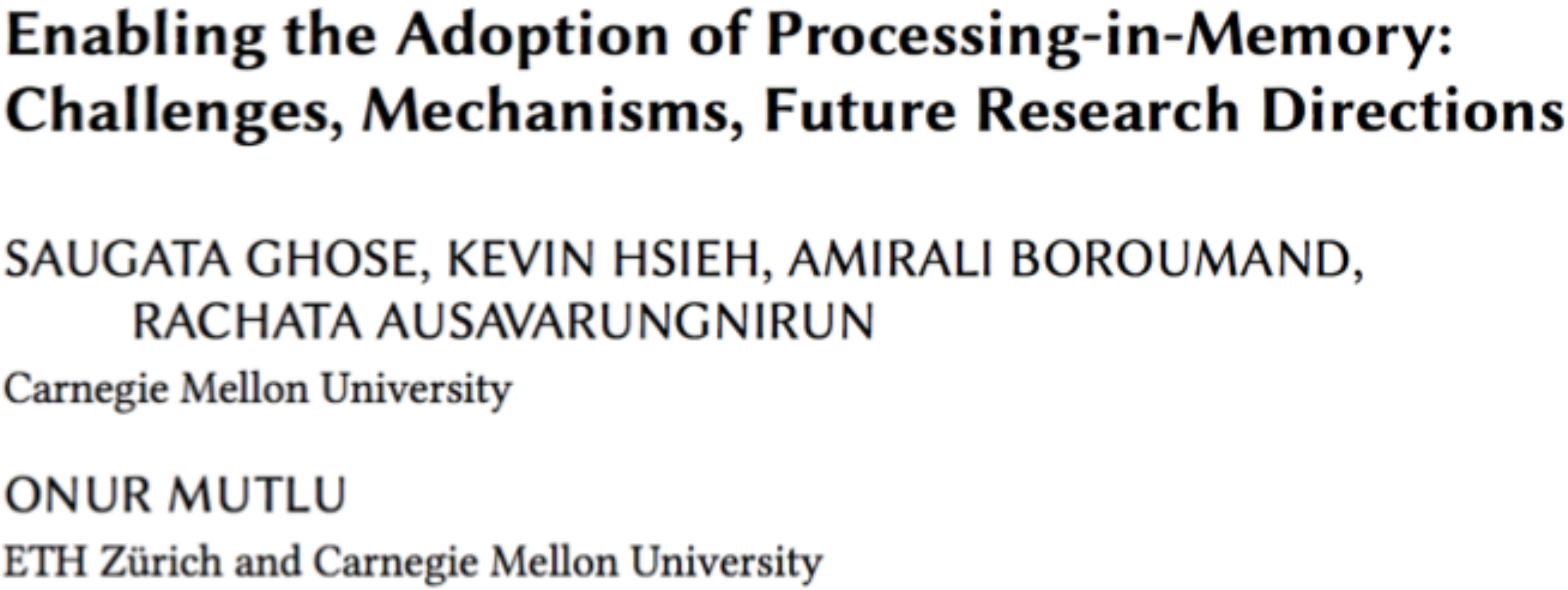
From The Sixteenth Asia Pacific Bioinformatics Conference 2018
Yokohama, Japan. 15-17 January 2018

Google Workloads for Consumer Devices: Mitigating Data Movement Bottlenecks

Amirali Boroumand

Saugata Ghose, Youngsok Kim, Rachata Ausavarungnirun,
Eric Shiu, Rahul Thakur, Daehyun Kim, Aki Kuusela,
Allan Knies, Parthasarathy Ranganathan, Onur Mutlu

Open Problems: PIM Adoption



Enabling the Adoption of Processing-in-Memory: Challenges, Mechanisms, Future Research Directions

SAUGATA GHOSE, KEVIN HSIEH, AMIRALI BOROUMAND,
RACHATA AUSAVARUNGNIRUN
Carnegie Mellon University

ONUR MUTLU
ETH Zürich and Carnegie Mellon University

https://arxiv.org/pdf/1802.00320.pdf

Agenda

- Major Trends Affecting Main Memory
- The Need for Intelligent Memory Controllers
  - Bottom Up: Push from Circuits and Devices
  - Top Down: Pull from Systems and Applications
- Processing in Memory: Two Directions
  - Minimally Changing Memory Chips
  - Exploiting 3D-Stacked Memory
- How to Enable Adoption of Processing in Memory
- Conclusion

Four Key Directions

- Fundamentally Secure/Reliable/Safe Architectures

- Fundamentally Energy-Efficient Architectures
  - Memory-centric (Data-centric) Architectures

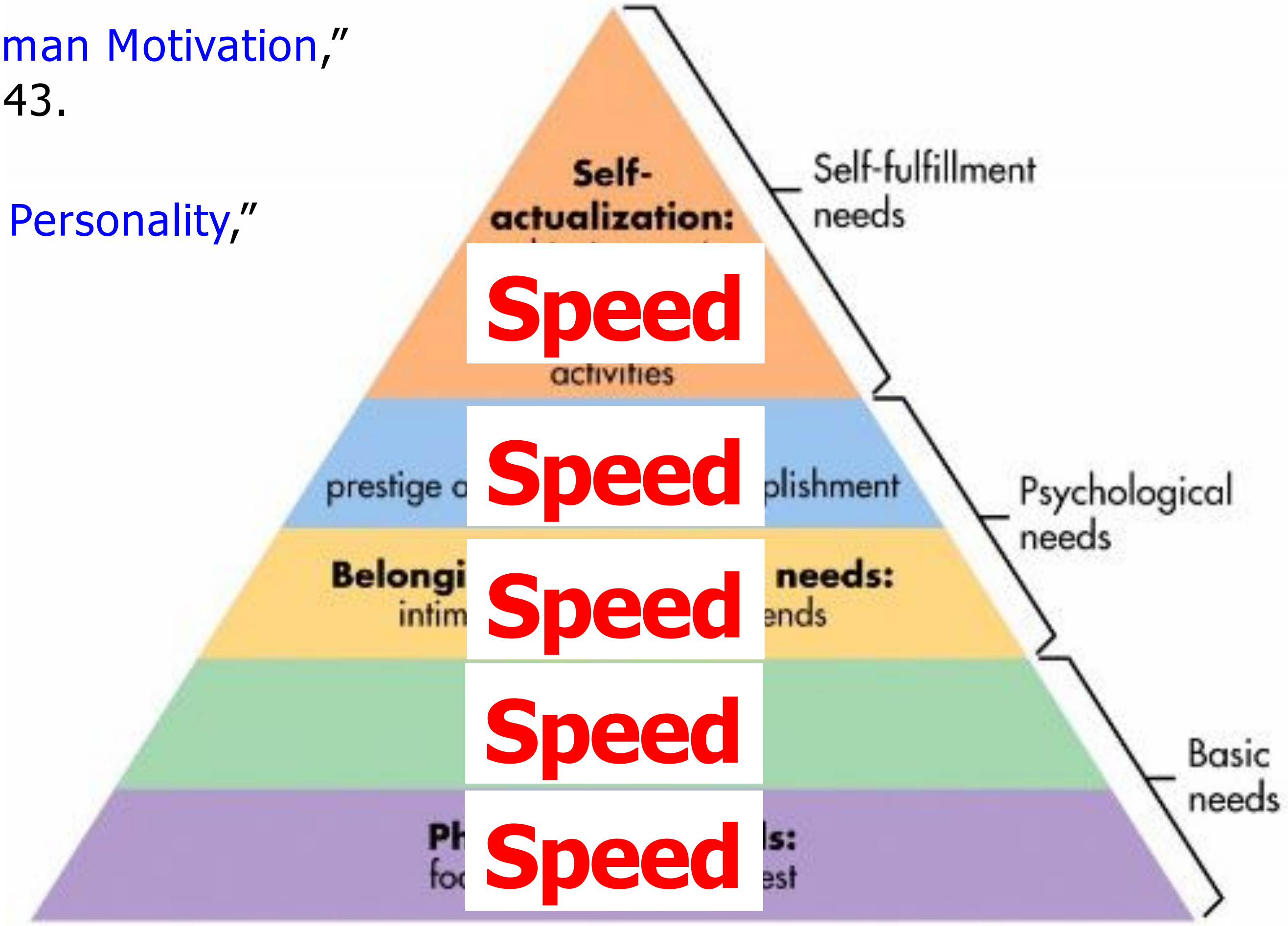
- Fundamentally Low-Latency Architectures

- Architectures for Genomics, Medicine, Health

Maslow’s Hierarchy of Needs, A Third Time

Maslow, “A Theory of Human Motivation,”
Psychological Review, 1943.

Maslow, “Motivation and Personality,”
Book, 1954-1970.



Source: https://www.simplypsychology.org/maslow.html

Challenge and Opportunity for Future

Fundamentally

Energy-Efficient

(Data-Centric)

Computing Architectures

Challenge and Opportunity for Future

Fundamentally

Low-Latency

(Data-Centric)

Computing Architectures

Challenge and Opportunity for Future

Computing Architectures

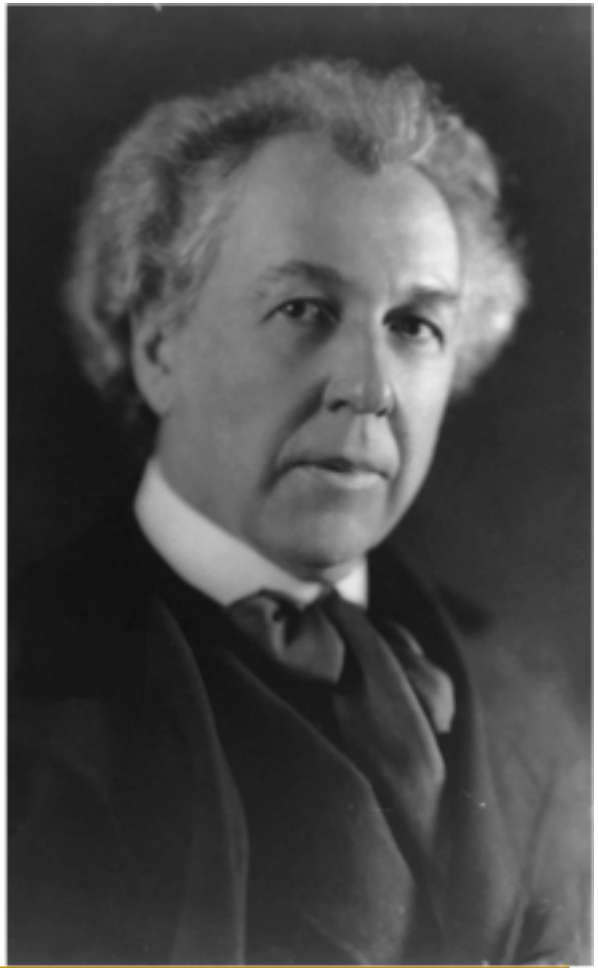
with

Minimal Data Movement

Concluding Remarks

A Quote from A Famous Architect

- “architecture […] based upon principle, and not upon precedent”



Precedent-Based Design?

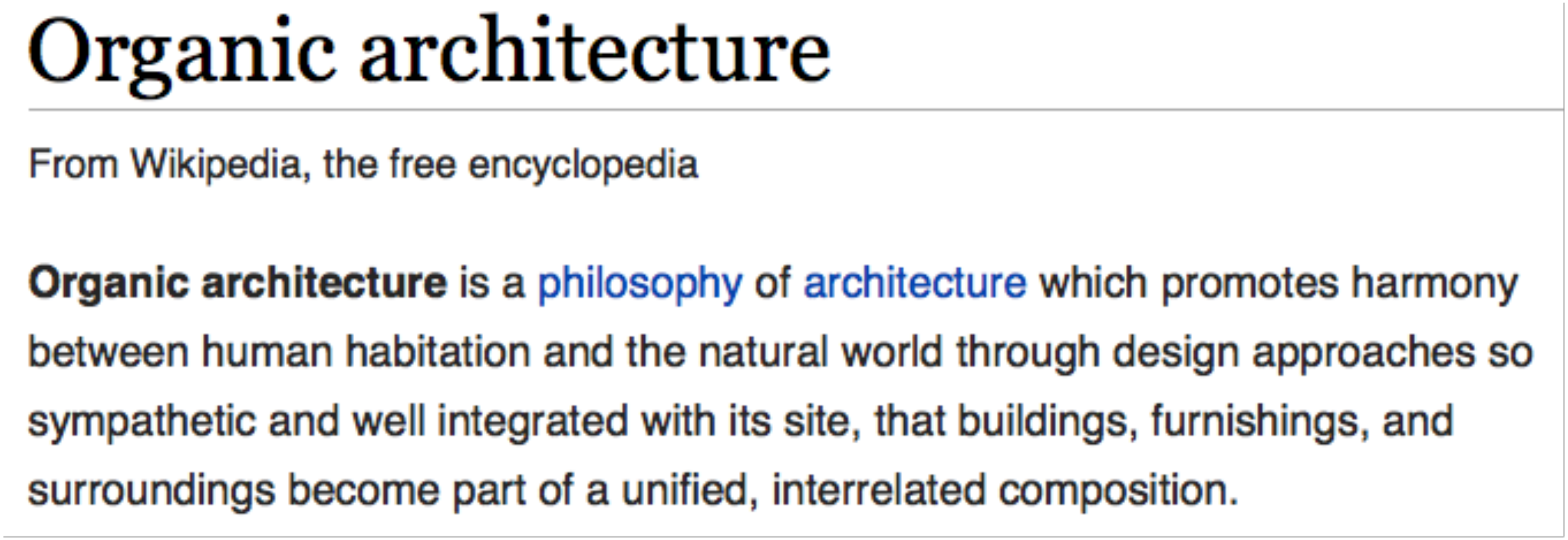
- “architecture […] based upon principle, and not upon precedent”

Principled Design

- "architecture […] based upon principle, and not upon precedent"

www.GreatBuildings.com

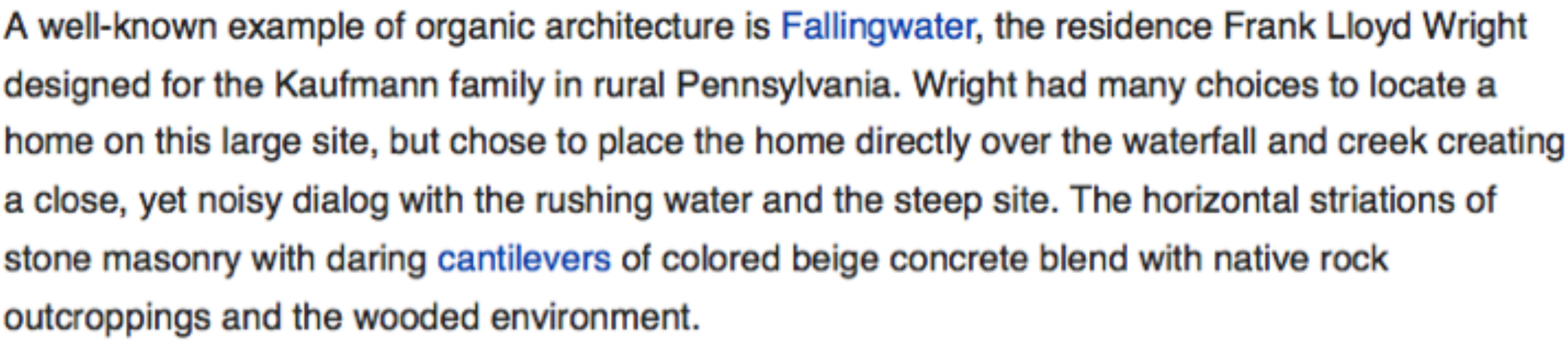
The Overarching Principle



Organic architecture

From Wikipedia, the free encyclopedia

Organic architecture is a philosophy of architecture which promotes harmony between human habitation and the natural world through design approaches so sympathetic and well integrated with its site, that buildings, furnishings, and surroundings become part of a unified, interrelated composition.



A well-known example of organic architecture is Fallingwater, the residence Frank Lloyd Wright designed for the Kaufmann family in rural Pennsylvania. Wright had many choices to locate a home on this large site, but chose to place the home directly over the waterfall and creek creating a close, yet noisy dialog with the rushing water and the steep site. The horizontal striations of stone masonry with daring cantilevers of colored beige concrete blend with native rock outcroppings and the wooded environment.

Another Example: Precedent-Based Design

Source: http://cookiemagik.deviantart.com/art/Train-station-207266944

Principled Design

Source: By Toni_V, CC BY-SA 2.0, https://commons.wikimedia.org/w/index.php?curid=4087256

Another Principled Design

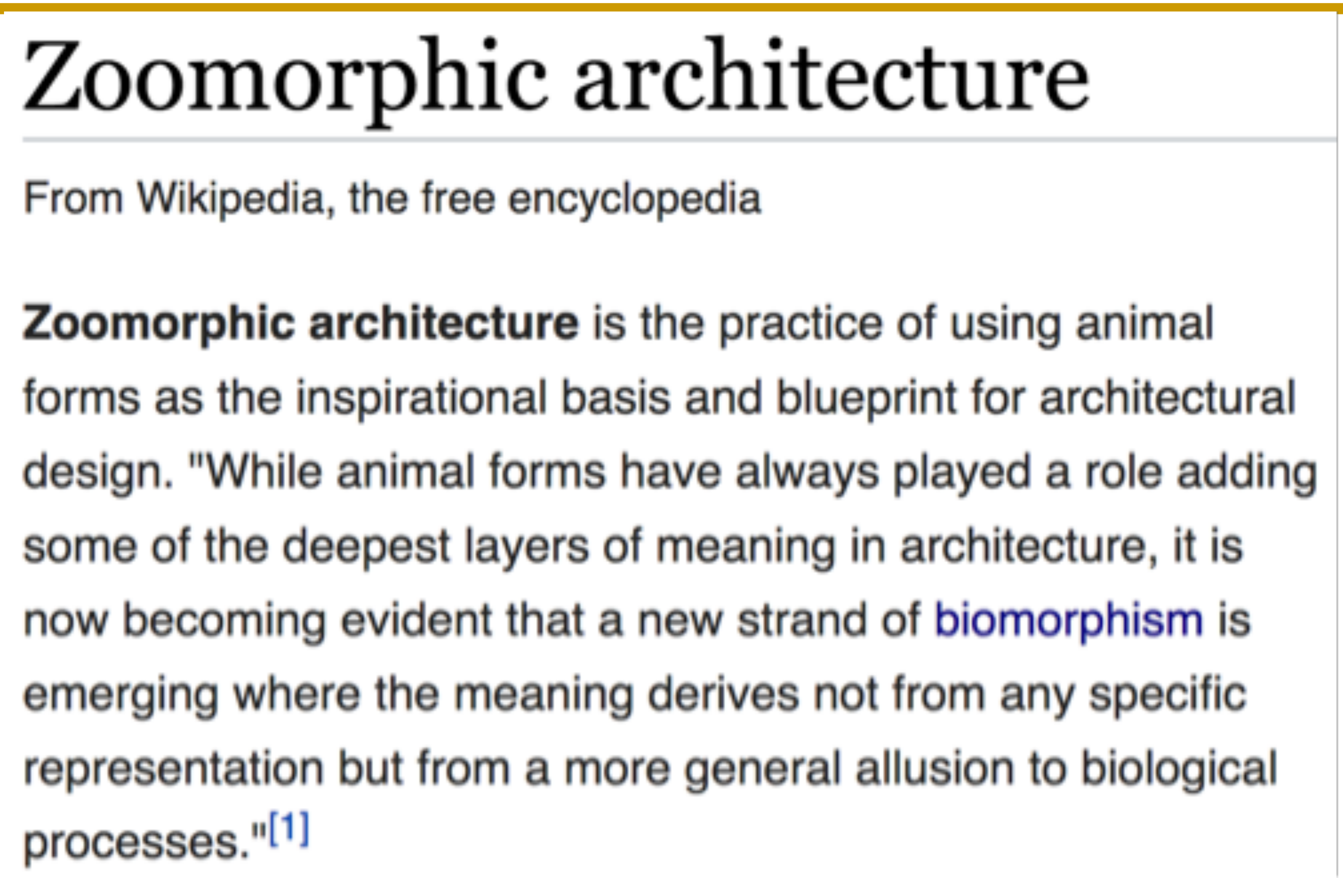
Source: By Martín Gómez Tagle - Lisbon, Portugal, CC BY-SA 3.0, https://commons.wikimedia.org/w/index.php?curid=13764903

Source: http://www.arcspace.com/exhibitions/unsorted/santiago-calatrava/

Principle Applied to Another Structure

Source: By 準建築人手札網站 Forgemind ArchiMedia - Flickr: IMG_2489.JPG, CC BY 2.0,
https://commons.wikimedia.org/w/index.php?curid=51495556, https://en.wikipedia.org/wiki/Santiago_Calatrava
ntiago-calatrava-oculus-world-trade-center-transportation-hub-new-york-photographs-hufton-crow/

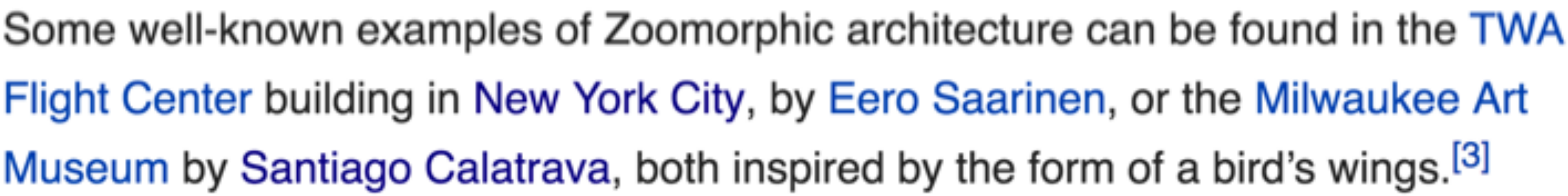
The Overarching Principle



Zoomorphic architecture

From Wikipedia, the free encyclopedia

Zoomorphic architecture is the practice of using animal forms as the inspirational basis and blueprint for architectural design. "While animal forms have always played a role adding some of the deepest layers of meaning in architecture, it is now becoming evident that a new strand of biomorphism is emerging where the meaning derives not from any specific representation but from a more general allusion to biological processes."[1]



Some well-known examples of Zoomorphic architecture can be found in the TWA Flight Center building in New York City, by Eero Saarinen, or the Milwaukee Art Museum by Santiago Calatrava, both inspired by the form of a bird's wings.[3]

Overarching Principle for Computing?

Source: http://spectrum.ieee.org/image/MjYzMzAyMg.jpeg

Concluding Remarks

- It is time to design principled system architectures to solve the memory problem

- Design complete systems to be balanced, high-performance, and energy-efficient, i.e., data-centric (or memory-centric)

- Enable computation capability inside and close to memory

- This can
    - Lead to **orders-of-magnitude** improvements
    - **Enable new applications & computing platforms**
    - **Enable better understanding of nature**
    - …

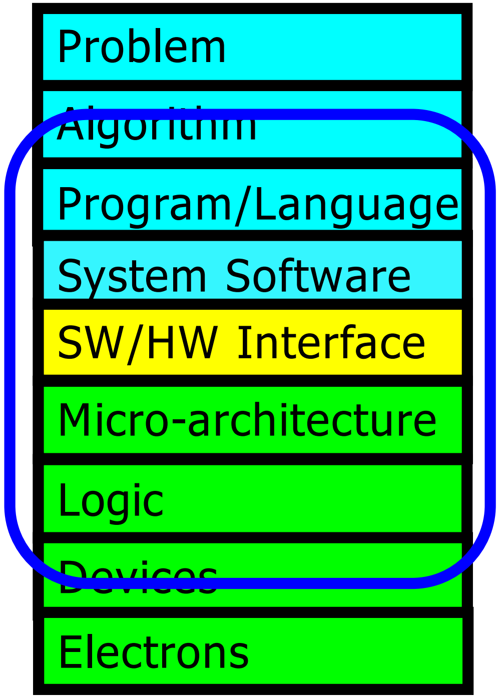
The Future of Processing in Memory is Bright

- Regardless of challenges
  - in underlying technology and overlying problems/requirements

Can enable:

- Orders of magnitude improvements

- New applications and computing systems



Problem

Algorithm

Program/Language

System Software

SW/HW Interface

Micro-architecture

Logic

Devices

Electrons

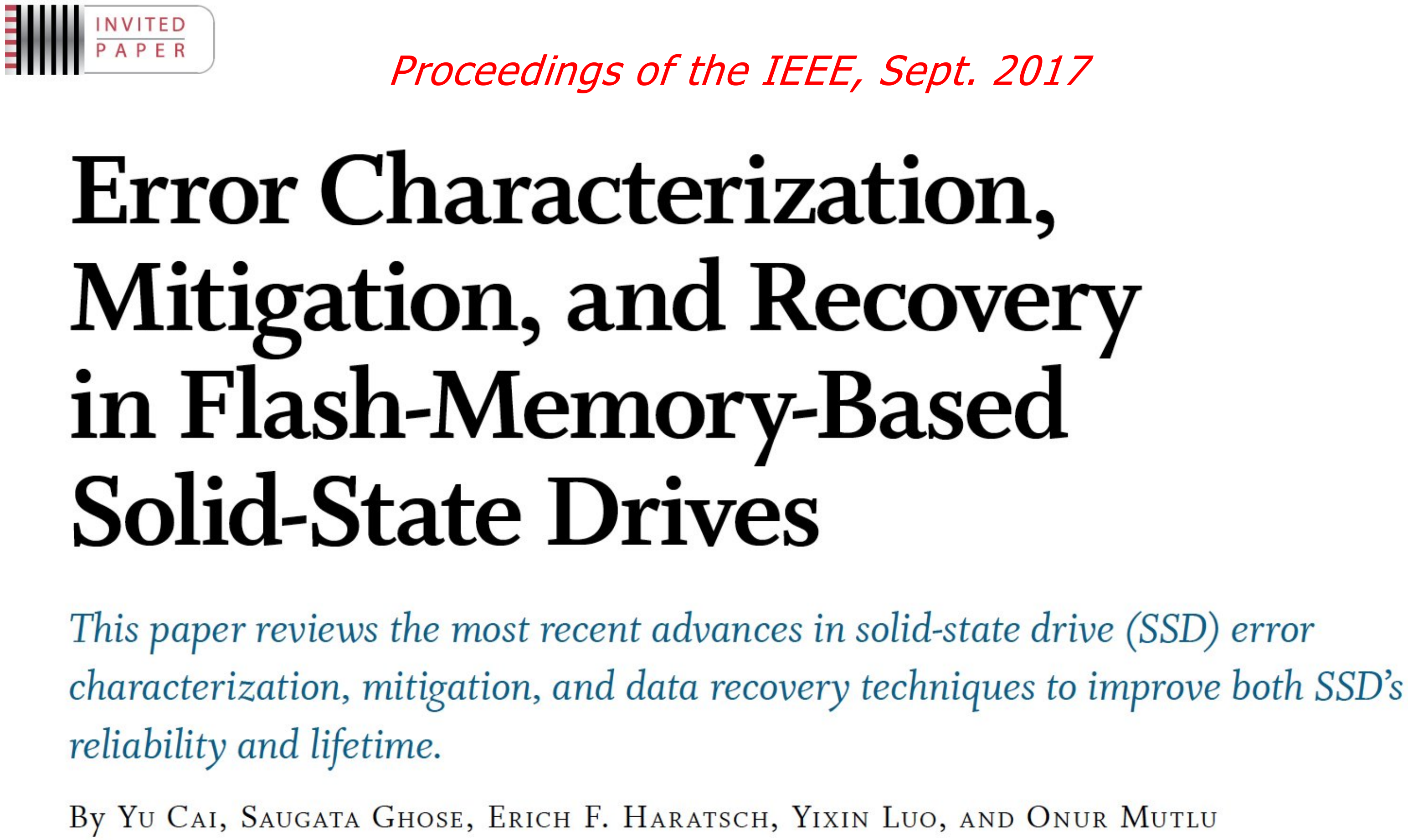
Yet, we have to

- Think across the stack

- Design enabling systems

If In Doubt, See Other Doubtful Technologies

- A very "doubtful" emerging technology
  - for at least two decades



INVITED PAPER

Proceedings of the IEEE, Sept. 2017

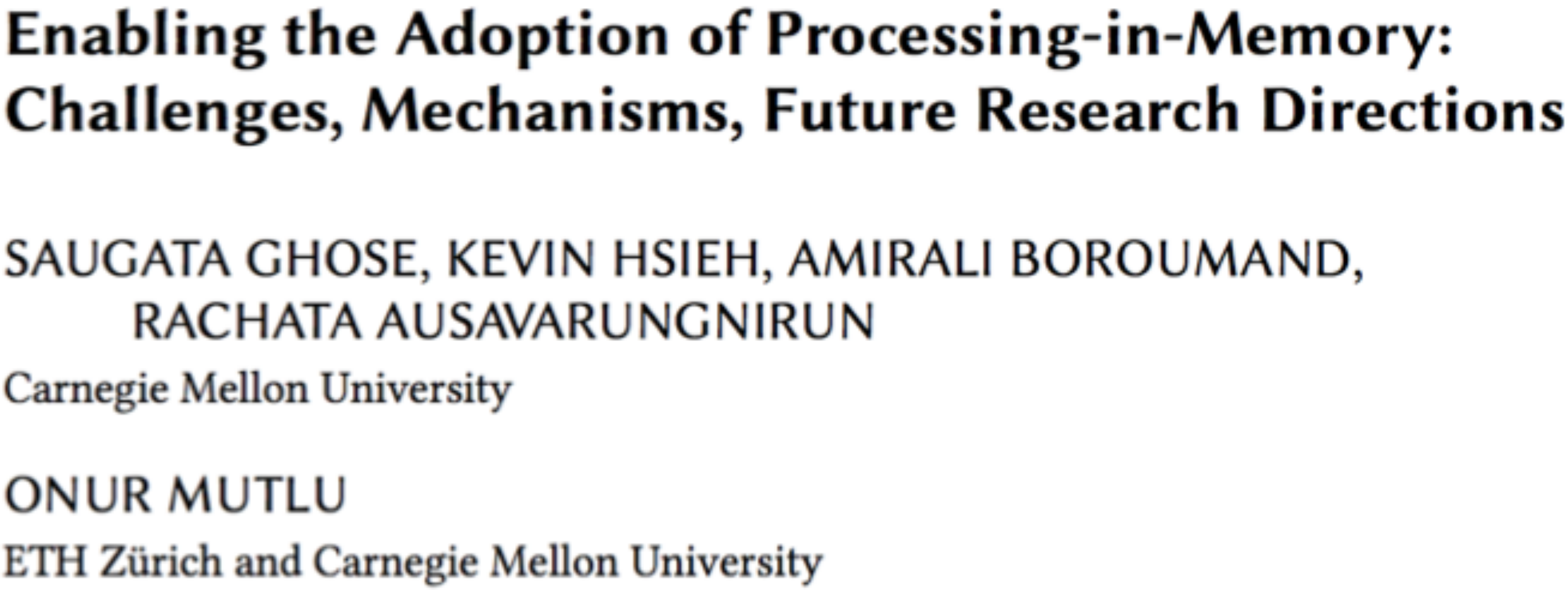
Error Characterization, Mitigation, and Recovery in Flash-Memory-Based Solid-State Drives

This paper reviews the most recent advances in solid-state drive (SSD) error characterization, mitigation, and data recovery techniques to improve both SSD's reliability and lifetime.

By Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu

https://arxiv.org/pdf/1706.08642

For Some Open Problems, See



Enabling the Adoption of Processing-in-Memory: Challenges, Mechanisms, Future Research Directions

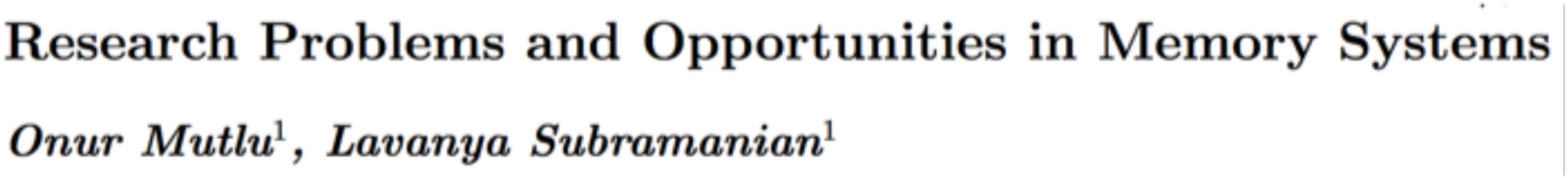
SAUGATA GHOSE, KEVIN HSIEH, AMIRALI BOROUMAND,
RACHATA AUSAVARUNGNIRUN
Carnegie Mellon University

ONUR MUTLU
ETH Zürich and Carnegie Mellon University

https://arxiv.org/pdf/1802.00320.pdf

For More Open Problems, See (I)

- Onur Mutlu and Lavanya Subramanian, **"Research Problems and Opportunities in Memory Systems"** *Invited Article in Supercomputing Frontiers and Innovations (**SUPERFRI**)*, 2014/2015.



Research Problems and Opportunities in Memory Systems

Onur Mutlu[1], *Lavanya Subramanian*[1]

For More Open Problems, See (II)

- Onur Mutlu,
  "The RowHammer Problem and Other Issues We May Face as Memory Becomes Denser"
  Invited Paper in Proceedings of the Design, Automation, and Test in Europe Conference (***DATE***), Lausanne, Switzerland, March 2017.
  [Slides (pptx) (pdf)]

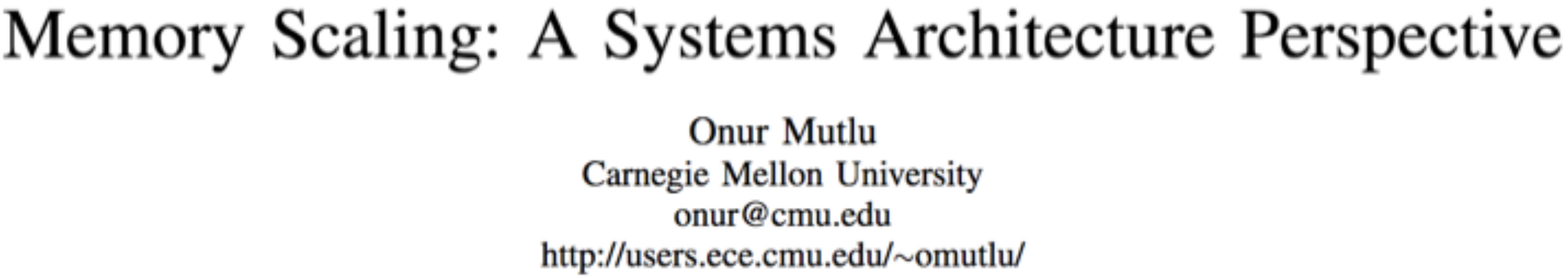
The RowHammer Problem and Other Issues We May Face as Memory Becomes Denser

Onur Mutlu
ETH Zürich
onur.mutlu@inf.ethz.ch
https://people.inf.ethz.ch/omutlu

https://people.inf.ethz.ch/omutlu/pub/rowhammer-and-other-memory-issues_date17.pdf

For More Open Problems, See (III)

- Onur Mutlu,
  "Memory Scaling: A Systems Architecture Perspective"
  *Technical talk at MemCon 2013 (**MEMCON**)*, Santa Clara, CA, August 2013. [Slides (pptx) (pdf)]
  [Video] [Coverage on StorageSearch]



Memory Scaling: A Systems Architecture Perspective

Onur Mutlu
Carnegie Mellon University
onur@cmu.edu
http://users.ece.cmu.edu/~omutlu/

For More Open Problems, See (IV)

- Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu,
  "Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives"
  to appear in Proceedings of the IEEE, 2017.

Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives

Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu

Related Videos and Course Materials (I)

- Undergraduate Computer Architecture Course Lecture Videos (2015, 2014, 2013)
- Undergraduate Computer Architecture Course Materials (2015, 2014, 2013)

- Graduate Computer Architecture Course Lecture Videos (2017, 2015, 2013)
- Graduate Computer Architecture Course Materials (2017, 2015, 2013)

- Parallel Computer Architecture Course Materials (Lecture Videos)

Related Videos and Course Materials (II)

- Freshman Digital Circuits and Computer Architecture Course Lecture Videos (2018, 2017)
- Freshman Digital Circuits and Computer Architecture Course Materials (2018)

- Memory Systems Short Course Materials

  (Lecture Video on Main Memory and DRAM Basics)

Processing Data Where It Makes Sense in Modern Computing Systems: Enabling In-Memory Computation

Onur Mutlu
omutlu@gmail.com
https://people.inf.ethz.ch/omutlu

24 June 2018

Design Automation Summer School @ DAC 2018

Some Open Source Tools

- Rowhammer
  - https://github.com/CMU-SAFARI/rowhammer
- Ramulator – Fast and Extensible DRAM Simulator
  - https://github.com/CMU-SAFARI/ramulator
- MemSim
  - https://github.com/CMU-SAFARI/memsim
- NOCulator
  - https://github.com/CMU-SAFARI/NOCulator
- DRAM Error Model
  - http://www.ece.cmu.edu/~safari/tools/memerr/index.html

- Other open-source software from my group
  - https://github.com/CMU-SAFARI/
  - http://www.ece.cmu.edu/~safari/tools.html

Referenced Papers

- All are available at
  http://users.ece.cmu.edu/~omutlu/projects.htm
  http://scholar.google.com/citations?user=7XyGUGkAAAAJ&hl=en

Acknowledgments

- My current and past students and postdocs
  - Rachata Ausavarungnirun, Abhishek Bhowmick, Amirali Boroumand, Rui Cai, Yu Cai, Kevin Chang, Saugata Ghose, Kevin Hsieh, Tyler Huberty, Ben Jaiyen, Samira Khan, Jeremie Kim, Yoongu Kim, Yang Li, Jamie Liu, Lavanya Subramanian, Donghyuk Lee, Yixin Luo, Justin Meza, Gennady Pekhimenko, Vivek Seshadri, Lavanya Subramanian, Nandita Vijaykumar, HanBin Yoon, Jishen Zhao, …
- My collaborators
  - Can Alkan, Chita Das, Phil Gibbons, Sriram Govindan, Norm Jouppi, Mahmut Kandemir, Mike Kozuch, Konrad Lai, Ken Mai, Todd Mowry, Yale Patt, Moinuddin Qureshi, Partha Ranganathan, Bikash Sharma, Kushagra Vaid, Chris Wilkerson, …

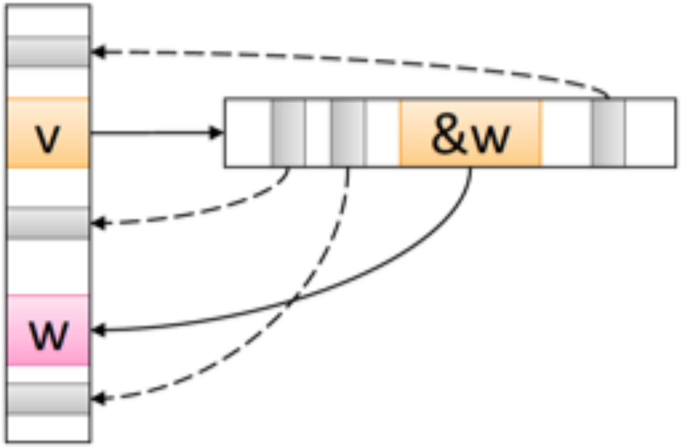
Funding Acknowledgments

- NSF
- GSRC
- SRC
- CyLab
- Alibaba, AMD, Google, Facebook, HP Labs, Huawei, IBM, Intel, Microsoft, Nvidia, Oracle, Qualcomm, Rambus, Samsung, Seagate, VMware

Tesseract: Extra Slides

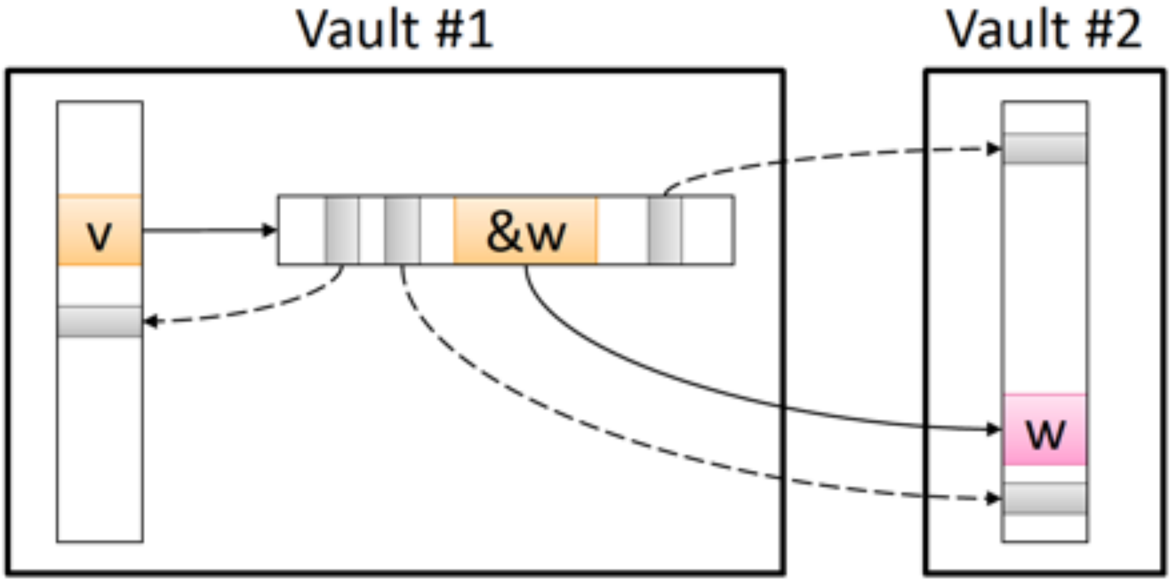
Communications In Tesseract (I)

```
for (v: graph.vertices) {
  for (w: v.successors) {
    w.next_rank += weight * v.rank;
  }
}
```



Communications In Tesseract (II)

```
for (v: graph.vertices) {
  for (w: v.successors) {
    w.next_rank += weight * v.rank;
  }
}
```

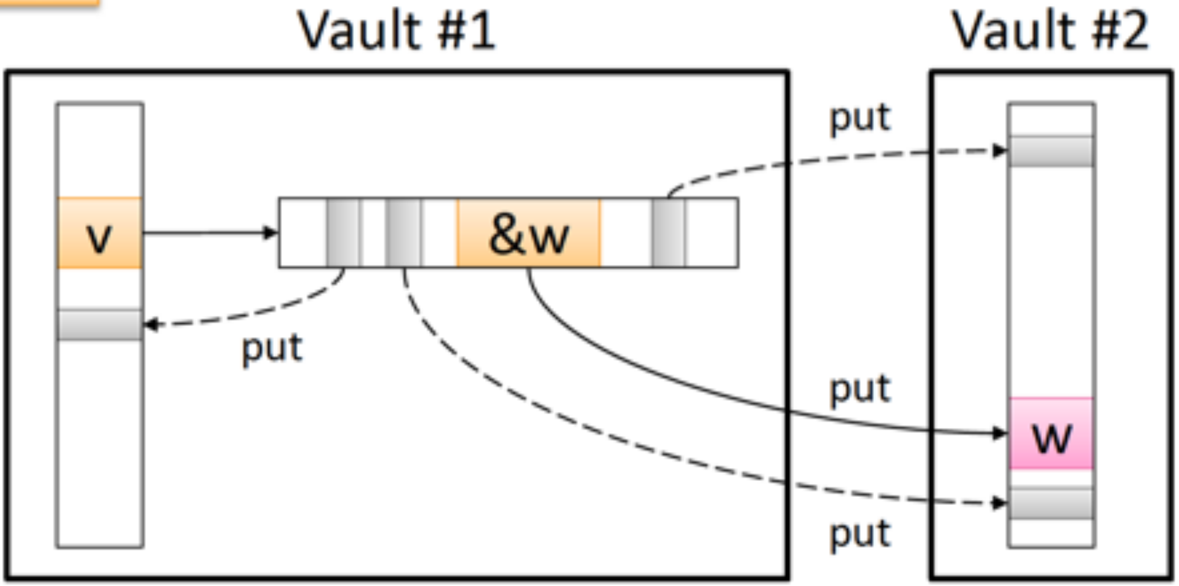


Communications In Tesseract (III)

```
for (v: graph.vertices) {
  for (w: v.successors) {
    put(w.id, function() { w.next_rank += weight * v.rank; });
  }
}
barrier();
```

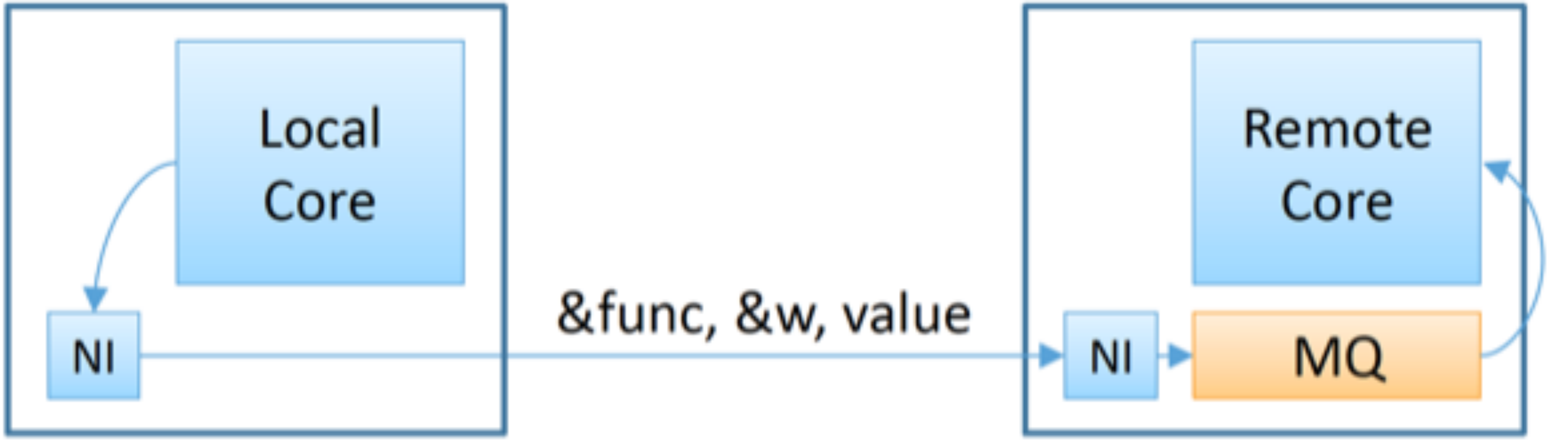
Non-blocking Remote Function Call

Can be **delayed**
until the nearest barrier



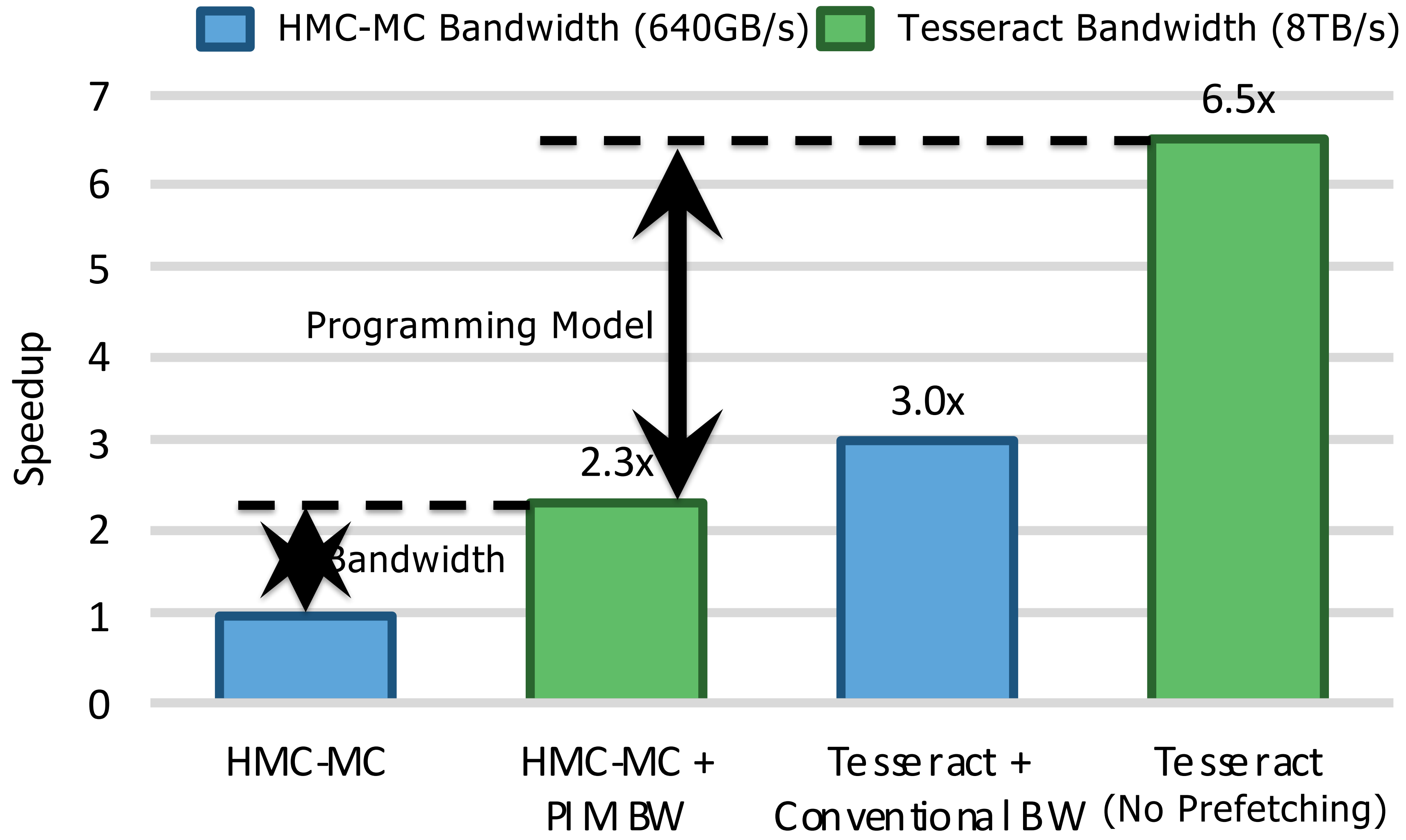
Remote Function Call (Non-Blocking)

1. Send function address & args to the remote core
2. Store the incoming message to the message queue
3. Flush the message queue when it is full or a synchronization barrier is reached



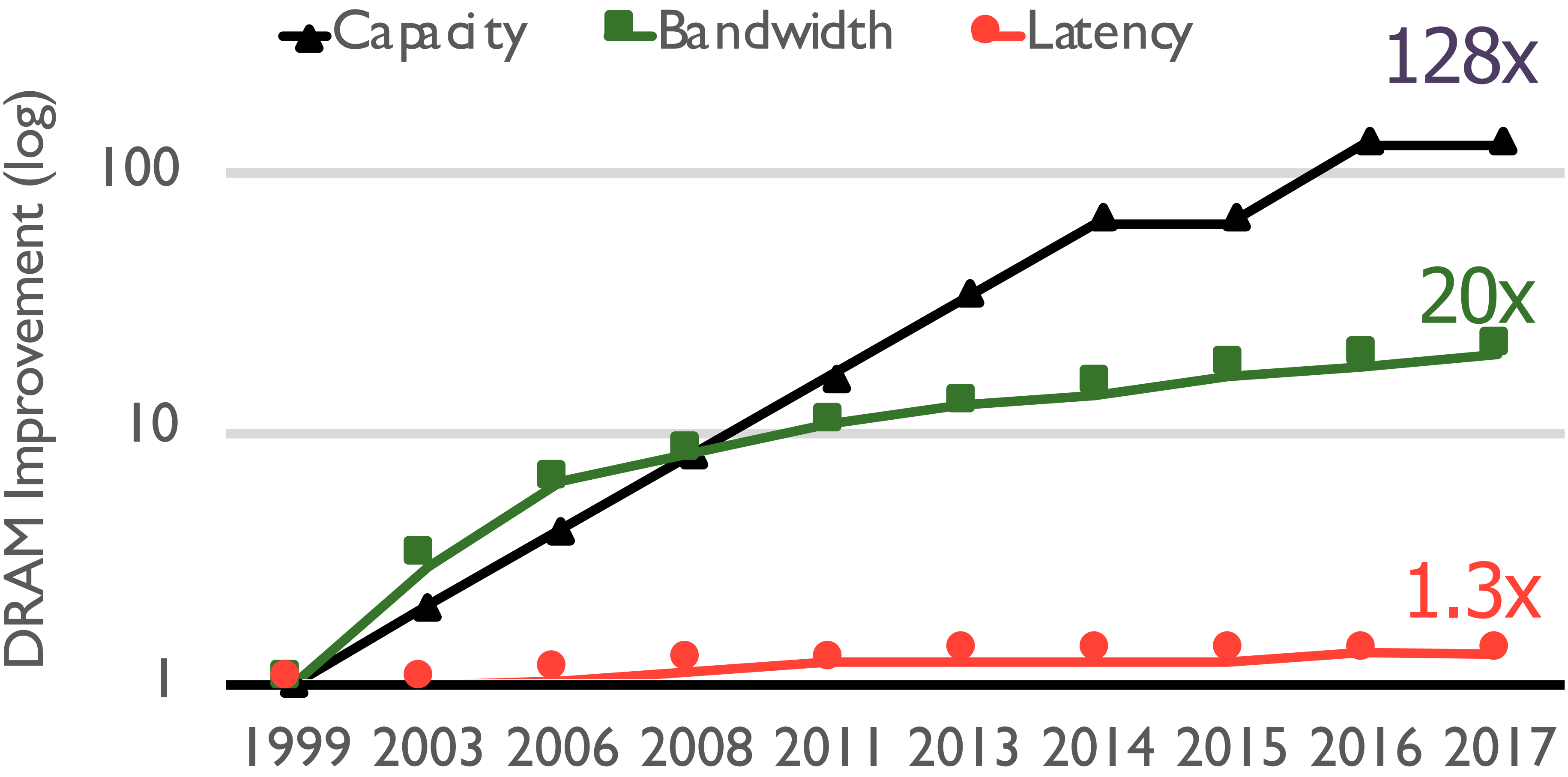
put(w.id, function() { w.next_rank += value; })

Effect of Bandwidth & Programming Model



Reducing Memory Latency

Main Memory Latency Lags Behind



Memory latency remains almost constant

A Closer Look …

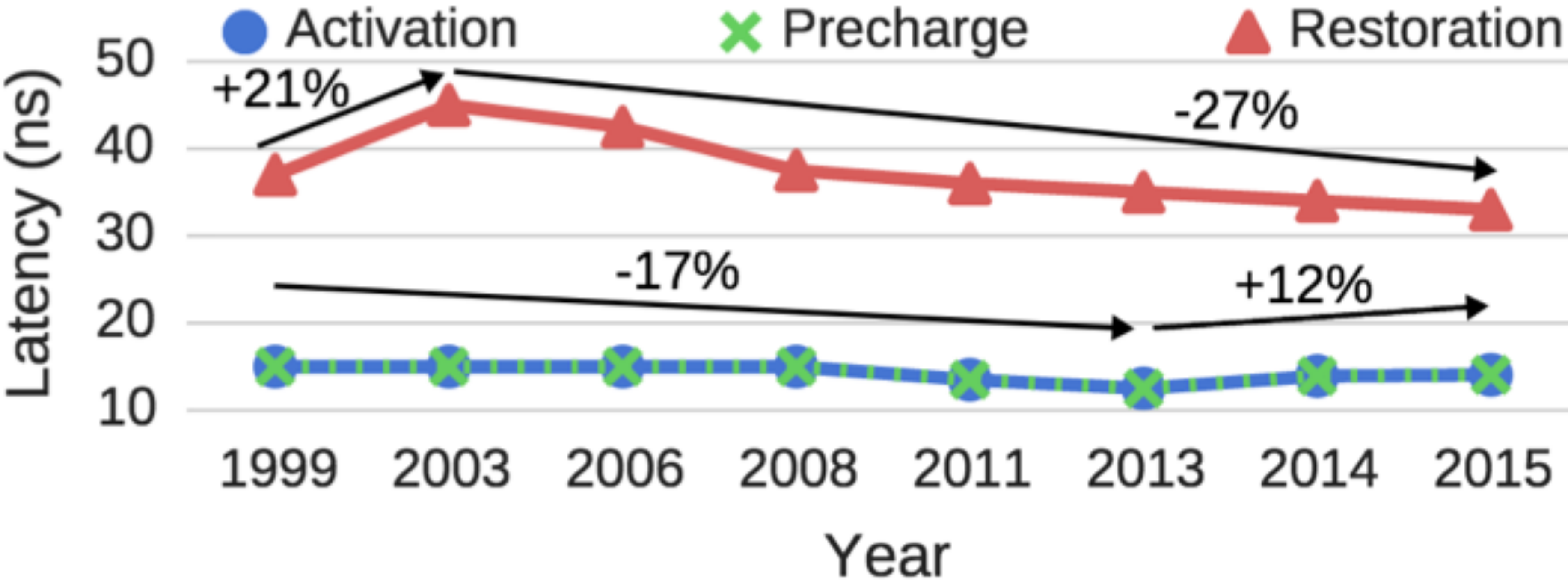
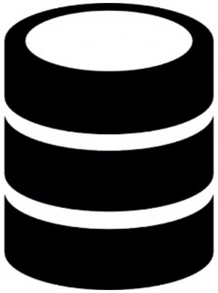


Figure 1: DRAM latency trends over time [20, 21, 23, 51].

Chang+, "**Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization"**," SIGMETRICS 2016.

DRAM Latency Is Critical for Performance



In-memory Databases

[Mao+, EuroSys'12;
Clapp+ (**Intel**), IISWC'15]

Graph/Tree Processing

[Xu+, IISWC'12; Umuroglu+, FPL'15]

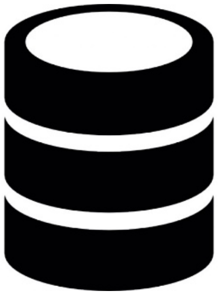
In-Memory Data Analytics

[Clapp+ (**Intel**), IISWC'15;
Awan+, BDCloud'15]

Datacenter Workloads

[Kanev+ (**Google**), ISCA'15]

DRAM Latency Is Critical for Performance



In-memory Databases

Graph/Tree Processing

Long memory latency → performance bottleneck

APACHE Spark™

In-Memory Data Analytics

[Clapp+ (**Intel**), IISWC'15;
Awan+, BDCloud'15]

Datacenter Workloads

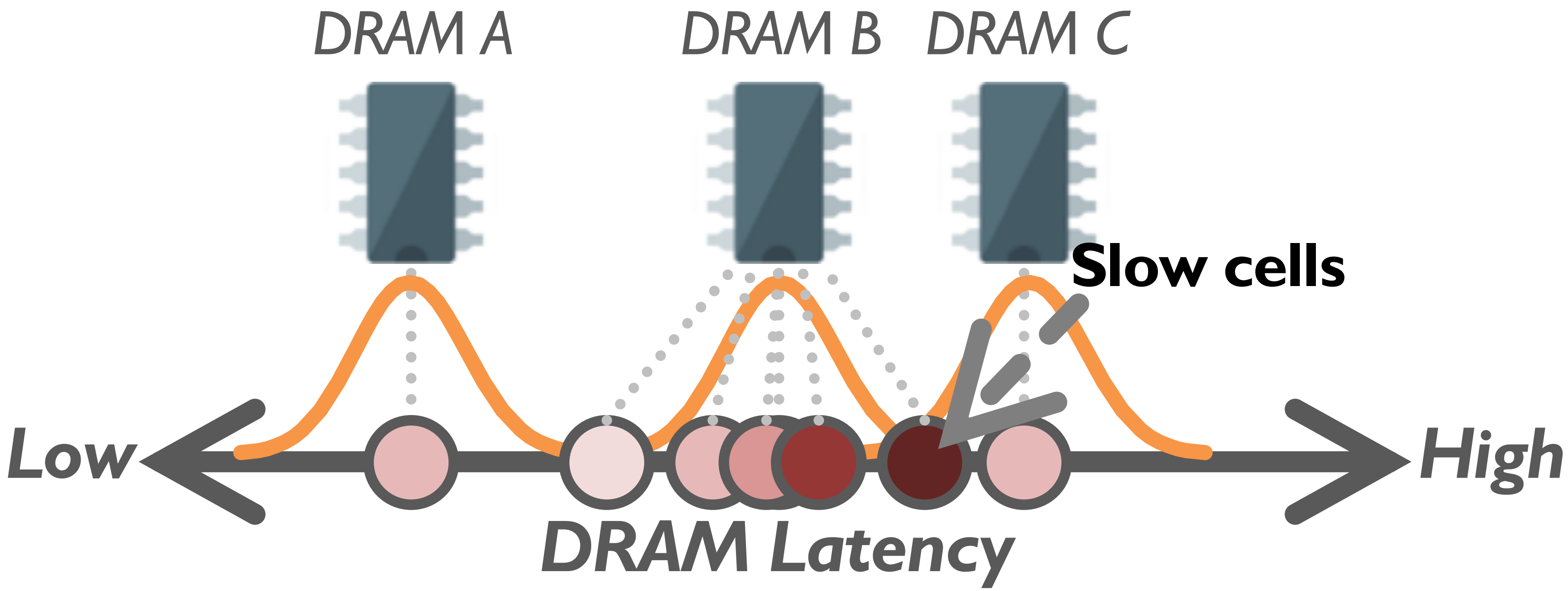
[Kanev+ (**Google**), ISCA'15]

Why the Long Latency?

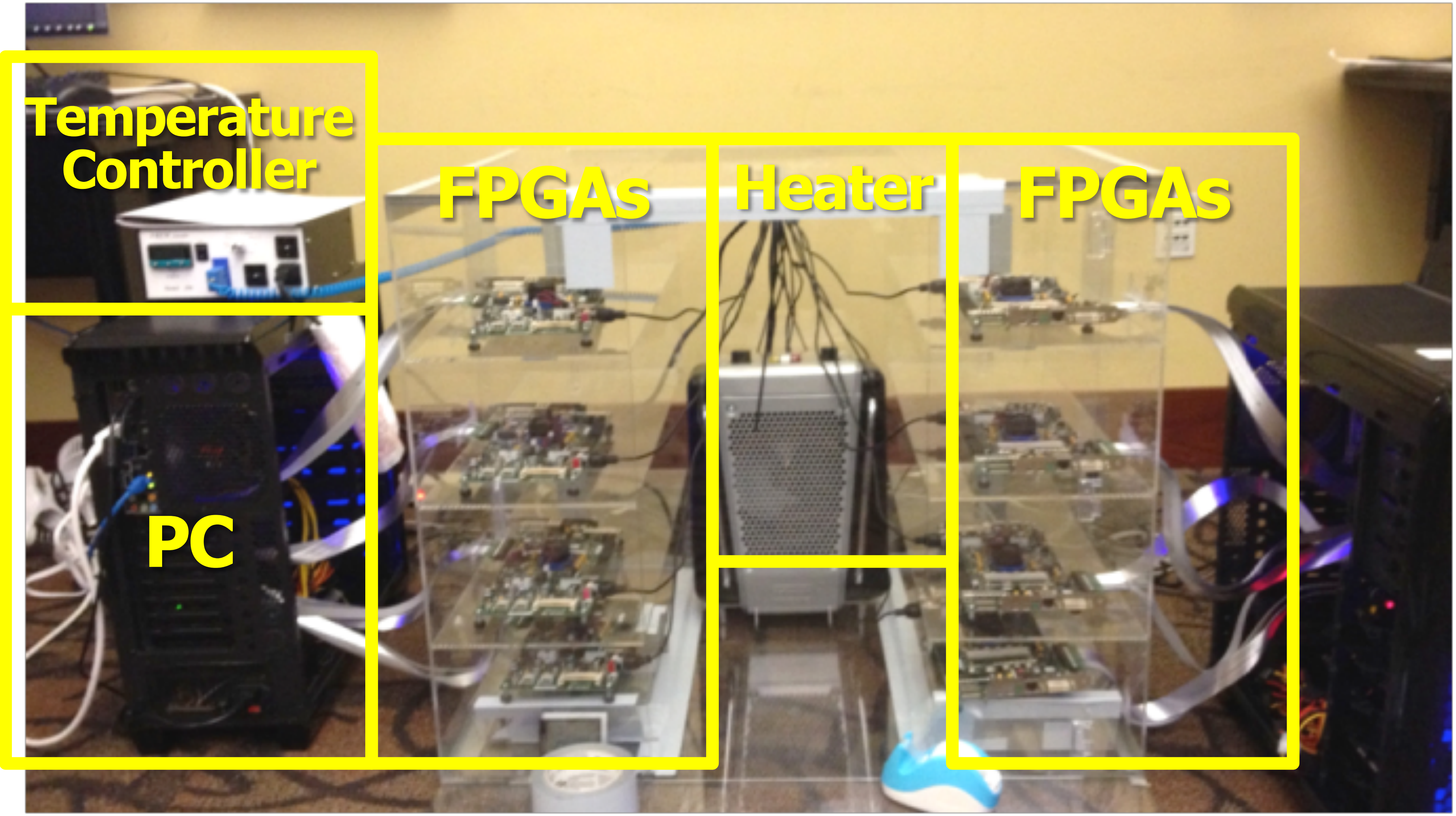
- Design of DRAM uArchitecture
  - Goal: Maximize capacity/area, not minimize latency
- "One size fits all" approach to latency specification
  - Same latency parameters for all temperatures
  - Same latency parameters for all DRAM chips (e.g., rows)
  - Same latency parameters for all parts of a DRAM chip
  - Same latency parameters for all supply voltage levels
  - Same latency parameters for all application data
  - ...

Latency Variation in Memory Chips

Heterogeneous manufacturing & operating conditions →
latency variation in timing parameters



DRAM Characterization Infrastructure



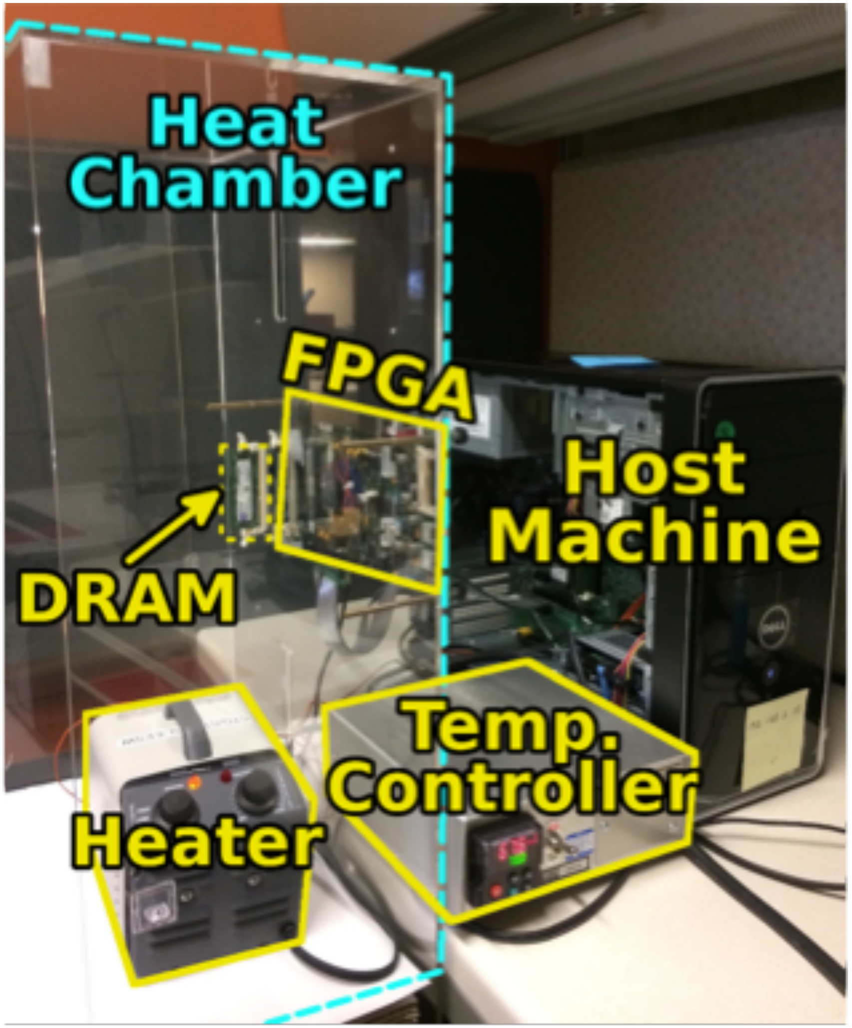
Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.

DRAM Characterization Infrastructure

- Hasan Hassan et al., **SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies**, HPCA 2017.

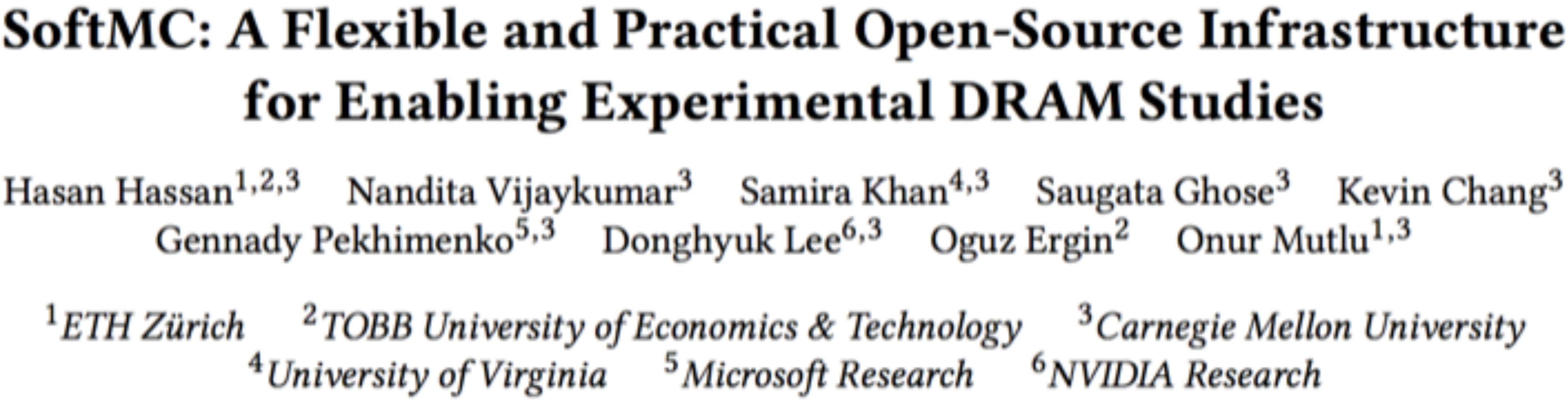
- **Flexible**
- **Easy to Use (C++ API)**
- **Open-source**

github.com/CMU-SAFARI/SoftMC



SoftMC: Open Source DRAM Infrastructure

- https://github.com/CMU-SAFARI/SoftMC



SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies

Hasan Hassan[1,2,3] Nandita Vijaykumar[3] Samira Khan[4,3] Saugata Ghose[3] Kevin Chang[3]
Gennady Pekhimenko[5,3] Donghyuk Lee[6,3] Oguz Ergin[2] Onur Mutlu[1,3]

[1]*ETH Zürich* [2]*TOBB University of Economics & Technology* [3]*Carnegie Mellon University*
[4]*University of Virginia* [5]*Microsoft Research* [6]*NVIDIA Research*

Tackling the Fixed Latency Mindset

- Reliable operation latency is actually very heterogeneous
  - Across temperatures, chips, parts of a chip, voltage levels, …

- Idea: Dynamically find out and use the lowest latency one can reliably access a memory location with
  - Adaptive-Latency DRAM [HPCA 2015]
  - Flexible-Latency DRAM [SIGMETRICS 2016]
  - Design-Induced Variation-Aware DRAM [SIGMETRICS 2017]
  - Voltron [SIGMETRICS 2017]
  - ...

- We would like to find sources of latency heterogeneity and exploit them to minimize latency

Adaptive-Latency DRAM

- *Key idea*
  - **Optimize DRAM timing parameters online**

- *Two components*
  - DRAM manufacturer provides multiple sets of reliable DRAM timing parameters at different temperatures for each DIMM
  - System monitors DRAM temperature & uses appropriate DRAM timing parameters

Lee+, "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case," HPCA 2015.

Latency Reduction Summary of 115 DIMMs

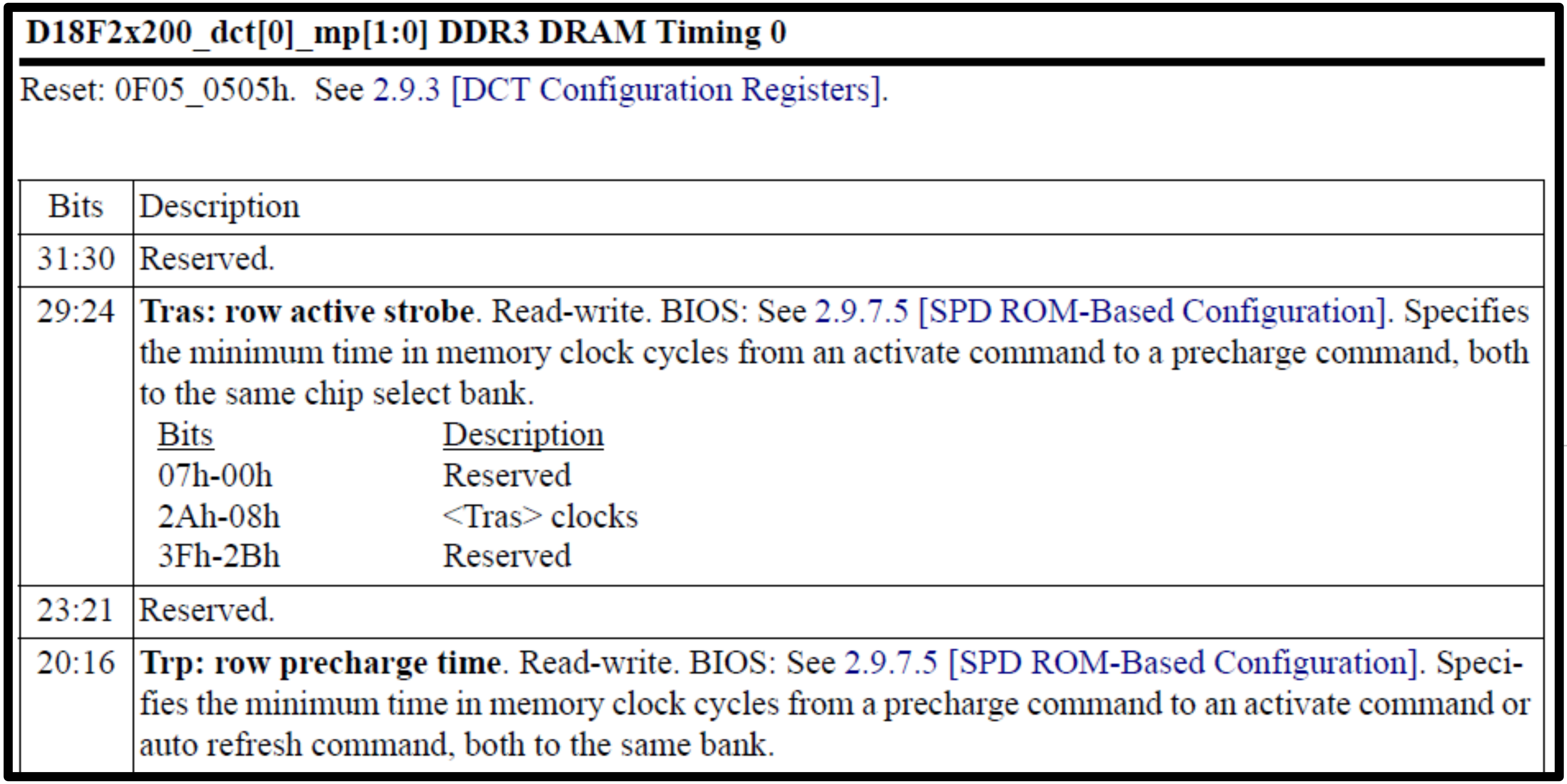
- *Latency reduction for read & write (55°C)*
  - *Read Latency:* ***32.7%***
  - *Write Latency:* ***55.1%***

- *Latency reduction for each timing parameter (55°C)*
  - *Sensing:* ***17.3%***
  - *Restore:* ***37.3%*** *(read),* ***54.8%*** *(write)*
  - *Precharge:* ***35.2%***

Lee+, "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case," HPCA 2015.

AL-DRAM: Real System Evaluation

- *System*
  - *CPU: AMD 4386 (8 Cores, 3.1GHz, 8MB LLC)*

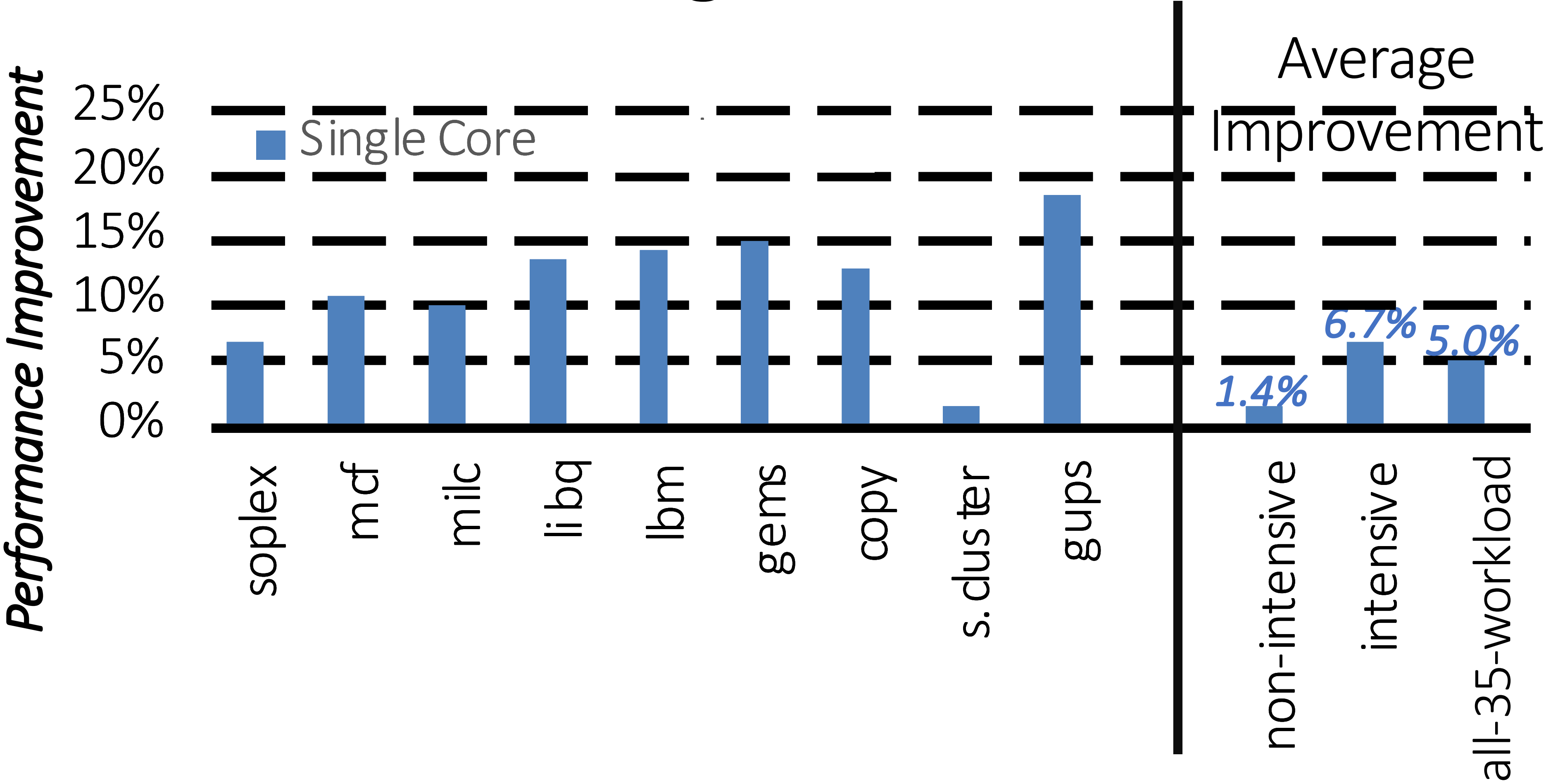


D18F2x200_dct[0]_mp[1:0] DDR3 DRAM Timing 0

Reset: 0F05_0505h. See 2.9.3 [DCT Configuration Registers].

Bits	Description
31:30	Reserved.
29:24	**Tras: row active strobe**. Read-write. BIOS: See 2.9.7.5 [SPD ROM-Based Configuration]. Specifies the minimum time in memory clock cycles from an activate command to a precharge command, both to the same chip select bank. Bits Description 07h-00h Reserved 2Ah-08h <Tras> clocks 3Fh-2Bh Reserved
23:21	Reserved.
20:16	**Trp: row precharge time**. Read-write. BIOS: See 2.9.7.5 [SPD ROM-Based Configuration]. Specifies the minimum time in memory clock cycles from a precharge command to an activate command or auto refresh command, both to the same bank.

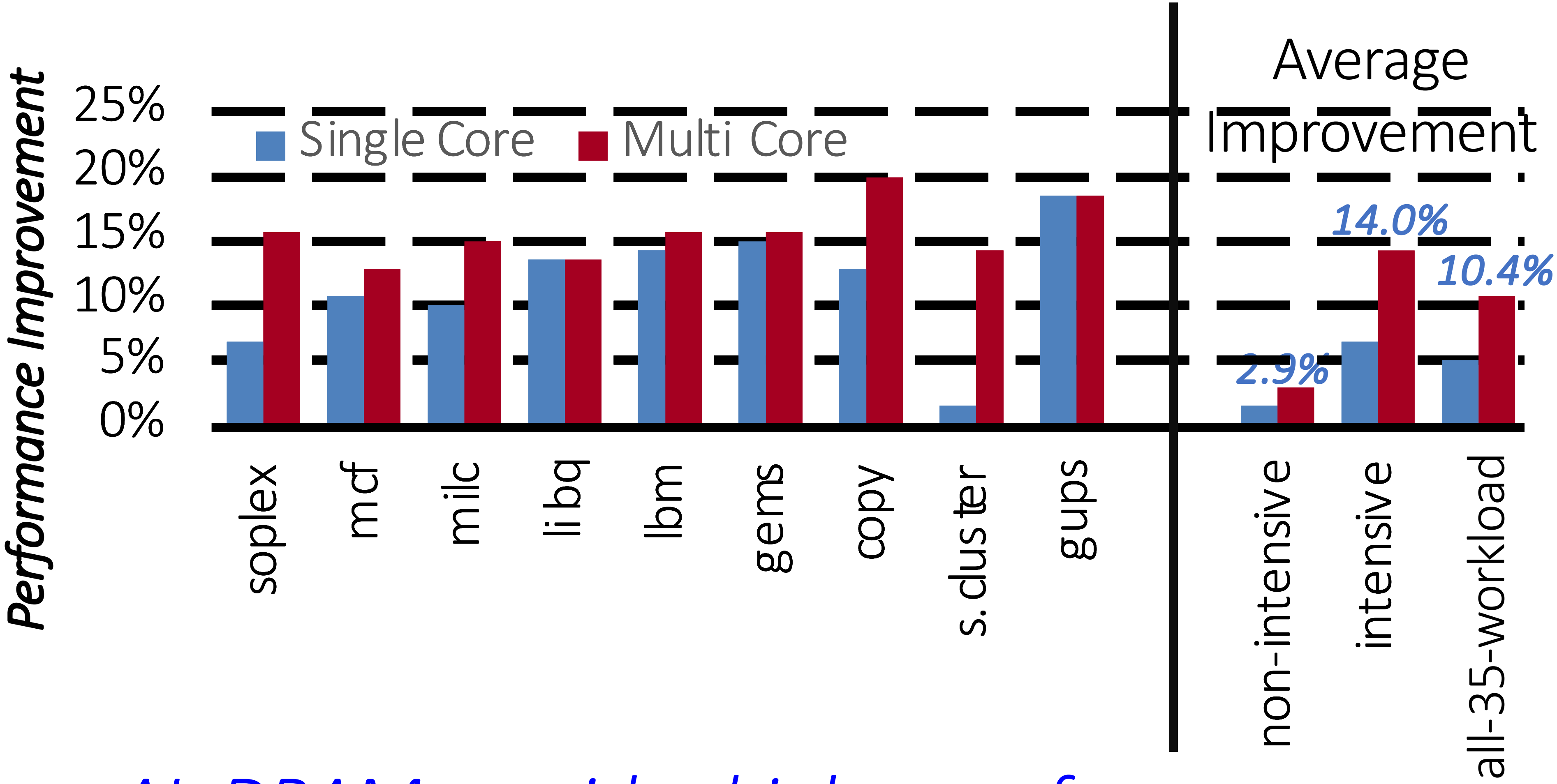
AL-DRAM: Single-Core Evaluation



AL-DRAM ***improves single-core performance***

on a real system

AL-DRAM: Multi-Core Evaluation



AL-DRAM provides higher performance on ***multi-programmed & multi-threaded workloads***

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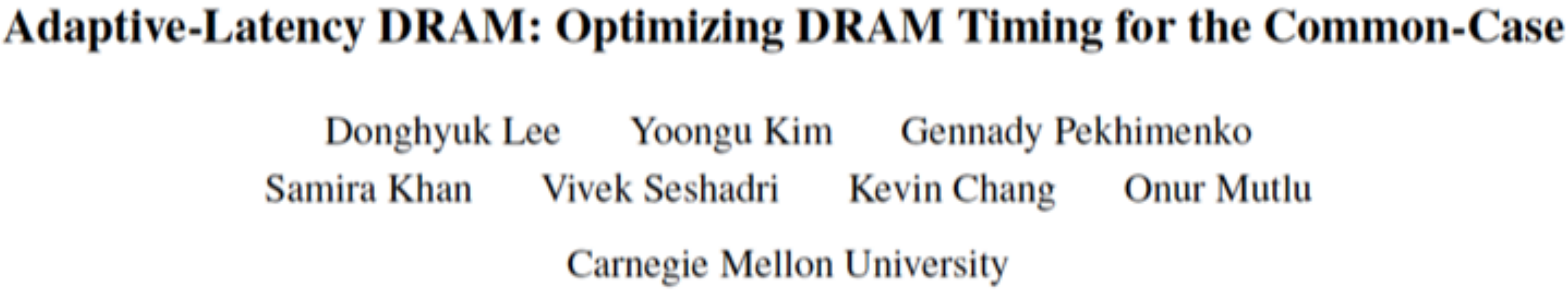
Reducing Latency Also Reduces Energy

- AL-DRAM reduces DRAM power consumption by 5.8%
- Major reason: reduction in row activation time

More on Adaptive-Latency DRAM

- Donghyuk Lee, Yoongu Kim, Gennady Pekhimenko, Samira Khan, Vivek Seshadri, Kevin Chang, and Onur Mutlu,
  "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case"
  Proceedings of the 21st International Symposium on High-Performance Computer Architecture (***HPCA***), Bay Area, CA, February 2015.
  [Slides (pptx) (pdf)] [Full data sets]

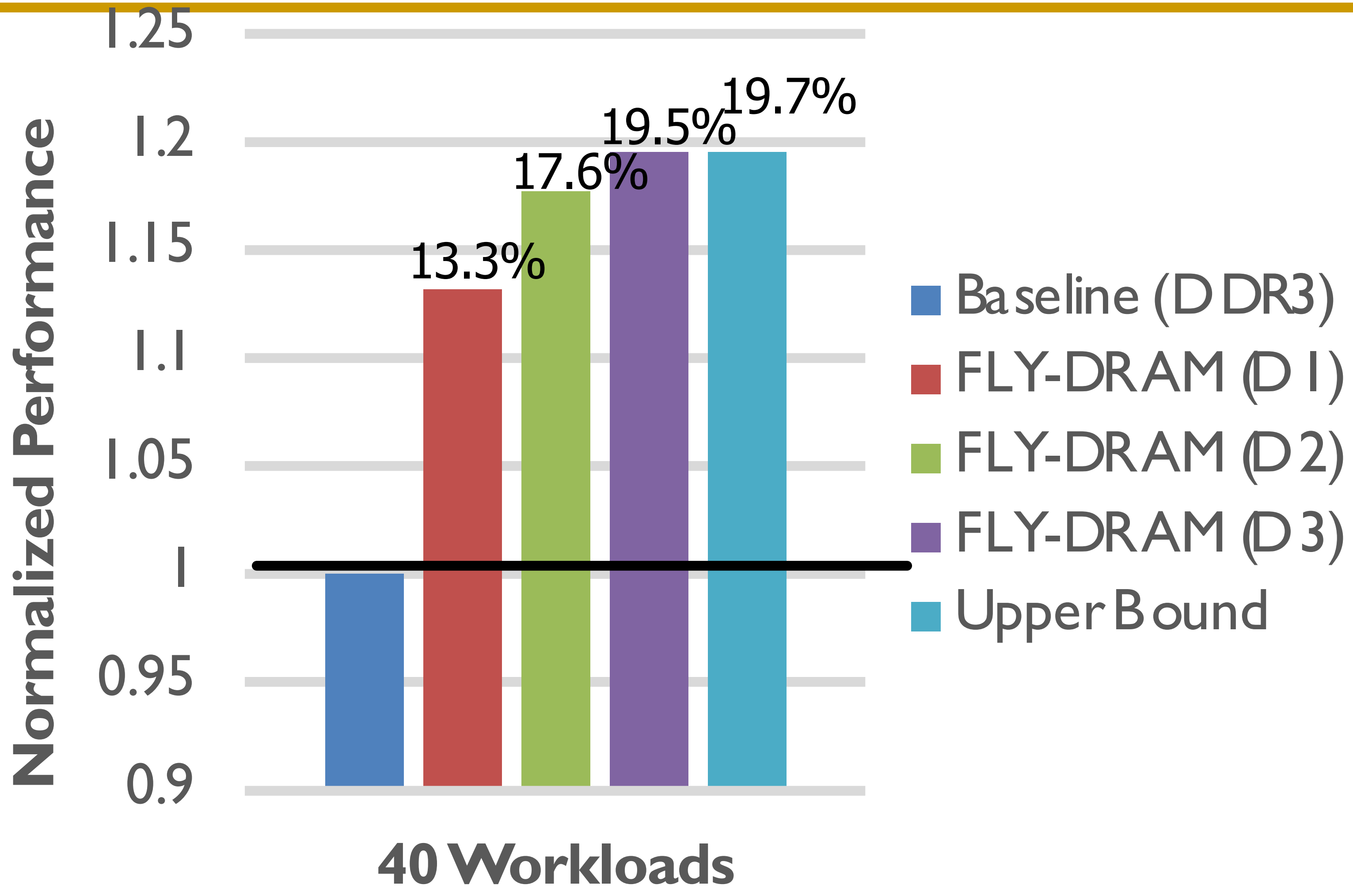


Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case

Donghyuk Lee Yoongu Kim Gennady Pekhimenko
Samira Khan Vivek Seshadri Kevin Chang Onur Mutlu

Carnegie Mellon University

Heterogeneous Latency within A Chip



Chang+, "**Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization"**," SIGMETRICS 2016.

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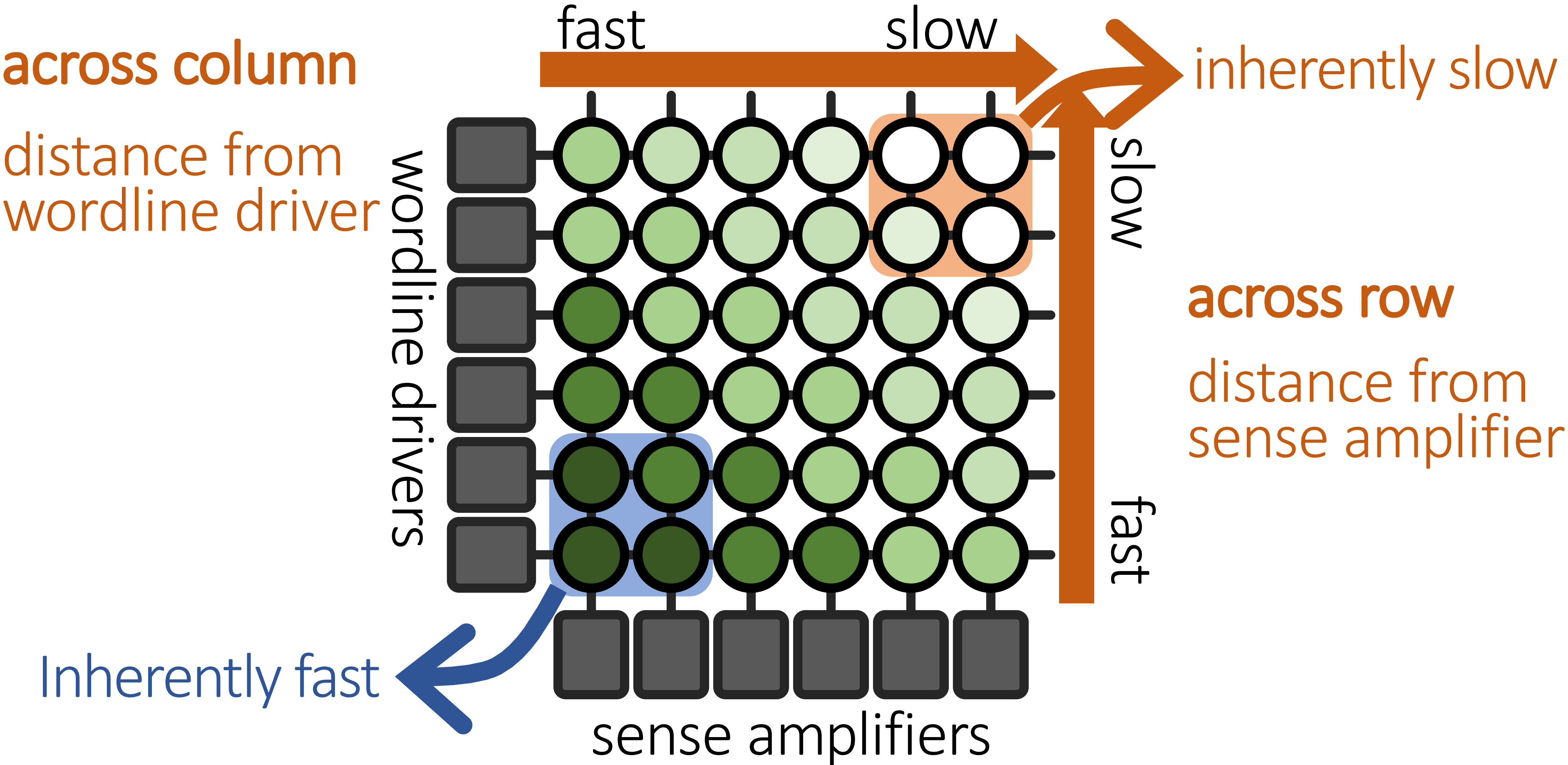
Analysis of Latency Variation in DRAM Chips

- Kevin Chang, Abhijith Kashyap, Hasan Hassan, Samira Khan, Kevin Hsieh, Donghyuk Lee, Saugata Ghose, Gennady Pekhimenko, Tianshi Li, and Onur Mutlu,
  "Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization"
  Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (***SIGMETRICS***), Antibes Juan-Les-Pins, France, June 2016.
  [Slides (pptx) (pdf)]
  [Source Code]

Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization

Kevin K. Chang[1] Abhijith Kashyap[1] Hasan Hassan[1,2]
Saugata Ghose[1] Kevin Hsieh[1] Donghyuk Lee[1] Tianshi Li[1,3]
Gennady Pekhimenko[1] Samira Khan[4] Onur Mutlu[5,1]
[1]Carnegie Mellon University [2]TOBB ETÜ [3]Peking University [4]University of Virginia [5]ETH Zürich

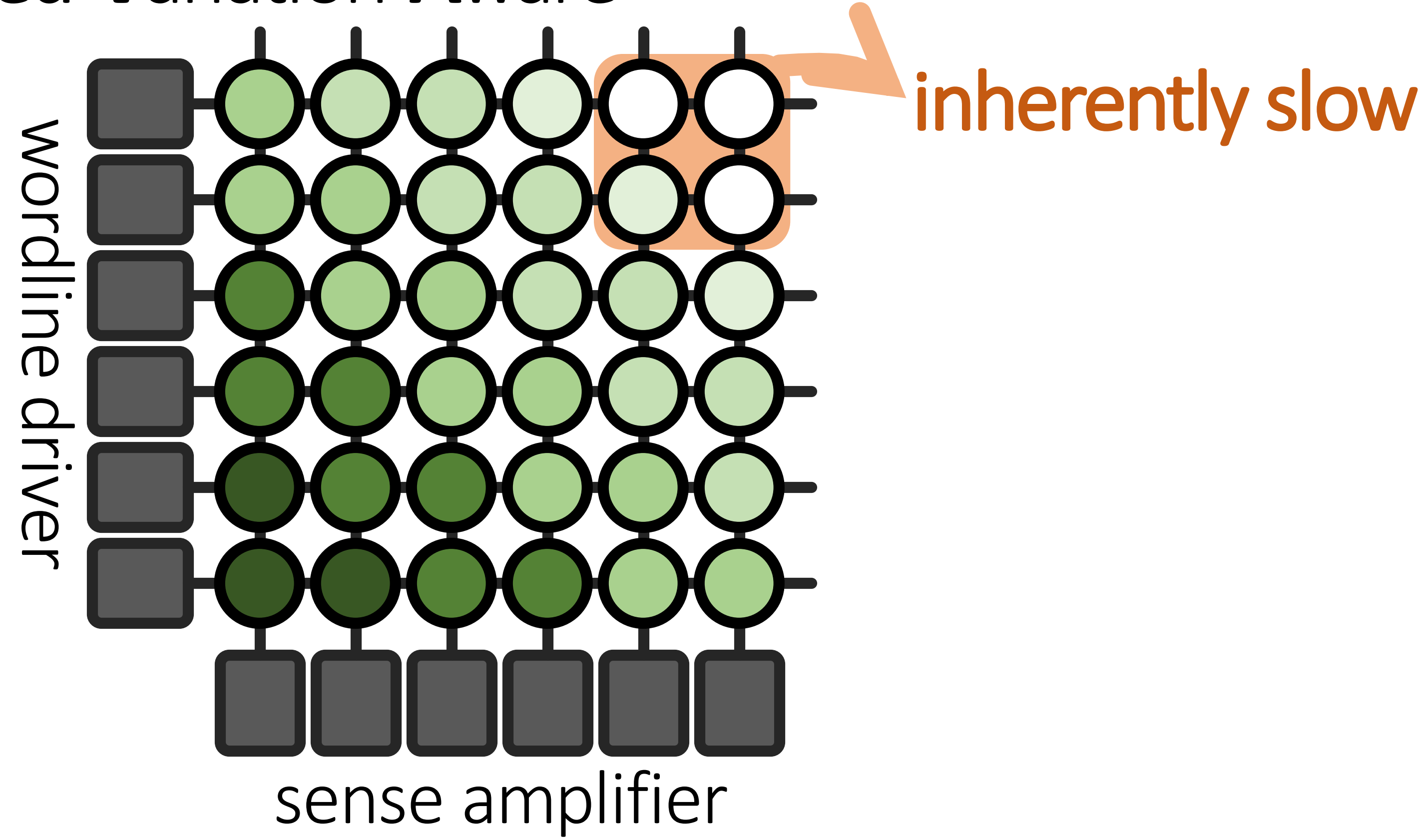
What Is Design-Induced Variation?



Systematic variation in cell access times caused by the ***physical organization*** of DRAM

DIVA Online **Profiling**

Design-**I**nduced-**V**ariation-**A**ware

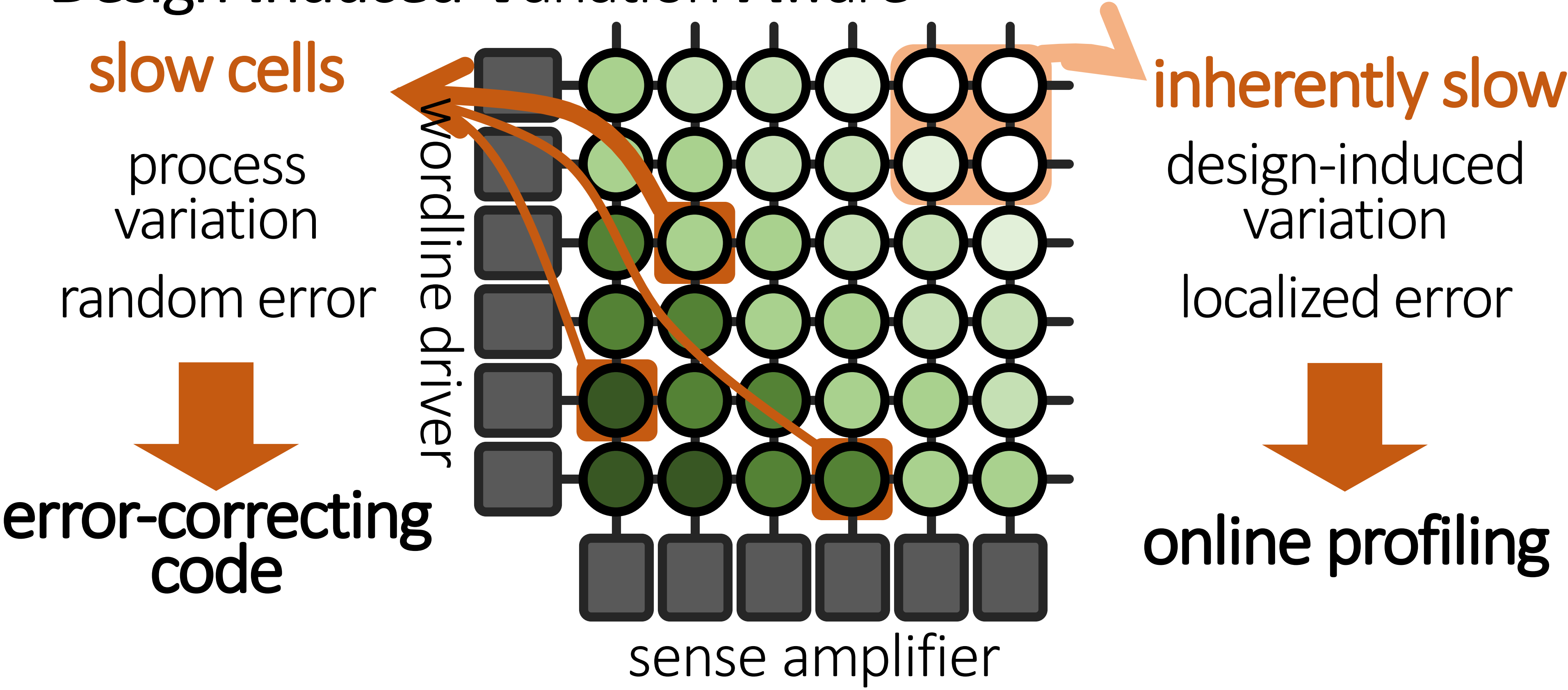


Profile *only slow regions* to determine min. latency

→ *Dynamic* & *low cost* latency optimization

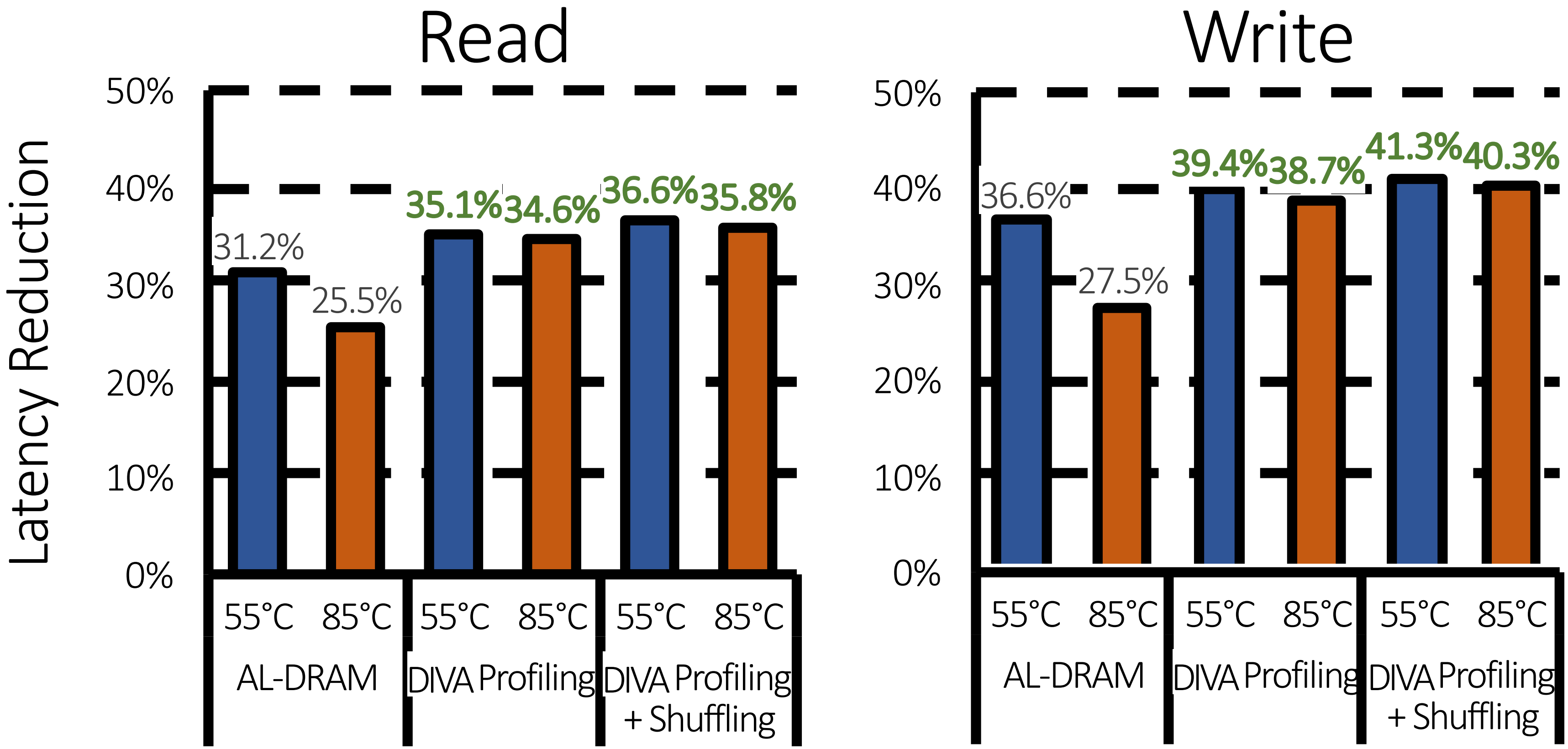
DIVA Online **Profiling**

Design-**I**nduced-**V**ariation-**A**ware



Combine error-correcting codes & online profiling
→ Reliably reduce DRAM latency

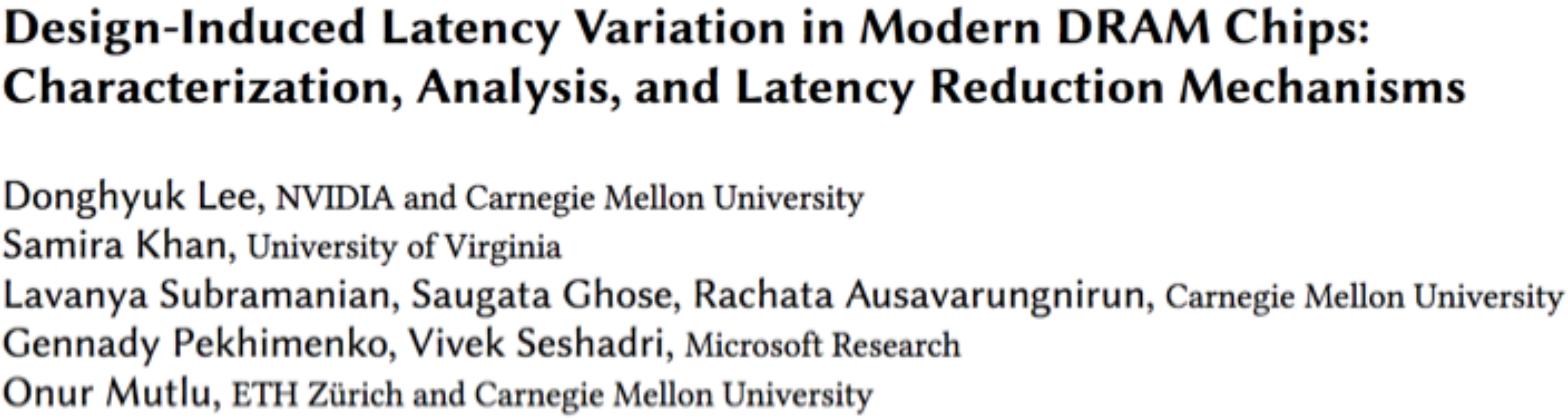
DIVA-DRAM Reduces Latency



DIVA-DRAM ***reduces latency more aggressively*** and uses ECC to correct random slow cells

Design-Induced Latency Variation in DRAM

- Donghyuk Lee, Samira Khan, Lavanya Subramanian, Saugata Ghose, Rachata Ausavarungnirun, Gennady Pekhimenko, Vivek Seshadri, and Onur Mutlu, **"Design-Induced Latency Variation in Modern DRAM Chips: Characterization, Analysis, and Latency Reduction Mechanisms"** *Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (**SIGMETRICS**)*, Urbana-Champaign, IL, USA, June 2017.



Design-Induced Latency Variation in Modern DRAM Chips: Characterization, Analysis, and Latency Reduction Mechanisms

Donghyuk Lee, NVIDIA and Carnegie Mellon University
Samira Khan, University of Virginia
Lavanya Subramanian, Saugata Ghose, Rachata Ausavarungnirun, Carnegie Mellon University
Gennady Pekhimenko, Vivek Seshadri, Microsoft Research
Onur Mutlu, ETH Zürich and Carnegie Mellon University

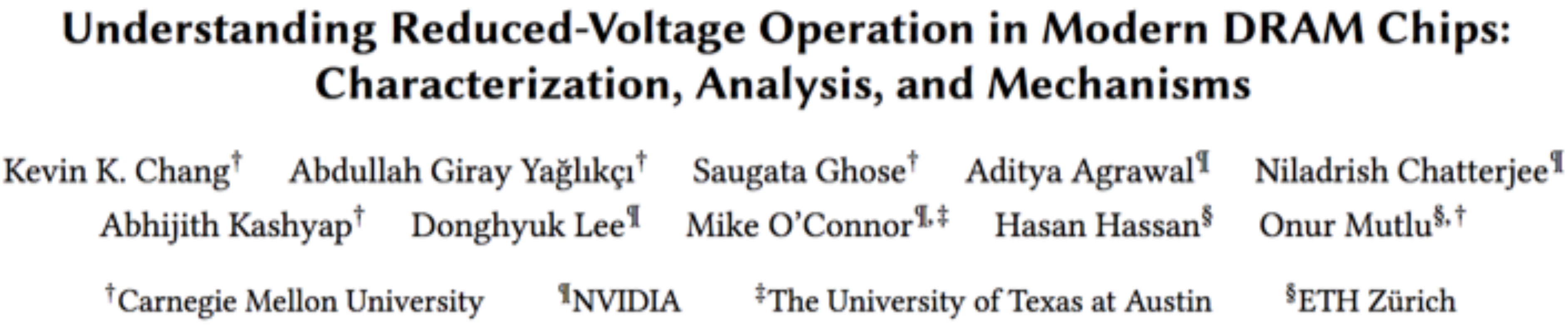
Voltron: Exploiting the Voltage-Latency-Reliability Relationship

Executive Summary

- DRAM (memory) power is significant in today's systems
  - Existing low-voltage DRAM reduces voltage **conservatively**
- Goal: Understand and exploit the reliability and latency behavior of real DRAM chips under ***aggressive reduced-voltage operation***
- Key experimental observations:
  - Huge voltage margin -- Errors occur beyond some voltage
  - Errors exhibit spatial locality
  - Higher operation latency mitigates voltage-induced errors
- **Voltron**: A new DRAM energy reduction mechanism
  - Reduce DRAM voltage **without introducing errors**
  - Use a **regression model** to select voltage that does not degrade performance beyond a chosen target → 7.3% system energy reduction

Analysis of Latency-Voltage in DRAM Chips

- Kevin Chang, A. Giray Yaglikci, Saugata Ghose, Aditya Agrawal, Niladrish Chatterjee, Abhijith Kashyap, Donghyuk Lee, Mike O'Connor, Hasan Hassan, and Onur Mutlu,
  "Understanding Reduced-Voltage Operation in Modern DRAM Devices: Experimental Characterization, Analysis, and Mechanisms"
  *Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (**SIGMETRICS**)*, Urbana-Champaign, IL, USA, June 2017.



Understanding Reduced-Voltage Operation in Modern DRAM Chips: Characterization, Analysis, and Mechanisms

Kevin K. Chang[†] Abdullah Giray Yağlıkçı[†] Saugata Ghose[†] Aditya Agrawal[¶] Niladrish Chatterjee[¶]
Abhijith Kashyap[†] Donghyuk Lee[¶] Mike O'Connor[¶,‡] Hasan Hassan[§] Onur Mutlu[§,†]

[†]Carnegie Mellon University [¶]NVIDIA [‡]The University of Texas at Austin [§]ETH Zürich

And, What If …

- … we can sacrifice reliability of some data to access it with even lower latency?

The DRAM Latency PUF:

Quickly Evaluating Physical Unclonable Functions by Exploiting the Latency-Reliability Tradeoff in Modern Commodity DRAM Devices

Jeremie S. Kim **Minesh Patel**
Hasan Hassan **Onur Mutlu**

Systems@ETH zürich

SAFARI

ETH zürich

Carnegie Mellon

Motivation

- A **PUF** is function that generates a signature **unique** to a given device

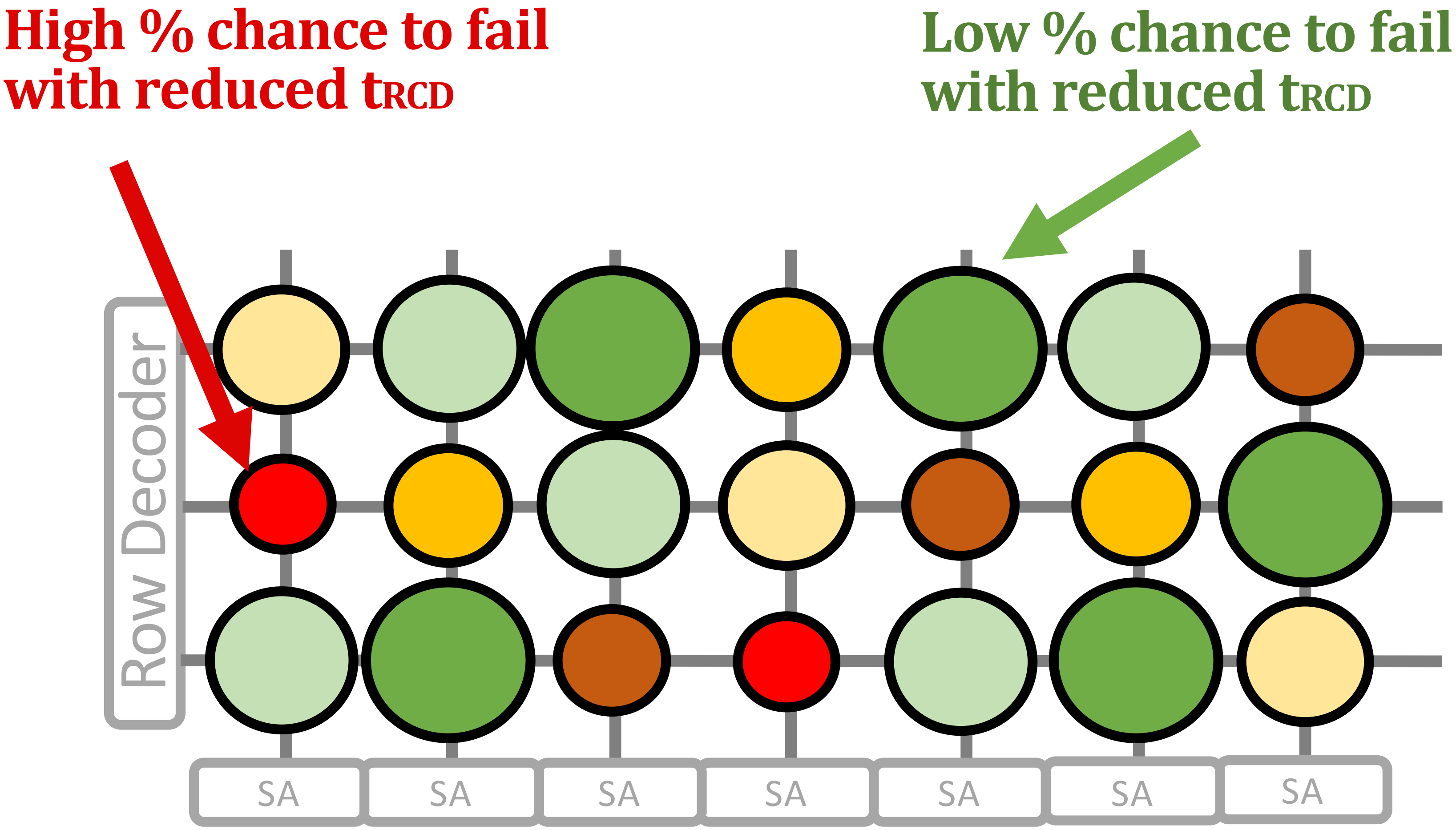
- Used in a **Challenge-Response Protocol**
  - Each device generates a unique **PUF response** depending the inputs
  - A trusted server **authenticates** a device if it generates the expected PUF response

DRAM Latency Characterization of 223 LPDDR4 DRAM Devices

- Latency failures come from accessing DRAM with **reduced** timing parameters.

- **Key Observations:**
  1. A cell's **latency failure** probability is determined by **random process variation**
  2. Latency failure patterns are **repeatable and unique to a device**

DRAM Latency PUF Key Idea


High % chance to fail
with reduced tRCD

Low % chance to fail
with reduced tRCD

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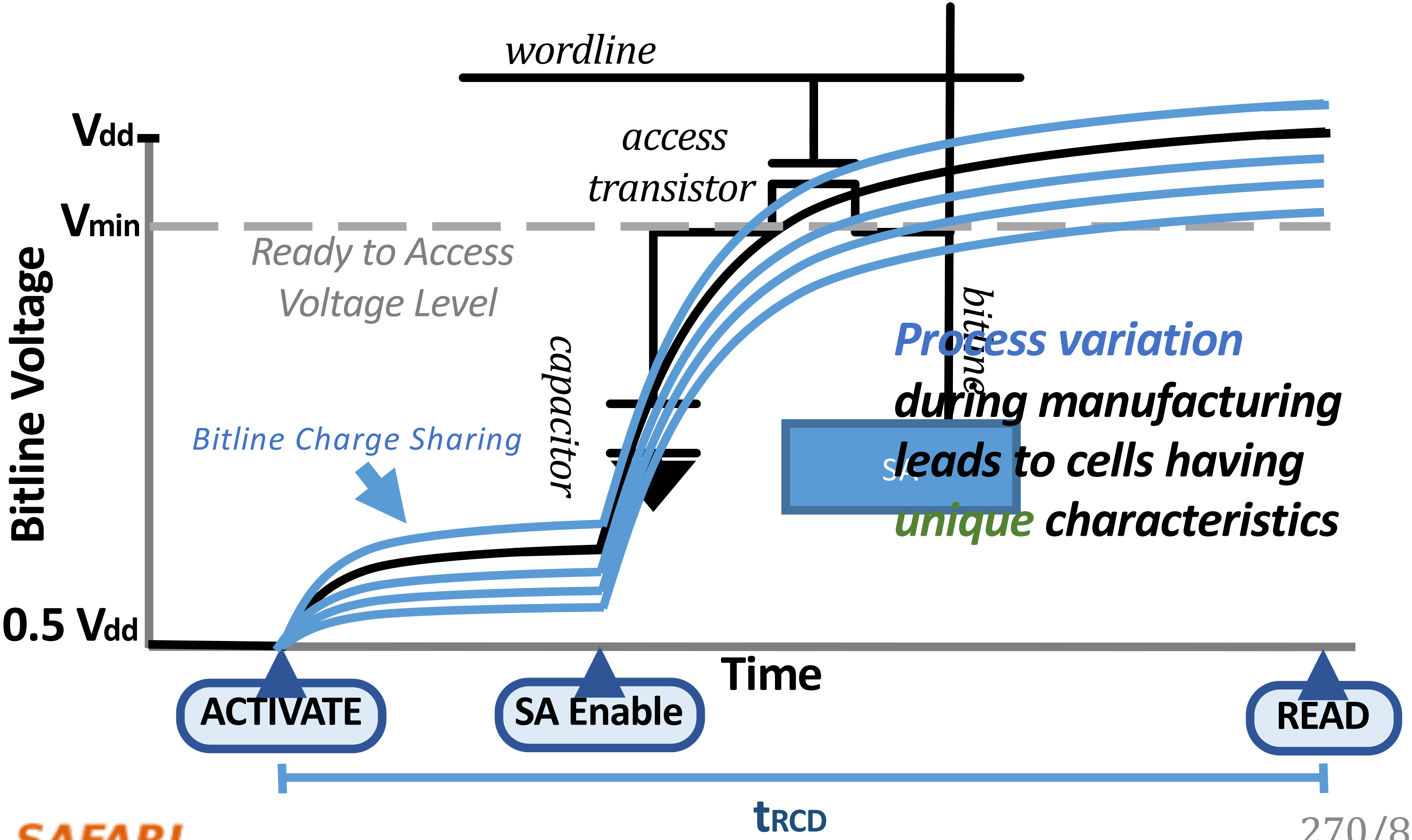
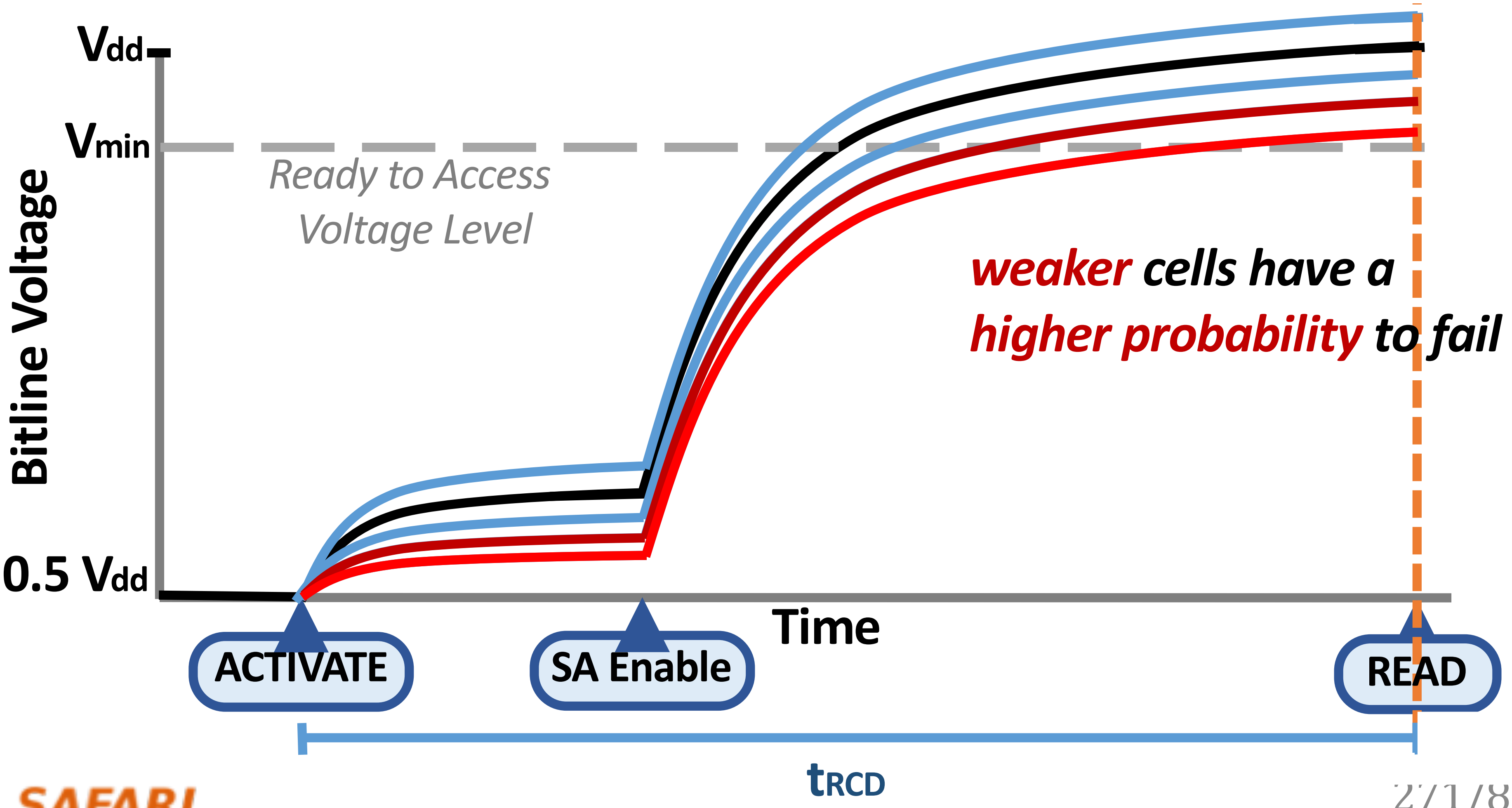
DRAM Accesses and Failures



***Process variation* during manufacturing leads to cells having *unique* characteristics**

DRAM Accesses and Failures



weaker cells have a higher probability to fail

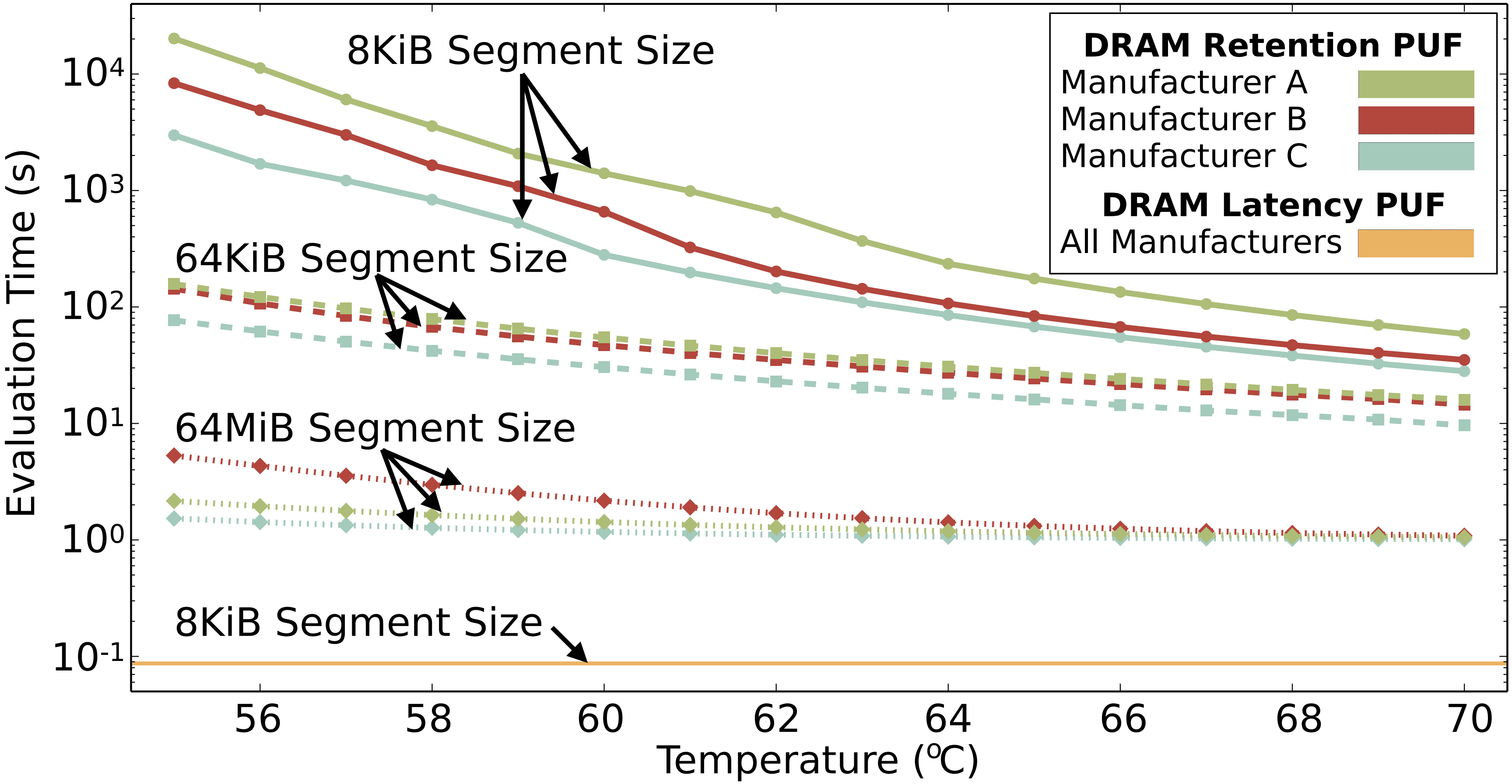
The DRAM Latency PUF Evaluation

- We generate PUF responses using **latency errors** in a region of DRAM

- The latency error patterns **satisfy PUF requirements**

- The DRAM Latency PUF **generates PUF responses in 88.2ms**

Results



- We are **orders of magnitude faster** than prior DRAM PUFs!

The DRAM Latency PUF:

Quickly Evaluating Physical Unclonable Functions by Exploiting the Latency-Reliability Tradeoff in Modern Commodity DRAM Devices

Jeremie S. Kim **Minesh Patel**
Hasan Hassan **Onur Mutlu**

HPCA 2018

QR Code for the paper
https://people.inf.ethz.ch/omutlu/pub/dram-latency-puf_hpca18.pdf

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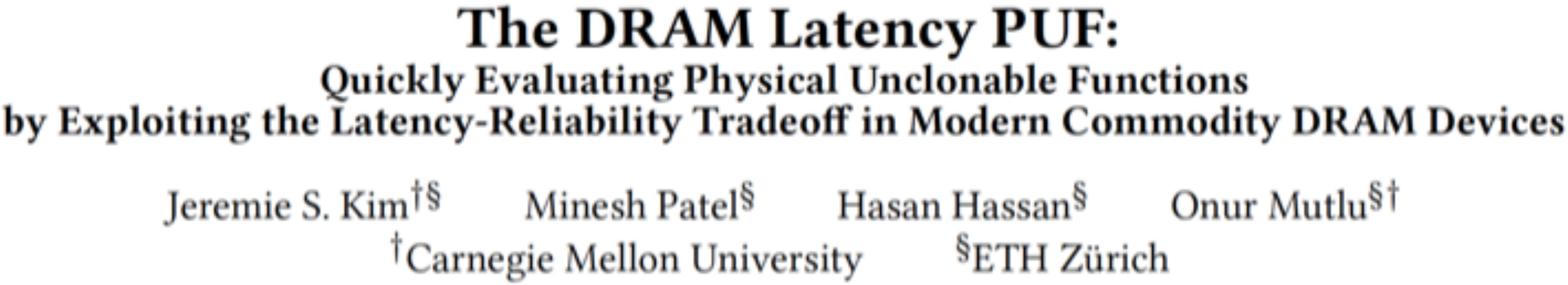
ETH Zürich

Carnegie Mellon

DRAM Latency PUFs

- Jeremie S. Kim, Minesh Patel, Hasan Hassan, and Onur Mutlu, **"The DRAM Latency PUF: Quickly Evaluating Physical Unclonable Functions by Exploiting the Latency-Reliability Tradeoff in Modern DRAM Devices"** *Proceedings of the 24th International Symposium on High-Performance Computer Architecture* (***HPCA***), Vienna, Austria, February 2018.
  [Lightning Talk Video]
  [Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)]

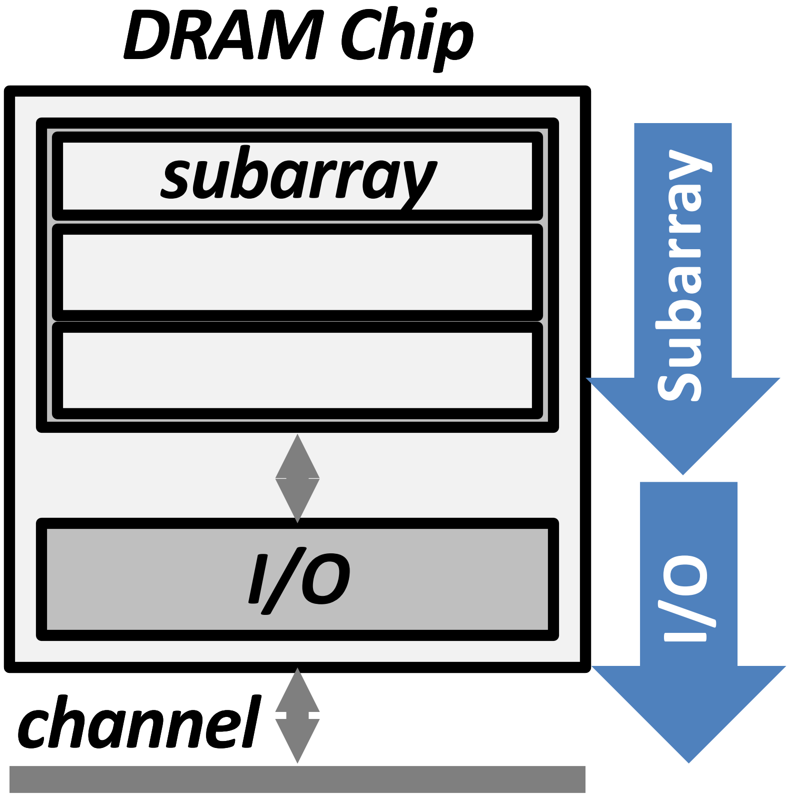


The DRAM Latency PUF:
Quickly Evaluating Physical Unclonable Functions
by Exploiting the Latency-Reliability Tradeoff in Modern Commodity DRAM Devices

Jeremie S. Kim[†§] Minesh Patel[§] Hasan Hassan[§] Onur Mutlu[§†]
[†]Carnegie Mellon University [§]ETH Zürich

Tiered Latency DRAM

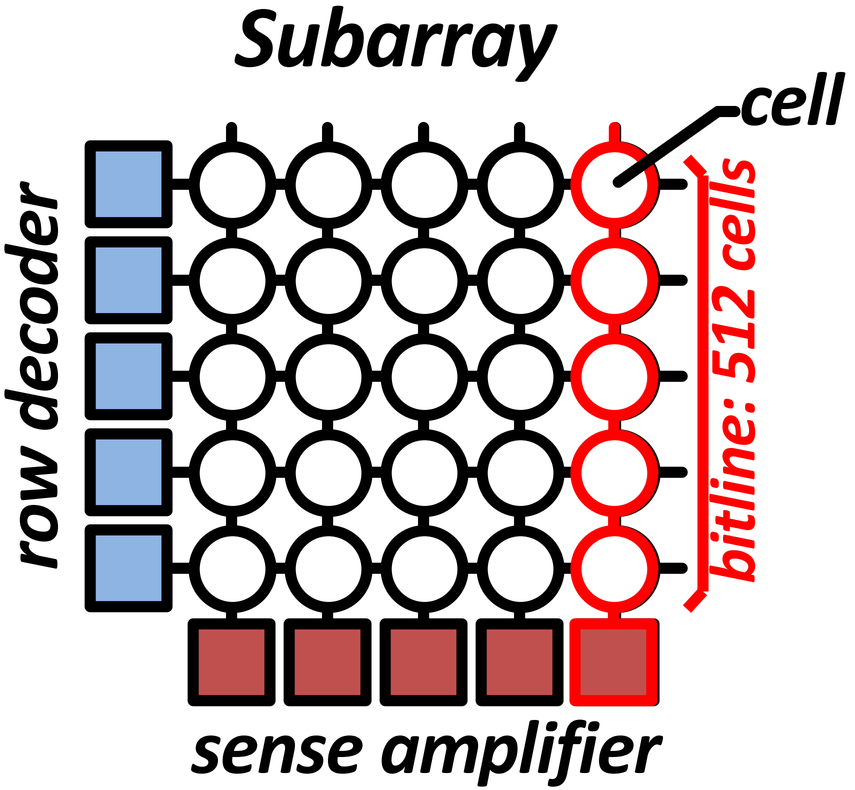
What Causes the Long Latency?

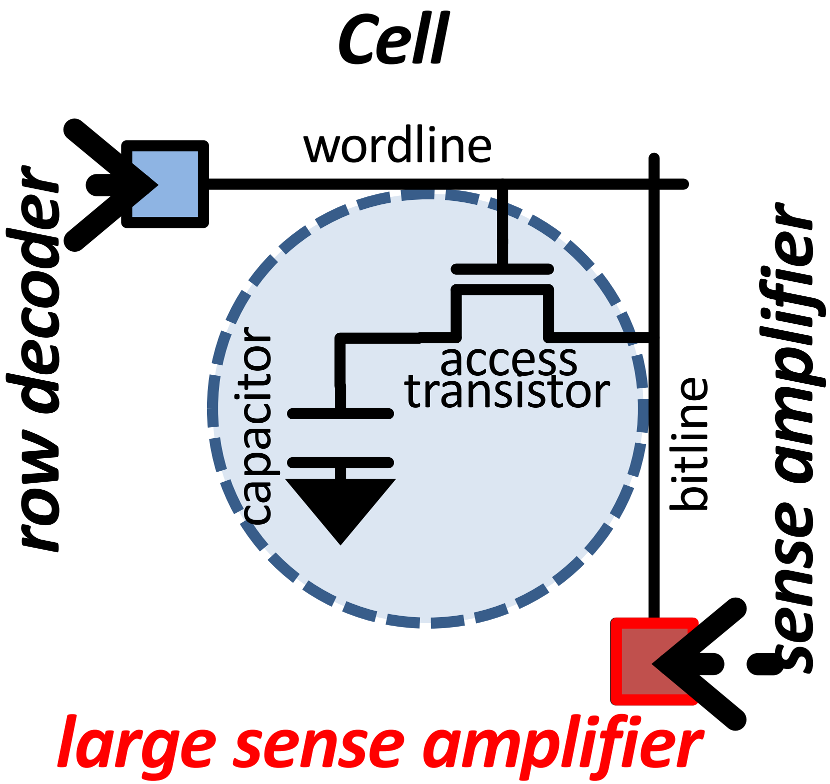


DRAM Latency = Subarray Latency + I/O Latency

Dominant

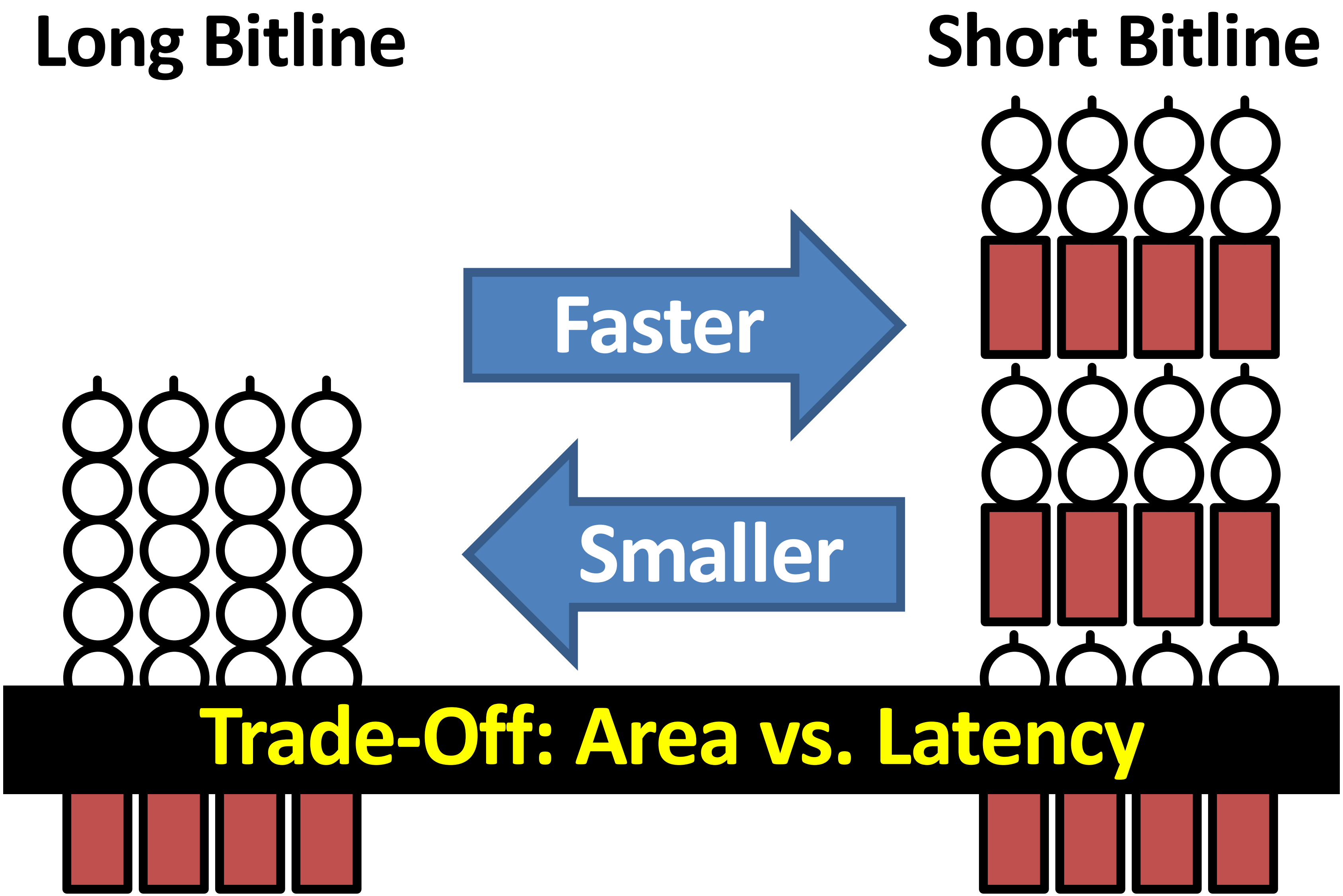
Why is the Subarray So Slow?





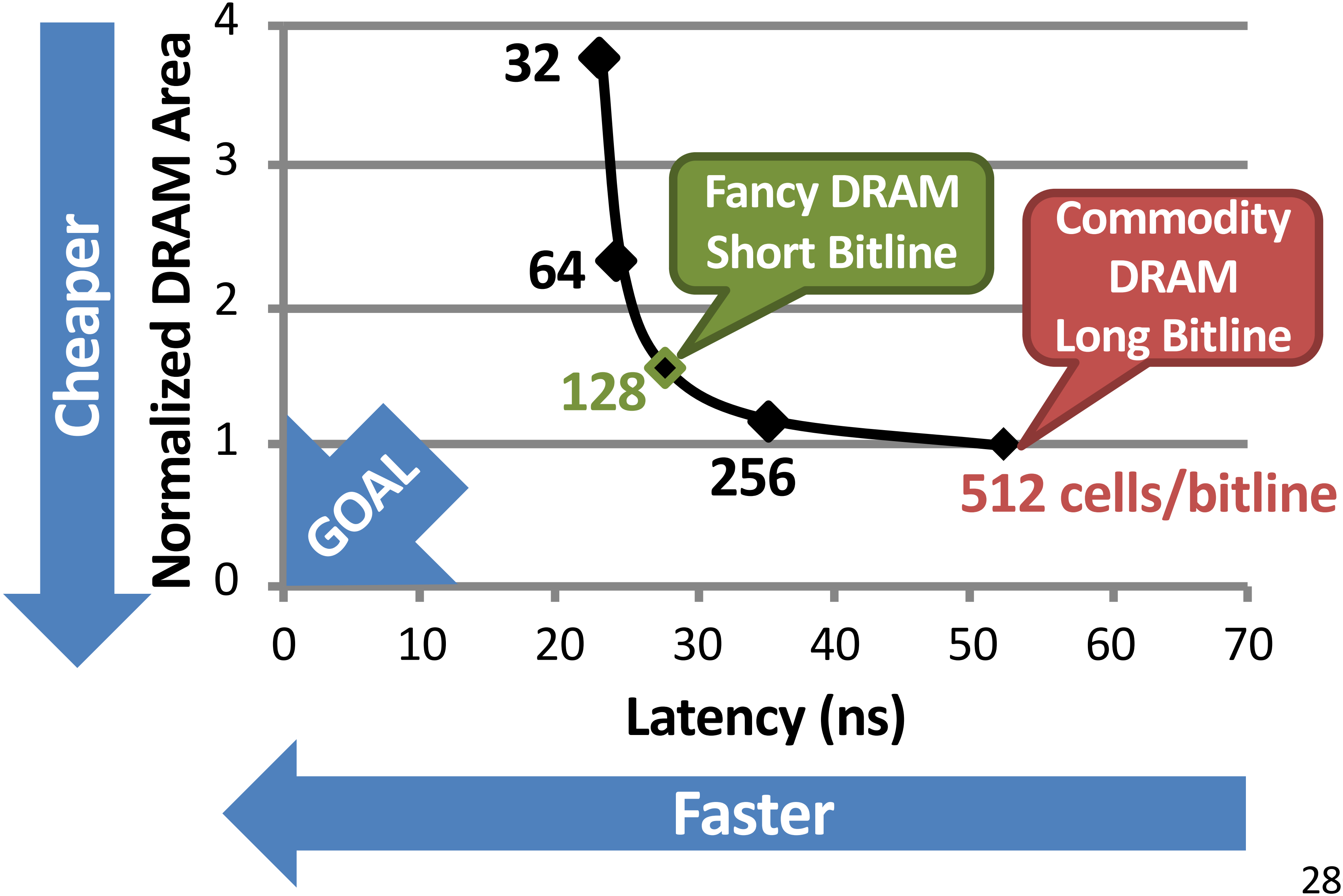
- **Long bitline**
  - **Amortizes sense amplifier cost → Small area**
  - **Large bitline capacitance → High latency & power**

Trade-Off: Area (Die Size) vs. Latency

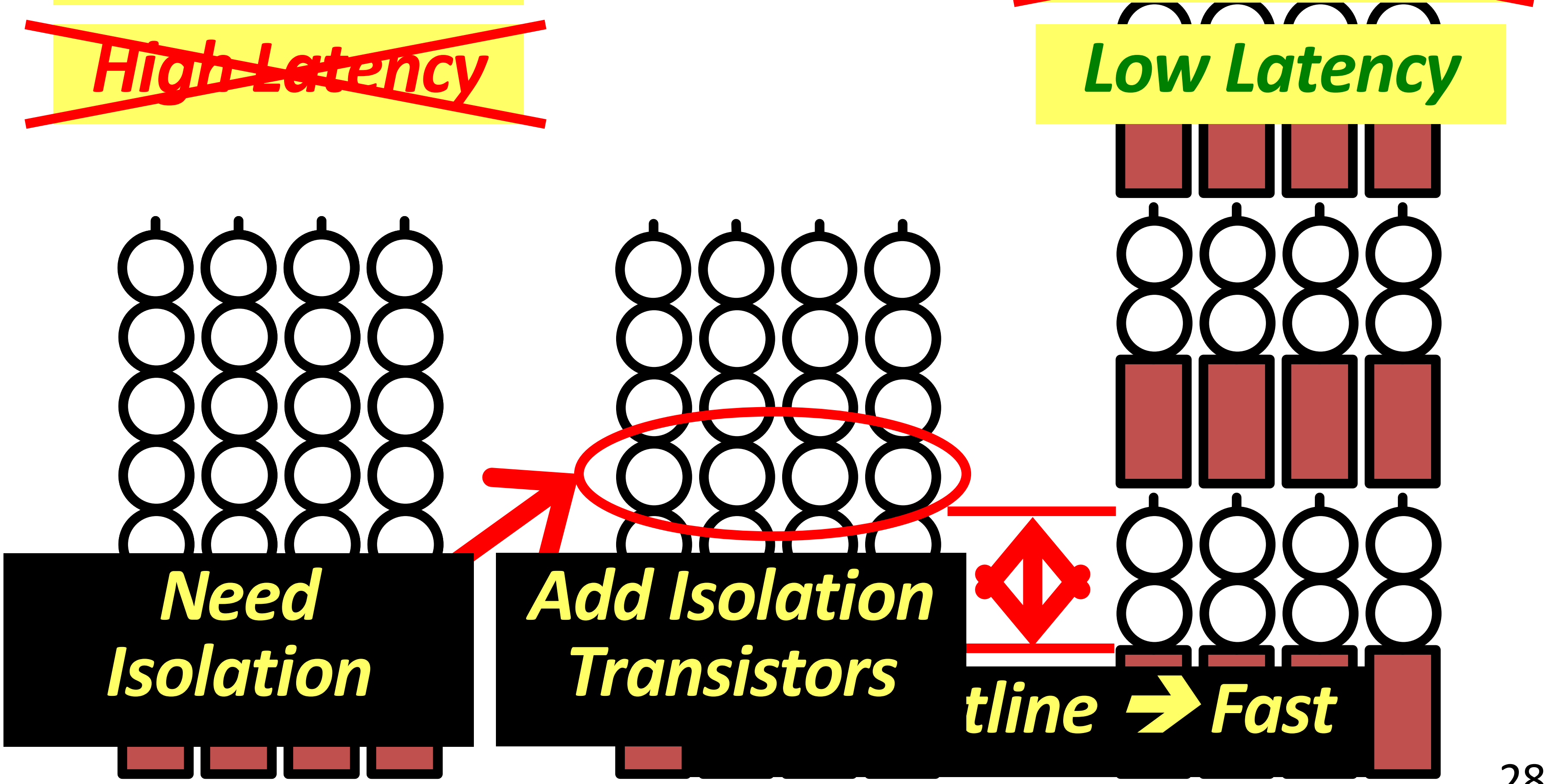


Trade-Off: Area vs. Latency

Trade-Off: Area (Die Size) vs. Latency



Approximating the Best of Both Worlds



Long Bitline

Small Area

~~High Latency~~

Need Isolation

Our Proposal

Add Isolation Transistors

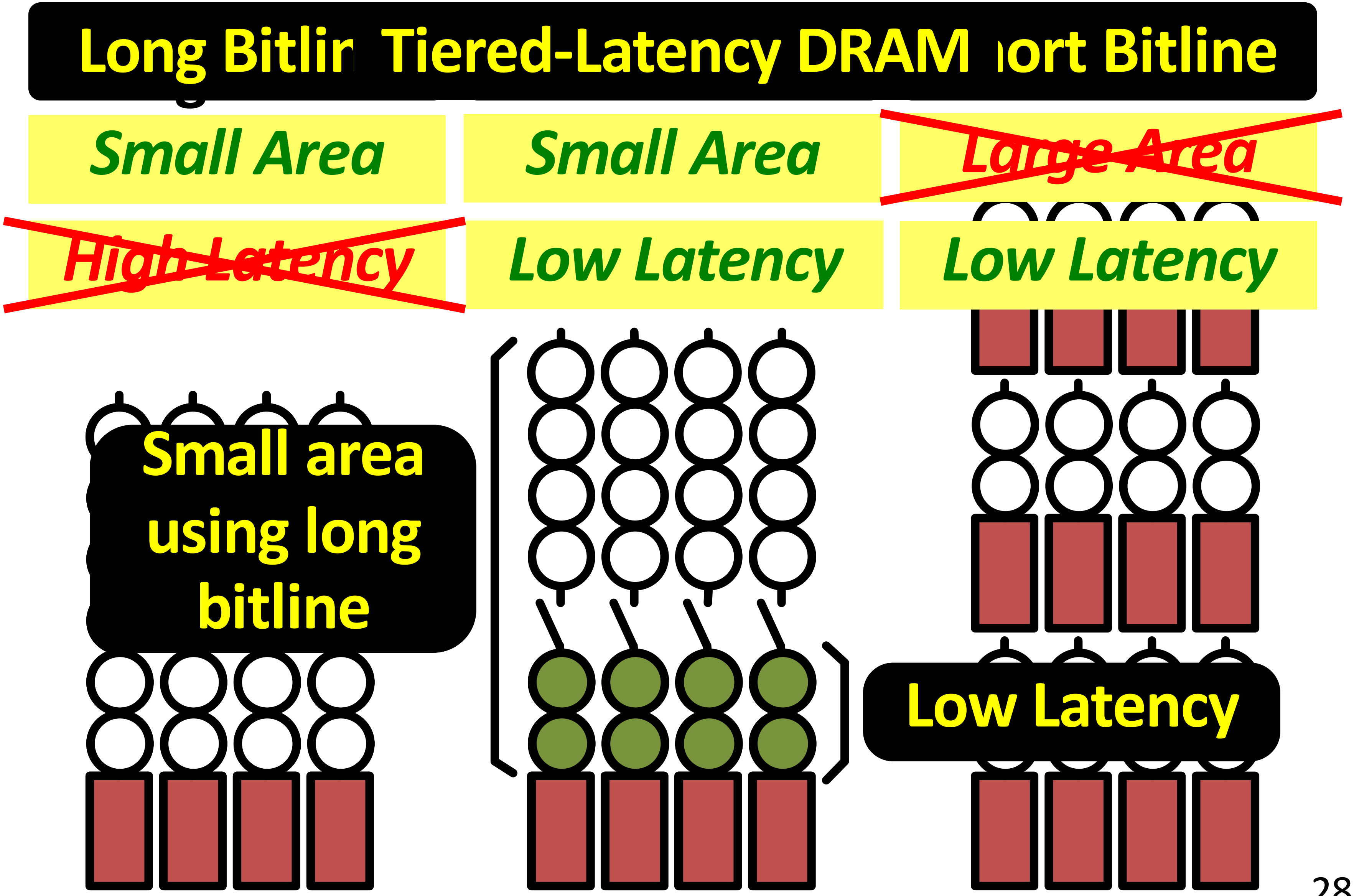
Short Bitline

~~Large Area~~

Low Latency

tline → Fast

Approximating the Best of Both Worlds



Long Bitlin **Tiered-Latency DRAM** **ort Bitline**

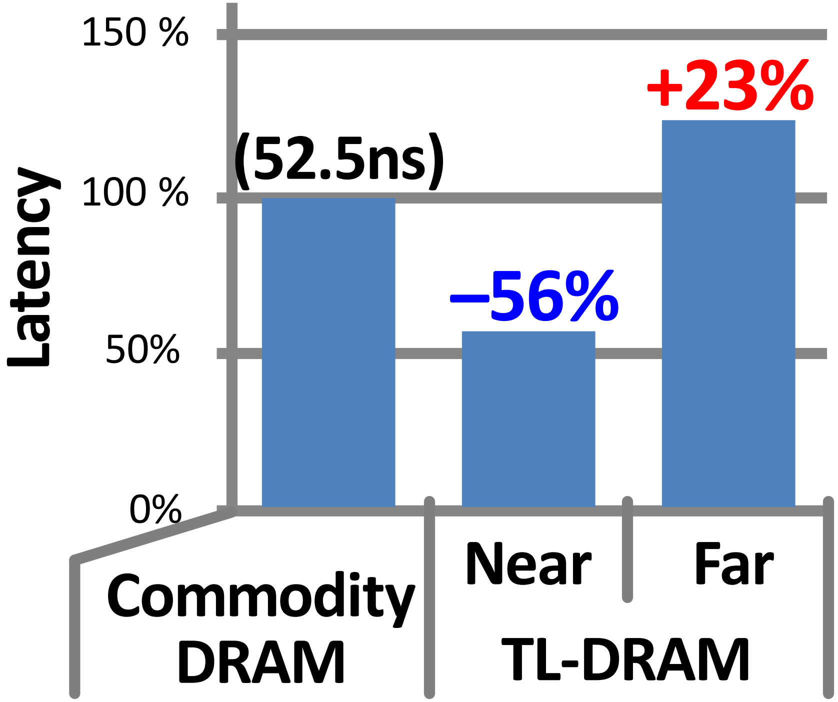
Small Area	*Small Area*	~~*Large Area*~~
~~*High Latency*~~	*Low Latency*	*Low Latency*

Small area using long bitline

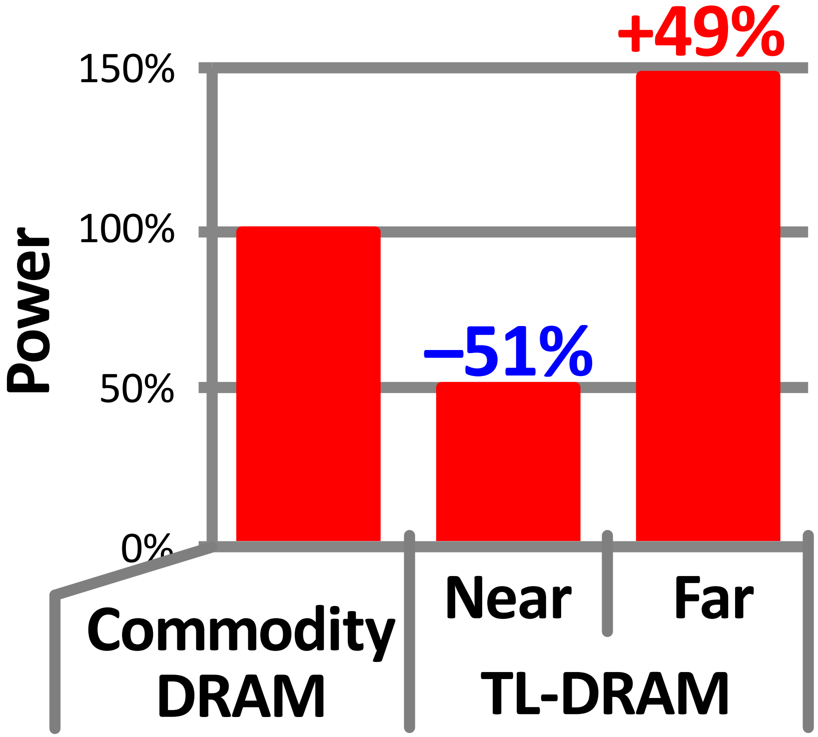
Low Latency

Commodity DRAM vs. TL-DRAM [HPCA 2013]

- **DRAM Latency** (tRC)

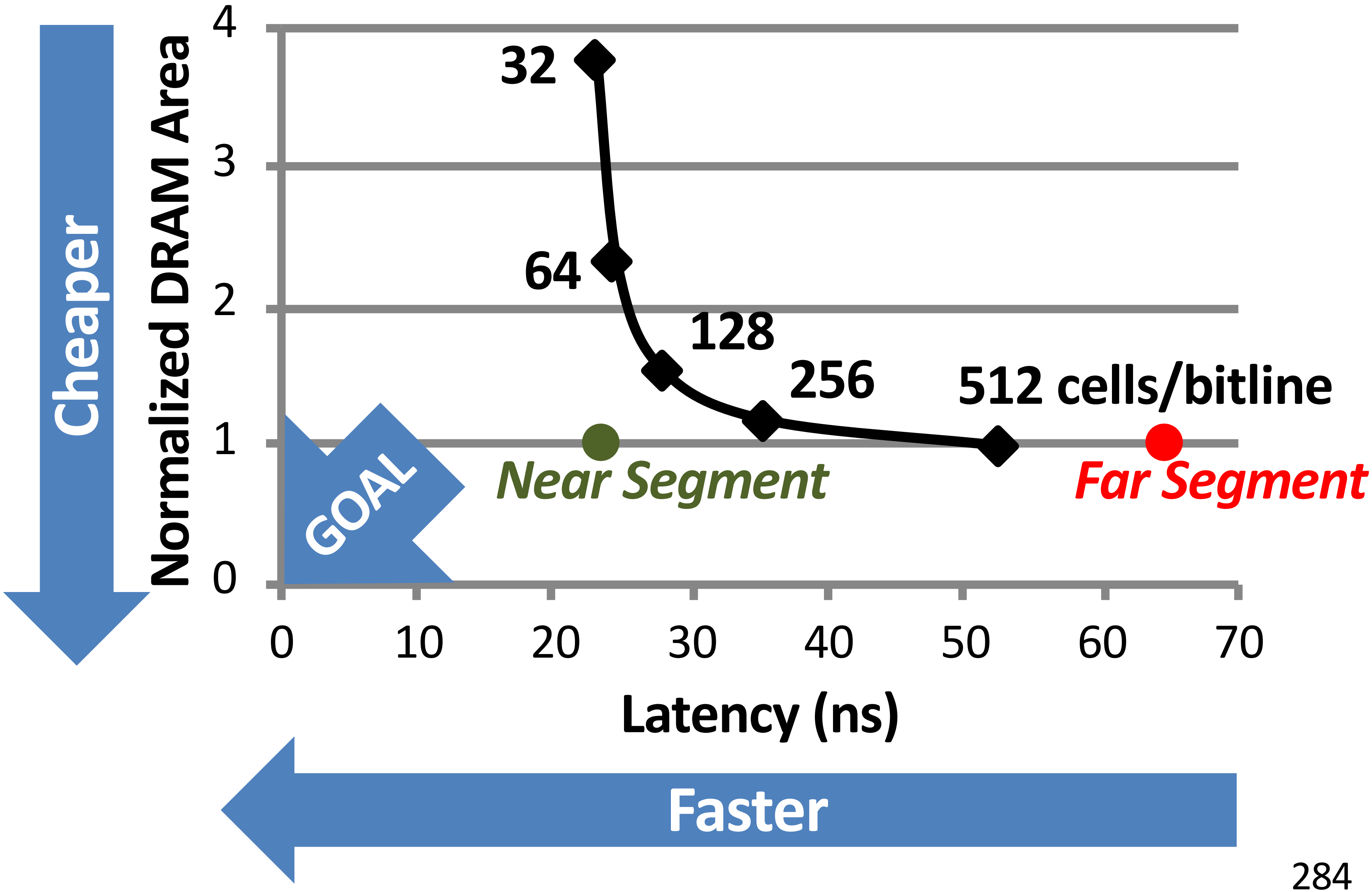


- **DRAM Power**



- **DRAM Area Overhead**
  - **~3%**: mainly due to the isolation transistors

Trade-Off: Area (Die-Area) vs. Latency



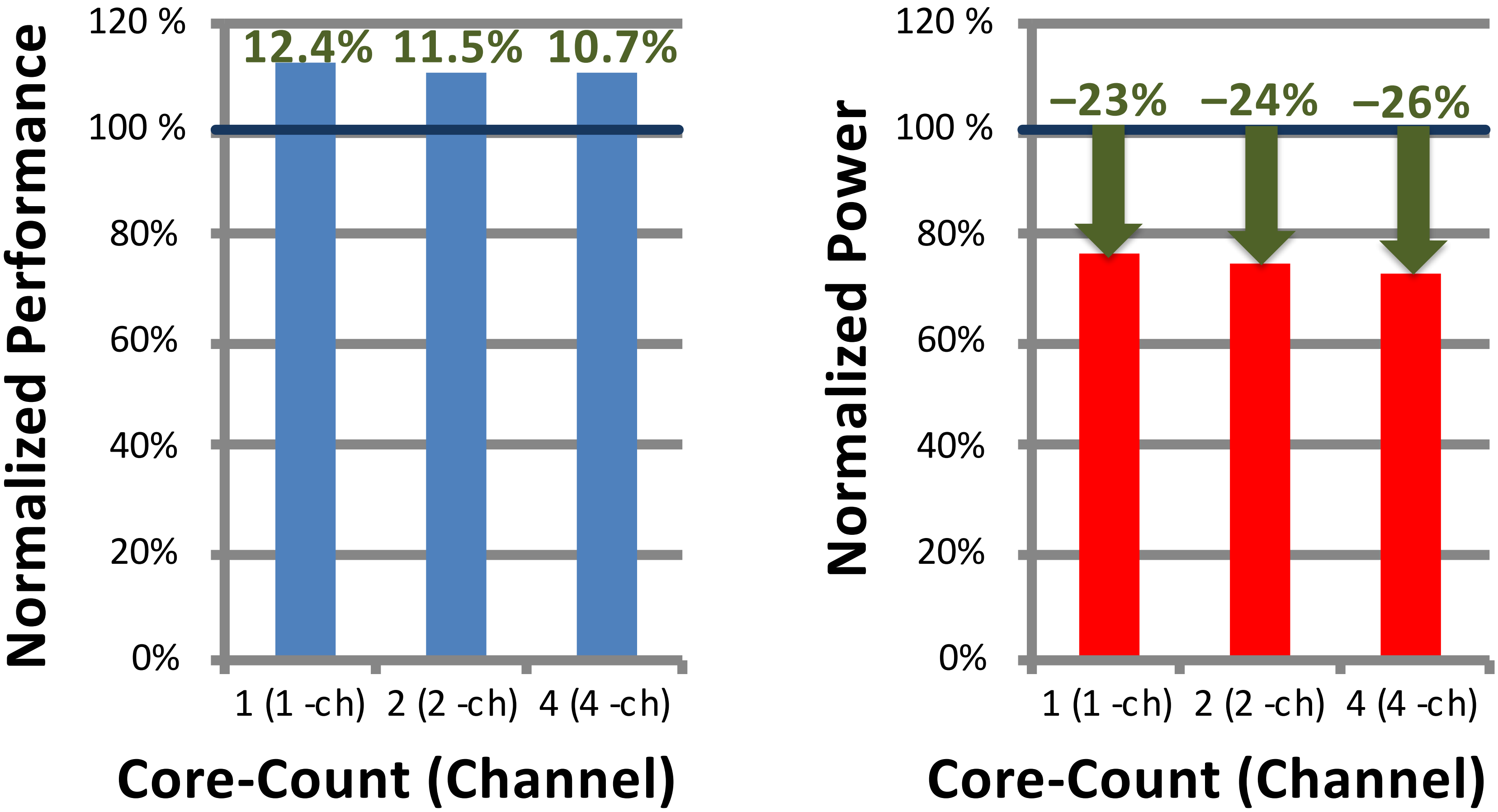
Leveraging Tiered-Latency DRAM

- TL-DRAM is a ***substrate*** that can be leveraged by the hardware and/or software

- Many potential uses
  1. Use near segment as hardware-managed ***inclusive*** cache to far segment
  2. Use near segment as hardware-managed ***exclusive*** cache to far segment
  3. Profile-based page mapping by operating system
  4. Simply replace DRAM with TL-DRAM

Lee+, "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.

Performance & Power Consumption



Using near segment as a cache improves performance and reduces power consumption

Lee+, "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.

Challenge and Opportunity for Future

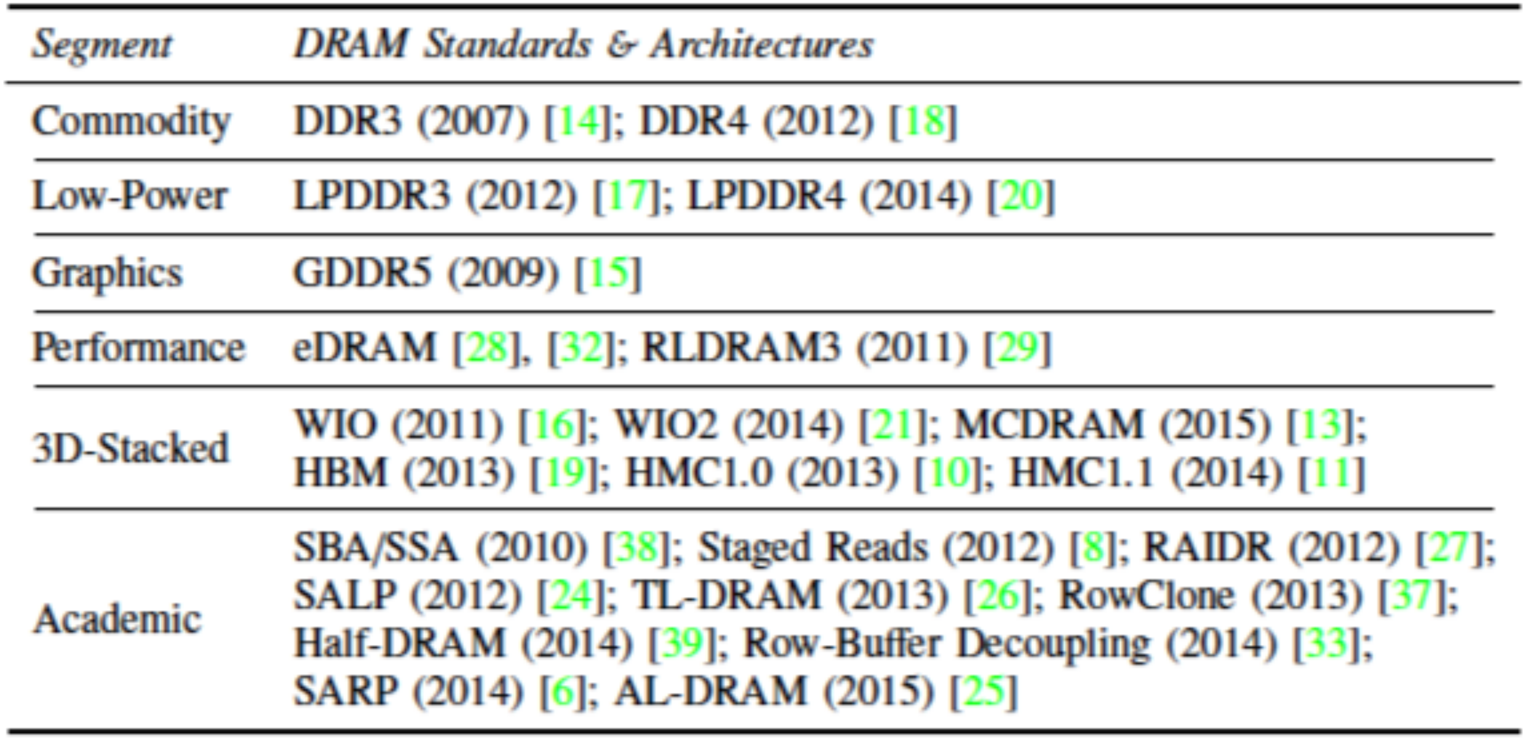
Fundamentally
Low Latency
Computing Architectures

Ramulator: A Fast and Extensible DRAM Simulator

[IEEE Comp Arch Letters'15]

Ramulator Motivation

- DRAM and Memory Controller landscape is changing
- Many new and upcoming standards
- Many new controller designs
- A fast and easy-to-extend simulator is very much needed

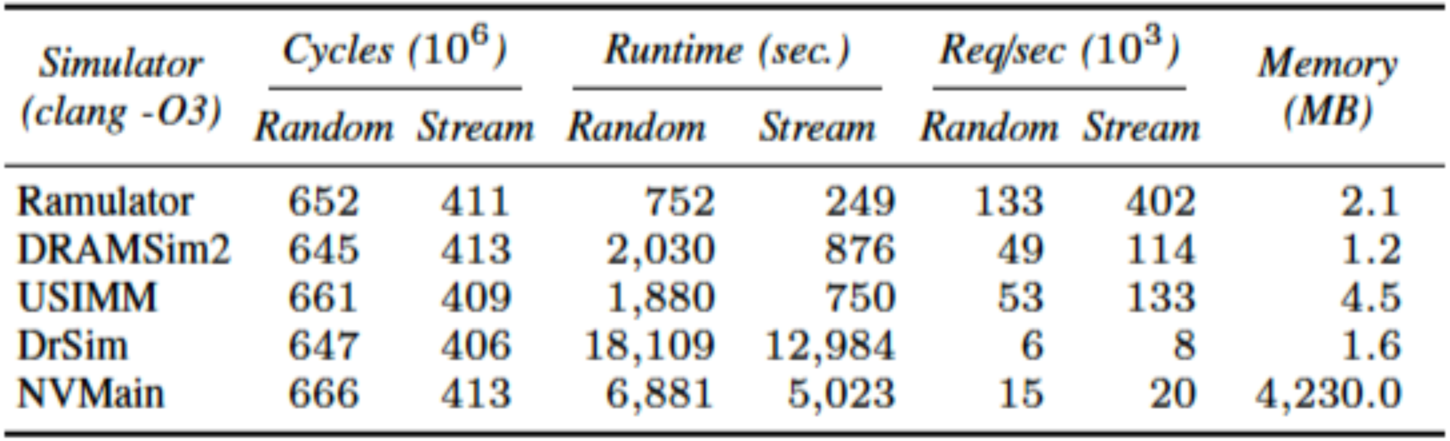


Segment	*DRAM Standards & Architectures*
Commodity	DDR3 (2007) [14]; DDR4 (2012) [18]
Low-Power	LPDDR3 (2012) [17]; LPDDR4 (2014) [20]
Graphics	GDDR5 (2009) [15]
Performance	eDRAM [28], [32]; RLDRAM3 (2011) [29]
3D-Stacked	WIO (2011) [16]; WIO2 (2014) [21]; MCDRAM (2015) [13]; HBM (2013) [19]; HMC1.0 (2013) [10]; HMC1.1 (2014) [11]
Academic	SBA/SSA (2010) [38]; Staged Reads (2012) [8]; RAIDR (2012) [27]; SALP (2012) [24]; TL-DRAM (2013) [26]; RowClone (2013) [37]; Half-DRAM (2014) [39]; Row-Buffer Decoupling (2014) [33]; SARP (2014) [6]; AL-DRAM (2015) [25]

Table 1. Landscape of DRAM-based memory

Ramulator

- Provides out-of-the box support for many DRAM standards:
  - DDR3/4, LPDDR3/4, GDDR5, WIO1/2, HBM, plus new proposals (SALP, AL-DRAM, TLDRAM, RowClone, and SARP)
- ~2.5X faster than fastest open-source simulator
- Modular and extensible to different standards



Simulator (clang -O3)	*Cycles (10^6)*		*Runtime (sec.)*		*Req/sec (10^3)*		*Memory (MB)*
	Random	*Stream*	*Random*	*Stream*	*Random*	*Stream*	
Ramulator	652	411	752	249	133	402	2.1
DRAMSim2	645	413	2,030	876	49	114	1.2
USIMM	661	409	1,880	750	53	133	4.5
DrSim	647	406	18,109	12,984	6	8	1.6
NVMain	666	413	6,881	5,023	15	20	4,230.0

Table 3. Comparison of five simulators using two traces

Case Study: Comparison of DRAM Standards

Standard	*Rate (MT/s)*	*Timing (CL-RCD-RP)*	*Data-Bus (Width×Chan.)*	*Rank-per-Chan*	*BW (GB/s)*
DDR3	1,600	11-11-11	64-bit × 1	1	11.9
DDR4	2,400	16-16-16	64-bit × 1	1	17.9
SALP†	1,600	11-11-11	64-bit × 1	1	11.9
LPDDR3	1,600	12-15-15	64-bit × 1	1	11.9
LPDDR4	2,400	22-22-22	32-bit × 2*	1	17.9
GDDR5 [12]	6,000	18-18-18	64-bit × 1	1	44.7
HBM	1,000	7-7-7	128-bit × 8*	1	119.2
WIO	266	7-7-7	128-bit × 4*	1	15.9
WIO2	1,066	9-10-10	128-bit × 8*	1	127.2

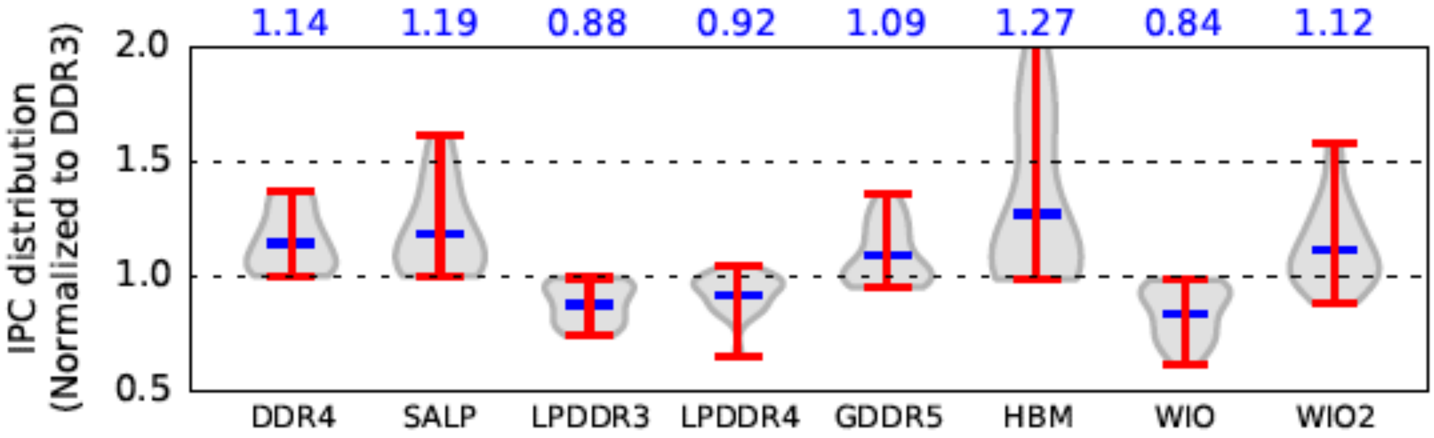


Figure 2. Performance comparison of DRAM standards

Across 22 workloads, simple CPU model

Ramulator Paper and Source Code

- Yoongu Kim, Weikun Yang, and Onur Mutlu, **"Ramulator: A Fast and Extensible DRAM Simulator"** *IEEE Computer Architecture Letters* (***CAL***), March 2015. [Source Code]

- Source code is released under the liberal MIT License
  - https://github.com/CMU-SAFARI/ramulator

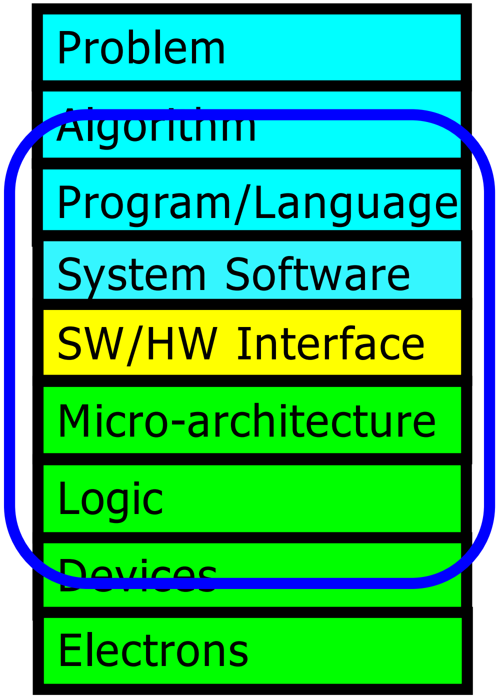
A Deeper Dive into DRAM Reliability Issues

There are Two Other Solution Directions

- **New Technologies:** Replace or (more likely) augment DRAM with a different technology
  - Non-volatile memories

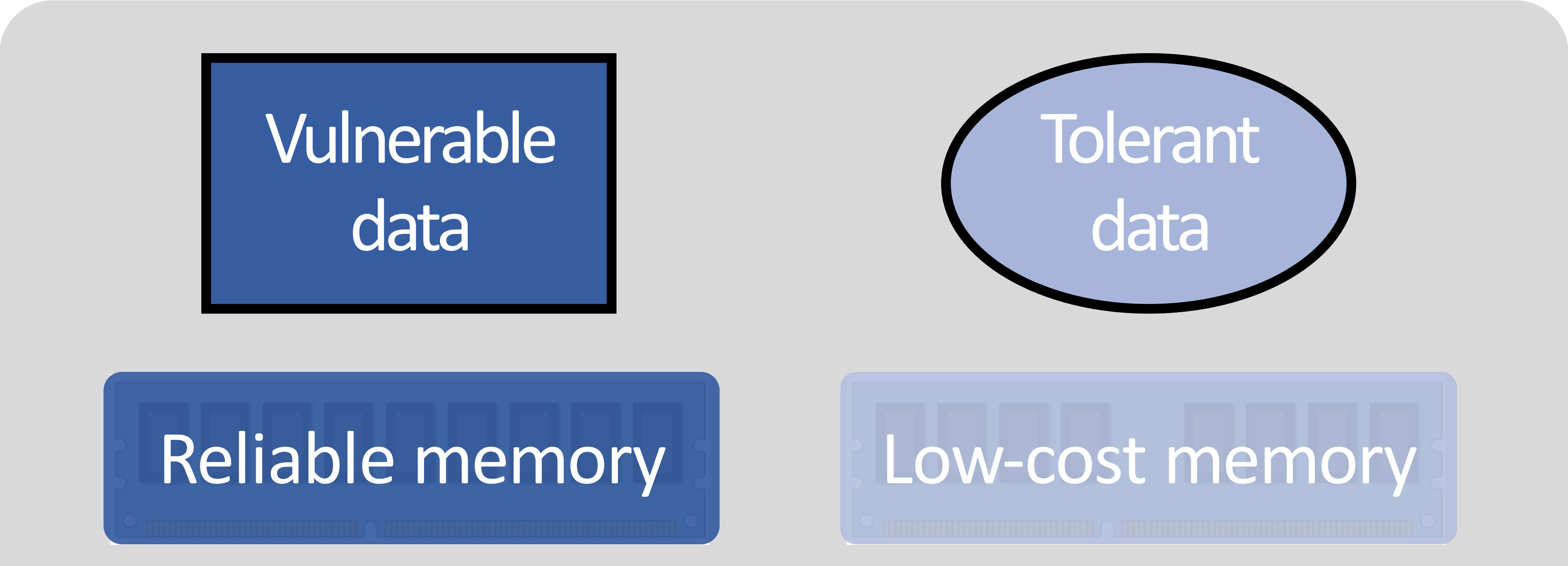
- **Embracing Un-reliability:** Design memories with different reliability and store data intelligently across them

- …



Fundamental solutions to security require co-design across the hierarchy

Exploiting Memory Error Tolerance with Hybrid Memory Systems



On Microsoft's Web Search workload

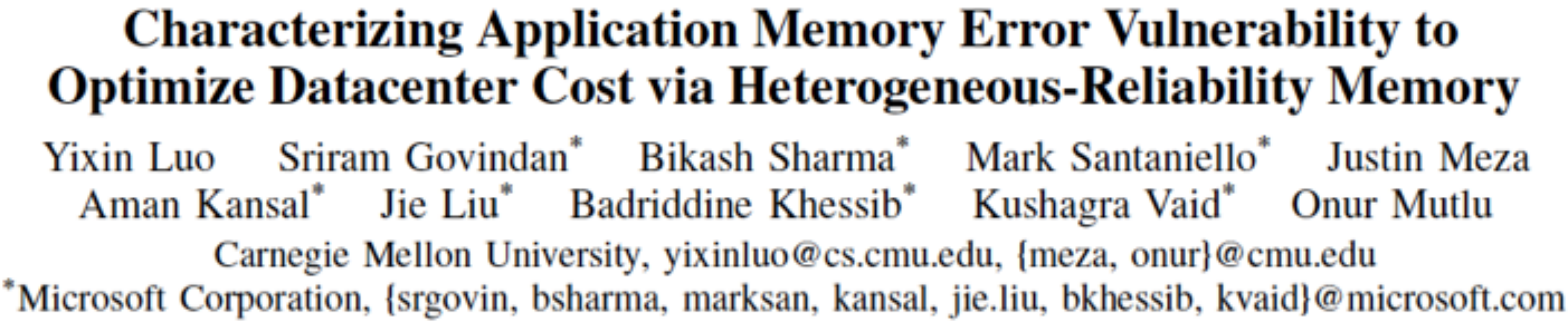
Reduces server hardware cost by 4.7 %

Achieves single server availability target of 99.90 %

Heterogeneous-**R**eliability **M**emory **[DSN 2014]**

More on Heterogeneous-Reliability Memory

- Yixin Luo, Sriram Govindan, Bikash Sharma, Mark Santaniello, Justin Meza, Aman Kansal, Jie Liu, Badriddine Khessib, Kushagra Vaid, and Onur Mutlu, **"Characterizing Application Memory Error Vulnerability to Optimize Data Center Cost via Heterogeneous-Reliability Memory"** *Proceedings of the 44th Annual IEEE/IFIP International Conference on Dependable Systems and Networks* (***DSN***), Atlanta, GA, June 2014. [Summary] [Slides (pptx) (pdf)] [Coverage on ZDNet]



Characterizing Application Memory Error Vulnerability to Optimize Datacenter Cost via Heterogeneous-Reliability Memory

Yixin Luo Sriram Govindan* Bikash Sharma* Mark Santaniello* Justin Meza
Aman Kansal* Jie Liu* Badriddine Khessib* Kushagra Vaid* Onur Mutlu
Carnegie Mellon University, yixinluo@cs.cmu.edu, {meza, onur}@cmu.edu
*Microsoft Corporation, {srgovin, bsharma, marksan, kansal, jie.liu, bkhessib, kvaid}@microsoft.com

Root Causes of Disturbance Errors

- *Cause 1: Electromagnetic coupling*
  - Toggling the wordline voltage briefly increases the voltage of adjacent wordlines
  - Slightly opens adjacent rows → Charge leakage
- *Cause 2: Conductive bridges*
- *Cause 3: Hot-carrier injection*

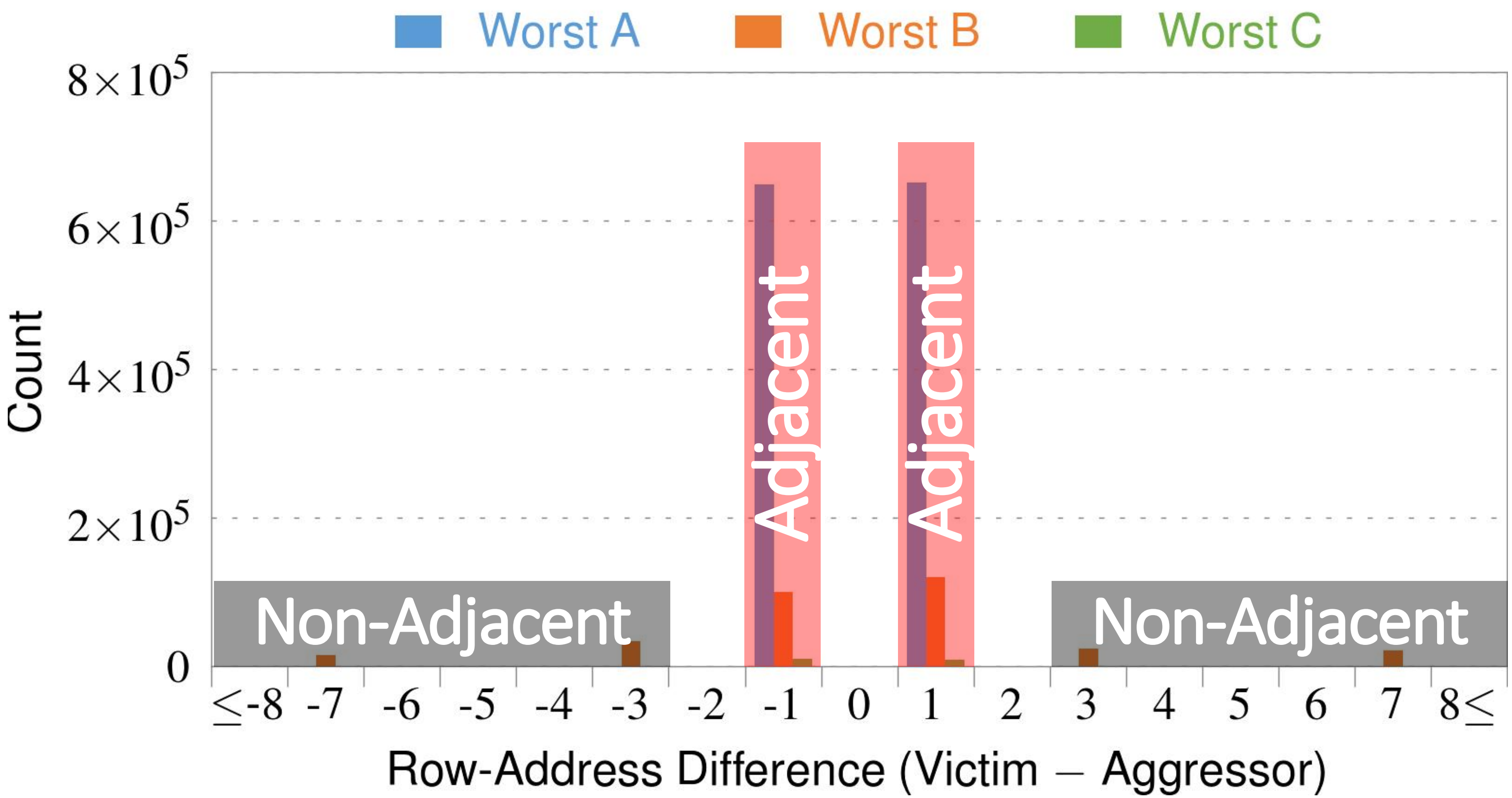
Confirmed by at least one manufacturer

RowHammer Characterization Results

1. Most Modules Are at Risk
2. Errors vs. Vintage
3. Error = Charge Loss
4. Adjacency: Aggressor & Victim
5. Sensitivity Studies
6. Other Results in Paper
7. Solution Space

Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors, (Kim et al., ISCA 2014)

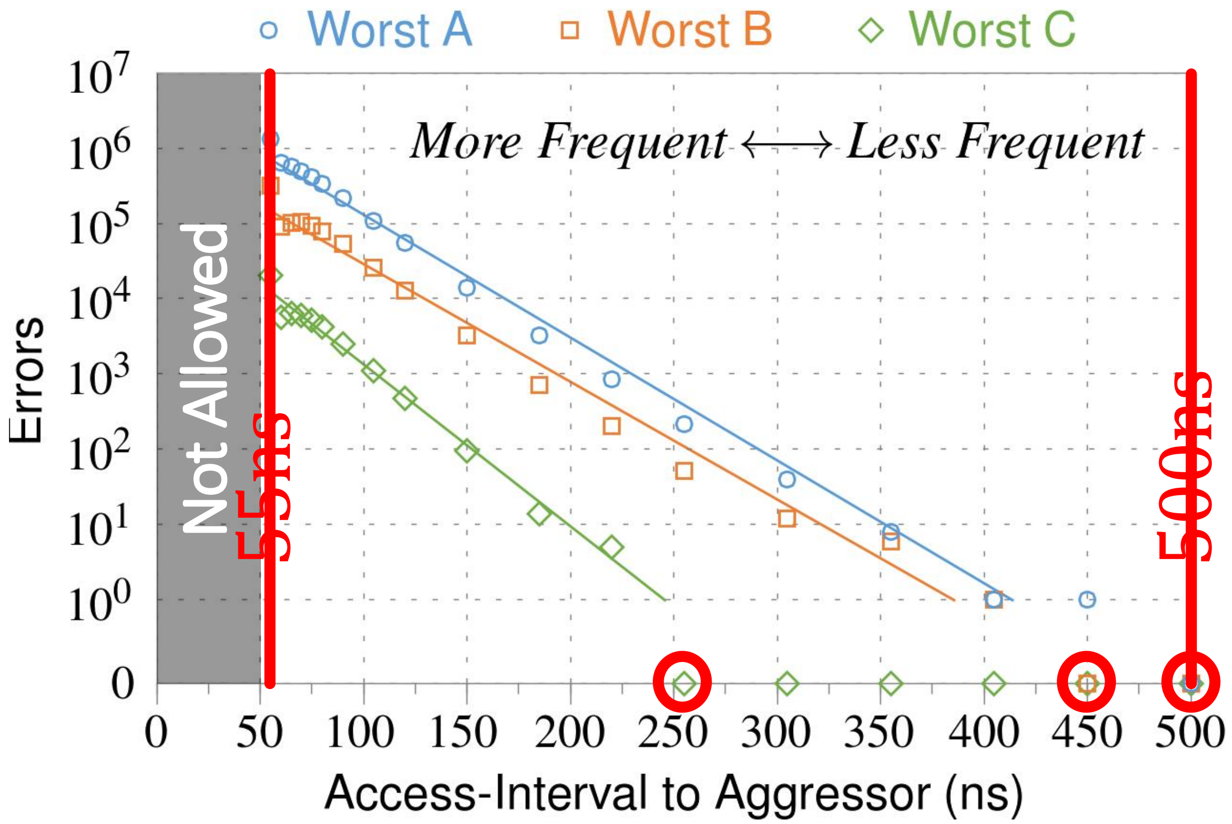
4. Adjacency: Aggressor & Victim



Note: For three modules with the most errors (only first bank)

Most aggressors & victims are adjacent

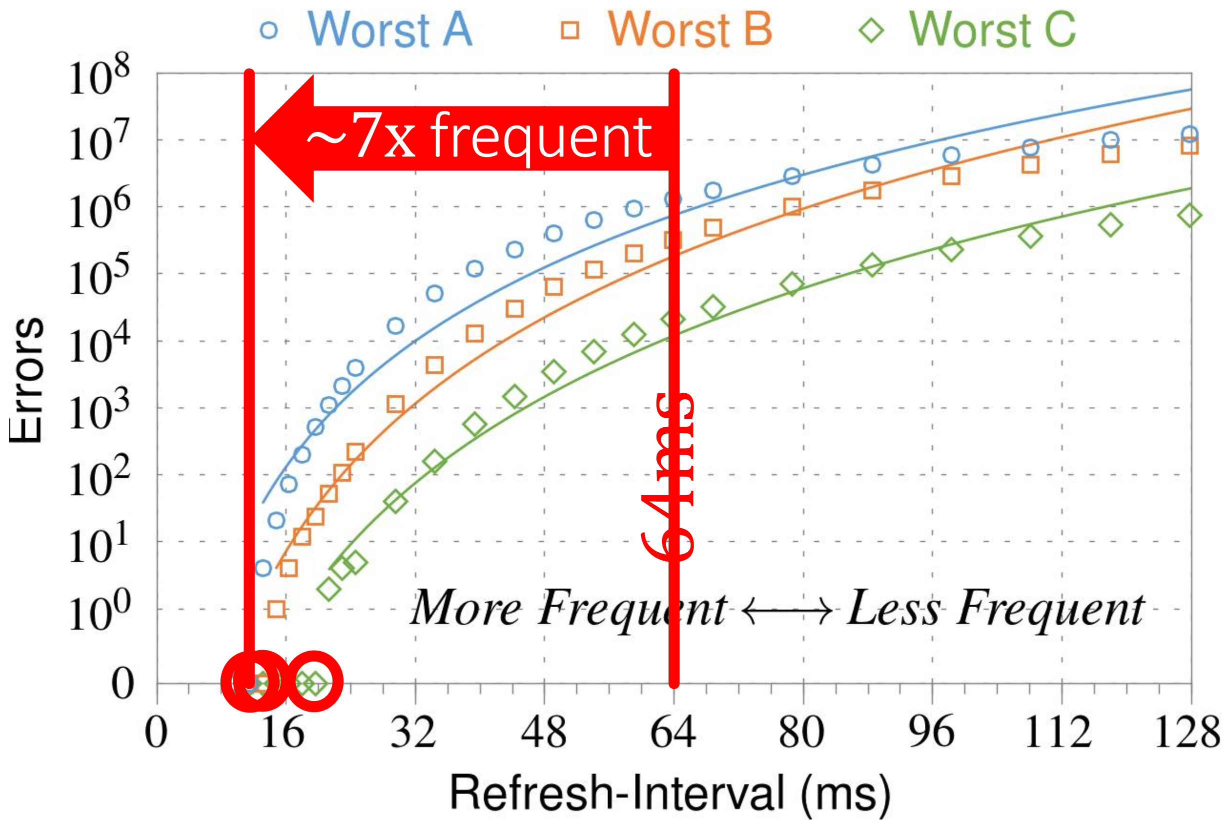
❶ Access Interval (Aggressor)



Note: For three modules with the most errors (only first bank)

Less frequent accesses → Fewer errors

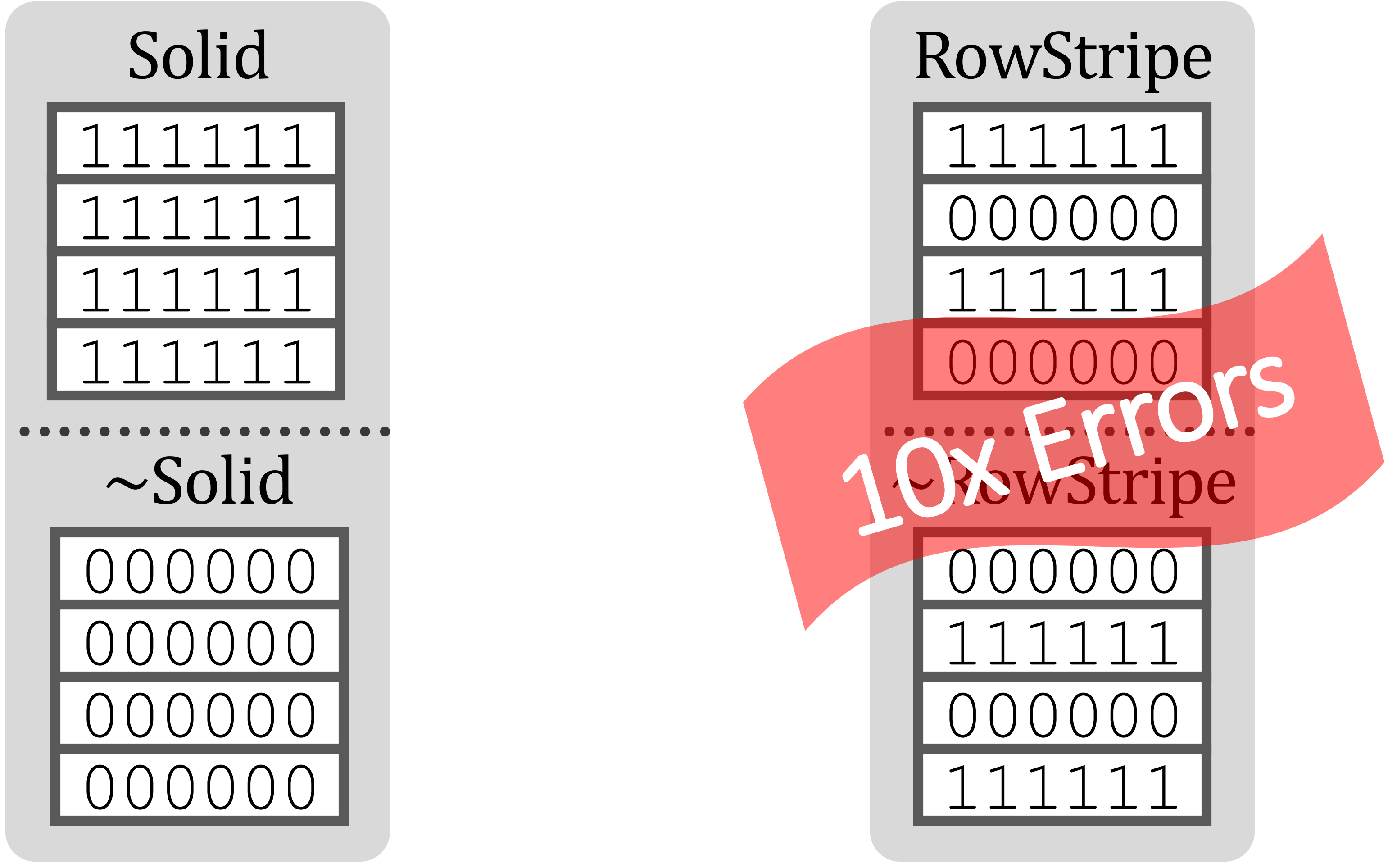
❷ Refresh Interval



Note: Using three modules with the most errors (only first bank)

More frequent refreshes → Fewer errors

③ Data Pattern



Solid

111111
111111
111111
111111

~Solid

000000
000000
000000
000000

RowStripe

111111
000000
111111
000000

~RowStripe

000000
111111
000000
111111

10x Errors

Errors affected by data stored in other cells

6. Other Results (in Paper)

- *Victim Cells ≠ Weak Cells (i.e., leaky cells)*
  - Almost no overlap between them
- *Errors not strongly affected by temperature*
  - Default temperature: 50°C
  - At 30°C and 70°C, number of errors changes <15%
- *Errors are repeatable*
  - Across ten iterations of testing, >70% of victim cells had errors in every iteration

6. Other Results (in Paper) cont'd

- *As many as 4 errors per cache-line*
  - Simple ECC (e.g., SECDED) cannot prevent all errors

- *Number of cells & rows affected by aggressor*
  - Victims cells per aggressor: ≤ 110
  - Victims rows per aggressor: ≤ 9

- *Cells affected by two aggressors on either side*
  - Very small fraction of victim cells (<100) have an error when either one of the aggressors is toggled

Some Potential Solutions

• Make better DRAM chips	Cost
• Refresh frequently	Power, Performance
• Sophisticated ECC	Cost, Power
• Access counters	Cost, Power, Complexity

Naive Solutions

❶ *Throttle accesses to same row*

- Limit access-interval: $\geq 500\text{ns}$
- Limit number of accesses: $\leq 128\text{K}$ $(=64\text{ms}/500\text{ns})$

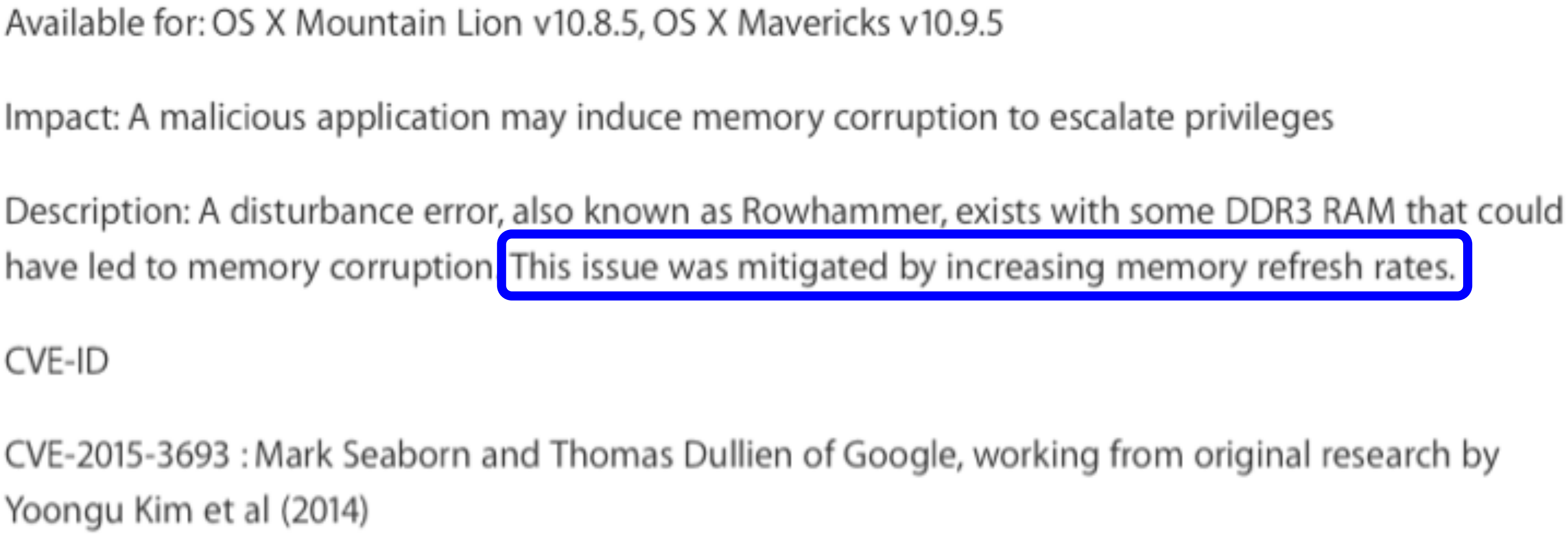
❷ *Refresh more frequently*

- Shorten refresh-interval by $\sim 7\text{x}$

Both naive solutions introduce significant overhead in performance and power

Apple's Patch for RowHammer

- https://support.apple.com/en-gb/HT204934



Available for: OS X Mountain Lion v10.8.5, OS X Mavericks v10.9.5

Impact: A malicious application may induce memory corruption to escalate privileges

Description: A disturbance error, also known as Rowhammer, exists with some DDR3 RAM that could have led to memory corruption. This issue was mitigated by increasing memory refresh rates.

CVE-ID

CVE-2015-3693 : Mark Seaborn and Thomas Dullien of Google, working from original research by Yoongu Kim et al (2014)

HP and Lenovo released similar patches

Our Solution to RowHammer

- PARA: *Probabilistic Adjacent Row Activation*

- Key Idea
  - After closing a row, we activate (i.e., refresh) one of its neighbors with a low probability: $p = 0.005$

- Reliability Guarantee
  - When $p=0.005$, errors in one year: 9.4×10^{-14}
  - By adjusting the value of p, we can vary the strength of protection against errors

Advantages of PARA

- *PARA refreshes rows infrequently*
  - Low power
  - Low performance-overhead
    - Average slowdown: 0.20% (for 29 benchmarks)
    - Maximum slowdown: 0.75%
- *PARA is stateless*
  - Low cost
  - Low complexity

- *PARA is an effective and low-overhead solution to prevent disturbance errors*

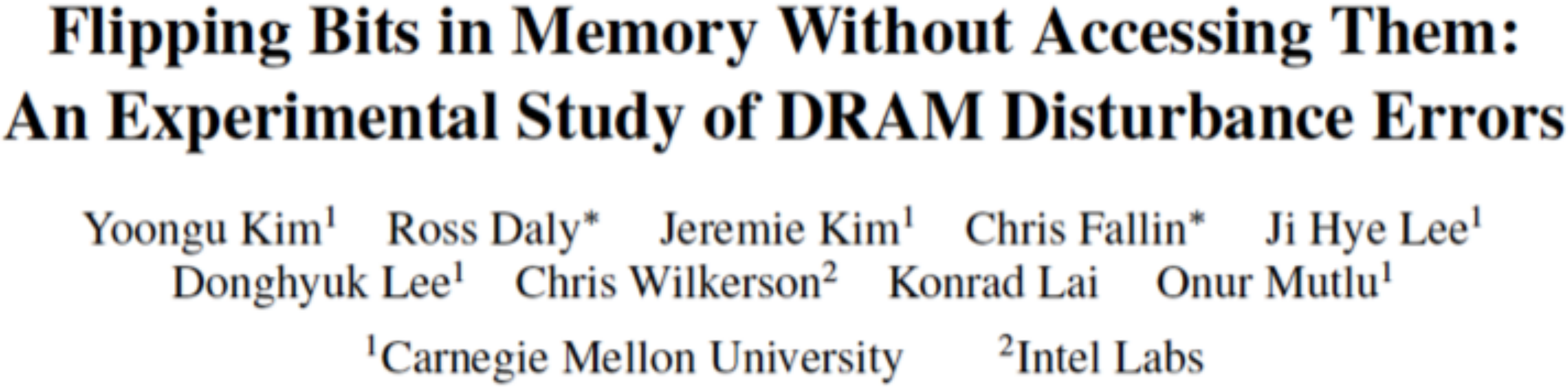
Requirements for PARA

- If implemented in DRAM chip
  - Enough slack in timing parameters
  - Plenty of slack today:
    - Lee et al., "**Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common Case**," HPCA 2015.
    - Chang et al., "**Understanding Latency Variation in Modern DRAM Chips**," SIGMETRICS 2016.
    - Lee et al., "**Design-Induced Latency Variation in Modern DRAM Chips**," SIGMETRICS 2017.
    - Chang et al., "**Understanding Reduced-Voltage Operation in Modern DRAM Devices**," SIGMETRICS 2017.

- If implemented in memory controller
  - Better coordination between memory controller and DRAM
  - Memory controller should know which rows are physically adjacent

More on RowHammer Analysis

- Yoongu Kim, Ross Daly, Jeremie Kim, Chris Fallin, Ji Hye Lee, Donghyuk Lee, Chris Wilkerson, Konrad Lai, and Onur Mutlu,
"Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors"
Proceedings of the 41st International Symposium on Computer Architecture (***ISCA***), Minneapolis, MN, June 2014.
[Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)] [Source Code and Data]



Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors

Yoongu Kim[1] Ross Daly* Jeremie Kim[1] Chris Fallin* Ji Hye Lee[1]
Donghyuk Lee[1] Chris Wilkerson[2] Konrad Lai Onur Mutlu[1]
[1]Carnegie Mellon University [2]Intel Labs

Retrospective on RowHammer & Future

- Onur Mutlu,
  "The RowHammer Problem and Other Issues We May Face as Memory Becomes Denser"
  Invited Paper in Proceedings of the Design, Automation, and Test in Europe Conference (***DATE***), Lausanne, Switzerland, March 2017.
  [Slides (pptx) (pdf)]

The RowHammer Problem
and Other Issues We May Face as Memory Becomes Denser

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https://people.inf.ethz.ch/omutlu/pub/rowhammer-and-other-memory-issues_date17.pdf

Challenge and Opportunity for Future

Fundamentally

Secure, Reliable, Safe

Computing Architectures

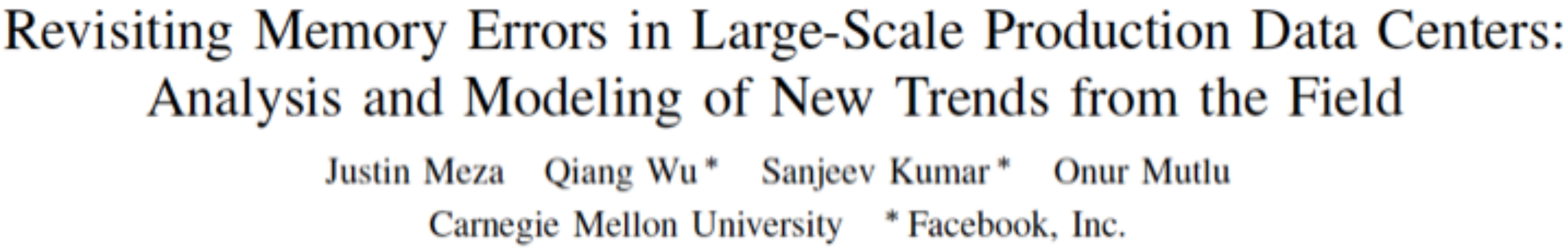
Future of Main Memory

- DRAM is becoming less reliable → more vulnerable

Large-Scale Failure Analysis of DRAM Chips

- Analysis and modeling of memory errors found in all of Facebook's server fleet

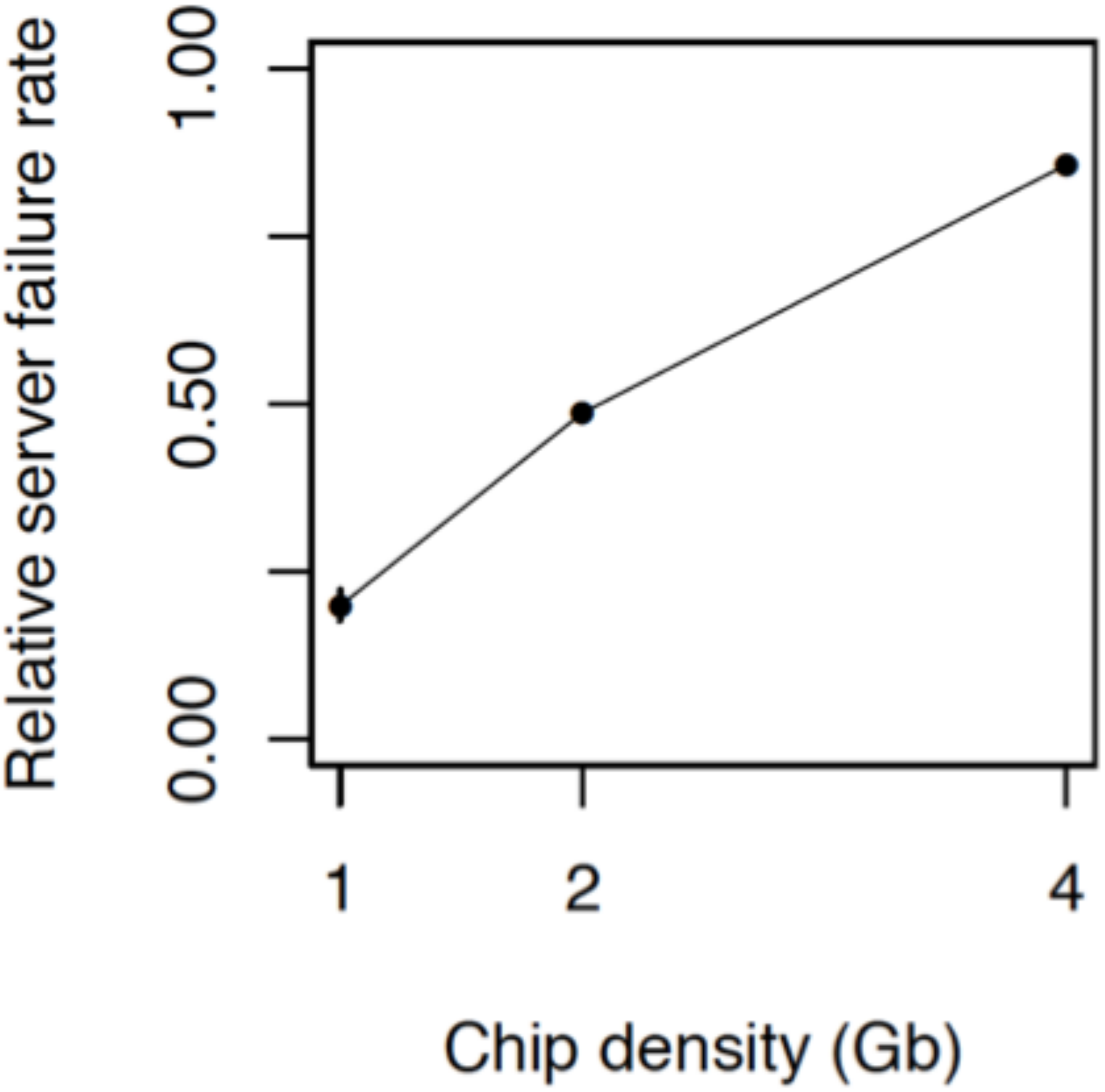
- Justin Meza, Qiang Wu, Sanjeev Kumar, and Onur Mutlu, **"Revisiting Memory Errors in Large-Scale Production Data Centers: Analysis and Modeling of New Trends from the Field"** *Proceedings of the 45th Annual IEEE/IFIP International Conference on Dependable Systems and Networks (**DSN**)*, Rio de Janeiro, Brazil, June 2015.
  [Slides (pptx) (pdf)] [DRAM Error Model]



Revisiting Memory Errors in Large-Scale Production Data Centers: Analysis and Modeling of New Trends from the Field

Justin Meza Qiang Wu * Sanjeev Kumar * Onur Mutlu
Carnegie Mellon University * Facebook, Inc.

DRAM Reliability Reducing



Intuition: quadratic increase in capacity

Aside: SSD Error Analysis in the Field

- First large-scale field study of flash memory errors
- Justin Meza, Qiang Wu, Sanjeev Kumar, and Onur Mutlu, **"A Large-Scale Study of Flash Memory Errors in the Field"** *Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems* (***SIGMETRICS***), Portland, OR, June 2015.
  [Slides (pptx) (pdf)] [Coverage at ZDNet]

A Large-Scale Study of Flash Memory Failures in the Field

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Future of Main Memory

- DRAM is becoming less reliable → more vulnerable

- Due to difficulties in DRAM scaling, other problems may also appear (or they may be going unnoticed)

- Some errors may already be slipping into the field
  - Read disturb errors (Rowhammer)
  - Retention errors
  - Read errors, write errors
  - …

- These errors can also pose security vulnerabilities

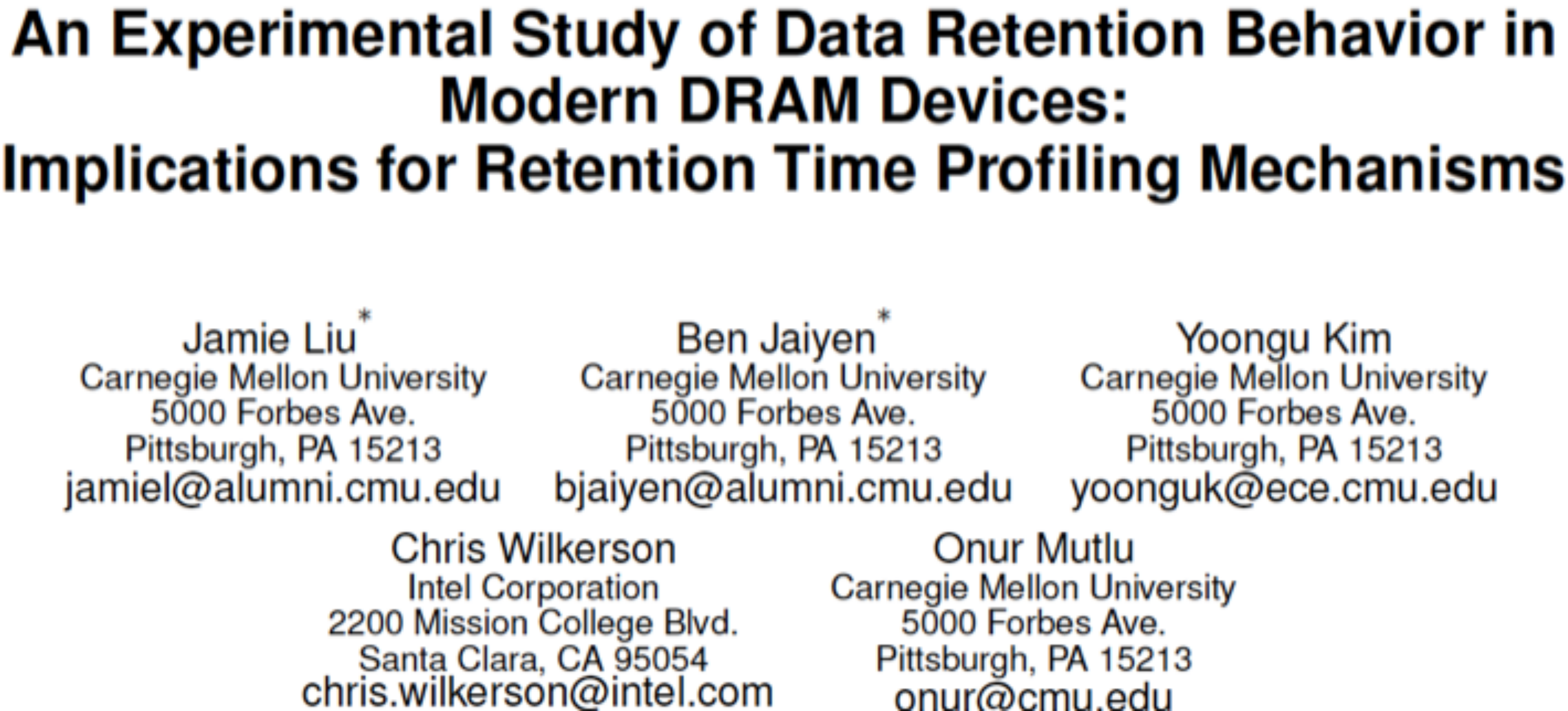
DRAM Data Retention Time Failures

- Determining the data retention time of a cell/row is getting more difficult

- Retention failures may already be slipping into the field

Analysis of Retention Failures **[ISCA'13]**

- Jamie Liu, Ben Jaiyen, Yoongu Kim, Chris Wilkerson, and Onur Mutlu, **"An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms"** *Proceedings of the 40th International Symposium on Computer Architecture (**ISCA**)*, Tel-Aviv, Israel, June 2013. Slides (ppt) Slides (pdf)



An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms

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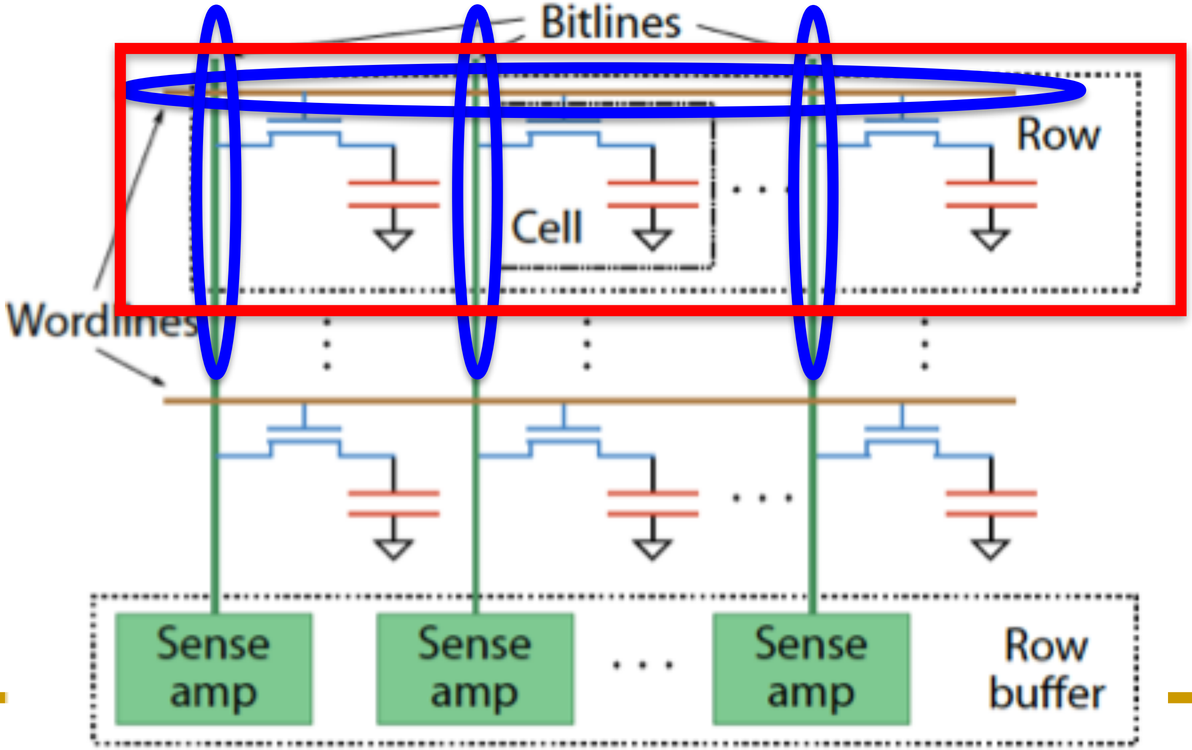
Two Challenges to Retention Time Profiling

- Data Pattern Dependence (DPD) of retention time

- Variable Retention Time (VRT) phenomenon

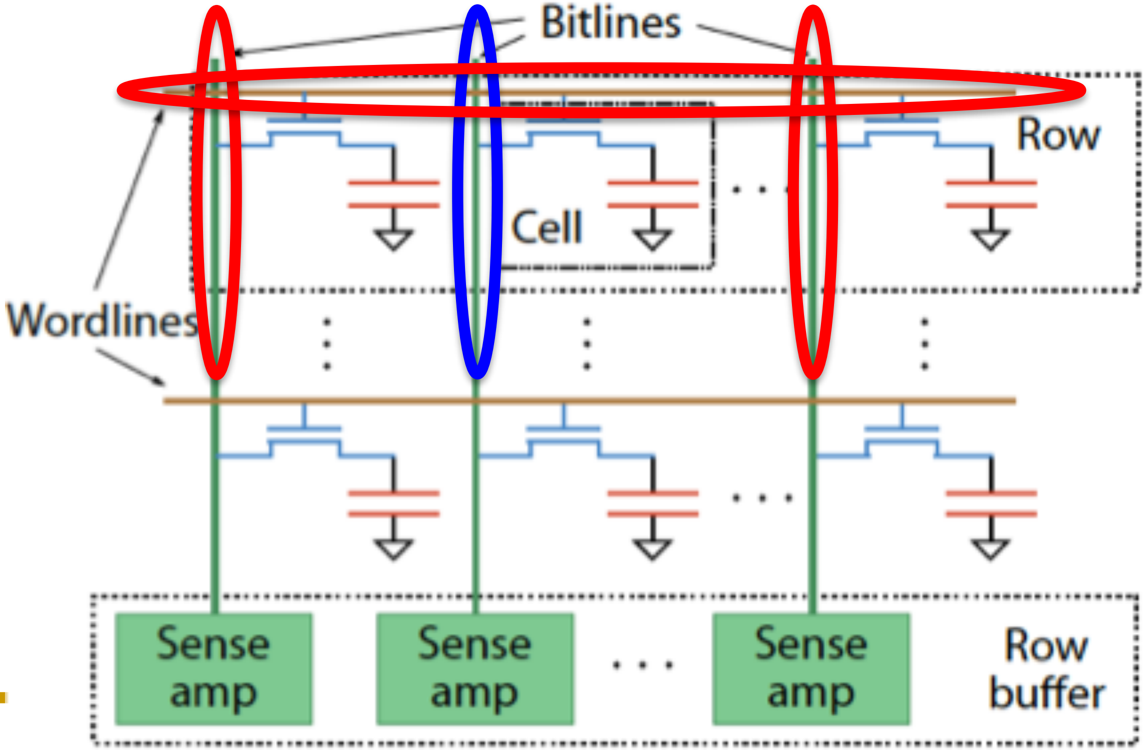
Two Challenges to Retention Time Profiling

- Challenge 1: Data Pattern Dependence (DPD)
  - Retention time of a DRAM cell depends on its value and the values of cells nearby it
  - When a row is activated, all bitlines are perturbed simultaneously



Data Pattern Dependence

- Electrical noise on the bitline affects reliable sensing of a DRAM cell
- The magnitude of this noise is affected by values of nearby cells via
  - Bitline-bitline coupling → electrical coupling between adjacent bitlines
  - Bitline-wordline coupling → electrical coupling between each bitline and the activated wordline



Data Pattern Dependence

- Electrical noise on the bitline affects reliable sensing of a DRAM cell
- The magnitude of this noise is affected by values of nearby cells via
  - Bitline-bitline coupling → electrical coupling between adjacent bitlines
  - Bitline-wordline coupling → electrical coupling between each bitline and the activated wordline

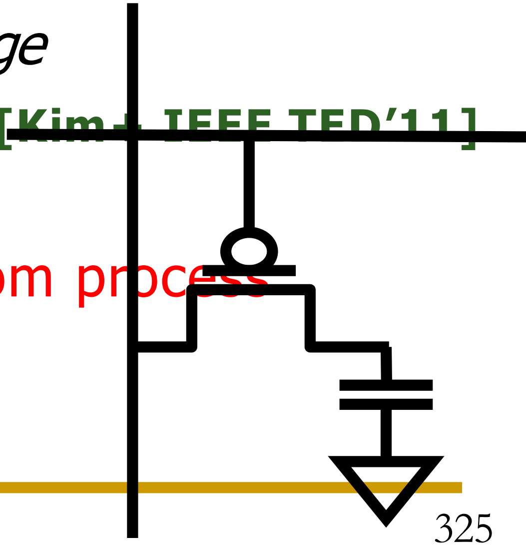
- Retention time of a cell depends on data patterns stored in nearby cells

  → need to find the worst data pattern to find worst-case retention time

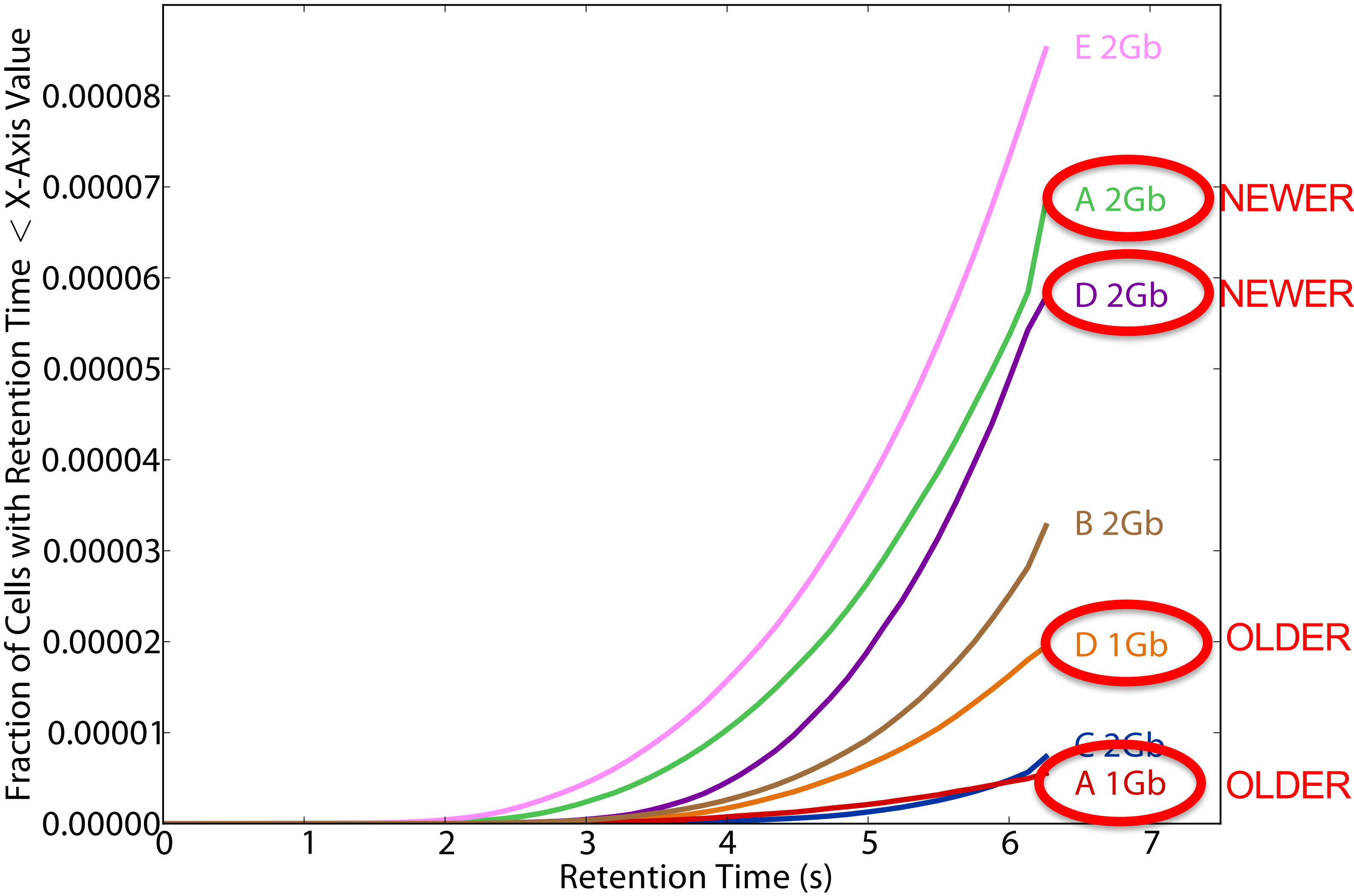
  → this pattern is location dependent

Two Challenges to Retention Time Profiling

- Challenge 2: Variable Retention Time (VRT)
  - Retention time of a DRAM cell changes randomly over time
    - a cell alternates between multiple retention time states
  - Leakage current of a cell changes sporadically due to a charge trap in the gate oxide of the DRAM cell access transistor
  - When the trap becomes occupied, charge leaks more readily from the transistor's drain, leading to a short retention time
    - Called *Trap-Assisted Gate-Induced Drain Leakage*
  - This process appears to be a random process [Kim+ IEEE TED'11]
  - Worst-case retention time depends on a random process → need to find the worst case despite this

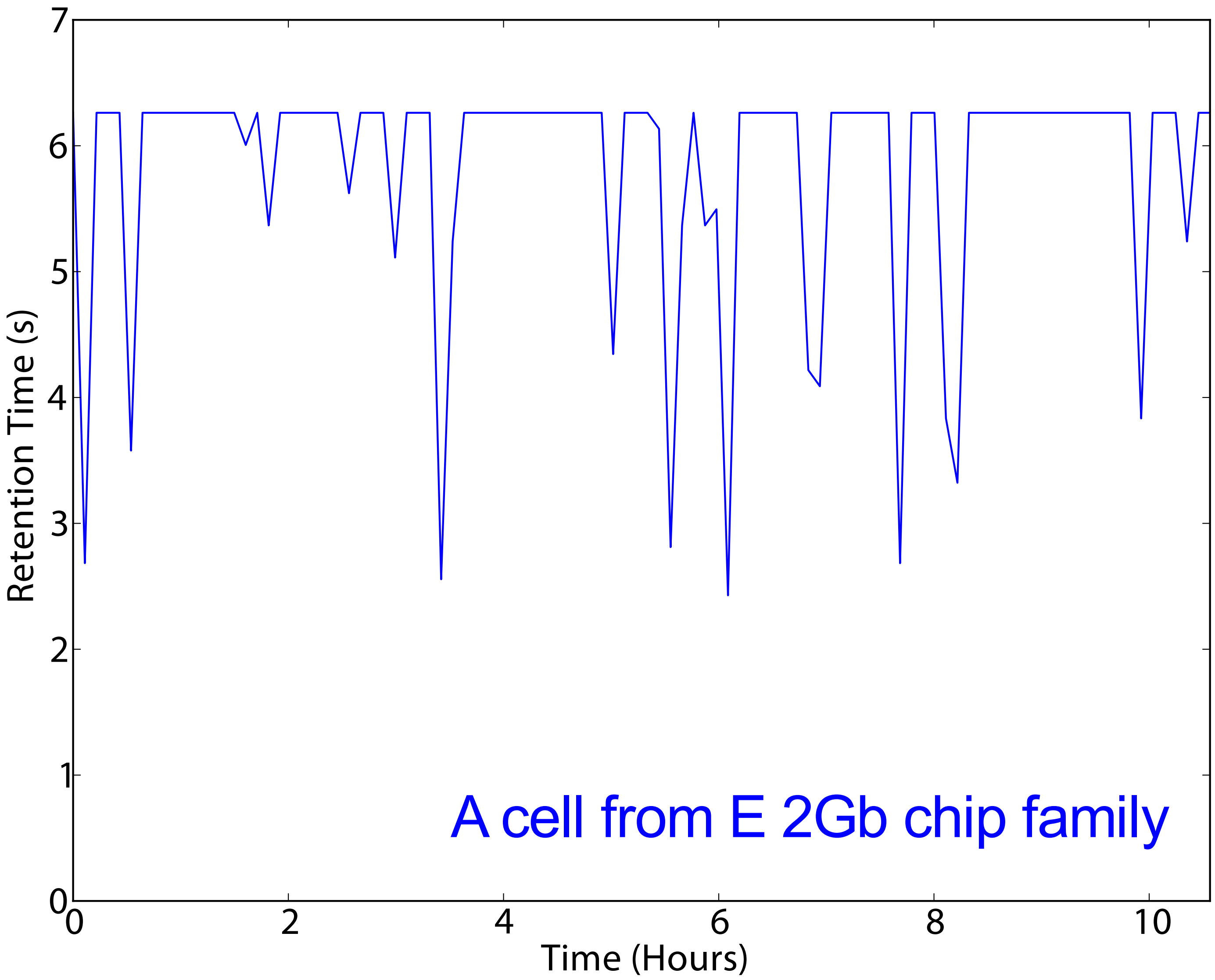


Modern DRAM Retention Time Distribution

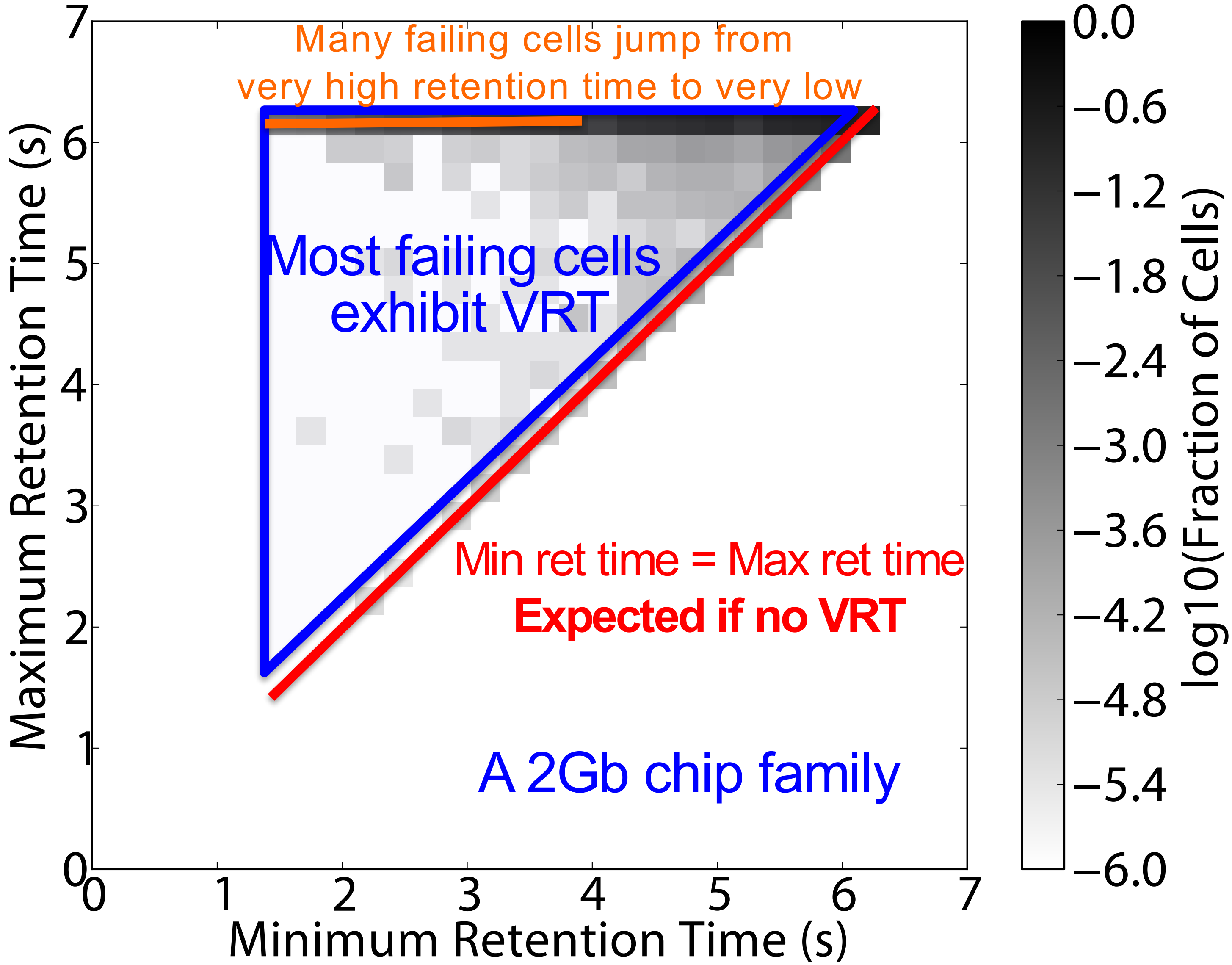


Newer device families have more weak cells than older ones
Likely a result of technology scaling

An Example VRT Cell



Variable Retention Time



Many failing cells jump from very high retention time to very low

Most failing cells exhibit VRT

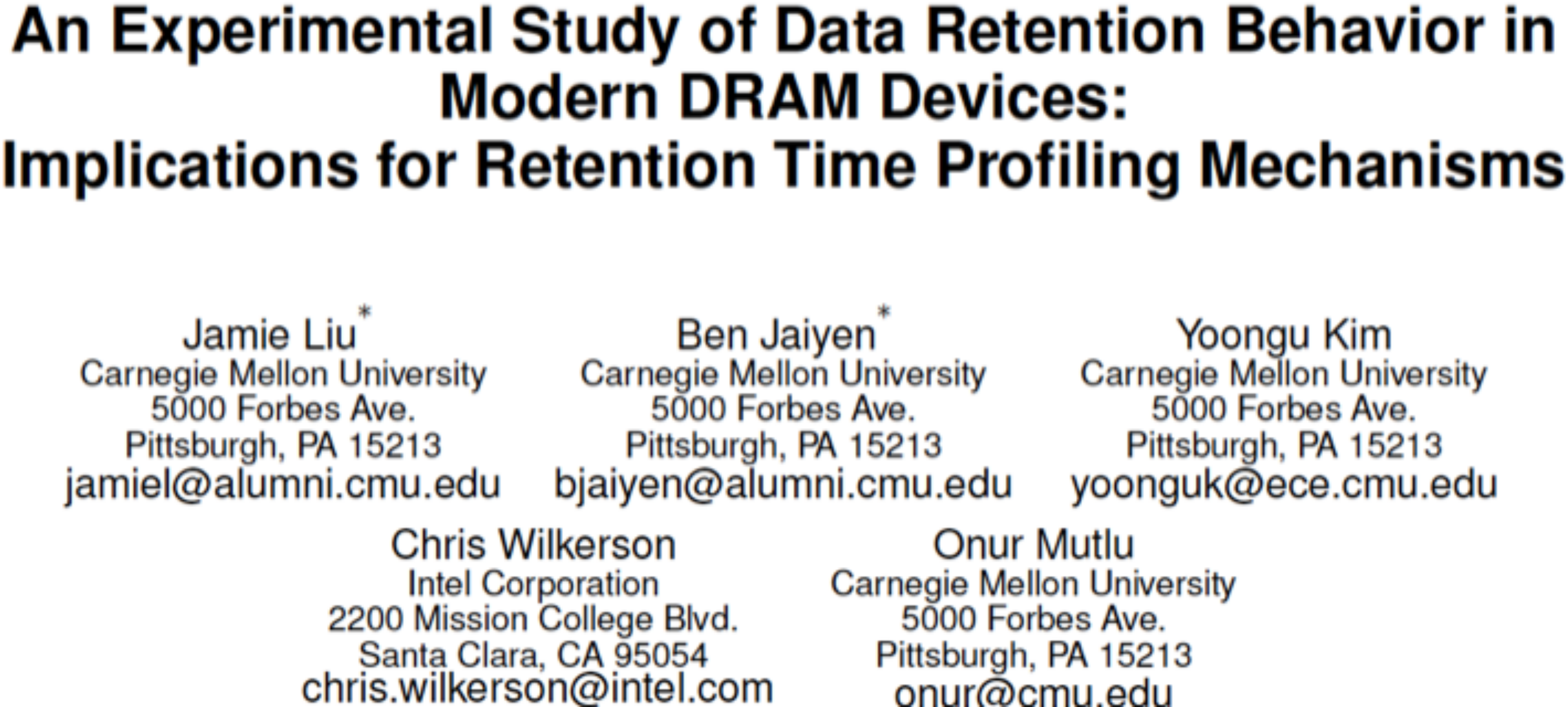
Min ret time = Max ret time

Expected if no VRT

A 2Gb chip family

More on DRAM Retention Analysis

- Jamie Liu, Ben Jaiyen, Yoongu Kim, Chris Wilkerson, and Onur Mutlu, **"An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms"** *Proceedings of the 40th International Symposium on Computer Architecture (**ISCA**)*, Tel-Aviv, Israel, June 2013. Slides (ppt) Slides (pdf)



An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms

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Pittsburgh, PA 15213
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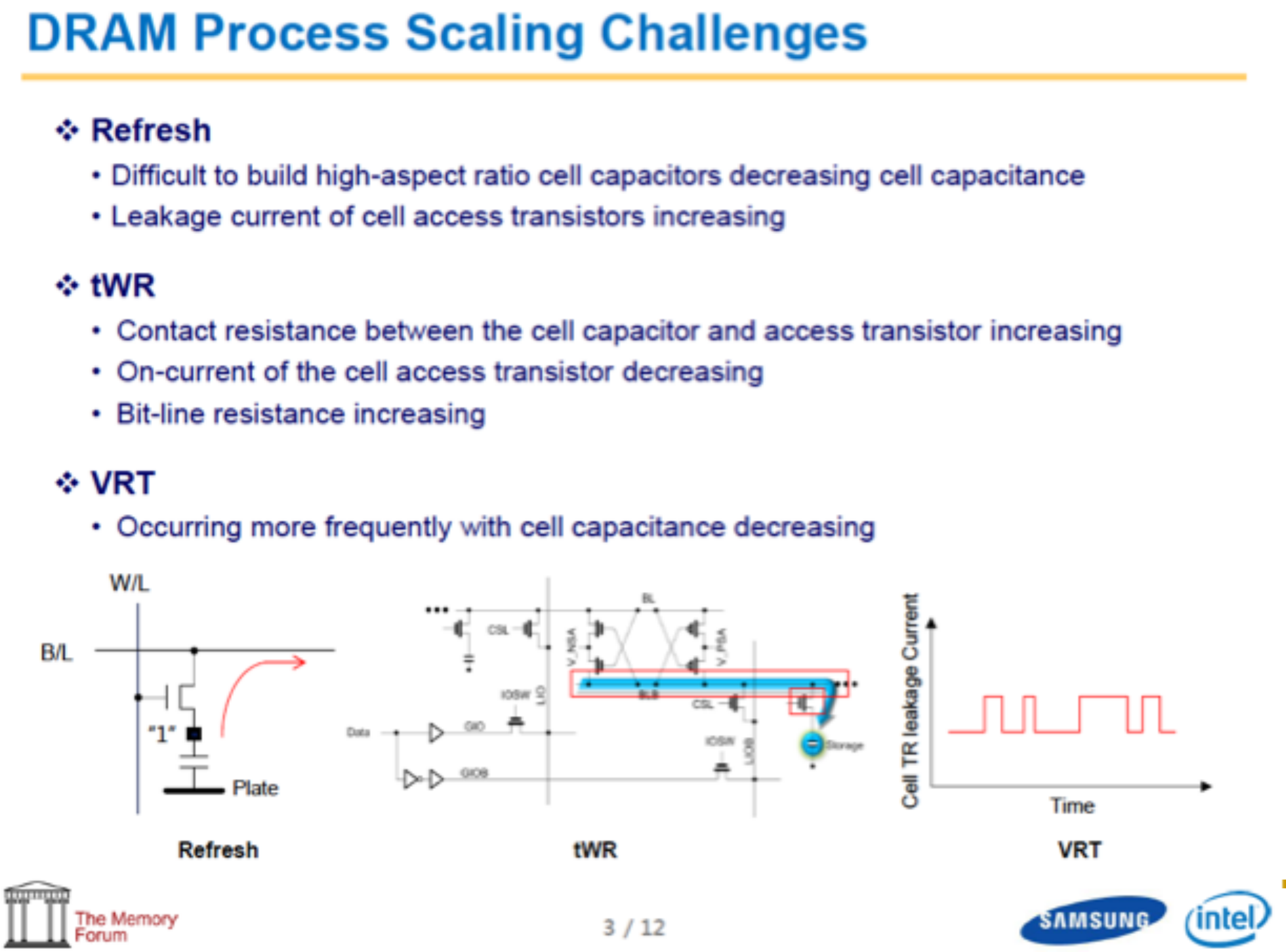
Industry Is Writing Papers About It, Too



DRAM Process Scaling Challenges

- **Refresh**
  - Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance
  - Leakage current of cell access transistors increasing
- **tWR**
  - Contact resistance between the cell capacitor and access transistor increasing
  - On-current of the cell access transistor decreasing
  - Bit-line resistance increasing
- **VRT**
  - Occurring more frequently with cell capacitance decreasing

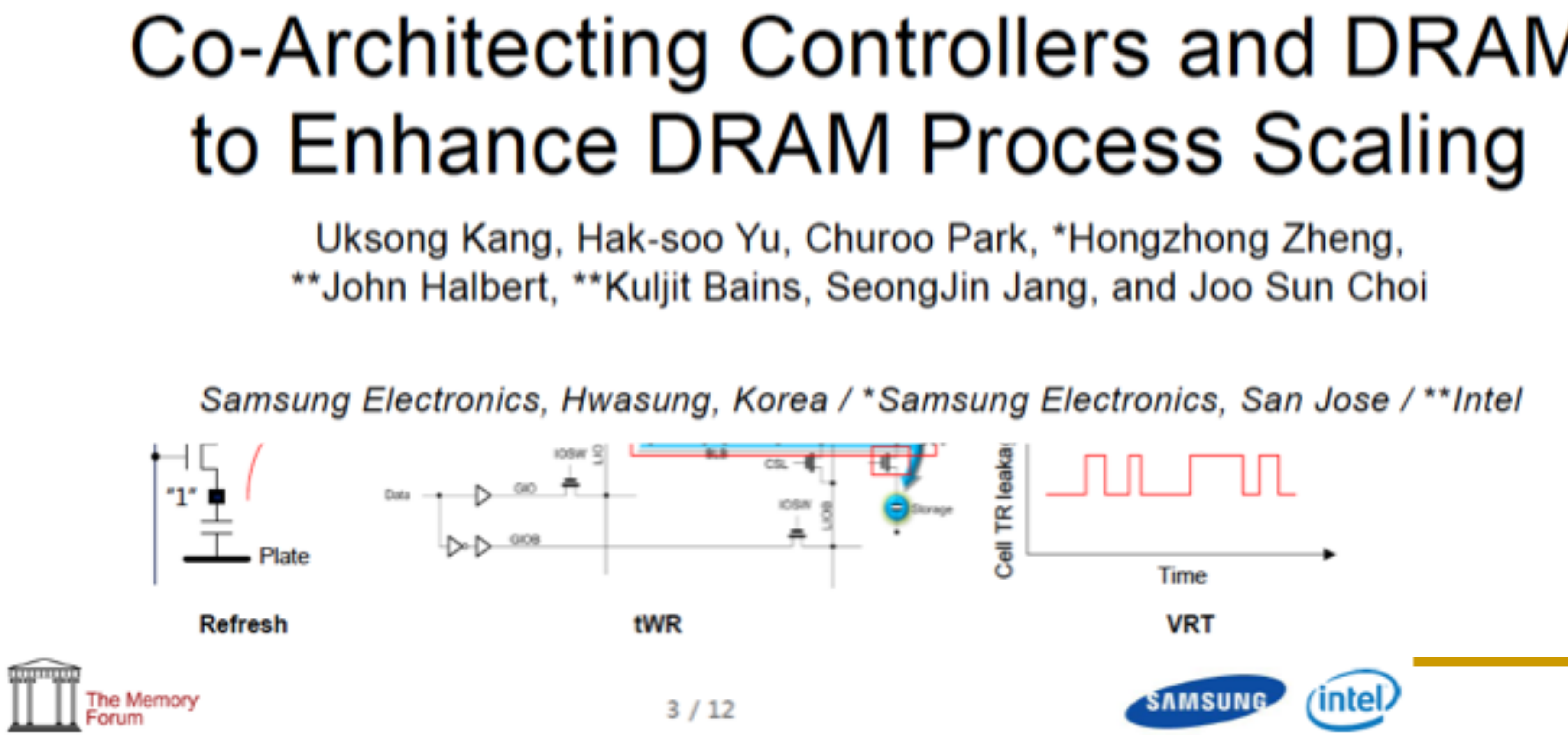
Refresh **tWR** **VRT**

Industry Is Writing Papers About It, Too

DRAM Process Scaling Challenges

- **Refresh**
  - Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance

THE MEMORY FORUM 2014



Co-Architecting Controllers and DRAM to Enhance DRAM Process Scaling

Uksong Kang, Hak-soo Yu, Churoo Park, *Hongzhong Zheng,
**John Halbert, **Kuljit Bains, SeongJin Jang, and Joo Sun Choi

*Samsung Electronics, Hwasung, Korea / *Samsung Electronics, San Jose / **Intel*

3 / 12

Mitigation of Retention Issues [SIGMETRICS'14]

- Samira Khan, Donghyuk Lee, Yoongu Kim, Alaa Alameldeen, Chris Wilkerson, and Onur Mutlu, **"The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study"** *Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (**SIGMETRICS**)*, Austin, TX, June 2014. [Slides (pptx) (pdf)] [Poster (pptx) (pdf)] [Full data sets]

The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study

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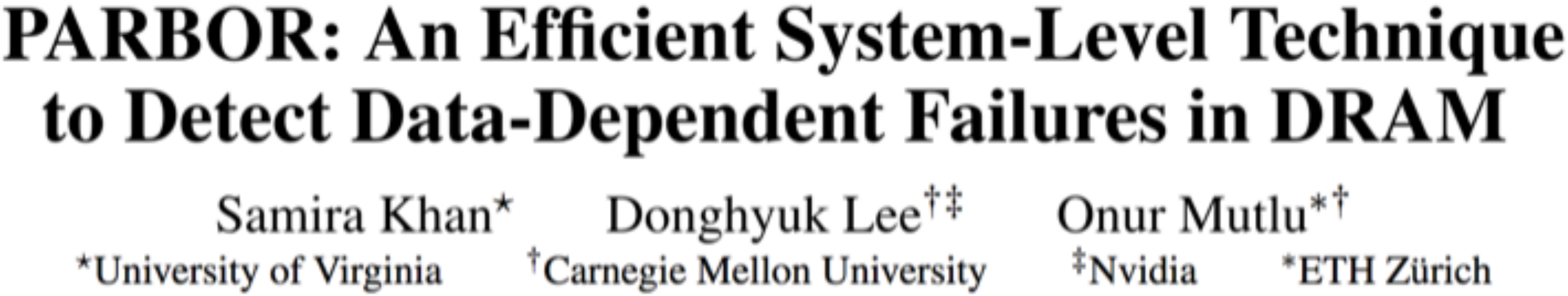
Handling Data-Dependent Failures [DSN'16]

- Samira Khan, Donghyuk Lee, Yoongu Kim, Alaa Alameldeen, Chris Wilkerson, and Onur Mutlu,
  "The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study"
  *Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (**SIGMETRICS**)*, Austin, TX, June 2014. [Slides (pptx) (pdf)] [Poster (pptx) (pdf)] [Full data sets]



PARBOR: An Efficient System-Level Technique to Detect Data-Dependent Failures in DRAM

Samira Khan* Donghyuk Lee†‡ Onur Mutlu*†
*University of Virginia †Carnegie Mellon University ‡Nvidia *ETH Zürich

Handling Data-Dependent Failures [CAL'16]

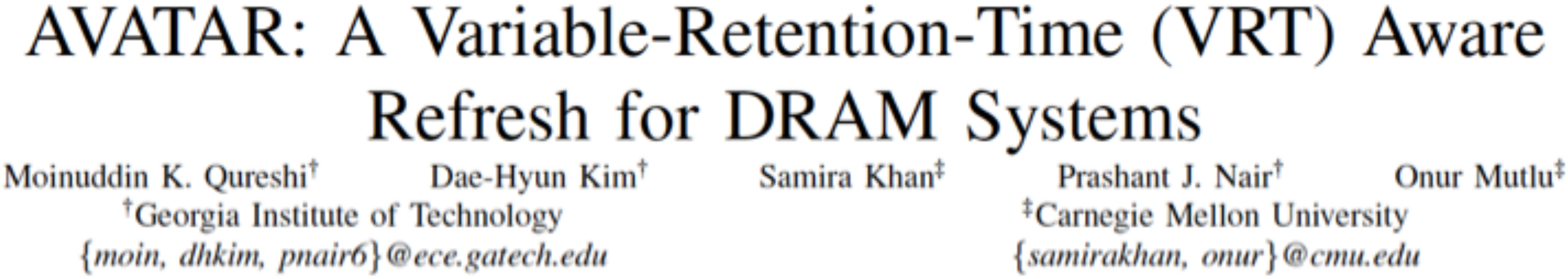
- Samira Khan, Chris Wilkerson, Donghyuk Lee, Alaa R. Alameldeen, and Onur Mutlu,
  "A Case for Memory Content-Based Detection and Mitigation of Data-Dependent Failures in DRAM"
  IEEE Computer Architecture Letters (***CAL***), November 2016.

A Case for Memory Content-Based Detection and Mitigation of Data-Dependent Failures in DRAM

Samira Khan[⋆], Chris Wilkerson[†], Donghyuk Lee[‡], Alaa R. Alameldeen[†], Onur Mutlu[•‡]
[⋆]University of Virginia [†]Intel Labs [‡]Carnegie Mellon University [•]ETH Zürich

Handling Variable Retention Time [DSN'15]

- Moinuddin Qureshi, Dae Hyun Kim, Samira Khan, Prashant Nair, and Onur Mutlu,
  "AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems"
  *Proceedings of the 45th Annual IEEE/IFIP International Conference on Dependable Systems and Networks (**DSN**)*, Rio de Janeiro, Brazil, June 2015.
  [Slides (pptx) (pdf)]



AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems

Moinuddin K. Qureshi[†] Dae-Hyun Kim[†] Samira Khan[‡] Prashant J. Nair[†] Onur Mutlu[‡]

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{moin, dhkim, pnair6}@ece.gatech.edu

[‡]Carnegie Mellon University
{samirakhan, onur}@cmu.edu

Handling Both DPD and VRT [ISCA'17]

- Minesh Patel, Jeremie S. Kim, and Onur Mutlu,
  "The Reach Profiler (REAPER): Enabling the Mitigation of DRAM Retention Failures via Profiling at Aggressive Conditions"
  *Proceedings of the 44th International Symposium on Computer Architecture (**ISCA**)*, Toronto, Canada, June 2017.

- First experimental analysis of (mobile) LPDDR4 chips
- Analyzes the complex tradeoff space of retention time profiling
- Key idea: enable fast and robust profiling at higher refresh intervals & temp.

The Reach Profiler (REAPER):
Enabling the Mitigation of DRAM Retention Failures
via Profiling at Aggressive Conditions

Minesh Patel[§‡] Jeremie S. Kim[‡§] Onur Mutlu[§‡]
[§]ETH Zürich [‡]Carnegie Mellon University

Summary: Memory Reliability and Security

- Memory reliability is reducing
- Reliability issues open up security vulnerabilities
  - Very hard to defend against
- Rowhammer is an example
  - Its implications on system security research are tremendous & exciting

- **Good news: We have a lot more to do.**
- Understand: Solid methodologies for failure modeling and discovery
  - Modeling based on real device data – small scale and large scale
- Architect: Principled co-architecting of system and memory
  - Good partitioning of duties across the stack
- Design & Test: Principled electronic design, automation, testing
  - High coverage and good interaction with system reliability methods

If Time Permits: NAND Flash Vulnerabilities

- Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu, **"Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives"**

  to appear in Proceedings of the IEEE, 2017.

Cai+, "Error Patterns in MLC NAND Flash Memory: Measurement, Characterization, and Analysis," DATE 2012.
Cai+, "Flash Correct-and-Refresh: Retention-Aware Error Management for Increased Flash Memory Lifetime," ICCD 2012.
Cai+, "Threshold Voltage Distribution in MLC NAND Flash Memory: Characterization, Analysis and Modeling," DATE 2013.
Cai+, "Error Analysis and Retention-Aware Error Management for NAND Flash Memory," Intel Technology Journal 2013.
Cai+, "Program Interference in MLC NAND Flash Memory: Characterization, Modeling, and Mitigation," ICCD 2013.
Cai+, "Neighbor-Cell Assisted Error Correction for MLC NAND Flash Memories," SIGMETRICS 2014.
Cai+,"Data Retention in MLC NAND Flash Memory: Characterization, Optimization and Recovery," HPCA 2015.
Cai+, "Read Disturb Errors in MLC NAND Flash Memory: Characterization and Mitigation," DSN 2015.
Luo+, "WARM: Improving NAND Flash Memory Lifetime with Write-hotness Aware Retention Management," MSST 2015.
Meza+, "A Large-Scale Study of Flash Memory Errors in the Field," SIGMETRICS 2015.
Luo+, "Enabling Accurate and Practical Online Flash Channel Modeling for Modern MLC NAND Flash Memory," IEEE JSAC 2016.
Cai+, "Vulnerabilities in MLC NAND Flash Memory Programming: Experimental Analysis, Exploits, and Mitigation Techniques," HPCA 2017.
Fukami+, "Improving the Reliability of Chip-Off Forensic Analysis of NAND Flash Memory Devices," DFRWS EU 2017.

Cai+, "Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives," Proc. IEEE 2017.

Overview Paper on Flash Reliability

- Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu,
  "Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives"
  to appear in Proceedings of the IEEE, 2017.

Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives

Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu

Challenge and Opportunity for Future

Fundamentally
Secure, Reliable, Safe
Computing Architectures

NAND Flash Memory Reliability and Security

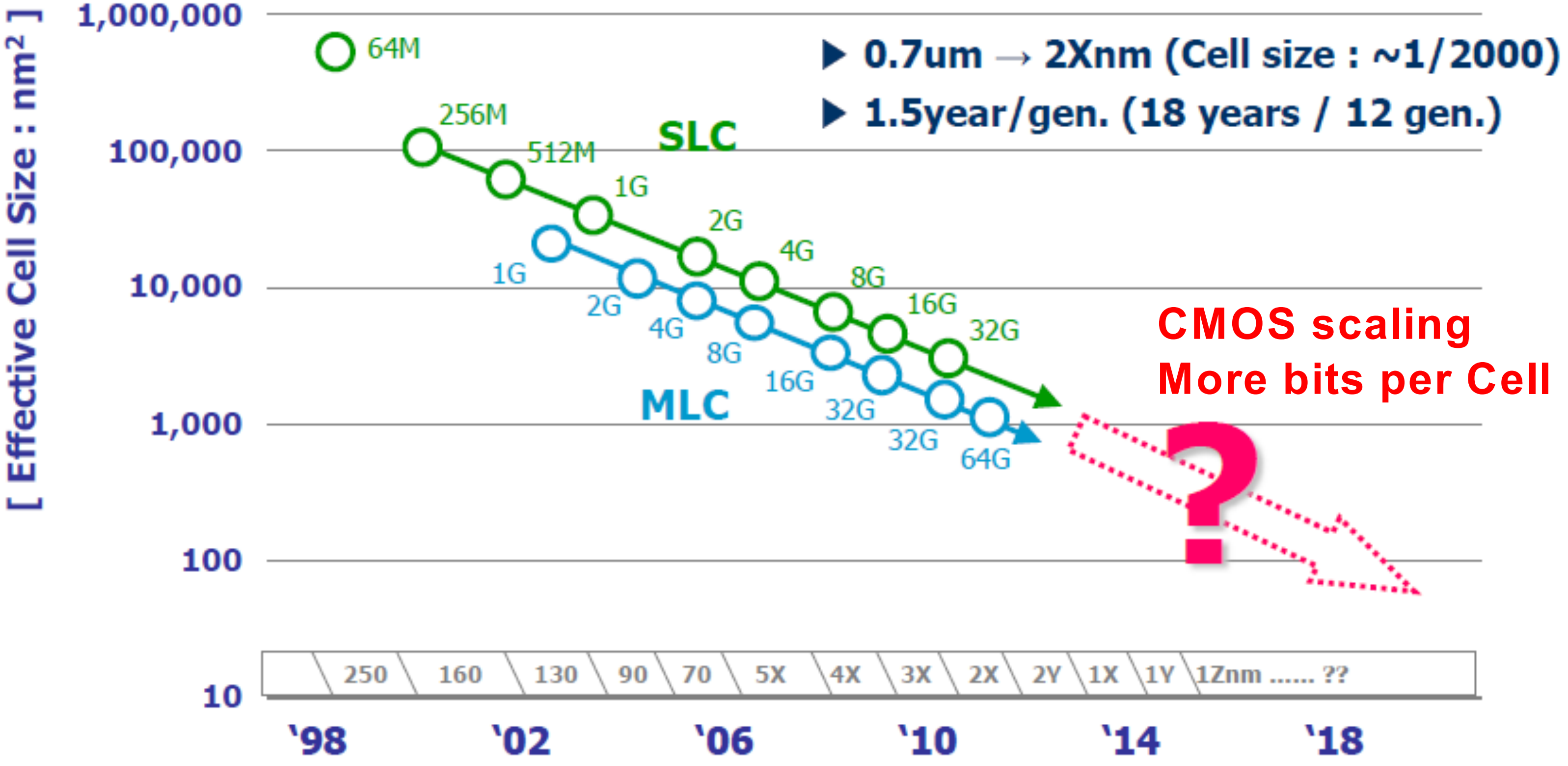
Upcoming Overview Paper

- Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu,
  "Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives"
  to appear in Proceedings of the IEEE, 2017.

Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives

Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu

Evolution of NAND Flash Memory



▶ 0.7um → 2Xnm (Cell size : ~1/2000)

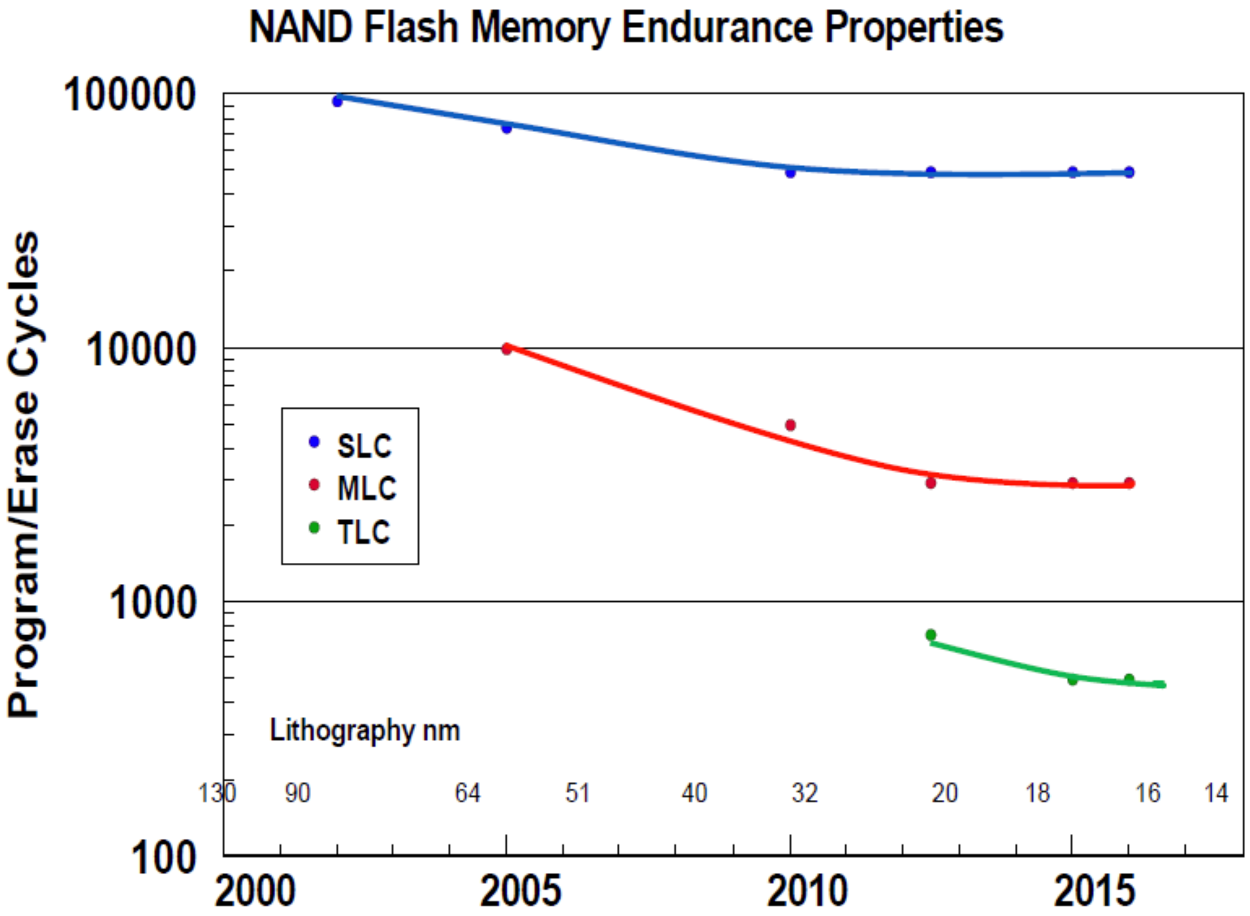
▶ 1.5year/gen. (18 years / 12 gen.)

CMOS scaling
More bits per Cell

Seaung Suk Lee, "Emerging Challenges in NAND Flash Technology", Flash Summit 2011 (Hynix)

- Flash memory is widening its range of applications
  - Portable consumer devices, laptop PCs and enterprise servers

Flash Challenges: Reliability and Endurance



E. Grochowski et al., "Future technology challenges for NAND flash and HDD products", Flash Memory Summit 2012

- **P/E cycles (provided)**

A few thousand

- **P/E cycles (required)**

Writing
the full capacity
of the drive
10 times per day
for 5 years
(STEC)

> 50k P/E cycles

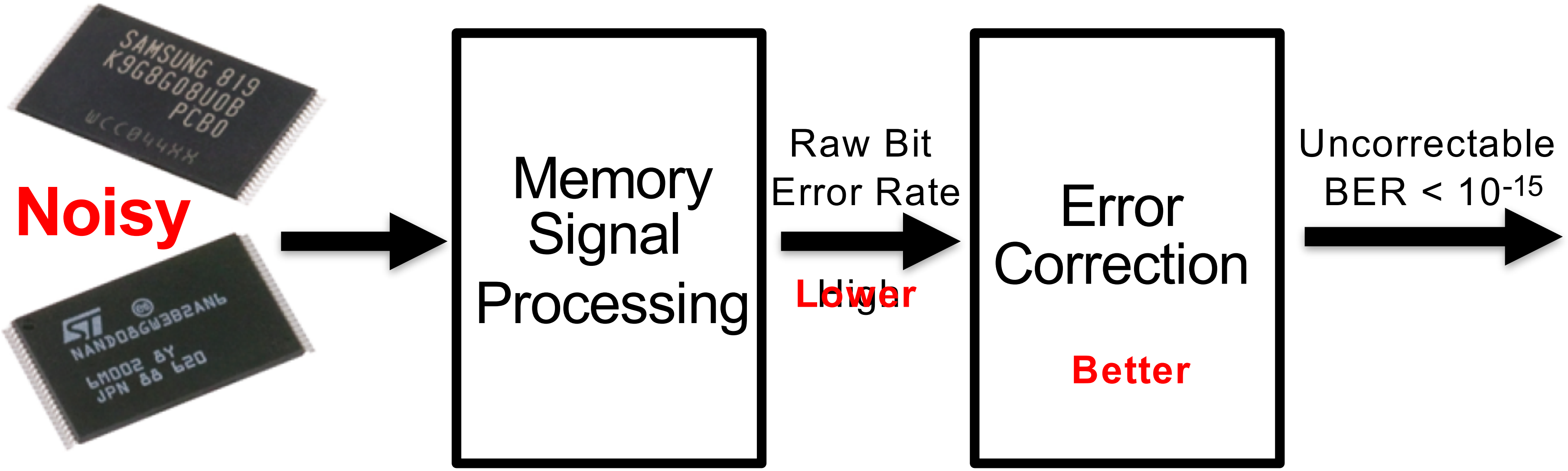
NAND Flash Memory is Increasingly Noisy

Write

Noisy NAND

Read

Future NAND Flash-based Storage Architecture



Noisy

Memory Signal Processing

Raw Bit Error Rate

High

Lower

Error Correction

Better

Uncorrectable BER < 10^{-15}

Our Goals:

Build reliable error models for NAND flash memory

Design efficient reliability mechanisms based on the model

NAND Flash Error Model

Experimentally characterize and model dominant errors

Cai et al., "Error Patterns in MLC NAND Flash Memory: Measurement, Characterization, and Analysis"", **DATE 2012**
Luo et al., "Enabling Accurate and Practical Online Flash Channel Modeling for Modern MLC NAND Flash Memory", **JSAC 2016**

- **Erase block**
- **Program page**

- **Neighbor page prog/read (c-to-c interference)**

- **Retention**

Cai et al., "Threshold voltage distribution in MLC NAND Flash Memory: Characterization, Analysis, and Modeling", **DATE 2013**

Cai et al., "Vulnerabilities in MLC NAND Flash Memory Programming: Experimental Analysis, Exploits, and Mitigation Techniques", **HPCA 2017**

Cai et al., "Program Interference in MLC NAND Flash Memory: Characterization, Modeling, and Mitigation", **ICCD 2013**

Cai et al., "Neighbor-Cell Assisted Error Correction in MLC NAND Flash Memories", **SIGMETRICS 2014**

Cai et al., "Read Disturb Errors in MLC NAND Flash Memory: Characterization and Mitigation", **DSN 2015**

Cai et al., "Flash Correct-and-Refresh: Retention-aware error management for increased flash memory lifetime", **ICCD 2012**

Cai et al., "Error Analysis and Retention-Aware Error Management for NAND Flash Memory, **ITJ 2013**

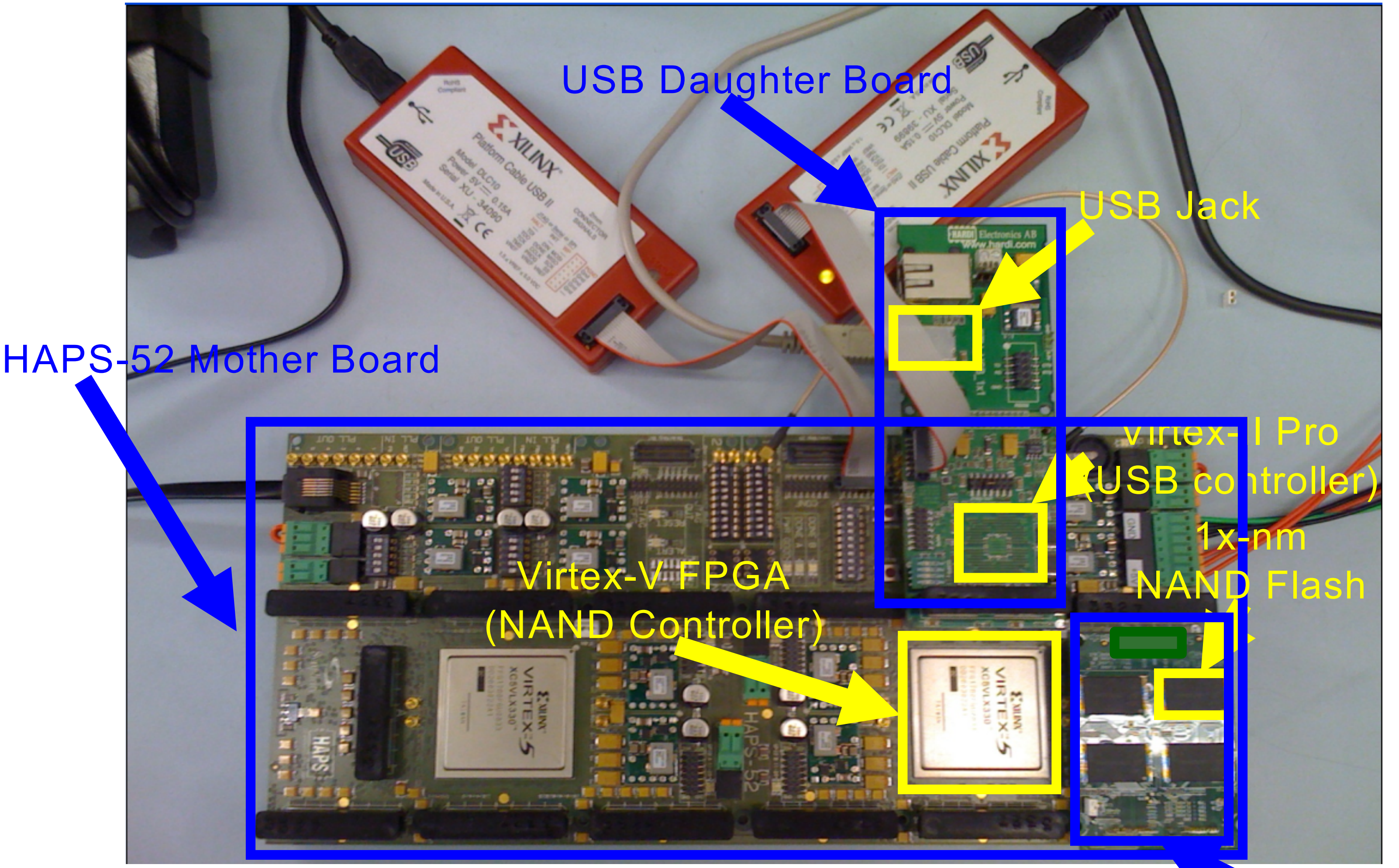
Cai et al., "Data Retention in MLC NAND Flash Memory: Characterization, Optimization and Recovery" **, HPCA 2015**

Our Goals and Approach

- Goals:
  - Understand error mechanisms and develop reliable predictive models for MLC NAND flash memory errors
  - Develop efficient error management techniques to mitigate errors and improve flash reliability and endurance

- Approach:
  - Solid experimental analyses of errors in real MLC NAND flash memory → drive the understanding and models
  - Understanding, models, and creativity → drive the new techniques

Experimental Testing Platform



[DATE 2012, ICCD 2012, DATE 2013, ITJ 2013, ICCD 2013, SIGMETRICS 2014, HPCA 2015, DSN 2015, MSST 2015, JSAC 2016, HPCA 2017, DFRWS 2017]

Cai et al., FPGA-based Solid-State Drive prototyping platform, FCCM 2011.

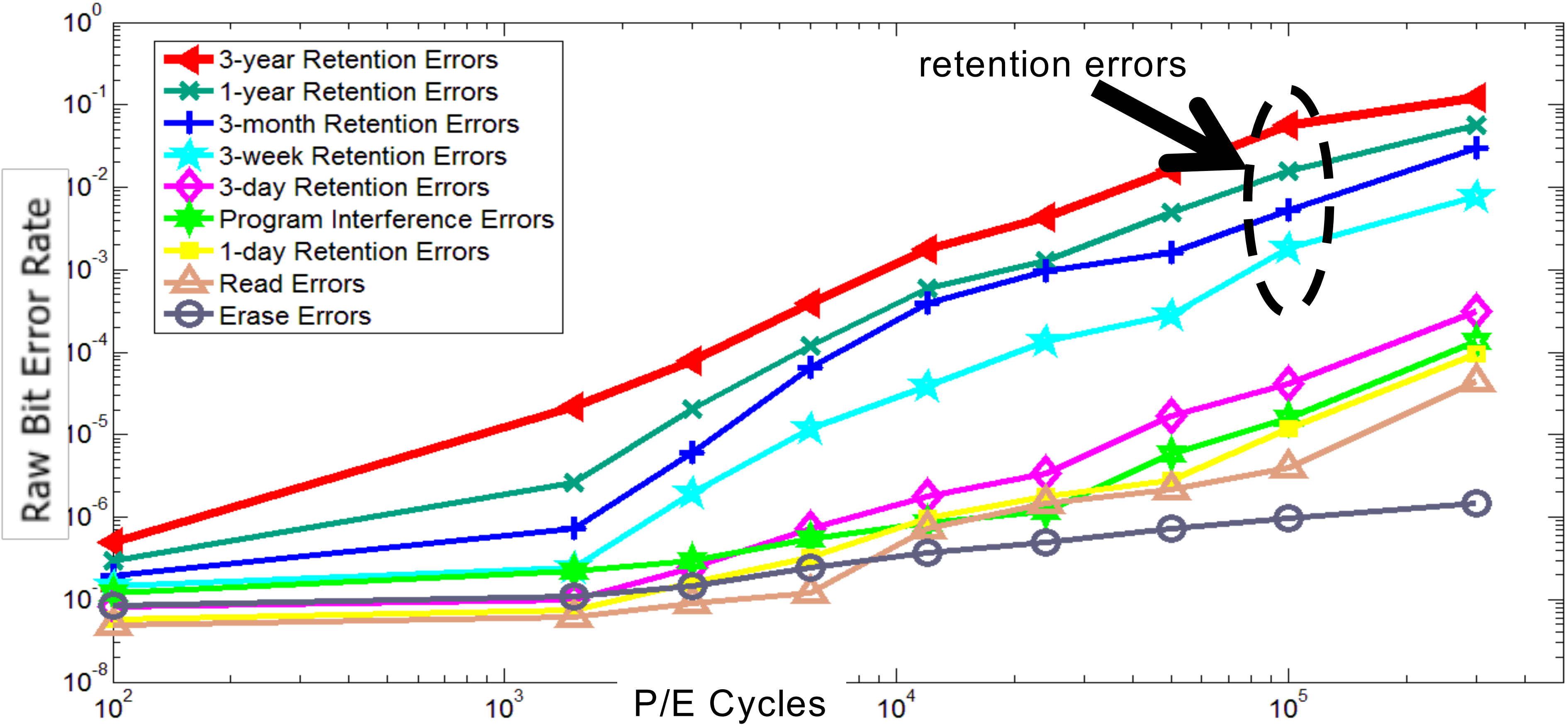
NAND Flash Error Types

- Four types of errors [Cai+, DATE 2012]

- Caused by common flash operations
  - Read errors
  - Erase errors
  - Program (interference) errors

- Caused by flash cell losing charge over time
  - Retention errors
    - Whether an error happens depends on required retention time
    - Especially problematic in MLC flash because threshold voltage window to determine stored value is smaller

Observations: Flash Error Analysis

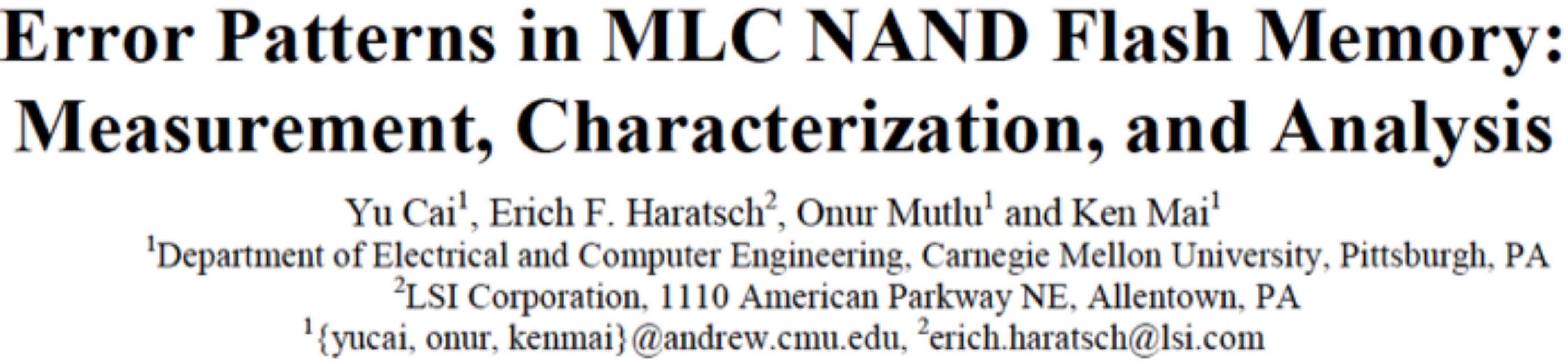


- Raw bit error rate increases exponentially with P/E cycles
- Retention errors are dominant (>99% for 1-year ret. time)
- Retention errors increase with retention time requirement

SAFARI Cai et al., Error Patterns in MLC NAND Flash Memory, DATE 2012.

More on Flash Error Analysis

- Yu Cai, Erich F. Haratsch, Onur Mutlu, and Ken Mai, **"Error Patterns in MLC NAND Flash Memory: Measurement, Characterization, and Analysis"** *Proceedings of the Design, Automation, and Test in Europe Conference* (***DATE***), Dresden, Germany, March 2012. Slides (ppt)



Error Patterns in MLC NAND Flash Memory: Measurement, Characterization, and Analysis

Yu Cai[1], Erich F. Haratsch[2], Onur Mutlu[1] and Ken Mai[1]
[1]Department of Electrical and Computer Engineering, Carnegie Mellon University, Pittsburgh, PA
[2]LSI Corporation, 1110 American Parkway NE, Allentown, PA
[1]{yucai, onur, kenmai}@andrew.cmu.edu, [2]erich.haratsch@lsi.com

Solution to Retention Errors

- Refresh periodically
- Change the period based on P/E cycle wearout
  - Refresh more often at higher P/E cycles
- Use a combination of in-place and remapping-based refresh

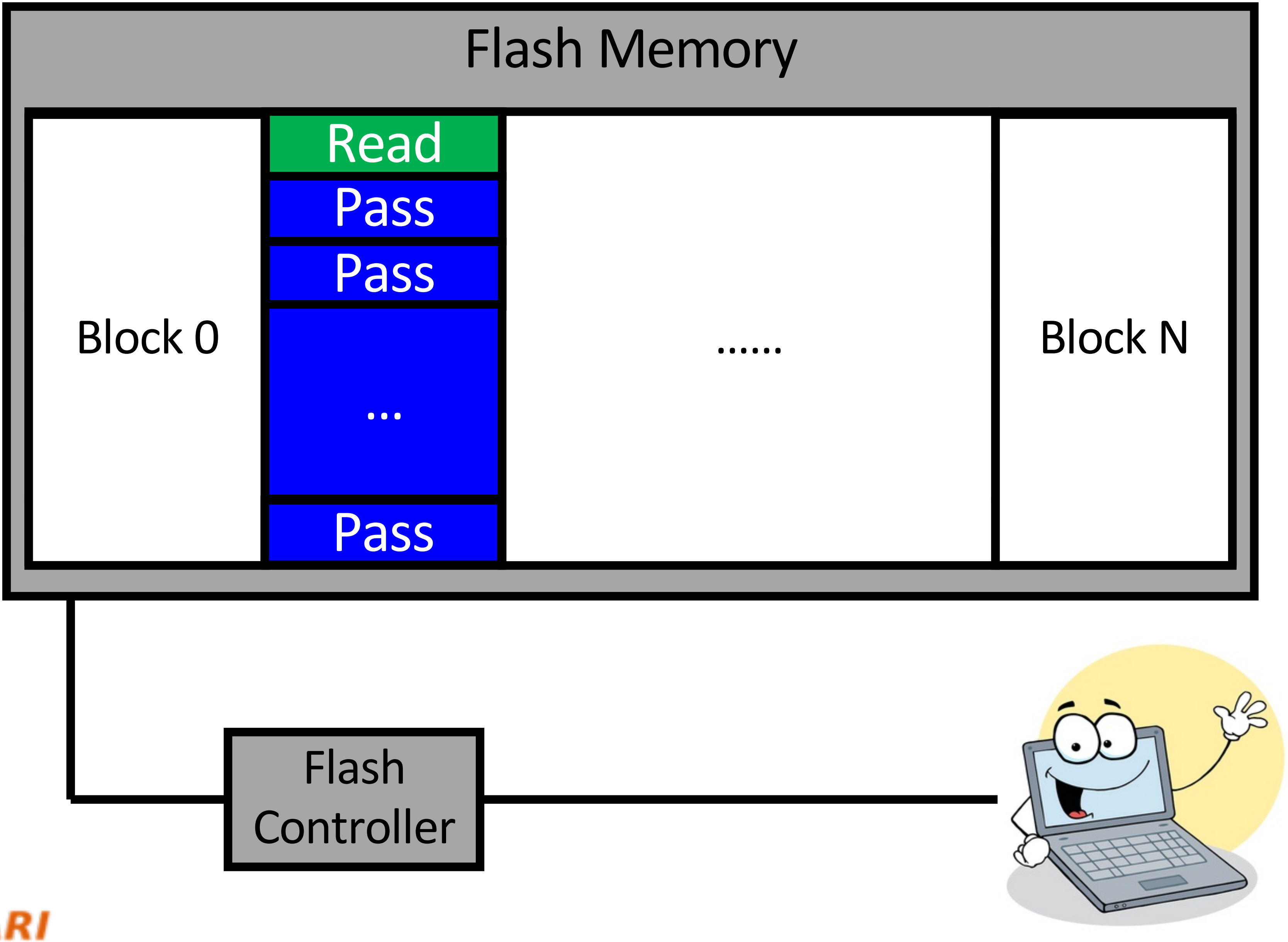
Flash Correct-and-Refresh: Retention-Aware Error Management for Increased Flash Memory Lifetime

Yu Cai[1], Gulay Yalcin[2], Onur Mutlu[1], Erich F. Haratsch[3], Adrian Cristal[2], Osman S. Unsal[2] and Ken Mai[1]
[1]DSSC, Department of Electrical and Computer Engineering, Carnegie Mellon University, Pittsburgh, PA
[2]Barcelona Supercomputing Center, C/Jordi Girona 29, Barcelona, Spain
[3]LSI Corporation, 1110 American Parkway NE, Allentown, PA

One Issue: Read Disturb in Flash Memory

- All scaled memories are prone to read disturb errors

NAND Flash Memory Background



Flash Memory

Block 0

Read

Pass

Pass

…

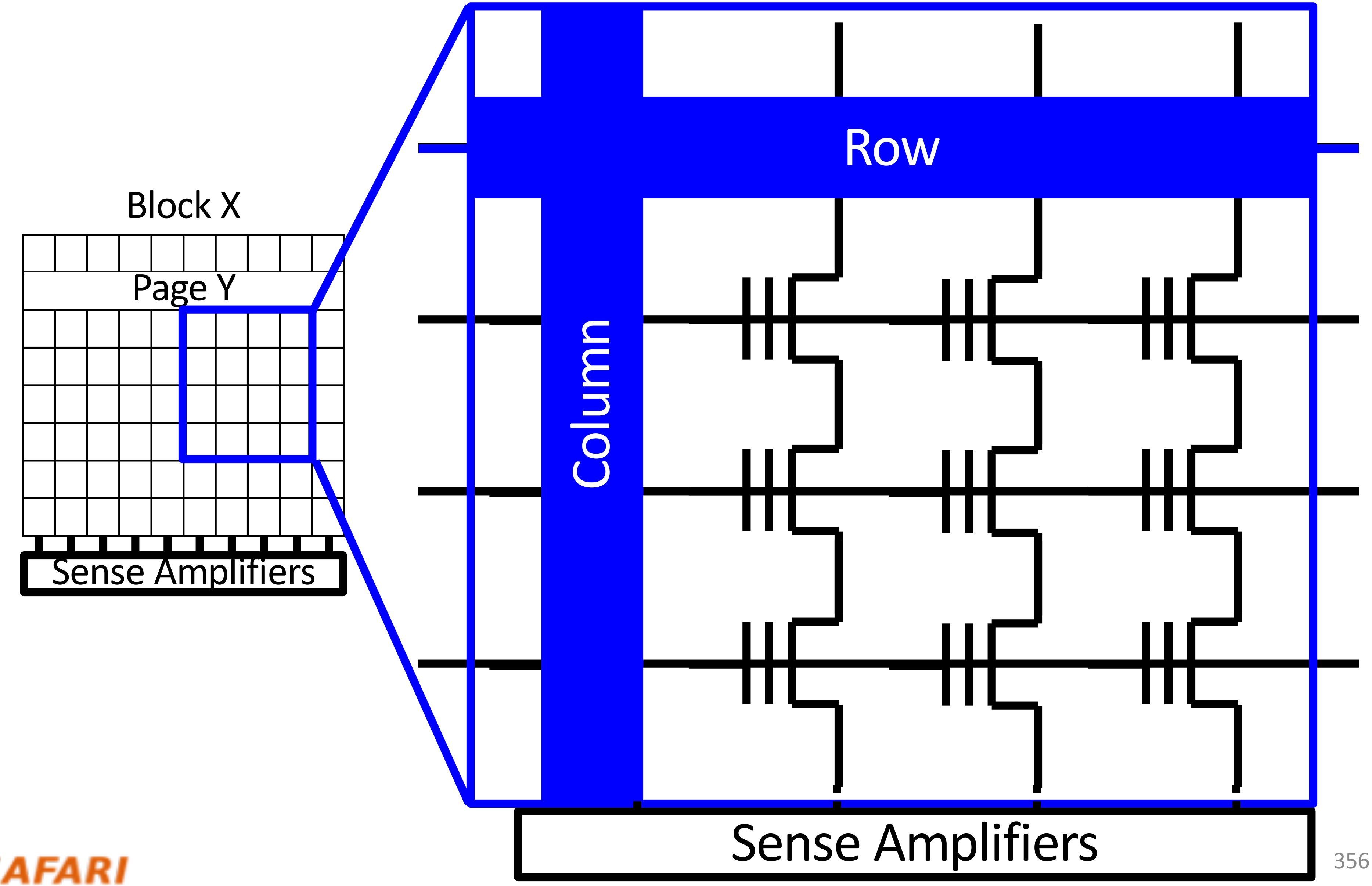
Pass

……

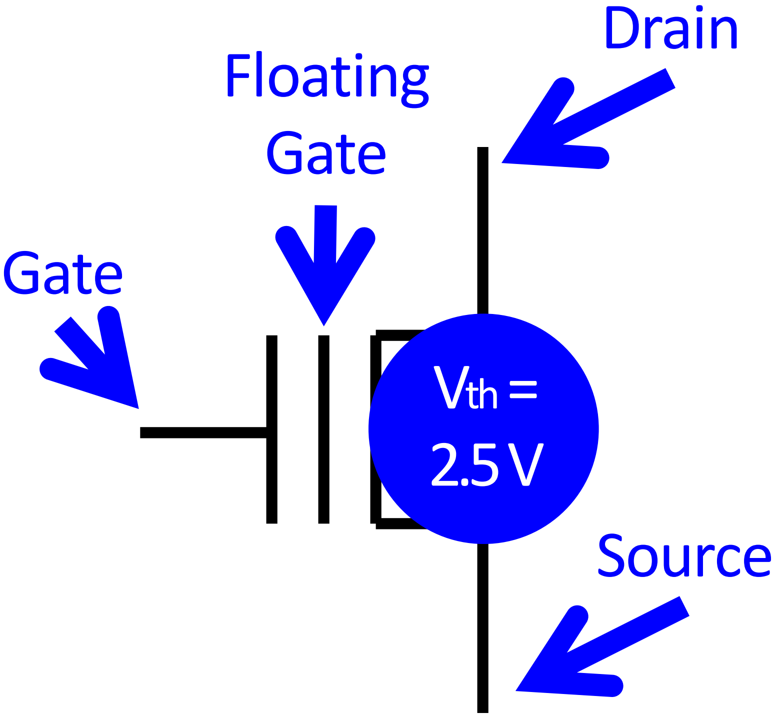
Block N

Flash Controller

Flash Cell Array

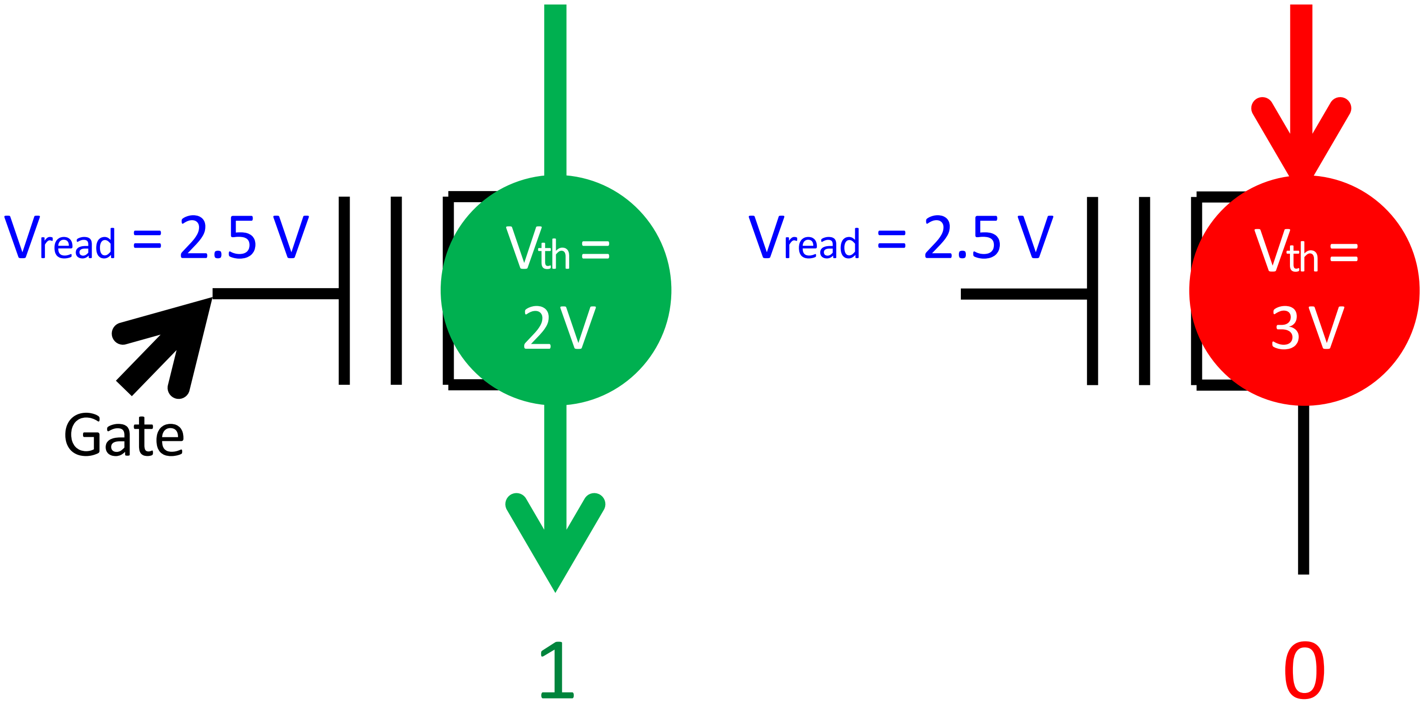


Flash Cell

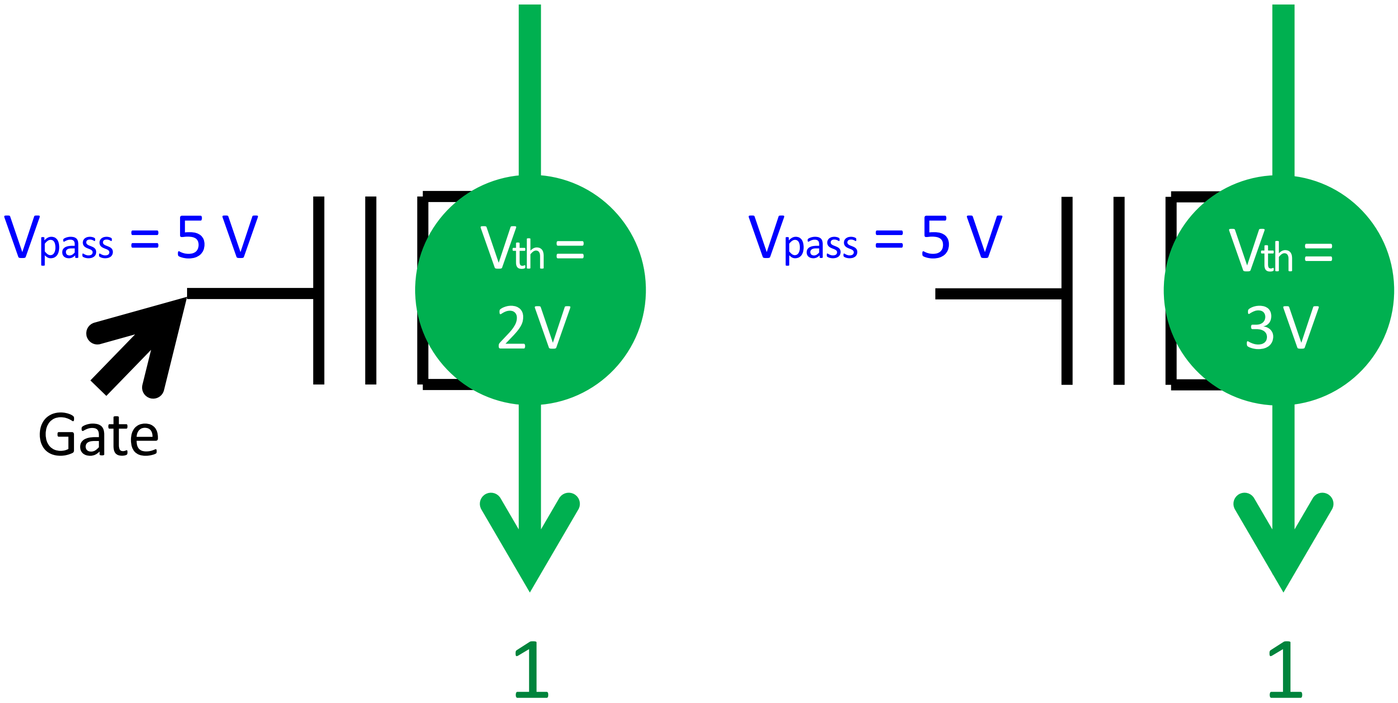


Floating Gate Transistor
(Flash Cell)

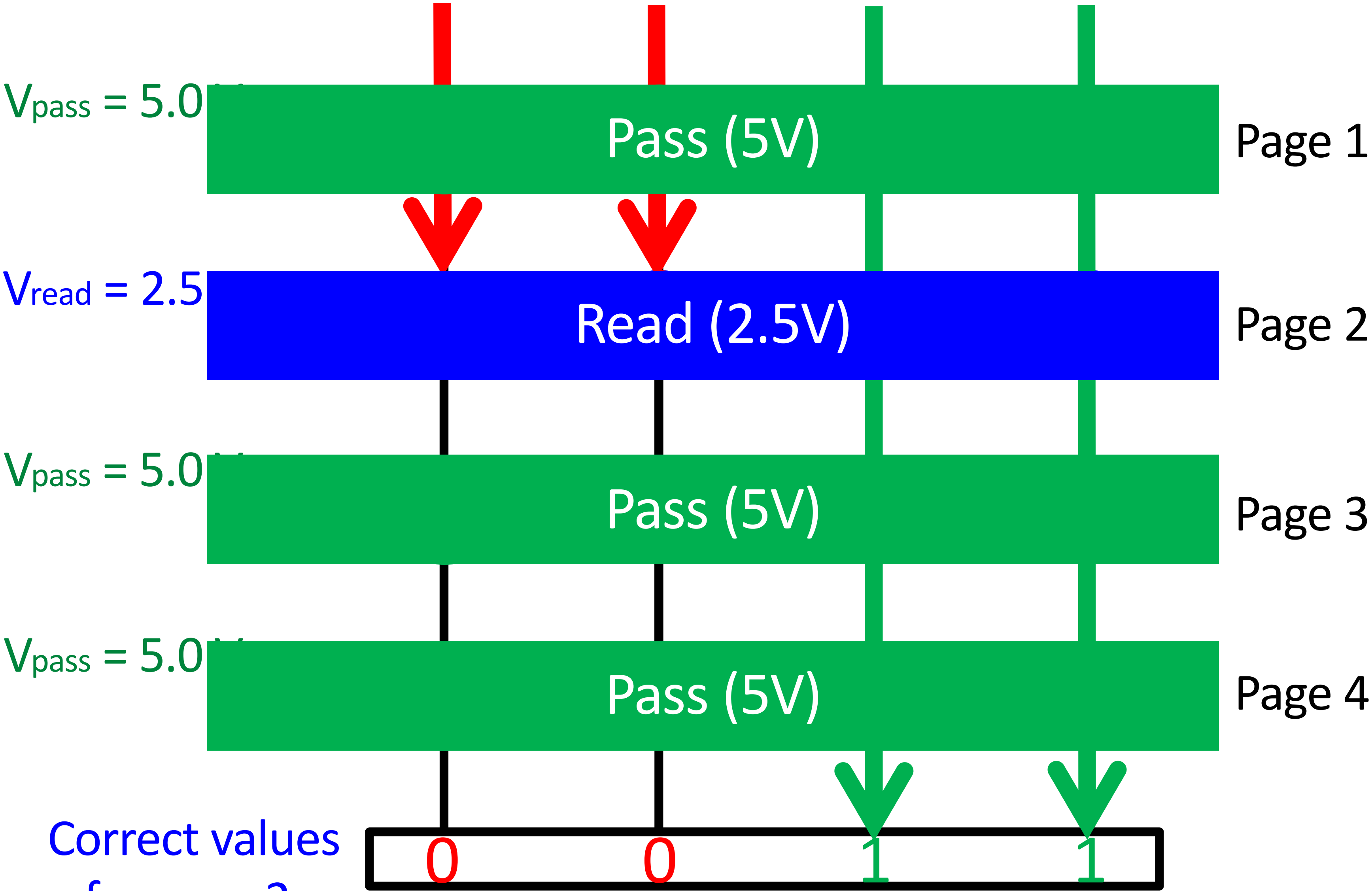
Flash Read



Flash Pass-Through



Read from Flash Cell Array



V_{pass} = 5.0

Pass (5V)

Page 1

V_{read} = 2.5

Read (2.5V)

Page 2

V_{pass} = 5.0

Pass (5V)

Page 3

V_{pass} = 5.0

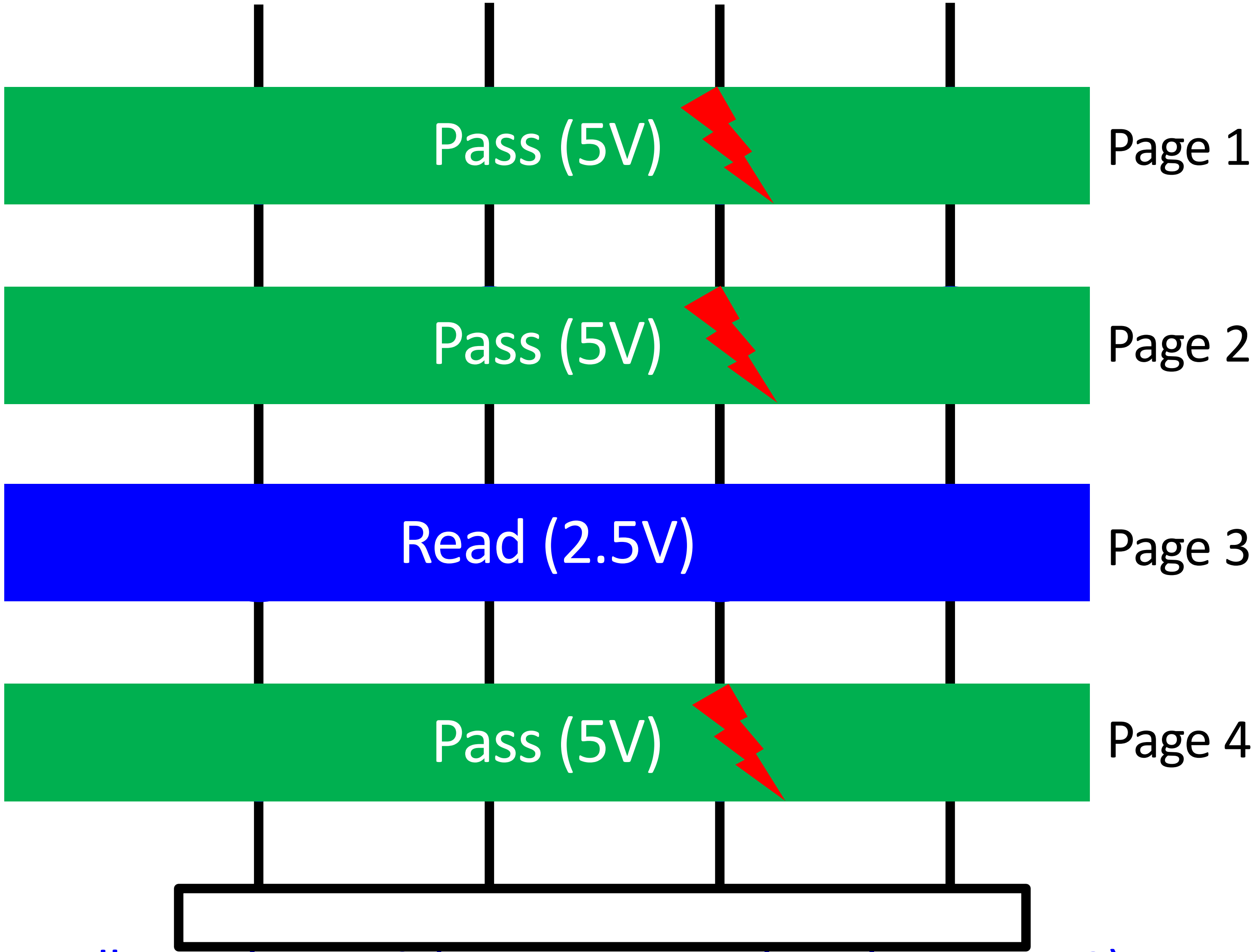
Pass (5V)

Page 4

Correct values for page 2:

0 0 1 1

Read Disturb Problem: "Weak Programming" Effect



Pass (5V) Page 1

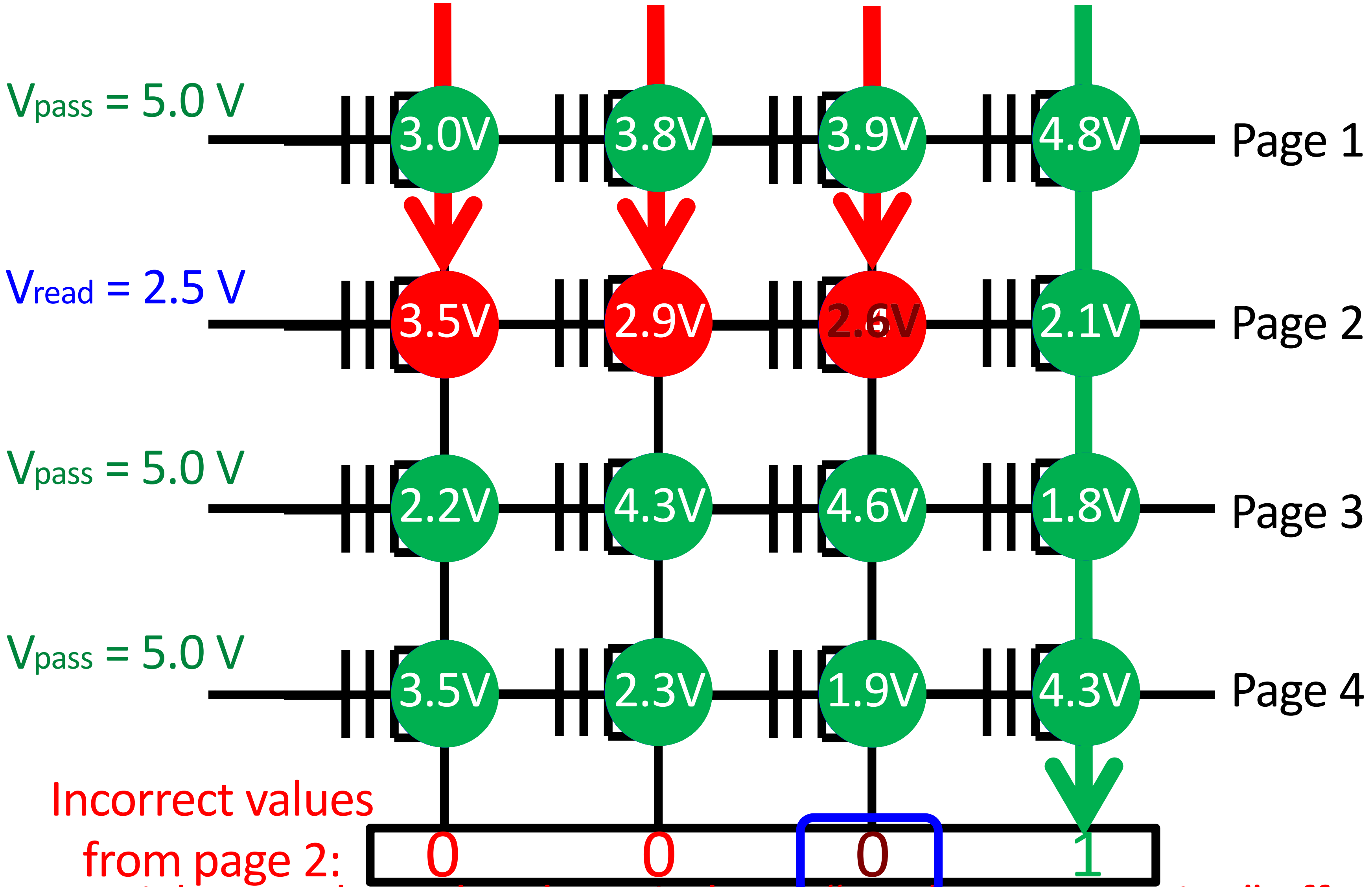
Pass (5V) Page 2

Read (2.5V) Page 3

Pass (5V) Page 4

Repeatedly read page 3 (or any page other than page 2)

Read Disturb Problem: “Weak Programming” Effect



$V_{pass} = 5.0$ V — Page 1

$V_{read} = 2.5$ V — Page 2

$V_{pass} = 5.0$ V — Page 3

$V_{pass} = 5.0$ V — Page 4

Incorrect values from page 2:

High pass-through voltage induces “weak-programming” effect

Executive Summary

- ***Read disturb errors*** limit flash memory lifetime today
  - Apply a *high pass-through voltage (V_{pass})* to multiple pages on a read
  - Repeated application of V_{pass} can alter stored values in unread pages
- We **characterize read disturb** on real NAND flash chips
  - Slightly lowering V_{pass} greatly reduces read disturb errors
  - Some flash cells are more prone to read disturb
- **Technique 1:** Mitigate read disturb errors online
  - ***V_{pass} Tuning*** dynamically finds and applies a lowered V_{pass} per block
  - Flash memory lifetime improves by 21%
- **Technique 2:** Recover after failure to prevent data loss
  - ***Read Disturb Oriented Error Recovery*** (RDR) selectively corrects cells more susceptible to read disturb errors
  - Reduces raw bit error rate (RBER) by up to 36%

SAFARI

More on Flash Read Disturb Errors

- Yu Cai, Yixin Luo, Saugata Ghose, Erich F. Haratsch, Ken Mai, and Onur Mutlu,
  "Read Disturb Errors in MLC NAND Flash Memory: Characterization and Mitigation"
  *Proceedings of the 45th Annual IEEE/IFIP International Conference on Dependable Systems and Networks (**DSN**)*, Rio de Janeiro, Brazil, June 2015.

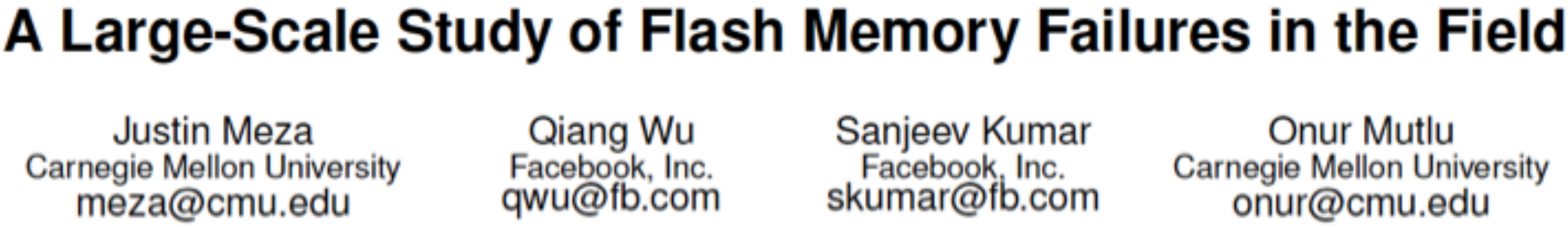
Read Disturb Errors in MLC NAND Flash Memory: Characterization, Mitigation, and Recovery

Yu Cai, Yixin Luo, Saugata Ghose, Erich F. Haratsch*, Ken Mai, Onur Mutlu
Carnegie Mellon University, *Seagate Technology
yucaicai@gmail.com, {yixinluo, ghose, kenmai, onur}@cmu.edu

Large-Scale Flash SSD Error Analysis

- First large-scale field study of flash memory errors

- Justin Meza, Qiang Wu, Sanjeev Kumar, and Onur Mutlu,
"A Large-Scale Study of Flash Memory Errors in the Field"
Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (***SIGMETRICS***), Portland, OR, June 2015.
[Slides (pptx) (pdf)] [Coverage at ZDNet] [Coverage on The Register] [Coverage on TechSpot] [Coverage on The Tech Report]



A Large-Scale Study of Flash Memory Failures in the Field

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skumar@fb.com

Onur Mutlu
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Another Time: NAND Flash Vulnerabilities

- Onur Mutlu,
  "Error Analysis and Management for MLC NAND Flash Memory"
  Technical talk at Flash Memory Summit 2014 (***FMS***), Santa Clara, CA, August 2014. Slides (ppt) (pdf)

Cai+, "Error Patterns in MLC NAND Flash Memory: Measurement, Characterization, and Analysis," DATE 2012.

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Fukami+, "Improving the Reliability of Chip-Off Forensic Analysis of NAND Flash Memory Devices," DFRWS EU 2017.

Flash Memory Programming Vulnerabilities

- Yu Cai, Saugata Ghose, Yixin Luo, Ken Mai, Onur Mutlu, and Erich F. Haratsch,
"Vulnerabilities in MLC NAND Flash Memory Programming: Experimental Analysis, Exploits, and Mitigation Techniques"
Proceedings of the 23rd International Symposium on High-Performance Computer Architecture (***HPCA***) *Industrial Session*, Austin, TX, USA, February 2017.
[Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)]

Vulnerabilities in MLC NAND Flash Memory Programming: Experimental Analysis, Exploits, and Mitigation Techniques

Yu Cai[†] Saugata Ghose[†] Yixin Luo[‡†] Ken Mai[†] Onur Mutlu[§†] Erich F. Haratsch[‡]
[†]*Carnegie Mellon University* [‡]*Seagate Technology* [§]*ETH Zürich*

Other Works on Flash Memory

NAND Flash Error Model

Write → Noisy NAND → Read

Experimentally characterize and model dominant errors

Cai et al., "Error Patterns in MLC NAND Flash Memory: Measurement, Characterization, and Analysis"", **DATE 2012**
Luo et al., "Enabling Accurate and Practical Online Flash Channel Modeling for Modern MLC NAND Flash Memory", **JSAC 2016**

Write

- **Erase block**
- **Program page**

- **Neighbor page prog/read (c-to-c interference)**

- **Retention**

Read

Cai et al., "Threshold voltage distribution in MLC NAND Flash Memory: Characterization, Analysis, and Modeling", **DATE 2013**

Cai et al., "Vulnerabilities in MLC NAND Flash Memory Programming: Experimental Analysis, Exploits, and Mitigation Techniques", **HPCA 2017**

Cai et al., "Program Interference in MLC NAND Flash Memory: Characterization, Modeling, and Mitigation", **ICCD 2013**

Cai et al., "Neighbor-Cell Assisted Error Correction in MLC NAND Flash Memories", **SIGMETRICS 2014**

Cai et al., "Read Disturb Errors in MLC NAND Flash Memory: Characterization and Mitigation", **DSN 2015**

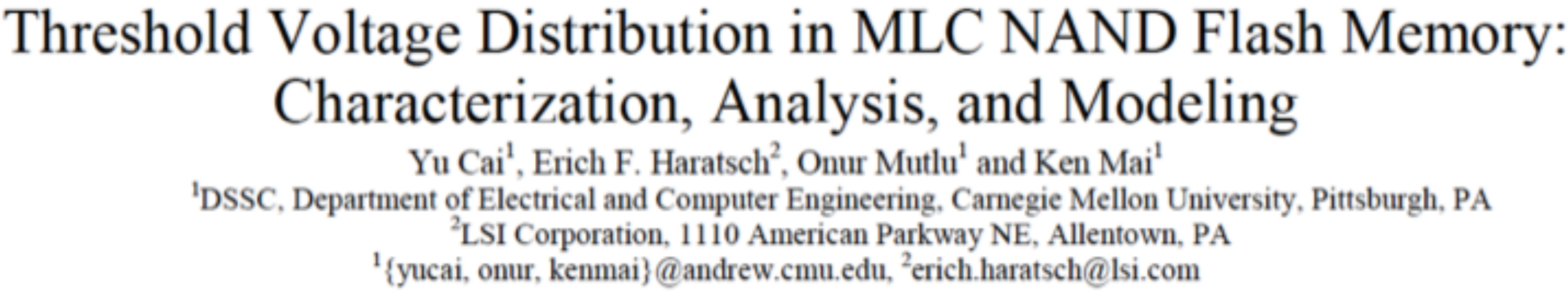
Cai et al., "Flash Correct-and-Refresh: Retention-aware error management for increased flash memory lifetime", **ICCD 2012**

Cai et al., "Error Analysis and Retention-Aware Error Management for NAND Flash Memory, **ITJ 2013**

Cai et al., "Data Retention in MLC NAND Flash Memory: Characterization, Optimization and Recovery" **, HPCA 2015**

Threshold Voltage Distribution

- Yu Cai, Erich F. Haratsch, Onur Mutlu, and Ken Mai, **"Threshold Voltage Distribution in MLC NAND Flash Memory: Characterization, Analysis and Modeling"** *Proceedings of the Design, Automation, and Test in Europe Conference* (***DATE***), Grenoble, France, March 2013. Slides (ppt)

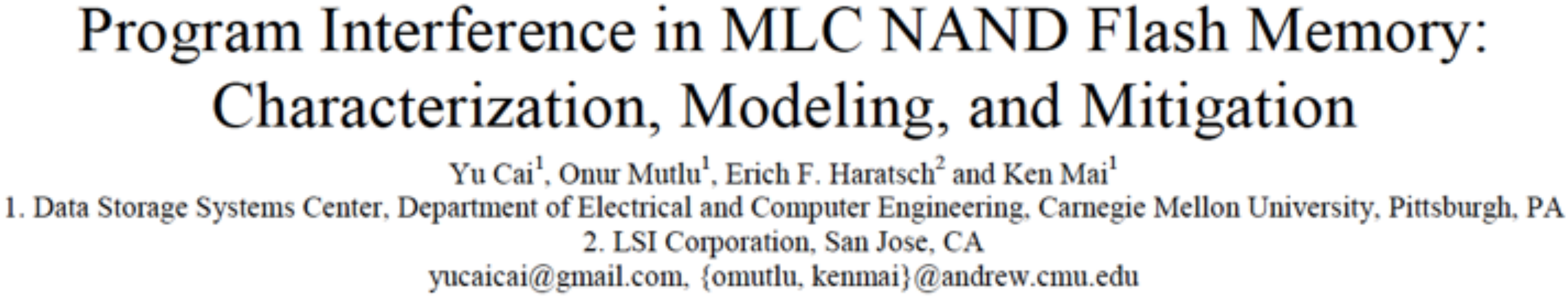


Threshold Voltage Distribution in MLC NAND Flash Memory: Characterization, Analysis, and Modeling

Yu Cai[1], Erich F. Haratsch[2], Onur Mutlu[1] and Ken Mai[1]
[1]DSSC, Department of Electrical and Computer Engineering, Carnegie Mellon University, Pittsburgh, PA
[2]LSI Corporation, 1110 American Parkway NE, Allentown, PA
[1]{yucai, onur, kenmai}@andrew.cmu.edu, [2]erich.haratsch@lsi.com

Program Interference and Vref Prediction

- Yu Cai, Onur Mutlu, Erich F. Haratsch, and Ken Mai, **"Program Interference in MLC NAND Flash Memory: Characterization, Modeling, and Mitigation"** *Proceedings of the 31st IEEE International Conference on Computer Design* (***ICCD***), Asheville, NC, October 2013. Slides (pptx) (pdf) Lightning Session Slides (pdf)



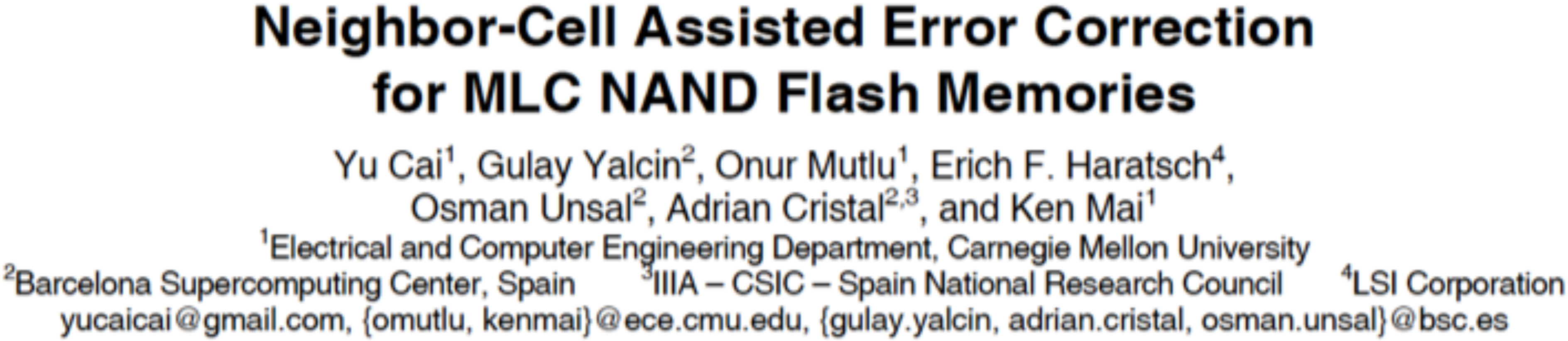
Program Interference in MLC NAND Flash Memory:
Characterization, Modeling, and Mitigation

Yu Cai[1], Onur Mutlu[1], Erich F. Haratsch[2] and Ken Mai[1]
1. Data Storage Systems Center, Department of Electrical and Computer Engineering, Carnegie Mellon University, Pittsburgh, PA
2. LSI Corporation, San Jose, CA
yucaicai@gmail.com, {omutlu, kenmai}@andrew.cmu.edu

Neighbor-Assisted Error Correction

- Yu Cai, Gulay Yalcin, Onur Mutlu, Eric Haratsch, Osman Unsal, Adrian Cristal, and Ken Mai,

  "Neighbor-Cell Assisted Error Correction for MLC NAND Flash Memories"
  Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems
  (***SIGMETRICS***), Austin, TX, June 2014. Slides (ppt) (pdf)

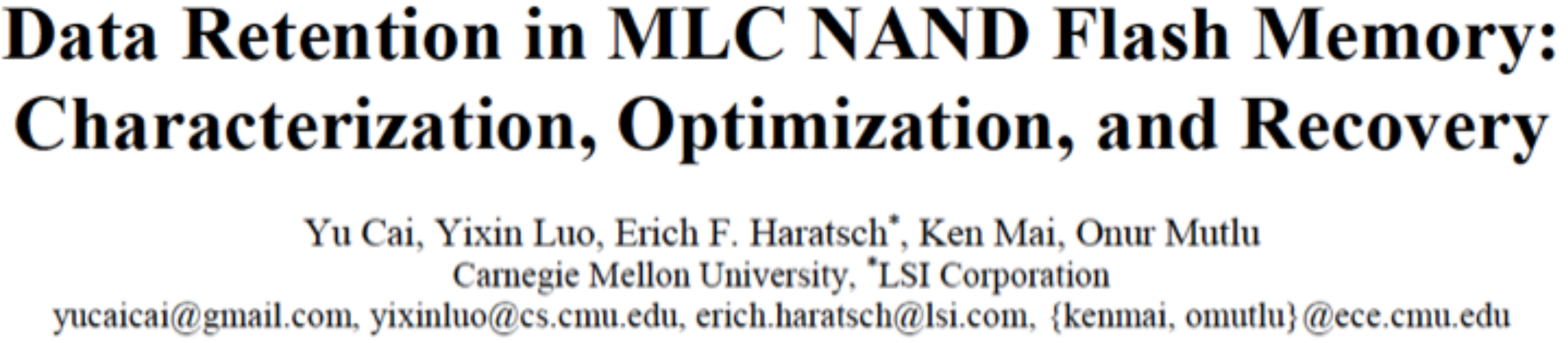


Neighbor-Cell Assisted Error Correction for MLC NAND Flash Memories

Yu Cai[1], Gulay Yalcin[2], Onur Mutlu[1], Erich F. Haratsch[4],
Osman Unsal[2], Adrian Cristal[2,3], and Ken Mai[1]
[1]Electrical and Computer Engineering Department, Carnegie Mellon University
[2]Barcelona Supercomputing Center, Spain [3]IIIA – CSIC – Spain National Research Council [4]LSI Corporation
yucaicai@gmail.com, {omutlu, kenmai}@ece.cmu.edu, {gulay.yalcin, adrian.cristal, osman.unsal}@bsc.es

Data Retention

- Yu Cai, Yixin Luo, Erich F. Haratsch, Ken Mai, and Onur Mutlu, **"Data Retention in MLC NAND Flash Memory: Characterization, Optimization and Recovery"** *Proceedings of the 21st International Symposium on High-Performance Computer Architecture* (***HPCA***), Bay Area, CA, February 2015. [Slides (pptx) (pdf)]



Data Retention in MLC NAND Flash Memory: Characterization, Optimization, and Recovery

Yu Cai, Yixin Luo, Erich F. Haratsch*, Ken Mai, Onur Mutlu
Carnegie Mellon University, *LSI Corporation
yucaicai@gmail.com, yixinluo@cs.cmu.edu, erich.haratsch@lsi.com, {kenmai, omutlu}@ece.cmu.edu

SSD Error Analysis in the Field

- First large-scale field study of flash memory errors
- Justin Meza, Qiang Wu, Sanjeev Kumar, and Onur Mutlu,
"A Large-Scale Study of Flash Memory Errors in the Field"
*Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (**SIGMETRICS**)*, Portland, OR, June 2015.
[Slides (pptx) (pdf)] [Coverage at ZDNet] [Coverage on The Register] [Coverage on TechSpot] [Coverage on The Tech Report]

A Large-Scale Study of Flash Memory Failures in the Field

Justin Meza	Qiang Wu	Sanjeev Kumar	Onur Mutlu
Carnegie Mellon University	Facebook, Inc.	Facebook, Inc.	Carnegie Mellon University
meza@cmu.edu	qwu@fb.com	skumar@fb.com	onur@cmu.edu

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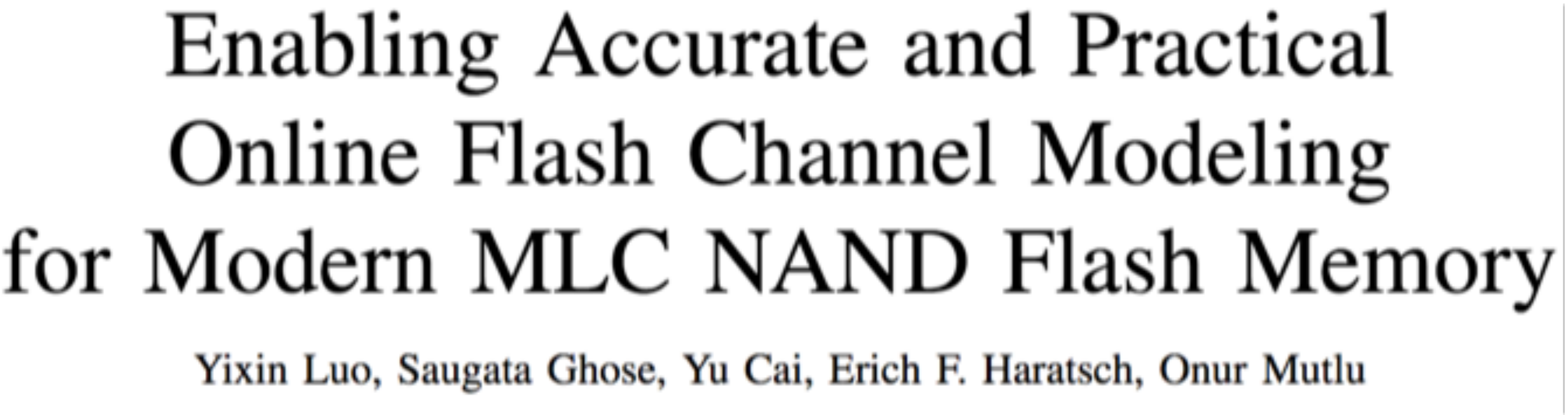
Vulnerabilities in MLC NAND Flash Memory Programming: Experimental Analysis, Exploits, and Mitigation Techniques

Yu Cai[†] Saugata Ghose[†] Yixin Luo[‡†] Ken Mai[†] Onur Mutlu[§†] Erich F. Haratsch[‡]
[†]*Carnegie Mellon University* [‡]*Seagate Technology* [§]*ETH Zürich*

Accurate and Online Channel Modeling

- Yixin Luo, Saugata Ghose, Yu Cai, Erich F. Haratsch, and Onur Mutlu, **"Enabling Accurate and Practical Online Flash Channel Modeling for Modern MLC NAND Flash Memory"** *to appear in IEEE Journal on Selected Areas in Communications* (***JSAC***), 2016.



Enabling Accurate and Practical Online Flash Channel Modeling for Modern MLC NAND Flash Memory

Yixin Luo, Saugata Ghose, Yu Cai, Erich F. Haratsch, Onur Mutlu

More on DRAM Refresh

Tackling Refresh: Solutions

- Parallelize refreshes with accesses [Chang+ HPCA'14]

- Eliminate unnecessary refreshes [Liu+ ISCA'12]
  - Exploit device characteristics
  - Exploit data and application characteristics

- Reduce refresh rate and detect+correct errors that occur [Khan+ SIGMETRICS'14]

- Understand retention time behavior in DRAM [Liu+ ISCA'13]

Summary: Refresh-Access Parallelization

- DRAM **refresh interferes with memory accesses**
  - Degrades system performance and energy efficiency
  - Becomes exacerbated as DRAM density increases
- Goal: Serve memory accesses in parallel with refreshes to reduce refresh interference on demand requests
- Our mechanisms:
  - 1. Enable more parallelization between refreshes and accesses across different banks with new per-bank refresh scheduling algorithms
  - 2. Enable serving accesses concurrently with refreshes in the same bank by exploiting parallelism across DRAM subarrays
- Improve system performance and energy efficiency for a wide variety of different workloads and DRAM densities
  - 20.2% and 9.0% for 8-core systems using 32Gb DRAM at low cost
  - Very close to the ideal scheme without refreshes

Chang+, "Improving DRAM Performance by Parallelizing Refreshes with Accesses," HPCA 2014.

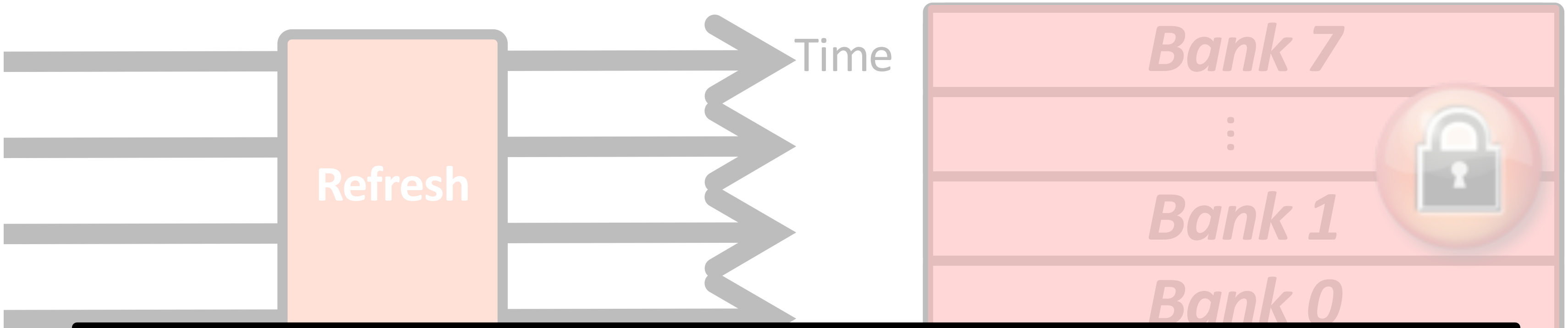
Refresh Penalty

Refresh interferes with memory accesses

Refresh delays requests by 100s of ns

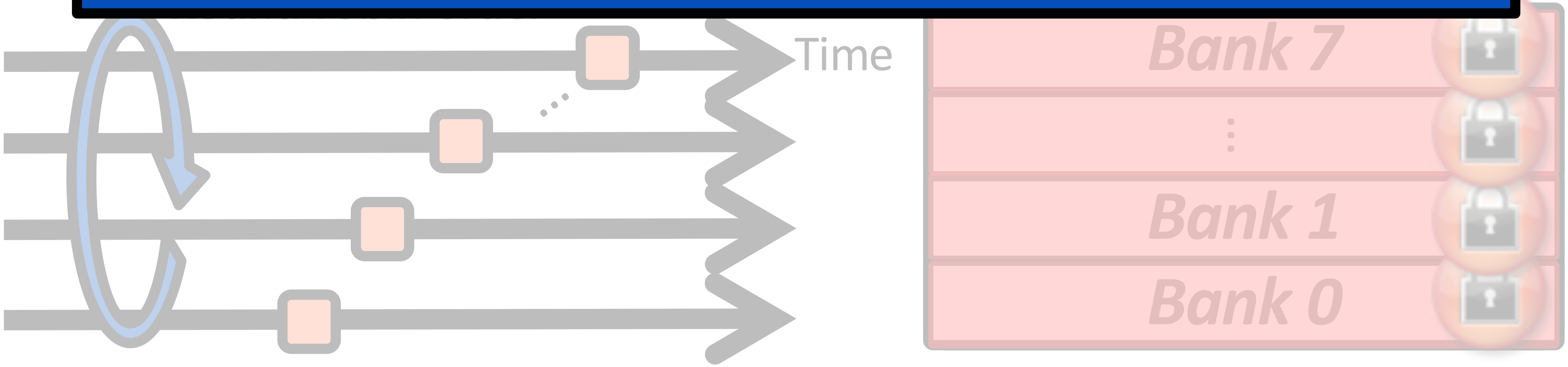
Existing Refresh Modes

All-bank refresh in commodity DRAM (DDRx)



Per-bank refresh allows accesses to other banks while a bank is refreshing

Per



Shortcomings of Per-Bank Refresh

- Problem 1: Refreshes to different banks are scheduled in a strict round-robin order
  - The static ordering is hardwired into DRAM chips
  - Refreshes busy banks with many queued requests when other banks are idle

- Key idea: Schedule per-bank refreshes to idle banks opportunistically in a dynamic order

Our First Approach: DARP

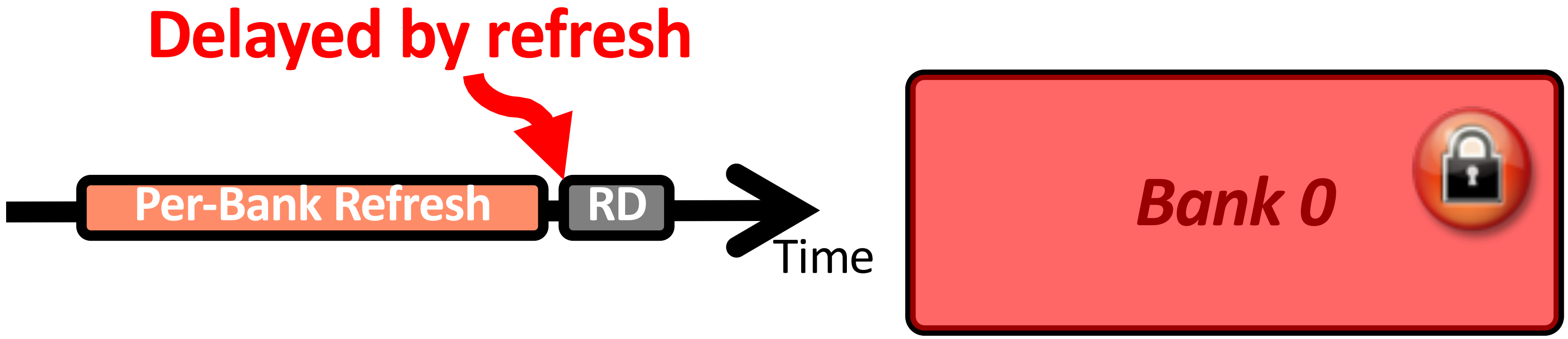
- **Dynamic Access-Refresh Parallelization (DARP)**
  - An improved scheduling policy for per-bank refreshes
  - Exploits refresh scheduling flexibility in DDR DRAM

- Component 1: **Out-of-order per-bank refresh**
  - Avoids poor static scheduling decisions
  - Dynamically issues per-bank refreshes to idle banks

- Component 2: **Write-Refresh Parallelization**
  - Avoids refresh interference on latency-critical reads
  - Parallelizes refreshes with **a batch of writes**

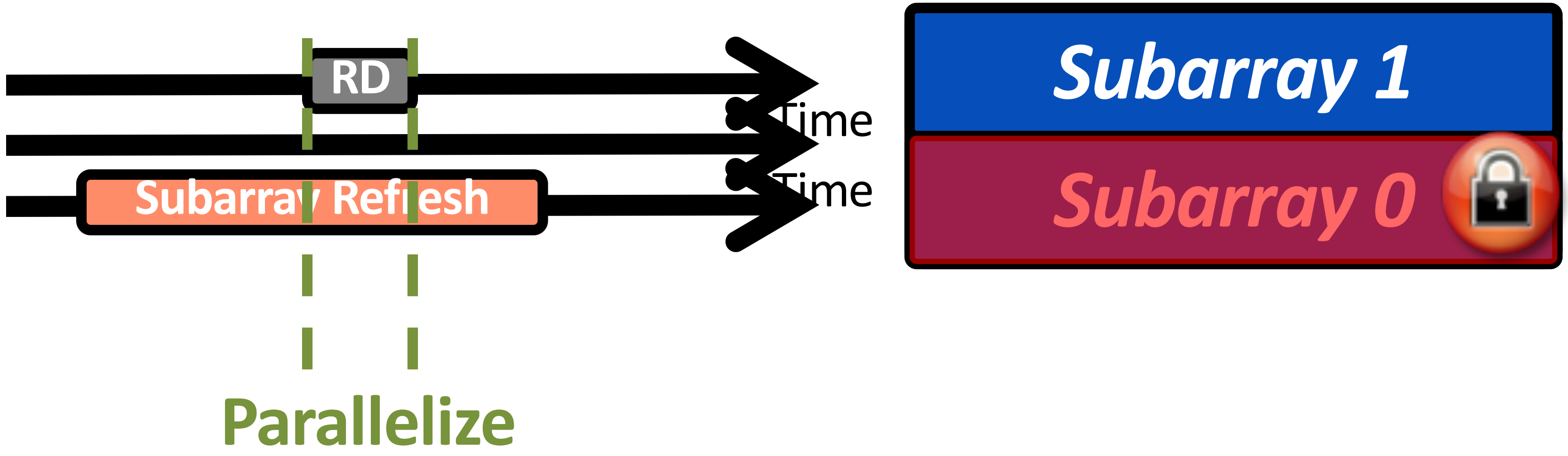
Shortcomings of Per-Bank Refresh

- Problem 2: Banks that are being refreshed cannot concurrently serve memory requests



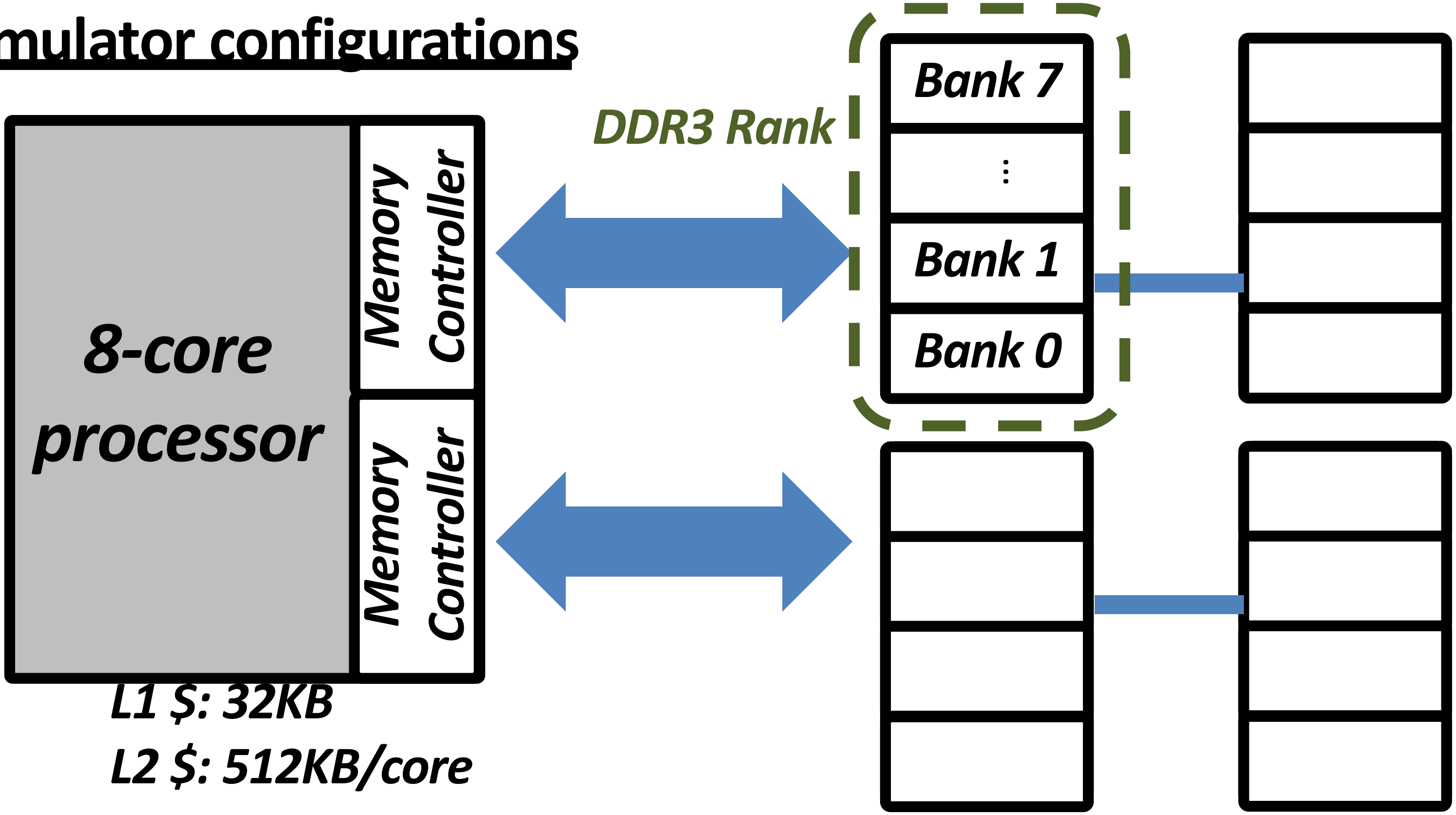
Shortcomings of Per-Bank Refresh

- Problem 2: Refreshing banks cannot concurrently serve memory requests
- Key idea: Exploit **subarrays** within a bank to parallelize refreshes and accesses across **subarrays**



Methodology

Simulator configurations

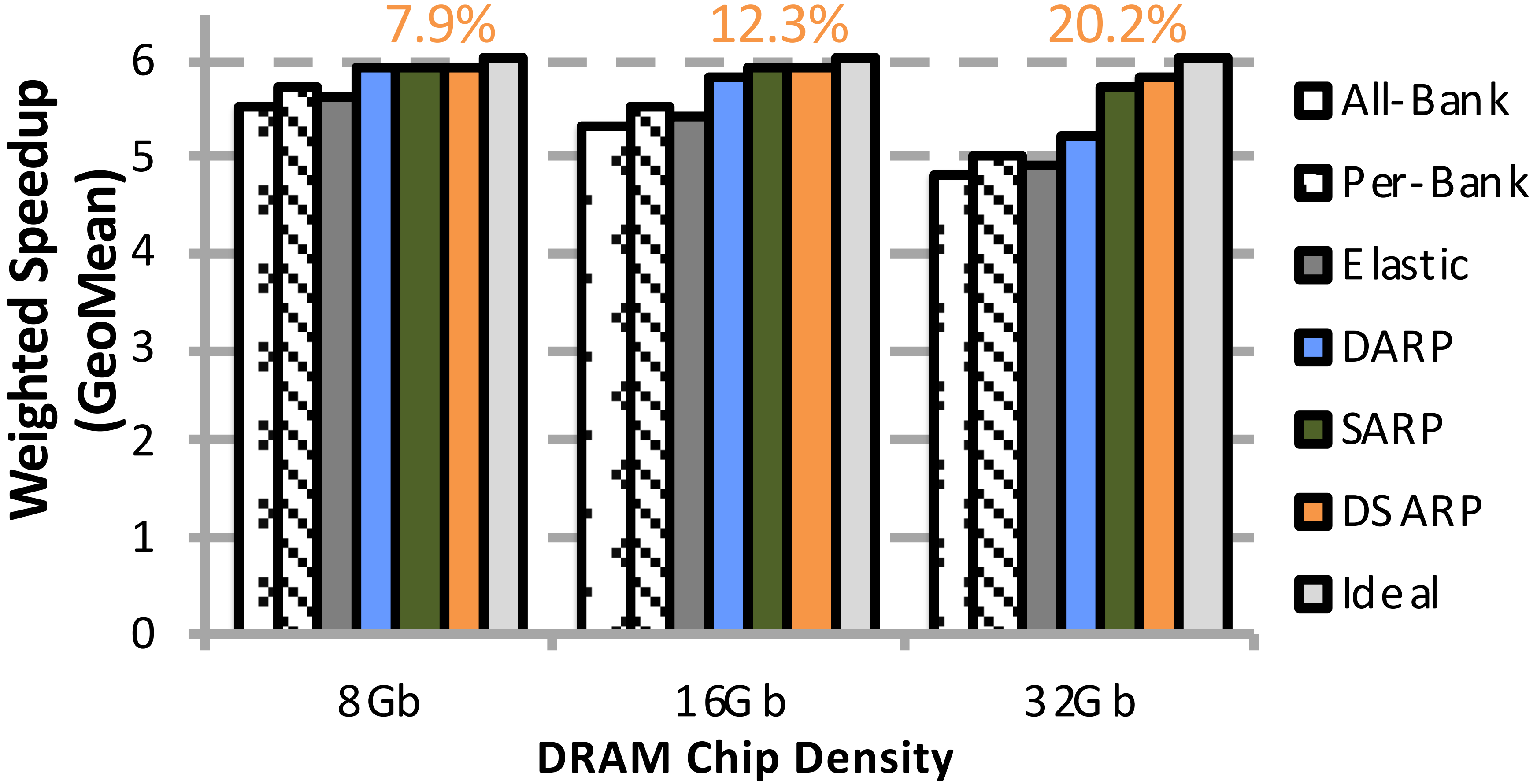


- **100 workloads**: SPEC CPU2006, STREAM, TPC-C/H, random access
- **System performance metric**: *Weighted speedup*

Comparison Points

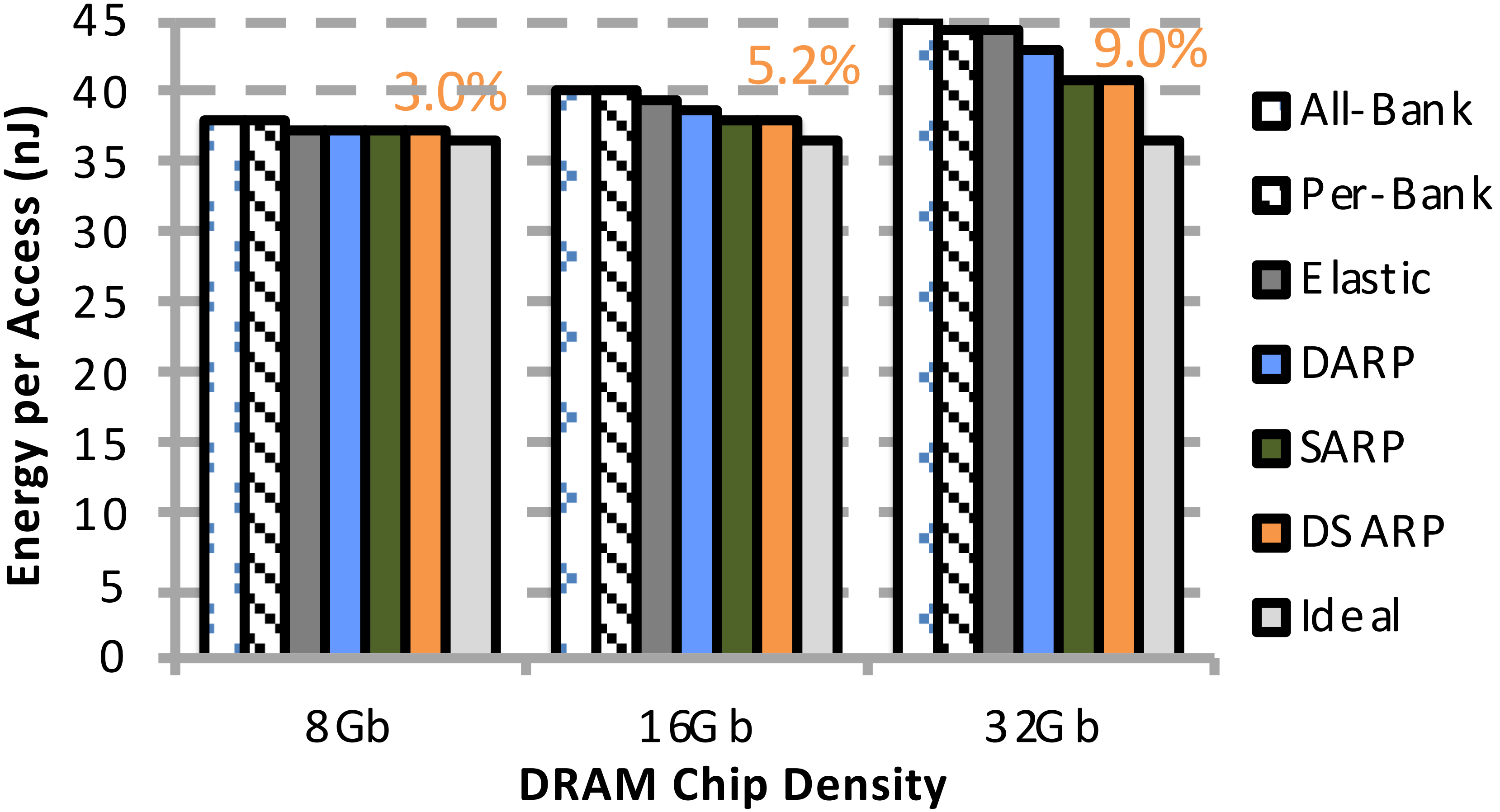
- **All-bank refresh** [DDR3, LPDDR3, …]
- **Per-bank refresh** [LPDDR3]
- **Elastic refresh** [Stuecheli et al., MICRO ‘10]:
  - Postpones refreshes by a time delay based on the predicted rank idle time to avoid interference on memory requests
  - Proposed to schedule all-bank refreshes without exploiting per-bank refreshes
  - Cannot parallelize refreshes and accesses within a rank
- **Ideal (no refresh)**

System Performance



*2. Consistent system performance improvement across DRAM densities (within **0.9%, 1.2%, and 3.8%** of ideal)*

Energy Efficiency



Consistent reduction on energy consumption

More Information on Refresh-Access Parallelization

- Kevin Chang, Donghyuk Lee, Zeshan Chishti, Alaa Alameldeen, Chris Wilkerson, Yoongu Kim, and Onur Mutlu,
  "Improving DRAM Performance by Parallelizing Refreshes with Accesses"
  *Proceedings of the 20th International Symposium on High-Performance Computer Architecture (**HPCA**)*, Orlando, FL, February 2014.
  [Summary] [Slides (pptx) (pdf)]

Reducing Performance Impact of DRAM Refresh by Parallelizing Refreshes with Accesses

Kevin Kai-Wei Chang Donghyuk Lee Zeshan Chishti†
Alaa R. Alameldeen† Chris Wilkerson† Yoongu Kim Onur Mutlu
Carnegie Mellon University †Intel Labs

Tackling Refresh: Solutions

- Parallelize refreshes with accesses [Chang+ HPCA'14]

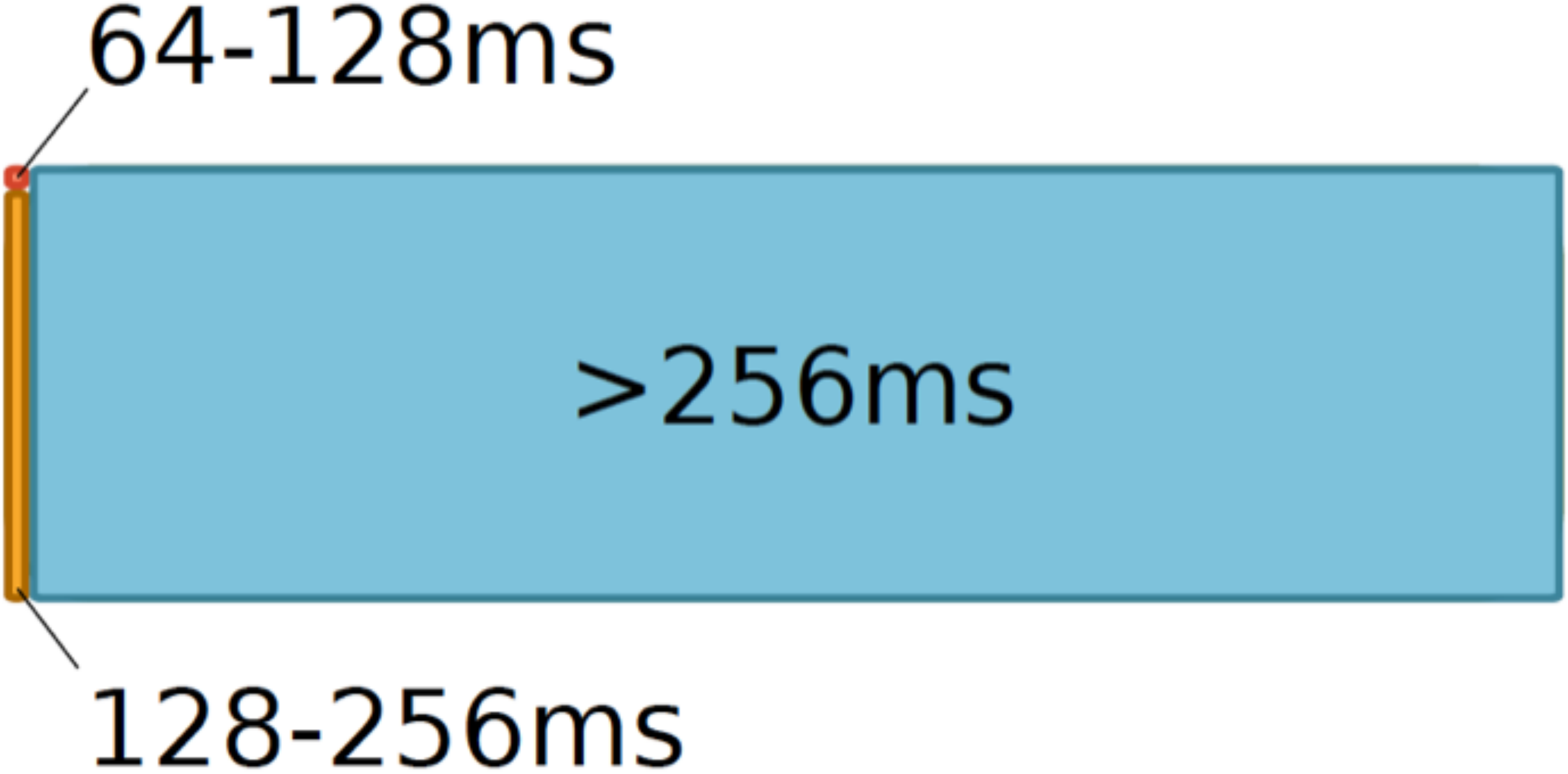
- Eliminate unnecessary refreshes [Liu+ ISCA'12]
  - Exploit device characteristics
  - Exploit data and application characteristics

- Reduce refresh rate and detect+correct errors that occur [Khan+ SIGMETRICS'14]

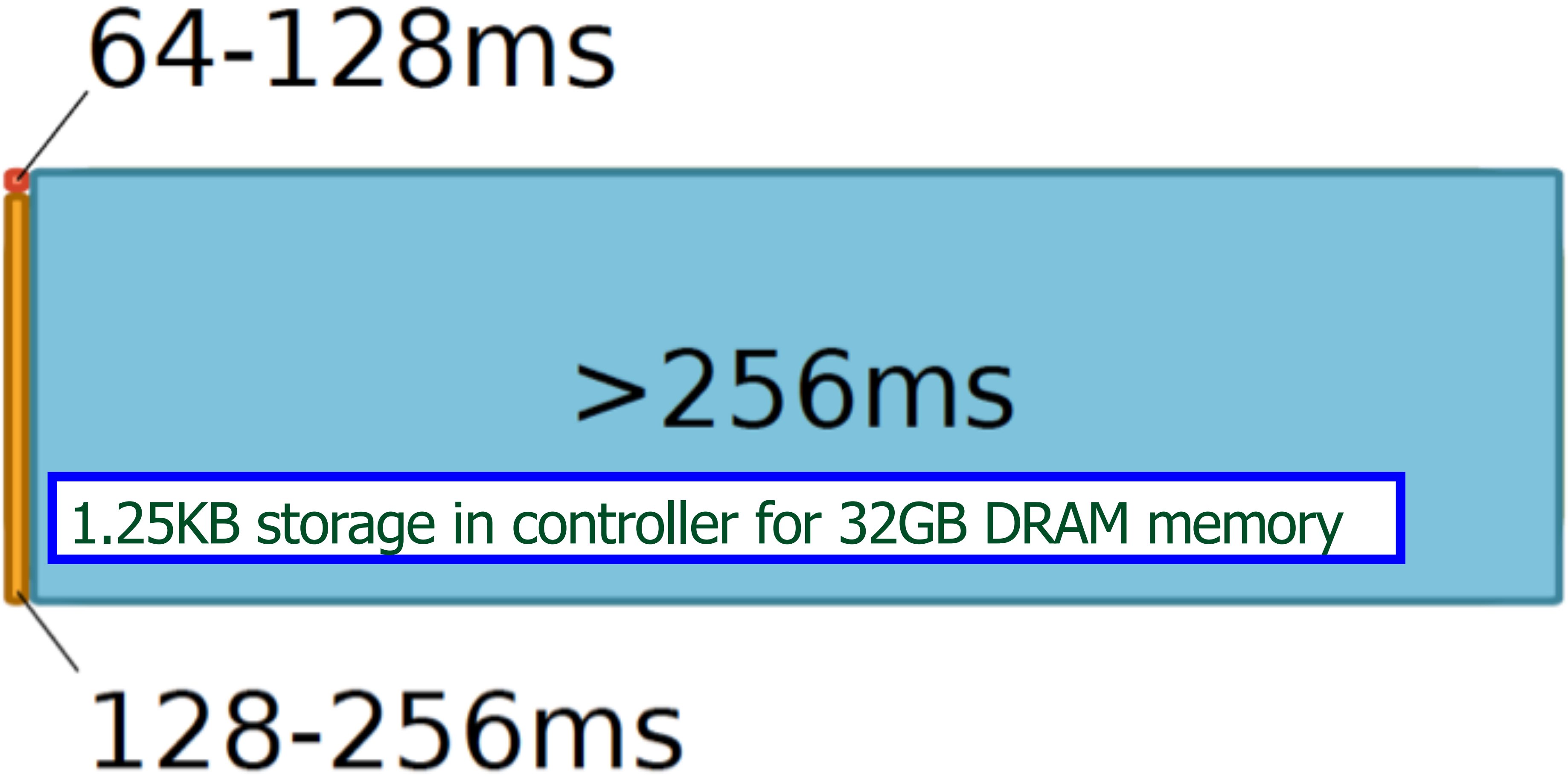
- Understand retention time behavior in DRAM [Liu+ ISCA'13]

Most Refreshes Are Unnecessary

- Retention Time Profile of DRAM looks like this:



RAIDR: Eliminating Unnecessary Refreshes

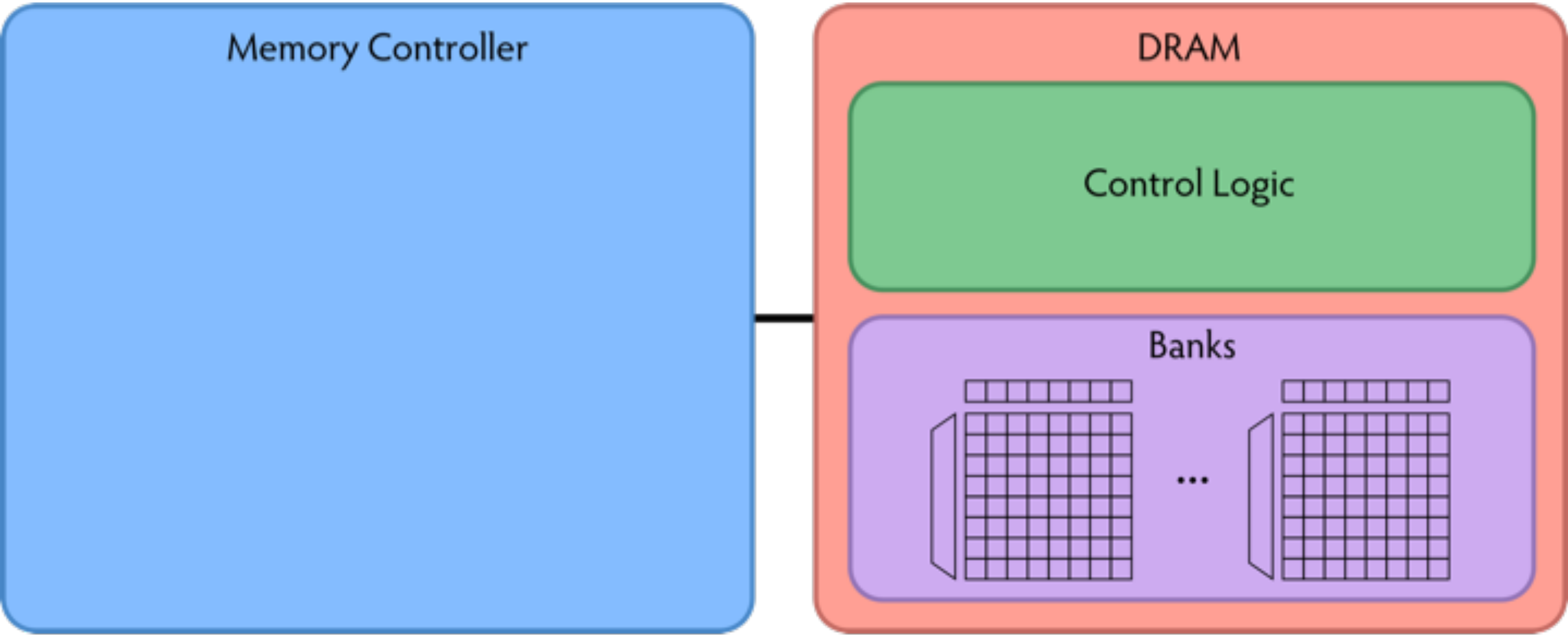


1.25KB storage in controller for 32GB DRAM memory

Can reduce refreshes by ~75%
→ reduces energy consumption and improves performance

Liu et al., "RAIDR: Retention-Aware Intelligent DRAM Refresh," ISCA 2012.

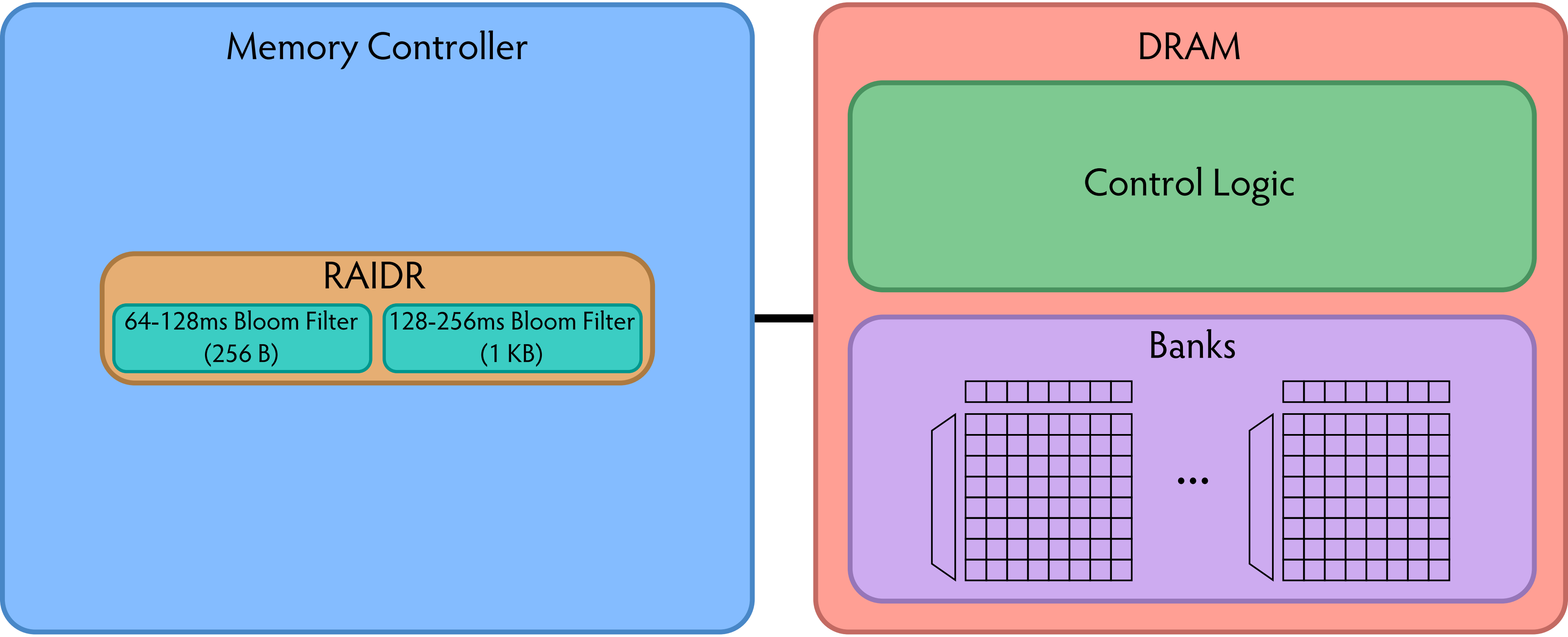
RAIDR: Baseline Design



Refresh control is in DRAM in today's auto-refresh systems

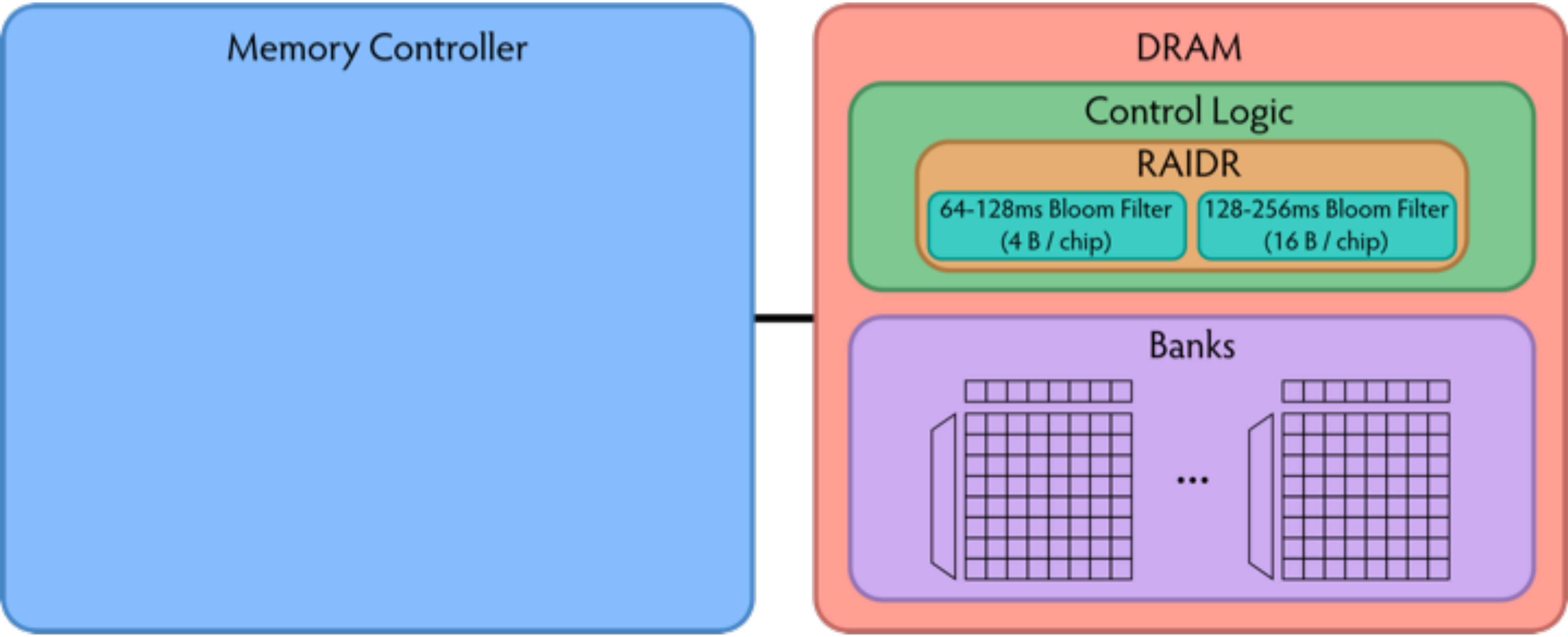
RAIDR can be implemented in either the controller or DRAM

RAIDR in Memory Controller: Option 1



Overhead of RAIDR in DRAM controller:
1.25 KB Bloom Filters, 3 counters, additional commands issued for per-row refresh (all accounted for in evaluations)

RAIDR in DRAM Chip: Option 2



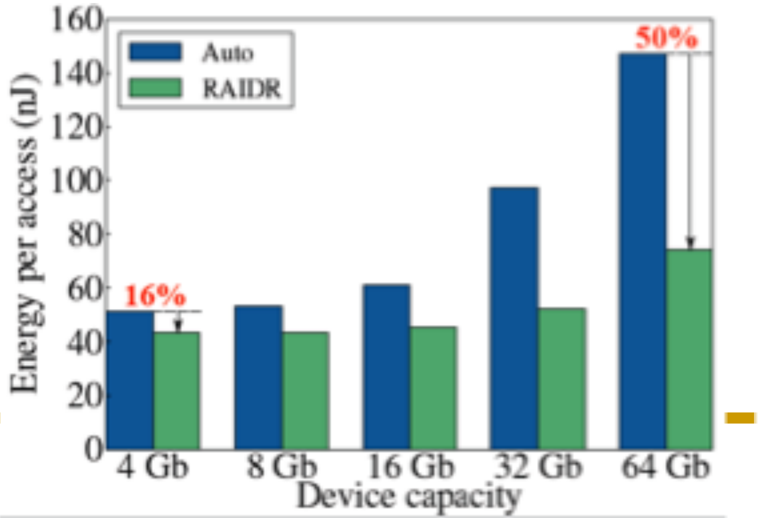
Overhead of RAIDR in DRAM chip:
Per-chip overhead: 20B Bloom Filters, 1 counter (4 Gbit chip)
Total overhead: 1.25KB Bloom Filters, 64 counters (32 GB DRAM)

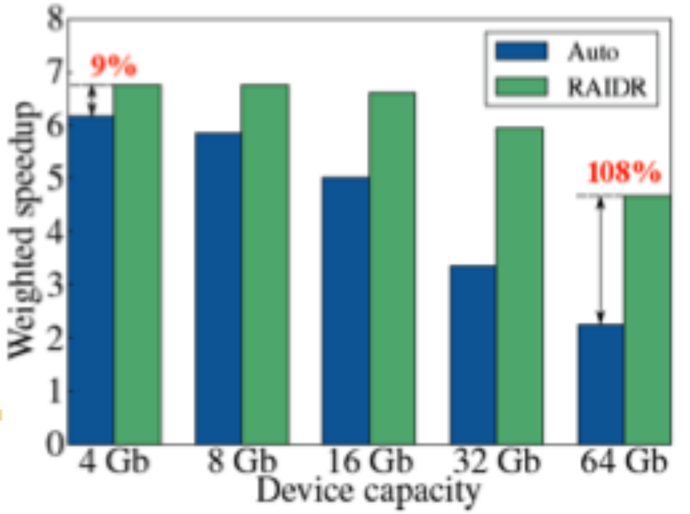
RAIDR: Results and Takeaways

- System: 32GB DRAM, 8-core; SPEC, TPC-C, TPC-H workloads

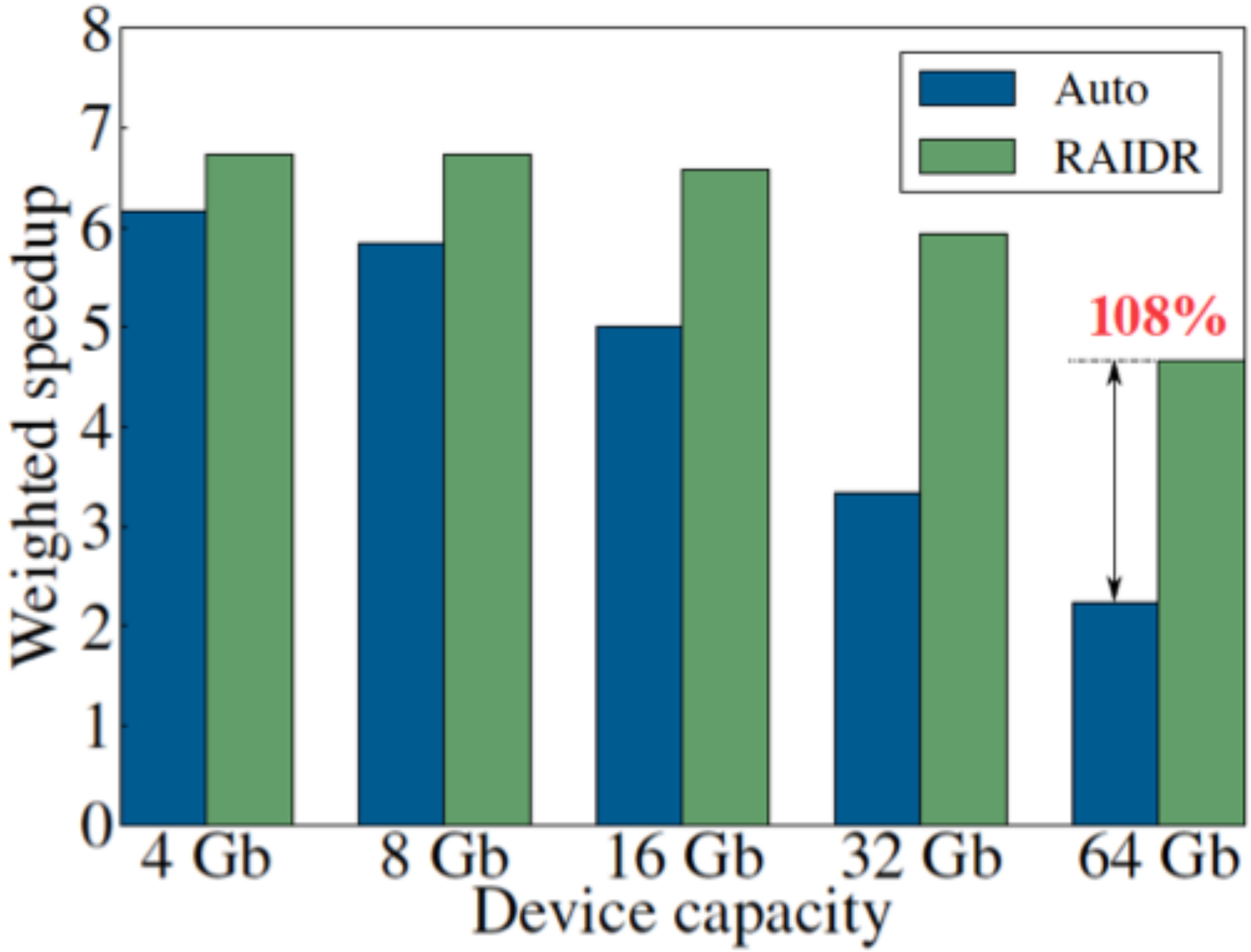
- RAIDR hardware cost: 1.25 kB (2 Bloom filters)
- Refresh reduction: 74.6%
- Dynamic DRAM energy reduction: 16%
- Idle DRAM power reduction: 20%
- Performance improvement: 9%

- Benefits increase as DRAM scales in density





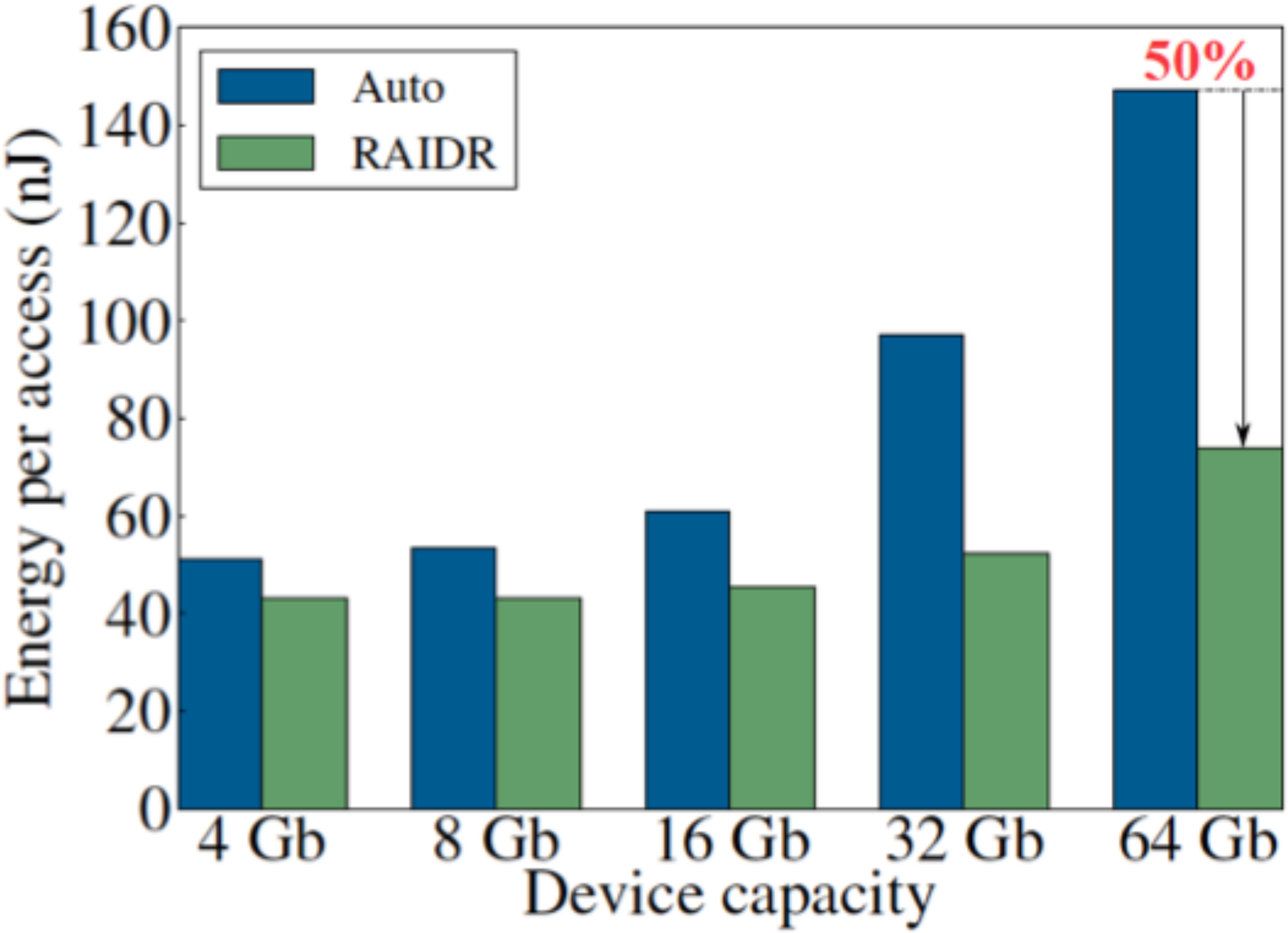
DRAM Device Capacity Scaling: Performance



RAIDR performance benefits increase with DRAM chip capacity

Liu et al., "RAIDR: Retention-Aware Intelligent DRAM Refresh," ISCA 2012.

DRAM Device Capacity Scaling: Energy

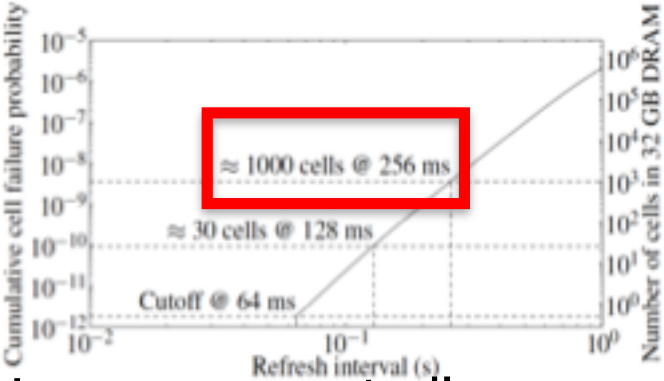


RAIDR energy benefits increase with DRAM chip capacity

Liu et al., "RAIDR: Retention-Aware Intelligent DRAM Refresh," ISCA 2012.

RAIDR: Eliminating Unnecessary Refreshes

- Observation: Most DRAM rows can be refreshed much less often without losing data **[Kim+, EDL'09][Liu+ ISCA'13]**

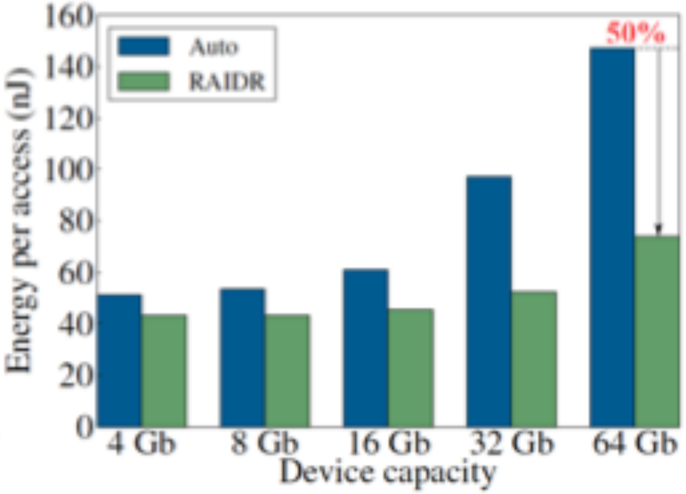


- Key idea: Refresh rows containing weak cells more frequently, other rows less frequently

  1. Profiling: Profile retention time of all rows
  2. Binning: Store rows into bins by retention time in memory controller

     Efficient storage with Bloom Filters (only 1.25KB for 32GB memory)
  3. Refreshing: Memory controller refreshes rows in different bins at different rates

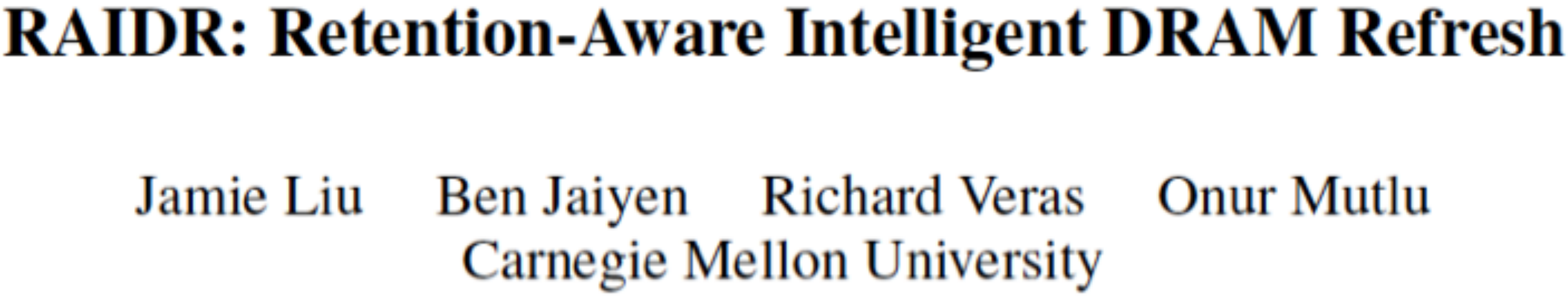
- Results: 8-core, 32GB, SPEC, TPC-C, TPC-H
  - 74.6% refresh reduction @ 1.25KB storage
  - ~16%/20% DRAM dynamic/idle power reduction
  - ~9% performance improvement
  - Benefits increase with DRAM capacity



Liu et al., "RAIDR: Retention-Aware Intelligent DRAM Refresh," ISCA 2012.

More on RAIDR

- Jamie Liu, Ben Jaiyen, Richard Veras, and Onur Mutlu, **"RAIDR: Retention-Aware Intelligent DRAM Refresh"** *Proceedings of the 39th International Symposium on Computer Architecture* (***ISCA***), Portland, OR, June 2012. Slides (pdf)



RAIDR: Retention-Aware Intelligent DRAM Refresh

Jamie Liu   Ben Jaiyen   Richard Veras   Onur Mutlu
Carnegie Mellon University

Tackling Refresh: Solutions

- Parallelize refreshes with accesses [Chang+ HPCA'14]

- Eliminate unnecessary refreshes [Liu+ ISCA'12]
  - Exploit device characteristics
  - Exploit data and application characteristics

- Reduce refresh rate and detect+correct errors that occur [Khan+ SIGMETRICS'14]

- Understand retention time behavior in DRAM [Liu+ ISCA'13]

Motivation: Understanding Retention

- Past works require accurate and reliable measurement of retention time of each DRAM row
  - To maintain data integrity while reducing refreshes

- Assumption: worst-case retention time of each row can be determined and stays the same at a given temperature
  - Some works propose writing all 1's and 0's to a row, and measuring the time before data corruption

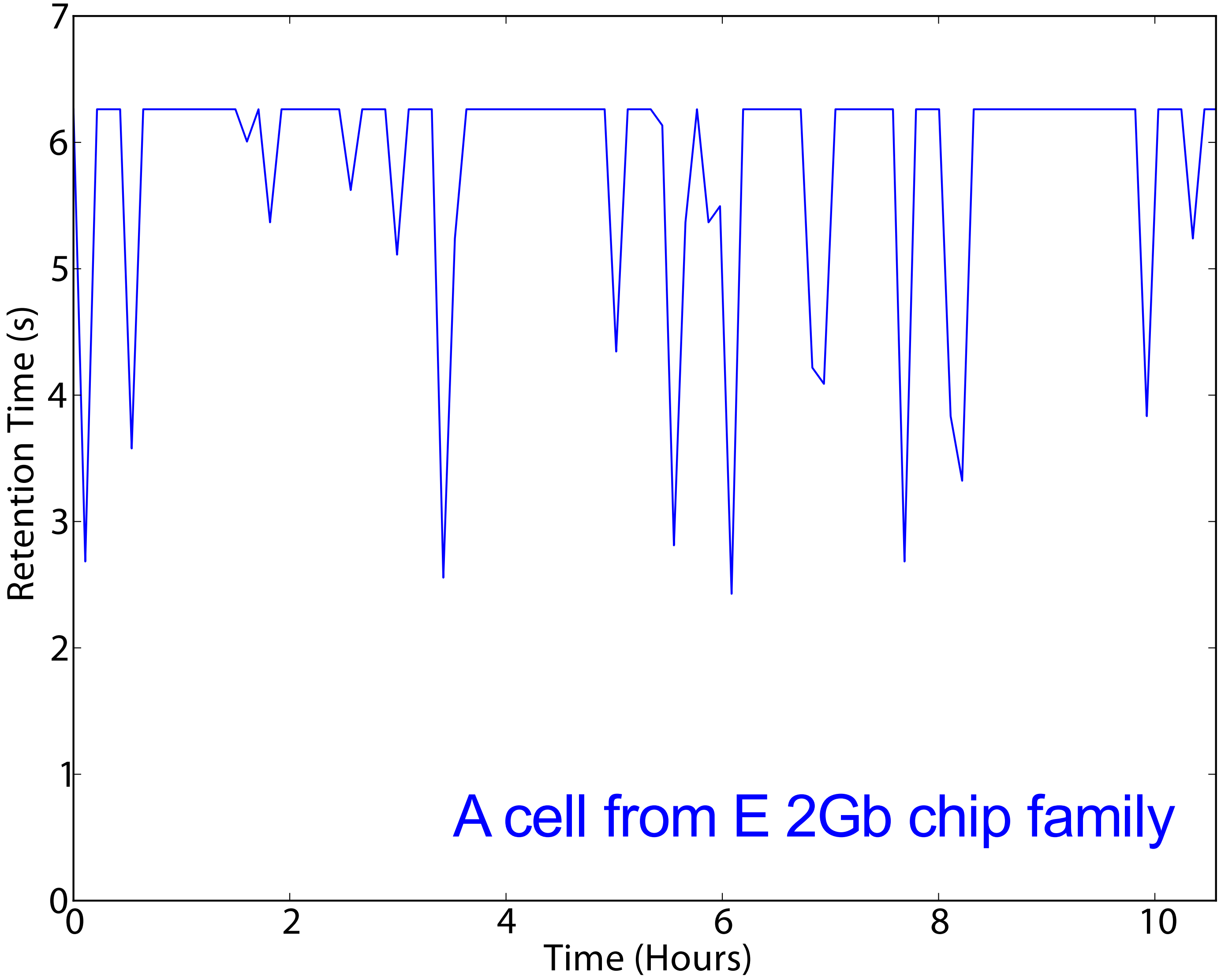
- Question:
  - Can we reliably and accurately determine retention times of all DRAM rows?

Two Challenges to Retention Time Profiling

- Data Pattern Dependence (DPD) of retention time

- Variable Retention Time (VRT) phenomenon

An Example VRT Cell



A cell from E 2Gb chip family

VRT: Implications on Profiling Mechanisms

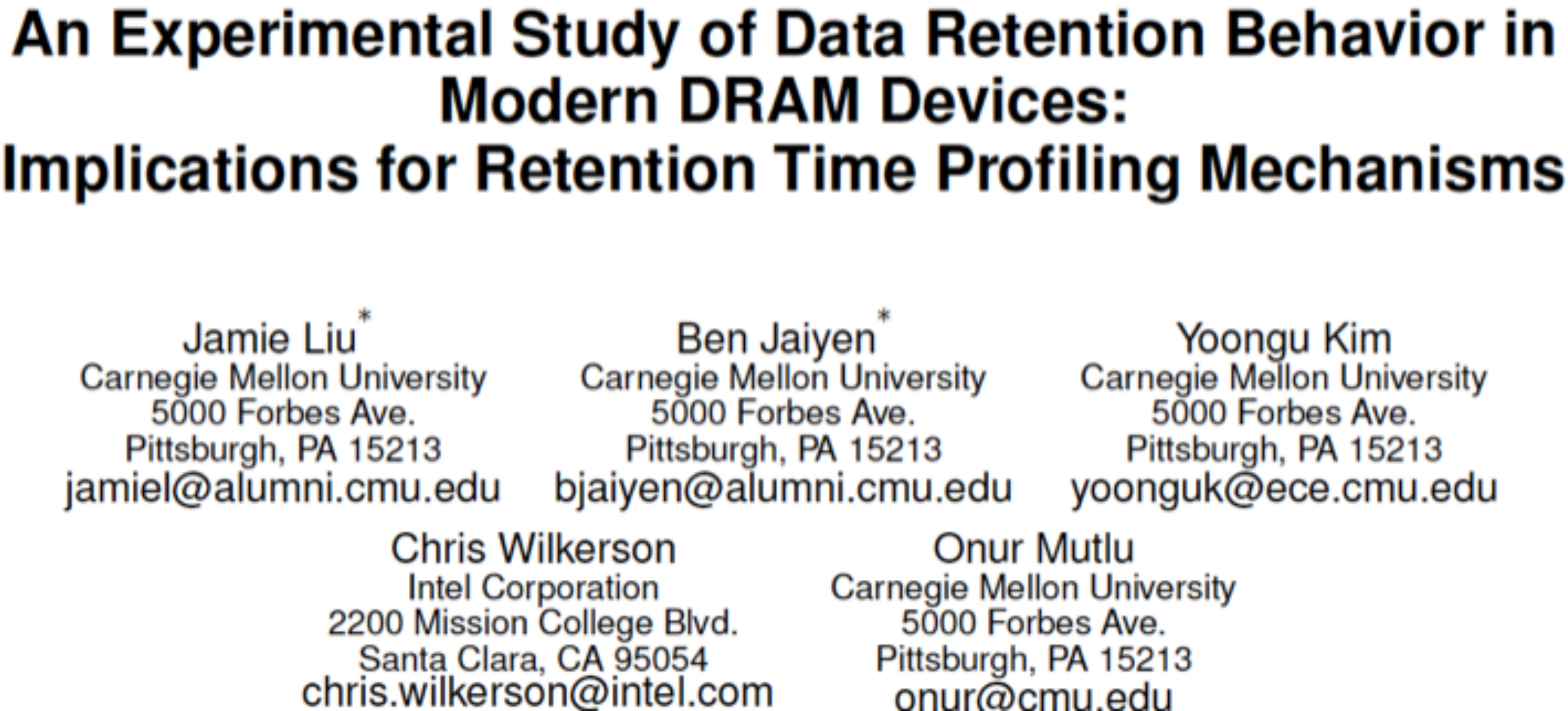
- Problem 1: There does not seem to be a way of determining if a cell exhibits VRT without actually observing a cell exhibiting VRT
  - VRT is a memoryless random process **[Kim+ JJAP 2010]**

- Problem 2: VRT complicates retention time profiling by DRAM manufacturers
  - Exposure to very high temperatures can induce VRT in cells that were not previously susceptible
    → can happen during soldering of DRAM chips
    → manufacturer's retention time profile may not be accurate

- One option for future work: Use ECC to continuously profile DRAM online while aggressively reducing refresh rate
  - Need to keep ECC overhead in check

More on DRAM Retention Analysis

- Jamie Liu, Ben Jaiyen, Yoongu Kim, Chris Wilkerson, and Onur Mutlu, **"An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms"** *Proceedings of the 40th International Symposium on Computer Architecture* (***ISCA***), Tel-Aviv, Israel, June 2013. Slides (ppt) Slides (pdf)



An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms

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- Understand retention time behavior in DRAM [Liu+ ISCA'13]

Towards an Online Profiling System

Key Observations:

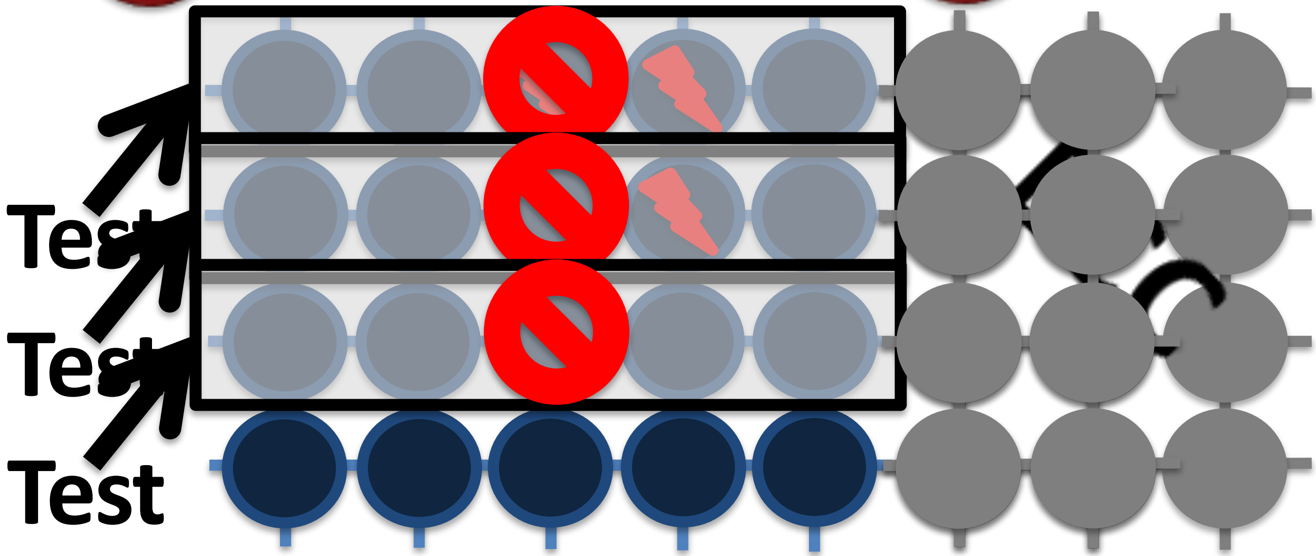
- Testing alone cannot detect all possible failures
- Combination of ECC and other mitigation techniques is much more effective
  - But degrades performance
- Testing can help to reduce the ECC strength
  - Even when starting with a higher strength ECC

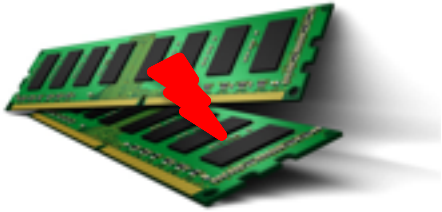
Khan+, "The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study," SIGMETRICS 2014.

Towards an Online Profiling System

Initially Protect DRAM with Strong ECC 1

Periodically Test Parts of DRAM 2





Mitigate errors and reduce ECC 3

Run tests periodically after a short interval at smaller regions of memory

More on Online Profiling of DRAM

- Samira Khan, Donghyuk Lee, Yoongu Kim, Alaa Alameldeen, Chris Wilkerson, and Onur Mutlu,
  "The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study"
  Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (***SIGMETRICS***), Austin, TX, June 2014. [Slides (pptx) (pdf)] [Poster (pptx) (pdf)] [Full data sets]

The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study

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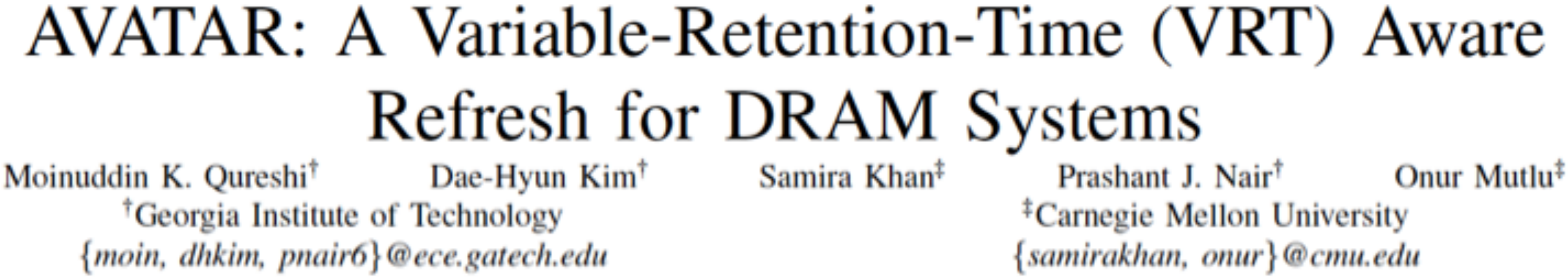
[†]Carnegie Mellon University [*]Intel Labs

How Do We Make RAIDR Work in the Presence of the VRT Phenomenon?

Making RAIDR Work w/ Online Profiling & ECC

- Moinuddin Qureshi, Dae Hyun Kim, Samira Khan, Prashant Nair, and Onur Mutlu,
  "AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems"
  *Proceedings of the 45th Annual IEEE/IFIP International Conference on Dependable Systems and Networks (**DSN**)*, Rio de Janeiro, Brazil, June 2015.
  [Slides (pptx) (pdf)]



AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems

Moinuddin K. Qureshi[†] Dae-Hyun Kim[†] Samira Khan[‡] Prashant J. Nair[†] Onur Mutlu[‡]

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{moin, dhkim, pnair6}@ece.gatech.edu

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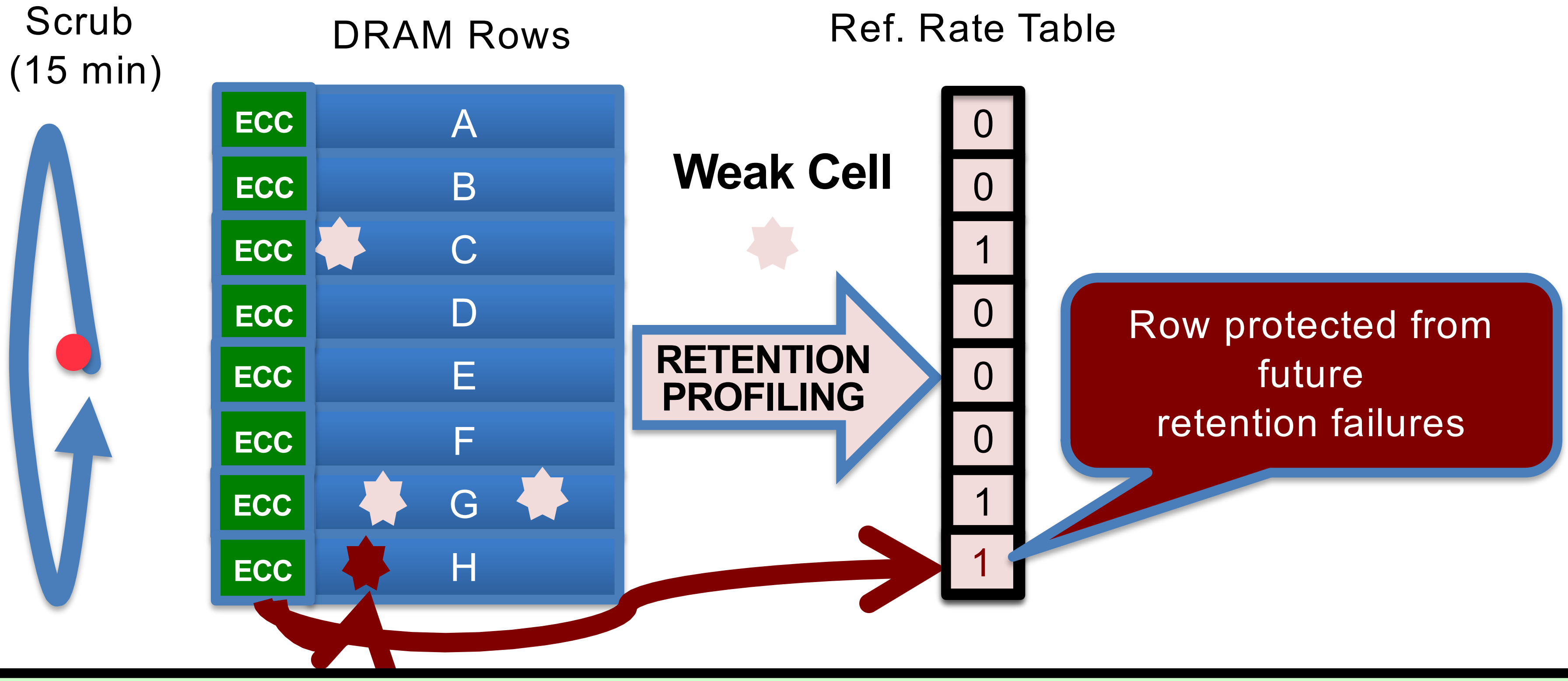
AVATAR

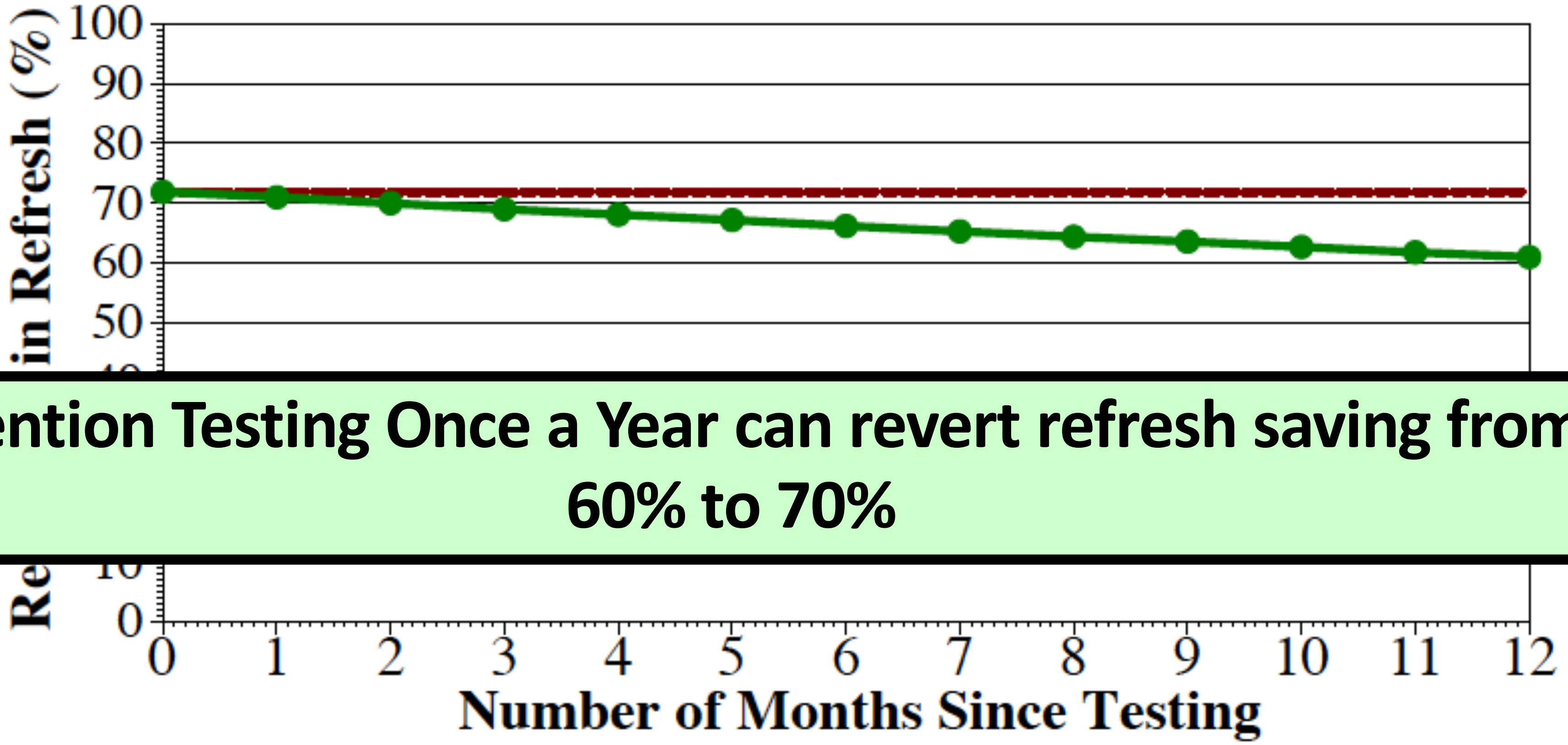
Insight: Avoid retention failures ➔ Upgrade row on ECC error

Observation: Rate of VRT >> Rate of soft error (50x-2500x)



AVATAR mitigates VRT by increasing refresh rate on error

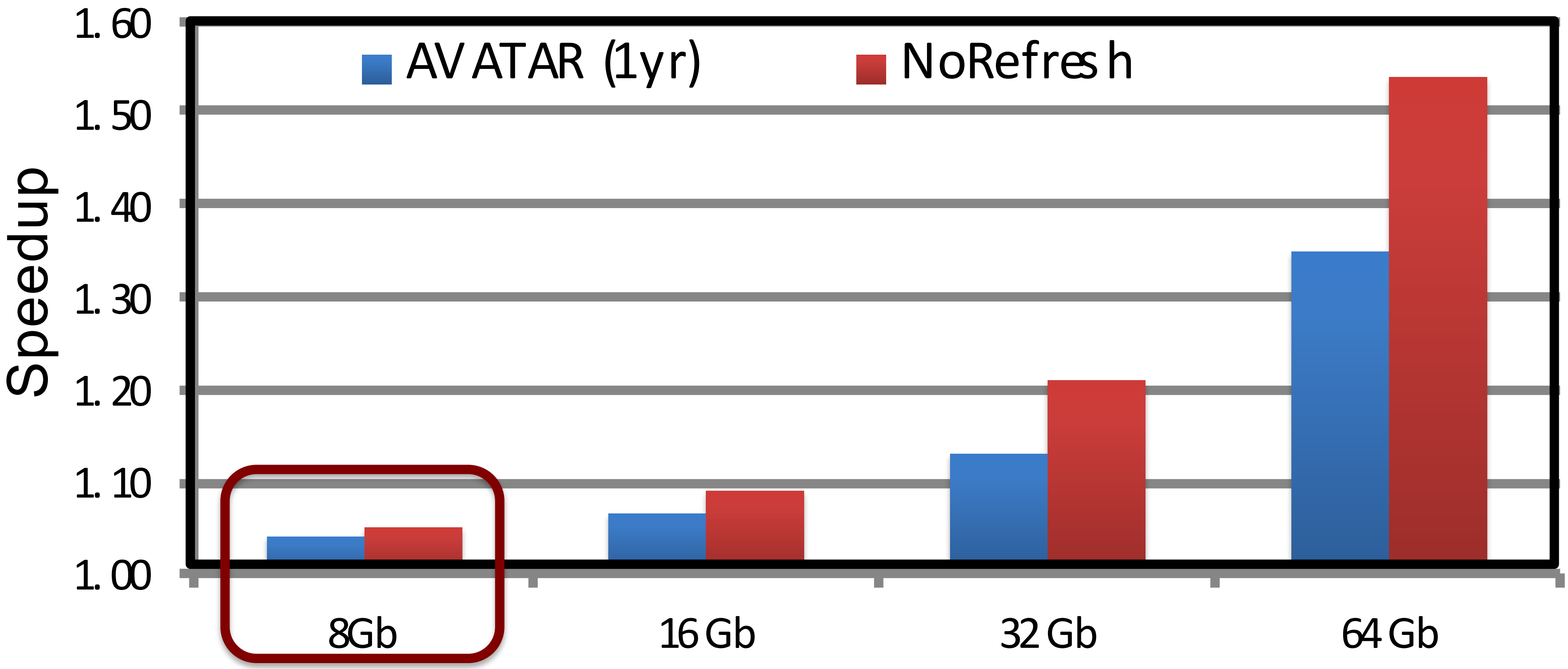
RESULTS: REFRESH SAVINGS



Retention Testing Once a Year can revert refresh saving from 60% to 70%

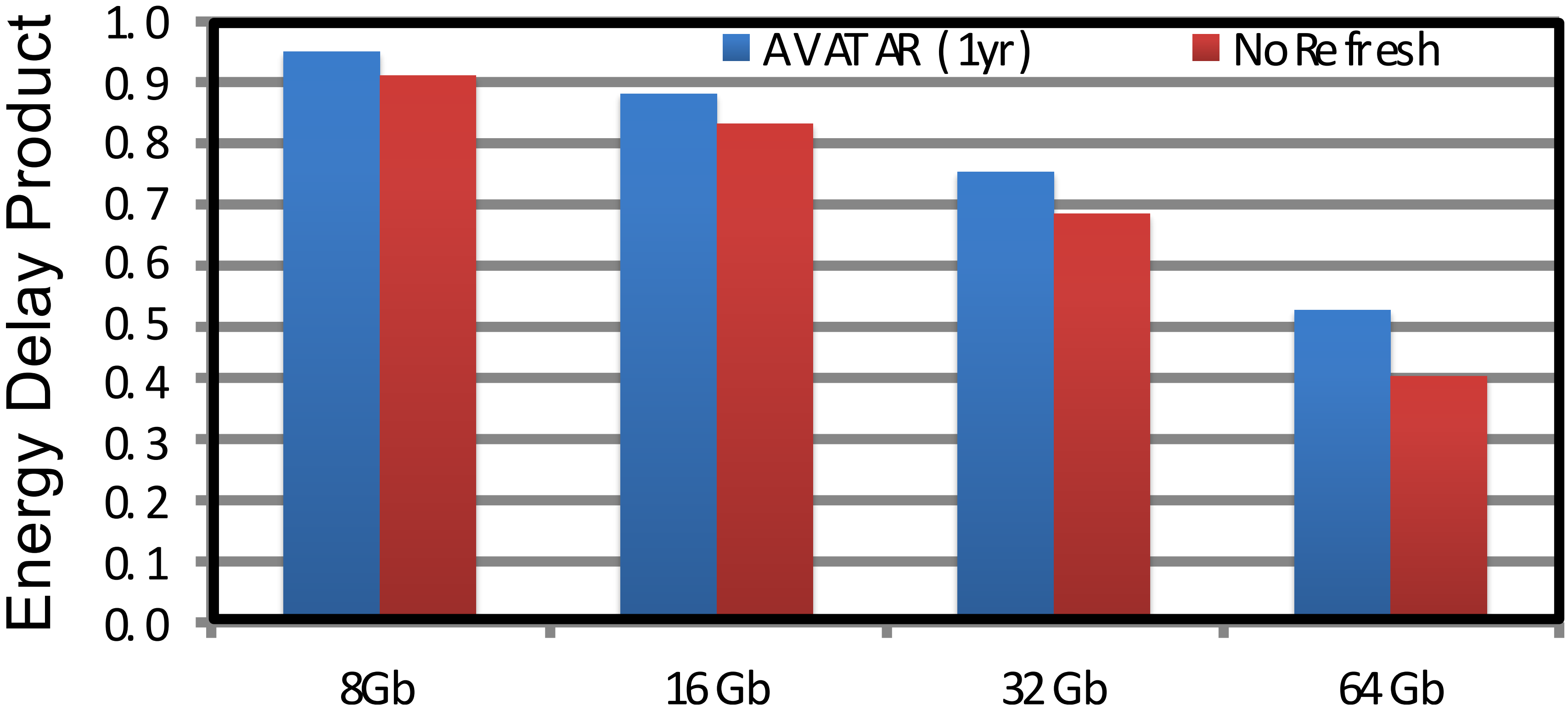
AVATAR reduces refresh by 60%-70%, similar to multi rate refresh but with VRT tolerance

SPEEDUP



AVATAR gets 2/3rd the performance of NoRefresh. More gains at higher capacity nodes

ENERGY DELAY PRODUCT



AVATAR reduces EDP,
Significant reduction at higher capacity nodes

Making RAIDR Work w/ Online Profiling & ECC

- Moinuddin Qureshi, Dae Hyun Kim, Samira Khan, Prashant Nair, and Onur Mutlu,
  "AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems"
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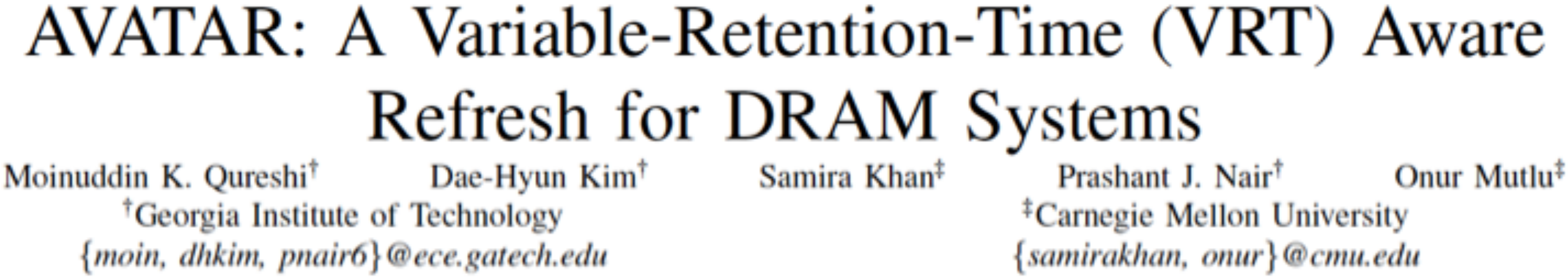


AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems

Moinuddin K. Qureshi[†] Dae-Hyun Kim[†] Samira Khan[‡] Prashant J. Nair[†] Onur Mutlu[‡]

[†]Georgia Institute of Technology
{moin, dhkim, pnair6}@ece.gatech.edu

[‡]Carnegie Mellon University
{samirakhan, onur}@cmu.edu

DRAM Refresh: Summary and Conclusions

- DRAM refresh is a critical challenge
  - in scaling DRAM technology efficiently to higher capacities

- Discussed several promising solution directions
  - Parallelize refreshes with accesses [Chang+ HPCA'14]
  - Eliminate unnecessary refreshes [Liu+ ISCA'12]
  - Reduce refresh rate and detect+correct errors that occur [Khan+ SIGMETRICS'14]

- Examined properties of retention time behavior [Liu+ ISCA'13]
  - Enable realistic VRT-Aware refresh techniques [Qureshi+ DSN'15]

- Many avenues for overcoming DRAM refresh challenges
  - Handling DPD/VRT phenomena
  - Enabling online retention time profiling and error mitigation
  - Exploiting application behavior

Other Backup Slides

Google Workloads for Consumer Devices: Mitigating Data Movement Bottlenecks

Amirali Boroumand

Saugata Ghose, Youngsok Kim, Rachata Ausavarungnirun,
Eric Shiu, Rahul Thakur, Daehyun Kim, Aki Kuusela,
Allan Knies, Parthasarathy Ranganathan, Onur Mutlu

Consumer Devices

Consumer devices are everywhere!

Energy consumption is a first-class concern in consumer devices

Popular Google Consumer Workloads

Chrome

Google's web browser

TensorFlow Mobile

Google's machine learning framework

VP9

YouTube

Video Playback

Google's video codec

VP9

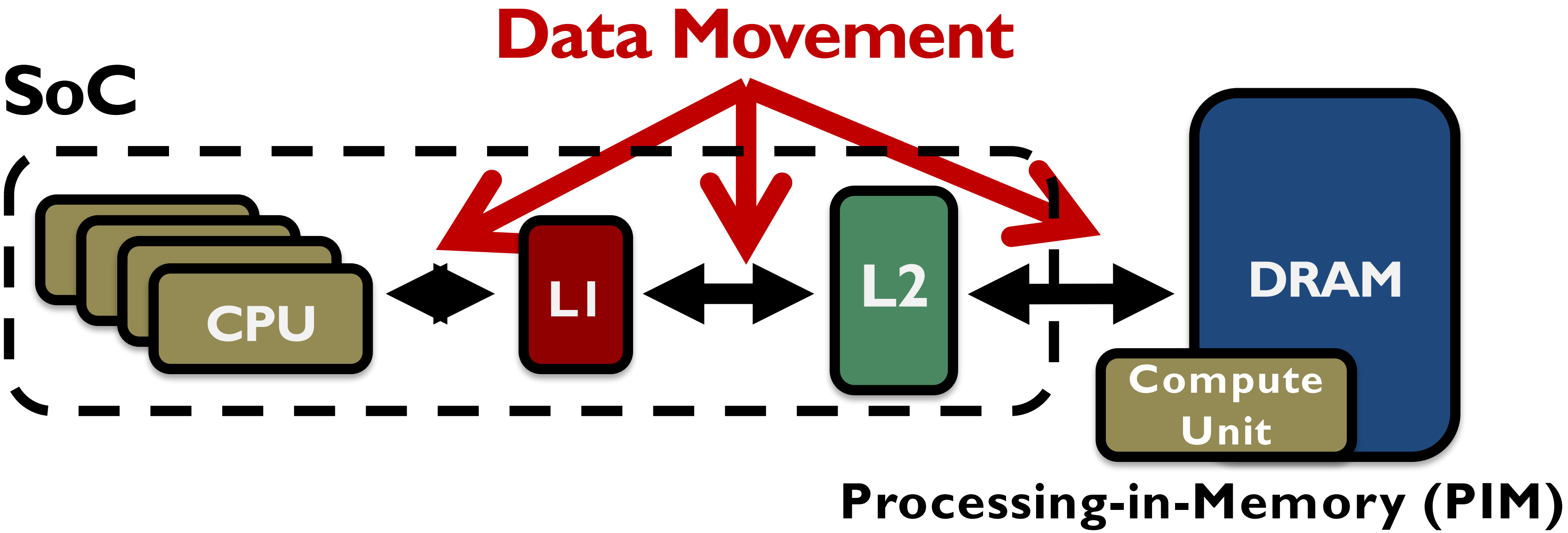
YouTube

Video Capture

Google's video codec

Energy Cost of Data Movement

1st key observation: 62.7% of the total system energy is spent on data movement



Potential solution: move computation close to data

Challenge: limited area and energy budget

Using PIM to Reduce Data Movement

2nd key observation: a significant fraction of data movement often comes from simple functions

We can design lightweight logic to implement these *simple functions* in memory

Small embedded low-power core

PIM Core

Small fixed-function accelerators

PIM Accelerator

Offloading to PIM logic reduces energy by 55.4% and improves performance by 54.2% on average

Goals

1 Understand the data movement related bottlenecks in modern consumer workloads

2 Analyze opportunities to mitigate data movement by using processing-in-memory (PIM)

3 Design PIM logic that can maximize energy efficiency given the limited area and energy budget in consumer devices

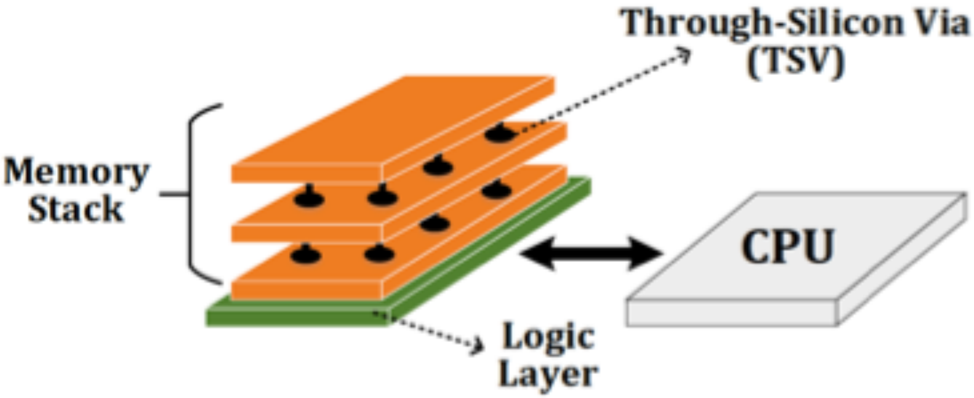
Outline

- Introduction
- **Background**
- Analysis Methodology
- Workload Analysis
- Evaluation
- Conclusion

Potential Solution to Address Data Movement

- **Processing-in-Memory (PIM)**
  - A potential solution to **reduce data movement**
  - **Idea:** move computation close to data
    - ✓ Reduces data movement
    - ✓ Exploits large in-memory bandwidth
    - ✓ Exploits shorter access latency to memory

- **Enabled by recent advances in 3D-stacked memory**



Outline

- Introduction
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- **Analysis Methodology**
- Workload Analysis
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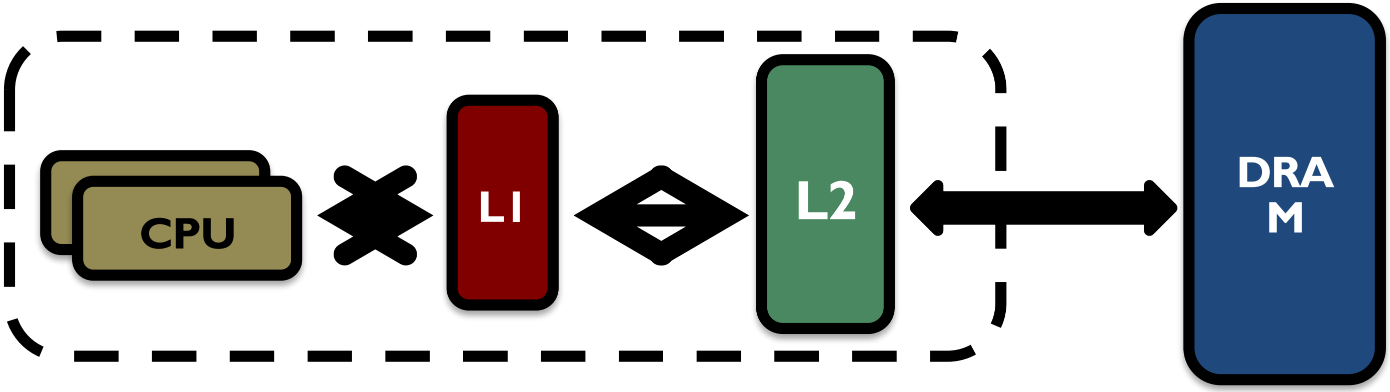
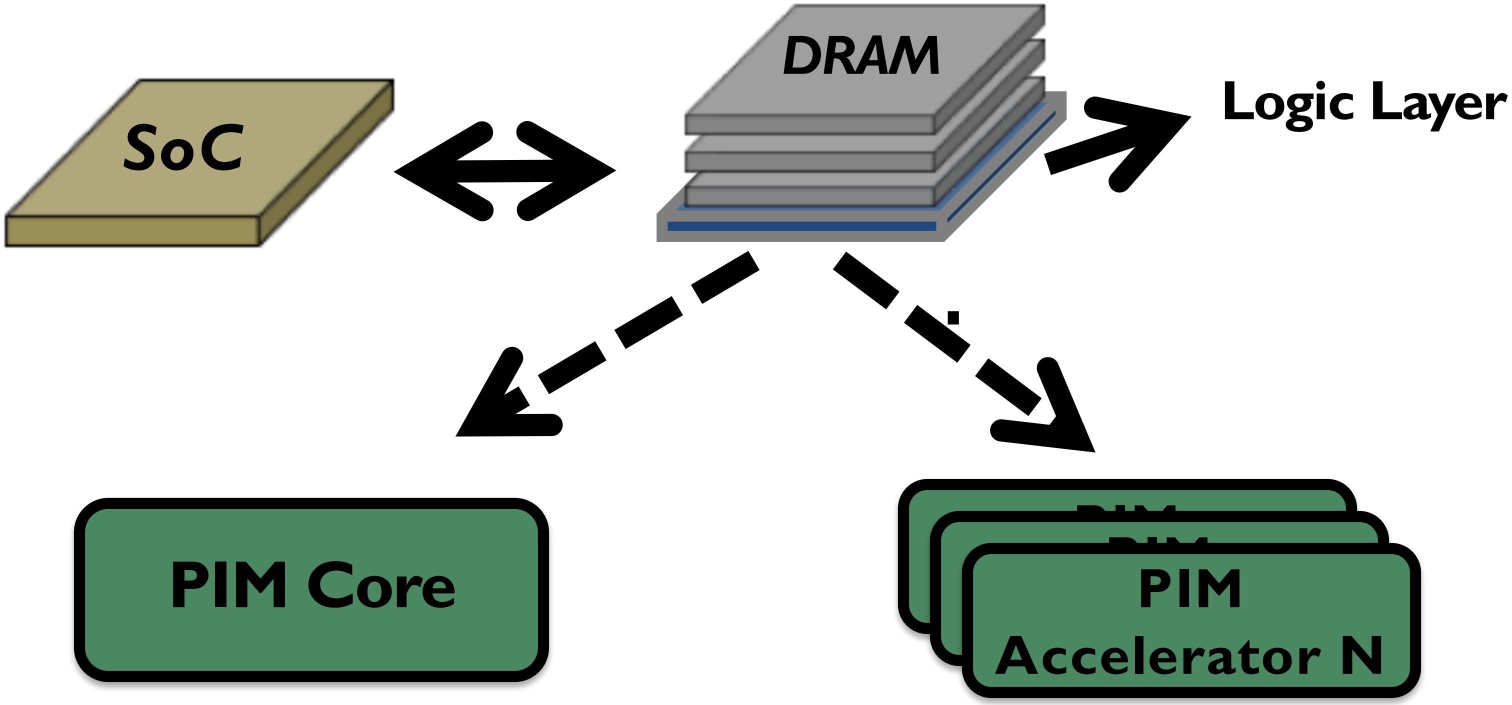
- Conclusion

Workload Analysis Methodology

- **Workload Characterization**
  - Chromebook with an Intel Celeron SoC and 2GB of DRAM
  - Extensively use performance counters within SoC
- **Energy Model**
  - Sum of the energy consumption within the **CPU**, **all caches**, **off-chip interconnects**, and **DRAM**



PIM Logic Implementation



SoC

DRAM

Logic Layer

PIM Core

PIM Accelerator N

Customized embedded general-purpose core

No aggressive ILP techniques

256-bit SIMD unit

Small fixed-function accelerators

Multiple copies of customized in-memory logic unit

Workload Analysis

Chrome

Google's web browser

TensorFlow

Google's machine learning framework

Video Playback

Google's **video codec**

Video Capture

Google's **video Codec**

Workload Analysis

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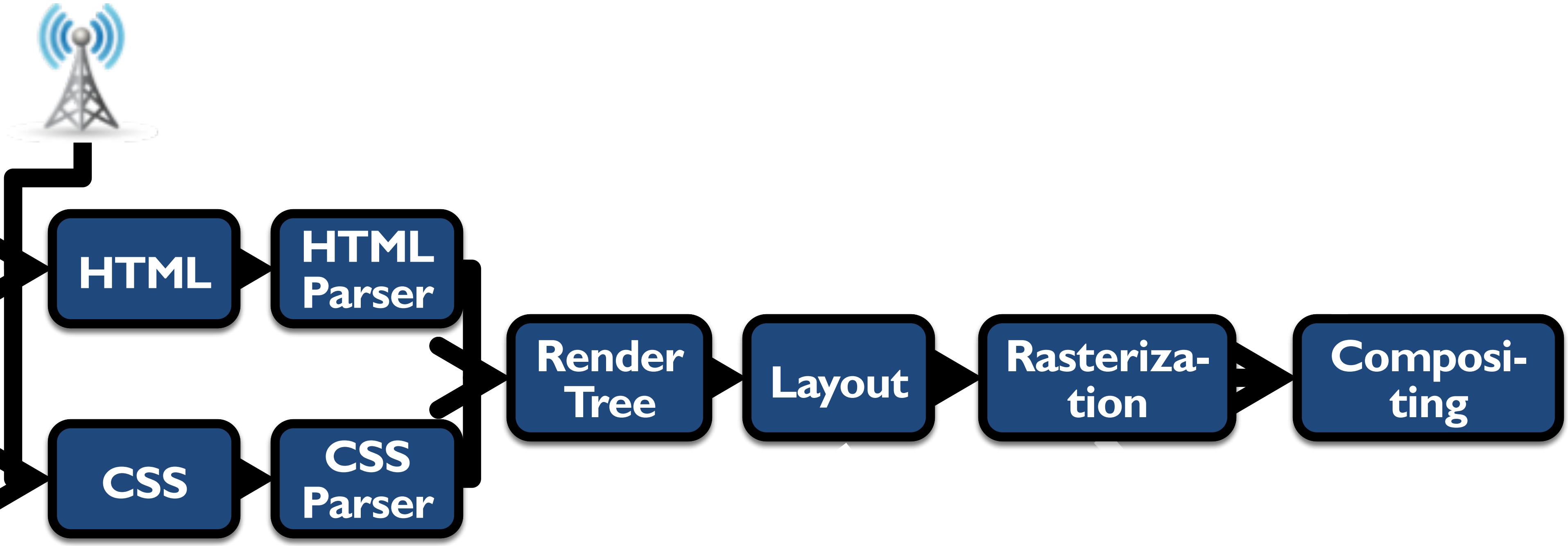
How Chrome Renders a Web Page



HTML

HTML Parser

CSS

CSS Parser

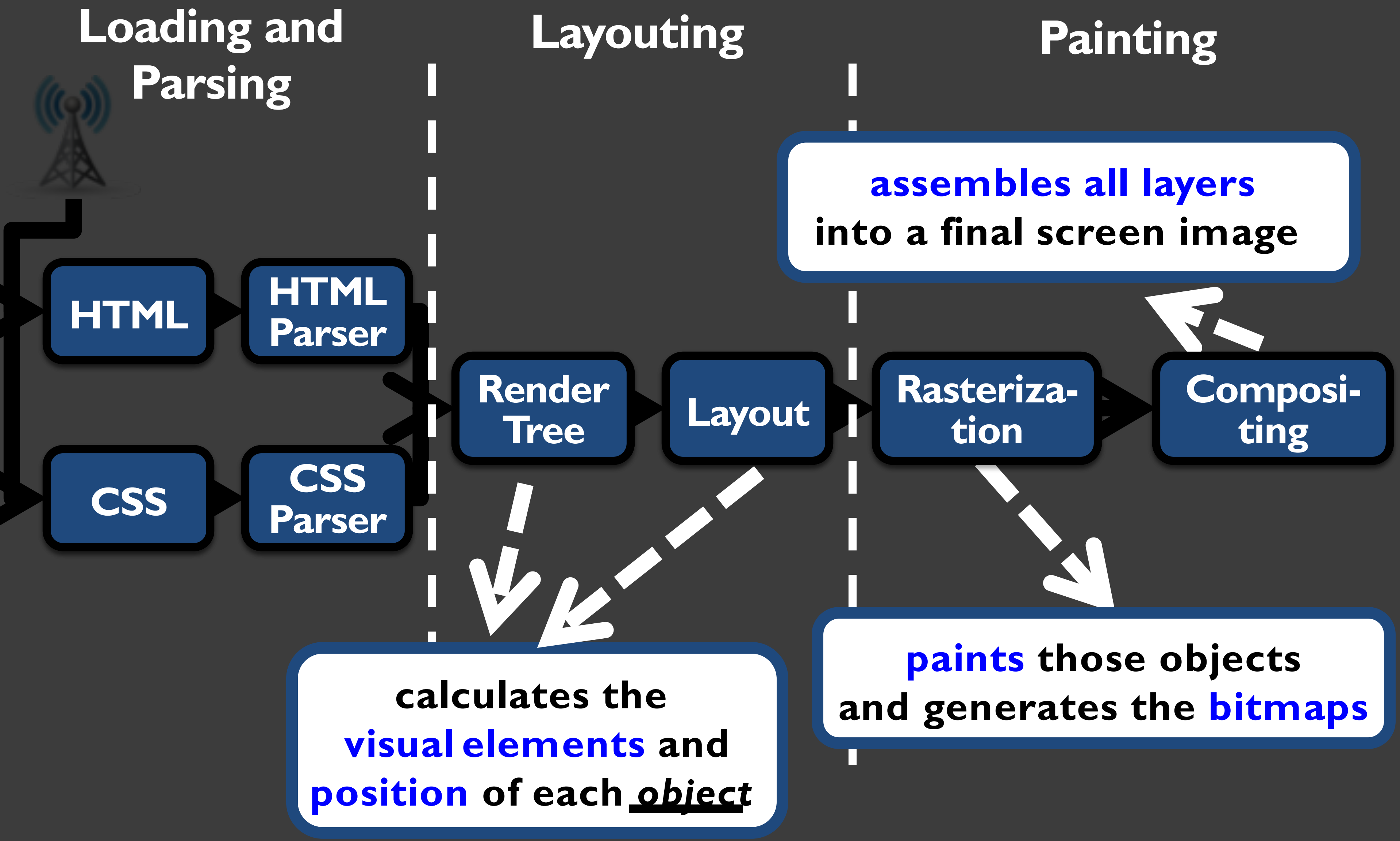
Render Tree

Layout

Rasterization

Compositing

How Chrome Renders a Web Page



Loading and Parsing

Layouting

Painting

HTML

HTML Parser

CSS

CSS Parser

Render Tree

Layout

Rasterization

Compositing

assembles all layers into a final screen image

calculates the **visual elements** and **position** of each *object*

paints those objects and generates the **bitmaps**

Browser Analysis

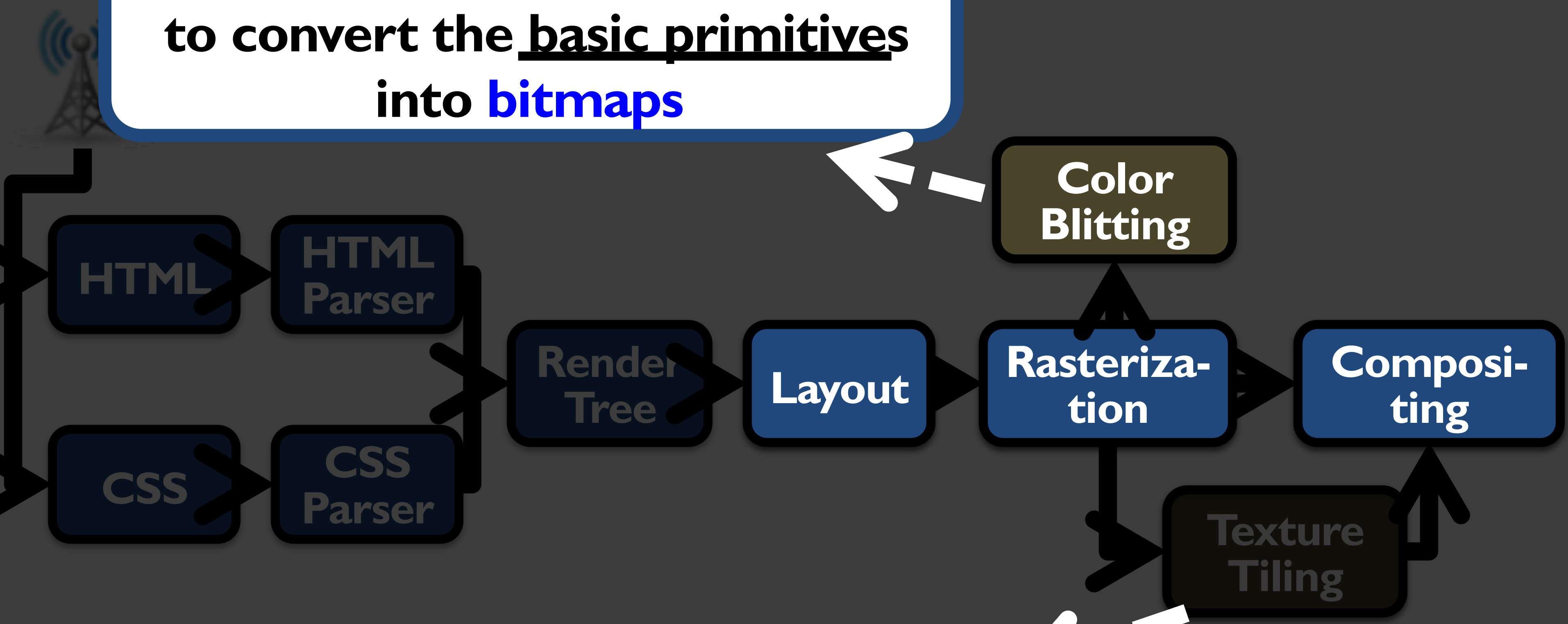
- **To satisfy user experience, the browser must provide:**
  - Fast **loading** of webpages
  - Smooth **scrolling** of webpages
  - Quick **switching** between browser tabs

- **We focus on two important user interactions:**
  1) **Page Scrolling**
  2) **Tab Switching**
  - Both include page loading

Scrolling

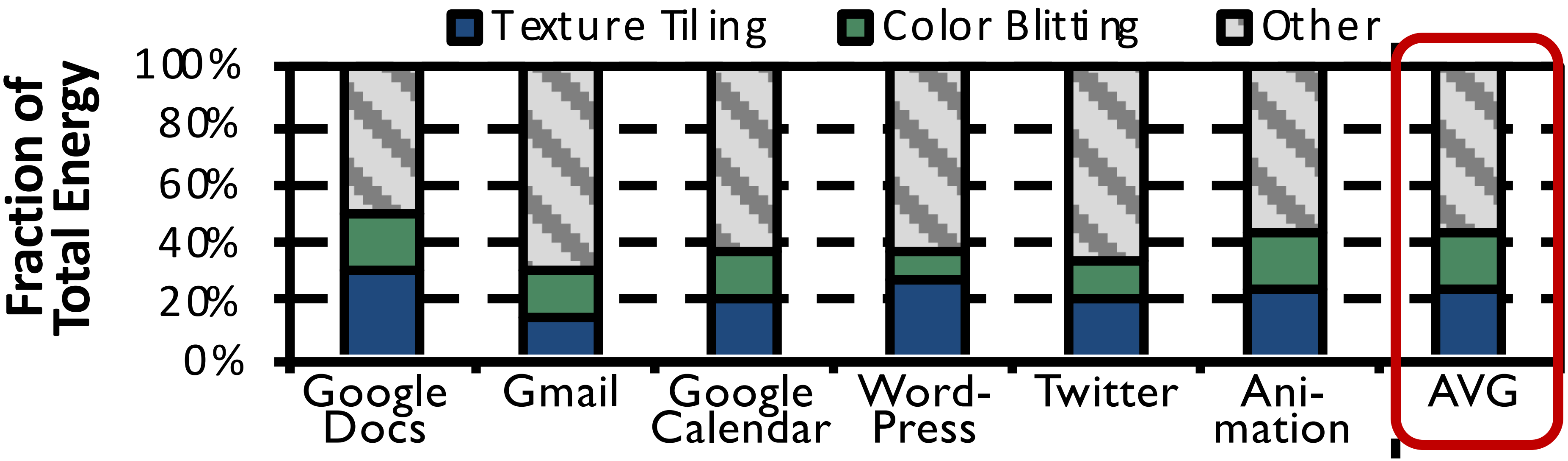
What Does Happen During Scrolling?

rasterization uses color blitters to convert the basic primitives into bitmaps



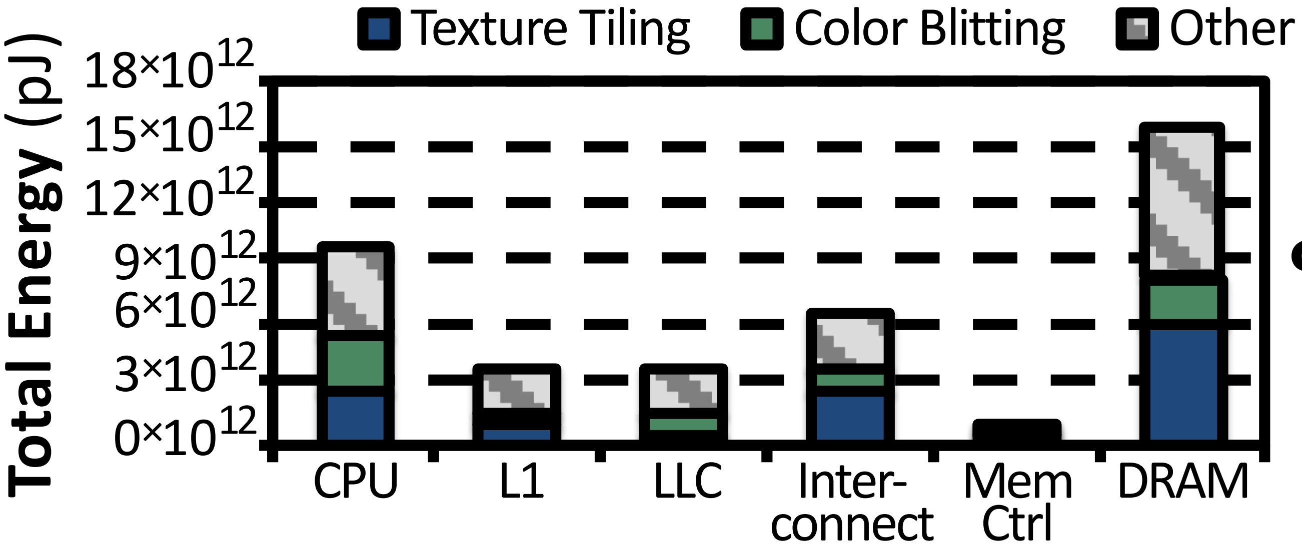
to minimize cache misses during compositing, the graphics driver reorganizes the bitmaps

Scrolling Energy Analysis



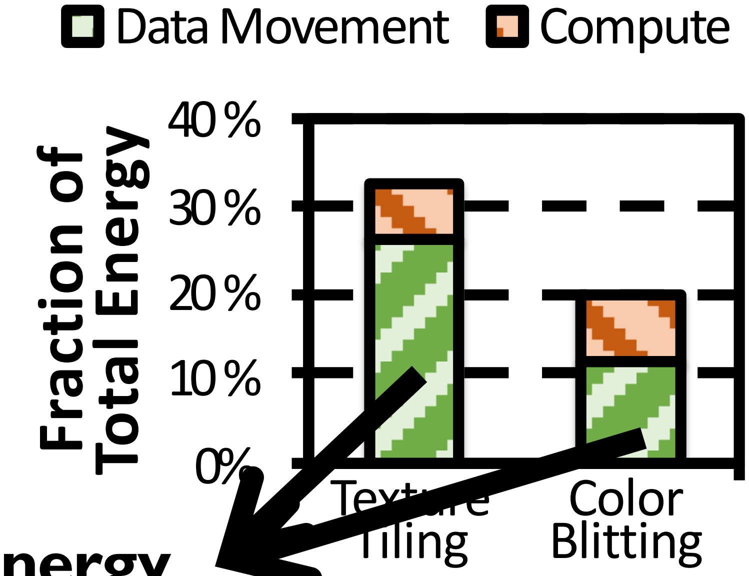
41.9% of page scrolling energy is spent on texture tiling and color blitting

Scrolling a Google Docs Web Page



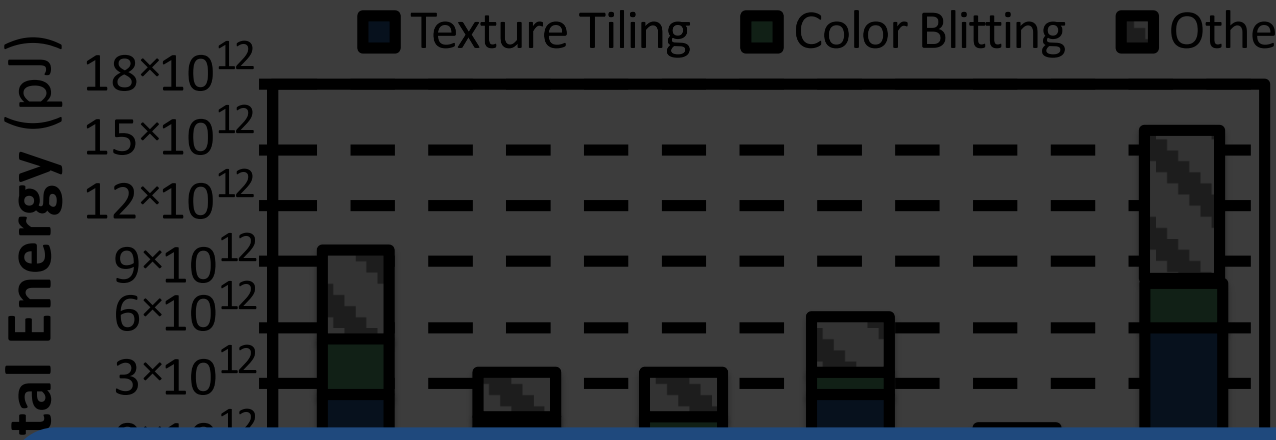
77% of total energy consumption goes to data movement

A significant portion of total data movement comes from texture tiling and color blitting



37.7% of total system energy

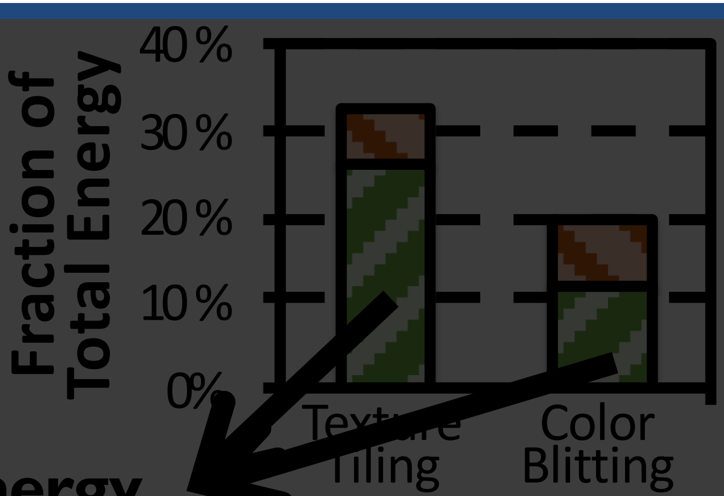
Scrolling a Google Docs Web Page



77% of total energy consumption goes to **data movement**

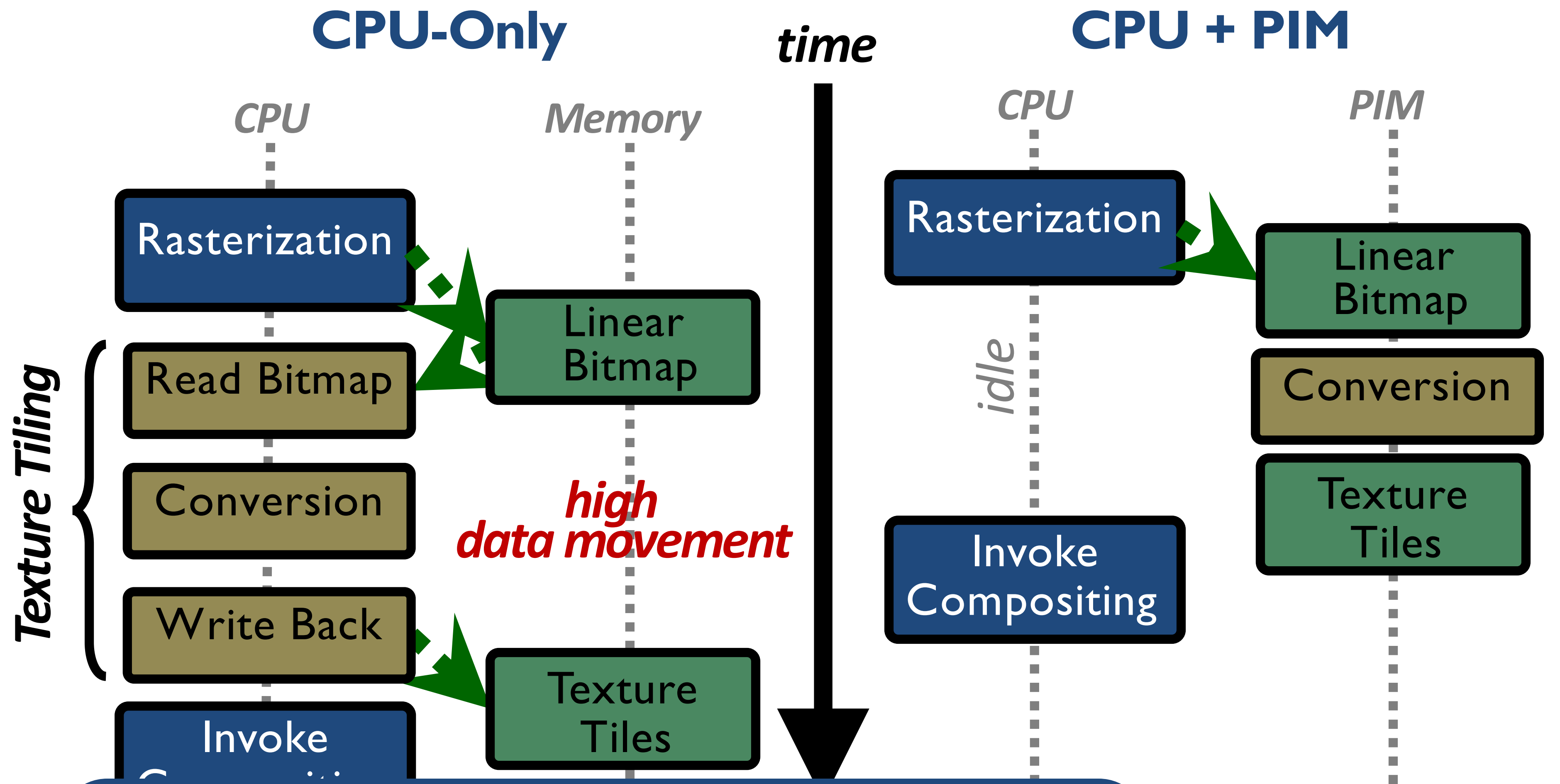
Can we use PIM to mitigate the data movement cost for texture tiling and color blitting?

A significant portion of total data movement comes from **texture tiling** and **color blitting**



37.7% of total system energy

Can We Use PIM for Texture Tiling?



CPU-Only

CPU

Memory

Rasterization

Linear Bitmap

Texture Tiling

Read Bitmap

Conversion

Write Back

high data movement

Texture Tiles

Invoke

time

CPU + PIM

CPU

PIM

Rasterization

Linear Bitmap

idle

Conversion

Texture Tiles

Invoke Compositing

Major sources of data movement:

Texture tiling is a good candidate for PIM execution

Can We Implement Texture Tiling in PIM Logic?

Requires simple primitives: memcopy, bitwise operations, and simple arithmetic operations

PIM Core

9.4% of the area available for PIM logic

PIM Accelerator

7.1% of the area available for PIM logic

PIM core and PIM accelerator are feasible to implement in-memory Texture Tiling

Color Blitting Analysis

Generates a large amount of data movement

Accounts for 19.1% of the total system energy during scrolling

Color blitting is a good candidate for PIM execution

Requires low-cost operations:
Memset, simple arithmetic, and shift operations

It is feasible to implement color blitting in PIM core and PIM accelerator

Scrolling Wrap Up

Texture tiling and **color blitting** account for a significant portion (41.9%) of energy consumption

↓

37.7% of total system energy goes to data movement generated by these functions

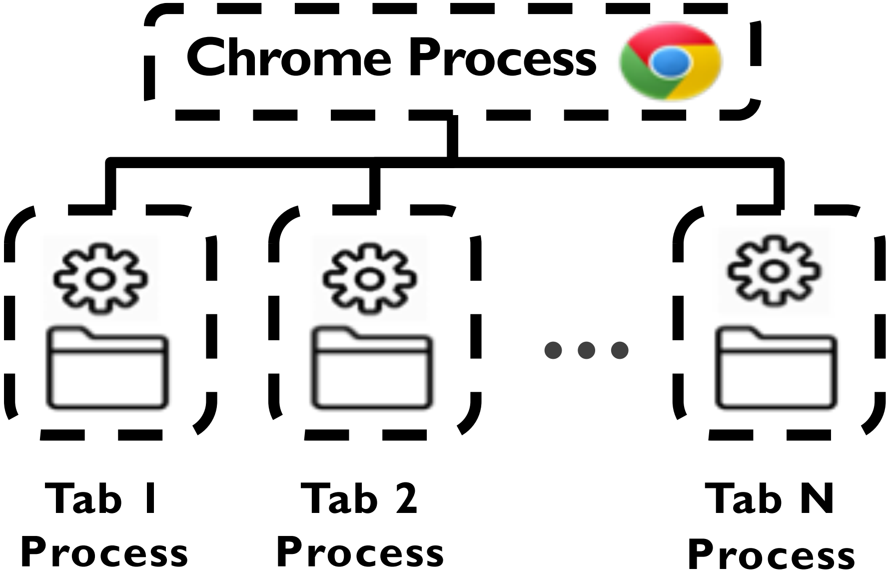
1 Both functions can benefit significantly from PIM execution

2 Both functions are feasible to implement as PIM logic

Tab Switching

What Happens During Tab Switching?

- **Chrome employs a multi-process architecture**
  - Each tab is a separate process

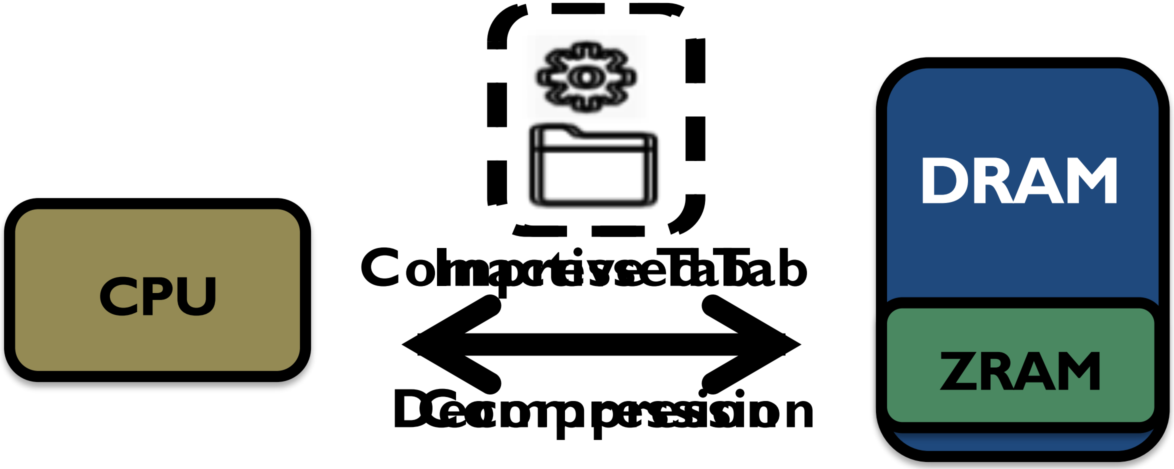


- **Main operations during tab switching:**
  - Context switch
  - Load the new page

Memory Consumption

- **Primary concerns during tab switching:**
  - How fast a new tab **loads** and **becomes interactive**
  - **Memory consumption**

Chrome uses compression to reduce each tab's memory footprint



Data Movement Study

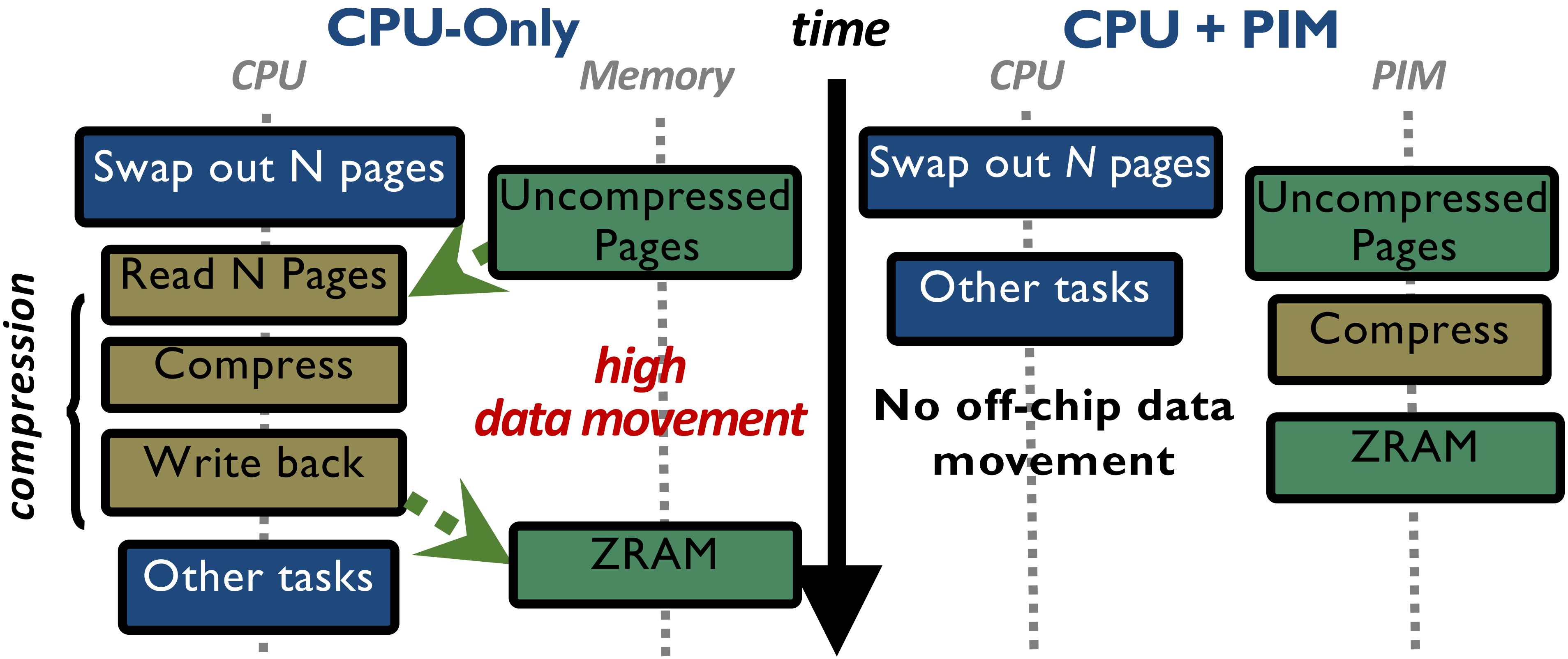
- To study data movement during tab switching, we emulate a user switching through 50 tabs

We make two key observations:

1 Compression and decompression contribute to 18.1% of the total system energy

2 19.6 GB of data moves between CPU and ZRAM

Can We Use PIM to Mitigate the Cost?



PIM core and PIM accelerator are feasible to implement in-memory compression/decompression

Tab Switching Wrap Up

A large amount of data movement happens during tab switching as Chrome attempts to compress and decompress tabs

Both functions can benefit from PIM execution and can be implemented as PIM logic

Workload Analysis

Chrome

Google's web browser

TensorFlow

Google's machine learning framework

Video Playback

Google's video codec

Video Capture

Google's video codec

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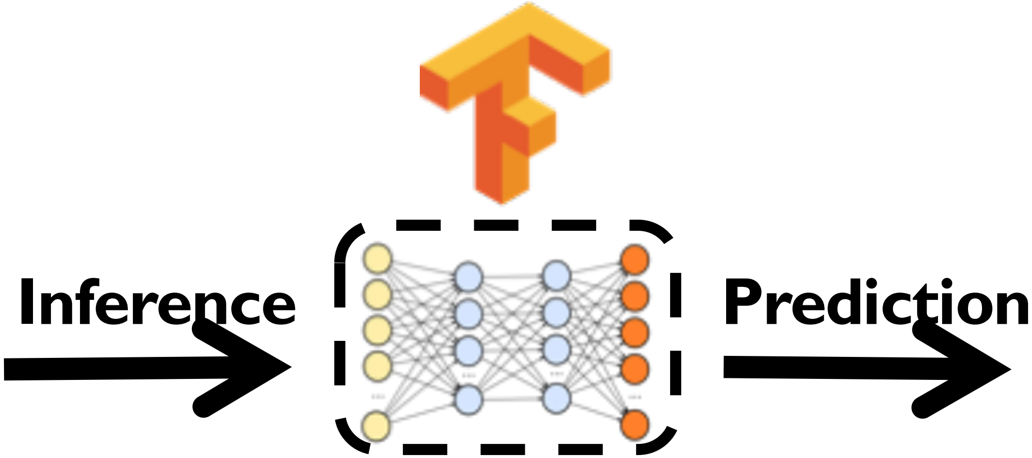
Google's video codec

TensorFlow Mobile


Inference

Prediction

57.3% of the inference energy is spent on data movement

↓

54.4% of the data movement energy comes from packing/unpacking and quantization

Packing

Reorders elements of matrices to minimize **cache misses** during **matrix multiplication**

Up to **40%** of the inference **energy** and **31%** of inference **execution time**

Packing's data movement accounts for up to **35.3%** of the inference **energy**

A simple data reorganization process that requires simple arithmetic

Quantization

Converts <u>32-bit floating point</u> to <u>8-bit integers</u> to improve inference <u>execution time</u> and <u>energy consumption</u>

Up to 16.8% of the inference energy and 16.1% of inference execution time

Majority of quantization energy comes from data movement

A simple data conversion operation that requires shift, addition, and multiplication operations

Quantization

Converts 32-bit floating point to 8-bit integers to improve inference execution time and energy consumption

Based on our analysis, we conclude that:

- Both functions are good candidates for PIM execution
- It is feasible to implement them in PIM logic

inference execution time

A simple data conversion operation that requires shift, addition, and multiplication operations

Video Playback and Capture

VP9

Compressed video

VP9 Decoder

Display

Captured video

VP9 Encoder

Compressed video

Majority of energy is spent on data movement

Majority of data movement comes from simple functions in decoding and encoding pipelines

Outline

- Introduction
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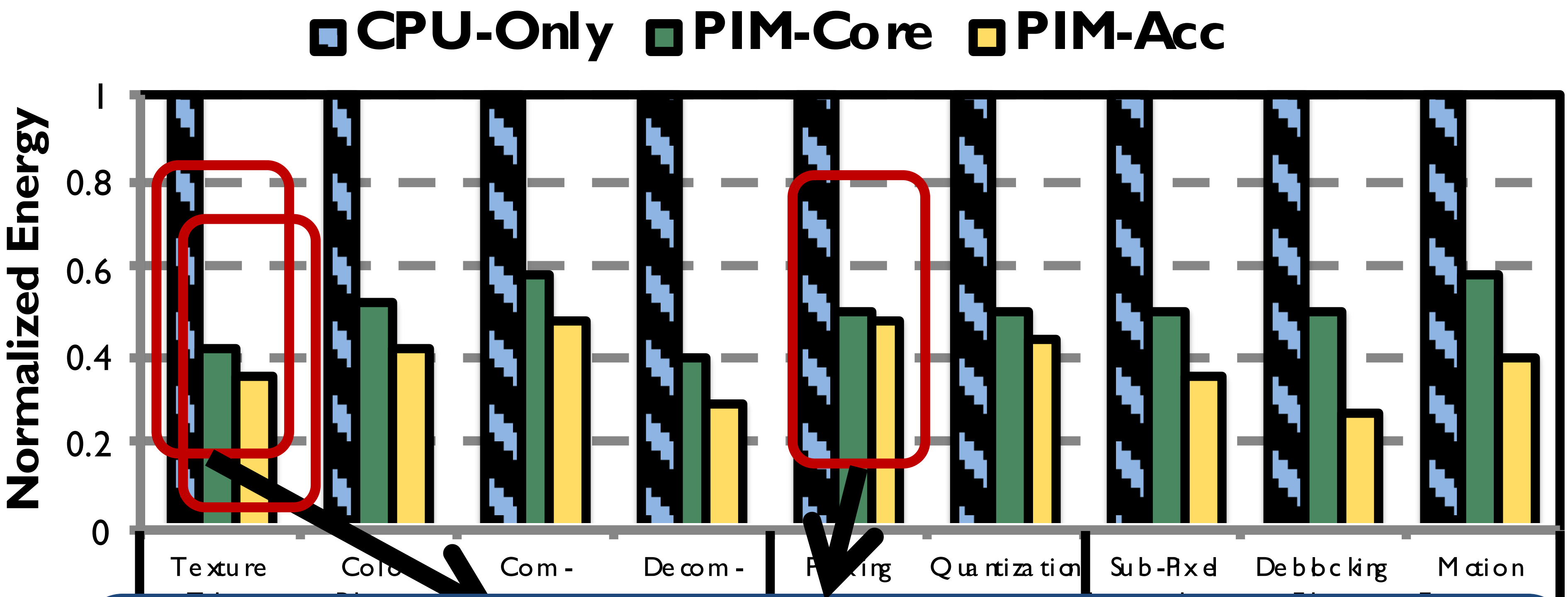
Evaluation Methodology

- **System Configuration (gem5 Simulator)**
  - **SoC:** 4 OoO cores, 8-wide issue, 64 kB L1cache, 2MB L2 cache
  - **PIM Core:** 1 core per vault, 1-wide issue, 4-wide SIMD, 32kB L1 cache
  - **3D-Stacked Memory:** 2GB cube, 16 vaults per cube
    - Internal Bandwidth: 256GB/S
    - Off-Chip Channel Bandwidth: 32 GB/s
  - **Baseline Memory:** LPDDR3, 2GB, FR-FCFS scheduler
- **We study each target in isolation and emulate each separately and run them in our simulator**

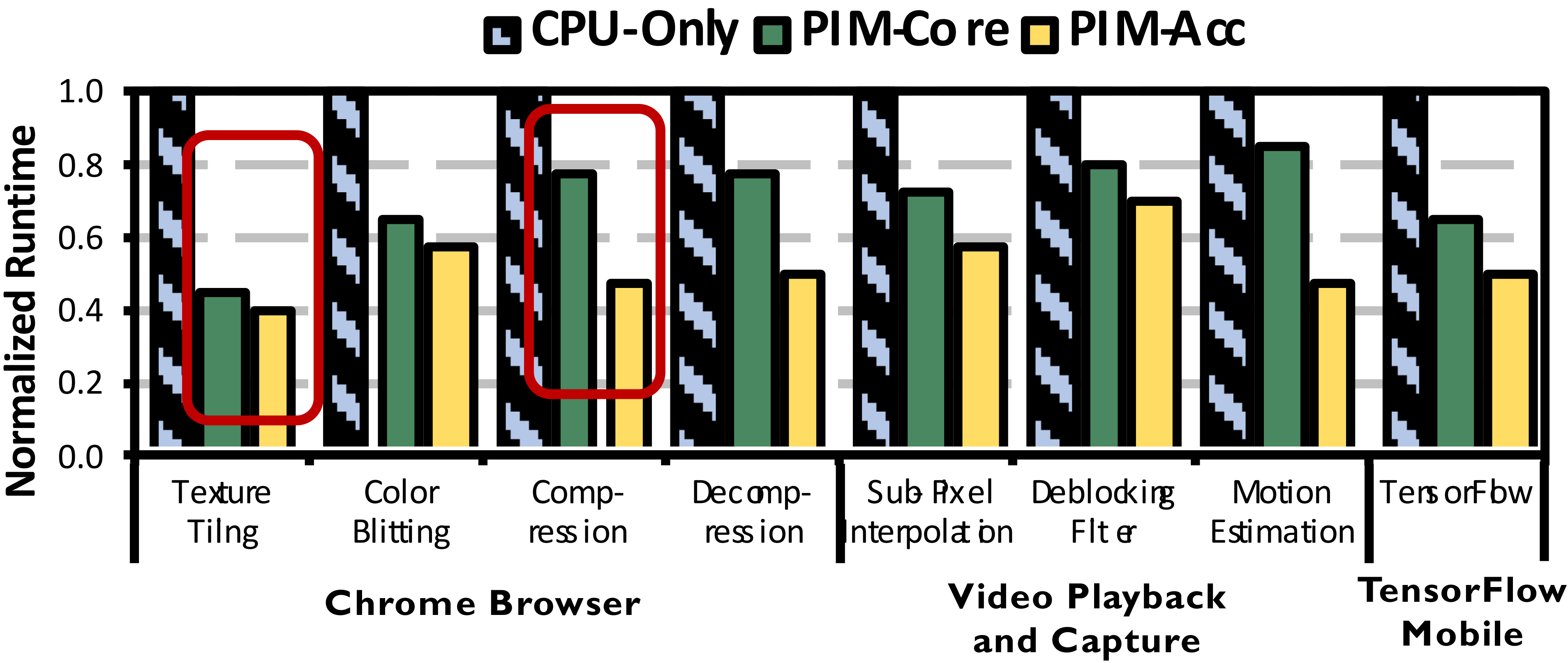
Normalized Energy



77.7% and **82.6%** of energy reduction for **texture tiling** and **packing** comes from eliminating **data movement**

PIM core and **PIM accelerator** reduces <u>energy consumption</u> on average by **49.1%** and **55.4%**

Normalized Runtime



Offloading these kernels to PIM core and PIM accelerator improves performance on average by 44.6% and 54.2%

Conclusion

- Energy consumption is a **major challenge** in consumer devices
- We conduct an in-depth analysis of popular **Google consumer workloads**
  - **62.7%** of the total system energy is spent on **data movement**
  - Most of the **data movement** comes from simple functions that consist of simple operations
- We use **PIM** to reduce **data movement cost**
  - We design **lightweight logic** to implement **simple operations** in DRAM

  - Reduces **total energy** by **55.4%** on average
  - Reduces **execution time** by **54.2%** on average

Google Workloads for Consumer Devices: Mitigating Data Movement Bottlenecks

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End of Backup Slides